

Handbook on the Physics and Chemistry of Rare Earths, volume 27

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PREFACE

Karl A. GSCHNEIDNER, Jr., and LeRoy EYRING

These elements perplex us in our rearches [sic], baffle us in our speculations, and haunt us in our very dreams. They stretch like an unknown sea before us – mocking, mystifying, and murmuring strange revelations and possibilities.

Sir William Crookes (February 16, 1887)

This volume of the *Handbook* is the last volume to be published with a 19xx imprint and contains three chapters which deal with rare earth alloys and intermetallic compounds.

Chapter 173 is by P.S. Salamakha, O.L. Sologub and O.I. Bodak and deals with ternary rare-earth–germanium alloys – their phase diagrams and the crystal structures of the intermediate phases. The largest number of intermetallic phases are found in the Group-VIII metals, i.e. iron, cobalt and nickel and their congeners ruthenium, rhodium and palladium. Although there is a paucity of data for the congeners in the third row of transition metals, the little information available indicates that osmium, iridium and platinum will also form as many intermetallic compounds. Of the group-VIII metals the first member of each row (iron, ruthenium and osmium) forms only about half (10) the number of compounds as the other two members, cobalt and nickel and their congeners.

Another interesting observation is that the ternary alloy systems of the rare earths and germanium with the s and p elements have hardly been investigated. And of those that have been studied, only a few intermediate phases have been observed in the ternary systems. The chapter ends with a discussion of the general trends and unusual features observed in the various sets of ternary phase diagrams.

In a companion chapter (174) P.S. Salamakha describes in detail the various structure types that have been adopted by the rare-earth–germanium ternary intermetallic compounds. The correlations, crystal chemistry and interrelationships of the 135 structure types are discussed. Two distinct behaviors are found depending on the nature of the outer bonding electrons: the p elements behave differently from the s and d elements, which behave similarly. When the third component is a p element the compounds maintain the same R to Ge ratio as found in the binary R_xGe_y phases, e.g. RGe_2 and R_3Ge_5 , where R is a rare earth metal. As one might expect many of the compounds have variable composition at a constant R content. For the s and d metals the compounds tend to fall on lines

connecting the three elements with binary phases of simple compositions, such as the R-MGe, M-RGe₂, Ge-RM lines, where M is an element other than R or Ge. The line connecting the RM_2 -RGe₂ binary phases also has several phases lying on it, including RMGe. The equiatomic composition RMGe has 20 known structure types.

Quaternary compounds and superstructures are also reviewed by Salamakha.

The last chapter (175) deals with scandium alloys and intermetallic compounds – binary, ternary and higher order systems. In their review B.Ya. Kotur and E. Gratz summarize the various phase diagrams of scandium systems and present the crystal structure properties of the various intermediate phases. The general trends observed in the phase relationships and crystal chemistry of these materials are discussed, and may be useful in finding new scandium phases. In the last section of their chapter Kotur and Gratz present physical property data on scandium intermetallic phases. The results are divided into three groups – compounds which have (1) a magnetic ground state, (2) a superconducting ground state and (3) those with neither a magnetic or a superconducting ground state.

CONTENTS

Preface v
Contents vii
Contents of Volumes 1–26 ix
173. P.S. Salamakha, O.L. Sologub and O.I. Bodak Ternary rare-earth-germanium systems 1
174. Petro S. Salamakha Crystal structures and crystal chemistry of ternary rare-earth germanides 225
175. Bogdan Ya. Kotur and Ernst Gratz Scandium alloy systems and intermetallics 339
Author index 535

Subject index 553

CONTENTS OF VOLUMES 1–26

VOLUME 1: Metals

1978, 1st repr. 1982, 2nd repr. 1991; ISBN 0-444-85020-1

- 1. Z.B. Goldschmidt, Atomic properties (free atom) 1
- 2. B.J. Beaudry and K.A. Gschneidner Jr, Preparation and basic properties of the rare earth metals 173
- 3. S.H. Liu, Electronic structure of rare earth metals 233
- 4. D.C. Koskenmaki and K.A. Gschneidner Jr, Cerium 337
- 5. L.J. Sundström, Low temperature heat capacity of the rare earth metals 379
- 6. K.A. McEwen, Magnetic and transport properties of the rare earths 411
- 7. S.K. Sinha, Magnetic structures and inelastic neutron scattering: metals, alloys and compounds 489
- 8. T.E. Scott, Elastic and mechanical properties 591
- 9. A. Jayaraman, High pressure studies: metals, alloys and compounds 707
- 10. C. Probst and J. Wittig, Superconductivity: metals, alloys and compounds 749
- 11. M.B. Maple, L.E. DeLong and B.C. Sales, Kondo effect: alloys and compounds 797
- 12. M.P. Dariel, *Diffusion in rare earth metals* 847 Subject index 877

VOLUME 2: Alloys and intermetallics

1979, 1st repr. 1982, 2nd repr. 1991; ISBN 0-444-85021-X

- 13. A. Iandelli and A. Palenzona, Crystal chemistry of intermetallic compounds 1
- 14. H.R. Kirchmayr and C.A. Poldy, Magnetic properties of intermetallic compounds of rare earth metals 55
- 15. A.E. Clark, Magnetostrictive RFe2 intermetallic compounds 231
- 16. J.J. Rhyne, Amorphous magnetic rare earth alloys 259
- 17. P. Fulde, Crystal fields 295
- 18. R.G. Barnes, NMR, EPR and Mössbauer effect: metals, alloys and compounds 387
- 19. P. Wachter, Europium chalcogenides: EuO, EuS, EuSe and EuTe 507
- A. Jayaraman, Valence changes in compounds 575 Subject index 613

VOLUME 3: Non-metallic compounds – I

1979, 1st repr. 1984; ISBN 0-444-85215-8

- 21. L.A. Haskin and T.P. Paster, Geochemistry and mineralogy of the rare earths 1
- 22. J.E. Powell, Separation chemistry 81
- 23. C.K. Jørgensen, Theoretical chemistry of rare earths 111
- 24. W.T. Carnall, The absorption and fluorescence spectra of rare earth ions in solution 171
- 25. L.C. Thompson, Complexes 209
- 26. G.G. Libowitz and A.J. Maeland, Hydrides 299
- 27. L. Eyring, The binary rare earth oxides 337
- 28. D.J.M. Bevan and E. Summerville, Mixed rare earth oxides 401
- 29. C.P. Khattak and F.F.Y. Wang, Perovskites and garnets 525
- L.H. Brixner, J.R. Barkley and W. Jeitschko, *Rare earth molybdates (VI)* 609 Subject index 655

VOLUME 4: Non-metallic compounds – II

1979, 1st repr. 1984; ISBN 0-444-85216-6

- 31. J. Flahaut, Sulfides, selenides and tellurides 1
- 32. J.M. Haschke, Halides 89
- 33. F. Hulliger, Rare earth pnictides 153
- 34. G. Blasse, Chemistry and physics of R-activated phosphors 237
- 35. M.J. Weber, Rare earth lasers 275
- 36. F.K. Fong, Nonradiative processes of rare-earth ions in crystals 317
- 37A. J.W. O'Laughlin, Chemical spectrophotometric and polarographic methods 341
- 37B. S.R. Taylor, Trace element analysis of rare earth elements by spark source mass spectroscopy 359
- 37C. R.J. Conzemius, Analysis of rare earth matrices by spark source mass spectrometry 377
- 37D. E.L. DeKalb and V.A. Fassel, Optical atomic emission and absorption methods 405
- 37E. A.P. D'Silva and V.A. Fassel, X-ray excited optical luminescence of the rare earths 441
- 37F. F.W.V. Boynton, Neutron activation analysis 457
- 37G. S. Schuhmann and J.A. Philpotts, Mass-spectrometric stable-isotope dilution analysis for lanthanides in geochemical materials 471
- 38. J. Reuben and G.A. Elgavish, Shift reagents and NMR of paramagnetic lanthanide complexes 483
- 39. J. Reuben, Bioinorganic chemistry: lanthanides as probes in systems of biological interest 515
- 40. T.J. Haley, *Toxicity* 553 Subject index 587

VOLUME 5

1982, 1st repr. 1984; ISBN 0-444-86375-3

- 41. M. Gasgnier, Rare earth alloys and compounds as thin films 1
- 42. E. Gratz and M.J. Zuckermann, Transport properties (electrical resitivity, thermoelectric power and thermal conductivity) of rare earth intermetallic compounds 117
- 43. F.P. Netzer and E. Bertel, Adsorption and catalysis on rare earth surfaces 217
- 44. C. Boulesteix, Defects and phase transformation near room temperature in rare earth sesquioxides 321
- 45. O. Greis and J.M. Haschke, Rare earth fluorides 387
- 46. C.A. Morrison and R.P. Leavitt, Spectroscopic properties of triply ionized lanthanides in transparent host crystals 461

Subject index 693

VOLUME 6

1984; ISBN 0-444-86592-6

- 47. K.H.J. Buschow, Hydrogen absorption in intermetallic compounds 1
- 48. E. Parthé and B. Chabot, Crystal structures and crystal chemistry of ternary rare earth-transition metal borides, silicides and homologues 113
- 49. P. Rogl, Phase equilibria in ternary and higher order systems with rare earth elements and boron 335
- H.B. Kagan and J.L. Namy, Preparation of divalent ytterbium and samarium derivatives and their use in organic chemistry 525 Subject index 567

VOLUME 7

1984; ISBN 0-444-86851-8

- 51. P. Rogl, Phase equilibria in ternary and higher order systems with rare earth elements and silicon 1
- 52. K.H.J. Buschow, Amorphous alloys 265
- H. Schumann and W. Genthe, Organometallic compounds of the rare earths 446 Subject index 573

CONTENTS OF VOLUMES 1-26

VOLUME 8

1986; ISBN 0-444-86971-9

- 54. K.A. Gschneidner Jr and F.W. Calderwood, Intra rare earth binary alloys: phase relationships, lattice parameters and systematics 1
- 55. X. Gao, Polarographic analysis of the rare earths 163
- 56. M. Leskelä and L. Niinistö, Inorganic complex compounds I 203
- 57. J.R. Long, Implications in organic synthesis 335
 Errata 375
 Subject index 379

VOLUME 9

1987; ISBN 0-444-87045-8

- 58. R. Reisfeld and C.K. Jørgensen, Excited state phenomena in vitreous materials 1
- 59. L. Niinistö and M. Leskelä, Inorganic complex compounds II 91
- 60. J.-C.G. Bünzli, Complexes with synthetic ionophores 321
- Zhiquan Shen and Jun Ouyang, Rare earth coordination catalysis in stereospecific polymerization 395 Errata 429 Subject index 431

VOLUME 10: High energy spectroscopy

1988; ISBN 0-444-87063-6

- 62. Y. Baer and W.-D. Schneider, High-energy spectroscopy of lanthanide materials An overview 1
- 63. M. Campagna and F.U. Hillebrecht, *f-electron hybridization and dynamical screening of core holes in intermetallic compounds* 75
- 64. O. Gunnarsson and K. Schönhammer, Many-body formulation of spectra of mixed valence systems 103
- 65. A.J. Freeman, B.I. Min and M.R. Norman, Local density supercell theory of photoemission and inverse photoemission spectra 165
- 66. D.W. Lynch and J.H. Weaver, Photoemission of Ce and its compounds 231
- 67. S. Hüfner, Photoemission in chalcogenides 301
- 68. J.F. Herbst and J.W. Wilkins, Calculation of 4f excitation energies in the metals and relevance to mixed valence systems 321
- 69. B. Johansson and N. Mårtensson, Thermodynamic aspects of 4f levels in metals and compounds 361
- 70. F.U. Hillebrecht and M. Campagna, Bremsstrahlung isochromat spectroscopy of alloys and mixed valent compounds 425
- 71. J. Röhler, X-ray absorption and emission spectra 453
- 72. F.P. Netzer and J.A.D. Matthew, *Inelastic electron scattering measurements* 547 Subject index 601

VOLUME 11: Two-hundred-year impact of rare earths on science

1988; ISBN 0-444-87080-6

H.J. Svec, Prologue 1

- 73. F. Szabadváry, The history of the discovery and separation of the rare earths 33
- 74. B.R. Judd, Atomic theory and optical spectroscopy 81
- 75. C.K. Jørgensen, Influence of rare earths on chemical understanding and classification 197
- 76. J.J. Rhyne, Highlights from the exotic phenomena of lanthanide magnetism 293
- 77. B. Bleaney, Magnetic resonance spectroscopy and hyperfine interactions 323
- 78. K.A. Gschneidner Jr and A.H. Daane, Physical metallurgy 409
- 79. S.R. Taylor and S.M. McLennan, The significance of the rare earths in geochemistry and cosmochemistry 485 Errata 579 Subject index 581

CONTENTS OF VOLUMES 1-26

VOLUME 12

1989; ISBN 0-444-87105-5

- 80. J.S. Abell, Preparation and crystal growth of rare earth elements and intermetallic compounds 1
- 81. Z. Fisk and J.P. Remeika, Growth of single crystals from molten metal fluxes 53
- 82. E. Burzo and H.R. Kirchmayr, *Physical properties of* $R_2Fe_{14}B$ -based alloys 71
- 83. A. Szytuła and J. Leciejewicz, Magnetic properties of ternary intermetallic compounds of the RT_2X_2 type 133
- 84. H. Maletta and W. Zinn, Spin glasses 213
- 85. J. van Zytveld, Liquid metals and alloys 357
- 86. M.S. Chandrasekharaiah and K.A. Gingerich, Thermodynamic properties of gaseous species 409
- 87. W.M. Yen, *Laser spectroscopy* 433 Subject index 479

VOLUME 13

1990; ISBN 0-444-88547-1

- 88. E.I. Gladyshevsky, O.I. Bodak and V.K. Pecharsky, *Phase equilibria and crystal chemistry in ternary rare* earth systems with metallic elements 1
- 89. A.A. Eliseev and G.M. Kuzmichyeva, *Phase equilibrium and crystal chemistry in ternary rare earth systems with chalcogenide elements* 191
- 90. N. Kimizuka, E. Takayama-Muromachi and K. Siratori, The systems R₂O₃-M₂O₃-MO 283
- 91. R.S. Houk, Elemental analysis by atomic emission and mass spectrometry with inductively coupled plasmas 385
- P.H. Brown, A.H. Rathjen, R.D. Graham and D.E. Tribe, *Rare earth elements in biological systems* 423 Errata 453 Subject index 455

VOLUME 14

1991; ISBN 0-444-88743-1

- 93. R. Osborn, S.W. Lovesey, A.D. Taylor and E. Balcar, Intermultiplet transitions using neutron spectroscopy 1
- 94. E. Dormann, NMR in intermetallic compounds 63
- 95. E. Zirngiebl and G. Güntherodt, Light scattering in intermetallic compounds 163
- 96. P. Thalmeier and B. Lüthi, The electron-phonon interaction in intermetallic compounds 225
- 97. N. Grewe and F. Steglich, *Heavy fermions* 343 Subject index 475

VOLUME 15

1991; ISBN 0-444-88966-3

- 98. J.G. Sereni, Low-temperature behaviour of cerium compounds 1
- 99. G.-y. Adachi, N. Imanaka and Zhang Fuzhong, Rare earth carbides 61
- 100. A. Simon, Hj. Mattausch, G.J. Miller, W. Bauhofer and R.K. Kremer, Metal-rich halides 191
- 101. R.M. Almeida, Fluoride glasses 287
- K.L. Nash and J.C. Sullivan, Kinetics of complexation and redox reactions of the lanthanides in aqueous solutions 347
- 103. E.N. Rizkalla and G.R. Choppin, Hydration and hydrolysis of lanthanides 393
- 104. L.M. Vallarino, Macrocycle complexes of the lanthanide(III) yttrium(III) and dioxouranium(VI) ions from metal-templated syntheses 443
 Errata 513
 Subject index 515

CONTENTS OF VOLUMES 1-26

MASTER INDEX, Vols. 1–15

1993; ISBN 0-444-89965-0

VOLUME 16

1993; ISBN 0-444-89782-8

- 105. M. Loewenhaupt and K.H. Fischer, Valence-fluctuation and heavy-fermion 4f systems 1
- 106. I.A. Smirnov and V.S. Oskotski, Thermal conductivity of rare earth compounds 107
- 107. M.A. Subramanian and A.W. Sleight, Rare earths pyrochlores 225
- 108. R. Miyawaki and I. Nakai, Crystal structures of rare earth minerals 249
- 109. D.R. Chopra, Appearance potential spectroscopy of lanthanides and their intermetallics 519 Author index 547 Subject index 579

VOLUME 17: Lanthanides/Actinides: Physics - I

1993; ISBN 0-444-81502-3

- M.R. Norman and D.D. Koelling, Electronic structure, Fermi surfaces, and superconductivity in f electron metals 1
- 111. S.H. Liu, Phenomenological approach to heavy-fermion systems 87
- 112. B. Johansson and M.S.S. Brooks, Theory of cohesion in rare earths and actinides 149
- 113. U. Benedict and W.B. Holzapfel, High-pressure studies Structural aspects 245
- 114. O. Vogt and K. Mattenberger, Magnetic measurements on rare earth and actinide monophictides and monochalcogenides 301
- 115. J.M. Fournier and E. Gratz, Transport properties of rare earth and actinide intermetallics 409
- 116. W. Potzel, G.M. Kalvius and J. Gal, Mössbauer studies on electronic structure of intermetallic compounds 539
- 117. G.H. Lander, Neutron elastic scattering from actinides and anomalous lanthanides 635 Author index 711 Subject index 753

VOLUME 18: Lanthanides/Actinides: Chemistry

1994; ISBN 0-444-81724-7

- 118. G.T. Seaborg, Origin of the actinide concept 1
- K. Balasubramanian, Relativistic effects and electronic structure of lanthanide and actinide molecules 29
- J.V. Beitz, Similarities and differences in trivalent lanthanide- and actinide-ion solution absorption spectra and luminescence studies 159
- 121. K.L. Nash, Separation chemistry for lanthanides and trivalent actinides 197
- 122. L.R. Morss, Comparative thermochemical and oxidation-reduction properties of lanthanides and actinides 239
- 123. J.W. Ward and J.M. Haschke, Comparison of 4f and 5f element hydride properties 293
- 124. H.A. Eick, Lanthanide and actinide halides 365
- 125. R.G. Haire and L. Eyring, Comparisons of the binary oxides 413
- 126. S.A. Kinkead, K.D. Abney and T.A. O'Donnell, *f-element speciation in strongly acidic media: lanthanide and mid-actinide metals, oxides, fluorides and oxide fluorides in superacids* 507
- 127. E.N. Rizkalla and G.R. Choppin, Lanthanides and actinides hydration and hydrolysis 529
- 128. G.R. Choppin and E.N. Rizkalla, Solution chemistry of actinides and lanthanides 559
- 129. J.R. Duffield, D.M. Taylor and D.R. Williams, *The biochemistry of the f-elements* 591
 Author index 623
 Subject index 659

VOLUME 19: Lanthanides/Actinides: Physics – II

1994; ISBN 0-444-82015-9

- 130. E. Holland-Moritz and G.H. Lander, Neutron inelastic scattering from actinides and anomalous lanthanides 1
- G. Aeppli and C. Broholm, Magnetic correlations in heavy-fermion systems: neutron scattering from single crystals 123
- 132. P. Wachter, Intermediate valence and heavy fermions 177
- J.D. Thompson and J.M. Lawrence, High pressure studies Physical properties of anomalous Ce, Yb and U compounds 383
- 134. C. Colinet and A. Pasturel, *Thermodynamic properties of metallic systems* 479
 Author index 649
 Subject index 693

VOLUME 20

1995; ISBN 0-444-82014-0

- 135. Y. Onuki and A. Hasegawa, Fermi surfaces of intermetallic compounds
- 136. M. Gasgnier, The intricate world of rare earth thin films: metals, alloys, intermetallics, chemical compounds, ... 105
- 137. P. Vajda, Hydrogen in rare-earth metals, including RH_{2+x} phases 207
- D. Gignoux and D. Schmitt, Magnetic properties of intermetallic compounds 293 Author index 425 Subject index 457

VOLUME 21

1995; ISBN 0-444-82178-3

- 139. R.G. Bautista, Separation chemistry 1
- 140. B.W. Hinton, Corrosion prevention and control 29
- 141. N.E. Ryan, High-temperature corrosion protection 93
- 142. T. Sakai, M. Matsuoka and C. Iwakura, Rare earth intermetallics for metal-hydrogen batteries 133
- 143. G.-y. Adachi and N. Imanaka, Chemical sensors 179
- 144. D. Garcia and M. Faucher, Crystal field in non-metallic (rare earth) compounds 263
- 145. J.-C.G. Bünzli and A. Milicic-Tang, Solvation and anion interaction in organic solvents 305
- 146. V. Bhagavathy, T. Prasada Rao and A.D. Damodaran, *Trace determination of lanthanides in high-purity rare-earth oxides* 367
 Author index 385
 Subject index 411

VOLUME 22

1996; ISBN 0-444-82288-7

- 147. C.P. Flynn and M.B. Salamon, Synthesis and properties of single-crystal nanostructures 1
- Z.S. Shan and D.J. Sellmyer, Nanoscale rare earth-transition metal multilayers: magnetic structure and properties 81
- W. Suski, The ThMn₁₂-type compounds of rare earths and actinides: structure, magnetic and related properties 143
- 150. L.K. Aminov, B.Z. Malkin and M.A. Teplov, Magnetic properties of nonmetallic lanthanide compounds 295
- 151. F. Auzel, Coherent emission in rare-earth materials 507
- M. Dolg and H. Stoll, *Electronic structure calculations for molecules containing lanthanide atoms* 607 Author index 731 Subject index 777

1996; ISBN 0-444-82507-X

- J.H. Forsberg, NMR studies of paramagnetic lanthanide complexes and shift reagents 153.
- N. Sabbatini, M. Guardigli and I. Manet, Antenna effect in encapsulation complexes of lanthanide 154. ions 69
- 155. C. Görller-Walrand and K. Binnemans, Rationalization of crystal-field parametrization 121
- 156. Yu. Kuz'ma and S. Chykhrij, Phosphides 285
- S. Boghosian and G.N. Papatheodorou, Halide vapors and vapor complexes 157. 435
- R.H. Byrne and E.R. Sholkovitz, Marine chemistry and geochemistry of the lanthanides 497 158. Author index 595
 - Subject index 631

VOLUME 24

1997; ISBN 0-444-82607-6

- 159. P.A. Dowben, D.N. McIlroy and Dongqi Li, Surface magnetism of the lanthanides 1
- 160. P.G. McCormick, Mechanical alloying and mechanically induced chemical reactions 47
- 161. A. Inoue, Amorphous, quasicrystalline and nanocrystalline alloys in Al- and Mg-based systems 83
- 162. B. Elschner and A. Loidl, Electron-spin resonance on localized magnetic moments in metals 221
- N.H. Duc, Intersublattice exchange coupling in the lanthanide-transition metal intermetallics 163. 339
- 164. R.V. Skolozdra, Stannides of rare-earth and transition metals 399 Author index 519 Subject index 559

VOLUME 25

1998; ISBN 0-444-82871-0

- H. Nagai, Rare earths in steels 165. 1
- R. Matchand, Ternary and higher order nitride materials 166. 51
- 167. C. Görller-Walrand and K. Binnemans, Spectral intensities of f-f transitions 101
- 168. G. Bombieri and G. Paolucci, Organometallic π complexes of the f-elements 265 Author Index 415 Subject Index 459

VOLUME 26

1999; ISBN 0-444-50815-1

- 169. D.F. McMorrow, D. Gibbs and J. Bohr, X-ray scattering studies of lanthanide magnetism 1
- 170. A.M. Tishin, Yu.I. Spichkin and J. Bohr, Static and dynamic stresses 87
- 171. N.H. Duc and T. Goto, Itinerant electron metamagnetism of Co sublattice in the lanthanide-cobalt intermetallics 177
- 172. A.J. Arko, P.S. Riseborough, A.B. Andrews, J.J. Joyce, A.N. Tahvildar-Zadeh and M. Jarrell, Photoelectron spectroscopy in heavy fermion systems: Emphasis on single crystals 265 Author index 383 405

Subject index

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Chapter 173

TERNARY RARE-EARTH-GERMANIUM SYSTEMS

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Contents

Symbols and abbreviations	5	3.2.2. Y-Al-Ge	23
1. Introduction	5	3.2.3. La-Al-Ge	24
2. Rare-earth-s element-germanium systems	8	3.2.4. Ce-Al-Ge	25
2.1. R-Li-Ge systems	8	3.2.5. Pr-Al-Ge	26
2.1.1. Sc-Li-Ge	8	3.2.6. Nd-Al-Ge	26
2.1.2. Y-Li-Ge	9	3.2.7. Sm-Al-Ge	27
2.1.3. La-Li-Ge	9	3.2.8. Eu–Al–Ge	27
2.1.4. Ce-Li-Ge	9	3.2.9. Gd–Al–Ge	28
2.1.5. PrLiGe	11	3.2.10. Tb-Al-Ge	29
2.1.6. Nd-Li-Ge	12	3.2.11. Dy-Al-Ge	29
2.1.7. Sm-Li-Ge	13	3.2.12. Ho-Al-Ge	30
2.1.8. Eu–Li–Ge	14	3.2.13. Er-Al-Ge	30
2.1.9. Gd-Li-Ge	14	3.2.14. Tm-Al-Ge	31
2.1.10. Tb-Li-Ge	15	3.2.15. Yb-Al-Ge	31
2.1.11. Dy-Li-Ge	15	3.2.16. Lu-Al-Ge	32
2.1.12. Ho-Li-Ge	15	3.3. R-Ga-Ge systems	32
2.1.13. Er-Li-Ge	16	3.3.1. Y-Ga-Ge	32
2.1.14. Tm-Li-Ge	17	3.3.2. Ce-Ga-Ge	32
2.1.15. Yb-Li-Ge	18	3.3.3. Nd-Ga-Ge	32
2.1.16. Lu-Li-Ge	19	3.3.4. GdGa-Ge	33
2.2. R-Mg-Ge systems	20	3.3.5. Tm–Ga–Ge	33
2.2.1. Eu-Mg-Ge	20	3.4. R-In-Ge systems	33
2.2.2. Yb-Mg-Ge	20	3.5. R–C–Ge systems	34
3. Rare-earth-p element-germanium systems	20	3.6. R-Si-Ge systems	34
3.1. R-B-Ge systems	20	3.6.1. Y-Si-Ge	34
3.1.1. Y-B-Ge	20	3.6.2. La-Si-Ge	35
3.1.2. La-B-Ge	20	3.6.3. Ce-Si-Ge	36
3.1.3. Ce-B-Ge	21	3.6.4. Pr–Si–Ge	37
3.1.4. Nd–B–Ge	22	3.6.5. Gd-Si-Ge	38
3.1.5. Gd-B-Ge	22	4. R-d element-germanium systems	39
3.1.6. Tb-B-Ge	22	4.1. Sc-d element-Ge systems	39
3.1.7. Dy–B–Ge	22	4.1.1. ScV-Ge	39
3.2. R-Al-Ge systems	23	4.1.2. Sc-Cr-Ge	40
3.2.1. Sc–Al–Ge	23	4.1.3. ScMnGe	41

4.1.4. Sc–Fe–Ge	42
4.1.5. Sc-Co-Ge	43
4.1.6. Sc–Ni–Ge	44
4.1.7. ScCuGe	45
4.1.8. ScNbGe	46
4.1.9. Sc-Mo-Ge	46
4.1.10. Sc-Ru-Ge	47
4.1.11. Sc-Rh-Ge	47
4.1.12. Sc-Pd-Ge	48
4.1.13. Sc-Ag-Ge	48
4.1.14. Sc-Hf-Ge	49
4.1.15. Sc-Ta-Ge	49
4.1.16. Sc-W-Ge	50
4.1.17. Sc-Re-Ge	50
4.1.18. Sc-Os-Ge	51
4.1.19. Sc–Ir–Ge	51
4.1.20. Sc-Pt-Ge	51
4.1.21. Sc-Au-Ge	52
4.2. Y-d element-Ge systems	52
4.2.1. Y-Cr-Ge	52
4.2.2. YMn-Ge	53
4.2.3. Y-Fe-Ge	53
4.2.4. YCo-Ge	53
4.2.5. Y-Ni-Ge	54
4.2.6. Y-Cu-Ge	56
4.2.7. Y-Nb-Ge	56
4.2.8. Y-Mo-Ge	56
4.2.9. Y-Ru(Rh, Pd)-Ge	57
4.2.10. Y-Ag-Ge	58
4.2.11. Y-Os(Ir, Pt)-Ge	58
4.2.12. Y-Au-Ge	58
4.3. La-d element-Ge systems	59
4.3.1. La-Mn-Ge	59
4.3.2. La-Fe-Ge	59
4.3.3. La-Co-Ge	59
4.3.4. La-Ni-Ge	60
4.3.5. La-Cu-Ge	61
4.3.6. La–Zn–Ge	61
4.3.7. La-Ru-Ge	62
4.3.8. La-Rh-Ge	62
4.3.9. La-PdGe	63
4.3.10. La-Ag-Ge	63
4.3.11, La-Os-Ge	64
4.3.12. La-Ir-Ge	64
4.3.13. La-Pt-Ge	65
4.3.14. La-Au-Ge	65
4.4. Ce-d element-Ge systems	65
4.4.1. Ce-Mn-Ge	65
4.4.2. Ce-Fe-Ge	66
4.4.3. Ce-Co-Ge	67
4.4.4. Ce-Ni-Ge	69

4.4.5. Ce–Cu–Ge	69
4.4.6. Ce–Zn–Ge	71
4.4.7. CeRuGe	72
4.4.8. Ce-Rh-Ge	74
4.4.9. Ce-Pd-Ge	75
4.4.10. Ce–Ag–Ge	77
4.4.11. CeOsGe	78
4.4.12. Ce–Ir–Ge	78
4.4.13. Ce–Pt–Ge	78
4.4.14. Ce-Au-Ge	80
4.5. Pr-d element-Ge systems	81
4.5.1. PrMnGe	81
4.5.2. PrFeGe	81
4.5.3. PrCoGe	82
4.5.4. Pr–Ni–Ge	83
4.5.5. PrCuGe	84
4.5.6. Pr–Zn–Ge	85
4.5.7. Pr–Ru–Ge	85
4.5.8. Pr–Rh–Ge	86
4.5.9. Pr–Pd–Ge	86
4.5.10. Pr–Ag–Ge	87
4.5.11. Pr-Os-Ge	87
4.5.12. Pr–Ir–Ge	88
4.5.13. Pr–Pt–Ge	88
4.5.14. Pr–Au–Ge	88
4.6. Nd-d element-Ge systems	89
4.6.1. Nd–V–Ge	89
4.6.2. Nd–Cr–Ge	89
4.6.3. Nd–Mn–Ge	90
4.6.4. Nd-Fe-Ge	91
4.6.5. Nd–Co–Ge	92
4.6.6. Nd–N1–Ge	94
4.6.7. Nd–Cu–Ge	94
4.6.8. Nd–Zn–Ge	96
4.6.9. Nd–Zr–Ge	96
4.6.10. Nd–Nb–Ge	97
4.6.11. Nd-Mo-Ge	97
4.6.12. Nd-Ru-Ge	90
4.6.13. Nd-Rn(Pd)-Ge	99 00
4.6.14. Nd-Ag-Ge	100
4.6.15. Nd-HI-Ge	100
4.0.10. Nd - Ia - Oe	100
4.0.17. Nu-W-Oc 4.6.19 Nd Ba Ga	100
4.0.18. Nd Os-Ge	101
4.0.17. Nd -0.00	101
4.6.21 Nd $41-Ge$	104
4.7 Sm_d element_Ge systems	104
4.71 Sm_Mn_Ge	104
$4.7.2$ Sm_Fe_Ge	105
4.7.3. Sm-Co-Ge	106

4.7.4. Sm-Ni-Ge	108
4.7.5. Sm-Cu-Ge	109
4.7.6. Sm–Zn–Ge	110
4.7.7. Sm-Ru-Ge	110
4.7.8. Sm-Rh-Ge	112
4.7.9. Sm-Pd-Ge	113
4.7.10. Sm-Ag-Ge	114
4.7.11. Sm–Os–Ge	115
4.7.12. Sm–Ir–Ge	115
4.7.13. Sm-Pt-Ge	116
4.7.14. Sm-Au-Ge	117
4.8. Eu-d element-Ge systems	117
4.8.1. Eu-Mn-Ge	117
4.8.2. Eu-Fe-Ge	118
4.8.3. Eu-Co-Ge	118
4.8.4. Eu-Ni-Ge	119
4.8.5. EuCuGe	120
4.8.6. Eu-Zn-Ge	121
4.8.7. Eu-Ru-Ge	121
4.8.8. Eu-Rh-Ge	121
4.8.9. Eu-Pd-Ge	121
4.8.10. Eu-Ag-Ge	122
4.8.11. Eu-Os-Ge	123
4.8.12. Eu-Ir-Ge	123
4.8.13. Eu-Pt-Ge	123
4.8.14. Eu-Au-Ge	124
4.9. Gd-d element-Ge systems	124
4.9.1. GdMnGe	124
4.9.2. GdFeGe	125
4.9.3. Gd-Co-Ge	126
4.9.4. Gd-Ni-Ge	127
4.9.5. GdCuGe	128
4.9.6. GdNbGe	128
4.9.7. GdRuGe	128
4.9.8. Gd-Rh-Ge	129
4.9.9. Gd-Pd-Ge	129
4.9.10. Gd-Ag-Ge	130
4.9.11. Gd-Re-Ge	130
4.9.12. Gd–Os–Ge	130
4.9.13. Gd-Ir-Ge	131
4.9.14. Gd-Pt-Ge	131
4.9.15. Gd-Au-Ge	132
4.10. Tb-d element-Ge systems	132
4.10.1. Tb-Cr-Ge	132
4.10.2. Tb-Mn-Ge	132
4.10.3. Tb-Fe-Ge	134
4.10.4. Tb-Co-Ge	135
4.10.5. Tb-Ni-Ge	136
4.10.6. Tb-Cu-Ge	138
4.10.7. Tb-Nb-Ge	139
4.10.8. Tb-Mo-Ge	139

4.10.9. Tb-Ru-Ge	139
4.10.10. Tb-Rh-Ge	140
4.10.11. Tb-Pd-Ge	140
4.10.12. Tb-Ag-Ge	141
4.10.13. Tb-Os-Ge	141
4.10.14. Tb-Ir-Ge	141
4.10.15. Tb-Pt-Ge	142
4.10.16. Tb-Au-Ge	142
4,11. Dy-d element-Ge systems	143
4.11.1. Dy-Cr-Ge	143
4.11.2. Dy-Mn-Ge	143
4.11.3. Dy-Fe-Ge	143
4.11.4. Dv-Co-Ge	144
4.11.5. Dv-Ni-Ge	145
4.11.6. Dv-Cu-Ge	146
4.11.7. Dv-Nb-Ge	147
4.11.8. Dv-Mo-Ge	147
4.11.9. Dv-Ru(Rh.Pd)-Ge	147
4.11.10. Dv-Ag-Ge	147
4.11.11. Dv-Os(Ir. Pt)-Ge	147
4.11.12. Dv-Au-Ge	149
4.12. Ho-d element-Ge systems	149
4.12.1. Ho-Cr-Ge	149
4.12.2. Ho-Mn-Ge	149
4.12.3. Ho-Fe-Ge	149
4.12.4. Ho-Co-Ge	151
4.12.5. Ho-Ni-Ge	152
4.12.6. Ho-Cu-Ge	154
4.12.7. Ho-Nb-Ge	154
4.12.8. Ho-Mo-Ge	154
4.12.9, Ho-Ru-Ge	155
4.12.10, Ho-Rh-Ge	156
4.12.11. Ho-Pd-Ge	157
4.12.12. Ho-Ag-Ge	159
4.12.13. Ho-Re-Ge	159
4.12.14, Ho-Os-Ge	160
4.12.15. Ho-Ir-Ge	160
4.12.16. Ho-Pt-Ge	162
4.12.17, Ho-Au-Ge	163
4.13. Er-d element-Ge systems	163
4.13.1. Er–Cr–Ge	163
4.13.2. Er-Mn-Ge	163
4.13.3. Er-Fe-Ge	164
4.13.4. Er-Co-Ge	165
4.13.5. Er-Ni-Ge	167
4.13.6. Er-Cu-Ge	169
4.13.7. Er-Nb-Ge	169
4.13.8. Er-Mo-Ge	169
4.13.9. ErRuGe	169
4.13.10. Er-Rh-Ge	170
4.13.11. Er-Pd-Ge	170

4.13.13. Er–Os–Ge 171 4.13.14. Er–Tr–Ge 171 4.13.15. Er–Pt–Ge 172 4.13.16. Er–Au–Ge 172 4.14. Tm–delement–Ge systems 172 4.14.1. Tm–Mn–Ge 172 4.14.2. Tm–Fe–Ge 173 4.14.3. Tm–Cu–Ge 174 4.14.4. Tm–Ni–Ge 175 4.14.3. Tm–Cu–Ge 177 4.14.4. Tm–Ni–Ge 178 4.14.5. Tm–Cu–Ge 178 4.14.7. Tm–Mo–Ge 178 4.14.9. Tm–Rh–Ge 178 4.14.9. Tm–Rh–Ge 179 4.14.10. Tm–Pd–Ge 179 4.14.11. Tm–Ag–Ge 179 4.14.12. Tm–Os–Ge 179 4.14.13. Tm–Ir–Ge 180 4.15.1. Yb–Mn–Ge 181 4.15.2. Vb–Fe–Ge 182 4.15.3. Yb–Co–Ge 183 4.15.4. Yb–Ni–Ge 181 4.15.5. Yb–Cu–Ge 183 4.15.1. Yb–Ni–Ge 184 4.15.2. Yb–Fe–Ge 182 4.15.3. Yb–Pt–Ge 186 4.15.4. Yb–Ni–Ge 187 4.15.9. Yb–Re–Ge 18		4.13.12.	Er-Ag-Ge	171	
4.13.14. Er-Ir-Ge 171 4.13.15. Er-Pt-Ge 172 4.13.16. Er-An-Ge 172 4.14.1. Tm-delement-Ge systems 172 4.14.1. Tm-Mn-Ge 172 4.14.1. Tm-Mn-Ge 172 4.14.2. Tm-Fe-Ge 173 4.14.3. Tm-Co-Ge 174 4.14.4. Tm-Ni-Ge 175 4.14.5. Tm-Cu-Ge 178 4.14.6. Tm-Nb-Ge 178 4.14.7. Tm-Mo-Ge 178 4.14.8. Tm-Ru-Ge 178 4.14.9. Tm-Rh-Ge 178 4.14.10. Tm-Pd-Ge 179 4.14.13. Tm-Lr-Ge 180 4.14.14. Tm-Pt-Ge 180 4.14.15. Tm-Au-Ge 181 4.15. Yb-d element-Ge systems 181 4.15.1. Yb-Mn-Ge 181 4.15.2. Yb-Fe-Ge 183 4.15.5. Yb-Cu-Ge 183 4.15.6. Yb-Nb-Ge 186 4.15.7. Yb-Ru-Ge 186 4.15.8. Yb-Ph-Ge 187 4.15.9. Yb-Pd-Ge 188 4.15.11. Yb-Os-Ge 188 4.15.2. Yb-Ir-Ge 189 4.15.3. Yb-Pt-Ge <td></td> <td>4.13.13.</td> <td>Er–Os–Ge</td> <td>171</td> <td></td>		4.13.13.	Er–Os–Ge	171	
4.13.15. Er-Pt-Ge 172 4.13.16. Er-Au-Ge 172 4.14.1. Tm-d element-Ge systems 172 4.14.2. Tm-Fe-Ge 173 4.14.2. Tm-Fe-Ge 173 4.14.3. Tm-Co-Ge 174 4.14.4. Tm-Ni-Ge 175 4.14.5. Tm-Cu-Ge 177 4.14.6. Tm-Nb-Ge 178 4.14.7. Tm-Mo-Ge 178 4.14.8. Tm-Ru-Ge 178 4.14.9. Tm-Rh-Ge 178 4.14.9. Tm-Rh-Ge 179 4.14.10. Tm-Pd-Ge 179 4.14.12. Tm-Os-Ge 179 4.14.13. Tm-Hr-Ge 180 4.14.14. Tm-Pt-Ge 180 4.14.15. Tm-Au-Ge 181 4.15. Yb-d element-Ge systems 181 4.15.1. Yb-Mn-Ge 181 4.15.2. Yb-Fe-Ge 182 4.15.5. Yb-Cu-Ge 183 4.15.6. Yb-Nb-Ge 186 4.15.7. Yb-Ru-Ge 186 4.15.8. Yb-Rh-Ge 187 4.15.9. Yb-Pd-Ge 188 4.15.10. Yb-Ag-Ge 188 4.15.11. Yb-Os-Ge 188 4.15.12. Yb-Ir-Ge		4.13.14.	Er–Ir–Ge	171	
4.13.16. Er-Au-Ge 172 4.14. Tm-d element-Ge systems 172 4.14.1. Tm-Mn-Ge 172 4.14.2. Tm-Fe-Ge 173 4.14.3. Tm-Co-Ge 174 4.14.4. Tm-Ni-Ge 175 4.14.5. Tm-Cu-Ge 177 4.14.6. Tm-Nb-Ge 178 4.14.7. Tm-Mo-Ge 178 4.14.8. Tm-Ru-Ge 178 4.14.9. Tm-Rh-Ge 178 4.14.9. Tm-Rb-Ge 179 4.14.10. Tm-Pd-Ge 179 4.14.11. Tm-Ag-Ge 179 4.14.12. Tm-Os-Ge 179 4.14.13. Tm-Ir-Ge 180 4.14.14. Tm-Pt-Ge 180 4.14.15. Tm-Au-Ge 181 4.15.2. Yb-Fe-Ge 182 4.15.3. Yb-Co-Ge 183 4.15.4. Yb-Ni-Ge 184 4.15.5. Yb-Cu-Ge 185 4.15.6. Yb-Nb-Ge 186 4.15.7. Yb-Ru-Ge 187 6. 4.15.9. Yb-Pd-Ge 187 4.15.10. Yb-Ag-Ge 188 4.15.2. Yb-Fre-Ge 188 4.15.3. Yb-Pt-Ge 188 4.15.4. Yb-Na-		4.13.15.	Er–Pt–Ge	172	
4.14. Tm-d element-Ge systems 172 4.14.1. Tm-Mn-Ge 172 4.14.2. Tm-Fe-Ge 173 4.14.3. Tm-Co-Ge 174 4.14.3. Tm-Co-Ge 174 4.14.4. Tm-Ni-Ge 175 4.14.5. Tm-Cu-Ge 177 4.14.6. Tm-Nb-Ge 178 4.14.7. Tm-Mo-Ge 178 4.14.8. Tm-Ru-Ge 178 4.14.9. Tm-Rh-Ge 179 4.14.10. Tm-Pd-Ge 179 4.14.11. Tm-Ag-Ge 179 4.14.12. Tm-Os-Ge 179 4.14.13. Tm-Ir-Ge 180 4.14.14. Tm-Pt-Ge 180 4.15.1. Yb-Mo-Ge 181 4.15.2. Yb-Fe-Ge 182 4.15.3. Yb-Co-Ge 183 4.15.4. Yb-Ni-Ge 184 4.15.5. Yb-Cu-Ge 185 4.15.6. Yb-Nb-Ge 186 4.15.7. Yb-Ru-Ge 187 6. 4.15.8. Yb-Rh-Ge 187 4.15.9. Yb-Pd-Ge 187 6. 4.15.11. Yb-Os-Ge 188 4.15.12. Yb-Ir-Ge 189 4.15.12. Yb-Ir-Ge 4.15.13. Yb-Pt-Ge		4.13.16.	Er–Au–Ge	172	
4.14.1. Tm-Mn-Ge 172 4.14.2. Tm-Fe-Ge 173 4.14.3. Tm-Co-Ge 174 4.14.3. Tm-Co-Ge 175 4.14.4. Tm-Ni-Ge 175 4.14.5. Tm-Cu-Ge 177 4.14.6. Tm-Nb-Ge 178 4.14.7. Tm-Mo-Ge 178 4.14.8. Tm-Ru-Ge 178 4.14.9. Tm-Rh-Ge 178 4.14.9. Tm-Rh-Ge 178 4.14.10. Tm-Pd-Ge 179 4.14.11. Tm-Ag-Ge 179 4.14.12. Tm-Os-Ge 179 4.14.13. Tm-Hr-Ge 180 4.14.14. Tm-Pt-Ge 180 4.14.15. Tm-Au-Ge 181 4.15.1. Yb-Mn-Ge 181 4.15.2. Yb-Fe-Ge 182 4.15.3. Yb-Cu-Ge 183 4.15.4. Yb-Ni-Ge 184 4.15.5. Yb-Cu-Ge 185 4.15.6. Yb-Nb-Ge 186 4.15.7. Yb-Ru-Ge 187 4.15.8. Yb-Rh-Ge 187 4.15.9. Yb-Pd-Ge 188 4.15.10. Yb-Ag-Ge 188 4.15.11. Yb-Os-Ge 189 4.15.12. Yb-Ir-Ge 189	4	.14. Tm-d el	ement-Ge systems	172	
4.14.2.Tm-Fe-Ge1734.14.3.Tm-Co-Ge1744.14.4.Tm-Ni-Ge1754.14.5.Tm-Cu-Ge1774.14.6.Tm-Nb-Ge1784.14.7.Tm-Mo-Ge1784.14.8.Tm-Ru-Ge1784.14.9.Tm-Rh-Ge1784.14.10.Tm-Pd-Ge1794.14.11.Tm-Ag-Ge1794.14.12.Tm-Os-Ge1794.14.13.Tm-I-Ge1804.14.14.Tm-Pt-Ge1804.14.15.Tm-Au-Ge1814.15.15.Yb-Mn-Ge1814.15.2.Yb-Fe-Ge1824.15.3.Yb-Co-Ge1834.15.4.Yb-Ni-Ge1844.15.5.Yb-Ge-Ge1854.15.6.Yb-Ne-Ge1864.15.7.Yb-Ru-Ge1864.15.9.Yb-Pd-Ge1874.15.10.Yb-Ag-Ge1884.15.11.Yb-Os-Ge1884.15.12.Yb-Ir-Ge1894.15.13.Yb-Ir-Ge1894.15.14.Yb-Au-Ge1904.16.15.Lu-Au-Ge1904.16.11.Lu-Mo-Ge1934.16.2.Lu-Re-Ge1934.16.3.Lu-Cu-Ge1934.16.4.Lu-Ni-Ge1934.16.5.Lu-Ag-Ge1934.16.10.Lu-Ag-Ge1934.16.11.Lu-Ag-Ge1934.16.12.Lu-Ag-Ge1954.16.11.Lu-Os(Ir)-Ge1954.16.11. </td <td></td> <td>4.14.1.</td> <td>Tm-Mn-Ge</td> <td>172</td> <td></td>		4.14.1.	Tm-Mn-Ge	172	
4.14.3. Tm-Co-Ge1744.14.4. Tm-Ni-Ge1754.14.5. Tm-Cu-Ge1774.14.6. Tm-Nb-Ge1784.14.7. Tm-Mo-Ge1784.14.7. Tm-Mo-Ge1784.14.8. Tm-Ru-Ge1784.14.9. Tm-Rh-Ge1794.14.10. Tm-Pd-Ge1794.14.11. Tm-Ag-Ge1794.14.12. Tm-Os-Ge1794.14.13. Tm-Ir-Ge1804.14.14. Tm-Pt-Ge1804.14.15. Tm-Au-Ge1814.15. Yb-Ge-Ge1824.15. Yb-Ge-Ge1824.15. Yb-Fe-Ge1824.15. Yb-Ge-Ge1834.15. Yb-Ge-Ge1854.15. Yb-Ni-Ge1844.15. Yb-Ne-Ge1864.15. Yb-Ne-Ge1864.15. Yb-Cu-Ge1854.15. Yb-Ne-Ge1864.15. Yb-Ne-Ge1864.15.1 Yb-Na-Ge1884.15.2 Yb-Fe-Ge1824.15.3 Yb-Cu-Ge1884.15.4 Yb-Ni-Ge1894.15.1 Yb-Na-Ge1894.15.1 Yb-Na-Ge1894.15.1 Yb-Au-Ge1904.16.1 Lu-Mn-Ge1904.16.1 Lu-Mn-Ge1904.16.2 Lu-Fe-Ge1914.16.3 Lu-Cu-Ge1934.16.4 Lu-Ni-Ge1934.16.5 Lu-Cu-Ge1934.16.6 Lu-Nb-Ge1934.16.7 Lu-Mo-Ge1934.16.8 Lu-Ru(Rh, Pd)-Ge1934.16.10 Lu-Re-Ge1954.16.11 Lu-Os(Ir)-Ge1954.16.12 Lu-Ag-Ge1955.1. Sc-R'-Ge systems <td></td> <td>4.14.2.</td> <td>Tm–Fe–Ge</td> <td>173</td> <td></td>		4.14.2.	Tm–Fe–Ge	173	
4.14.4.Tm-Ni-Ge1754.14.5.Tm-Cu-Ge1774.14.5.Tm-Nb-Ge1784.14.6.Tm-Nb-Ge1784.14.7.Tm-Mo-Ge1784.14.8.Tm-Ru-Ge1784.14.9.Tm-Rh-Ge1794.14.10.Tm-Pd-Ge1794.14.11.Tm-Ag-Ge1794.14.12.Tm-Os-Ge1794.14.13.Tm-In-Ge1804.14.14.Tm-Pt-Ge1804.14.15.Tm-Au-Ge1814.15.1Yb-Mn-Ge1814.15.2.Yb-Fe-Ge1824.15.3.Yb-Co-Ge1834.15.4.Yb-Ni-Ge1864.15.5.Yb-Cu-Ge1854.15.6.Yb-Ni-Ge1864.15.7.Yb-Ru-Ge1864.15.8.Yb-Rb-Ge1874.15.9.Yb-Pd-Ge1874.15.10.Yb-Ag-Ge1884.15.11.Yb-Os-Ge1884.15.12.Yb-Ir-Ge1894.15.13.Yb-Pt-Ge1894.16.1.Lu-Mn-Ge1904.16.2.Lu-Fe-Ge1904.16.3.Lu-Cu-Ge1934.16.4.Lu-Ni-Ge1934.16.5.Lu-Cu-Ge1934.16.6.Lu-Nb-Ge1934.16.7.Lu-Ag-Ge1934.16.8.Lu-Ru(Rh, Pd)-Ge1934.16.10.Lu-Ag-Ge1954.16.11.Lu-Ag-Ge1955.Rare earth-f element-germanium systems196		4.14.3.	Tm-Co-Ge	174	
4.14.5. Tm-Cu-Ge177 $4.14.6.$ Tm-Nb-Ge178 $4.14.6.$ Tm-Nb-Ge178 $4.14.7.$ Tm-Mo-Ge178 $4.14.8.$ Tm-Ru-Ge178 $4.14.9.$ Tm-Rh-Ge179 $4.14.9.$ Tm-Rh-Ge179 $4.14.10.$ Tm-Pd-Ge179 $4.14.11.$ Tm-Ag-Ge179 $4.14.12.$ Tm-Os-Ge179 $4.14.13.$ Tm-Ir-Ge180 $4.14.13.$ Tm-Ir-Ge180 $4.14.14.$ Tm-Pt-Ge181 $4.15.$ Tm-Au-Ge181 $4.15.$ Tm-Au-Ge181 $4.15.$ Tm-Au-Ge181 $4.15.$ Yb-d element-Ge systems181 $4.15.2.$ Yb-Fe-Ge182 $4.15.3.$ Yb-Co-Ge183 $4.15.4.$ Yb-Ni-Ge186 $4.15.5.$ Yb-Cu-Ge185 $4.15.6.$ Yb-Nb-Ge186 $4.15.7.$ Yb-Ru-Ge186 $4.15.9.$ Yb-Pd-Ge187 $4.15.10.$ Yb-Ag-Ge188 $4.15.11.$ Yb-Os-Ge188 $4.15.12.$ Yb-Ir-Ge189 $4.16.1.$ Lu-Ma-Ge190 $4.16.1.$ Lu-Ma-Ge190 $4.16.1.$ Lu-Ma-Ge190 $4.16.1.$ Lu-Ma-Ge191 $4.16.1.$ Lu-Ni-Ge192 $4.16.1.$ Lu-Ni-Ge193 $4.16.1.$ Lu-Na-Ge193 $4.16.1.$ Lu-Ag-Ge195 $4.16.1.$ Lu-Ag-Ge195<		4.14.4.	Tm-Ni-Ge	175	
4.14.6. Tm-Nb-Ge1784.14.7. Tm-Mo-Ge1784.14.8. Tm-Ru-Ge1784.14.9. Tm-Rh-Ge1784.14.10. Tm-Pd-Ge1794.14.11. Tm-Ag-Ge1794.14.12. Tm-Os-Ge1794.14.13. Tm-Ir-Ge1804.14.14. Tm-Pt-Ge1804.14.15. Tm-Au-Ge1814.15. Yb-d element-Ge systems1814.15. Yb-Ge-Ge1824.15. Yb-Mn-Ge1814.15. Yb-Me-Ge1824.15. Yb-Me-Ge1834.15. Yb-Me-Ge1844.15. Yb-Ni-Ge1844.15. Yb-Ne-Ge1854.15. Yb-Ne-Ge1864.15. Yb-Ne-Ge1864.15.9. Yb-Pd-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Ir-Ge1894.15.13. Yb-Pt-Ge1894.15.14. Yb-Au-Ge1904.16.14. Lu-Mn-Ge1904.16.2. Lu-Fe-Ge1904.16.3. Lu-Co-Ge1914.16.4. Lu-Ni-Ge1924.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1934.16.9. Lu-Ag-Ge1954.16.10. Lu-Re-Ge1954.16.10. Lu-Re-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4.14.5.	TmCuGe	177	
4.14.7.Tm-Mo-Ge1784.14.8.Tm-Ru-Ge1784.14.9.Tm-Rh-Ge1784.14.10.Tm-Pd-Ge1794.14.11.Tm-Ag-Ge1794.14.12.Tm-Os-Ge1794.14.13.Tm-Ir-Ge1804.14.14.Tm-Pt-Ge1804.14.15.Tm-Au-Ge1814.15.Yb-d element-Ge systems1814.15.1.Yb-Ma-Ge1814.15.2.Yb-Fe-Ge1824.15.3.Yb-Co-Ge1834.15.4.Yb-Ni-Ge1834.15.5.Yb-Cu-Ge1854.15.6.Yb-Nb-Ge1864.15.7.Yb-Ru-Ge1864.15.8.Yb-Rh-Ge1874.15.10.Yb-Ag-Ge1884.15.11.Yb-Os-Ge1884.15.12.Yb-Ir-Ge1894.15.13.Yb-Pt-Ge1894.15.14.Yb-Au-Ge1904.16.1.Lu-Fe-Ge1904.16.1.Lu-Fe-Ge1904.16.2.Lu-Fe-Ge1914.16.3.Lu-Co-Ge1934.16.4.Lu-Ni-Ge1934.16.5.Lu-Ag-Ge1934.16.6.Lu-Nb-Ge1934.16.7.Lu-Ag-Ge1934.16.8.Lu-Ag-Ge1954.16.10.Lu-Ag-Ge1955.Rare earth-f element-germanium systems1965.Rare earth-f element-germanium systems196		4.14.6.	Tm-Nb-Ge	178	
4.14.8. Tm-Ru-Ge1784.14.9. Tm-Rh-Ge1784.14.10. Tm-Pd-Ge1794.14.11. Tm-Ag-Ge1794.14.12. Tm-Os-Ge1794.14.13. Tm-Ir-Ge1804.14.14. Tm-Pt-Ge1804.14.15. Tm-Au-Ge1814.15. Yb-d element-Ge systems1814.15.1. Yb-Mn-Ge1814.15.2. Yb-Fe-Ge1824.15.3. Yb-Co-Ge1834.15.4. Yb-Ni-Ge1844.15.5. Yb-Cu-Ge1854.15.6. Yb-Nb-Ge1864.15.7. Yb-Ru-Ge1864.15.8. Yb-Rh-Ge1874.15.9. Yb-Pd-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Ir-Ge1894.15.13. Yb-Pd-Ge1894.15.14. Yb-Au-Ge1904.16.1. Lu-Mn-Ge1904.16.2. Lu-Fe-Ge1914.16.3. Lu-Co-Ge1934.16.4. Lu-Ni-Ge1924.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1934.16.9. Lu-Ag-Ge1944.16.9. Lu-Ag-Ge1954.16.11. Lu-Os(Ir)-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4.14.7.	Tm-Mo-Ge	178	
4.14.9. Tm-Rh-Ge1784.14.10. Tm-Pd-Ge1794.14.11. Tm-Ag-Ge1794.14.12. Tm-Os-Ge1794.14.13. Tm-Ir-Ge1804.14.14. Tm-Pt-Ge1804.14.15. Tm-Au-Ge1814.15. Yb-d element-Ge systems1814.15.1. Yb-Mn-Ge1814.15.2. Yb-Fe-Ge1824.15.3. Yb-Co-Ge1834.15.4. Yb-Ni-Ge1844.15.5. Yb-Cu-Ge1854.15.6. Yb-Nb-Ge1864.15.7. Yb-Ru-Ge1864.15.8. Yb-Rh-Ge1874.15.9. Yb-Pd-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Ir-Ge1894.15.13. Yb-Pd-Ge1894.15.14. Yb-Au-Ge1904.16.1. Lu-Mn-Ge1904.16.2. Lu-Fe-Ge1914.16.3. Lu-Co-Ge1934.16.4. Lu-Ni-Ge1934.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1934.16.9. Lu-Ag-Ge1944.16.9. Lu-Ag-Ge1954.16.11. Lu-Os(Ir)-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4.14.8.	Tm-Ru-Ge	178	
4.14.10. Tm-Pd-Ge1794.14.11. Tm-Ag-Ge1794.14.12. Tm-Os-Ge1794.14.13. Tm-Ir-Ge1804.14.14. Tm-Pt-Ge1804.14.15. Tm-Au-Ge1814.15. Yb-d element-Ge systems1814.15.1. Yb-Mn-Ge1814.15.2. Yb-Fe-Ge1824.15.3. Yb-Co-Ge1834.15.4. Yb-Ni-Ge1844.15.5. Yb-Cu-Ge1854.15.6. Yb-Nb-Ge1864.15.7. Yb-Ru-Ge1864.15.8. Yb-Rh-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Fr-Ge1884.15.13. Yb-Pd-Ge1884.15.14. Yb-Au-Ge1904.16.1. Lu-Mn-Ge1904.16.1. Lu-Mn-Ge1904.16.2. Lu-Fe-Ge1914.16.3. Lu-Co-Ge1934.16.4. Lu-Ni-Ge1934.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1934.16.9. Lu-Ag-Ge1944.16.10. Lu-Re-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4.14.9.	Tm-Rh-Ge	178	
4.14.11. Tm-Ag-Ge1794.14.12. Tm-Os-Ge1794.14.13. Tm-Ir-Ge1804.14.13. Tm-Ir-Ge1804.14.14. Tm-Pt-Ge1814.15. Yb-d element-Ge systems1814.15.1. Yb-Mn-Ge1814.15.2. Yb-Fe-Ge1824.15.3. Yb-Co-Ge1834.15.4. Yb-Ni-Ge1844.15.5. Yb-Cu-Ge1854.15.6. Yb-Nb-Ge1864.15.7. Yb-Ru-Ge1864.15.8. Yb-Rh-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Fr-Ge1894.15.13. Yb-Pt-Ge1894.15.14. Yb-Au-Ge1904.16.1. Lu-Mn-Ge1904.16.1. Lu-Mn-Ge1904.16.3. Lu-Co-Ge1934.16.5. Lu-Nb-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1934.16.9. Lu-Ag-Ge1934.16.10. Lu-Re-Ge1954.16.11. Lu-Os(Ir)-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4.14.10.	Tm-Pd-Ge	179	
4.14.12.Tm-Os-Ge1794.14.13.Tm-Ir-Ge1804.14.14.Tm-Pt-Ge1804.14.15.Tm-Au-Ge1814.15.Yb-d element-Ge systems1814.15.Yb-Mn-Ge1814.15.1.Yb-Mn-Ge1814.15.2.Yb-Fe-Ge1824.15.3.Yb-Co-Ge1834.15.4.Yb-Ni-Ge1844.15.5.Yb-Cu-Ge1854.15.6.Yb-Nb-Ge1864.15.7.Yb-Ru-Ge1864.15.8.Yb-Rh-Ge1874.15.10.Yb-Ag-Ge1884.15.11.Yb-Os-Ge1884.15.12.Yb-Ir-Ge1894.15.13.Yb-Pt-Ge1894.15.14.Yb-Au-Ge1904.16.1.Lu-Mn-Ge1904.16.3.Lu-Co-Ge1914.16.4.Lu-Ni-Ge1924.16.5.Lu-Re-Ge1934.16.6.Lu-Nb-Ge1934.16.7.Lu-Ag-Ge1944.16.9.Lu-Ag-Ge1954.16.10.Lu-Re-Ge1955.Rare earth-f element-germanium systems1965.1.Sc-R'-Ge systems196		4.14.11.	Tm-Ag-Ge	179	
4.14.13. Tm-Ir-Ge1804.14.14. Tm-Pt-Ge1804.14.15. Tm-Au-Ge1814.15. Yb-d element-Ge systems1814.15. Yb-d element-Ge systems1814.15. Yb-d element-Ge systems1814.15. Yb-Ge-Ge1824.15.3. Yb-Co-Ge1834.15.4. Yb-Ni-Ge1844.15.5. Yb-Cu-Ge1854.15.6. Yb-Nb-Ge1864.15.7. Yb-Ru-Ge1864.15.8. Yb-Rh-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Ir-Ge1894.15.13. Yb-Pt-Ge1894.15.14. Yb-Au-Ge1904.16.1. Lu-Ma-Ge1904.16.2. Lu-Fe-Ge1914.16.3. Lu-Co-Ge1934.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1934.16.9. Lu-Ag-Ge1944.16.9. Lu-Ag-Ge1954.16.11. Lu-Os(Ir)-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4.14.12.	Tm-Os-Ge	179	
4.14.14. Tm-Pt-Ge1804.14.15. Tm-Au-Ge1814.15.1. Yb-d element-Ge systems1814.15.1. Yb-Mn-Ge1814.15.2. Yb-Fe-Ge1824.15.3. Yb-Co-Ge1834.15.4. Yb-Ni-Ge1844.15.5. Yb-Cu-Ge1854.15.6. Yb-Nb-Ge1864.15.7. Yb-Ru-Ge1864.15.8. Yb-Rh-Ge1874.15.9. Yb-Pd-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Ir-Ge1894.15.13. Yb-Pt-Ge1894.15.14. Yb-Au-Ge1904.16.1. Lu-Mn-Ge1904.16.2. Lu-Fe-Ge1914.16.3. Lu-Co-Ge1934.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1934.16.9. Lu-Ag-Ge1944.16.9. Lu-Ag-Ge1954.16.11. Lu-Os(Ir)-Ge1954.16.12. Lu-Re-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4.14.13.	Tm-Ir-Ge	180	
4.14.15. Tm-Au-Ge1814.15. Tm-Au-Ge1814.15. Yb-d element-Ge systems1814.15.1. Yb-Mn-Ge1814.15.2. Yb-Fe-Ge1824.15.3. Yb-Co-Ge1834.15.4. Yb-Ni-Ge1844.15.5. Yb-Cu-Ge1854.15.6. Yb-Nb-Ge1864.15.7. Yb-Ru-Ge1864.15.8. Yb-Rh-Ge1874.15.9. Yb-Pd-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Ir-Ge1894.15.13. Yb-Pt-Ge1894.15.14. Yb-Au-Ge1904.16.1. Lu-Mn-Ge1904.16.2. Lu-Fe-Ge1914.16.3. Lu-Co-Ge1934.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1934.16.9. Lu-Ag-Ge1944.16.9. Lu-Ag-Ge1954.16.11. Lu-Os(Ir)-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4.14.14.	Tm-Pt-Ge	180	
4.15. Yb-d element-Ge systems 181 4.15.1. Yb-Mn-Ge 181 4.15.1. Yb-Mn-Ge 181 4.15.2. Yb-Fe-Ge 182 4.15.3. Yb-Co-Ge 183 4.15.4. Yb-Ni-Ge 184 4.15.5. Yb-Cu-Ge 185 4.15.6. Yb-Nb-Ge 186 4.15.7. Yb-Ru-Ge 186 4.15.8. Yb-Rh-Ge 187 4.15.9. Yb-Pd-Ge 187 4.15.10. Yb-Ag-Ge 188 4.15.12. Yb-Ir-Ge 189 4.15.13. Yb-Pt-Ge 189 4.15.14. Yb-Au-Ge 190 4.16.1. Lu-Mn-Ge 190 4.16.2. Lu-Fe-Ge 190 4.16.3. Lu-Co-Ge 191 4.16.4. Lu-Ni-Ge 192 4.16.5. Lu-Cu-Ge 193 4.16.6. Lu-Nb-Ge 193 4.16.7. Lu-Mo-Ge 193 4.16.8. Lu-Ru(Rh, Pd)-Ge 193 4.16.9. Lu-Ag-Ge 194 4.16.9. Lu-Ag-Ge 195 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 4.16.12. Lu-Au-Ge 195 5. Rare earth-f elemen		4.14.15.	TmAu-Ge	181	
11.110.110.110.110.110.1 $4.15.1.$ Yb-Mn-Ge181 $4.15.2.$ Yb-Fe-Ge182 $4.15.3.$ Yb-Co-Ge183 $4.15.4.$ Yb-Ni-Ge183 $4.15.5.$ Yb-Cu-Ge185 $4.15.6.$ Yb-Nb-Ge186 $4.15.7.$ Yb-Ru-Ge186 $4.15.8.$ Yb-Rh-Ge187 $4.15.9.$ Yb-Pd-Ge187 $4.15.9.$ Yb-Pd-Ge187 $4.15.10.$ Yb-Ag-Ge188 $4.15.12.$ Yb-Ir-Ge189 $4.15.13.$ Yb-Pt-Ge189 $4.15.14.$ Yb-Au-Ge190 $4.16.1.$ Lu-Mn-Ge190 $4.16.2.$ Lu-Fe-Ge191 $4.16.3.$ Lu-Co-Ge191 $4.16.5.$ Lu-Cu-Ge193 $4.16.6.$ Lu-Nb-Ge193 $4.16.7.$ Lu-Mo-Ge193 $4.16.8.$ Lu-Ru(Rh, Pd)-Ge194 $4.16.9.$ Lu-Ag-Ge194 $4.16.10.$ Lu-Re-Ge195 $4.16.11.$ Lu-Ag-Ge195 $4.16.12.$ Lu-Ag-Ge195 $5.$ Rare earth-f element-germanium systems196 $5.1.$ Sc-R'-Ge systems196	4	15. Yb-d el	ement_Ge systems	181	
4.15.2. Yb-Fe-Ge 182 $4.15.2.$ Yb-Fe-Ge 182 $4.15.3.$ Yb-Co-Ge 183 $4.15.3.$ Yb-Co-Ge 183 $4.15.4.$ Yb-Ni-Ge 184 $4.15.5.$ Yb-Cu-Ge 185 $4.15.6.$ Yb-Nb-Ge 186 $4.15.7.$ Yb-Ru-Ge 186 $4.15.7.$ Yb-Ru-Ge 187 $4.15.8.$ Yb-Rh-Ge 187 $4.15.9.$ Yb-Pd-Ge 187 $4.15.9.$ Yb-Pd-Ge 188 $4.15.10.$ Yb-Ag-Ge 188 $4.15.12.$ Yb-Ir-Ge 189 $4.15.12.$ Yb-Ir-Ge 189 $4.15.13.$ Yb-Pt-Ge 189 $4.15.14.$ Yb-Au-Ge 190 $4.16.1.$ Lu-Mn-Ge 190 $4.16.2.$ Lu-Fe-Ge 190 $4.16.3.$ Lu-Co-Ge 191 $4.16.4.$ Lu-Ni-Ge 192 $4.16.5.$ Lu-Cu-Ge 193 $4.16.6.$ Lu-Nb-Ge 193 $4.16.6.$ Lu-Nb-Ge 193 $4.16.8.$ Lu-Ru(Rh, Pd)-Ge 194 $4.16.9.$ Lu-Ag-Ge 194 $4.16.9.$ Lu-Ag-Ge 195 $4.16.10.$ Lu-Re-Ge 195 $4.16.10.$ Lu-Re-Ge 195 $4.16.10.$ Lu-Re-Ge 195 $4.16.10.$ Lu-Re-Ge 195 $5.$ Rare earth-f element-germanium systems 196 $5.1.$ Sc-R'-Ge systems 196		4151	Yh-Mn-Ge	181	
4.15.1.Yb-Co-Ge1834.15.3.Yb-Co-Ge1834.15.4.Yb-Ni-Ge1844.15.5.Yb-Cu-Ge1854.15.6.Yb-Nb-Ge1864.15.7.Yb-Ru-Ge1864.15.8.Yb-Rh-Ge1874.15.9.Yb-Pd-Ge1874.15.10.Yb-Ag-Ge1884.15.11.Yb-Os-Ge1884.15.12.Yb-Ir-Ge1894.15.13.Yb-Pt-Ge1894.15.14.Yb-Au-Ge1904.16.1.Lu-Mn-Ge1904.16.2.Lu-Fe-Ge1904.16.3.Lu-Co-Ge1914.16.4.Lu-Ni-Ge1934.16.5.Lu-Cu-Ge1934.16.6.Lu-Nb-Ge1934.16.7.Lu-Mo-Ge1934.16.8.Lu-Re/Ge1944.16.9.Lu-Ag-Ge1944.16.10.Lu-Re-Ge1954.16.11.Lu-Os(Ir)-Ge1954.16.12.Lu-Au-Ge1955.Rare earth-f element-germanium systems1965.1.Sc-R'-Ge systems196		4152	Yb-Fe-Ge	182	
4.15.1. Yb-Ni-Ge1844.15.4. Yb-Ni-Ge1854.15.5. Yb-Cu-Ge1854.15.5. Yb-Nb-Ge1864.15.7. Yb-Ru-Ge1864.15.8. Yb-Rh-Ge1874.15.9. Yb-Pd-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Ir-Ge1894.15.13. Yb-Pt-Ge1894.15.14. Yb-Au-Ge1904.16.1. Lu-Mn-Ge1904.16.2. Lu-Fe-Ge1904.16.3. Lu-Co-Ge1914.16.4. Lu-Ni-Ge1924.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1944.16.9. Lu-Ag-Ge1944.16.10. Lu-Re-Ge1954.16.11. Lu-Os(Ir)-Ge1954.16.12. Lu-Au-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4 15 3	Yb-Co-Ge	182	
4.15Yb-Cu-Ge 185 4.15 Yb-Cu-Ge 185 4.15 Yb-Nb-Ge 186 4.15 Yb-Ru-Ge 186 4.15 Yb-Rh-Ge 187 4.15 Yb-Pd-Ge 187 4.15 Yb-Pd-Ge 187 4.15 Yb-Pd-Ge 188 4.15 Yb-Pd-Ge 188 4.15 Yb-Pd-Ge 188 4.15 Yb-Pd-Ge 188 4.15 Yb-Pd-Ge 189 4.15 Yb-Pt-Ge 189 4.15 Yb-Pt-Ge 189 4.15 Yb-Pt-Ge 190 4.16 Lu-Mn-Ge 190 4.16 Lu-Fe-Ge 190 4.16 Lu-Fe-Ge 191 4.16 Lu-Nb-Ge 193 4.16 Lu-Nb-Ge 193 4.16 Lu-Nb-Ge 193 4.16 Lu-Ag-Ge 194 4.16 Lu-Ag-Ge 194 4.16 Lu-Ag-Ge 195 $4.16.1$ Lu-Ag-Ge 195 5 Rare earth-f element-germanium systems 196 5.1 Sc-R'-Ge systems 196		4 15 4	Yh-Ni-Ge	184	
4.15.6. Yb-Nb-Ge1864.15.6. Yb-Nb-Ge1864.15.7. Yb-Ru-Ge1864.15.7. Yb-Ru-Ge1874.15.9. Yb-Pd-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Ir-Ge1894.15.13. Yb-Pt-Ge1894.15.14. Yb-Au-Ge1904.16.1. Lu-Mn-Ge1904.16.2. Lu-Fe-Ge1914.16.3. Lu-Co-Ge1914.16.4. Lu-Ni-Ge1924.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1944.16.9. Lu-Ag-Ge1944.16.10. Lu-Re-Ge1954.16.11. Lu-Os(Ir)-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4 15 5	Yb-Cu-Ge	185	
4.15.7. Yb-Ru-Ge186 $4.15.7.$ Yb-Ru-Ge186 $4.15.8.$ Yb-Rh-Ge187 $4.15.9.$ Yb-Pd-Ge187 $4.15.9.$ Yb-Pd-Ge187 $4.15.10.$ Yb-Ag-Ge188 $4.15.11.$ Yb-Os-Ge188 $4.15.12.$ Yb-Ir-Ge189 $4.15.13.$ Yb-Pt-Ge189 $4.15.14.$ Yb-Au-Ge190 $4.16.1.$ Lu-d element-Ge systems190 $4.16.2.$ Lu-Fe-Ge190 $4.16.3.$ Lu-Co-Ge191 $4.16.4.$ Lu-Ni-Ge192 $4.16.5.$ Lu-Cu-Ge193 $4.16.6.$ Lu-Nb-Ge193 $4.16.7.$ Lu-Mo-Ge193 $4.16.8.$ Lu-Ru(Rh, Pd)-Ge194 $4.16.9.$ Lu-Ag-Ge194 $4.16.10.$ Lu-Re-Ge195 $4.16.11.$ Lu-Os(Ir)-Ge195 $4.16.12.$ Lu-Au-Ge195 $5.$ Rare earth-f element-germanium systems196 $5.1.$ Sc-R'-Ge systems196		4 15 6	Yh-Nh-Ge	186	
4.15.11Yb-Rh-Ge1876. $4.15.8$ Yb-Pd-Ge187 $4.15.9$ Yb-Pd-Ge187 $4.15.9$ Yb-Pd-Ge188 $4.15.10$ Yb-Ag-Ge188 $4.15.11$ Yb-Os-Ge188 $4.15.12$ Yb-Ir-Ge189 $4.15.13$ Yb-Pt-Ge189 $4.15.14$ Yb-Au-Ge190 $4.16.1$ Lu-Mn-Ge190 $4.16.1$ Lu-Fe-Ge190 $4.16.2$ Lu-Fe-Ge191 $4.16.3$ Lu-Co-Ge191 $4.16.4$ Lu-Ni-Ge193 $4.16.5$ Lu-Cu-Ge193 $4.16.6$ Lu-Nb-Ge193 $4.16.8$ Lu-Ru(Rh, Pd)-Ge194 $4.16.9$ Lu-Ag-Ge194 $4.16.10$ Lu-Re-Ge195 $4.16.11$ Lu-Os(Ir)-Ge195 $4.16.12$ Lu-Au-Ge195 5 Rare earth-f element-germanium systems196 5.1 Sc-R'-Ge systems196		4 15 7	Yh-Ru-Ge	186	
4.15.9. Yb-Pd-Ge1874.15.9. Yb-Pd-Ge1874.15.10. Yb-Ag-Ge1884.15.11. Yb-Os-Ge1884.15.12. Yb-Ir-Ge1894.15.13. Yb-Pt-Ge1894.15.14. Yb-Au-Ge1904.16. Lu-d element-Ge systems1904.16.1. Lu-Mn-Ge1904.16.2. Lu-Fe-Ge1914.16.3. Lu-Co-Ge1914.16.4. Lu-Ni-Ge1924.16.5. Lu-Cu-Ge1934.16.6. Lu-Nb-Ge1934.16.7. Lu-Mo-Ge1934.16.8. Lu-Ru(Rh, Pd)-Ge1944.16.9. Lu-Ag-Ge1944.16.10. Lu-Re-Ge1954.16.11. Lu-Os(Ir)-Ge1955. Rare earth-f element-germanium systems1965.1. Sc-R'-Ge systems196		4 15 8	Yh-Rh-Ge	187	6.
4.15.10.Yb-Ag-Ge188 $4.15.10.$ Yb-Ag-Ge188 $4.15.11.$ Yb-Os-Ge188 $4.15.12.$ Yb-Ir-Ge189 $4.15.13.$ Yb-Pt-Ge189 $4.15.13.$ Yb-Pt-Ge189 $4.15.14.$ Yb-Au-Ge190 $4.16.$ Lu-d element-Ge systems190 $4.16.1.$ Lu-Mn-Ge190 $4.16.2.$ Lu-Fe-Ge191 $4.16.3.$ Lu-Co-Ge191 $4.16.4.$ Lu-Ni-Ge193 $4.16.5.$ Lu-Cu-Ge193 $4.16.6.$ Lu-Nb-Ge193 $4.16.7.$ Lu-Mo-Ge193 $4.16.8.$ Lu-Ru(Rh, Pd)-Ge194 $4.16.9.$ Lu-Ag-Ge195 $4.16.10.$ Lu-Re-Ge195 $4.16.11.$ Lu-Os(Ir)-Ge195 $5.$ Rare earth-f element-germanium systems196 $5.1.$ Sc-R'-Ge systems196		4 15 9	Yh-Pd-Ge	187	
4.15.11. Yb-Os-Ge 188 4.15.11. Yb-Os-Ge 188 4.15.12. Yb-Ir-Ge 189 4.15.13. Yb-Pt-Ge 189 4.15.14. Yb-Au-Ge 190 4.16. Lu-delement-Ge systems 190 4.16.1. Lu-Mn-Ge 190 4.16.2. Lu-Fe-Ge 190 4.16.3. Lu-Co-Ge 191 4.16.4. Lu-Ni-Ge 192 4.16.5. Lu-Cu-Ge 193 4.16.6. Lu-Nb-Ge 193 4.16.7. Lu-Mo-Ge 193 4.16.8. Lu-Ru(Rh, Pd)-Ge 194 4.16.9. Lu-Ag-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4 15 10	Vh-Ag-Ge	188	
4.15.12. Yb-Jr-Ge 189 $4.15.12.$ Yb-Jr-Ge 189 $4.15.13.$ Yb-Pt-Ge 189 $4.15.13.$ Yb-Pt-Ge 189 $4.15.13.$ Yb-Pt-Ge 190 $4.15.14.$ Yb-Au-Ge 190 $4.16.1.$ Lu-Mn-Ge 190 $4.16.1.$ Lu-Mn-Ge 190 $4.16.1.$ Lu-Mn-Ge 190 $4.16.2.$ Lu-Fe-Ge 190 $4.16.3.$ Lu-Co-Ge 191 $4.16.4.$ Lu-Ni-Ge 192 $4.16.5.$ Lu-Cu-Ge 193 $4.16.6.$ Lu-Nb-Ge 193 $4.16.7.$ Lu-Mo-Ge 193 $4.16.8.$ Lu-Ru(Rh, Pd)-Ge 194 $4.16.9.$ Lu-Ag-Ge 194 $4.16.10.$ Lu-Re-Ge 195 $4.16.10.$ Lu-Re-Ge 195 $4.16.12.$ Lu-Au-Ge 195 $5.$ Rare earth-f element-germanium systems 196 $5.1.$ Sc-R'-Ge systems 196		4 15 11	Yh-Os-Ge	188	
4.15.12. Yb-Pt-Ge 189 4.15.13. Yb-Pt-Ge 189 4.15.14. Yb-Au-Ge 190 4.16.1. Lu-Mn-Ge 190 4.16.1. Lu-Mn-Ge 190 4.16.1. Lu-Mn-Ge 190 4.16.1. Lu-Mn-Ge 190 4.16.2. Lu-Fe-Ge 190 4.16.3. Lu-Co-Ge 191 4.16.4. Lu-Ni-Ge 192 4.16.5. Lu-Cu-Ge 193 4.16.6. Lu-Nb-Ge 193 4.16.7. Lu-Mo-Ge 193 4.16.8. Lu-Ru(Rh, Pd)-Ge 194 4.16.9. Lu-Ag-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4 15 12	Vb-Ir-Ge	189	
4.15.1.1. 10 Fr GC 109 4.15.1.4. Yb-Au-Ge 190 4.15.14. Yb-Au-Ge 190 4.16.1. Lu-delement-Ge systems 190 4.16.1. Lu-Mn-Ge 190 4.16.1. Lu-Mn-Ge 190 4.16.2. Lu-Fe-Ge 190 4.16.3. Lu-Co-Ge 191 4.16.4. Lu-Ni-Ge 192 4.16.5. Lu-Cu-Ge 193 4.16.6. Lu-Nb-Ge 193 4.16.7. Lu-Mo-Ge 193 4.16.8. Lu-Ru(Rh, Pd)-Ge 194 4.16.9. Lu-Ag-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4.15.12.	Vh_Pt_Ge	189	
4.16. Lu-d element-Ge systems 190 4.16. Lu-Mn-Ge 190 4.16.1. Lu-Mn-Ge 190 4.16.1. Lu-Mn-Ge 190 4.16.2. Lu-Fe-Ge 190 4.16.3. Lu-Co-Ge 191 4.16.4. Lu-Ni-Ge 192 4.16.5. Lu-Cu-Ge 193 4.16.6. Lu-Nb-Ge 193 4.16.7. Lu-Mo-Ge 193 4.16.8. Lu-Ru(Rh, Pd)-Ge 194 4.16.9. Lu-Ag-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4 15 14	Vh-Au-Ge	190	
4.16.Lu - Mn-Ge190 $4.16.1.$ Lu-Mn-Ge190 $4.16.2.$ Lu-Fe-Ge190 $4.16.3.$ Lu-Co-Ge191 $4.16.3.$ Lu-Co-Ge192 $4.16.5.$ Lu-Cu-Ge193 $4.16.5.$ Lu-Cu-Ge193 $4.16.6.$ Lu-Nb-Ge193 $4.16.7.$ Lu-Mo-Ge193 $4.16.8.$ Lu-Ru(Rh, Pd)-Ge194 $4.16.9.$ Lu-Ag-Ge194 $4.16.10.$ Lu-Re-Ge195 $4.16.11.$ Lu-Os(Ir)-Ge195 $4.16.12.$ Lu-Au-Ge1955.Rare earth-f element-germanium systems196 $5.1.$ Sc-R'-Ge systems196	4	16 Ju_d ele	ement_Ge_systems	190	
4.16.2 Lu-Fe-Ge 190 $4.16.2$ Lu-Fe-Ge 191 $4.16.3$ Lu-Co-Ge 191 $4.16.3$ Lu-Ni-Ge 192 $4.16.5$ Lu-Cu-Ge 193 $4.16.5$ Lu-Nb-Ge 193 $4.16.5$ Lu-Nb-Ge 193 $4.16.7$ Lu-Mo-Ge 193 $4.16.8$ Lu-Ru(Rh, Pd)-Ge 194 $4.16.9$ Lu-Ag-Ge 194 $4.16.10$ Lu-Re-Ge 195 $4.16.11$ Lu-Os(Ir)-Ge 195 $4.16.12$ Lu-Au-Ge 195 $5.$ Rare earth-f element-germanium systems 196 $5.1.$ Sc-R'-Ge systems 196	ч.	4 16 1	Lu–Mn–Ge	190	
4.16.3. Lu-Co-Ge 191 $4.16.3.$ Lu-Co-Ge 191 $4.16.3.$ Lu-Ni-Ge 192 $4.16.4.$ Lu-Ni-Ge 193 $4.16.5.$ Lu-Cu-Ge 193 $4.16.5.$ Lu-Nb-Ge 193 $4.16.5.$ Lu-Nb-Ge 193 $4.16.7.$ Lu-Mo-Ge 193 $4.16.8.$ Lu-Ru(Rh, Pd)-Ge 194 $4.16.9.$ Lu-Ag-Ge 194 $4.16.10.$ Lu-Re-Ge 195 $4.16.11.$ Lu-Os(Ir)-Ge 195 $4.16.12.$ Lu-Au-Ge 195 $5.$ Rare earth-f element-germanium systems 196 $5.1.$ Sc-R'-Ge systems 196		4.16.2	Lu–Fe–Ge	190	
$\begin{array}{cccccccccccccccccccccccccccccccccccc$		4 16 3	Lu-Co-Ge	191	
4.16.5. Lu-Cu-Ge 192 4.16.5. Lu-Cu-Ge 193 4.16.5. Lu-Nb-Ge 193 4.16.7. Lu-Mo-Ge 193 4.16.8. Lu-Ru(Rh, Pd)-Ge 194 4.16.9. Lu-Ag-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4 16 4	Lu-Ni-Ge	192	
4.16.5. Lu -Nb-Ge 193 4.16.6. Lu-Nb-Ge 193 4.16.7. Lu-Mo-Ge 193 4.16.8. Lu-Ru(Rh, Pd)-Ge 194 4.16.9. Lu-Ag-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 4.16.12. Lu-Au-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4 16 5	Lu-Cu-Ge	192	
4.16.7. Lu-Mo-Ge 193 4.16.7. Lu-Mo-Ge 193 4.16.8. Lu-Ru(Rh, Pd)-Ge 194 4.16.9. Lu-Ag-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 4.16.12. Lu-Au-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4.16.5.	Lu_Nh_Ge	193	
4.16.7. Lu -Ru (Rh, Pd)-Ge 193 4.16.8. Lu-Ru (Rh, Pd)-Ge 194 4.16.9. Lu-Ag-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 4.16.12. Lu-Au-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4 16 7	Lu-Mo-Ge	193	
4.16.9. Lu-Ag-Ge 194 4.16.9. Lu-Ag-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 4.16.12. Lu-Au-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4.16.8	Lu-Ru(Rh Pd)_Ge	194	
4.16.0. Lu-Re-Ge 194 4.16.10. Lu-Re-Ge 195 4.16.11. Lu-Os(Ir)-Ge 195 4.16.12. Lu-Au-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4 16 0	Lu-Ao-Ge	194	
4.16.10. Lu -Osc 195 4.16.11. Lu-Os(Ir)-Ge 195 4.16.12. Lu-Au-Ge 195 5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4 16 10	Lu-Re-Ge	195	
4.16.11.Lu-Sul-Ge1955. Rare earth-f element-germanium systems1965.1.Sc-R'-Ge systems196		4 16 11	Lu IV-OC Lu-Os(Ir)-Ge	195	
5. Rare earth-f element-germanium systems 196 5.1. Sc-R'-Ge systems 196		4 16 12	Lu-Au-Ge	195	
5.1. Sc-R'-Ge systems 196	5 P	are earth_f e	lement_germanium systems	196	
	J. K	$51 \text{ Sc} - \mathbb{R}' - \mathbb{C}$	ie systems	196	

	5.1.1. Sc–Y–Ge	196
	5.1.2. Sc-La-Ge	196
	5.1.3. Sc-Ce-Ge	197
	5.1.4. Sc-Pr-Ge	197
	5.1.5. Sc-Nd-Ge	198
	5.1.6. Sc-Sm-Ge	198
	5.1.7. Sc-Eu-Ge	199
	5.1.8. Sc-Gd-Ge	199
	5.1.9. Sc-Tb-Ge	199
	5.1.10. ScDy-Ge	199
5.2	Y-R'-Ge systems	200
	52.1. Y-Ce-Ge	200
53	La-R'-Ge systems	201
5.5.	531 La-Ce-Ge	201
	532 La-Gd-Ge	201
5 1	$C_{a} \mathbf{P}'$ C_{a} systems	201
5.4.	5.4.1 Co. Gd. Go	202
	5.4.2 Co Dr. Go	202
	5.4.2. Ce-Dy-Ge	202
	5.4.4. On En Ca	202
	5.4.4. Ce-Er-Ge	203
	5.4.5. Ce-Im-Ge	203
	5.4.6. Ce-Lu-Ge	203
5.5.	Sm–R'–Ge systems	204
	5.5.1. Sm-Lu-Ge	204
5.6.	Dy–R′–Ge systems	204
	5.6.1. Dy-Ho-Ge	204
5.7.	Er–R′–Ge systems	204
	5.7.1. ErTmGe	204
Discu	ssion	204
6.1.	Peculiarities of the interactions in the	
	R-s element-Ge systems	204
	6.1.1. R-Li-Ge systems	204
	6.1.2. R-Mg-Ge	206
6.2.	Peculiarities of the interactions in the	
	R-p element-Ge systems	206
	6.2.1. R-B-Ge systems	206
	6.2.2. R-Al-Ge systems	206
	6.2.3. R-Ga(In, C)-Ge systems	207
	6.2.4. R-Si-Ge systems	207
6.3.	Peculiarities of the interactions in the	
	R-d element-Ge systems	207
	6.3.1. R-Fe-Ge systems	207
	6.3.2. R-Co-Ge systems	208
	6.3.3. R-Ni-Ge systems	209
	6.3.4. R-Cu(Ag, Au)-Ge systems	212
	6.3.5. R-platinum metals-Ge	
	systems	213
6.4.	Peculiarities of the interactions in the	
	R-R'-Ge systems	214
Refer	ences	216

Symbols and abbreviations

a, b, c	Unit cell dimensions (in nm)	X_{R}	Electronegativity of the R component
at.%	Composition in atomic percent	α, β, γ	unit cell angles (in degrees)
h	Hours	~	Precedes the composition formula of a
М	s-, p-, d-, f-element		compound to indicate that the composition
0	Orthorhombic structure		is given approximately
R, R′	Rare-earth metal, Y, Sc, and the lanthanides		
r _R	Atomic radius of the R component		
Т	Tetragonal structure		
x	indicates variable component contents, when it is used as index in compound compositional formula. The expression N-x (where N is a number) means N minus x, with the x value given in the text		

1. Introduction

The aim of this chapter is to systematize the current knowledge concerning phase diagrams and crystal structures of ternary metal germanides with the R elements ($R \equiv Sc$, Y, and the lanthanides). The isothermal sections for the ternary R–s, p, d, f element–Ge systems have been extensively studied in recent years by the researchers at the Inorganic Chemistry Department at L'viv University. The crystal structure of ternary compounds has been investigated by various groups of authors. The present status of information on phase diagrams and formation of rare-earth metal germanides is summarized in tables 1, 2 and 3.

This review consists of six sections. Sections 2–5 review the literature published on the systems, i.e., isothermal sections and crystallographic characteristics of ternary compounds, and outline the experimental methods that have been utilized. All lattice parameter values in this chapter are reported in nm units. The literature was searched back to the year 1966.

The phase diagrams of R-M-Ge systems presented in the following sections are listed in the order of Mendeleyevs Table, and divided into four major groups:

- (a) R-s element-Ge systems. In this group, lithium-containing ternary systems are the most studied (see table 1).
- (b) R-p element-Ge systems. As one can see from table 1, information on these systems is still scarce. Phase diagrams have been investigated for only a few ternary R-M-Ge combinations.
- (c) R-d element-Ge systems. Phase diagrams have been established for a large number of possible combinations, and crystal structures have been determined for a majority of compounds observed (table 2).

Table 1	mation of ternary compounds and phase equilibria within ternary R-s,p element-Ge systems ^a
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Na																
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has been established; a solid triangle indicates that a partial isothermal section has been established.

P.S. SALAMAKHA et al.

 Table 3

 Formation of ternary compounds and phase equilibria within ternary R-R'-Ge systems^a



^a The number in a table cell corresponds to the number of ternary germanide compounds observed; a solid square indicates that a complete isothermal section has been established.

(d) R-f element-Ge systems. Isothermal sections were constructed for a small number of ternary R-R'-Ge systems (table 3).

The general features and tendencies in the R-s, p, d, f element-Ge systems are discussed in sect. 6.

A detailed description of the structure types and crystal chemistry of ternary germanides will found in the next chapter (174) of this volume; the physical properties of ternary germanides are not included in the present review.

2. Rare-earth-s element-germanium systems

2.1. R-Li-Ge systems

2.1.1. Sc-Li-Ge

The only piece of information available on the interaction of components in the Sc-Li-Ge system is due to the work of Grund (1985) who identified and characterized by X-ray powder diffraction the compound ScLiGe (MgAgAs type, a=0.6407). Sample was obtained by heating the mixture of elements in the ratio 1:2:1 in a Ta crucible which was placed into an argon filled quartz ampoule. The heating schedule was 2 to 4 h at 770 K followed by 9 to 12 h at 1070 K. The resulting alloy was not single phase ScLiGe, the other phases were not identified.

9

2.1.2. *Y–Li–Ge*

No ternary phase diagram exists for the Y-Li-Ge system; however the formation of three ternary compounds has been reported by Czybulka et al. (1979), Pavlyuk et al. (1990) and Pavlyuk (1993).

YLiGe was found to adopt a ZrNiAl type with lattice parameters a = 0.7065, c = 0.4233 (Czybulka et al. 1979). The measured and X-ray-derived densities were 4.56 g cm^{-3} and 4.58 g cm^{-3} , respectively. The alloy was prepared by heating the elements in the stoichiometric ratio 1:2:1 in a Ta crucible under dry Ar to a temperature above 1000 K. The sample was annealed under unspecified conditions until only YLiGe and excess Li were detected by X-ray analysis. The stoichiometry was confirmed by chemical analysis (33.3 at.% Y, 32.0 at.% Li and 34.7 at.% Ge). The purity of the starting components is unstated.

Y₄LiGe₄ was found to adopt the Tm₄LiGe₄ type (a=0.7144, b=1.4799, c=0.7757; X-ray powder diffraction) by Pavlyuk et al. (1990). Samples were arc melted from the elements (Y 99.90 at.%, Li 98.2 at.%, Ge 99.999 at.%) under purified Ar at a pressure of 1.01×10^5 Pa and annealed at 470 K for 240 h in a Ta container which was placed in a vacuum sealed quartz ampoule. Finally the alloy was quenched in ice-cold water.

 $Y_3Li_2Ge_3$ crystallizes with $Hf_3Ni_2Si_3$ -type structure, a = 0.4102, b = 1.0690, c = 1.4212 (Pavlyuk 1993; X-ray powder diffraction). The sample preparation procedure was the same as for Y_4LiGe_4 .

2.1.3. La–Li–Ge

No phase diagram exists at present for the ternary La-Li-Ge system; however a series of ternary compounds have been prepared and characterized by Pavlyuk et al. (1986, 1989a).

LaLiGe₂ was found to crystallize with a CaLiSi₂ type, a=0.7922, b=0.4032, c=1.0946 (Pavlyuk et al. 1986; X-ray powder diffraction). Samples were arc melted from the elements (La 99.96 at.%, Li 98.2 at.%, Ge 99.999 at.%) under purified Ar at a pressure of 1.01×10^5 Pa and annealed at 470 K for 240 h in Ta containers.

Pavlyuk et al. (1989a) investigated the crystal structure for La₂Li₂Ge₃ (La₂Li₂Ge₃ type, a=0.4487, b=1.8936, c=0.7036; X-ray powder diffraction) and for LaLi₂Ge (AlCr₂C type, a=0.4556, c=0.7759; X-ray powder diffraction) compounds. The alloys were prepared in the same manner as LaLiGe₂.

2.1.4. Ce-Li-Ge

An isothermal section of the Ce–Li–Ge system at 470 K was reported by Pavlyuk et al. (1989a) from an X-ray powder analysis of 154 alloys (fig. 1). The samples were obtained by arc melting the elements in purified argon under a pressure of 1.01×10^5 Pa and annealing at 470 K for 500 h in a Ta container. Finally the alloys were water quenched. Purity of the starting components was Ce 99.56%, Li 98.2% and Ge 99.999%. Six ternary compounds were found to exist. The immiscibility gap which exists in the Ce–Li binary system, extends in the ternary system to 17 at.% Ge.



Fig. 1. Ce-Li-Ge, isothermal section at 470 K. The dashed line indicates the liquid immiscibility gap region.

Information on the ternary phases in the Ce-Li-Ge system is due to the work of two independent groups of authors.

Schuster and Czybulka (1974) investigated the crystal structure of the CeLi₂Ge (1)¹ compound by means of X-ray powder and single-crystal analyses from samples which were obtained by melting of elements at 1270 K followed by long-term annealing at 1070 K and rapid quenching. The results of chemical analysis were Ce 24.6 at.%, Li 47.6 at.%, and Ge 27.8 at.%. This phase was found to adopt an orthorhombic structure with lattice parameters a=1.8738, b=0.6926, c=0.4519. The measured density was 5.143, in agreement with the X-ray density. At variance with these data, Pavlyuk et al. (1989a) announced the AlCr₂C type for the CeLi₂Ge alloy which was arc melted and annealed at 470 K (a=0.4537, c=0.7569; X-ray powder diffraction).

Czybulka and Schuster (1979) prepared the compound Ce₅Li₃Ge₄ by melting components, of unspecified purity, in the atomic ratio 1:2:1 and subsequently annealing for 24 h at 1150 K. The product contained the ternary compound together with a small amount of Li₂₂Ge₅ and some unreacted Li. The excess of Li was extracted chemically. Chemical analysis gave Ce 42.7 at.%, Li 25.5 at.%, and Ge 31.8 at.%. The lattice parameters were a=0.4476, b=1.8846, c=0.6947 with a measured density of 5.582 g cm⁻³ and an X-ray density (based on space group Cm2m) of 5.734 g cm⁻³. Pavlyuk et al. (1988b) observed a ternary phase with almost identical lattice parameters (a=0.44795, b=1.8846, c=0.69570) and with the composition Ce₂Li₂Ge₃ (5) (X-ray single-crystal diffraction).

The remaining four ternary compounds were prepared in the same manner as described by Pavlyuk et al. (1989a): Ce₂LiGe₆ (2), Pr₂LiGe₆ type, a = 0.4140, b = 2.1054, c = 0.4363(Pavlyuk et al. 1988b); CeLiGe₂ (3), CaLiSi₂ type, a = 0.7185, b = 0.3965, c = 1.0748

¹ Numbers in parentheses refer to corresponding locations in figures and tables.

(Pavlyuk et al. 1986); Ce₂LiGe₅ (4), Ce₂MnGe₅ type, a = 0.4360, b = 0.4197, c = 2.0711(Pavlyuk et al. 1989a); Ce₂₆Li₅Ge_{22+x} (6) x = 0.37, own structure type, a = 1.5402, c = 1.0900 (Pavlyuk et al. 1987b).

2.1.5. Pr-Li-Ge

The isothermal section for the Pr–Li–Ge system at 470 K was established by Pavlyuk (1993) and Bodak et al. (1995) (fig. 2). For sample preparation, see Ce–Li–Ge. One ternary compound, PrLiGe, was confirmed, and five ternary phases were observed for the first time. No homogeneous ranges were encountered for the ternary compounds. The liquid immiscibility region, existing in the Pr–Li binary system, extends to 17 at.% Ge in the ternary system.

Grund et al. (1986) reported the crystal structure of the PrLiGe (6) compound: ZrNiAl type, a=0.7048, c=4242. The sample was prepared by heating the elements (99.99 mass% Pr, 99.7 mass% Li, 99.999 mass% Ge) in the ratio 1:2:1 in a Ta crucible which was placed in an Ar-filled quartz ampoule. The heating schedule was 5–12 h at 850 K followed by 12–15 h at 1170 K. Excess Li was extracted from the product chemically. Chemical analysis confirmed the stoichiometry to be 33.2 at.% Pr, 34.5 at.% Li, and 32.3 at.% Ge.

Five other ternary compounds were observed and characterized by the Ukrainian group at L'viv University: Pr_2LiGe_6 (1) belongs to a new structure type, a=0.41268, b=2.10520, c=0.43455 (Pavlyuk et al. 1988a); $PrLi_2Ge$ (2) adopts $AlCr_2C$ with a=0.4499, c=0.7543 (Pavlyuk et al. 1989a); $PrLiGe_2$ (3) is of the CaLiSi₂ type, a=0.7813, b=0.3948, c=1.0695 (Pavlyuk et al. 1986); Pr_2LiGe_5 (4) crystallizes with the Ce₂MnGe₅ type, a=0.4299, b=0.4157, c=2.0597 (Pavlyuk et al. 1989a); $Pr_2Li_2Ge_3$ (5) belongs to the



Fig. 2. Pr-Li-Ge, isothermal section at 470 K. The dashed line indicates the liquid immiscibility gap region.

 $Ce_2Li_2Ge_3$ type, a=0.4422, b=1.8653, c=0.6908 (Pavlyuk et al. 1989a). The alloys for investigations were prepared in the same manner as used for the investigation of the Pr-Li-Ge isothermal section.

2.1.6. Nd-Li-Ge

Pavlyuk and Bodak (1992a) were the first to investigate the phase equilibria within the Nd–Li–Ge system at 470 K over the whole concentration region by X-ray powder diffraction from the samples which were prepared in the manner indicated in the present review in the Ce–Li–Ge section. Phase relations are characterized by the existence of five ternary compounds (fig. 3). The liquid immiscibility field, originating from the Nd– Li binary system, extends to 17 at.% Ge at higher temperatures in the ternary system.

NdLiGe (5) was found to crystallize with the ZrNiAl type with lattice parameters as a=0.7267, c=0.4351 by Czybulka et al. (1990) (X-ray diffraction). Results of chemical analysis confirmed the stoichiometry (33.3 at.% Nd, 34.1 at.% Li and 32.6 at.% Ge). The alloy was obtained by heating the elements in the ratio 1:2.5:1 in a Ta crucible under dry Ar for 12 h at 770 K followed by slow heating to 1100 K and holding at 1100 for 48 h.

The crystal structure of the NdLiGe₂ (2) compound was investigated by Pavlyuk et al. (1986). It was found to adopt the CaLiSi₂ type with lattice parameters as a=0.7728, b=0.3915, c=1.0564. For experimental details, see Nd–Li–Ge.

Pavlyuk et al. (1989a) prepared and characterized the compounds NdLi₂Ge (1), AlCr₂C type, a=0.4445, b=0.7455; Nd₂LiGe₅ (3), Ce₂MnGe₅ type, a=0.4297, b=0.4152, c=2.0378; Nd₂Li₂Ge₃ (4), Ce₂Li₂Ge₃ type, a=0.4414, b=1.8621, c=0.6892. For sample preparation, see Nd–Li–Ge.



Fig. 3. Nde-Li-Ge, isothermal section at 470 K. The dashed line indicates the liquid immiscibility gap region.

2.1.7. Sm–Li–Ge

The phase-field distribution in the ternary Sm–Li–Ge system at 470 K is characterized by existence of four ternary compounds (fig. 4) (Pavlyuk 1993, Bodak et al. 1995). No homogeneous ranges were encountered for the ternary compounds. The immiscibility gap which exists in the Sm–Li binary system, extends in the ternary system to 17 at.% Ge. The alloys were synthesized by arc melting in a purified Ar atmosphere under a pressure of 1.01×10^5 Pa using 99.89 mass% Sm, 98.2 mass% Li and 99.999 mass% Ge. The resulting buttons were annealed at 470 K for 500 h in a Ta container. Finally the alloys were water quenched.



Fig. 4. Sm-Li-Ge, isothermal section at 470 K. The dashed line indicates the liquid immiscibility gap region.

SmLiGe (4) was found to crystallize with the ZrNiAl type with a lattice parameters a=0.7192, c=0.4308 by Czybulka et al. (1990) (X-ray diffraction). Chemical analysis gave 33.5 at.% Sm, 32.3 at.% Li and 34.2 at.% Ge, confirming the stoichiometry. The alloy was obtained by heating the elements in the ratio 1:2.5:1 in a Ta crucible under dry Ar for 12 h at 770 K followed by slow heating to 1100 K and holding at 1100 K for 48 h. Pavlyuk (1989) confirmed the crystal structure and determined the lattice parameters as a=0.7193, c=0.4316.

SmLiGe₂ (1) was observed to adopt the CaLiSi₂ type, a = 0.7741, b = 0.3973, c = 1.0488 (Pavlyuk et al. 1986; X-ray diffraction). For experimental details, see Sm–Li–Ge.

Pavlyuk et al. (1989a) prepared and characterized the following compounds: Sm_2LiGe_5 (2), Ce_2MnGe_5 type, a=0.4238, b=0.4123, c=2.0287; $Sm_2Li_2Ge_3$ (3), $Ce_2Li_2Ge_3$ type, a=0.4394, b=1.8537, c=0.6860. For sample preparation, see Sm-Li-Ge.

2.1.8. *Eu–Li–Ge*

The only information available on the interaction of the components in the Eu–Li–Ge system is the formation of the EuLiGe₂ compound which was observed by Pavlyuk et al. (1986). It was reported to adopt the CaLiSi₂ type, a=0.8174, b=0.3977, c=1.0988 from X-ray powder diffraction analysis. For sample preparation, see Ce–Li–Ge.

2.1.9. Gd-Li-Ge

Figure 5 represents the isothermal section of the Gd–Li–Ge system at 470 K after Pavlyuk (1989). For sample preparation, see Ce–Li–Ge. Phase relations are characterized by the existence of three ternary compounds. The liquid immiscibility gap which exists in the Gd–Li system, extends to 22 at.% Ge in the ternary system.

Czybulka et al. (1979) reported the crystallographic characteristics for the GdLiGe compound (ZrNiAl type, a=0.7135, c=0.4285). The measured and X-ray densities were 6.17 g cm⁻³ and 6.23 g cm⁻³, respectively. The alloy was prepared by heating the elements in the stoichiometric ratio 1:2:1 in a Ta crucible under dry Ar to a temperature above 1000 K. The sample was annealed under unspecified conditions until only GdLiGe and excess Li were detected by X-ray analysis. The stoichiometry was confirmed by chemical analysis (34.0 at.% Gd, 33.2 at.% Li and 32.8 at.% Ge).

GdLiGe₂ and Gd₄LiGe₄ were found to adopt the CaLiSi₂ type (a=0.7784, b=0.3867, c=1.0416; X-ray powder diffraction) by Pavlyuk (1989) and the Tm₄LiGe₄ type (a=0.7159, b=1.4749, c=0.7713; X-ray powder diffraction) by Pavlyuk et al. (1990), respectively. For sample preparation, see Gd–Li–Ge.



Fig. 5. Gd-Li-Ge, isothermal section at 470 K. The dashed line indicates the liquid immiscibility gap region.

2.1.10. Tb--Li-Ge

Information on the interaction of terbium with lithium and germanium is due to the work of two groups of authors: Grund et al. (1986) and Pavlyuk (1993).

Grund et al. (1986) investigated the crystal structure of TbLiGe. The structure type was established as ZrNiAl with lattice parameters a=0.7083, c=0.4257 from X-ray powder diffraction analysis. The measured density was 6.44 g cm^{-3} and the X-ray density 6.42 g cm^{-3} . The sample was prepared by heating the elements (99.99 mass% Tb, 99.7 mass% Li, 99.999 mass% Ge) in the ratio 1:2:1 in a Ta crucible which was placed in an Ar-filled quartz ampoule. The heating schedule was 5-12 h at 850 K followed by 12-15 h at 1170 K. Excess Li was extracted from the product chemically. Chemical analysis confirmed the stoichiometry to be 32.5 at.% Tb, 34.1 at.% Li and 33.4 at.% Ge.

Two more compounds were observed and characterized by Pavlyuk (1993): Tb₄LiGe₄ with the Tm₄LiGe₄ type, a=0.7079, b=1.4682, c=0.7699 (X-ray powder diffraction) and Tb₃Li₂Ge₃ with the Hf₃Ni₂Si₃ type, a=0.4107, b=1.0740, c=1.4198 (X-ray powder diffraction). For experimental details, see Ce–Li–Ge.

2.1.11. *Dy–Li–Ge*

Little information exists on the Dy-Li-Ge system, however three ternary compounds were found and characterized.

Grund et al. (1986) reported the crystal structure of the DyLiGe compound: ZrNiAl type, a = 0.7048, c = 0.4242. The measured density was 6.46 g cm⁻³ and the X-ray density 6.61 g cm⁻³. Results of chemical analysis confirmed the stoichiometry to be 33.2 at.% Dy, 34.5 at.% Li and 32.3 at.% Ge. For sample preparation, see Tb–Li–Ge.

Two more compounds were observed and characterized by Pavlyuk (1993): Dy₄LiGe₄ with the Tm₄LiGe₄ type, a=0.7064, b=1.4654, c=0.7681 (X-ray powder diffraction) and Dy₃Li₂Ge₃ with the Hf₃Ni₂Si₃ type, a=0.4097, b=1.0602, c=1.4121 (X-ray powder diffraction). For experimental details, see Ce–Li–Ge.

2.1.12. Ho-Li-Ge

Phase relations have been established for the ternary Ho–Li–Ge system at 470 K by Pavlyuk (1993) (fig. 6); seven ternary compounds have been observed and characterized. The immiscibility gap which exists in the Ho–Li binary system, extends in the ternary system to 17 at.% Ge. For experimental details, see Ce–Li–Ge.

From the preliminary investigation of the interaction of holmium with lithium and germanium, HoLiGe was found to crystallize with ZrNiAl type with lattice parameters a=0.7036, c=0.4241 by Czybulka et al. (1990) (X-ray diffraction). Chemical analysis gave 33.4 at.% Ho, 34.2 at.% Li and 32.4 at.% Ge. The alloy was obtained by heating the elements in the ratio 1:2.5:1 in a Ta crucible under dry Ar for 12 h at 770 K followed by slow heating to 1100 K and holding at 1100 K for 48 h.

Investigating the phase equilibria in the ternary Ho–Li–Ge system, Pavlyuk (1993) observed and characterized three ternary compounds: Ho₄LiGe₄ was found to adopt a Tm₄LiGe₄ type, a=0.7039, b=1.4649, c=0.7674 (X-ray powder diffraction); Ho₃Li₂Ge₃



Fig. 6. Ho-Li-Ge, isothermal section at 470 K. The dashed line indicates the liquid immiscibility gap region.

was reported to crystallize with the Hf₃Ni₂Si₃ type, a=0.4003, b=1.0509, c=1.4097 (X-ray powder diffraction); TmLi_{1-x}Ge₂ type was announced for the HoLi_{1-x}Ge₂ compound, a=0.4017, b=0.8126, c=0.3881, $\gamma=104.24^{\circ}$. Three more ternary compounds with an unknown structure were observed by Pavlyuk (1993), HoLi₆Ge₃, HoLi₄Ge₅ and Ho₂Li₅Ge₃. For experimental details, see Ce–Li–Ge.

2.1.13. Er-Li-Ge

A partial isothermal section for the Er–Li–Ge system was constructed by Pavlyuk (1993); four ternary compounds were found to exist (fig. 7). For sample preparation, see Ce–Li–Ge.

ErLiGe (2) was found to crystallize with a ZrNiAl type with lattice parameters a = 0.7005, c = 0.4214 (Pavlyuk 1989; Pavlyuk et al. 1991a) from X-ray powder diffraction of arc melted in a purified Ar atmosphere under a pressure of 1.01×10^5 Pa samples which were annealed in Ta containers at 470 K for 240 h. Purity of the starting components was 99.82 mass% Er, 98.2 mass% Li and 99.999 mass% Ge. Czybulka et al. (1990) confirmed the crystal structure for the compound of equiatomic composition, ZrNiAl type, a=0.6985, c=0.4219 (X-ray single-crystal data). Chemical analysis gave 33.6 at.% Er, 32.4 at.% Li and 34.0 at.% Ge. For sample preparation, see Ho–Li–Ge.

Pavlyuk et al. (1990) reported on the crystal structure investigation for the Er_4LiGe_4 (4) compound, Tm_4LiGe_4 type, a=0.7031, b=1.4555, c=0.7664 (X-ray powder diffraction). For sample preparation, see Er-Li-Ge system after Pavlyuk (1989) and Pavlyuk et al. (1991a).

Two more ternary compounds were observed and characterized by Pavlyuk (1993): $Er_3Li_2Ge_3$ (3) was reported to crystallize with the $Hf_3Ni_2Si_3$ type, a=0.4001, b=



Fig. 7. Er–Li–Ge, partial isothermal section at 470 K (30–70 at.% Ge).

1.0498, c = 1.4091 (X-ray powder diffraction); TmLi_{1-x}Ge₂ type was announced for the ErLi_{1-x}Ge₂ (1) compound, a = 0.4007, b = 0.8101, c = 0.3876, $\gamma = 104.24^{\circ}$. For experimental details, see Er-Li-Ge after Pavlyuk (1989) and Pavlyuk et al. (1991a).

2.1.14. Tm-Li-Ge

The phase diagram for the Tm-Li-Ge system was constructed by Pavlyuk (1989) (fig. 8). Phase relations are characterized by existence of four ternary compounds. No



Fig. 8. Tm-Li-Ge, isothermal section at 470 K. The dashed line indicates the liquid immiscibility gap region.

homogeneity regions were observed for the ternary phases. The liquid immiscibility gap which originates from the Tm–Li binary system, stretches to 23 at.% Ge in the ternary system. For sample preparation, see Ce–Li–Ge system.

The crystal structure for four ternary compounds was established by the Ukrainian group at L'viv University: TmLi_{1-x}Ge₂ (1) crystallizes with its own structure type, a = 0.4008, b = 0.8123, c = 0.3875, $\gamma = 104.24^{\circ}$ (Pavlyuk et al. 1991b; X-ray single-crystal data); TmLiGe (2) belongs to the ZrNiAl type, a = 0.6917, c = 0.4813 (Pavlyuk et al. 1991a; X-ray powder diffraction); Tm₃Li₂Ge₃ (3) adopts the Hf₃Ni₂Si₃ type, a = 0.3990, b = 1.0506, c = 1.4090 (Pavlyuk and Bodak 1992b); Tm₄LiGe₄ (4) represents a new type of structure, a = 0.7013, b = 1.4429, c = 0.7524 (Pavlyuk et al. 1990; X-ray single-crystal diffraction data). For experimental details, see Ce–Li–Ge.

2.1.15. Yb-Li-Ge

The phase-field distribution in the ternary Yb–Li–Ge system at 470 K is characterized by existence of four ternary compounds (fig. 9) (Pavlyuk 1993 and Bodak et al. 1995). No homogeneous ranges were encountered for the ternary compounds. The immiscibility gap which exists in the Yb–Li binary system, extends in the ternary system to 17 at.% Ge. The alloys were synthesized by arc melting in a purified Ar atmosphere under a pressure of 1.01×10^5 Pa. The resulting buttons were annealed at 470 K for 500 h in a Ta container which were placed in the evacuated vacuum sealed quartz tube. Finally the alloys were quenched in ice cold water. The purity of the starting materials was Yb 99.82 mass%, Li 98.2 mass% and Ge 99.999 mass%.

Grund et al. (1986) reported the crystal structure of the YbLiGe (1) compound: ZrNiAl type, a=0.6939, c=4183. The measured density was 7.18 g cm⁻³ and the X-ray density 7.21 g cm⁻³. Results of chemical analysis confirmed the stoichiometry and gave



Fig. 9. Yb–Li–Ge, partial isothermal section at 470 K (30–70 at.% Ge).

33.6 at.% Yb, 33.2 at.% Li and 33.2 at.% Ge. For sample preparation, see Tb–Li–Ge. The crystal structure was confirmed by Pavlyuk (1993) and Bodak et al. (1995): a=0.6944, c=0.4190.

The results of X-ray single-crystal investigation for three other compounds are the following: Yb₈LiGe₁₃ (2) belongs to a new structure type, a=1.1317, b=1.5577, c=1.0817, $\gamma=106.24^{\circ}$ (Pavlyuk et al. 1987a); Yb₅Li₄Ge₄ (3) crystallizes with the Nb₅Cu₄Si₄ type, a=1.1210, c=0.43698 (Pavlyuk et al. 1989b); Yb₄LiGe₄ (4) adopts the Tm₄LiGe₄ type, a=0.701, b=1.441, c=0.753 (Pavlyuk et al. 1990). The samples were prepared in the same manner as the alloys for the investigations of the Yb–Li–Ge phase diagram.

2.1.16. Lu-Li-Ge

The phase diagram for the Lu–Li–Ge system was constructed by Pavlyuk (1993) (fig. 10). The phase relations are characterized by existence of four ternary compounds. No homogeneity regions were observed for the ternary phases. The liquid immiscibility gap which originates from the Lu–Li binary system, stretches to 23 at.% Ge in the ternary system. For sample preparation, see Ce–Li–Ge.

The crystal structure for four ternary compounds was established by the Ukrainian group at L'viv University: $\text{LuLi}_{1-x}\text{Ge}_2$ (1) crystallizes with the $\text{TmLi}_{1-x}\text{Ge}_2$ structure type, a = 0.3988, b = 0.8019, c = 0.3867, $\gamma = 104.2^{\circ}$ (Pavlyuk et al. 1991b; X-ray powder diffraction); LuLiGe (2) belongs to the ZrNiAl type, a = 0.6933, c = 0.4200 (Pavlyuk et al. 1991a; X-ray powder diffraction); Lu_3\text{Li}_2\text{Ge}_3 (3) adopts the Hf₃Ni₂Si₃ type, a = 0.3959, b = 1.0475, c = 1.4051 (Pavlyuk and Bodak 1992b); Lu₄LiGe₄ (4) has the Tm₄LiGe₄ type of structure, a = 0.7000, b = 1.4322, c = 0.7524 (Pavlyuk et al. 1990; X-ray powder diffraction data). For experimental details, see Ce–Li–Ge.



Fig. 10. Lu-Li-Ge, isothermal section at 470 K. The dashed line indicates the liquid immiscibility gap region.

2.2. R-Mg-Ge systems

2.2.1. Eu–Mg–Ge

The information on the interaction of the components in the Eu-Mg-Ge system is due to Zmii et al. (1973) and Merlo et al. (1993).

Zmii et al. (1973) investigated the crystal structures of EuMg₃Ge₃ compound (own structure type, a=0.4485, b=3.060, c=0.4485; X-ray single-crystal diffraction).

Merlo et al. (1993) synthesized EuMgGe compound and established its crystal structure as the TiNiSi type, a = 0.7756, b = 0.4580, c = 0.8444 from X-ray powder diffraction. The alloy was obtained from metals with a purity of 99% for europium, and 99.999% for magnesium and germanium. The proper amounts of constituent elements were placed in sealed tantalum crucibles, which were arc welded under argon, melted in an induction furnace and annealed for 1 month at 870 K.

2.2.2. Yb-Mg-Ge

Merlo et al. (1993) investigated the crystal structure of YbMgGe compound by the X-ray single-crystal method. It was found to adopt the TiNiSi type, a=0.7474, b=0.4436, c=0.8343. The sample was synthesized in the same manner as EuMgGe.

3. Rare-earth-p element-germanium systems

3.1. R-B-Ge systems

3.1.1. *Y*–*B*–*Ge*

The isothermal section of the Y–B–Ge system at 1070 K (fig. 11) was investigated by Marko et al. (1978) using X-ray powder analysis of samples prepared by arc melting solid pieces of yttrium and germanium with compacted powder of boron. The melted buttons were then annealed in evacuated quartz tubes at 1070 K. No ternary compounds were observed.

3.1.2. *La–B–Ge*

An early investigation of the La–B–Ge system reported on the existence of solid solution of boron in the binary La₅Ge₃ compound which was observed by X-ray methods (Mayer and Felner 1974). Samples were obtained by heating of mixture of starting components up to 1870 K in the He atmosphere in tantalum crucibles. The phase relations in the complete isothermal section at 970 K have been determined by Marko et al. (1978). For sample preparation, see Y–B–Ge. Phase relations are characterized by the absence of ternary compounds (fig. 12). No solubility of boron in the La₅Ge₃ compound has been observed.



3.1.3. Ce–B–Ge

Phase relations in the isothermal section at 870 K have been determined by Marko and Kuz'ma (1979) from X-ray powder diffraction analysis (fig. 13). For sample preparation, see Y–B–Ge. No ternary compounds have been found. Mutual solid solubilities of the binary compounds were found to be negligible.



Fig. 13. Ce–B–Ge, isothermal section at 870 K.

3.1.4. Nd–B–Ge

No phase diagram exists for the Nd–B–Ge system, however the solubility of boron in the Nd_5Ge_3 compound has been studied by means of X-ray diffraction (Mayer and Felner 1974). The limits of solid solution have not been reported. Samples were obtained by heating of mixture of starting components up to 1870 K in the He atmosphere in Ta crucibles.

3.1.5. Gd-B-Ge

The only information on the Gd–B–Ge system is due to Mayer and Felner (1974) who investigated the solubility of boron in the Gd_5Ge_3 compound by means of X-ray diffraction. The limits of solid solution have not been indicated. For sample preparation, see La–B–Ge.

3.1.6. *Tb*–*B*–*Ge*

No ternary phase diagram exists for the Tb–B–Ge system; however the formation of a solid solution originating at the binary Tb_5Ge_3 compound has been observed (Mayer and Felner 1974). The maximum concentration of boron in Tb_5Ge_3 has not been shown. For experimental details, see La–B–Ge.

3.1.7. *Dy*–*B*–*Ge*

Solubility of boron in the Dy₅Ge₃ compound has been studied by X-ray methods (Mayer and Felner 1974). For experimental details, see La–B–Ge.

22

3.2. *R*–*Al*–*Ge systems*

3.2.1. Sc-Al-Ge

No phase diagram exists for the Sc–Al–Ge system, however the formation of $Sc_{11}Al_2Ge_8$ compound has been reported by Zhao et al. (1991). It was found to crystallize with a new ordered variant of the Ho₁₁Ge₁₀ type with Al atoms substituting for Ge atoms on one crystallographic site. The lattice parameters are a=1.0419, c=1.4974. A single crystal was isolated from a sample which was arc melted in an argon atmosphere. Purity of starting components was 99.99 mass% for Sc, Al and Ge.

The same group of authors observed and characterized the ScAlGe compound, YAlGe type, a=0.3934, b=0.9928, c=0.5519 (Zhao and Parthé 1990; X-ray powder diffraction).

3.2.2. Y-Al-Ge

Figure 14 represents the partial isothermal section of the Y–Al–Ge system at 770 K after Muravyeva et al. (1971). Three ternary compounds were found to exist from X-ray phase analysis of alloys prepared by arc melting the proper amounts of pure components in an argon atmosphere. The resulting buttons were annealed for two weeks at 770 K and finally quenched in ice-cold water. Purity of starting components was greater than 99.9 mass%.

Muravyeva et al. (1971) reported on the crystal structure investigation for the $YAl_{1.7-2.2}Ge_{2.3-1.8}$ (1) (CaAl₂Si₂type, a=0.4196-0.4196, b=0.6702-0.6775; X-ray powder diffraction).

The YAl_{0.9-1.3}Ge_{1.1-0.7} compound (3) was claimed by Yanson (1975) to adopt the DyAlGe type (Cmc2₁ space group) at the equiatomic composition with lattice parameters a=0.4200, b=1.062, c=0.5908 (X-ray powder diffraction data). At variance with these data, Zhao and Parthé (1990) announced the YAlGe type with Cmcm space



Fig. 14. Y-Al-Ge, partial isothermal section at 770 K (0-33 at.% Y).

group and lattice parameters a = 0.40504, b = 1.04440, c = 0.57646 (X-ray single-crystal diffraction).

 Y_3AlGe_6 (2) has a hexagonal lattice with unknown unit cell dimensions (Yanson 1975).

3.2.3. La-Al-Ge

Phase equilibria in the partial isothermal section (0-33 at.% La) at 770K have been derived by Muravyeva and Zarechnyuk (1970) by means of X-ray powder diffraction of alloys, as shown in fig. 15. For sample preparation, see Y–Al–Ge. Five ternary compounds were found to exist. LaGe₂ dissolves 13 at.% Al.

The formation of two ternary compounds was reported in the early investigations performed by Raman and Steinfink (1967): LaAl_{1.5-1.8}Ge_{0.5-0.2} (5) with AlB₂ type, a = 0.435-0.440, c = 0.442-0.440 and LaAlGe (4), α -ThSi₂ type, a = 0.4307, c = 1.472. The structure of the latter phase has been confirmed by Zhao and Parthé (1990), a = 0.4341, c = 1.4784 (X-ray powder diffraction). The alloy was prepared by arc melting under an argon atmosphere followed by annealing at 873 K for 100 h.

Muravyeva et al. (1971) observed the CaAl₂Si₂ type for the LaAl₂Ge₂ compound (2) (a=0.428, c=0.700; X-ray powder diffraction).

Two more ternary compounds which had been indicated as ~LaAlGe₃ (1) and ~LaAl_{0.8-1}Ge_{2.2-2} (3) by Muravyeva and Zarechnyuk (1970) in the course of investigation of the isothermal section, have been characterized by the researchers from Geneva University. La₂Al_{1+x}Ge_{6-x} (x=0.60) is a new structure type which is a vacancy variant of the orthorhombic SmNiGe₃ structure, a=0.8373, b=0.8833, c=1.0887, $\beta=101.34^{\circ}$ (Zhao and Parthé 1991a; X-ray single-crystal diffraction data). La₂Al₃Ge₄ was announced to crystallize with the Ba₂Cd₃Bi₄ type, a=0.6146, b=1.5194, c=0.8037 (X-ray single-



Fig. 15. La-Al-Ge, partial isothermal section at 770 K (0-33 at.% La).

crystal diffraction, Zhao and Parthé 1991b). Single crystals were isolated from samples obtained by arc melting the proper amounts of pure components in an argon atmosphere (La, Al and Ge: 99.99 mass%). The weight losses were 0.4% and 0.5% for La₂Al_{1+x}Ge_{6-x} (x = 0.60) and La₂Al₃Ge₄, respectively. The alloys were annealed at 770 K for two months in an Ar-filled silica tube.

3.2.4. Ce-Al-Ge

The isothermal section of the Ce–Al–Ge system at 770 K (0–33 at.% Ce) was reported by Muravyeva and Zarechnyuk (1970) from an X-ray powder analysis of alloys prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the alloys were quenched in water. The purity of the starting components was greater than 99.9 mass%. Five ternary compounds were found to exist (fig. 16). For all of them except CeAl₂Ge₂, the formation of homogeneity regions was observed.

Information on the ternary phases in the Ce–Al–Ge system is due to the work of three independent groups of authors.

The formation of one ternary compound was reported in an early investigation performed by Raman and Steinfink (1967): CeAl_{0.5-0.6}Ge_{0.5-0.4} (5) with the AlB₂ type, a = 0.433 - 0.436, c = 0.432 - 0.429.

Muravyeva and Zarechnyuk (1970) observed the $CaAl_2Si_2$ type for the $CeAl_2Ge_2$ compound (2) (a=0.427, c=0.695; X-ray powder diffraction). For sample preparation, see above.

Three more ternary compounds which had earlier been indicated as $\sim CeAl_{0.5-0.8}Ge_{3.5-3.2}$ (1), $\sim CeAl_{0.8-1}Ge_{2.2-2}$ (3) and $CeAl_{0.7-1.2}Ge_{1.3-0.8}$ (4) by Muravyeva and Zarechnyuk (1970) during the investigation of the isothermal section, have been characterized by the group of authors from Geneva University. $Ce_2Al_{1+x}Ge_{6-x}$ (1) was found to adopt the



Fig. 16. Ce–Al–Ge, partial isothermal section at 770 K (0–33 at.% Ce).
La₂Al_{1+x}Ge_{6-x}-type structure, a=0.8292, b=0.8691, c=1.0739, $\beta=101.15^{\circ}$ (Zhao and Parthé 1991a; X-ray powder diffraction data). Ce₂Al₃Ge₄ (3) was announced to crystallize with the Ba₂Cd₃Bi₄ type, a=0.60935, b=1.5061, c=0.7974 (X-ray powder diffraction; Zhao and Parthé 1991b). α -ThSi₂-type structure was observed for the CeAlGe (4) compound, a=0.42889, c=1.4721 (X-ray powder diffraction, Zhao and Parthé 1990). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Ce, Al and Ge: 99.99 mass%). The alloys were annealed at 770 K for two months in an Ar-filled silica tube.

3.2.5. Pr-Al-Ge

No phase diagram is available for the ternary Pr–Al–Ge system, however information on the formation and crystal structure of four compounds exists due to the work of the Ukrainian scientific group from L'viv University as well as of the group of authors from Geneva University.

PrAlGe belongs to the α -ThSi₂ type, a = 0.4273, c = 1.463 (Ryabokon' 1974; X-ray powder diffraction). Zhao and Parthé (1990) confirmed the structure for the equiatomic compound, a = 0.42642, b = 1.4685 (X-ray powder diffraction). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Pr, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for 100 h in a silica tube.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the PrAl₂Ge₂ compound (a = 0.4264, c = 0.6896; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

Two more ternary compounds have been observed and characterized by Zhao and Parthé (1991a,b). $Pr_2Al_{1+x}Ge_{6-x}$ was found to adopt the $La_2Al_{1+x}Ge_{6-x}$ type structure, a=0.8244, b=0.8630, c=1.0711, $\beta=101.09^{\circ}$ (Zhao and Parthé 1991a; X-ray powder diffraction data). $Pr_2Al_3Ge_4$ (3) was announced to crystallize with the $Ba_2Cd_3Bi_4$ type, a=0.6056, b=1.5000, c=0.7920 (X-ray powder diffraction, Zhao and Parthé 1991b). In both cases samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Pr, Al and Ge: 99.99 mass%). The alloys were annealed at 770 K for two months in an Ar-filled silica tubes.

3.2.6. Nd-Al-Ge

No phase diagram is available yet for the ternary Nd–Al–Ge system, however information on the existence and crystal structure of five compounds exists due to the work of different scientific groups.

The formation of the NdAl_{1.0-1.25}Ge_{1.0-0.75} compounds was reported in an early investigation performed by Raman and Steinfink (1967): AlB₂ type, a = 0.4298-0.4308, c = 0.4210-0.4204.

NdAlGe belongs to the α -ThSi₂ type, a=0.4272, c=1.466 (Ryabokon' 1974; X-ray powder diffraction). Zhao and Parthé (1990) confirmed the structure for the equiatomic compound, a=0.4233, b=1.4638 (X-ray powder diffraction). Samples were obtained by

arc melting the proper amounts of pure components in an argon atmosphere (Nd, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for 100 h in a silica tube.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the NdAl₂Ge₂ compound (a = 0.4265, c = 0.6827; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

Nd₂Al_{1+x}Ge_{6-x} was found to adopt the La₂Al_{1+x}Ge_{6-x}-type structure, a=0.8220, b=0.8623, c=1.0671, $\beta=101.05^{\circ}$ (Zhao and Parthé 1991a; X-ray powder diffraction data). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Nd, Al and Ge: 99.99 mass%). The alloys were annealed at 770 K for two months in an Ar-filled silica tube.

Nd₂Al₃Ge₄ was announced to crystallize with the Ba₂Cd₃Bi₄ type, a=0.6042, b=1.4965, c 0.7897 (X-ray powder diffraction, Zhao and Parthé 1991b). The sample was obtained in the same manner as indicated for the Nd₂Al_{1+x}Ge_{6-x} compound.

3.2.7. Sm-Al-Ge

No phase diagram has been derived yet for the ternary Sm-Al-Ge system, however information on the formation and crystal structure of four compounds exists due to the work of scientific groups from L'viv University and Geneva University.

SmAlGe belongs to the α -ThSi₂ type, a = 0.4188, c = 1.452 (Ryabokon' 1974; X-ray powder diffraction). Zhao and Parthé (1990) confirmed the structure for the equiatomic compound, a = 0.41957, b = 1.4588 (X-ray powder diffraction). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Sm, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for 100 h in a silica tube.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the PrAl₂Ge₂ compound (a = 0.4233, c = 0.6805; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

Two more ternary compounds have been observed and investigated by the group of authors from Geneva University. Sm₂Al_{1+x}Ge_{6-x} was found to adopt the La₂Al_{1+x}Ge_{6-x}-type structure, a = 0.8105, b = 0.8458, c = 1.0613, $\beta = 101.00^{\circ}$ (Zhao and Parthé 1991a; X-ray powder diffraction data). Sm₂Al₃Ge₄ was announced to crystallize with the Ba₂Cd₃Bi₄ type, a = 0.6007, b = 1.4921, c = 0.7820 (X-ray powder diffraction, Zhao and Parthé 1991b). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Sm, Al and Ge: 99.99 mass%). The alloys were annealed at 770 K for two months in an Ar-filled silica tube.

3.2.8. Eu–Al–Ge

Little information exists on the interaction of components in the ternary Eu-Al-Ge system. Two ternary compounds were observed and characterized.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the EuAl₂Ge₂ compound (a = 0.422, c = 0.731; X-ray powder diffraction). The alloy was prepared by arc melting the

elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

The α -ThSi₂ type was indicated for the EuAlGe compound, a=0.42000, c=1.4604 (X-ray powder diffraction, Zhao and Parthé 1990). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Eu, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for two months in a silica tube.

3.2.9. Gd-Al-Ge

Figure 17 represents the partial isothermal section of the Gd–Al–Ge system at 770 K after Zarechnyuk et al. (1981) from X-ray powder phase analysis of samples which were arc melted and annealed in evacuated quartz tubes for two weeks. Three ternary compounds were found to exist.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the GdAl₂Ge₂ (1) compound (a=0.4248, c=0.6714; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

GdAlGe (3) was found to crystallize with the α -ThSi₂ type, a=0.4152, c=1.4421 (Ryabokon' 1974; X-ray powder diffraction). The sample was arc melted and annealed at 770 K. Contrary to these data, Zhao and Parthé (1990) found two types of structure for the equiatomic composition: a compound with the α -ThSi₂ type was found to exist above 1300 K (a=0.41521, c=1.4415; X-ray powder diffraction), and YAlGe-type was realized below 1300 K (a=0.4063, b=1.0513, c=0.5801). The phase transition temperature was determined from thermal differential analysis. Samples were obtained by arc melting



Fig. 17. Gd–Al–Ge, partial isothermal section at 770 K (0–33 at.% Gd).

the proper amounts of pure components in an argon atmosphere (Gd, Al and Ge: 99.99 mass%).

At variance with the phase diagram proposed by Zarechnyuk et al. (1981), two more compounds have been characterized by the scientific group from Geneva University. $Gd_2Al_{1+x}Ge_{6-x}$ was found to adopt the $La_2Al_{1+x}Ge_{6-x}$ -type structure, a=0.8041, b=0.8351, c=1.0546, $\beta=100.81^{\circ}$ (Zhao and Parthé 1991a; X-ray powder diffraction data). $Gd_2Al_3Ge_4$ was announced to crystallize with the $Ba_2Cd_3Bi_4$ type, a=0.5948, b=1.4875, c=0.7762 (X-ray powder diffraction, Zhao and Parthé 1991b). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Gd, Al and Ge: 99.99 mass%). The alloys were annealed at 770 K for two months in an Ar-filled silica tube. These two phases are not shown in the 770 K isothermal section, fig. 17.

3.2.10. Tb-Al-Ge

No phase diagram has been derived yet for the ternary Tb-Al-Ge system, however information on the investigation of the crystal structure of three compounds exists due to the work of different scientific groups.

The TbAlGe compound was claimed by Yanson (1975) to adopt the DyAlGe type (Cmc2₁ space group) with lattice parameters as a=0.4121, b=1.052, c=0.5831 from X-ray powder diffraction of alloy which was obtained by arc melting and homogenized at 770 K. At variance with these data, Zhao and Parthé (1990) announced that this phase had the YAlGe type structure with Cmcm space group and lattice parameters a=0.4044, b=1.0434, c=0.5767 (X-ray powder diffraction). The sample was obtained by arc melting the proper amounts of pure components in an argon atmosphere (Tb, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for 100 h in a silica tube.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the TbAl₂Ge₂ compound (a= 0.424, c=0.663; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

Tb₂Al₃Ge₄ was announced to crystallize with the Ba₂Cd₃Bi₄ type, a=0.5914, b=1.4834, c 0.7720 (X-ray powder diffraction, Zhao and Parthé 1991b). The sample was obtained by arc melting the proper amounts of pure components in an argon atmosphere (Ce, Al and Ge: 99.99 mass%). The resulting alloy was annealed at 770 K for two months in an Ar-filled silica tube.

3.2.11. Dy-Al-Ge

Formation and crystal structure of three compounds have been reported in the Dy-Al-Ge system.

DyAlGe was claimed by Yanson (1975) to crystallize with a new structure type (Cmc2₁ space group) with lattice parameters a=0.4091, b=1.046, c=0.5903 (X-ray powder diffraction data) from the alloy which was synthesized by arc melting and annealed at 770 K. At variance with these data, Zhao and Parthé (1990) announced the YAlGe type for DyAlGe with Cmcm space group and lattice parameters a=0.4035, b=1.0396, c=0.5752

(X-ray powder diffraction). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Dy, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for 100 h in a silica tube.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the DyAl₂Ge₂ compound (a = 0.421, c = 0.667; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

 $Dy_2Al_3Ge_4$ was reported to crystallize with the $Ba_2Cd_3Bi_4$ type, a=0.5881, b=1.4800, c=0.7690 (X-ray powder diffraction, Zhao and Parthé 1991b). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Dy, Al and Ge: 99.99 mass%). The resulting alloy was annealed at 770 K for two months in an Arfilled silica tube.

3.2.12. *Ho–Al–Ge*

No phase diagram has been constructed for the ternary Ho–Al–Ge system, however data on the formation and crystal structure of three compounds exist due to the independent investigations of research groups from L'viv University and Geneva University.

The HoAlGe compound was claimed by Yanson (1975) to adopt a DyAlGe type (Cmc2₁ space group) with lattice parameters a=0.4123, b=1.040, c=0.5827 (X-ray powder diffraction data). For sample preparation, see Dy-Al-Ge. At variance with these data, Zhao and Parthé (1990) found the YAlGe type structure with Cmcm space group and lattice parameters a=0.4031, b=1.0357, c=0.5729 for this alloy (X-ray powder diffraction). Samples were obtained by arc melting the proper amounts of pure components in an argon atmosphere (Ho, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for 100 h in a silica tube.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the HoAl₂Ge₂ compound (a= 0.4196, c= 0.6668; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

Ho₂Al₃Ge₄ was announced to crystallize with the Ba₂Cd₃Bi₄ type, a=0.5865, b=1.4765, $c \ 0.7657$ (X-ray powder diffraction; Zhao and Parthé 1991b). The sample was obtained by arc melting the proper amounts of pure components in an argon atmosphere (Ho, Al and Ge: 99.99 mass%). The resulting alloy was annealed at 770 K for two months in an Ar-filled silica tube.

3.2.13. Er-Al-Ge

Formation and crystal structure of three compounds have been reported in the Er-Al-Ge system.

The ErAlGe compound was claimed by Yanson (1975) to adopt a DyAlGe type (Cmc2₁ space group) with lattice parameters a=0.4101, b=1.034, c=0.5840 (X-ray powder diffraction data). The alloy was synthesized in the same manner as DyAlGe. At variance with these data, Zhao and Parthé (1990) found that this phase had the YAlGe type

structure with Cmcm space group and lattice parameters a = 0.4010, b = 1.0314, c = 0.5704 (X-ray powder diffraction). Samples were obtained by arc melting the proper amounts of the pure components in an argon atmosphere (Er, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for 100 h in a silica tube.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the ErAl₂Ge₂ compound (a = 0.4184, c = 0.6662; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

 $Er_2Al_3Ge_4$ was announced to crystallize with a $Ba_2Cd_3Bi_4$ type, a=0.5838, b=1.4747, c=0.7637 (X-ray powder diffraction; Zhao and Parthé 1991b). Samples were obtained by arc melting the appropriate amounts of the pure components in an argon atmosphere (Er, Al and Ge: 99.99 mass%). The resulting alloy was annealed at 770 K for two months in an Ar-filled silica tube.

3.2.14. Tm-Al-Ge

Little information exists on the ternary Tm-Al-Ge system; however two ternary compounds were observed and characterized.

Contrary to the data presented by Yanson (1975) for the TmAlGe compound (DyAlGe type, a=0.402, b=1.033, c=0.5865; X-ray powder diffraction), Zhao and Parthé (1990) indicated the YAlGe type for the compound of equiatomic composition (Cmcm space group, a=0.4010, b=1.0314, c=0.5704; X-ray powder diffraction). Samples were obtained by arc melting the proper amounts of the pure components in an argon atmosphere (Tm, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for 100 h in a silica tube.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the TmAl₂Ge₂ compound (a = 0.4184, c = 0.6662; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks, and finally quenched in water. The purity of the starting components was greater than 99.9 mass%.

3.2.15. *Yb–Al–Ge*

Formation and crystal structure of three compounds have been reported in the Yb–Al– Ge system.

The YbAlGe compound was claimed by Yanson (1975) to adopt a DyAlGe type (Cmc2₁ space group) with lattice parameters a = 0.4307, b = 1.057, c = 0.5935. For experimental details, see Dy-Al-Ge.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the YbAl₂Ge₂ compound (a = 0.4118, c = 0.705; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

Yb₇Al₅Ge₈ was reported by Zhao and Parthé (1991c) to crystallize with a new structure type, a=1.5958, b=0.42871, c=1.2611, $\beta=95.78^{\circ}$ (X-ray single-crystal data). A single crystal was obtained from the as-cast sample which was prepared by reaction of the pure

metals in a high-frequency furnace under an argon atmosphere (Yb 99.9, Al 99.99 and Ge 99.99 mass%). The reaction was observed at a temperature of about 773 K and the sample was left in the furnace at 1000 K for half an hour.

3.2.16. Lu–Al–Ge

Little information exists on the ternary Lu-Al-Ge system; however two ternary compounds were observed and characterized.

Zhao and Parthé (1990) indicated the YAIGe type structure for the LuAIGe compound (Cmcm space group, a=0.3999, b=1.0227, c=0.5659; X-ray powder diffraction). Samples were obtained by arc melting the proper amounts of the pure components in an argon atmosphere (Lu, Al and Ge: 99.99 mass%). The alloy was annealed at 870 K for 100 h in a silica tube.

Zarechnyuk et al. (1970) observed the CaAl₂Si₂ type for the LuAl₂Ge₂ compound (a = 0.417, c = 0.663; X-ray powder diffraction). The alloy was prepared by arc melting the elements in purified argon and annealing at 770 K for two weeks. Finally the sample was quenched in water. The purity of the starting components was greater than 99.9 mass%.

3.3. R-Ga-Ge systems

3.3.1. *Y*–*Ga*–*Ge*

Investigations in the ternary system Y–Ga–Ge are due to Belyavina et al. (1996). Five ternary compounds were found to exist from X-ray powder phase analysis: $Y_{1.13}Ga_{0.5-1.0}Ge_{3.37-2.87}$ (SmNiGe₃-type structure, a=0.3984, b=2.0703, c=0.4120); $Y_2Ga_{2.70-3.60}Ge_{4.30-3.40}$ (La₂AlGe₆ type, a=0.7969, b=1.0550, c=2.0763, $\gamma=100.97^{\circ}$); $Y_{2.25}Ga_{0.67}Ge_{6.08}$ (Pr₂LiGe₆ type, a=0.3956, b=2.0763, c=0.4100); $Y_3Ga_{1.4-3.0}Ge_{3.6-2.0}$ (α -GdSi₂ type); $Y_3Ga_{3.4}Ge_{1.6}$ (α -ThSi₂ type). Samples were prepared by arc melting high purity components and annealed at 670 K.

3.3.2. Ce--Ga--Ge

While no phase diagram is available for the Ce–Ga–Ge system, X-ray phase analysis of 180 ternary alloys indicated the formation of four ternary compounds in the Ce–Ga–Ge system (Gryniv et al. 1989). Alloys were synthesized by arc melting metal ingots in an argon atmosphere followed by annealing at 870 K.

Ce₂Ga_{1.6}Ge_{5.4} was observed to crystallize with a new structure type, a=0.8664, b=0.8307, c=2.1550 (Gryniv et al. 1989). Ce₄Ga₄Ge₇ belongs to the La₄Ga₄Ge₇ type with lattice parameters a=0.8414, b=0.8620, c 3.109 (Gryniv et al. 1989). CeGaGe is reported to form the α -ThSi₂ type, a=0.4292, c=1.4518. Ce₅Ga₂Ge was found to adopt the Cr₅B₃ structure type, a=0.8019, c=1.3850 (Gryniv et al. 1989).

3.3.3. Nd–Ga–Ge

Five ternary compounds were observed and characterized for the Nd–Ga–Ge system from X-ray powder diffraction of alloys which were arc melted and annealed at 870 K (Opainych et al. 1992). Crystallographic data for these compounds are as follows:

 $Nd_2(Ga_xGe_{1-x})_7$, $Ce_2(Ga_3Ge_{1-x})_7$, $type_1 = 0.8511 - 0.8552$, b = 0.8151 - 0.863, c = 2.1210 - 0.8632.1379; Nd₄(Ga_xGe_{1-x})₁₁, x=0.33-0.43, La₄(Ga_xGe)₁₁ type, a=0.8213-0.8314, b=0.8311–0.8463, c = 0.3591-0.3600; NdGa_{1+x}Ge_{1 x}, x = 0-0.2, α -ThSi₂ type, a = 0.4240-0.26 $0.4238, c = 1.4511 - 1.4510; Nd(Ga_xGe_{1-x})_2, x = 0.75 - 0.85, AlB_2 \text{ type}, a = 0.4247 - 0.4231,$ c = 0.4245 - 0.4229; Nd₅(Ga_{0.53}Ge_{0.47})₃, Cr₅B₃ type, a = 0.7939, c = 1.3908.

3.3.4. *Gd–Ga–Ge*

Golovata et al. (1996) reported results of the X-ray powder phase analysis of alloys of Gd-Ga-Ge system at 1070 K and 670 K. Six ternary compounds were found to exist. They are GdGa_{0.32-0.55}Ge_{3.00-2.77}, Gd₂Ga_{2.34-3.58}Ge_{4.66-3.42}, GdGa_{3.00-3.09}Ge_{0.50-0.41}, $GdGa_{0,29-0,36}Ge_{1,93-1,86}$, $GdGa_{1,21-1,36}Ge_{0,82-0,67}$, and $GdGa_{0,03-0,13}Ge_{0,88-0,78}$. The crystal structure and lattice parameters were determined for two compounds by X-ray powder diffraction: GdGa_{0.32-0.55}Ge_{3.00-2.77} (SmNiGe₃ type, a = 0.4005, b = 2.0826, c = 0.4161 for $GdGa_{0,32}Ge_{3,00}$ and $Gd_2Ga_{2,34-3,58}Ge_{4,66-3,42}$ (La₂AlGe₆ type, a = 0.8182, b = 1.0812, c = 0.08120.8420, $\gamma = 100.85^{\circ}$ for GdGa_{3.15}Ge_{3.85}).

3.3.5. *Tm-Ga-Ge*

The formation of eight ternary compounds is reported for the Tm-Ga-Ge system (Gryniv and Myakush 1989) from arc-melted samples annealed at 870 K. They are: $Tm_2Ga_{0.5}Ge_{4.5}$ (new structure type, a=0.3915, b=0.4048, c=1.8209; X-ray powder diffraction), TmGa_{1.94}Ge_{0.06} (AlB₂ type, a=0.4171, c=0.3995; X-ray powder diffraction), $Tm_3(Ga_{0.5}Ge_{0.5})_5$ (new structure type, a = 0.7748, c = 1.0836; X-ray singlecrystal method), $Tm_{10}Ga_6Ge_9$ (unknown structure type), $Tm_{11}Ga_2Ge_{12}$ (unknown type), $Tm_3Ga_{3,2-2,4}Ge_{0,4-1,2}$ (unknown type), $Tm_5Ga_3Ge_2$ (unknown type), $Tm_4Ga_7Ge_9$ (unknown type).

3.4. R-In-Ge systems

No phase diagrams exist for the R–In–Ge system, however a series of ternary compounds, La₂InGe₂, have been observed and characterized by Zaremba et al. (1997) (see table 4).

Compound	Lattice paramet	ters for the R_2 ly meters (nm)	nGe ₂ compounds, Mo ₂ F	Lattice parameters (nm)		
compound	a a	c	Compound		c	
Y ₂ InGe ₂	0.7339	0.4242	Gd ₂ InGe ₂	0.7378	0.4248	
La ₂ InGe ₂	0.7664	0.4450	Tb ₂ InGe ₂	0.7337	0.4215	
Ce ₂ InGe ₂	0.7577	0.4391	Dy ₂ InGe ₂	0.7322	0.4187	
Pr ₂ InGe ₂	0.7546	0.4374	Ho ₂ InGe ₂	0.7303	0.4167	
Nd ₂ InGe ₂	0.7496	0.4342	Yb ₂ InGe ₂	0.7205	0.4294	
Sm ₂ InGe ₂	0.7445	0.4289				

Table 4

^a Source: Zaremba et al. (1997).

Alloys were synthesized by arc melting pure metals (99.9 mass% R; 99.99 mass% In and Ge) followed by annealing for 700 h at 870 K in evacuated quartz tubes. Crystal structure was investigated by the single-crystal method for the La_2InGe_2 compound, for other phases the X-ray powder method was employed.

3.5. R-C-Ge systems

The only information on the interaction of the components in the ternary R–C–Ge systems is due to Mayer and Shidlowsky (1969), who investigated the crystal structure of R_5CGe_3 compounds. They were found to form a partly filled Mn_5Si_3 type. Crystallographic characteristics of the isotypic R_5CGe_3 series are listed in table 5. The samples were synthesized by melting of the pure components in an induction furnace at 1773–1873 K.

Compound	Lattice parameters (nm)		Compound	Lattice parameters (nm)	
	a	с		a	С
Y ₅ CGe ₃	0.845	0.645	Tb ₅ CGe ₃	0.849	0.641
Ce ₅ CGe ₃	0.884	0.672	Dy ₅ CGe ₃	0.845	0.642
Pr ₅ CGe ₃	0.879	0.671	Ho ₅ CGe ₃	0.837	0.638
Nd ₅ CGe ₃	0.874	0.668	Er ₅ CGe ₃	0.834	0.637
Sm5CGe3	0.864	0.659	Tm ₅ CGe ₃	0.830	0.632
Gd₅CGe₃	0.857	0.652	Lu ₅ CGe ₃	0.823	0.626

Table 5 Lattice parameters for the R_5CGe_3 compounds, Mn_5Si_3 -type^a

^a Source: Mayer and Shidlowsky (1969).

3.6. *R–Si–Ge systems*

3.6.1. Y-Si-Ge

The isothermal section of the Y–Si–Ge phase diagram at 870 K was constructed by Muratova (1976) using X-ray powder diffraction data of arc-melted alloys annealed for 400 h. The purity of the starting components was greater than 99.90 mass%. The phase relations are characterized by the existence of two ternary compounds and by the formation of three continuous solid solutions between isostructural binary compounds: $Y_5(Si,Ge)_3$, Y(Si,Ge) and $Y_2(Si,Ge)_3$ (fig. 18). Three extended ranges of solid solutions were found to exist within the Y–Si–Ge system at 870 K, originating at Y_5Ge_4 , $Y_{11}Ge_{10}$ and YGe_2 , which dissolve 20, 15 and 37 at.% Si, respectively.

YSi_{1.4}Ge_{0.6} (1) was reported to crystallize with the α -GdSi₂ type, a=0.4044, b=0.3988, c=1.348 (Muratova 1976; X-ray powder diffraction). For the experimental procedure, see above.

 $YSi_{1.8}Ge_{0.2}$ (2) belongs to the α -ThSi₂ type, a=0.4002, c=1.336 (Muratova 1976; X-ray powder diffraction). The samples were synthesized in the same manner as that applied for the investigation of the Y-Si-Ge isothermal section.



Fig. 18. Y-Si-Ge, isothermal section at 870 K.

3.6.2. *La–Si–Ge*

The phase equilibria in the La–Si–Ge system at 870 K (fig. 19) were investigated by Muratova et al. (1974) and Bodak and Muratova (1981) by means of X-ray phase analysis of alloys which were arc melted and subsequently annealed in evacuated silica tubes for 400 h and finally quenched in water. Starting materials were La 99.79 mass%,



Fig. 19. La-Si-Ge, isothermal section at 870 K.

Si 99.9 mass% and Ge 99.99 mass%. Phase relations are characterized by the formation of continuous solid solution originating at the isotypic binary compounds LaSi and LaGe. A complete solid solution with successive changing of the tetragonal α -ThSi₂ (T) and orthorhombic α -GdSi₂ (O) structure types was also observed between LaSi_{2-x} and LaGe_{2-x}. No ternary compounds were found. La₃Ge and La₅Ge₄ dissolve 15 and 10 at.% Si. Solubilities of Ge in La₅Si₃ and La₅Si₄ were reported to be approximately 27.5 and 29.5 at.%, respectively.

3.6.3. *Ce–Si–Ge*

Investigations in the ternary system Ce–Si–Ge were performed by two different research groups, i.e. Haschke et al. (1966) and Bodak and Muratova (1979).

Phase relations in an isothermal section at 1070 K were determined by Haschke et al. (1966) by means of X-ray powder diffraction methods (fig. 20). Samples were synthesized by heating compacted mixtures of 99.9 mass% purity for a few minutes in an induction furnace slightly above the melting point. The formation of two complete solid solutions was reported: Ce(Si,Ge) and Ce(Si,Ge)_{2-x}. No ternary compounds were observed.

A partial isothermal section at 870 K within 0–50 at.% Ce is presented in fig. 21 from X-ray powder analysis of 92 alloys which were arc melted from ingots of pure metals and annealed in evacuated quartz tubes for 400 h (Bodak and Muratova 1979). The purity of the metals was greater than 99.9 mass%. A continuous solid solution with successive changing of the α -ThSi₂ (T) and α -GdSi₂ (O) structure types was observed between CeSi_{2-x} and CeGe_{2-x}. No ternary compounds were found.



Fig. 20. Ce–Si–Ge, isothermal section at 1170 K.



Fig. 21. Ce–Si–Ge, partial isothermal section at 870 K (0–40 at.% Ce).

3.6.4. *Pr–Si–Ge*

The phase relations in the Pr–Si–Ge ternary system at 873 K were investigated by Muratova and Bodak (1974) using X-ray powder analysis (fig. 22). Samples were obtained by arc melting, and homogenized at 873 K for 500 h. No ternary compounds were found, but a continuous solid solution $Pr(Si,Ge)_{2-x}$ was observed. The solubilities of germanium



Fig. 22. Pr-Si-Ge, isothermal section at 870 K.

in Pr_5Si_3 , Pr_5Si_4 and PrSi were determined as 12.5, 7 and 40 at.%, respectively, whereas Pr_3Ge and Pr_5Ge_3 dissolve 18 and 20 at.% Si, respectively.

Muratova (1974) reported on the X-ray powder investigation of the crystal structure of alloys within the homogeneity field $Pr(Si,Ge)_{2-x}$. The Ge-rich region of solid solution was found to crystallize with a tetragonal α -ThSi₂ type (T). With increasing Ge/Si exchange, a continuous transition into the orthorhombic α -GdSi₂ (O) was observed; no two-phase field was established.

3.6.5. Gd–Si–Ge

The phase equilibria in the Gd–Si–Ge system at 870 K (fig. 23) were investigated by Muratova et al. (1975) by means of X-ray phase analysis of alloys which were arc melted and subsequently annealed in evacuated silica tubes for 400 h and finally quenched in water. The purity of the starting materials was greater than 99.9 mass%. No ternary compounds were observed. Phase relations are characterized by the existence of three continuous solid solutions: $Gd(Si,Ge)_{2-x}$, $Gd_5(Si,Ge)_3$ and $Gd_2(Si,Ge)_3$. The crystal structure of $Gd(Si,Ge)_{2-x}$ solid solution was said to change with increasing Si content from α -GdSi₂ (O) type through α -ThSi₂ type (T) to α -GdSi₂ (O) type (Muratova 1974; X-ray powder diffraction). Binary compounds GdGe, GdSi and Gd₅Ge₄ dissolve 33, 10 and 8 at.% of third component respectively (Muratova et al. 1975).

During a study of the magnetic properties of alloys heat treated at 1870 K for 5 hours in the pseudobinary system $Gd_5(Si_xGe_{1-x})_4$, Holtzberg et al. (1967) report extended solubility of Si in Gd_5Ge_4 ($0.0 \le x \le 0.3$) and Ge in Gd_5Si_4 ($0.5 \le x \le 1.0$). They also



Fig. 23. Gd-Si-Ge, isothermal section at 870 K.

acknowledge the existence of the ternary intermediate phase with unidentified crystal structure extending between 0.3 < x < 0.5. These seemingly contradicting experimental results regarding the phase relations in the Gd₅Ge₄--Gd₅Si₄ pseudobinary system suggest that the Gd₅Si₄-based solid solution and the ternary phase are probably high-temperature phases, which decompose during the heat treatment between 870 K and 1870 K, and that the solid solubility of Si in Gd₅Ge₄ is strongly temperature dependent.

Pecharsky and Gschneidner (1997) investigated 12 as-cast alloys from the pseudobinary system $Gd_5(Si_xGe_{1-x})_4$ by X-ray single-crystal and powder diffraction. The Gd_5Si_4 -based solid solution where Ge statistically substitutes for Si maintains the Sm_5Ge_4 -type orthorhombic crystal structure of the binary Gd_5Si_4 compound and extends from $0.5 < x \le 1$. The Gd_5Ge_4 -based solid solution where Si statistically substitutes for Ge also maintains the Sm_5Ge_4 -type orthorhombic crystal structure of the binary Gd_5Si_4 compound and extends from $0 < x \le 0.2$. The crystal structure of the ternary phase, which exists for $0.24 \le x \le 0.5$, has been determined for the first time, and it was shown to be a monoclinically distorted derivative of orthorhombic Sm_5Ge_4 -type (P112₁/a space group, a=0.75808, b=1.4802, c=0.77799, $\gamma=93.190$) for $Gd_5Si_2Ge_2$.

4. R-d element-germanium systems

4.1. Sc-d element-Ge systems

4.1.1. Sc-V-Ge

The phase equilibria in the Sc–V–Ge system were investigated by Kotur (1987) by means of X-ray analysis of alloys which were arc melted and subsequently annealed in evacuated silica tubes for 350–650 h at 1070 K and finally quenched in water (fig. 24). Starting



Fig. 24. Sc–V–Ge, isothermal section at 870 K.

materials were Sc 99.92 mass%, V 99.9 mass% and Ge 99.99 mass%.

Two ternary compounds were observed at 1070 K: $Sc_{1-1.8}V_{5-4.2}Ge_5$ (1) with the V₆Si₅-type structure (a=0.7872-0.7850, c=0.5091-0.5157) and $Sc_2V_3Ge_4$ (2) with the Ce₂Sc₃Si₄-type structure (a=0.6614, b=1.2774, c=0.6776) (Kotur et al. 1986).

Kotur et al. (1983) reported on the preliminary X-ray single-crystal investigation of a $Sc_xV_{5-x}Ge_3$ sample which was isotypic to Sc_5Ge_3 (a=0.743, c=0.502). The single crystal was obtained from a cast alloy. This phase is not shown in the 870 K isothermal section, fig. 24.

4.1.2. Sc-Cr-Ge

The isothermal section of the Sc–Cr–Ge phase diagram at 1070 K was constructed by Kotur et al. (1988b). The phase relations are characterized by the formation of four ternary compounds and by the existence of a solid solution range of Cr in Sc_5Ge_3 (7.5 at.%) (fig. 25). For details of sample preparation, see Sc–V–Ge.

Venturini et al. (1985a) investigated the crystal structure of the ScCrGe₂ (3) compound (TiMnSi₂-type structure: a=0.937, b=1.009, c=0.813). The sample was arc melted and annealed at 1073 K in an evacuated quartz capsule. The purity of the starting materials was 99.9 mass%.

Kotur et al. (1988a) confirmed the existence of this compound with similar lattice parameters (a=0.9355, b=1.0148, c=0.8141) and investigated the crystal structure of the other three compounds: ScCr₆Ge₆ (1) with the HfFe₆Ge₆-type (a=0.5102, c=0.8229), Sc₂Cr₄Ge₅ (2) with the Nb₂Cr₄Si₅-type (a=0.7821, b=1.6662, c=0.5146) and Sc₇Cr_{4+x}Ge_{10-x} (x=1.3) (4) with the Sc₇Cr_{4+x}Si_{10-x} type (a=1.0150, c=1.4352).



Fig. 25. Sc--Cr--Ge, isothermal section at 1070 K.



Fig. 26. Sc-Mn-Ge, isothermal section at 870 K.

4.1.3. Sc-Mn-Ge

The ternary phase diagram of the Sc-Mn-Ge system at 870K was studied by means of X-ray powder diffraction by Andrusyak and Kotur (1991) (fig. 26). For sample preparation, see Sc-V-Ge. Six ternary manganese germanides of scandium were found and investigated (Andrusyak 1988).

Crystallographic data for the ternary compounds which were observed in the course of phase-equilibrium studies in the Sc-Mn-Ge system at 870K are listed in table 6.

Venturini et al. (1992) investigated the crystal structure for the $ScMn_6Ge_6$ compound at 1073 K and confirmed the same structure type with similar lattice parameters. The alloy was synthesized by a powder metallurgical reaction in an evacuated silica tube at 1073 K for 14 days.

	Crystallographic data for the ternary Sc-Mn-Ge compounds at 870 K						
No.	Compound	Structure		e paramet	ers (nm)	Reference	
			a	b	с	-	
1	ScMn ₆ Ge ₆	HfFe ₆ Ge ₆	0.5176		0.8099	Andrusyak (1986)	
			0.5177		0.8084	Venturini et al. (1992)	
2	$ScMn_6Ge_4$	ZrFe ₆ Ge ₄	0.5066		2.0013	Kotur (1995)	
3	$Sc_3Mn_7Ge_8$	unknown				Andrusyak and Kotur (1991)	
4	ScMnGe ₂	ZrCrSi ₂	1.0191	0.9342	0.8083	Andrusyak and Kotur (1991)	
5	ScMnGe	ZrNiAl	0.6677		0.3946	Kotur and Andrusyak (1984a)	
6	$Sc_7Mn_{4+x}Ge_{10-x}$ (x = 1.3)	$Sc_7Cr_{4+x}Si_{10-x}$	0.9995		1.4168	Kotur et al. (1988a)	

Table 6



Fig. 27. Sc-Fe-Ge, isothermal section at 870 K.

4.1.4. Sc-Fe-Ge

The phase-field distribution in the Sc–Fe–Ge system at 870 K is characterized by the formation of eight ternary compounds and by the existence of substitutional exchange of Ge/Fe in the solid solutions $Sc_5(Fe_xGe_{1-x})_3$ for 0 < x < 0.15 and $Sc(Fe_xGe_{1-x})_2$ for 0 < x < 0.1 after Andrusyak and Kotur (1991) (fig. 27). For details of sample preparation, see Sc–V–Ge. The starting materials were Sc 99.92 mass%, Fe 99.95 mass%, and Ge 99.99 mass%.

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Table 7 Crystallographic data for the ternary Sc-Fe-Ge compounds

^a For ScFe_{1.79}Ge_{0.21}.

The ScFe₆Ge₆ compound with the HfFe₆Ge₆-type was observed by Olenych et al. (1981). Samples were obtained by arc melting and annealing for 300 h at 1070 K. Andrusyak (1986) and Venturini et al. (1992) confirmed the formation and crystal structure of this compound at 870 K and 1173 K respectively.

The existence and structural characteristics of the ScFeGe₂ compound at 1073 K was reported by Venturini et al. (1985a) (X-ray powder diffraction method) and was confirmed by Andrusyak and Kotur (1991) at 870 K.

The formation and crystal structure of six other ternary compounds were reported by Kotur and Andrusyak (1984a), Andrusyak and Kotur (1989, 1991).

Crystallographic data on the ternary Sc-Fe-Ge compounds are listed in table 7.

4.1.5. Sc-Co-Ge

A systematic study of the Sc–Co–Ge system at 870 K was performed by Kotur and Andrusyak (1991). For sample preparation, see Sc–V–Ge. The starting materials were Sc 99.92 mass%, Co 99.92 mass% and Ge 99.99 mass%. Seven ternary compounds were found to exist (see fig. 28). The limits of solid solutions origining at ScCo₂, ScGe₂, Sc₁₁Ge₁₀, Sc₅Ge₄ and Sc₅Ge₃ were established as 11.5 at.% Ge and 6 at.%, 4 at.%, 4 at.%, 3 at.% Co, respectively, by means of X-ray powder diffraction. The lattice parameter of ScCo_{2-1.65}Ge_{0-0.35} varies linearly within a = 0.6902-0.6984. Simarily for ScGe₂ the solid-solution range of Co is given by ScCo_{0-0.18}Ge_{2-1.82} (Kotur 1995).

The crystallographic characteristics for the ternary Sc–Co–Ge compounds are presented in table 8.

A single crystal of the Sc₃Co₂Ge₃ compound, which is not shown in fig. 28, was obtained from an arc-melted and slowly cooled sample: Hf₃Ni₂Si₃ type, a=0.4078, b=0.9930, c=1.3243 (Kotur and Andrusyak 1991).



Fig. 28. Sc–Co–Ge, isothermal section at 870 K.

No.	Compound	Structure	Lattice parameters (nm)			Reference
			a	b	с	• •
1	ScCo ₆ Ge ₆	HfFe ₆ Ge ₆	0.5056		0.7799	Buchholz and Schuster (1981)
			0.5064		0.7778	Kotur and Andrusyak (1991)
2	$Sc_4Co_{11}Ge_5$	unknown				Kotur and Andrusyak (1991)
3	$Sc_4Co_7Ge_6$	$U_4 Re_7 Si_6$	0.7850			Kotur and Andrusyak (1991)
4	ScCoGe ₂	TiMnSi ₂	0.919	1.009	0.796	Venturini et al. (1985a)
			0.9186	1.0102	0,7958	Kotur (1995)
5	$Sc_4Co_4Ge_7$	Zr ₄ Co ₄ Ge ₇	1.3215		0.5229	Andrusyak and Kotur (1989)
6	ScCoGe	TiNiSi	0.6495	0.4000	0.7072	Kotur and Andrusyak (1984a)
7	Sc ₂ CoGe ₂	Sc ₂ CoSi ₂	0.9595	0.9828	0.3914	Kotur and Andrusyak (1991)
				$\gamma = 123.2$	2°	

 Table 8

 Crystallographic data for the ternary Sc-Co-Ge compounds

4.1.6. Sc-Ni-Ge

In the course of phase-equilibrium studies in the Sc–Ni–Ge system at 870 K, Kotur and Andrusyak (1991) observed eight ternary nickel germanides of scandium (see fig. 29). For details of sample preparation, see Sc–V–Ge. The binary germanides of scandium dissolve 2-8 at.% Ni; the solubility of Ge in ScNi₂ is 3.5 at.% (Kotur 1995).

Crystallographic data for the ternary Sc-Ni-Ge compounds observed at 870 K are listed in table 9.

Andrusyak (1988) studied the crystal structure of the Sc₉Ni₅Ge₈ compound by the



Fig. 29. Sc-Ni-Ge, isothermal section at 870 K.

No.	Compound	Structure	Lattice parameters (nm)			Reference
			a	b	с	
1	ScNi ₆ Ge ₆	ScNi ₆ Ge ₆	1.0152		0.7813	Buchholz and Schuster (1981)
			1.0158		0.7816	Andrusyak (1986)
2	$Sc_3Ni_{11}Ge_4$	$\mathrm{Sc}_3\mathrm{Ni}_{11}\mathrm{Si}_4$	0.8130		0.8505	Kotur and Andrusyak (1991)
3	Sc _{12.3} Ni _{40.7} Ge ₃₁	own	1.7865		0.8220	Bodak et al. (1990)
4	Sc ₆ Ni ₁₈ Ge ₁₁	$Sc_6Ni_{18}Si_{11}$	1.8322	1.2461	0.8191	Andrusyak and Kotur (1987)
5	Sc ₆ Ni ₁₆ Ge ₇	Mg ₆ Cu ₁₆ Si ₇	1.1654			Gladyshevsky et al. (1962)
6	Sc ₃ Ni ₄ Ge ₄	Gd ₆ Cu ₈ Ge ₈	1.2910	0.6598	0.3908	Kotur and Sikirica (1982)
7	ScNiGe	TiNiSi	0.6454	0.4071	0.7068	Kotur and Andrusyak (1984a)
8	$Sc_{13}Ni_6Ge_{15}$	unknown				Kotur (1995)

 Table 9

 Crystallographic data for the ternary Sc-Ni-Ge compounds

X-ray single-crystal method (own type of structure, a = 2.0426, b = 0.9129, c = 0.39822). The single crystal was obtained from an as-cast sample.

Andrusyak and Kotur (1989) reported on X-ray single-crystal investigation of the $Sc_4Ni_4Ge_{7-x}$ (x=0.8) compound which existed in arc melted alloys and decomposed at 870 K (Zr₄Co₄Ge₇ type, a=1.3276, c=0.5225.

Neither of these two phases are shown in the 870 K isothermal section, fig. 29.

4.1.7. Sc-Cu-Ge

Kotur and Andrusyak (1984b) studied phase equilibria in the Sc--Cu--Ge system (fig. 30)



Fig. 30. Sc-Cu-Ge, isothermal section at 870 K.

and reported the existence of two compounds at 870 K. For sample preparation, see Sc–V–Ge.

The crystal structure for the Sc₃Cu₄Ge₄ compound (1) was studied by Thirion et al. (1983) (Gd₆Cu₈Ge₈ type, a=1.330, b=0.6516, c=0.3996) and was confirmed by Kotur and Andrusyak (1984b) (a=1.332, b=0.6523, c=0.4004).

The crystallographic characteristics for the ScCuGe compound (2) (ZrNiAl type, a = 0.6515, c = 0.3972) reported by Kotur and Andrusyak (1984b) are in good agreement with those announced earlier by Dwight et al. (1973).

4.1.8. Sc-Nb-Ge

The isothermal section of the Sc-Nb-Ge phase diagram at 1070 K was investigated by Kotur (1986) (fig. 31). The phase relations are characterized by the formation of one



Fig. 31. Sc–Nb–Ge, isothermal section at 870 K.

ternary Sc₂Nb₃Ge₄ compound and by the existence of a rather extended substitutional exchange of Sc/Nb in the $(Sc_{1-x}Nb_x)_5$ Ge₃ solid solution for 0 < x < 0.8 with the following unit cell dimensions for the Nb-rich end boundary sample: a=0.7752, c=0.5362. For sample preparation, see Sc–V–Ge. The starting components were Sc 99.92 mass%, Nb 99.9 mass%, Ge 99.99 mass%.

 $Sc_2Nb_3Ge_4$ belongs to the $Ce_2Sc_3Ge_4$ -type with lattice parameters a=0.6860, b=1.339, c=0.7160 (Kotur 1986, X-ray powder diffraction).

4.1.9. Sc-Mo-Ge

The phase diagram for Sc-Mo-Ge was reported by Kotur and Bodak (1988) (fig. 32). For the details of synthesis, see Sc-V-Ge.



Fig. 32. Sc-Mo-Ge, isothermal section at 1070 K.

Only one ternary compound was found to exist at 1070 K, $\text{Sc}_{2-4}\text{Mo}_{3-1}\text{Ge}_4$ with Sm_5Ge_4 structure type, a = 0.6691 - 0.6813, b = 1.2872 - 1.3285, c = 0.6905 - 0.7027 (X-ray powder diffraction method).

4.1.10. Sc-Ru-Ge

No ternary phase diagram has been established for the Sc-Ru-Ge system, but three ternary compounds have been characterized by various authors.

ScRuGe crystallizes with the ZrNiAl-type of structure, a=0.6962, c=0.3468 (Hovestreydt et al. 1982; X-ray powder diffraction). The sample was arc melted under an argon atmosphere and annealed at 1270 K for 1–2 weeks in an evacuated silica tube.

According to X-ray powder diffraction data reported by Venturini et al. (1985a), the compound ScRuGe₂ is isostructural with TiMnSi₂ (a=0.928, b=1.032, c=0.812). For sample preparation, see Sc–Cr–Ge.

Engel et al. (1984) reported the crystal structure of the $Sc_4Ru_7Ge_6$ compound crystallizing with the U₄Re₇Si₆-type of structure (a = 0.8129, X-ray powder diffraction data). The sample was prepared by arc melting a cold-pressed mixture of proper amounts of binary ScGe₂ alloy and ruthenium. The ternary alloy was finally annealed at 1270 K for 5 weeks. The starting materials were Sc 99.95 mass%, Ge 99.999 mass%, Ru 99.9 mass%.

4.1.11. Sc-Rh-Ge

No ternary phase diagram is available for the Sc-Rh-Ge system. However, four ternary phases have been identified.

Hovestreydt et al. (1982) reported two types of structures for the ScRhGe compound: TiNiSi type, a=0.6497, b=0.4112, c=0.7385 and ZrNiAl type, a=0.6672, c=0.3794. For sample preparation, see Sc-Ru-Ge.

 $Sc_4Rh_7Ge_6$ was found to be isostructural with the U₄Re₇Si₆-type (*a*=0.81255) by Engel et al. (1984). The crystal structure was determined on a single crystal and was refined to an *R* value of 0.056 for 99 independent reflections. For details concerning the sample preparation, see Sc-Ru-Ge.

ScRhGe₂ was observed to adopt the TiMnSi₂-type structure (a=0.9302, b=1.0359, c=0.8146) by Parthé and Chabot (1984).

Venturini et al. (1986a) investigated the crystal structure of the $Sc_4Rh_6Ge_{19}$ compound. It was found to crystallize with its own structure type, a = 1.2605. Samples were obtained by heating a mixture of starting components (Sc, Rh, Ge: 99.999 mass%) in an evacuated quartz tube at 1173 K.

4.1.12. Sc-Pd-Ge

Only one compound was reported for the Sc–Pd–Ge system: ScPdGe, ZrNiAl-type of structure, a = 0.6715, c = 0.3925 (Hovestreydt et al. 1982, X-ray powder diffraction). For sample preparation, see Sc–Ru–Ge.

4.1.13. Sc-Ag-Ge

The isothermal section at 870 K was constructed by Kotur and Boichuk (1988) (fig. 33). For experimental details, see Sc–V–Ge. The starting materials were Sc 99.92 mass%, Ag 99.99 mass%, Ge 99.999 mass%.

Only one compound was found for the Sc–Ag–Ge combination by Kotur and Boichuk (1988): ScAgGe with the ZrNiAl type, a = 0.6882, c = 0.4026.



Fig. 33. Sc–Ag–Ge, isothermal section at 870 K.





4.1.14. Sc--Hf--Ge

The isothermal section of the Sc-Hf-Ge phase diagram at 1070 K was reported by Kotur (1991) (fig. 34). No ternary compounds were observed. Continuous solid solutions between isotypic pairs of binary germanides $ScGe_2$ -HfGe₂, Sc_5Ge_4 -Hf₅Ge₄ and Sc_5Ge_3 -Hf₅Ge₃ were observed. Also ~25 at.% Sc substitutes for Hf in Hf₃Ge.

4.1.15. Sc-Ta-Ge

The phase-field distribution in the Sc-Ta-Ge system at 1070 K (fig. 35) is characterized



Fig. 35. Sc–Ta–Ge, isothermal section at 1070 K.

by the formation of a ternary $Sc_{2-3}Ta_{3-2}Ge_4$ compound with a large homogeneity region and by the existence of the $Sc_{5-3.25}Ta_{0-1.75}Ge_3$ solid solution originating at Sc_5Ge_3 , after Kotur and Bodak (1990). For sample preparation, see Sc–V–Ge. Starting materials were Sc 99.92 mass%, Ta 99.99 mass%, Ge 99.99 mass%.

 $Sc_{2-3}Ta_{3-2}Ge_4$ was found to crystallize with a Sm_5Ge_4 type, a=0.6823-0.6855, b=1.3177-1.3230, c=0.6977-0.6993, from X-ray powder diffraction of an arc melted alloy annealed at 1070 K (Kotur and Bodak 1990).

4.1.16. Sc-W-Ge

No ternary compounds were observed by Kotur et al. (1989) in the ternary Sc–W–Ge system at 1070 K (fig. 36). The binary Sc₅Ge₃ compound dissolves 3 at.% W. For sample preparation, see Sc–V–Ge.



Fig. 36. Sc–W–Ge, isothermal section at 1070 K.

4.1.17. Sc-Re-Ge

Figure 37 represents the isothermal section of the Sc-Re-Ge system at 1070K after Kotur (1995). For sample preparation, see Sc-V-Ge. The mutual solid solutibility of components in binary compounds is negligible.

In the course of phase studying the equilibria in the Sc–Re–Ge system at 1070 K, the formation of the ScReGe₂ compound (1) with TiMnSi₂-type structure has been confirmed and the existence of two compounds [Sc₃Re₂Ge₃ (2) and Sc₉Re₃Ge₈ (3)] with unknown structures has been observed by Kotur 1995.

The lattice parameters for ScReGe₂ are as follows a=0.939, b=1.017, c=0.832 after Venturini et al. (1985a) (powder diffraction data; for sample preparation, see Sc–Cr–Ge) and a=0.9385, b=1.0173, c=0.8323 after Kotur (1995).





4.1.18. Sc-Os-Ge

No phase diagram is established for the Sc-Os-Ge system.

ScOsGe was observed to adopt the ZrNiAl-type structure with lattice parameters a = 0.6928, c = 0.3407 (Hovestreydt et al. 1982; X-ray powder diffraction analysis). For sample preparation, see Sc-Ru–Ge.

ScOsGe₂ crystallizes with the TiMnSi₂-type structure, a=0.929, b=1.033, c=0.817 (Venturini et al. 1985a; powder X-ray diffraction data). For the experimental details, see Sc-Cr-Ge.

Engel et al. (1984), from X-ray powder diffraction data, characterized the compound $Sc_4Os_7Ge_6$ to be isostructural with $U_4Re_7Si_6$, a=0.8146. The sample was synthesized in the same manner as $Sc_4Ru_7Ge_6$.

4.1.19. Sc-Ir-Ge

No ternary phase diagram is available for the Sc-Ir-Ge system; however, the formation of two ternary scandium iridium germanides has been reported so far.

From X-ray powder analysis Hovestreydt et al. (1982) reported ScIrGe to crystallize with the TiNiSi-type structure. The crystallographic data were: a=0.6446, b=0.4107, c=0.7482. For sample preparation, see Sc-Ru-Ge.

 $Sc_4Ir_7Ge_6$ is isotypic with the crystal structure of $U_4Re_7Si_6$, a=0.8146 (Engel et al. 1984; X-ray powder diffraction). The details of sample preparation are the same as for $Sc_4Ru_7Ge_6$.

4.1.20. Sc-Pt-Ge

No phase diagram has been established for the Sc-Pt-Ge system. Only one study on the interaction of scandium with platinum and germanium has been reported. According

to Hovestreydt et al. (1982), ScPtGe was found to be isostructural with the TiNiSitype structure, a=0.6585, b=0.4215, c=0.7141 (X-ray powder diffraction). For sample preparation, see Sc-Ru-Ge.

4.1.21. Sc-Au-Ge

Little information exists on the Sc-Au-Ge system; only one ternary germanide has been characterized.

The crystal structure of the ScAuGe compound has been investigated by Pöttgen et al. (1996a) by the X-ray single-crystal method. It was found to crystallize with a LiGaGe type, a = 0.43082, c = 0.68458. The alloy has been prepared by melting a mixture of the elements in an arc furnace and subsequently annealing at 1070 K.

4.2. Y-d element-Ge systems

4.2.1. Y-Cr-Ge

The phase equilibria in the Y–Cr–Ge system were investigated by Bodak and Gladyshevsky (1985) by means of X-ray analysis of alloys which were arc melted and subsequently annealed in evacuated silica tubes at 870 K and finally quenched in water. The isothermal section of the Y–Cr–Ge system at 870 K is presented in fig. 38.

Brabers et al. (1994) reported the existence of a compound YCr₆Ge₆ with the HfFe₆Ge₆ type (a=0.5167, c=0.8273; X-ray powder diffraction). The sample was prepared by arc melting and subsequent annealing at 1073 K for three weeks in a sealed tube. This phase is not shown in the 870 K isothermal section of the Y–Cr–Ge system (fig. 38).



Fig. 38. Y–Cr–Ge, isothermal section at 870 K.

4.2.2. Y-Mn-Ge

No ternary phase diagram is available for the Y-Mn-Ge system. Two ternary compounds have been reported for yttrium-manganese-germanium combinations.

YMn₆Ge₆ was found to crystallize in the HfFe₆Ge₆-type structure by Venturini et al. (1992), a=0.5233, c=0.8153 (X-ray powder diffraction data). The alloy was synthesized by powder metallurgical reaction in evacuated silica tube at 1073 K for 14 days.

Rossi et al. (1978b) reported on investigation of the crystal structure of the YMn₂Ge₂ compound (CeGa₂Al₂ type, a=0.3995, c=1.0886; X-ray powder method). The alloy was obtained by melting under argon in an induction furnace and was annealed at 770 K for one week. The metals used were of purity greater than 99.9 mass% for Y, and greater than 99.99 mass% for Mn and Ge.

4.2.3. Y–Fe–Ge

No phase diagram has been constructed for the Y–Fe–Ge system; five ternary compounds have been found and characterized by various authors.

YFe₆Ge₆ was reported to be isotypic with the crystal structure of YCo₆Ge₆with lattice parameters a = 0.5110, c = 0.4049 (Mruz et al. 1984). The sample was prepared by arc melting proper amounts of starting components followed by annealing at 870 K for two weeks. At variance with the data of Mruz et al. (1984), YFe₆Ge₆ was found to crystallize with the TbFe₆Sn₆ type, a = 0.8116, b = 1.7672, c = 0.5120, by Venturini et al. (1992) from X-ray powder diffraction data. The alloy was obtained by powder metallurgical reaction in an evacuated silica tube at 1173 K for two weeks.

Pecharsky et al. (1989) reported YFe_{0.33}Ge₂ to crystallize with the CeNiSi₂-type (a = 0.4118, b = 1.5903, c = 0.4002; X-ray powder analysis). The alloy was arc melted and annealed at 870 K. The purity of the starting materials was greater than 99.9 mass%.

YFe₄Ge₂ is isotypic with the crystal structure of ZrFe₄Si₂ with lattice parameters a = 0.7314, c = 0.3864, after Fedyna (1988). The alloy was prepared by arc melting the proper amounts of starting components followed by annealing at 870 K for 400 hours.

Oleksyn (1990) investigated the crystal structure of the $Y_{117}Fe_{52}Ge_{112}$ compound by the X-ray powder method (Tb₁₁₇Fe₅₂Ge₁₁₂ type, a=2.8409). The alloy was synthesized by arc melting followed by annealing at 1070 K for 350 h. The starting materials were Y 99.83 mass%, Fe 99.9 mass%, Ge 99.99 mass%.

According to X-ray single-crystal data, YFe_2Ge_2 was found to be isostructural with the CeGa₂Al₂ type, with lattice parameters a = 0.3961, c = 1.0421 (Venturini and Malaman 1996). Samples were prepared from stoichiometric amounts of pure elements. After a first reaction in a silica tube under argon, the mixture was melted in an induction furnace.

4.2.4. Y-Co-Ge

The phase diagram of the Y–Co–Ge system has not been established; eight ternary compounds have been identified for yttrium–cobalt–germanium combinations.

Méot-Meyer et al. (1985a) reported the crystal structure of the YCo_{1-x}Ge₂, x = 0.55 (CeNiSi₂ type, a = 0.4106, b = 1.612, c = 0.4026). Samples were prepared by powder

metallurgical reaction and annealed in evacuated silica tube at 1173 K. Pecharsky et al. (1989) investigated the formation and crystal structure of the $YCo_{1-x}Ge_2$ compound by X-ray powder analysis of arc melted alloys annealed at 870 K. The CeNiSi₂-type structure was confirmed and in addition, the existence of an extended homogeneity region was observed: 0.2 < x < 0.9, a = 0.4067 - 0.4115, b = 1.5840 - 1.6080, c = 0.3946 - 0.4019.

The crystal structure of $Y_3Co_4Ge_{13}$ (Yb₃Rh₄Sn₁₃ type, a=0.8757; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample which was prepared by heating a compacted mixture of starting materials (Y in pieces, 99.9 mass%; Co and powder Ge, 99.99 mass%) in an evacuated quartz tube at 1073 K.

Bruskov et al. (1986) reported on the single-crystal investigation of $Y_3Co_4Ge_{13}$ (own structure type, a = 0.8769). The single crystal was obtained from arc melted and annealed at 870 K alloy.

McCall et al. (1973a) mentioned the existence of the YCo₂Ge₂ compound with the CeGa₂Al₂-type. Venturini and Malaman (1996) confirmed the crystal structure for the YCo₂Ge₂ compound and established the lattice parameters (a = 0.39698, c = 1.0025; X-ray single-crystal data). The sample was prepared in the same manner as YFe₂Ge₂.

From an X-ray powder analysis of alloy annealed at 1173 K, $Y_2Co_3Ge_5$ was reported to adopt the Lu₂Co₃Si₅ type structure, a = 0.9642, b = 1.180, c = 0.5707, $\beta = 91.9^{\circ}$ (Venturini et al. 1986b).

The crystal structure of the YCo₆Ge₆ compound was reported by Buchholz and Schuster (1981) (own structure type, a = 0.5074, c = 0.39908). Samples were melted under an argon atmosphere in a corundum crucible at 1073–1273 K.

Gorelenko et al. (1984) reported the crystal structure of YCoGe (TiNiSi type, a = 0.6880, b = 0.4212, c = 0.7258; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Y₃Co₂Ge₄ crystallizes with the Tb₃Co₂Ge₄ type structure, a=1.0608, b=0.8050, c=0.4181, $\gamma=107.80^{\circ}$. Samples were prepared by arc melting and annealing at 873 K for 1450 h. The starting materials were: Y (>99.9 mass%), Co (99.99 mass%), Ge (99.999 mass%) (Mruz et al. 1989).

 Y_2CoGe_6 is isotypic with Ce₂CuGe₆, a=0.3940, b=0.3993, c=2.1426 (Oleksyn et al. 1991; X-ray powder diffraction data). The sample was melted in an arc furnace and annealed at 1070 K in an evacuated quartz capsule for 400 h. The purity of the starting materials was greater than 99.9 mass%.

4.2.5. *Y–Ni–Ge*

Figure 39 represents the isothermal sections of Y–Ni–Ge phase diagram at 1070 K (0–33 at.% Y) and at 670 K (33–100 at.% Y) which were studied by Koterlyn et al. (1988). The isothermal sections were constructed by means of X-ray powder analysis of alloys, which were arc melted and subsequently annealed in evacuated silica tubes for 400 h and finally quenched in water. Starting materials were Y 99.99 mass%, Ni 99.98 mass% and Ge 99.99 mass%.

The ternary phase diagram is characterized by the existence of ten ternary compounds and by the formation of a substitutional exchange of Ge/Ni in the solid solutions



Fig. 39. Y-Ni-Ge, isothermal section at 1070 K (0-33 at.% Y) and at 670 K (33-100 at.% Y).

 $Y_2(Ni_{1-x}Ge_x)_{17}$ and $Y(Ni_{1-x}Ge_x)_5$ for 0 < x < 0.12. This behavior corresponds to the solid solution range of Ge in nickel. Nonstoichiometry and a homogeneity range were observed for $YNi_{1-x}Ge_2$ (0.4 < x < 0.7) (8). The binary compound Y_2Ge_3 dissolves 20 at.% Ni.

 YNi_5Ge_3 (1) was reported to crystallize with an YNi_5Si_3 type, a=1.9108, b=0.3864, c=0.6773 by Fedyna (1988). The alloy, arc melted and annealed at 870 K, was investigated by X-ray powder diffraction analysis. Starting materials were Y 99.83 mass%, Ni 99.99 mass%, Ge 99.99 mass%.

 $Y_3Ni_{11}Ge_4$ (2) belongs to the Sc₃Ni₁₁Si₄ type, a=0.8319, c=0.8821 after Fedyna (1988). For sample preparation, see the previous paragraph.

The YNi₂Ge₂ (3) compound was found to adopt the CeGa₂Al₂-type structure, a = 0.4043, c = 0.9763 (Rieger and Parthé 1969b). Venturini and Malaman (1996) confirmed the crystal structure for the YNi₂Ge₂ compound and established the lattice parameters a = 0.39698, c = 1.0025 from X-ray single crystal diffraction. The sample was prepared in the same manner as YFe₂Ge₂, see Y–Fe–Ge.

YNiGe₃ (4) with the ScNiSi₃-type of structure (a=2.1657, b=0.4102, c=0.4092, X-ray powder diffraction analysis) was reported by Bodak et al. (1985). For the details of sample preparation and purity of starting materials, see YNi₅Ge₃.

Y₂NiGe₆ (6) has been found by Oleksyn (1990) from X-ray powder diffraction to be isostructural with Ce₂CuGe₆-type structure (a=0.3956, b=2.1265, c=0.4007). The sample was prepared by arc melting ingots of the constituting elements and annealing at 1070 K for 700 h. For the purity of starting materials, see YNi₅Ge₃, above.

Pecharsky et al. (1989) investigated the formation and crystal structure of the

 $YNi_{1-x}Ge_2$ (8) compound by X-ray powder analysis of arc melted alloys annealed at 870 K (CeNiSi₂ type, a = 0.4090-0.4101, b = 1.607-1.629, c = 0.3969-0.4012). For sample preparation, see YFe_{1-x}Ge₂ under Y-Fe-Ge.

Gorelenko et al. (1984) reported the crystal structure of YNiGe (8) (TiNiSi type, a = 0.6970, b = 0.4212, c = 0.7258; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Bodak et al. (1982) reported on the crystal structure of Y_3NiGe_2 (10) from X-ray powder diffraction (La₃NiGe₂ type, a=1.1304, b=0.4215, c=1.1299). The proper amounts of starting components were arc melted and annealed at 870 K.

The crystal structure of two ternary compounds $YNiGe_2$ (5) and $Y_{4.75}NiGe_{4.25}$ (9) has not been determined (Koterlyn et al. 1988).

4.2.6. *Y*-*Cu*-*Ge*

No isothermal section is available for the Y–Cu–Ge system; four ternary compounds have been found and analyzed by different groups of authors.

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented were $YCu_{1-0.67}Ge_{1-1.33}$ with a=0.404-0.4217, c=0.405-0.3696. In variance with the data by Rieger and Parthé (1969a), Iandelli (1993) observed YCuGe with the CaIn₂-type (a=0.4228, c=0.7325, X-ray powder analysis). The alloy was prepared from filings or powders of metals (yttrium 99.7 mass%, copper and germanium 99.99 mass%), which were mixed and sealed in tantalum crucible under argon, melted by induction heating and annealed for 10 days at 1023 K.

 $Y_6Cu_8Ge_8$ crystallizes with the Gd₆Cu₈Ge₈-type structure and the lattice parameters are a = 1.392, b = 0.665, c = 0.419 (Hanel and Nowotny 1970).

Konyk et al. (1988) investigated the crystal structure of Y_2CuGe_6 alloy prepared by arc melting under argon and annealed at 870 K in evacuated quartz tube for 720 h. From X-ray powder analysis a Ce₂CuGe₆-type was claimed, a=0.3993, b=0.4108, c=2.0980.

Rieger and Parthé (1969b) prepared YCu₂Ge₂ with a CeGa₂Al₂-type of structure, a = 0.4035, c = 1.0303.

4.2.7. Y-Nb-Ge

The phase diagram of the Y–Nb–Ge system has not been established. The existence of a compound $Y_2Nb_3Ge_4$ with the Ce₂Sc₃Si₄-type (a=0.6964, b=1.3572, c=0.7182) was reported by Le Bihan et al. (1996a) from X-ray powder diffraction data of arc melted alloy. The starting materials were: Y and Nb 99.99 mass%, Ge 99.999 mass%.

4.2.8. Y-Mo-Ge

No ternary compounds or solid solutions were found in the Y-Mo-Ge system at 870 K by Bodak and Gladyshevsky (1985) from X-ray powder diffraction of arc melted samples which were annealed at 870 K for three weeks (see fig. 40).

The existence of a compound $Y_2Mo_3Ge_4$ with the Ce₂Sc₃Si₄ type (a=0.6912, b=1.3134, c=0.7067) was reported by Le Bihan et al. (1996b) from X-ray powder diffraction of arc melted alloy. For the purity of the starting materials, see Y–Nb–Ge.



Fig. 40. Y–Mo–Ge, isothermal section at 870 K.

4.2.9. Y-Ru(Rh, Pd)-Ge

The ternary Y-Ru(Rh, Pd)-Ge systems have been studied only with respect to the formation of compounds with specific composition and structure. Their crystallographic characteristics are listed in table 10.

Table 10 Crystallographic data for the ternary Y-Ru(Rh, Pd)-Ge compounds						
Compound	Structure	Lattice	e paramet	ers (nm)	Reference	
		a	b	с	-	
YRu ₂ Ge ₂	CeGa ₂ Al ₂	0.4225		0.9837	Francois et al. (1985)	
$Y_2Ru_3Ge_5$	U2Co3Si5	0.9808	1.243	0.5735	Venturini et al. (1986b)	
$Y_3Ru_4Ge_{13}$	$Yb_3Rh_4Sn_{13}$	0.8962			Segre et al. (1981a)	
YRh_2Ge_2	CeGa ₂ Al ₂	0.4103		1.0207	Francois et al. (1985)	
$Y_2Rh_3Ge_5$	$Lu_2Co_3Si_5$	0.9963	1.2045	0.5820	Venturini et al. (1986b)	
			$\beta = 91.9$	0		
$Y_5 Rh_4 Ge_{10}$	$Sc_5Co_4Si_{10}$	1.2944		0.4270	Venturini et al. (1984)	
Y ₂ Rh ₃ Ge	own	0.5552		1.182	Cenzual et al. (1987)	
Y ₃ Rh ₂ Ge ₂	$La_3Ni_2Ga_2$	0.5563	0.7814	1.182	Gladyshevsky et al. (1991a)	
$Y_3Rh_4Ge_{13}$	$Yb_3Rh_4Sn_{13}$	0.8923			Venturini et al. (1985b)	
Y ₄ Rh ₁₃ Ge ₉	$Ho_4Ir_{13}Ge_9$				Verniere et al. (1995)	
YRhGe	TiNiSi	0.6899	0.4276	0.7550	Hovestreydt et al. (1982)	
YPd ₂ Ge	YPd ₂ Si	0.7352	0.7036	0.5562	Jorda et al. (1983)	
Y_2 PdGe ₆	Ce ₂ CuGe ₆	0.4079	0.4016	2.1525	Sologub et al. (1995a)	
YPdGe	KHg ₂	0.4365	0.6952	0.7549	Hovestreydt et al. (1982)	

4.2.10. Y-Ag-Ge

No phase diagram is available for the Y-Ag-Ge system. Protsyk (1994) reported the existence of the YAg_{0.33}Ge_{1.67} compound with α -ThSi₂ type (a 0.4070, c = 1.3710; X-ray powder diffraction data). Samples were arc melted and annealed at 870 K for 400 hours.

Gibson et al. (1996) investigated the crystal structure of the YAgGe compound (ZrNiAl type, a=0.71180, c=0.41968). The sample was prepared from the elements by arc melting and annealing at 970K for ten days.

4.2.11. Y-Os(Ir, Pt)-Ge

The ternary Y-Os(Ir, Pt)-Ge systems have been studied only with respect to the formation of compounds with specific composition and structure. Their crystallographic data are presented in table 11.

Compound	Structure	Lattice	e paramet	ers (nm)	Reference
		а	b	с	
$Y_5Os_4Ge_{10}$	Sc ₅ Co ₄ Si ₁₀	1.3006		0.4229	Braun et al. (1980)
$Y_3Os_4Ge_{13}$	$Yb_3Rh_4Sn_{13}$	0.8985			Segre et al. (1981a)
YIrGe ₂	own	0.4264	1.5976	0.8813	Francois et al. (1987)
Y ₂ Ir ₃ Ge ₅	$U_2Co_3Si_5$	1.0133	1.172	0.5955	Venturini et al. (1986b)
Y ₄ Ir ₇ Ge ₆	$U_4 Re_7 Si_6$	0.8324 Francois et al		Francois et al. (1985)	
Y ₅ Ir ₄ Ge ₁₀	$Sc_5Co_4Si_{10}$	1.2927		0.4308	Braun et al. (1980)
$Y_3Ir_4Ge_{13}$	$Yb_3Rh_4Sn_{13}$	13 0.8948 Venturini et		Venturini et al. (1985a)	
Y ₄ Ir ₁₃ Ge ₉	Ho ₄ Ir ₁₃ Ge ₉				Verniere et al. (1995)
YIrGe	TiNiSi	0.6843	0.4265	0.7619	Hovestreydt et al. (1982)
YPtGe ₂	YIrGe ₂	0.4307	1.5976	0.8813	Francois et al. (1987)
$Y_3Pt_4Ge_6$	own	0.8692	0.4306 $\beta = 99.4$.4306 1.3161 Venturini and Malaman (19 =99.45°	
YPt ₂ Ge ₂	LaPt ₂ Ge ₂	0.4314 0.4358 0.9659 Venturini et al. (198 $\beta = 91.08^{\circ}$		Venturini et al. (1989a)	
YPtGe	TiNiSi	0.6986	0.4338	0.7557	Hovestreydt et al. (1982)
Y ₂ PtGe ₆	Ce ₂ CuGe ₆	0.4057	0.4012	2.1677	Sologub et al. (1995a)

	Table 11		
Crystallographic data	for the ternary	Y-Os(Ir, Pt)-Ge	compound

4.2.12. Y-Au-Ge

No ternary phase diagram is available for the Y-Au-Ge system, however, a ternary compound of yttrium with gold and germanium with the 1:1:1 stoichiometric ratio has been identified and studied by means of X-ray and metallographic analyses by Rossi et al. (1992). It was found to adopt the LiGaGe type with lattice parameters a = 0.4408, c =0.7307. The sample was prepared by melting the metals (purity around 99.9 mass% for yttrium and 99.99 mass% for gold and germanium) in an induction furnace and annealing at 1070 K for one week.

4.3. La-d element-Ge systems

4.3.1. La-Mn-Ge

No phase diagram is available for the system La--Mn-Ge, however, two ternary compounds have been observed and characterized.

The LaMn₂Ge₂ compound has been prepared and studied by Rossi et al. (1978b). It was found to be of CeGa₂Al₂ type with lattice parameters a=0.4108, c=1.0685. The alloy was obtain by melting under argon atmosphere in an induction furnace. The sample was then annealed at 500°C for one week. The lanthanum used was of a purity greater than 99.9 mass%, for manganese and germanium the purity was greater than 99.99 mass%.

The LaMnGe compound with PbFCI-type was observed by Welter et al. (1995); a=0.4254, c=0.7425. The compound was prepared from commercially available high purity elements. Compacted pellet of stoichiometric mixture was sealed under argon (100 mmHg) in silica tube which was heated at 1273 K as a preliminary homogenization treatment and then melted in an induction furnace. The resulting ingot was annealed for 2 weeks at 1173 K.

4.3.2. La-Fe-Ge

No phase diagram is available at present for the La–Fe–Ge system; the formation of three ternary germanides has been reported by various authors.

The LaFe_{0.67}Ge_{1.33} compound was found to adopt the AlB₂-type structure (a = 0.4223, c = 0.4316; X-ray powder diffraction) (Felner and Schieber 1973). The sample was prepared by melting elements together (lanthanum 99.9 mass%, Ge 99.99 mass%), Fe 99.95 mass%). The metals were mixed and heated in an alumina crucible in an induction furnace under the protective atmosphere of argon. The sample was homogenized by annealing at 1870 K for about 30 min.

The LaFe₂Ge₂ compound was initially investigated by Rossi et al. (1978a) (CeGa₂Al₂ type, a = 0.4110, c = 1.0581) by means of X-ray diffraction. Bara et al. (1990) confirmed the crystal structure of the LaFe₂Ge₂ compound (a = 0.4128, c = 1.0602; X-ray powder diffraction) from an arc melted sample, annealed for 1 week at 1073 K. The purity of the starting elements was La, 4N; Fe, 3N; Ge, 5N.

Francois et al. (1990) investigated the occurrence of the CeNiSi₂ type for lanthanum– iron–germanium combinations from the alloys annealed at 1173 K (LaFe_{0.60–0.69}Ge₂; a = 0.4347-0.4359, b = 1.683-1.679, c = 0.4210-0.4225).

4.3.3. La-Co-Ge

The equilibrium phase diagram for the La-Co-Ge system has not been reported. Lanthanum-cobalt-germanium combinations have been investigated only with respect to

the formation and crystal structure of compounds with various stoichiometries. To date five compounds have been identified.

Méot-Meyer et al. (1985a) reported the crystal structure of LaCo_{0.96}Ge₂ (CeNiSi₂ type, a=0.4309, b=1.688, c=0.4238). The sample was prepared by powder metallurgical reaction and annealed in evacuated silica tube at 1173 K. Pecharsky et al. (1989) investigated the formation and crystal structure of the LaCo_{1-x}Ge₂ compound by X-ray powder analysis of arc melted alloy annealed at 870 K. The CeNiSi₂-type structure was confirmed for the sample of stoichiometric composition (a=0.4335, b=1.6945, c=0.4279).

McCall et al. (1973b) investigated the crystal structure of the LaCo₂Ge₂ compound (BaAl₄ type, a = 0.4123, c = 1.0277; X-ray powder diffraction). The sample was melted in an induction furnace. Starting components were Co, Ge (5N) and La (3N).

The crystal structure of LaCoGe₃ (BaNiSn₃ type, a=0.4350, c=0.9865; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample which was prepared by heating a compacted mixture of starting materials (La in pieces, 99.9 mass%; Co and powder Ge, 99.99 mass%) in an evacuated quartz tube at 1073 K. Later the crystal structure of LaCoGe₃ compound was confirmed by Pecharsky et al. (1993) by means of metallography and room-temperature X-ray powder diffractometry. The crystal structure has been established and lattice parameters have been measured (BaNiSn₃ type, a= 0.43497, c=0.98679). The alloy was prepared by arc melting pieces of the metals under an argon atmosphere and then heat treating it at 1173 K for 7 days in a helium-filled quartz tube. The starting metals were La 99.79 mass%, Co and Ge >99.999 mass%.

The LaCoGe compound with PbFCl-type structure was observed by Welter et al. (1993a); a=0.4194, c=0.7028. The compound was prepared from commercially available high-purity elements. A compacted pellet of stoichiometric mixture was sealed under argon (100 mmHg) in a silica tube which was heated at 1173 K as a preliminary homogenization treatment and then melted in an induction furnace. The resulting ingot was annealed for 2 weeks at 1173 K.

The crystal structure of the La₆Co₁₃Ge compound was reported by Weitzer et al. (1990) (Nd₆Fe₁₃Si type, a = 0.80620, c = 2.29224). The sample was melted under argon and annealed at 1073 K for 5 days. Starting materials were commercially available high-purity elements.

4.3.4. La–Ni–Ge

No phase diagram is available for the La-Ni-Ge system, but nine ternary phases have been identified.

Bodak et al. (1982) investigated the crystal structure of the La₃NiGe₂ compound (own structure type, a = 1.2041, b = 0.4358, c = 1.1871) by the single-crystal diffraction method. For sample preparation and purity of starting elements, see Y–Ni–Ge.

The LaNi₂Ge₂ compound was found to adopt the CeGa₂Al₂-type structure, a = 0.4187, c = 0.9918 (Rieger and Parthé 1969b).

Pecharsky et al. (1989) reported the crystal structure of the LaNiGe₂ (CeNiSi₂ type, a = 0.4314, b = 1.688, c = 0.4235) from X-ray powder analysis of arc melted alloy annealed at 870 K. The stoichiometric composition and crystal structure type were confirmed by Francois et al. (1990). For sample preparation, see La–Fe–Ge.

Gladyshevsky and Bodak (1965) determined the AlB₂-type structure for the compound LaNi_{0.67-0.5}Ge_{1.33-1.5}, a = 0.4202-0.4193, c = 0.4306-0.4336 (X-ray powder diffraction).

Bruskov (1984) investigated the crystal structure for the compounds La₃Ni₄Ge₄ (U₃Ni₄Si₄-type structure, a=0.4223, b=0.4230, c=2.4156; X-ray single-crystal method); La₁₁Ni₄Ge₆ (own structure type, a=1.8637, b=0.4384, c=1.4191, $\beta=106,13^{\circ}$; X-ray single-crystal method); La₈NiGe₅ (own structure type, a=1.5586, b=1.8384, c=1.1351; X-ray single-crystal method); La₈NiGe₅ (own structure type, a=1.1371); and La₂NiGe (own structure type, a=0.7947, c=1.4262; X-ray single-crystal method). For sample preparation, see Y–Ni–Ge.

4.3.5. *La–Cu–Ge*

No phase diagram is available for the system La–Cu–Ge, however the crystallographic characteristics for a series of ternary compounds are presented in the literature.

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented were LaCu_{1-0.67}Ge_{1-1.33} with a=0.4323-0.4223, c=0.4050-0.4322. Iandelli (1993) confirmed AlB₂-type (a=0.4335, c=0.4040, X-ray powder analysis) from the LaCuGe alloy which was prepared from filings or powders of the metals (La 99.7 mass%), Co and Ge 99.99 mass%), sealed in a tantalum crucible under argon followed by melting in an induction furnace; afterwards the sample was annealed for 10 days at 1023 K.

Konyk et al. (1988) reported on the crystal structure of La₂CuGe₆ alloy prepared by arc melting under argon and annealed at 870 K in an evacuated quartz tube for 720 h. From X-ray powder analysis a Ce₂CuGe₆-type was claimed, a = 0.4100, b = 0.4258, c = 2.1838.

Rieger and Parthé (1969b) prepared LaCu₂Ge₂ with the CeGa₂Al₂-type of structure, a=0.4265, c=1.0170.

Francois et al. (1990) reported the crystal structure of the LaCu_{0.82-0.92}Ge₂ (CeNiSi₂ type, a = 0.4335-4333, b = 1.740-1740, c = 0.4175-0.4193). For sample preparation, see La–Fe–Ge.

4.3.6. La–Zn–Ge

No isothermal section is available for the ternary La–Zn–Ge system, however one ternary compound was observed and characterized by Rossi and Ferro (1996). LaZn_{1.5}Ge_{0.5} was found to crystallize with an AlB₂ type, a=0.4471, c=0.4032 from X-ray powder diffraction of melted in an induction furnace alloy which was afterwards annealed at 1070 K for one week. An electronic micrographic examination as well as microprobe analysis were carried out. The metals employed in the synthesis of sample had a nominal purity of 99.9 mass% for La, and 99.999 mass% for other metals.
4.3.7. La–Ru–Ge

The phase diagram for the La–Ru–Ge system is not yet available, however several groups of authors investigated lanthanum–ruthenium–germanium combinations with respect to the formation and crystal structure of compounds.

Venturini et al. (1985b) reported on the X-ray powder diffraction study of the LaRuGe₃ compound from the sample which was prepared by heating a mixture of the starting components (La 3N, Ru 4N, Ge 4N) in evacuated quartz tube at 1073 K. The crystal structure was found to adopt the BaNiSn₃ type, a=0.4414, c=1.0123.

Venturini and Malaman (1996) reported on the single crystal refinement of the CeGa₂Al₂-type structure of the LaRu₂Ge₂ composition, a=0.42866, c=1.0121. Samples were prepared from stoichiometric amounts of pure elements. After a first reaction in a silica tube under argon, the mixture was melted in an induction furnace.

La₂Ru₃Ge₅ was found to crystallize with U₂Co₃Si₅-type (a = 1.00108, b = 1.2496, c = 0.59256, X-ray single-crystal diffraction method) by Venturini et al. (1989b).

The crystal structure of the LaRuGe compound was investigated by Welter et al. (1993b). It was found to adopt the PbFCl-type structure, a = 0.4294, c = 0.7019 (X-ray powder diffraction). The compound was prepared from commercially available high purity elements. A compact of a stoichiometric mixture was heated in sealed under argon silica tube at 1173 K for preliminary homogenization and then melted in an induction furnace.

La₃Ru₂Ge₂ compound was found to crystallize with La₃Ni₂Ga₂-type (a=0.5787, b=0.7946, c=1.3729, X-ray powder diffraction) from the arc melted and annealed at 870 K sample (Bodak et al. 1989a).

4.3.8. *La*–*Rh*–*Ge*

Venturini et al. (1985b) reported on the X-ray powder diffraction study of the LaRhGe₃ compound from the sample which was prepared by heating the mixture of starting components (La 3N, Rh 4N, Ge 4N) in evacuated quartz tube at 1073 K. The crystal structure was found to adopt the BaNiSn₃ type, a=0.4419, c=1.0046.

Venturini and Malaman (1996) reported on the single crystal refinement of the CeGa₂Al₂-type structure germanide of the LaRh₂Ge₂ composition, a = 0.4174, c = 1.0519. Samples were prepared from stoichiometric amounts of pure elements. After a first reaction in a silica tube under argon, the mixture was melted in an induction furnace.

La₂Rh₃Ge₅ was found to crystallize with U₂Co₃Si₅-type structure (a = 1.0135, b = 1.2177, c = 0.60410, X-ray single-crystal diffraction method) by Venturini et al. (1989a).

Gladyshevsky et al. (1991a) reported on the crystal structure for the La₃Rh₂Ge₂ compound (La₃Ni₂Ge₂ type, a = 0.5766, b = 0.8195, c = 1.3609; X-ray powder diffraction). The alloy was prepared by arc melting and annealing at 1070 K.

Francois et al. (1990) reported the crystal structure of LaRhGe₂ (CeNiSi₂ type, a = 0.4375, b = 1.715, c = 0.4367). For sample preparation, see LaFeGe₂ under La-Fe-Ge.

La₃Rh₄Ge₄ crystallizes with U₃Ni₄Si₄ type, a=0.4174, b=0.4241, c=2.5234 (Parthé and Chabot 1984).

4.3.9. La-Pd-Ge

Phase relations have not been established for the La–Pd–Ge system; formation and crystal structure for five ternary compounds have been reported so far.

Venturini and Malaman (1996) reported on the single crystal refinement of the CeGa₂Al₂-type structure germanide of the LaPd₂Ge₂ composition, a=0.43669, c=1.0027. For the details of synthesis, see LaRu₂Ge₂ under La–Ru–Ge.

Francois et al. (1990) reported the crystal structure of the LaPdGe₂ (CeNiSi₂ type, a = 0.4379, b = 1.737, c = 0.4382). For sample preparation, see LaFeGe₂ under La–Ru–Ge.

According to an X-ray powder diffraction analysis Hovestreydt et al. (1982) reported the compound LaPdGe adopted the KHg₂-type structure, a=0.4518, b=0.7409, c=0.7740. An alloy was arc melted under argon and annealed at 1270 K for 1–2 weeks. Starting materials were La (3N), Pd (4N) and Ge (5N).

The crystal structure of the compound LaPd₂Ge was found to be of the YPd₂Si type (a=0.7711, b=0.6972, c=0.5828; X-ray powder diffraction) by Jorda et al. (1983). The sample was obtained by induction heating of pressed powder compacts in a levitation coil under an argon atmosphere pressure of 4 atm. After the rapid reaction in the liquid state the molten sample was dropped into a boron nitride crucible. Then alloy was annealed in evacuated quartz tube for 10 days at 1173 K. Starting materials were Pd 99.99 mass%, Ge, specpure quality, La 99.9 mass%.

Sologub et al. (1995a) reported on the X-ray powder analysis of the La₂PdGe₆ compound which was found to crystallize with the Ce₂CuGe₆ type structure, a=0.4211, b=0.4110, c=2.2265. The sample was synthesized by argon arc melting followed by a heat treatment at 870K for 150 hours. Starting materials used were obtained from Johnson & Matthey, UK (99.9 mass%).

4.3.10. La-Ag-Ge

A systematic study of the La–Ag–Ge system at 770 K was performed by Protsyk (1994). The samples were prepared by arc melting under argon and annealed in evacuated quartz ampoules at 770 K for 500 hours. Starting materials were La 99.98 mass%, Ag 99.9 mass% and Ge 99.99 mass%. Phase relations are characterized by the formation of four ternary compounds (see fig. 41).

Sologub et al. (1995a) reported on the X-ray powder analysis of the La₂AgGe₆ (2) compound which was found to crystallize with the Ce₂CuGe₆-type structure, a=0.43409, b=0.41598, c=2.1901. For the experimental details, see La₂PdGe₆ under La–Pd–Ge.

LaAgGe (3) with the LiGaGe-type of structure (a = 0.45587, c = 0.78969; X-ray powder diffraction data) was observed by Pecharsky et al. (1991) from arc melted alloy heat-treated at 1023 K in a helium-filled sealed quartz tube for one week. The lanthanum was 99.79 mass% pure; the silver was 99.99 mass% pure and the germanium was 99.999 mass% pure.

The existence of LaAg₂Ge₂ (1) (CeGa₂Al₂-type structure, a = 0.4358, c = 1.0982) and LaAg_{0.8}Ge_{1.2} (4) (AlB₂ type, a = 0.4366, c = 0.4280) was reported by Protsyk (1994) from X-ray powder diffraction of alloy annealed at 773 K.



Fig. 41. La-Ag-Ge, isothermal section at 770 K.

4.3.11. La-Os-Ge

Little information exists on the interaction of lanthanum and osmium with germanium. One ternary compound was observed and characterized within the La–Os–Ge system. The crystal structure of the LaOsGe₃ compound (BaNiSn₃ type, a=0.4441, c=1.0124; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from the sample which was prepared by heating a compacted mixture of the starting materials (La in pieces, 99.9 mass%; Os and powder Ge, 99.99 mass%) in an evacuated quartz tube at 1073 K.

4.3.12. La–Ir–Ge

No ternary phase diagram has been established for the La-Ir-Ge system, however five ternary compounds have been characterized.

Venturini et al. (1985b) reported on the X-ray powder diffraction study of the LaIrGe₃ compound from a sample prepared by heating a mixture of starting components (La 3N, Ir 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to be BaNiSn₃ type, a = 0.4428, c = 1.0042.

La₂Ir₃Ge₅ was found to crystallize with U₂Co₃Si₅-type structure (a = 1.0218, b = 1.2028, c = 0.6091, X-ray single-crystal diffraction method) by Venturini et al. (1989b).

Francois et al. (1990) reported the crystal structure of LaIrGe₂ (CeNiSi₂ type, a = 0.4389, b = 1.716, c = 0.4389). For sample preparation, see LaFeGe₂ under La-Fe-Ge.

According to X-ray powder diffraction analysis reported by Hovestreydt et al. (1982) the compound LaIrGe adopted the LaPtSi-type structure, a = 0.43166, c = 1.4430. The alloy was arc melted under argon and annealed at 1270 K for 1–2 weeks. Starting materials were La (3N), Ir (4N) and Ge (5N).

LaIr₂Ge₂ is isotypic with the crystal structure of CaBe₂Ge₂ with lattice parameters a = 0.4273, c = 1.0134 (Francois et al. 1985).

Verniere et al. (1995) observed the existence of the $La_4Ir_{13}Ge_9$ compound with $Ho_4Ir_{13}Ge_9$ -type structure from an arc melted sample annealed at 1170 K for 8 days. No lattice parameters were given. The purity of the starting elements was 3N for the lanthanum, 4N for the iridium and 6N for the germanium.

4.3.13. La-Pt-Ge

Francois et al. (1990) reported the crystal structure of LaPtGe₂ (CeNiSi₂ type, a = 0.4404, b = 1.720, c = 0.4404). For sample preparation, see La–Fe–Ge.

According to X-ray powder diffraction analysis reported by Hovestreydt et al. (1982) the compound LaPtGe adopted the LaPtSi-type structure, a=0.4266, c=0.14970. The alloy was arc melted under argon and annealed at 1270 K for 1–2 weeks. Starting materials were La (3N), Pt (4N) and Ge (5N).

The existence of the LaPt₂Ge₂ compound (CeGa₂Al₂ type, a=0.4412, c=0.9923) was reported by Rossi et al. (1979) from X-ray powder diffraction of the induction melted sample which was annealed at 773 K for 1 week. Starting components were La (3N), Pt (4N) and Ge (4N). Venturini et al. (1989a) investigated the crystal structure of LaPt₂Ge₂ from an arc melted sample annealed at 1273 K for 5 days. The crystal structure was found to belong to a new structure type, a=0.4301, b=0.4346, c=0.9682, $\beta=91.26^{\circ}$. Starting materials were La (3N), Pt (4N) and Ge (4N).

4.3.14. La-Au-Ge

No ternary phase diagram exists for the La–Au–Ge system, however, a ternary compound of lanthanum with gold and germanium of the 1:1:1 stoichiometric ratio has been identified and studied by means of X-ray and metallographic analyses by Rossi et al. (1992). The LaAuGe compound was found to adopt the LiGaGe-type structure with lattice parameters a = 0.4463, c = 0.8169. The sample was prepared by melting the metals (around 99.9 mass% for lanthanum and 99.99 mass% for gold and germanium) in an induction furnace and annealing at 1070 K for one week.

4.4. Ce-d element-Ge systems

4.4.1. Ce-Mn-Ge

The phase equilibria in the Ce–Mn–Ge system (fig. 42) have been investigated by Konyk (1989) by means of X-ray analysis of 104 alloys which were arc melted and subsequently annealed in evacuated silica tubes for 400–720 h at 670 K and finally quenched in water. Starting materials were Ce 99.85 mass%, Mn 99.91 mass% and Ge 99.99 mass%. The existence of one ternary compound was confirmed [CeMn₂Ge₂ (1)] and the formation of three new ternary cerium manganese germanides was observed [Ce₂MnGe₆ (2), Ce₂MnGe₅ (3) and CeMnGe (4)].



Fig. 42. Ce–Mn–Ge, isothermal section at 670 K.

The formation of the CeMn₂Ge₂ compound (CeGa₂Al₂ type, a=0.4144, c=1.0970; for sample preparation, see LaMn₂Ge₂) was reported in an early investigation of the ternary rare-earth germanides with the stoichiometric ratio 1:2:2 by Rossi et al. (1978b). Crystallographic characteristics after Konyk (1989) are as follows: CeGa₂Al₂ type, a=0.4135, c=1.0928.

The Ce₂MnGe₆ compound crystallizes with the Ce₂CuGe₆-type of structure with lattice parameters a = 0.4103, b = 0.4342, c = 2.188 (Konyk 1989).

Ce₂MnGe₅ was reported by Konyk (1989) to crystallize with a new structure type, a=0.4308, b=0.4170, c=2.1134 (X-ray powder diffraction data).

CeMnGe was found to be isostructural with the PbFCl type, a=0.4235, c=0.7393 (Konyk 1989). The crystal structure of CeMnGe was recently confirmed by Welter et al. (1995) (PbFCl type, a=0.4235, c=0.7386; powder X-ray diffraction). For details of the experimental procedure, see LaMnGe.

4.4.2. Ce-Fe-Ge

The isothermal sections for the Ce–Fe–Ge phase diagram at 870 K were reported by Salamakha et al. (1996a) from a combined X-ray and micrography examination of 139 alloys. For details of sample preparation, see Ce–Mn–Ge. The microstructure of the alloys was revealed by etching in dilute solutions of HCl and HF. Starting materials were Ce 99.85 mass%, Fe 99.90 mass%, Ge 99.99 mass%.

The phase relations are characterized by the formation of seven ternary compounds (fig. 43); the crystal structure has been determined for three of these. Mutual solid solubilities of the binary compounds have been found to be insignificantly small. Crystallographic characteristics for these ternary compounds are summarized in table 12.



Fig. 43. Ce–Fe–Ge, isothermal sections at 870 K (0–50 at.% Ce) and at 670 (50-100 at.% Ce).

Table 12 Crystallographic data for the ternary Ce-Fe-Ge compounds at 870 K

No.	Compound	Structure	Lattice	paramet	ers (nm)	Reference
			a	b	с	
1	~CeFe ₁₀ Ge ₉	unknown		-		Salamakha et al. (1996b)
2	CeFe ₂ Ge ₂	CeGa ₂ Al ₂	0.4070 0.4069		1.0483 1.04495	Rossi et al. (1978a) Bara et al. (1990)
3 4	CeFeGe ₃	BaNiSn ₃	0.4339		0.9974	Salamakha et al. (1996b)
4 5	$\sim Ce_3 Fe_2 Ge_7$ CeFe _{0.64} Ge ₂	CeNiSi ₂	0.4278	1.6608	0.4150	Pecharsky et al. (1996)
6 7	~Ce ₂ FeGe ₄ ~Ce ₆ FeGe ₁₃	unknown unknown				Salamakha et al. (1996b) Salamakha et al. (1996b)

4.4.3. *Ce–Co–Ge*

Phase equilibria in the Ce–Co–Ge system have been determined by Konyk (1989) by means of powder X-ray and micrographic analyses of 160 ternary alloys at 870 K (0– 50 at.% Ce) and at 670 K (50–100 at.% Ce) (fig. 44). The phase relations are characterized by the formation of eleven ternary compounds and by the existence of two substitutional solid solution ranges: Ge in CeCo₅ (12 at.%) and Ge in Ce₂Co₁₇ (10 at.%). For sample preparation, see Ce–Mn–Ge. The purity of the starting materials was Ce 99.85 mass%, Co 99.90 mass%, Ge 99.99 mass%.

Crystallographic data for the ternary compounds are summarized in table 13.



Fig. 44. Ce-Co-Ge, isothermal sections at $870\,K$ (0–50 at.% Ce) and at 670 (50-100 at.% Ce).

No.	Compound	Structure	Lattice	e paramete	ers (nm)	Reference
			a	b	с	
1	CeCo ₂ Ge ₂	$CeGa_2Al_2$	0.4071		1.0170	McCall et al. (1973b)
2	Ce ₂ Co ₃ Ge ₅	$Lu_2Co_3Si_5$	1.1376	0.5847	1.1796 $\gamma = 120.7$	Konyk (1989) 77º
		$U_2Co_3Si_5$	0.9814	1.184	0.5862	Venturini et al. (1986b)
3	CeCoGe ₃	BaNiSn ₃	0.4329 0.4319 0.4317		0.9850 0.98298 0.9833	Konyk (1989) Pecharsky et al. (1993) Venturini et al. (1985b)
1	CeCoGe ₂	CeNiSi ₂	0.4253 0.4245	1.6773 1.674	0.4213 0.4197	Pecharsky et al. (1989) Méot-Meyer et al. (1985a)
5	~Ce ₃ CoGe ₆	unknown				Konyk (1989)
5	~Ce ₁₅ Co ₄ Ge ₃₁	unknown				Konyk (1989)
7	CeCoGe	PbFCl	0.4198 0.4170		$0.6887 \\ 0.6865$	Konyk (1989) Welter et al. (1993a)
3	CeCo _{0.5} Ge _{1.5}	AlB ₂	0.4177 0.4182		0.4233 0.4151	Konyk (1989) Gladyshevsky and Bodak (1965)
9	Ce ₃ CoGe ₂	La ₃ NiGe ₂	1.1951	0.4302	1.1477	Konyk (1989)
10	~Ce ₅ CoGe ₄	unknown				Konyk (1989)
11	~Ce ₅ CoGe ₂	unknown				Konyk (1989)

Table 13



Fig. 45. Ce–Ni–Ge, isothermal sections at 870 K (0–50 at.% Ce) and at 670 (50-100 at.% Ce).

4.4.4. *Ce–Ni–Ge*

Information about the phase equilibria in the Ce–Ni–Ge system is due to the work of Salamakha et al. (1996b) who employed X-ray phase analysis of 227 alloys which were arc melted and annealed at 870 K (0–50 at.% Ce) and 670 K (50–100 at.% Ce) in evacuated quartz tubes for two weeks (fig. 45). Twenty ternary compounds were found and characterized. A large homogeneity range was observed for the CeNi₅ compound by the same authors; the maximum concentration of Ge in Ce(Ni, Ge)₅ solid solution was indicated as 15 at.%.

Crystallographic information on the ternary compounds is summarized in table 14 (overleaf).

One more compound was observed by Belsky et al. (1987) in arc melted alloys, Ce₅NiGe₂. A new structure type was reported with lattice parameters a=1.1760, c=0.6429.

4.4.5. Ce–Cu–Ge

Salamakha et al. (1996c) were the first to derive the phase equilibria in an isothermal section at 870 K, employing room-temperature X-ray powder diffraction analysis. Alloys were synthesized by arc melting proper amounts of the constituent elements (Ce 99.85 mass%, Cu 99.99 mass%, Ge 99.99 mass%) under high purity argon on a water cooled copper hearth. Finally alloys were annealed at 870 K in evacuated quartz tubes for two weeks and quenched in water. Phase-field distributions are characterized by existence of eight ternary compounds and one solid solution originating at CeGe_{2-x}. The solidsolution limit was established as 10 at.% Cu. The isothermal section of the Ce–Cu–Ge system at 870 K is presented in fig. 46.

No.	Compound	Structure	Lattice	paramete	rs (nm)	Reference
			a	b	с	
1	CeNi _{8.5} Ge _{4.5}	CeNi _{8.5} Si _{4.5}	0.79702		1.17516	Salamakha et al. (1996c)
2	CeNi ₂ Ge ₂	CeGa ₂ Al ₂	0.4150		0.9854	Bodak et al. (1966)
3	Ce ₂ Ni ₃ Ge ₅	U2Co3Si5	0.9790	1.1842	0.5928	Salamakha et al. (1996c)
4	CeNiGe ₃	SmNiGe ₃	0.4140	2.1824	0.4174	Salamakha et al. (1996c)
5	Ce ₂ NiGe ₆	Ce ₂ CuGe ₆	0.40695	0.41668	2.1705	Salamakha et al. (1996c)
6	CeNiGe ₂	$CeNiSi_2$	0.4260 0.4244	1.6793 1.6647	0.4215 0.4199	Salamakha et al. (1996c) Bodak et al. (1966)
7	Ce ₃ Ni ₂ Ge ₇	$U_3Fe_2Si_7$	0.4243	2.5758	0.4289	Konyk (1988)
8	Ce ₃ Ni ₄ Ge ₄	$U_3Ni_4Si_4$	0.41162	0.41829	2.3962	Salamakha et al. (1996c)
9	CeNiGe	TiNiSi	0.72418	0.43078	0.72408	Salamakha et al. (1996c)
10	Ce(Ni,Ge) ₂	AlB_2	0.41618- 0.41734	_	0.42665 0.41926	-Salamakha et al. (1996c)
11	~Ce _{4.7} Ni _{1.3} Ge _{4.0}	unknown				Salamakha et al. (1996c)
12	~Ce ₂ NiGe	unknown				Salamakha et al. (1996c)
13	Ce ₃ NiGe ₂	La ₃ NiGe ₂	1.1924	0.4311	1.1624	Bodak et al. (1982)
14	~Ce _{5.0} Ni _{0.8} Ge _{4.2}	unknown				Salamakha et al. (1996c)
15	~Ce _{5.0} Ni _{0.4} Ge _{4.6}	unknown				Salamakha et al. (1996c)
16	$Ce_{11}Ni_4Ge_6$	$La_{11}Ni_4Ge_6$	1.8236	0.4321 $\gamma = 106.7$	1.3939	Salamakha et al. (1996c)
17	~Ce _{5.2} Ni _{0.8} Ge _{4.0}	unknown				Salamakha et al. (1996c)
18	~Ce ₁₁ Ni ₄ Ge ₅	unknown				Salamakha et al. (1996c)
19	~Ce ₅ Ni ₂ Ge	unknown				Salamakha et al. (1996c)
20	~Ce ₅ NiGe ₂	unknown				Salamakha et al. (1996c)

Table 14 Crystallographic data for the ternary Ce–Ni–Ge compounds

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented were $CeCu_{1-0.67}Ge_{1-1.33}$ with a=0.4296-0.4197, c=0.3988-0.4215. Salamakha et al. (1996c) reported on the existence of two compounds with AlB₂-type within the Ce–Cu–Ge system at 870 K: CeCuGe (5) (a=0.4316, c=0.3967) and CeCu_{0.6-0.8}Ge_{1.4-1.2} (6) (a=0.4214–0.4188, c=0.4206-0.4264). Iandelli (1993) confirmed AlB₂-type (a=0.4308 c=0.3966, X-ray powder analysis) from an alloy of the stoichiometric composition which was prepared from a mixture of filings or powders of the metals (cerium 99.7 mass%, copper and germanium 99.99 mass%) which were sealed in tantalum crucibles under argon followed by melting in an induction furnace; afterwards the sample was annealed for 10 days at 1023 K.

Konyk et al. (1988) reported on the crystal structure of Ce_2CuGe_6 (2) alloy prepared by arc melting under argon and annealed at 870 K in an evacuated quartz tube for 720 h. From X-ray powder diffraction analysis a new structure type was suggested, a=0.40756, b=



Fig. 46. Ce–Cu–Ge, isothermal sections at 870 K (0–50 at.% Ce) and at 670 (50-100 at.% Ce).

0.42152, c = 2.15408. The crystal structure was confirmed later by Sologub et al. (1995a), a = 0.42116, 0.40725, c = 2.1584 (X-ray powder analysis).

Rieger and Parthé (1969b) prepared CeCu₂Ge₂ (1) with the CeGa₂Al₂-type structure, a=0.4172, c=1.0212.

Francois et al. (1990) reported the crystal structure of $CeCu_{0.86}Ge_2$ (4) (CeNiSi₂ type, a=0.4276, b=1.729, c=0.4145). For sample preparation, see LaFeGe₂.

The Ce₂Cu₃Ge₃ compound (3) was found to crystallize with a new structure type, a=0.41680, c=1.7409, c=0.42108, X-ray powder data (Konyk 1988). For sample preparation, see Ce–Cu–Ge.

Salamakha et al. (1996c) reported the existence of two cerium copper germanides of unknown structure, $Ce_{0.60}Cu_{0.25}Ge_{0.15}$ (7) and $Ce_{0.60}Cu_{0.05}Ge_{0.35}$ (8), from X-ray powder diffraction of the alloys which were prepared in the same manner as discussed above.

4.4.6. *Ce*–*Zn*–*Ge*

The isothermal section of the equilibrium phase diagram of the Ce–Zn–Ge system at 470 K has been investigated by Opainych (1996) by X-ray powder diffraction analysis. Samples were prepared by argon arc melting from ingots of the high-purity elements (Ce 99.97 mass%, Zn 99.98 mass%, Ge 99.99 mass%) under a pressure of 1.1 atm. Weight losses due to vaporization while melting were compensated beforehand by extra amounts of Zn (about 0.5 mass%). The arc melted buttons were annealed at 470 K for 1500 hours in evacuated quartz tubes and finally quenched by submerging the capsules into cold water.

The phase relations after Opainych (1996) are characterized by the formation of eight ternary compounds (fig. 47). The solid solubility of the third component in the Ce–Zn and Ce–Ge binary compounds has been found to be negligible.



The Ce₄Zn₈Ge_{11-x} (2) compound was found to crystallize in an own structure type with lattice parameters a = 0.59468, c = 2.4740 (Opainych 1996; X-ray single-crystal analysis). For sample preparation, see above.

Opainych (1996) reported on the investigation of Ce₂Zn₁₅Ge₂ (Ce₂Al₂Co₁₅ type, a=0.9021, c=1.3787) (1), CeZn_{1.8}Ge_{1.2} (AuCu₃ type, a=0.5420) (3) and Ce(Zn, Ge)₂ (α -ThSi₂ type, a=0.4231, c=1.4219) (5) from X-ray powder analysis of arc melted alloys annealed at 470 K.

The existence of four ternary phases with unknown structure has been observed by Opainych (1996) in the course of investigating the isothermal section of the Ce–Zn–Ge system at 470 K. They exist at the following compositions: $\sim Ce_7Zn_8Ge_5$ (4), $\sim Ce_2Zn_2Ge$ (6), $\sim Ce_9Zn_3Ge_8$ (7) and $\sim Ce_6Zn_3Ge$ (8).

One more ternary compound which was not observed in the course of phaseequilibrium studies, was characterized by Rossi and Ferro (1996). $CeZn_{1.5}Ge_{0.5}$ was found to be isotypic with an AlB₂ type, a=0.4447, c=0.3924 from X-ray powder diffraction of an induction melted alloy which was afterwards annealed at 1070 K for one week. An electronic micrographic examination as well as microprobe microanalysis were carried out. The metals employed in the synthesis of samples had a nominal purity of 99.9 mass% for cerium, and 99.999 mass% for other metals.

4.4.7. Ce-Ru-Ge

The phase equilibria in the Ce–Ru–Ge system have been investigated by Shapiev (1993) by means of X-ray and metallographic analyses of 125 ternary alloys, which were arc



Fig. 48. Ce–Ru–Ge, isothermal section at 870 K.

melted and subsequently annealed in evacuated silica tubes at 870 K for 1000 hours and finally quenched in water. Starting materials were Ce 99.0 mass%, Ru 99.99 mass%, Ge 99.99 mass%. According to phase diagram, seven ternary compounds exist within the Ce–Ru–Ge system at 870 K (fig. 48). The mutual solid solubilities of binary compounds were found to be small, i.e. approximately 1-2 at.% of third component.

Early investigations of the CeRu₂Ge₂ (1) compound determined it to have the CeGa₂Al₂-type structure: a = 0.4263, c = 1.008 after Felner and Nowik (1985) from X-ray powder analysis of induction melted alloy and a = 0.4270, c = 1.0088 (Francois et al. 1985) from X-ray powder analysis of alloy obtained by powder metallurgical reaction at 1273 K. Starting components were Ce (3N), Ru (4N) and Ge (4N). The crystal structure type was confirmed by Shapiev (1993) with lattice parameters a = 0.42717, c = 1.0054 from arc melted alloy annealed at 870 K.

Venturini et al. (1986b) and Shapiev (1993) reported the structure for the Ce₂Ru₃Ge₅ compound (2) crystallizing with the U₂Co₃Si₅-type structure. Lattice parameters were reported to be a=0.99197, b=1.238, c=0.5887 (Venturini et al. 1986b; X-ray powder diffraction; for sample preparation, see La₂Ru₃Ge₅) and a=1.003, b=1.204, c=0.5895 (Shapiev 1993).

The crystal structure of the CeRuGe compound (4) was investigated by Welter et al. (1993b). It was found to adopt the PbFCl type, a=0.4275, c=0.6871 (X-ray powder diffraction). The compound was prepared from commercially available high-purity elements. A compacted stoichiometric mixture pellet was heated to 1173 K under argon in a sealed silica tube for preliminary homogenization and then melted in an induction furnace. Shapiev (1993) reported the same crystal structure with slightly different lattice parameters: a=0.4195, c=0.6916.

Pr₃Rh₄Sn₁₃-type structure was announced for the Ce₃Ru₄Ge₁₃ compound (a=0.9045) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. Starting materials were Ce (3N), Ru (3N), Ge (6N). Ghosh et al. (1995) reported on combined X-ray and neutron diffraction studies of the Ce_{4-x}Ru₄Ge_{12+x} alloys (a=0.90661 for x=0 and a=0.90494 for x=1). The samples were arc melted and annealed at 1170 K for two weeks. At variance with these data, Shapiev observed CeRuGe₃ (3) with the ScNiSi₃ type, lattice parameters a=2.185, b=0.4234, c=0.4285, from X-ray powder analysis of arc melted alloy annealed at 870 K.

Gladyshevsky et al. (1992) reported on the existence of the Ce₅RuGe₂ (7) compound with a S₅HfY₂-anti-type structure, a = 1.2255, b = 0.8898, c = 0.8008 (X-ray single-crystal data). The single crystal was obtained from an alloy which was arc melted and annealed at 870 K.

Two compounds of unknown structure [$\sim Ce_2RuGe$ (5) and $\sim Ce_5Ru_2Ge$ (6)] were observed by Shapiev (1993) from arc melted samples annealed at 870 K.

Ce₃Ru₂Ge₂ was found to crystallize with La₃Ni₂Ga₂-type (a=0.5751, b=0.7934, c=1.3657, X-ray powder diffraction) from an arc melted and sample annealed at 870 K (Bodak et al. 1989b). This phase is not shown in the Ce–Ru–Ge phase diagram of fig. 48.

4.4.8. Ce-Rh-Ge

The phase equilibria in the Ce–Rh–Ge system have been investigated by Shapiev (1993) by means of X-ray and metallographic analyses of 219 ternary alloys, which were arc melted and subsequently annealed in evacuated silica tubes for 1000 hours at 870 K and finally quenched in water. Starting materials were Ce 99.0 mass%, Rh 99.99 mass%, Ge 99.99 mass%. According to the phase diagram, twenty ternary compounds exist within the Ce–Rh–Ge system at 870 K (fig. 49). The limits of solid solutions originating at binary Ce–Rh and Rh–Ge compounds are not indicated by Shapiev (1993).

Venturini et al. (1985b) reported on an X-ray powder diffraction study of the CeRhGe₃ compound (9) from a sample which was prepared by heating a mixture of starting components (Ce 3N, Rh 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to adopt the BaNiSn₃-type (a=0.4394, c=1.0026). Shapiev (1993) confirmed the crystal structure and reported the lattice parameters a=0.4394, c=1.0019.

Early investigations on the CeRh₂Ge₂ compound (7) determined the CeGa₂Al₂-type: a=0.4161, c=1.045 (Felner and Nowik (1985)) and a=0.4160, c=1.0438 (Francois et al. 1985). For sample preparation, see CeRu₂Ge₂. The crystal structure type was confirmed by Shapiev (1993): a=0.4154, c=1.0472 from X-ray powder diffraction of an alloy which was arc melted and annealed at 870 K.

Ce₂Rh₃Ge₅ (8) was found to crystallize with U₂Co₃Si₅-type (a = 1.0097, b = 1.209, c = 0.5987) by Venturini et al. (1986b) from X-ray powder analysis. Lattice parameters after Shapiev are a = 0.9856, b = 1.2049, c = 0.5851.

Hovestreydt et al. (1982) reported the crystal structure of the CeRhGe compound (15) (TiNiSi type, a=0.7424, b=0.4468, c=0.7120; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. Starting components were Ce (3N), Rh (4N)



Fig. 49. Ce-Rh-Ge, isothermal section at 870 K.

and Ge (5N). Shapiev (1993) confirmed the TiNiSi-type for the sample annealed at 870 K (a=0.7199, b=0.4352, c=0.7378; X-ray powder diffraction).

Gladyshevsky et al. (1991a) reported on the crystal structure of the Ce₃Rh₂Ge₂ (18) compound (La₃Ni₂Ge₂ type, a=0.57001, b=0.8099, c=1.3461; X-ray single-crystal method). For the details of sample preparation, see La₃Rh₂Ge₂.

CeRh_{1-x}Ge_{2+x} (13) with a new structure type was investigated by Shapiev et al. (1991): a = 0.4322, b = 0.4329, c = 1.7107 by a single-crystal method. For the experimental procedure, see Ce–Rh–Ge.

Verniere et al. (1995) mentioned the existence of Ce₄Rh₁₃Ge₉ (4) with Ho₄Ir₁₃Ge₉type. No lattice parameters were given. For experimental details and purity of starting metals see La–Ir–Ge. Salamakha and Sologub (1997) investigated the crystal structure and established the lattice parameters a=0.4055, b=1.1372, c=1.9804 (X-ray powder data; arc melted sample annealed at 870 K).

Investigating the phase diagram, Shapiev (1993) established the crystal structure for Ce₃Rh₄Ge₁₃ (5) (Y₃Co₄Ge₁₃ type, a=0.908), for CeRh_{1.4}Ge_{0.6} (14) (MgZn₂ type, a=0.5310, c=0.8950) and for CeRh_{0.5}Ge_{1.5} (16) (AlB₂ type, a=0.4220, a=0.4208), and observed ten compounds with unknown structures: CeRh₇Ge₆ (1), CeRh₆Ge₂ (2), CeRh₅Ge₃ (3), Ce₃Rh₉Ge₅ (6), Ce₂Rh₅Ge₂ (10), Ce₂Rh₄Ge₃ (11), CeRh₂Ge (12), Ce₂RhGe₂ (17), Ce₂RhGe (19), Ce₇RhGe₂ (20).

4.4.9. Ce-Pd-Ge

A systematic study of the Ce–Pd–Ge system at 870 K was performed by Gribanov (1994) over the whole concentration region by means of X-ray powder and single-crystal analyses as well as using metallography and microprobe analyses. The samples were prepared



Fig. 50. Ce-Pd-Ge, isothermal section at 870 K.

by arc melting under argon the proper amount of starting elements, and annealed in evacuated quartz ampoules at 870 K for 720 hours. Starting materials were 99.8 mass% pure or better.

The phase-field distribution in the isothermal section at 870 K is characterized by existence of sixteen ternary compounds (fig. 50). Maximum solubility of germanium in the binary compounds of Ce–Pd and Ce–Ge systems is 12 at.% Ge for CePd₃. CeGe_{2-x} dissolves 11 at.% Pd. Solubility of cerium in the palladium germanides was found to be negligible. As reported by Gribanov (1994), homogeneity fields were observed for the compounds CePd₂Ge₂ (3) and Ce(Pd,Ge)₂ (4).

The crystal structure of the compounds Ce₃Pd₂₀Ge₆ (8) (own structure type, a = 1.24453, Gribanov et al. 1994) and Ce₇Pd₄Ge₂ (12) (own structure type, a = 0.9315, b = 1.2277, c = 1.2698, $\beta = 114.31^{\circ}$, Gribanov et al. 1993b) was investigated by the X-ray single-crystal analysis of specimens obtained from alloys annealed at 870 K.

The existence of the CePd₂Ge₂ (3) compound (CeGa₂Al₂ type, a=0.4369, c=1.0055) was reported by Rossi et al. (1979). For details of sample preparation see LaMn₂Ge₂ under La–Mn–Ge. The existence of the 1:2:2 compound was confirmed by Gribanov (1994) (CeGa₂Al₂ type, a=0.4359, b=1.001; X-ray powder diffraction) while investigating the Ce–Pd–Ge phase diagram at 870 K.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982) the compound CePdGe (5) adopts the KHg₂-type structure. For sample preparation, see La–Pd–Ge. Starting materials were Ce (3N), Pd (4N) and Ge (5N). The existence of the CePdGe compound was later confirmed by Gribanov (1994) (KHg₂ type, a=0.4480, b=0.7288, c=0.7672; X-ray powder data).

The crystal structure of the compound CePd₂Ge (10) was found to be of the YPd₂Si type (a = 0.7668, b = 0.6972, c = 0.5757; X-ray powder diffraction) by Jorda et al. (1983).

For the experimental procedure, see LaPd₂Ge under La-Pd-Ge. Starting materials were Pd 99.99 mass%, Ge specpure quality; Ce 99.9 mass%. Gribanov (1994) confirmed the structure type and determined the lattice parameters a = 0.6980, b = 0.7702, c = 0.5789 from X-ray powder analysis.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Ce₂PdGe₆ (1) compound which was found to crystallize with the Ce₂CuGe₆ type, a=0.41784, b=0.40900, c=2.2043. For the experimental procedure, see La₂PdGe₆ under La–Pd–Ge. The starting materials used were obtained from Johnson & Matthey, UK (99.9 mass%).

Ce(Pd,Ge)₂ (4) was found to crystallize with the AlB₂ type, a = 0.42946, c = 0.41732 (Gribanov 1994; X-ray powder diffraction data).

The formation of nine more ternary phases with unknown structure has been observed by Gribanov et al. (1994) while investigating the isothermal section of the Ce–Pd–Ge system at 870 K: $\sim Ce_{0.05}Pd_{0.68}Ge_{0.27}$ (7), $\sim Ce_{0.10}Pd_{0.60}Ge_{0.30}$ (6), $\sim Ce_{0.16}Pd_{0.60}Ge_{0.24}$ (9), $\sim Ce_{0.25}Pd_{0.17}Ge_{0.58}$ (2), $\sim Ce_{0.50}Pd_{0.30}Ge_{0.20}$ (11), $\sim Ce_{0.50}Pd_{0.20}Ge_{0.30}$ (14), $\sim Ce_{0.58}Pd_{0.20}$ Ge_{0.22} (13), $\sim Ce_{0.62}Pd_{0.08}Ge_{0.30}$ (15) and $\sim Ce_{0.75}Pd_{0.10}Ge_{0.15}$ (16).

4.4.10. *Ce–Ag–Ge*

The phase equilibria in the Ce–Ag–Ge system were investigated by Protsyk (1994) by means of X-ray analysis of 80 alloys which were arc melted and subsequently annealed in evacuated silica tubes for 500 h at 770 K and finally quenched in water. Starting materials were Ce 99.85 mass%, Ag 99.9 mass% and Ge 99.99 mass%. The formation of ten new ternary silver germanides of cerium was observed (fig. 51). The CeAg₅ compound was found to dissolve 10 at.% Ge. Crystal structure was established for four germanides; six ternary compounds were reported to be of unknown structure type. Crystallographic characteristics of ternary cerium silver germanides are listed in table 15.



Fig. 51. Ce–Ag–Ge, isothermal section at 770 K.

No.	. Compound	mpound Structure		neters (nm)	Reference
			a	a t	c
1	CeAg ₂ Ge ₂	$CeGa_2Al_2$	0.4296	1.0955	Protsyk (1994)
3	Ce ₂ AgGe ₆	Ce ₂ CuGe ₆	0.43089 0.41	44 2.1674	Sologub et al. (1995a)
5	CeAgGe	LiGaGe	0.45442	0.77108	Pecharsky et al. (1991)
6	CeAg _{0.8} Ge _{1.2}	$A1B_2$	0.4375	0.4129	Protsyk (1994)
8	CeAg _{0.33} Ge _{1.67}	α -ThSi ₂	0.4239	1.4697	Protsyk (1994)

 Table 15

 Crystallographic data for the ternary Ce-Ag-Ge compounds

4.4.11. Ce–Os–Ge

The only information on the interaction of components in the Ce–Os–Ge system is from Segre et al. (1981a) who announced a $Pr_3Rh_4Sn_{13}$ -type for the Ce₃Os₄Ge₁₃ compound (*a*=0.9075) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. Starting materials were Ce (3N), Os (3N), Ge (6N).

4.4.12. Ce–Ir–Ge

No ternary phase diagram has been established for the Ce–Ir–Ge system, however five ternary compounds have been observed and characterized by various groups of authors.

Ce₂Ir₃Ge₅ was found to crystallize with U₂Co₃Si₅-type (a = 1.0189, b = 1.197, c = 0.6060; X-ray powder diffraction method) by Venturini et al. (1985b).

Venturini et al. (1985b) reported on the X-ray powder diffraction study of the Ce₃Ir₄Ge₁₃ compound from a sample which was prepared by heating a mixture of starting components (Ce 3N, Ir 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃ type, a = 0.9061.

CeIr₂Ge₂ is isotypic with the crystal structure of CaBe₂Ge₂ with lattice parameters a = 0.4246, c = 1.0098 (Francois et al. 1985).

Verniere et al. (1995) observed the existence of the Ce₄Ir₁₃Ge₉ compound with a Ho₄Ir₁₃Ge₉ type from X-ray powder analysis and metallographic examination. No lattice parameters are available. For the experimental procedure, see La₄Ir₁₃Ge₉.

Hovestreydt et al. (1982) reported the compound CeIrGe to adopt the TiNiSi type, a = 0.7071, b = 0.4375, c = 0.7574, from X-ray powder diffraction. For sample preparation, see La-Pd-Ge.

4.4.13. Ce-Pt-Ge

A systematic study of the Ce–Pt–Ge system at 870 K was performed by Gribanov et al. (1996) over the whole concentration region by means of X-ray powder and single-crystal analyses as well as using metallography and microprobe analyses. The samples were prepared by arc melting under argon and annealed in evacuated quartz ampoules at 870 K for 720 hours. Starting materials were 99.8 mass% pure or better. In the metallographic studies, Pt-rich samples (>50 at.% Pt) were etched in an HNO₃+HCl (1:1) solution.



Fig. 52. Ce–Pt–Ge, isothermal section at 870 K.

A mixture of $HNO_3 + H_2O$ (2:1) was used for etching alloys with <50 at.% Ce. Ce-rich samples (>50 at.% Ce) were etched by highly diluted HNO₃.

Phase relations are characterized by the existence of twelve ternary compounds and by the formation of extended solid solutions originating at Ce–Pt and Ce–Ge binary compounds (see fig. 52). CePt₅ and CePt dissolve up to 20 at.% Ge. The maximum concentration of Ge in Ce₇(Pt, Ge)₃ was observed as 15 at.%. A large homogeneity range of not less than 24–33 at.% Ce was determined for the CePt₂ compound; the limits of extension of CePt₂ into the ternary system were not indicated by the author. The binary phases of the Pt–Ge system and the remaining binary phases in the other two systems dissolve less than 5 at.% of third component.

The crystal structures of the compounds Ce₃Pt₄Ge₆ (4) (own structure type, a=0.4419, b=0.4422, c=2.6222; Gribanov et al. 1992a), Ce₂Pt₇Ge₄ (10) (own structure type, a=1.9866, b=0.4089, c=1.1439; Gribanov et al. 1992b) and Ce₃Pt₂₃Ge₁₁ (9) (own structure type, a=1.71833; Gribanov et al. 1993a) were investigated by X-ray single-crystal analysis of specimens obtained from alloys annealed at 870 K. Ce(Pt, Ge)₂ (5) was found to crystallize with the AlB₂ type, a=0.4272, c=0.4204 (Gribanov et al. 1996; X-ray powder analysis).

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982) the compound CePtGe (7) adopted the KHg₂-type of structure, a=0.4450, b=0.7347, c=0.7615. For sample preparation, see La–Pd–Ge. The crystal structure was confirmed later by Rogl et al. (1989), a=0.44515, b=0.73439, c=0.76161 (X-ray powder diffraction), and by Gribanov et al. (1996), a=0.44455, b=0.7239, c=0.7609 (X-ray powder diffraction).

The existence of the CePt₂Ge₂ (3) compound (CeGa₂Al₂ type, a = 0.440, c = 0.987) was reported by Rossi et al. (1979). For sample preparation see LaMn₂Ge₂ under La–Mn–Ge.

Dommann et al. (1985) observed the CaBe₂Ge₂-type for the CePt₂Ge₂ compound with lattice parameters a=0.4397, c=0.9802 (X-ray single-crystal data) from an arc melted sample. Starting materials were Ce (3N), Ge (4N), Pt (3N). CaBe₂Ge₂-type was confirmed by Gribanov et al. (1996) for CePt₂Ge₂; a=0.44033, c=0.9808 from an alloy annealed at 870 K (X-ray powder diffraction) and was shown to exist over a wide composition range, see fig. 52. Venturini et al. (1989a) investigated the crystal structure of CePt₂Ge₂ from an arc melted sample annealed at 1273 K for 5 days. The crystal structure was found to belong to the LaPt₂Ge₂ type, a=0.4389, b=0.4402, c=0.9818, $\beta=90.83^\circ$. Starting materials were Ce (3N), Pt (4N) and Ge (4N).

Sologub et al. (1995a) reported on the X-ray powder analysis of the Ce₂PtGe₆ (1) compound which was found to crystallize with the Ce₂CuGe₆ type, a=0.41503, b=0.40858, c=2.2183. For sample preparation, see La₂PdGe₆ under La–Pd–Ge. Gribanov et al. (1996) confirmed the structure type and obtained the lattice parameters a=0.4142, b=0.4082, c=2.209 (X-ray powder diffraction).

Francois et al. (1987) reported the crystal structure of the CePtGe₂ (YIrGe₂ type, a = 0.4428, b = 1.648, c = 0.8795; X-ray powder data). The sample was prepared by heating the mixture of powders of starting components [Ce (3N), Ir (3N) and Ge (3N)] in an evacuated silica tube at 1173 K. The existence of the CePtGe₂ compound was not confirmed by Gribanov et al. (1996) at 870 K.

The formation of five more ternary phases with unknown structure has been observed by Gribanov et al. (1996) while investigating the isothermal section of the Ce–Pt–Ge system at 870 K. They exist at the compositions $\sim Ce_{11}Pt_{53}Ge_{36}$ (6), $\sim Ce_{20}Pt_{60}Ge_{20}$ (11), $\sim Ce_{25}Pt_{20}Ge_{55}$ (2), $\sim Ce_{40}Pt_{28}Ge_{32}$ (8), $\sim Ce_{62}Pt_{18}Ge_{20}$ (12).

4.4.14. Ce–Au–Ge

Little information exists about the Ce-Au-Ge system; three ternary germanides were characterized.

A ternary compound of cerium with gold and germanium of the stoichiometric ratio 1:1:1 was identified and studied by means of X-ray and metallographic analyses by Rossi et al. (1992). The CeAuGe compound was found to have the LiGaGe-type structure with lattice parameters a = 0.4464, c = 0.7910. The sample was prepared by melting the metals (~99.9 mass% for cerium and 99.99 mass% for gold and germanium) in an induction furnace and annealing at 1070 K for one week. The crystal structure of the CeAuGe compound has been confirmed by Pöttgen et al. (1996a) from an alloy which was prepared by melting a mixture of the elements in an arc furnace and subsequently annealing at 1070 K (a = 0.44603, c = 0.79360; X-ray powder data).

Ce₂AuGe₆ was reported to crystallize with a Ce₂CuGe₆ type, a=0.42587, b=0.41263, c=2.1852 (Sologub et al. 1995a; X-ray powder data). For sample preparation, see La₂PdGe₆ under La–Pd–Ge.

The structure of CeAu_{0.75}Ge_{1.25} was derived by Jones et al. (1997) from single-crystal X-ray data: AlB₂ structure type, a = 0.4335, c = 0.4226. The sample was prepared from the elemental components by arc melting and subsequent annealing at 1170 K.

4.5. Pr-d element-Ge systems

4.5.1. Pr-Mn-Ge

No phase diagram exists for the system Pr-Mn-Ge, however, a series of ternary compounds have been observed and characterized.

The $PrMn_2Ge_2$ compound have been prepared and studied by Rossi et al. (1978b). It was found to be of $CeGa_2Al_2$ type with following lattice parameters a=0.4117, c=1.0902. The alloy was obtain by melting under argon in an induction furnace. The samples were then annealed at 770 K for one week. Praseodymium used was of purity greater than 99.9 mass%, for manganese and germanium the purity was greater than 99.99 mass%.

A PrMnGe compound with PbFCI-type structure was observed by Welter et al. (1995); a=0.4182, c=0.7308. The compound was prepared from commercially available high purity elements. A compacted pellet of stoichiometric mixture was sealed under argon (100 mmHg) in a silica tube, heated at 1273 K as a preliminary homogenization treatment and then melted in an induction furnace. The resulting ingot was annealed for 2 weeks at 1173 K.

4.5.2. *Pr*–*Fe*–*Ge*

Phase equilibria for the complete isothermal section at 870 K have been determined by Fedyna (1988) using X-ray powder diffraction and microstructural analyses of 209 ternary alloys synthesized by arc melting ingots of Pr (99.75 mass%), Fe (99.90 mass%) and Ge (99.99 mass%). The alloys were annealed in evacuated quartz tubes for 500–900 hours at 870 K. The total number of compounds observed was nine. The mutual solid solubilities of the binary compounds were reported to be negligible. Phase equilibria in the isothermal section at 870 K are presented in fig. 53.

 $PrFe_6Ge_6$ (1) was observed and studied by Mruz et al. (1984). It was found to crystallize with YCo₆Ge₆ type, lattice parameters a = 0.5091, c = 0.4036, by X-ray powder diffraction



Fig. 53. Pr–Fe–Ge, isothermal section at 870 K.

of arc melted alloy annealed at 870 K. The existence of the PrFe₆Ge₆ compound was confirmed by Fedyna (1988) while constructing the isothermal section.

The formation and crystal structure of the $PrFe_2Ge_2$ (2) compound was reported in an early investigation of praseodymium-iron-germanium combinations by Rossi et al. (1978a,b): CeGa₂Al₂ type, a=0.4055, c=1.0540 was later confirmed by Bara et al. (1990), a=0.4060, c=1.0508. For sample preparation, see LaMn₂Ge₂ under La-Mn-Ge, and LaFe₂Ge₂ under La-Fe-Ge, respectively.

The crystal structures of four more compounds within Pr–Fe–Ge system at 870 K were determined by Fedyna (1988): PrFeGe₃ (3) with BaNiSn₃ type, a=0.4312, c=0.9932; PrFe_{1-x}Ge₂, x=0.45 (5) with CeNiSi₂ type, a=0.4253, b=1.6478, c=0.4130; Pr₄Fe_{1-x}Ge₇, x=0.15 (8) with Sm₄CoGe₇ type, a=0.42166, b=3.0520, c=0.41278; Pr₁₁₇Fe₅₂Ge₁₁₂ (9) with Tb₁₁₇Fe₅₂Ge₁₁₂ type, a=2.9428.

 $Pr_6Fe_{13}Ge$ (7) was found to adopt the Nd₆Fe₁₃Si type by Weitzer et al. (1990), a = 0.80986, c = 2.30836. For sample preparation, see La₆Co₁₃Ge under La–Co–Ge.

The crystal structures of two germanides $\sim Pr_{2.3}Fe_{1.7}Ge_6$ (4) and $\sim Pr_{2.7}Fe_{1.3}Ge_6$ (6) have not been solved yet.

4.5.3. Pr-Co-Ge

Isothermal sections of the Pr–Co–Ge system at 1070 K (0–33 at.% Pr) and 670 K (33– 100 at.% Pr) were derived by Fedyna (1988) employing X-ray phase and partly microstructural analyses of 287 alloys prepared by arc melting solid pieces of Pr (99.75 mass%), Co (99.90 mass%) and Ge (99.99 mass%). The melted buttons were then annealed in evacuated silica tubes for 500–900 hours. Thirteen ternary compounds were found to exist. The solubilities of cobalt in PrGe_{2-x} and Pr₅Ge₃ binaries were established as 11 at.% and 8 at.%, respectively, from the variation of lattice parameters. Figure 54 represents the



Fig. 54. Pr–Co–Ge, isothermal sections at 1070 K (0–33 at.% Pr) and at 670 (33–100 at.% Pr).

No.	Compound	Structure	Lattice	paramete	rs (nm)	Reference
			a	b	с	
1	$Pr_{1-x}(Co, Ge)_{13}, x=0.31$	CeNi _{8.5} Si _{4.5}	0.7932		1.1817	Fedyna (1988)
2	PrCo ₂ Ge ₂	CeGa ₂ Al ₂	0.4048		1.0178	Fedyna (1988)
3	$Pr_2Co_3Ge_5$	U ₂ Co ₃ Si ₅	0.9783	1.1896	0.5831	Fedyna (1988)
4	$PrCo_{1-x}Ge_3, x=0.136$	BaNiSn ₃	0.43107		0.98332	Fedyna (1988)
5	$\sim Pr_{2,3}Co_{2,1}Ge_{5,6}$	unknown				Fedyna (1988)
6	~Pr _{2.3} Co _{1.8} Ge _{5.8}	unknown				Fedyna (1988)
7	$\sim Pr_{2.5}Co_{1.5}Ge_{6.0}$	unknown				Fedyna (1988)
8	~Pr _{2.7} Co _{1.5} Ge _{5.8}	unknown				Fedyna (1988)
9	$PrCo_{1-x}Ge_2$,	CeNiSi ₂	0.4249–	1.6650-	0.4136-	Fedyna (1988)
	x = 0.10 - 0.52		0.4262	1.6770	0.4230	
10	PrCoGe	PbFC1	0.4181		0.6842	Fedyna (1988)
11	$PrCo_{0.5}Ge_{1.5}$	AlB_2	0.4163		0.4193	Fedyna (1988)
12	$Pr_{117}Co_{52}Ge_{112}$	Tb ₁₁₇ Fe ₅₂ Ge ₁₁₂	2.9318			Fedyna (1988)
13	Pr ₃ CoGe ₂	La ₃ NiGe ₂	1.1840	0.4272	1.1519	Fedyna (1988)

 Table 16

 Crystallographic data for the ternary Pr–Co–Ge compounds

isothermal sections of the Pr-Co-Ge system at 1070 K and 670 K.

Crystallographic information on the Pr-Co-Ge ternary compounds is summarized in table 16.

The crystal structure of $PrCoGe_3$ (BaNiSn₃ type, a=0.4307, c=0.9803; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample prepared by heating a compacted mixture of starting materials (Pr in pieces, 99.9 mass%; Co and Ge in powder, 99.99 mass%) in an evacuated quartz tube at 1073 K. Later the same structure type was indicated by Fedyna (1988) for a sample with composition $PrCo_{1-x}Ge_3$, x=0.136 (see table 16; X-ray powder diffraction data; for the experimental procedure, see above).

4.5.4. Pr–Ni–Ge

The isothermal sections of the Pr–Ni–Ge phase diagram at 870 K (0–50 at.% Pr) and at 670 K (50–100 at.% Pr) was constructed by Fedyna (1988) from X-ray powder and microstructural analyses of 255 alloys. A detailed description of the experimental procedure is given under Pr–Fe–Ge. Starting materials were Pr (99.75 mass%), Ni (99.99 mass%) and Ge (99.99 mass%).

The phase relations are characterized by the existence of eleven ternary compounds and by the formation of an extended homogeneity region for the $Pr(Ni,Ge)_{2-x}$ (9) compound as well as two solid solutions originating at $PrNi_5$ (20 at.% Ge) and $PrGe_{2-x}$ (9 at.% Ni). The isothermal section of the Pr–Ni–Ge system after Fedyna (1988) is presented in fig. 55.

Bodak et al. (1982) investigated the crystal structure of the Pr_3NiGe_2 compound (10) (Pr_3NiGe_2 structure type, a=1.1810, b=0.4293, c=1.1611) by the X-ray powder



Fig. 55. Pr–Ni–Ge, isothermal section at 870 K.

diffraction method. For sample preparation and purity of starting elements, see Y₃NiGe₂ under Y-Ni-Ge.

Early investigations of the interaction of germanium with praseodymium and nickel has shown the existence of PrNi_{0.6}Ge_{1.4} with AlB₂ type, a=0.4161, c=0.4207 (Gladyshevsky and Bodak 1965, Rieger and Parthé 1969a; X-ray powder diffraction). Fedyna (1988) confirmed the AlB₂-type for this composition and observed the formation of a large homogeneity field with the formula Pr(Ni_{0.42-0.28}Ge_{0.58-0.72})_{2-x}, x=0.14 (9) and lattice parameters a=0.4158-0.4150, c=0.4134-0.4220.

PrNi₂Ge₂ (2) is isotypic with CeGa₂Ge₂; a=0.4136, c=0.9844 (Rieger and Parthé 1969b; X-ray powder diffraction).

The crystal structures of seven other compounds have been studied by Fedyna (1988). $Pr_{1-x}(Ni,Ge)_{13}$, x=0.24 (1) belongs to the CeNi_{8.5}Si_{4.5}-type; Pr₂Ni₃Ge₅ (3) crystallizes with the U₂Co₃Si₅-type structure, a=0.9812, b=1.1832, c=0.5912 (powder X-ray diffraction data); PrNiGe₃ (4) is isostructural with the ScNiSi₃ type, a=2.1779, b= 0.41052, c 0.41440; Pr₂NiGe₆ (5) was reported to crystallize with the Ce₂CuGe₆ type, a=0.40343, b=0.41124, c=2.1722; Pr₃Ni₄Ge₄-(6) was claimed to adopt the U₃Ni₄Ge₄type structure, a=0.4098, b=0.4182, c=2.4013; PrNi_{1-x}Ge₂, x=0.33 (7) is isotypic with CeNiSi₂, a=0.4210, b=1.668, c=0.4160; PrNiGe (8) was found to be of TiNiSi type, a=0.72757, b=0.43429, c=0.72981.

Investigating the isothermal section, Fedyna (1988) observed the $\sim Pr_{0.5}Ni_{0.1}Ge_{0.4}$ (11) compound with unknown crystal.

4.5.5. Pr–Cu–Ge

Praseodymium-copper-germanium combinations were investigated by various groups of authors, however no isothermal section was constructed for the Pr-Cu-Ge system so far.

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented were $PrCu_{1-0.67}Ge_{1-1.33}$ with a=0.4374-0.4183, c=0.3971-0.4197. Iandelli (1993) confirmed the AlB₂-type (a=0.4288, c=0.3942; X-ray powder analysis) from the PrCuGe alloy which was prepared from mixed filings or powders of metals (praseodymium 99.7 mass%, copper and germanium 99.99 mass%) and sealed in tantalum crucibles under argon followed by melting in an induction furnace. Afterwards the sample was annealed for 10 days at 1023 K.

Sologub et al. (1995a) investigated the crystal structure of Pr_2CuGe_6 alloy which was prepared by arc melting under argon and annealed at 1070 K in an evacuated quartz tube for 150 h. From X-ray powder analysis the compound was determined to have the Ce₂CuGe₆-type structure, a = 0.41950, b = 0.40585, c = 2.1485.

Pr₂Cu₃Ge₃ was found to crystallize with the Ce₂Cu₃Ge₃ structure type, a = 0.4141, c = 1.7371, c = 0.4183, X-ray powder data (Konyk 1988). For sample preparation, see Ce-Cu-Ge.

Rieger and Parthé (1969b) synthesized $PrCu_2Ge_2$ with the CeGa₂Al₂-type structure, a=0.4154, c=1.0206.

The existence of a compound $Pr_6Cu_8Ge_8$ with the $Gd_6Cu_8Ge_8$ structure (a=1.421, b=0.6687, c=0.4293) was reported by Fedyna et al. (1995) from X-ray powder diffraction data of arc melted alloy annealed at 870 K.

Francois et al. (1990) reported the crystal structure of the $PrCu_{0.76}Ge_2$ compound (CeNiSi₂ type, a=0.4247, b=1.724, c=0.4109). For sample preparation, see LaFeGe₂ under La-Fe-Ge.

4.5.6. Pr-Zn-Ge

No isothermal section is available for the ternary Pr–Zn–Ge system, however one ternary compound was observed and characterized by Rossi and Ferro (1996). $PrZn_{1.5}Ge_{0.5}$ was found to crystallize with AlB₂ type, a=0.4440, c=0.3883, from X-ray powder diffraction of an alloy melted in an induction furnace and then annealed at 1070 K for one week. An electronic micrographic examination as well as microprobe microanalysis were carried out. The metals employed in sample synthesis had a nominal purity of 99.9 mass% for praseodymium, and 99.999 mass% for the other metals.

4.5.7. Pr-Ru-Ge

The phase diagram for the Pr–Ru–Ge system is not available yet, however several groups of authors investigated praseodymium–ruthenium–germanium combinations with respect to the formation and crystal structure of the compounds.

Early investigations of the $PrRu_2Ge_2$ compound determined the $CeGa_2Al_2$ -type: a = 0.4263, c = 1.0022 (Francois et al. 1985) from X-ray powder analysis of alloy obtained by powder metallurgical reaction at 1273 K. Starting components were Pr (3N), Ru (4N) and Ge (4N).

Venturini et al. (1986b) reported that the $Pr_2Ru_3Ge_5$ compound has the $U_2Co_3Si_5$ -type structure. The lattice parameters were reported as a=0.9933, b=1.247, c=0.5846 from X-ray powder diffraction.

 $Pr_3Rh_4Sn_{13}$ -type was announced for the $Pr_3Ru_4Ge_{13}$ compound (a=0.907) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. Starting materials were Pr (3N), Ru (3N), Ge (6N).

The crystal structure of the PrRuGe compound was investigated by Welter et al. (1993b). It was found to adopt the PbFCl type, a=4268, c=0.6842 (X-ray powder diffraction). The compound was prepared from commercially available high-purity elements. A compacted stoichiometric mixture in a silica tube sealed under argon was heated to 1173 K for preliminary homogenization and then melted in an induction furnace.

 $Pr_3Ru_2Ge_2$ was found to crystallize with the La₃Ni₂Ga₂ type (a=0.5699, b=0.7909, c=1.3593, X-ray powder diffraction) from an arc melted sample annealed at 870 K (Bodak et al. 1989a).

4.5.8. *Pr*–*Rh*–*Ge*

Phase equilibria in the system Pr-Rh-Ge have not been established yet, but at least six different ternary phases have been verified.

 $Pr_2Rh_3Ge_5$ was found to crystallize with $U_2Co_3Si_5$ -type structure (a=1.0073, b=1.209, c 0.5969) by Venturini et al. (1986b) from X-ray powder analysis.

Early investigations of the PrRh₂Ge₂ compound determined it to have the CeGa₂Al₂-type structure: a=0.4147, c=1.0436 (Francois et al. 1985). For sample preparation, see CeRu₂Ge₂ under Ce–Ru–Ge.

Venturini et al. (1985b) reported an X-ray powder diffraction study of the PrRhGe₃ compound from a sample prepared by heating of a mixture of the starting components (Pr 3N, Rh 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to adopt the BaNiSn₃ type, a=0.4383, c=1.0011.

Hovestreydt et al. (1982) reported the crystal structure of the PrRhGe compound (TiNiSi type, a=0.7376, b=0.4476, c=0.7124; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. Starting components were Pr (3N), Rh (4N) and Ge (5N).

Gladyshevsky et al. (1991a) reported on the crystal structure of $Pr_3Rh_2Ge_2$ (La₃Ni₂Ge₂ type, a=0.5674, b=0.8059, c=1.3445; X-ray powder diffraction). For the details of sample preparation, see La₃Rh₂Ge₂ under La–Rh–Ge

 Pr_2Rh_3Ge crystallizes with the Y_2Rh_3Ge -type of structure with lattice parameters a = 0.5626, c = 1.193 (Cenzual et al. 1987).

Verniere et al. (1995) mentioned the existence of $Pr_4Rh_{13}Ge_9$ compound with $Ho_4Ir_{13}Ge_9$ -type; no lattice parameters were given. For the experimental details, see $La_4Rh_{13}Ge_9$ under La–Rh–Ge.

4.5.9. Pr–Pd–Ge

Phase relations have not been yet established for the Pr–Pd–Ge system; only three ternary compounds have been observed.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Pr_2PdGe_6 , compound which was found to crystallize with the Ce_2CuGe_6 type structure, a=0.4152, b=0.4073, c=2.197. Samples were synthesized by argon arc melting followed by a heat

treatment at 870 K for 150 hours. Starting materials used were obtained from Johnson & Matthey, UK (99.9 mass%).

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound PrPdGe adopts the KHg₂-type structure, a=0.4472, b=0.7256, c=0.7654. The alloy was arc melted under argon and annealed at 1270 K for 1–2 weeks. The starting materials were Pr (3N), Pd (4N) and Ge (5N).

The crystal structure of the compound $PrPd_2Ge$ was found to be of the YPd_2Si type (a=0.7617, b=0.6993, c=0.5735; X-ray powder diffraction) by Jorda et al. (1983). The sample was obtained by induction melting under an argon atmosphere and annealing in evacuated quartz tube for 10 days at 1173 K. The starting materials were palladium (4N), germanium (4N), praseodymium (3N).

4.5.10. Pr-Ag-Ge

Information on interaction of praseodymium with silver and germanium is due to the work of several groups of authors; six ternary compounds have been observed and analyzed. Crystallographic characteristics of the ternary Pr–Ag–Ge phases are listed in table 17.

Compound	Structure	Lattice	paramete	rs (nm)	Reference
-		а	b	с	
Pr ₂ AgGe ₆	Ce ₂ CuGe ₆	0.42887 0.42856	0.41295 0.41263	2.1610 2.15869	Sologub et al. (1995a) Savysyuk and Gladyshevsky (1995)
$PrAg_{0.8}Ge_{1.2}$	AlB ₂	0.4356 0.43793		0.4130 0.40903	Protsyk (1994) Savysyuk and Gladyshevsky (1995)
PrAg ₂ Ge ₂	$CeGa_2Al_2$	0.42801		1.09977	Savysyuk and Gladyshevsky (1995)
Pr ₃ Ag ₄ Ge ₄	$Gd_3Cu_4Ge_4$	0.4342	0.71126	1.47306	Savysyuk and Gladyshevsky (1995)
PrAg _{1.4} Ge _{0.6}	Fe ₂ P	0.72989		0.43340	Savysyuk and Gladyshevsky (1995)
PrAgGe	LiGaGe	0.45276		0.76357	Savysyuk and Gladyshevsky (1995)

Table 17 Crystallographic data for the ternary Pr–Ag–Ge compounds

Savysyuk and Gladyshevsky (1995) employed X-ray powder diffraction analysis of arc melted samples, which were homogenized by annealing at 773 K and 1073 K for 1000 hours. For detailed experimental procedure for Pr_2AgGe_6 (Sologub et al. 1995a) and $PrAg_{0.8}Ge_{1.2}$ (Protsyk 1994), see La_2AgGe_6 (under La-Ag-Ge) and Ce-Ag-Ge, respectively.

4.5.11. Pr–Os–Ge

No phase diagram exists at present for the system Pr–Os–Ge, however, one ternary germanide has been observed and characterized by Segre et al. (1981a). $Pr_3Os_4Ge_{13}$ was found to crystallize with the $Pr_3Rh_4Sn_{13}$ -type structure, a=0.9098. For sample preparation, see Ce₃Ru₄Ge₁₃ under Ce–Ru–Ge.

4.5.12. *Pr–Ir–Ge*

Phase relations have not yet been established for the Pr–Ir–Ge system; information concerning the formation of six compounds and their crystal structure is due to the work of different groups of authors.

Francois et al. (1987) reported the crystal structure of the PrIrGe₂ (YIrGe₂ type, a=0.4393, b=1.617, c=0.8908). The sample was prepared by heating the mixture of powders of starting components (Pr 3N, Ir 3N and Ge 3N) in evacuated silica tube at 1173 K.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound PrIrGe adopts the TiNiSi-type structure, a=0.7357, b=0.4440, c=0.71197. For the experimental procedure, see La–Ir–Ge.

PrIr₂Ge₂ is isotypic with the crystal structure of CaBe₂Ge₂ with lattice parameters a = 0.4235, c = 1.0057 (Francois et al. 1985).

 $Pr_2Ir_3Ge_5$ was found to crystallize with the U₂Co₃Si₅ type (*a*=1.0185, *b*=1.190, *c*= 0.6045) by Venturini et al. (1986b) from X-ray powder analysis.

Verniere et al. (1995) observed the existence $Pr_4Ir_{13}Ge_9$ compound with $Ho_4Ir_{13}Ge_9$ type. Lattice parameters have not been established. For the experimental procedure, see La_4Ir_{13}Ge_9 under La_Ir_Ge.

Venturini et al. (1985b) reported on the X-ray powder diffraction study of the $Pr_3Ir_4Ge_{13}$ compound from a sample which was prepared by heating a mixture of starting components (Pr 3N, Ir 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃-type structure, a = 0.9053.

4.5.13. Pr-Pt-Ge

Francois et al. (1987) reported the crystal structure of the PrPtGe₂ (YIrGe₂ type, a = 0.4416, b = 1.644, c = 0.8793). For sample preparation, see PrIrGe₂ under Pr–Ir–Ge.

Venturini et al. (1989a) investigated the crystal structure of $PrPt_2Ge_2$ from an arc melted sample annealed at 1273 K for 5 days. The crystal structure was found to belong to the LaPt₂Ge₂ type, a=0.4374, b=0.4396, c=0.9779, $\beta=91.94^{\circ}$. The starting materials were Pr (3N), Pt (4N) and Ge (4N).

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound PrPtGe adopts the KHg₂-type of structure, a=0.4438, b=0.7292, c=0.7616. For the experimental procedure, see La–Ir–Ge.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Pr_2PtGe_6 compound which was found to crystallize with the Ce_2CuGe_6 type structure, a=0.4134, b=0.4070, c=2.2084. For sample preparation, see La₂PdGe₆ under La–Pd–Ge.

4.5.14. Pr-Au-Ge

No ternary phase diagram exists for the Pr-Au-Ge system, however, a ternary compound of praseodymium with gold and germanium in the stoichiometric ratio 1:1:1 has been identified and studied by means of X-ray powder diffractometry and metallography by Rossi et al. (1992). The PrAuGe compound was found to adopt the LiGaGe type with lattice parameters a = 0.4457, c = 0.7803. The sample was prepared by melting the metals (99.9 mass% for praseodymium and 99.99 mass% for gold and germanium) in an induction furnace and annealing at 1070 K for one week.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Pr_2AuGe_6 compound which was found to crystallize with the Ce_2CuGe_6 type, a=0.4241, b=0.4113, c=2.1172. For sample preparation, see La₂PdGe₆ under La–Pd–Ge.

4.6. Nd-d element-Ge systems

4.6.1. Nd-V-Ge

The phase equilibria in the Nd–V–Ge system have been investigated by Salamakha et al. (1994) by means of X-ray analysis of 40 ternary alloys. No ternary compounds were observed. The isothermal section of the phase diagram at 870 K is shown in fig. 56.



The ternary samples used to derive the phase relations in the ternary section at 870 K, each with a total weight of 2 g, were synthesized by arc melting proper amounts of the constituent elements under high-purity argon on a water-cooled copper hearth. The starting materials were used in the form of ingots of high-purity elements: neodymium (99.85 mass%), vanadium (99.99 mass%), germanium (99.99 mass%). The weight losses were generally less than 1%. The alloys were annealed at 870 K in evacuated quartz tubes for 2 weeks and quenched in ice cold water.

4.6.2. Nd--Cr--Ge

The isothermal section of the Nd–Cr–Ge phase diagram at 870 K was constructed by Salamakha et al. (1994). The phase relations are characterized by the formation of two



Fig. 57. Nd–Cr–Ge, isothermal section at 870 K. The curved line indicates the liquid immiscibility gap region.

ternary compounds, Nd₂Cr₉Ge₈ (1) and Nd₁₁₇Cr₅₂Ge₁₁₂ (2), and by a region of liquid immiscibility that stretches up to 20 at.% Ge (fig. 57). For details of sample preparation, see Nd–V–Ge. The purity of the starting materials was Nd 99.85 mass%, Cr 99.93 mass%, Ge mass 99.99%.

 $Nd_2Cr_9Ge_8$ (own structure type, a=0.9388, b=0.4046, c=0.8045) was observed by Bodak et al. (1989a) from X-ray single-crystal analysis. For sample preparation, see Nd–V–Ge.

Salamakha et al. (1994) observed the Nd₁₁₇Cr₅₂Ge₁₁₂ compound in the course of investigating the Nd–Cr–Ge isothermal section. It was found to crystallize with the Tb₁₁₇Fe₅₂Ge₁₁₂-type structure, a = 2.9439 from X-ray powder analysis.

4.6.3. Nd–Mn–Ge

The phase-field distribution in the Nd–Mn–Ge system at 870 K is characterized by the formation of three ternary compounds: NdMn₆Ge₆ (1), NdMn₂Ge₂ (2) and NdMn_xGe₂ (3) after Salamakha et al. (1994) (fig. 58). The samples were prepared by argon arc melting. Weight losses due to vaporization while melting were compensated beforehand by extra amounts of manganese (about 0.5 mass%). The arc melted buttons were annealed at 870 K for 2 weeks in vacuum-sealed quartz capsules and finally quenched by submerging the ampoules into cold water. The starting materials were Nd 99.85 mass%, Mn 99.98 mass%, Ge 99.99 mass%.

NdMn₆Ge₆(1) has been found by Salamakha et al. (1994) from X-ray powder diffraction to be isostructural with the YCo₆Ge₆ type, a=0.5249, c=0.4098. For the experimental procedure, see above.

NdMn₂Ge₂ (2) was reported to crystallize with the CeGa₂Al₂-type structure, a = 0.4105, c = 1.0216 (Salamakha et al. 1994; X-ray powder diffraction).



Fig. 58. Nd–Mn–Ge, isothermal section at 870 K.

The crystallographic characteristics for NdMn_xGe₂ (3) were reported by Salamakha et al. 1994 from X-ray powder analysis (CeNiSi₂ type, a = 0.4232, b = 1.653, c = 0.4092).

A compound of equiatomic composition with the PbFCl type was observed by Welter et al. (1995) at 1070 K with lattice parameters a=0.4134, c=0.7375. For sample preparation, see Pr–Mn–Ge. Apparently the NdMnGe phase does not exist at 870 K (fig. 58).

4.6.4. Nd–Fe–Ge

Figure 59 represents the isothermal section of the Nd-Fe-Ge system at 870 K as derived



Fig. 59. Nd–Fe–Ge, isothermal section at 870 K.

No.	Compound	pound Structure	Lattice parameters (nm)			Reference
			а	Ь	с	-
1	NdFe ₆ Ge ₆	YCo ₆ Ge ₆	0.5142		0.4049	Salamakha et al. (1996b)
2	NdFe ₂ Ge ₂	CeGa ₂ Al ₂	0.4038		1.0510	Salamakha et al. (1996b)
3	~Nd ₅ Fe ₃ Ge ₁₂	unknown				Salamakha et al. (1996b)
4	~Nd ₅ Fe ₂ Ge ₁₃	unknown				Salamakha et al. (1996b)
5	NdFe _{0.37} Ge ₂	CeNiSi ₂	0.4214	1.6450	0.4084	Salamakha et al. (1996b)
6	~Nd ₃ FeGe ₇	unknown				Salamakha et al. (1996b)
7	~Nd ₄ FeGe ₁₀	orthorhomb	0.422	0.403	2.828	Salamakha et al. (1996b)
8	Nd ₄ Fe _{0.64} Ge ₇	$Sm_4Co_{1-x}Ge_7$	0.4198	0.4095	3.037	Salamakha et al. (1996b)

Table 18 Crystallographic data for the ternary Nd–Fe–Ge compounds at 870 K

from X-ray phase analysis of 150 samples by Salamakha et al. (1996b). The phasefield distribution is characterized by the presence of eight ternary compounds. The binary compound Fe₃Ge does not appear in the Nd–Fe–Ge ternary. None of the binary phases shows an appreciable range of mutual solid solubility. For the experimental details, see Nd–V–Ge. The starting materials were Nd 99.85 mass%, Fe 99.98 mass%, Ge 99.99 mass%.

Crystallographic data of the ternary phases, observed by Salamakha et al. (1996b) investigating the isothermal section of the Nd–Fe–Ge system, are listed in table 18.

Two more ternary compounds are known from early investigations of ternary neodymium-iron-germanium combinations performed by Felner and Schieber (1973) and Weitzer et al. (1990) which have not been observed in the course of studying the Nd-Fe-Ge isothermal section at 870 K. The NdFe_{0.67}Ge_{1.33} compound was found to adopt the AlB₂ type (a=0.4174, c=0.4163; X-ray powder diffraction) (Felner and Schieber 1973). The samples were prepared by melting elements together (Nd 99.9 mass%, Ge 99.99 mass%, Fe 99.95 mass%). The metals were mixed and heated in an alumina crucible in an induction furnace at about 1870 K under a protective argon atmosphere. The samples were homogenized by annealing them in the induction furnace at the melting temperature for about 30 min. The crystal structure of the Nd₆Fe₁₃Ge compound was reported by Weitzer et al. (1990) (Nd₆Fe₁₃Si type, a=0.8043, c=2.3204). The sample was melted under argon and annealed at 1073 K for 5 days. The starting materials were commercially available high-purity elements.

4.6.5. Nd--Co--Ge

The isothermal section of the Nd–Co–Ge system at 870K is shown in fig. 60. The phase-field distribution is characterized by the presence of sixteen ternary compounds as reported by Salamakha (1997). Mutual solid solubilities of the binary compounds are insignificantly small. For sample preparation, see Nd–V–Ge. The starting materials were Nd 99.85 mass%, Co 99.99 mass%, Ge 99.99 mass% pure.

Crystallographic data of the ternary Nd-Co-Ge compounds are listed in table 19.



Fig. 60. Nd–Co–Ge, isothermal section at 870 K.

No.	Compound	Structure	Lattice	e paramet	ers (nm)	Reference
			а	b	с	-
1	NdCo ₂ Ge ₂	CeGa ₂ Al ₂	0.4042		1.0183	Salamakha (1997)
2	Nd ₂ Co ₃ Ge ₅	$U_2Co_3Si_5$	0.9710	1.203	0.5707	Salamakha (1997)
3	NdCoGe ₃	BaNiSn ₃	0.4296		0.9811	Salamakha (1997)
			0.4297		0.9812	Venturini et al. (1985b)
4	~Nd ₅ Co ₂ Ge ₁₃	unknown				Salamakha (1997)
5	~Nd ₅ Co ₃ Ge ₁₂	unknown				Salamakha (1997)
6	~Nd ₃ Co ₂ Ge ₇	unknown				Salamakha (1997)
7	NdCo _{0.55} Ge ₂	CeNiSi ₂	0.4212	1.6509	0.4087	Pecharsky et al. (1989)
			0.4210	1.670	0.4152	Méot-Meyer et al. (1985a)
8	NdCoGe	PbFCl	0.4149		0.6786	Salamakha (1997)
			0.4140		0.6785	Welter et al. (1993a)
9	NdCo _{0.5} Ge _{1.5}	AlB_2	0.4144		0.4151	Salamakha (1986)
10	Nd ₂ CoGe ₂	Sc_2CoSi_2	1.0882	0.4301	1.0438	Bodak et al. (1986)
				$\beta = 118.$	60°	
11	Nd ₁₁₇ Co ₅₂ Ge ₁₁₂	Tb ₁₁₇ Fe ₅₂ Ge ₁₁₂	2.9162			Salamakha (1997)
12	Nd ₆ Co ₅ Ge _{2.2}	own	0.9272		0.4188	Salamakha et al. (1986)
13	Nd ₃ CoGe ₂	La ₃ NiGe ₂	1.207	0.403	1.157	Salamakha (1997)
14	~Nd ₁₁ Co ₄ Ge ₅	unknown				Salamakha (1997)
15	~Nd ₅ CoGe ₂	unknown				Salamakha (1997)
16	~Nd ₅ Co ₂ Ge	unknown				Salamakha (1997)

Table 19 Crystallographic data for the ternary Nd–Co–Ge compounds

P.S. SALAMAKHA et al.

Venturini et al. (1986b), from X-ray powder diffraction analysis of a sample synthesized by powder metallurgical reaction at 1173 K, characterized the compound Nd₂Co₃Ge₅ to be isostructural with the Lu₂Co₃Si₅-type (a=1.115, b=1.193, c=0.5812, $\gamma=118.45^{\circ}$). These data suggest that Nd₂Co₃Ge₅ has two polymorphic phases (compound 2, table 19).

4.6.6. Nd--Ni-Ge

Figure 61 shows the isothermal section of the Nd–Ni–Ge system at 870 K as derived from X-ray phase analysis of 180 arc melted samples which were annealed and subsequently quenched in water (Salamakha et al. 1996c). Starting materials were Nd 99.85 mass%, Ni 99.99 mass%, Ge 99.99 mass%. The phase-field distribution is characterized by the presence of nine ternary compounds. The binary compounds Nd₂Ni₁₇ and NdNi₅ dissolve approximately 15 at.% Ge.



Fig. 61. Nd-Ni-Ge, isothermal section at 870 K.

Crystallographic data for the ternary phases of the Nd–Ni–Ge system are listed in table 20.

Additionally two ternary compounds of an unknown structure type, \sim Nd₅NiGe₂ and \sim Nd₅Ni₂Ge, have been observed by Salamakha et al. (1996c) in "as-cast" samples (X-ray powder analysis).

4.6.7. Nd-Cu-Ge

Information about the phase equilibria in the Nd–Cu–Ge system (fig. 62) is due to the work of Salamakha (1988) who employed X-ray phase analysis of argon arc melted ternary alloys; the samples were annealed in vacuum-sealed quartz ampoules at 870 K for

		erjeunegraphie enn					
No.	Compound	Structure	Lattice	paramete	ers (nm)	Reference	
			a	b	с		
1	NdNi ₈₅ Ge _{4.5}	CeNi _{8.5} Si _{4.5}	0.7942		1.1732	Salamakha et al. (1996c)	
2	NdNi ₂ Ge ₂	CeGa ₂ Al ₂	0.4115		0.9842	Rieger and Parthé (1969a,b)	
3	Nd ₂ Ni ₃ Ge ₅	unknown				Salamakha et al. (1996c)	
4	NdNiGe ₃	SmNiGe ₃	2.1733	0.4123	0.4124	Bodak et al. (1985)	
5	Nd ₂ NiGe ₆	Ce ₂ CuGe ₆	0.4031	0.4110	2.1718	Salamakha et al. (1996c)	
6	NdNi1-0.8 Ge2-2.2	CeNiSi ₂	0.4199–	1.6765-	0.4174-	Pecharsky et al. (1989)	
	1 117 2 112	-	0.4202	1.6742	0.4154		
7	NdNiGe	TiNiSi	0.7232	0.4253	0.7307	Salamakha et al. (1996c)	
8	NdNi ₀₆ Ge ₁₄	AlB ₂	0.4157		0.4145	Salamakha (1986)	
9	Nd_3NiGe_2	La ₃ NiGe ₂	1.1764	0.4279	1.1159	Bodak et al. (1982)	

 Table 20

 Crystallographic data for the ternary Nd–Ni–Ge compounds



Fig. 62. Nd–Cu–Ge, isothermal section at 870 K.

300 hours. The formation of six ternary phases has been reported. Mutual solid solubilities of the binaries were reported to be negligible.

The crystallographic characteristics of the ternary compounds of the Nd–Cu–Ge system at 870 K are listed in table 21.

One more compound has been observed and investigated by Salamakha et al. (1996d) from an as-cast sample: Nd₆Cu₈Ge₈ (Gd₆Cu₈Ge₈ type, a=0.4302, b=0.6711, c=1.4249; X-ray single-crystal method).

No	Compound	Structure	Lattice	paramete	ers (nm)	Reference
			a	b	с	
1	NdCu ₂ Ge ₂	CeGa ₂ Al ₂	0.4129		1.0216	Rieger and Parthé (1969a,b)
2	Nd ₂ CuGe ₆	Ce ₂ CuGe ₆	0.4059	0.4172	2.1359	Konyk et al. (1988)
3	Nd ₂ Cu ₃ Ge ₃	$Ce_2Cu_3Ge_3$				Salamakha (1988)
4	NdCuGe ₂	CeNiSi ₂	0.4215	1.714	0.4077	Salamakha (1988)
5	NdCuGe	AlB ₂	0.4272		0.3881	Salamakha (1986)
6	NdCu _{0.71-0.56} Ge _{1.29-1.44}	AlB_2	0.4172-		0.4160-	Salamakha (1986, 1988)
	• <i>···</i>	-	0.4151		0.4188	

Table 21 Crystallographic data for the ternary Nd–Cu–Ge compounds

4.6.8. Nd-Zn-Ge

No isothermal section is available for the ternary Nd–Zn–Ge system, however one ternary compound was observed and characterized by Rossi and Ferro (1996). NdZn_{1.5}Ge_{0.5} was found to crystallize with the AlB₂ type, a=0.4432, c=0.3820, from X-ray powder diffraction of an induction-melted alloy which was annealed at 1070 K for one week. Electronic micrographic examination as well as microprobe microanalysis was carried out. The metals employed in sample synthesis had a nominal purity of 99.9 mass% for neodymium, and 99.999 mass% for the other metals.

4.6.9. Nd–Zr–Ge

Salamakha and Starodub (1991) were the first to investigate the phase relations within the isothermal section at 870 K over the whole concentration region by X-ray powder analysis (fig. 63). No ternary compounds were observed. For sample preparation, see Nd–V–Ge.



Fig. 63. Nd–Zr–Ge, isothermal section at 870 K.



Fig. 64. Nd–Nb–Ge, isothermal section at 870 K.

4.6.10. Nd-Nb-Ge

The phase relations in the ternary system Nd–Nb–Ge at 870 K are presented in fig. 64 after Salamakha (1997). As determined from X-ray powder diffraction analysis of samples annealed at 870 K, phase equilibria revealed the absence of ternary compounds. For sample preparation, see Nd–V–Ge.

4.6.11. Nd-Mo-Ge

Salamakha (1997) reported the Nd–Mo–Ge phase diagram shown in fig. 65. No ternary compounds or solid solutions have been observed at 870 K. For sample preparation, see Nd–V–Ge.



Fig. 65. Nd–Mo–Ge, isothermal section at 870 K.
4.6.12. Nd–Ru–Ge

Phase equilibria in the Nd–Ru–Ge system have been derived by Salamakha et al. (1996e) by means of powder X-ray analysis of samples prepared by direct arc melting of highpurity components (Nd 99.85 mass%, Ru 99.9 mass%, Ge 99.99 mass%), annealed at 870 K for two weeks in evacuated quartz ampoules and quenched in cold water. The isothermal section is shown in fig. 66. The phase relations are characterized by the existence of seven ternary neodymium–ruthenium germanides. Mutual solid solubilities of the binary compounds were observed to be negligible.

Crystallographic data of ternary Nd-Ru-Ge compounds are listed in table 22.



Fig. 66. Nd–Ru–Ge, partial isothermal section at 870 K (0–33 at.% Nd).

		Table 22		
Crystallographic	data for	the ternary	Nd-Ru-Ge	compounds

No. C	Compound	ound Structure	Lattice	paramete	ers (nm)	Reference
			a	b	с	-
1	Nd ₃ Ru ₄ Ge ₁₃	Y ₃ Co ₄ Ge ₁₃	0.9055			Salamakha et al. (1989a)
	5 1 15	Yb ₃ Rh ₄ Sn ₁₃	0.9055			Segre et al. (1981b)
2	NdRu ₂ Ge ₂	CeGa ₂ Al ₂	0.4250		0.9953	Salamakha et al. (1996e)
	2 2		0.4257		0.9986	Salamakha et al. (1989a)
3	Nd₂Ru₃Ge₅	U ₂ Co ₃ Si ₅	0.9897	1.243	0.5819	Salamakha et al. (1996e)
4	~Nd ₃ RuGe ₆	orthorhombic				Salamakha et al. (1996e)
5	NdRuGe	PbFCl	0.4267		0.6791	Salamakha et al. (1996e)
6	~Nd ₂ RuGe ₂	monoclinic				Salamakha et al. (1996e)
7	$Nd_3Ru_2Ge_2$	La ₃ Ni ₂ Ga ₂	0.5658	0.7863	1.3581	Bodak et al. (1989a)

Compound	Structure	Lattice	e paramet	ers (nm)	Reference
		а	b	с	-
NdRh ₂ Ge ₂	CeGa ₂ Al ₂	0.4143		1.0408	Francois et al. (1985)
Nd ₂ Rh ₃ Ge ₅	$U_2Co_3Si_5$	1.0041	1.2083	0.5931	Venturini et al. (1986b)
Nd ₃ Rh ₄ Ge ₁₃	$Yb_3Rh_4Sn_{13}$	0.9018			Venturini et al. (1985b)
NdRhGe	TiNiSi	0.7229	0.4443	0.7322	Hovestreydt et al. (1982)
NdRh _{0.5} Ge _{1.5}	AlB_2	0.4237		0.4087	Salamakha et al. (1989a)
Nd ₄ Rh ₄ Ge ₃	own	2.1021	0.7941	0.5652	Salamakha (1989)
			$\gamma \approx 110.$	08°	
$Nd_3Rh_2Ge_2$	$La_3Ni_2Ga_2$	0.5654	0.8017	1.3411	Gladyshevsky et al. (1991a)
NdRh _x Ge ₂	CeNiSi ₂	0.4282	1.693	0.4261	Francois et al. (1990)
Nd ₂ RhGe ₂	Sc_2CoSi_2				Salamakha (1989)
Nd ₄ Rh ₁₃ Ge ₉	Ho ₄ Ir ₁₃ Ge ₉				Verniere et al. (1995)
$NdPd_2Ge_2$	$CeGa_2Al_2$	0.4300		0.9865	Rossi et al. (1979)
Nd ₂ PdGe ₆	Ce_2CuGe_6	0.4139	0.4060	2.187	Sologub et al. (1995a)
NdPdGe	KHg ₂	0.4452	0.7205	0.7639	Hovestreydt et al. (1982)
NdPd ₂ Ge	YPd ₂ Si	0.7598	0.6992	0.5749	Jorda et al. (1983)
NdPd _x Ge ₂	$CeNiSi_2$	0.4261	1.724	0.4218	Francois et al. (1990)
NdPd _{0.6} Ge _{1.4}	AlB_2	0.4238		0.4170	Salamakha et al. (1989a)

Table 23 Crystallographic characteristics of the ternary Nd–Rh(Pd)–Ge compounds

4.6.13. Nd-Rh(Pd)-Ge

No ternary phase diagrams have been established for the Nd–Rh–Ge system and the Nd– Pd–Ge system, but the crystal structures of ternary compounds have been characterized by several groups of authors. Crystallographic data for the ternary neodymium–rhodium germanides and neodymium–palladium germanides are compiled in table 23.

4.6.14. Nd–Ag–Ge

Phase equilibria have been established in the ternary Nd–Ag–Ge system over the whole concentration region for the isothermal sections at 870 K and 1070 K by Salamakha et al. (1996f) and Zaplatynsky et al. (1996) (figs. 67a,b). The existence of four and five ternary compounds respectively have been observed. Samples were melted from pieces of high purity components (Nd 99.85 mass%, Ag 99.99 mass%, Ge 99.99 mass%) under argon atmosphere in an arc furnace with water-cooled copper hearth. The ingots were subsequently annealed at 870 K (1070 K) and quenched in cold water. The isothermal sections were constructed using X-ray powder diffraction film data obtained by the Debye–Scherrer technique with non-filtered CrK radiation.

Crystallographic characteristics of the ternary phases which exist within the Nd–Ag–Ge system at 870 K and 1070 K are listed in table 24.



Fig. 67. Nd-Ag-Ge, isothermal sections at 870 K (a) and 1070 K (b).

No. C	Compound Str	Structure	Lattice parameters (nm)			Reference
			a	b	с	
1	NdAg ₂ Ge ₂	CeGa ₂ Al ₂	0.4244		1.0978	Salamakha et al. (1996f)
2	Nd ₂ AgGe ₆	Ce ₂ CuGe ₆	0.4271	0.4117	2.1517	Salamakha et al. (1996f)
3	Nd ₆ Ag ₈ Ge ₈	Gd ₆ Cu ₈ Ge ₈	1.4636	0.7082	0.4407	Salamakha et al. (1996d)
4	$NdAg_{1.1}Ge_{0.9}$	Fe ₂ P	0.7339		0.4329	Salamakha et al. (1996f)
5	NdAg _{0.7} Ge _{1.3}	AlB_2	0.4335		0.4072	Zaplatynsky et al. (1996)

Table 24 Crystallographic data for the ternary Nd–Ag–Ge compounds

4.6.15. Nd–Hf–Ge

Salamakha and Starodub (1991) reported the phase diagram shown in fig. 68. No ternary compounds or solid solutions have been observed at 870 K. For sample preparation, see Nd–V–Ge.

4.6.16. Nd-Ta-Ge

The results of X-ray investigations of the isothermal section of the Nd–Ta–Ge systems at 870 K are shown in fig. 69 after Salamakha (1997). No ternary compounds were observed. For sample preparation, see Nd–V–Ge.

4.6.17. Nd–W–Ge

Salamakha (1997) derived the Nd–W–Ge phase diagram shown in fig. 70. No solid solibility or ternary compounds have been found at 870 K. For sample preparation, see Nd–V–Ge.

100



4.6.18. Nd–Re–Ge

No ternary compounds were found in the ternary Nd-Re-Ge system at 870 K (fig. 71) (Salamakha 1997). For sample preparation, see Nd-V-Ge.

4.6.19. Nd–Os–Ge

The partial isothermal section of the Nd-Os-Ge system at 870 K is shown in fig. 72, after Salamakha et al. (1996e). Samples were prepared in the same manner as for the



investigation of the Nd-Ru-Ge system. Two ternary compounds were found to exist within the concentration region under investigation.

The Nd₃Os₄Ge₁₃ (1) compound has been found to crystallize with $Y_3Co_4Ge_{13}$ type at 870 K, a=0.9080 nm (Salamakha et al. 1989a) whereas at 1170 K the Yb₃Rh₄Sn₁₃ type has been realized (Segre et al. 1981b).

The crystal structure of the $\sim Nd_3OsGe_6$ (2) compound has not been determined.

The $Nd_2Os_3Ge_5$ compound was established to crystallize with the $U_2Co_3Si_5$ -type structure from X-ray powder diffraction of an as-cast specimen (Salamakha et al. 1996e).



Fig. 72. Nd–Os–Ge, partial isothermal section at 870 K (0–33 at.% Nd).

4.6.20. Nd–Ir(Pt)–Ge

No ternary phase diagrams have been established for the Nd–Ir(Pt)–Ge systems, but the crystal structures of ternary compounds have been characterized by various authors (see table 25).

Crystallographic data for the ternary Nd-Ir(Pt)-Ge compounds						
Structure	Lattice	e paramete	ers (nm)	Reference		
	a	b	с	-		
CaBe ₂ Ge ₂	0.4222		1.0032	Francois et al. (1985)		
$U_2Co_3Si_5$	1.0172	1.1881	0.6030	Venturini et al. (1986b)		
Yb ₃ Rh ₄ Sn ₁₃	0.9042			Venturini et al. (1985b)		
TiNiSi	0.7302	0.4448	0.7335	Hovestreydt et al. (1982)		
AIB_2	0.4229		0.4125	Salamakha et al. (1989a)		
Sc ₂ CoSi ₂	1.0840	0.4352	1.0545	Salamakha et al. (1989a)		
		$\beta = 117.2$	23°			
YIrGe ₂	0.4358	0.8809	1.6153	Salamakha et al. (1989b)		
Ho ₄ Ir ₁₃ Ge ₉				Verniere et al. (1995)		
CeGa ₂ Al ₂	0.4380		0.9865	Rossi et al. (1979)		
LaPt2Ge2	0.4363	0.4389	0.9779	Venturini et al. (1989a)		
2 2		$\beta = 90.83$	8°			
Ce ₂ CuGe ₆	0.4120	0.4063	2.2007	Sologub et al. (1995a)		
YIrGe,	0.4398	0.8770	1.6418	Salamakha et al. (1989b)		
KHg ₂	0.4428	0.7245	0.7599	Hovestrevdt et al. (1982)		
AlB ₂	0.4227		0.4181	Salamakha et al. (1989a)		
	ystallographic data for Structure CaBe ₂ Ge ₂ U ₂ Co ₃ Si ₅ Yb ₃ Rh ₄ Sn ₁₃ TiNiSi AlB ₂ Se ₂ CoSi ₂ YIrGe ₂ Ho ₄ Ir ₁₃ Ge ₉ CeGa ₂ Al ₂ LaPt ₂ Ge ₂ Ce ₂ CuGe ₆ YIrGe ₂ KHg ₂ AlB ₂	$\begin{array}{c c} \mbox{ystallographic data for the ternary} \\ \hline \\ $	$\begin{array}{c c} \mbox{ystallographic data for the ternary Nd-Ir(F)} \\ \hline \\ $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $		

Table 25 rystallographic data for the ternary Nd–Ir(Pt)–Ge compounds



Fig. 73. Nd–Au–Ge, partial isothermal section at 870 K (33–100 at.% Ge)..

	Tab	ole 26	
Crystallographic da	ta for the	ternary Nd-A	u–Ge compounds

No. Coi	. Compound	Structure	Lattice	paramete	Reference	
			а	b	с	-
1	NdAu ₂ Ge ₂	CeGa ₂ Al ₂	0.4411		1.0559	Salamakha (1997)
2	Nd ₂ AuGe ₆	Ce ₂ CuGe ₆	0.42265	0.41272	2.1689	Sologub et al. (1995a)
3	NdAuGe ₂	unknown				Salamakha (1997)
4	NdAuGe	LiGaGe	0.4439 0.4447		0.7718 0.7702	Salamakha (1997) Rossi et al. (1992)
5	NdAu _{0.7} Ge _{1.3}	AlB_2	0.4369		0.4278	Salamakha (1997)

4.6.21. Nd-Au-Ge

A partial isothermal section of the Nd–Au–Ge system at 870 K is shown in fig. 73, after Salamakha (1997). The phase relations are characterized by the formation of five ternary neodymium germanides of gold. Their crystallographic data are listed in table 26. For the details of sample preparation, see Nd–Ag–Ge.

4.7. Sm-d element-Ge systems

4.7.1. Sm-Mn-Ge

No phase diagram is available for the system Sm-Mn-Ge, however, a series of ternary compounds have been observed and characterized.

104

The SmMn₂Ge₂ compound has been prepared and studied by Rossi et al. (1978b). It was found to be of CeGa₂Al₂ type with lattice parameters a=0.4062, c=1.0896. For sample preparation, see LaMn₂Ge₂ under La–Mn–Ge.

SmMnGe with PbFCl-type was observed by Welter et al. (1995), a=0.4134, c=0.7375. The compound was prepared from commercially available high-purity elements. A compacted pellet of stoichiometric mixture was sealed under argon (100 mmHg) in a silica tube, heated at 1273 K as a preliminary homogenization treatment and then melted in an induction furnace. The resulting ingot was annealed for 2 weeks at 1173 K.

SmMn₆Ge₆ was found to crystallize in the YCo₆Ge₆-type structure by Venturini et al. (1992), a = 0.5245, c = 0.8187 (X-ray powder diffraction data). The alloy was synthesized by powder metallurgical reaction in an evacuated silica tube at 1073 K for 14 days.

Francois et al. (1990) investigated the occurrence of CeNiSi₂ type for samariummanganese-germanium combinations for alloys annealed at 1173 K (SmMn_{0.40}Ge₂; a = 0.4194, b = 1.633, c = 0.4062).

4.7.2. Sm-Fe-Ge

Phase equilibria in the isothermal sections at 870 K (0–40 at.% Sm) and 670 K (40–100 at.% Sm) have been determined by Mruz (1988) using X-ray powder diffraction and partly microstructural analyses of 202 ternary alloys synthesized by arc melting ingots of Sm (99.77 mass%), Fe (99.90 mass%) and Ge (99.99 mass%); the alloys were then annealed in evacuated quartz tubes for 500–900 hours. The total number of compounds observed was nine. The Sm₅Ge₃ binary compound was found to dissolve up to 8 at.% Fe. Solubility of the third component in the binary compounds was reported to be negligible. Phase equilibria in the isothermal sections at 870 K and 670 K are presented in fig. 74.



Fig. 74. Sm-Fe-Ge, isothermal sections at 870 K (0-40 at.% Sm) and 670 K (40-100 at.% Sm).

The SmFe₆Ge₆ (2) compound was observed and studied by Mruz et al. (1984). It was found to crystallize with YCo₆Ge₆ type with lattice parameters a=0.5135, c=0.4091 by X-ray powder diffraction of an arc melted alloy annealed at 870 K.

The formation and crystal structure of SmFe₂Ge₂ (3) was reported in an early investigation of samarium-iron-germanium combinations by Mruz et al. (1983): CeGa₂Al₂ type, a=0.4005, c=1.0476 (arc melted sample annealed at 870 K; X-ray powder diffraction data) later confirmed by Bara et al. (1990), a=0.4010, c=1.0491.

Pecharsky et al. (1989) investigated the formation and crystal structure of the $SmFe_{1-x}Ge_2$ (7) compound by X-ray single-crystal analysis of an arc melted sample annealed at 870 K. The CeNiSi₂-type structure was established with lattice parameters a=0.4188-0.4198, b=1.6208-1.6232, c=0.4058-4079. Francois et al. (1990) confirmed the crystal structure of SmFe_{0.52}Ge₂ (CeNiSi₂ type, a=0.4195, b=1.619, c=0.4076). The sample was prepared by powder metallurgical reaction and annealed in an evacuated silica tube at 1173 K.

The crystal structures of three compounds within the Sm–Fe–Ge system at 870 K were determined by Mruz (1988): Sm₄Fe_{0.64}Ge₇ (8) with Sm₄CoGe₇-type structure, a = 0.4161, b = 0.4067, c = 3.021; Sm₁₁₇Fe₅₂Ge₁₁₂ (9) with Tb₁₁₇Fe₅₂Ge₁₁₂-type structure, a = 2.8989; and ~Sm₅Fe₃Ge₁₂ (6) was found to adopt a new structure type a = 0.4079, b = 2.5715, c = 0.4275.

The crystal structures of three more germanides, \sim SmFe₃₀Ge₁₉ (1), \sim Sm₃Fe₂Ge₉ (4) and \sim Sm₃Fe₂Ge₇ (5), have not been resolved.

The SmFe_{0.67}Ge_{1.33} compound was found to adopt the AlB₂ type (a=0.4141, c=0.4092; X-ray powder diffraction) (Felner et al. 1972). This compound was not observed at 870 K by Mruz (1988) in the course of studying the phase equilibria in this system.

4.7.3. Sm-Co-Ge

Phase equilibria in the isothermal sections at 870 K (0–40 at.% Sm) and 670 K (40–100 at.% Sm) have been determined by Mruz (1988) using X-ray powder diffraction and microstructural analyses of 342 ternary alloys synthesized by arc melting ingots of Sm (99.77 mass%), Co (99.90 mass%) and Ge (99.99 mass%). The alloys were annealed in evacuated quartz tubes for 500–900 hours. The phase relations are characterized by the formation of eighteen ternary compounds and by the existence of rather extended solid solutions originating at Sm₅Ge₃ (up to 17.5 at.% Co), SmCo₅ (up to 15 at.% Ge) and SmCo₃ (up to 10 at.% Ge). Phase equilibria in the isothermal sections at 870 K and 670 K are presented in fig. 75.

Méot-Meyer et al. (1985a) reported the crystal structure of $\text{SmCo}_{0.71}\text{Ge}_2$ (8) (CeNiSi₂ type, a = 0.4169, b = 1.649, c = 0.4097). The sample was prepared by powder metallurgical reaction and annealed in evacuated silica tube at 1173 K. Pecharsky et al. (1989) investigated the formation and crystal structure of the $\text{SmCo}_{0.72-0.56}\text{Ge}_2$ compound by X-ray powder analysis of arc melted alloys annealed at 870 K alloys. The CeNiSi₂-type structure was confirmed (a = 0.4174-0.4169, b = 1.6542-1.6395, c = 0.4122-0.4069).



Fig. 75. Sm–Co–Ge, isothermal sections at 870 K (0–40 at.% Sm) and 670 K (40–100 at.% Sm).

The formation and crystal structure of $SmCo_2Ge_2$ (2) was reported in an early investigation of samarium-cobalt-germanium combinations by Mruz et al. (1983): CeGa₂Al₂ type, a=0.4016, c=1.0133 (arc melted sample annealed at 870 K; X-ray single-crystal diffraction data).

Sm₂Co₃Ge₅ (3) was found to crystallize with the Lu₂Co₃Si₅-type (a=1.1244, b=1.193, c=0.5768, $\gamma=120.2^{\circ}$) by Venturini et al. (1986b) from X-ray powder analysis.

Gorelenko et al. (1984) reported the crystal structure of SmCoGe (9) (TiNiSi type, a=0.7137, b=0.4319, c=0.7133; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Sm₃Co₂Ge₄ (11) crystallizes with the Tb₃Co₂Ge₄ type structure, a = 1.0846, b = 0.8138, c = 0.4185, $\gamma = 107.70^{\circ}$. The sample was prepared by arc melting and annealing at 873 K for 1450 hours. The starting materials were Sm >99.9 mass%, Co 99.99 mass%, Ge 99.999 mass% (Mruz et al. 1989).

Bodak et al. (1986) reported the crystal structure for Sm_2CoGe_2 (15) (Sc₂CoSi₂ type, a=1.0818, b=1.0343, c=0.4254, $\gamma=118.53^\circ$; X-ray powder diffraction) from an arc melted sample annealed at 870 K.

Investigating the isothermal section of the Sm–Co–Ge system, Mruz et al. (1987a) observed the Sm₄Co_{0.64}Ge₇ (12) compound which belonged to a new structure type. The crystal structure was investigated by a single-crystal method, the lattice parameters were obtained as a = 0.4166, b = 0.4083, c = 3.018.

The crystal structure of three compounds within the Sm–Co–Ge system at 870 K was determined by Mruz (1988): Sm₂Co_{15.1–14.1}Ge_{1.9–2.9} (1) belongs to the Th₂Zn₁₇ type, a = 0.8425-0.8433, c = 1.2336-1.2368; SmCoGe₃ (4) crystallizes with the BaNiSn₃ type, a = 0.8425-0.8433, c = 1.2336-1.2368; SmCoGe₃ (4) crystallizes with the BaNiSn₃ type, a = 0.8425-0.8433, c = 0.8425-0.8433, c

0.4277, c = 0.9799; and Sm₅Co_{3-2.5}Ge_{12-12.5} (7) was observed to form a new structure type with lattice parameters a = 0.4143-0.4174, b = 2.5534-2.5597, c = 0.4216-0.4221.

The crystal structures of eight more germanides, $\sim Sm_3Co_2Ge_8$ (5), $\sim Sm_3Co_2Ge_7$ (6), $\sim Sm_5Co_4Ge_6$ (10), $\sim Sm_{2.9}Co_{0.9}Ge_{4.2}$ (13), $\sim Sm_3Co_2Ge_3$ (14), $\sim Sm_{14}Co_4Ge_{11}$ (16), $\sim Sm_3Co_2Ge_2$ (17), $\sim Sm_5Co_2Ge_4$ (18) have not been solved yet.

Mruz (1988) observed the existence of the $Sm_{117}Co_{52}Ge_{112}$ compound at 870 K (Tb₁₁₇Fe₅₂Ge₁₁₂ type, a=2.8928) which was found to decompose at 670 K. This compound is not shown in fig. 75, since it contains ~42 at.% Sm and thus is outside of the composition range of the 870 K isothermal section (0–40 at.% Sm), and as it does not exist at 670 K it does not appear in this isothermal section.

Venturini et al. (1985b) reported an X-ray powder diffraction study of the $Sm_3Co_4Ge_{13}$ compound from a sample prepared by heating a mixture of the starting components in an evacuated quartz tube and homogenizing at 1073 K. Finally the sample was quenched in water. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃ type, *a* = 0.8814. The purity of the starting components was Sm 99.9 mass%, Co 99.99 mass% and Ge 99.99 mass%.

4.7.4. Sm--Ni--Ge

Phase equilibria in the isothermal sections at 870 K (0–40 at.% Sm) and 670 K (40–100 at.% Sm) have been established by Mruz (1988) using X-ray powder diffraction and microstructural analyses of 247 ternary alloys synthesized by arc melting ingots of Sm (99.77 mass%), Ni (99.99 mass%) and Ge (99.99 mass%); the alloys were then annealed in evacuated quartz tubes for 500–900 hours. The phase relations are characterized by the formation of twelve ternary compounds and by the existence of rather extended solid solutions originating at Sm_5Ge_3 (dissolves up to 12.5 at.% Ni), SmNi₅ (15 at.% Ge) and Sm_2Ni_{17} (15 at.% Ge). Phase equilibria in the isothermal sections at 870 K and 670 K are presented in fig. 76.

SmNi₅Ge₃ (3) was reported to crystallize with the YNi₅Si₃ type, a=1.9196, b=0.38981, c=0.67917 by Mruz (1988). The arc melted alloy was annealed at 870 K and investigated by X-ray powder diffraction analysis.

The SmNi₂Ge₂ (5) compound was found to adopt the CeGa₂Al₂-type of structure, a = 0.4091, c = 0.9814 (Rieger and Parthé 1969b).

SmNiGe₃ (7) with its own structure type (a=2.1657, b=0.4102, c=0.4092, X-ray single-crystal analysis) was reported by Bodak et al. (1985). For details of sample preparation and purity of starting materials, see above.

Sm₂NiGe₆ (8) has been found by Mruz (1988) from X-ray powder diffraction to be isostructural with the Ce₂CuGe₆ type (a=0.4062, b=0.3995, c=2.1496). The sample was prepared by arc melting ingots of the constituting elements and annealing at 870 K for 700 hours. For the purity of starting materials, see above.

Pecharsky et al. (1989) investigated the formation and crystal structure of the SmNi_{1-0.75}Ge₂ (9) compound by X-ray powder analysis of arc melted alloys annealed at 870 K (CeNiSi₂ type, a = 0.4147 - 0.4168, b = 1.6701 - 1.6589, c = 0.4147 - 0.4105).



Fig. 76. Sm-Ni-Ge, isothermal sections at 870 K (0-40 at.% Sm) and 670 K (40-100 at.% Sm).

Mruz et al. (1987b) reported the crystal structure of SmNiGe (10) (TiNiSi type, a = 0.7100, b = 0.4275, c = 0.7301; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 500 hours.

An early investigation of the interaction of germanium with samarium and nickel has shown the existence of the SmNi_{0.6-0.5}Ge_{1.4-1.5} (11) compound with AlB₂ type, a=0.4125-0.4114, c=0.4101-0.4127 (Gladyshevsky and Bodak 1965; X-ray powder diffraction).

The crystal structures of five germanides, \sim SmNi₇Ge₂ (1), \sim SmNi₆Ge₂ (2), \sim Sm₂Ni₉Ge₅ (4), \sim Sm₂Ni₃Ge₅ (6), \sim Sm₃NiGe₂ (12) have not been evaluated (Mruz 1988).

One more ternary compound was reported by Bodak et al. (1982) who investigated the crystal structure of Sm₃NiGe₂ compound (La₃NiGe₂ type, a = 1.1605, b = 0.4242, c = 1.1470) by the powder X-ray diffraction method. Apparently this compound does not exist at 870 K. For sample preparation and purity of starting elements, see Y₃NiGe₂ under Y–Ni–Ge.

The SmNi₃Ge₃ compound was investigated by the single-crystal method (own structure type, a = 0.4070, c = 2.5137). The single crystal was obtained from "as-cast" alloy (Mruz 1988). This compound was not observed at 870 K.

4.7.5. Sm-Cu-Ge

No phase diagram is available for the Sm-Cu-Ge system, but five ternary compounds have been found.

Rieger and Parthé (1969a) investigated the occurrence of the AlB_2 -type structure by means of X-ray powder diffraction of arc melted alloys. The data presented were SmCu_{1-0.67}Ge_{1-1.33} with a = 0.4255 - 0.4152, c = 0.3847 - 0.4101. Iandelli (1993) confirmed the AlB₂ type (a = 0.4259 c = 0.3810, X-ray powder analysis) from the SmCuGe alloy which was prepared from filings or powders of the metals (samarium 99.7 mass%, copper and germanium 99.99 mass%) mixed and sealed in a tantalum crucible under argon, followed by melting in an induction furnace; afterwards the sample was annealed for 10 days at 1023 K.

Sologub et al. (1995a) reported on the crystal structure of Sm_2CuGe_6 alloy prepared by arc melting under argon and annealing at 870 K in an evacuated quartz tube for one week. From X-ray powder analysis, it was shown that this compound has the Ce₂CuGe₆-type structure with a = 0.41496, b = 0.40275, c = 2.1221.

Rieger and Parthé (1969b) prepared SmCu₂Ge₂ with the CeGa₂Al₂-type of structure, a=0.4088, c=1.0223.

Francois et al. (1990) reported the crystal structure of the SmCu_{0.55}Ge₂ (CeNiSi₂ type, a=0.4163, b=1.690, c=0.4028). For sample preparation, see LaFeGe₂ under La–Fe–Ge.

Sm₆Cu₈Ge₈ crystallizes with the Gd₆Cu₈Ge₈-type and lattice parameters a = 1.412, b = 0.668, c = 0.426 (Hanel and Nowotny 1970).

4.7.6. Sm-Zn-Ge

No isothermal section is available for the ternary Sm–Zn–Ge system, however one ternary compound was observed and characterized by Rossi and Ferro (1996). SmZn_{1.5}Ge_{0.5} was found to crystallize with the AlB₂ type, a = 0.4412, c = 0.3737 from X-ray powder diffraction of an induction melted alloy which was annealed at 1070 K for one week. An electronic micrographic examination, as well as microprobe microanalysis, was carried out. The metals employed in the synthesis of samples had a nominal purity of 99.9 mass% for samarium, and 99.999 mass% for other metals.

4.7.7. Sm-Ru-Ge

The phase equilibria in the Sm–Ru–Ge system have been investigated by Morozkin et al. (1996) by means of X-ray phase and local X-ray spectral analyses of ternary alloys, which were arc melted and subsequently annealed in evacuated silica tubes at 870 K for 1000 hours and finally quenched in water. Starting materials were Sm 99.98 mass%, Ru 99.99 mass%, Ge 99.99 mass%. According to the phase diagram, six ternary compounds exist within the Sm–Ru–Ge system at 870 K (fig. 77). The system contains an extended region of ternary solid solution based at SmRu₂.

Early investigations of the SmRu₂Ge₂ (1) compound showed that it had the CeGa₂Al₂type structure: a=0.4236, c=0.9944, after Felner and Nowik (1985) from X-ray powder analysis of an induction melted alloy; and a=0.4238, c=0.9953 (Francois et al. 1985) from X-ray powder analysis of alloy obtained by powder metallurgical reaction at 1273 K. The starting components were Sm (3N), Ru (4N) and Ge (4N). The crystal structure type was confirmed by Morozkin et al. (1996): a=0.4237, c=0.9918 from arc melted alloy annealed at 870 K.



Fig. 77. Sm-Ru-Ge, isothermal section at 870 K.

Venturini et al. (1986b) and Morozkin et al. (1996) reported that the $Sm_2Ru_3Ge_5$ (2) compound crystallizes with the U₂Co₃Si₅-type structure. Lattice parameters were reported as a=0.9867, b=1.244, c=0.5790 (Venturini et al. 1986b; X-ray powder diffraction; for sample preparation, see La₂Ru₃Ge₅ under La-Ru-Ge) and a=0.9880, b=1.2403, c=0.5778 (Morozkin et al. 1996).

The $Pr_3Rh_4Sn_{13}$ -type structure was reported for the $Sm_3Ru_4Ge_{13}$ compound (a= 0.9018) by Segre et al. (1981a) from X-ray powder analysis of arc melted samples annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Sm (3N), Ru (3N), Ge (6N). At variance with these data, Morozkin et al. (1996) observed the SmRuGe_3 (3) compound with the same structure type and lattice parameters a= 0.9012 from X-ray powder analysis of arc melted alloy annealed at 870 K.

Sm₃Ru₂Ge₂ (4) was found to crystallize with the La₃Ni₂Ga₂-type structure (a=0.5611, b=0.7818, c=1.3473, X-ray powder diffraction) from arc melted samples annealed at 870 K (Bodak et al. 1989a). Morozkin et al. (1996) observed the same structure type and determined the lattice parameters a=0.5595, b=0.7799, c=1.3527.

The crystal structure of the Sm₂RuGe₂ (5) compound belongs to the Zr₂CoSi₂ type, a=1.0713, b=1.114, c=0.413, $\gamma=129.3^{\circ}$ (Morozkin et al. 1996).

A compound of unknown structure, $Sm_{0.62}Ru_{0.28}Ge_{0.10}$ (6), was observed by Morozkin et al. (1996) from a sample annealed at 870 K.

The crystal structure of the SmRuGe compound was investigated by Welter et al. (1993b). It was found to adopt the PbFCl type, a=0.4244, c=0.6711 (X-ray powder diffraction). The compound was prepared from commercially available high-purity elements. A compacted stoichiometric mixture under argon in a sealed silica tube was

heated to 1173 K for preliminary homogenization and then melted in an induction furnace. This compound apparently does not exist at 870 K.

4.7.8. Sm-Rh-Ge

The phase equilibria in the Sm–Rh–Ge system have been investigated by Morozkin et al. (1996) by means of X-ray phase and local X-ray spectral analyses of ternary alloys, which were arc melted and subsequently annealed in evacuated silica tubes at 870 K for 1000 hours and finally quenched in water. The starting materials were Sm 99.98 mass%, Rh 99.99 mass%, Ge 99.99 mass% pure. Fourteen ternary compounds were found to exist within the Sm–Rh–Ge system at 870 K (fig. 78). The system contains an extended region of ternary solid solution based at SmRh₂.

Venturini et al. (1985b) reported an X-ray powder diffraction study of the Sm₃Rh₄Ge₁₃ compound from a sample which was prepared by heating a mixture of starting components in an evacuated quartz tube and homogenized at 1073 K. Finally the sample was quenched in water. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃ type, a=0.8985. The purity of the starting components was Sm 99.9 mass%, Rh 99.99 mass% and Ge 99.99 mass%. Morozkin et al. (1996) observed the homogeneity field for this compound which includes the SmRhGe₃ composition: Sm_{3+x}Rh₄Ge_{13-x} (x=0-1) (4), a=0.8969-0.8976 from X-ray powder analysis of arc melted alloy annealed at 870 K.

Early investigations of the SmRh₂Ge₂ (2) compound determined the CeGa₂Al₂ type: a=0.4126, c=1.037 (Francois et al. 1985). For sample preparation, see CeRu₂Ge₂ under Ce-Ru-Ge. The structure type for this compound was confirmed later by Morozkin et al. (1996), a=0.4101, c 1.0310 from arc melted alloy annealed at 870 K.



Fig. 78. Sm-Rh-Ge, isothermal section at 870 K.

Sm₂Rh₃Ge₅ (3) was found to crystallize with the Lu₂Co₃Si₅ type (a=1.0005, b=1.2084, c=0.5894, $\beta=120.2^{\circ}$) by Venturini et al. (1986b) from X-ray powder analysis.

Hovestreydt et al. (1982) reported the crystal structure of the SmRhGe (5) compound (TiNiSi type, a=0.7074, b=0.4371, c=0.7468; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. The starting components were Sm (3N), Rh (4N) and Ge (5N). Morozkin et al. (1996) observed the TiNiSi type for the sample annealed at 870 K (a=0.7060, b=0.4360, c=0.7448).

Gladyshevsky et al. (1991a) reported on the crystal structure for the Sm₃Rh₂Ge₂ (6) compound (La₃Ni₂Ge₂ type, a = 0.5608, b = 0.7933, c = 1.3332; X-ray powder diffraction). For the details of sample preparation, see La₃Rh₂Ge₂ under La–Rh–Ge. Morozkin et al. (1996) observed the same structure type and lattice parameters a = 0.5592, b = 0.7895, c = 1.3293 from X-ray powder diffraction.

Studying this phase diagram, Morozkin et al. (1996) established the crystal structure for SmRh₅Ge₃ (1) (UCo₅Si₃ type, a = 1.5848, c = 0.3679), SmRh_{1-x}Ge_{2+x} (9) (CeRh_{1-x}Ge_{2+x} type, a = 0.4225, b = 0.4304, c = 1.507), Sm₃₃Rh₂₅₋₂₀Ge₄₂₋₄₇ (8) (AlB₂ type, a = 0.4219-0.4208, c = 0.4017-0.4025), Sm₂RhGe₂ (7) (Zr₂CoSi₂ type, a = 1.065, b = 1.118, c = 0.4106, $\gamma = 129.96^{\circ}$) and for Sm₂RhGe₆ (10) (Ce₂CuGe₆ type, a = 0.4060, b = 0.4008, c = 2.190). In addition they observed four compounds with an unknown structure: \sim Sm_{0.33}Rh_{0.53}Ge_{0.14} (11), \sim SmRh₂Ge (12), \sim Sm_{0.18}Rh_{0.64}Ge_{0.18} (13), \sim SmRh₃Ge₆ (14).

Verniere et al. (1995) mentioned the existence of $Sm_4Rh_{13}Ge_9$ compound with the $Ho_4Ir_{13}Ge_9$ type. No lattice parameters were given. For the experimental procedure, see $La_4Ir_{13}Ge_9$ under La–Ir–Ge. This compound was not observed by Morozkin et al. (1996) in the investigation of phase equilibria in the Sm–Rh–Ge system at 870 K.

4.7.9. Sm-Pd-Ge

A systematic study of the Sm–Pd–Ge system at 870 K was performed by Barakatova (1994) over the whole concentration region by means of X-ray powder and single-crystal analyses as well as using metallography and microprobe analyses. The samples were prepared by arc melting under argon and annealing in evacuated quartz ampoules at 870 K for 1000 hours.

The phase-field distribution in the isothermal section at 870 K (fig. 79) is characterized by existence of ten ternary compounds. Maximum solubilities of germanium in the binary compounds of the Sm–Pd system are 10 at.% for SmPd and 5 at.% for SmPd_{3–2.3}. Solubility of samarium in the palladium germanides was found to be negligible. As reported by Barakatova (1994), SmPd₂Ge₂ (2) and Sm(Pd,Ge)₂ (9) dissolve 15 at.% Ge and 10 at.% Ge respectively.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound SmPdGe (8) adopts the KHg₂-type of structure, a=0.44263, b=0.7110, c=0.7606. For sample preparation, see LaPdGe under La-Pd-Ge. The starting materials were Sm (3N), Pd (4N) and Ge (5N). The existence of SmPdGe was later confirmed by Barakatova (1994) (KHg₂ type, a=0.4426, b=0.7110, c=0.7606; X-ray powder data).



Fig. 79. Sm-Pd-Ge, isothermal section at 870 K.

The crystal structure of the compound SmPd₂Ge (6) was found to be of the YPd₂Si type (a=0.7501, b=0.6996, c=0.5673; X-ray powder diffraction) by Jorda et al. (1983). For the experimental procedure, see LaPd₂Ge under La–Pd–Ge. The starting materials were palladium 99.99 mass%; germanium, specpure quality; samarium 99.9 mass%. Barakatova (1994) confirmed the structure type and determined the lattice parameters a=0.7504, b=0.6995, c=0.5680 from X-ray powder analysis.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Sm₂PdGe₆ (4) compound which was found to crystallize with the Ce₂CuGe₆-type structure, a=0.4116, b=0.4044, c=2.170. For the experimental procedure, see La₂PdGe₆ under La–Pd–Ge. The starting materials used were obtained from Johnson & Matthey, UK (99.9 mass%). The structure type after Barakatova (1994) is the same and lattice parameters are a=0.4115, b=0.4031, c=2.164.

During the phase investigation in the Sm–Pd–Ge system, Barakatova (1994) established the crystal structure for Sm₃Pd₂₀Ge₆ (1) (Ce₃Pd₂₀Ge₆ type, a=1.242-1.245); SmPd_{2.5-1.75}Ge_{1.5-2.25} (2) (BaAl₄ type, a=0.4238-0.4258, c=0.9971-1.0066); Sm₂Pd₃Ge₅ (3) (U₂Co₃Si₅ type, a=1.0136, b=1.2203, c=0.5983); Sm_{0.25}Pd_{0.65}Ge_{0.10} (5) (CaTiO₃ type, a=0.4158); SmPdGe₂ (7) (YIrGe₂ type, a=0.4345, b=0.8762, c=1.6558); SmPd_{0.8-0.5}Ge_{1.2-1.5} (9) (AlB₂ type, a=0.4276-0.4216, c=0.3669-0.4115); and Sm₂PdGe (10) (FeB type, a=0.8453, b=0.3732, c=0.5582).

4.7.10. Sm-Ag-Ge

Information on interaction of samarium with silver and germanium is due to the work of three groups of authors (Sologub et al. 1995a, Protsyk 1994, Gibson et al. 1996). The

phase diagram of the Sm-Ag-Ge system is not available; three ternary compounds have been observed and analyzed.

The crystal structure of Sm_2AgGe_6 was found to be isotypic with Ce_2CuGe_6 , a = 0.42394, b = 0.40956, c = 2.1346 by Sologub et al. (1995a) who employed X-ray powder diffraction analysis of an arc melted sample which was homogenized by annealing at 873 K for 150 hours.

Protsyk (1994) reported the SmAg₂Ge₂ compound with the CeGa₂Al₂-type structure, a=0.4223, c=1.1048. For sample preparation, see Ce–Ag–Ge.

The crystal structure of the SmAgGe compound was investigated by Gibson et al. (1996) with X-ray powder diffraction. It was found to adopt the ZrNiAl type with lattice parameters a = 0.72005, c = 0.42692. The alloy was arc melted and annealed at 970 K for 10 days.

4.7.11. Sm–Os–Ge

No phase diagram is available at present for the system Sm–Os–Ge, however, one ternary germanide has been observed and characterized by Segre et al. (1981a). Sm₃Os₄Ge₁₃ was found to crystallize with the Pr₃Rh₄Sn₁₃ type, a=0.9043. For sample preparation, see Ce₃Ru₄Ge₁₃ under Ce–Ru–Ge.

4.7.12. Sm–Ir–Ge

Phase relations have not been established for the Sm-Ir-Ge system; information concerning the formation of compounds and their crystal structure is due to the work of different groups of authors.

Francois et al. (1987) reported the crystal structure of SmIrGe₂ (YIrGe₂ type, a = 0.4314, b = 1.603, c = 0.8871). The sample was prepared by heating a mixture of powders of the starting components (Sm 3N, Ir 3N and Ge 3N) in an evacuated silica tube at 1173 K.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound SmIrGe adopts the TiNiSi-type structure, a=0.7017, b=0.4346, c=0.7557. For the experimental procedure, see LaIrGe under La–Ir–Ge.

SmIr₂Ge₂ was found to crystallize in the P4/nmm space group with lattice parameters a=0.4203, c=1.0084 (Francois et al. 1985).

Sm₂Ir₃Ge₅ was found to adopt the U₂Co₃Si₅-type structure (a = 1.0151, b = 1.182, c = 0.6005) by Venturini et al. (1986b) from X-ray powder analysis.

Verniere et al. (1995) observed the existence of $Sm_4Ir_{13}Ge_9$ with $Ho_4Ir_{13}Ge_9$ -type. The lattice parameters have not been established. For the experimental details, see $La_4Ir_{13}Ge_9$ under La–Ir–Ge.

Venturini et al. (1985b) reported on the X-ray powder diffraction study of the $Sm_3Ir_4Ge_{13}$ compound from a sample which was prepared by heating a mixture of the starting components (Sm 3N, Ir 4N, Ge 4N) in an evacuated quartz tube and homogenizing at 1073 K. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃ type, *a*=0.9012.



Fig. 80. Sm-Pt-Ge, isothermal section at 870 K.

4.7.13. Sm–Pt–Ge

A systematic study of the Sm–Pt–Ge system at 870 K was performed by Barakatova (1994) over the whole concentration region by means of X-ray powder and single-crystal analyses as well as using metallography and microprobe analyses of 158 alloys. The samples were prepared by arc melting under argon and annealing in evacuated quartz ampoules at 870 K for 1000 hours.

The phase-field distribution in the isothermal section at 870 K (fig. 80) is characterized by the existence of 21 ternary compounds. The maximum solubility of germanium in the binary compounds of Sm–Pt is not indicated by the author. The solubility of samarium in the palladium germanides was found to be negligible.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound SmPtGe (18) adopts the TiNiSi-type of structure, a=0.7144, b=0.4396, c=0.7585. For sample preparation, see LaPdGe under La-Pd-Ge. The starting materials were Sm (3N), Pt (4N) and Ge (5N). At variance with these data, Barakatova (1994) observed the SmPtGe compound with the KHg₂ type, lattice parameters a=0.4377, b=0.7114, c=0.7573, from X-ray powder analysis of arc melted alloy annealed at 870 K.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Sm₂PtGe₆ (14) compound which was found to crystallize with the Ce₂CuGe₆ type, a=0.40955, b=0.40412, c=2.1871. For the experimental procedure, see La₂PdGe₆ under La–Pd–Ge. The starting materials used were obtained from Johnson & Matthey, UK (99.9 mass%).

Venturini et al. (1989a) investigated the crystal structure of SmPt₂Ge₂ (11) from an arc melted sample annealed at 1273 K for 5 days. The crystal structure was found to

belong to the LaPt₂Ge₂ type, a = 0.4345, b = 0.4378, c = 0.9751, $\beta = 91.02^{\circ}$. The starting materials were Sm (3N), Pt (4N) and Ge (4N).

Francois et al. (1987) mentioned the existence of SmPtGe₂ (17) with the YIrGe₂-type of structure. No lattice parameters were given. Barakatova (1994) confirmed the crystal structure and established the lattice parameters a = 0.4367, b = 0.8720, c = 1.6332 by X-ray powder analysis.

In the course of phase equilibrium investigation in the Sm–Pt–Ge system, Barakatova (1994) established the crystal structure for Sm_{0.165}Pt_{0.735}Ge_{0.1} (5) (CaCu₅ type, a=0.5296, c=0.4413), SmPt_{2.25}Ge_{1.75} (10) (CaBe₂Ge₂ type, a=0.4288, c=0.9975), SmPt_{1.87}Ge_{2.13} (12) (CaBe₂Ge₂ type, a=0.4325, c=0.9909), Sm₂Pt₃Ge₅ (13) (U₂Co₃Ge₅ type, a=0.9874, b=1.1987, c=0.5731), Sm₃Pt₄Ge₆ (15) (Ce₃Pt₄Ge₆ type, a=0.4351, b=0.4359, c=2.5886), SmPt₂Ge (16) (Fe₃C type, a=0.7436, b=0.6901, c=0.5585), SmPt_{0.35-0.65}Ge_{1.65-1.35} (19) (AlB₂ type, a=0.4252-0.4185, c=0.4022-0.4157), SmPt_{0.24} Ge_{1.76} (20) (α -ThSi₂ type, a=0.4147, c=1.4131) and Sm₂Pt_{1-1.6}Ge_{1-0.4} (21) (CrB type, a=0.4033-0.3894, b=1.0884-1.0760, c=0.4287-0.4415).

The formation of eight more ternary phases with unknown structures has been observed by Barakatova (1994) while investigating the isothermal section of the Sm–Pt–Ge system at 870 K. They exist at compositions close to $\text{Sm}_{0.075}\text{Pt}_{0.625}\text{Ge}_{0.30}$ (1), $\text{Sm}_{0.075}\text{Pt}_{0.475}\text{Ge}_{0.45}$ (2), $\text{Sm}_{0.10}\text{Pt}_{0.665}\text{Ge}_{0.235}$ (3), $\text{Sm}_{0.12}\text{Pt}_{0.58}\text{Ge}_{0.30}$ (4), $\text{Sm}_{0.165}\text{Pt}_{0.635}\text{Ge}_{0.20}$ (6), $\text{Sm}_{0.165}\text{Pt}_{0.57}$ Ge_{0.265} (7), $\text{Sm}_{0.165}\text{Pt}_{0.525}\text{Ge}_{0.32}$ (8) and $\text{Sm}_{0.20}\text{Pt}_{0.60}\text{Ge}_{0.20}$ (9).

4.7.14. Sm-Au-Ge

Information on interaction of samarium with gold and germanium is due to the work of two groups of authors (Sologub et al. 1995a and Rossi et al. 1992). The phase diagram of the Sm–Au–Ge system is not available; two ternary compounds have been observed and analyzed.

Sologub et al. (1995a) employed X-ray powder diffraction analysis for investigation the crystal structure of the Sm₂AuGe₆ compound from an arc melted sample, which was homogenized by annealing at 873 K for 150 hours. The crystal structure was found to be isotypic with Ce₂CuGe₆, a=0.42394, b=0.40956, c=2.1346.

A ternary compound of samarium with gold and germanium in the stoichiometric ratio 1:1:1 has been identified and studied by means of X-ray and metallographic analyses by Rossi et al. (1992). The SmAuGe compound was found to adopt the LiGaGe type with lattice parameters a=0.4434, c=0.7533. The sample was prepared by melting the metals (about 99.9 mass% for samarium and 99.99 mass% for gold and germanium) in an induction furnace and annealing at 1070 K for one week.

4.8. Eu-d element-Ge systems

4.8.1. Eu–Mn–Ge

No phase diagram exists for the system Eu-Mn-Ge, and only one ternary compound has been observed from induction melted alloy by Felner and Novik (1978). According

to X-ray powder diffraction analysis, the EuMn₂Ge₂ compound crystallizes with the CeGa₂Al₂ type, a=0.4244, c=1.075.

4.8.2. Eu-Fe-Ge

Information on the phase equilibria in the ternary Eu–Fe–Ge system is due to the work of Belan (1988) who employed X-ray powder diffraction on samples prepared by arc melting of pure components. The resulting alloys were annealed at 670 K for 300 hours. The equilibrium phase diagram is shown in fig. 81. No ternary compounds were observed.



Fig. 81. Eu–Fe–Ge, isothermal section at 670 K.

4.8,3. Eu-Co-Ge

The isothermal section of the Eu–Co–Ge phase diagram at 670 K was constructed by Oniskovetz et al. (1985). The phase relations are characterized by the formation of three ternary compounds (fig. 82). For details of sample preparation, see Eu–Fe–Ge.

The crystal structures of two compounds have been studied by Oniskovetz et al. (1985). EuCo_{2.5}Ge_{1.5} (1) belongs to the BaAl₄ type, a=0.4035, c=0.9746; EuCoGe₃ (2) crystallizes with the BaNiSn₃ type, a=0.4345, c=0.9953 (powder X-ray diffraction data). Venturini et al. (1985b) confirmed the crystal structure for the Eu₃Co₄Ge₁₃ compound from a sample prepared by heating a mixture of the starting components in an evacuated quartz tube and homogenizing at 1073 K. Finally the sample was quenched in water. It was found to adopt the Yb₃Rh₄Sn₁₃-type structure, a=0.8814 (X-ray powder diffraction data). The purity of the starting components was Eu 99.9 mass%, Ge 99.99 mass%.



Fig. 82. Eu–Co–Ge, isothermal section at 670 K.

One more ternary compound with an unknown structure has been observed by Oniskovetz et al. (1985) in the course of phase equilibrium investigation in the Eu–Co–Ge system: $Eu_2Co_{1-1,2}Ge_{1-0.8}$ (3).

Felner and Novik (1978) observed the formation of the EuCo₂Ge₂ compound and investigated its crystal structure: CeGa₂Al₂ type, a = 0.4035, c = 1.046. The sample was melted in an induction furnace at about 1870 K under a protective argon atmosphere; afterwards the alloy was homogenized by annealing in the induction furnace at the melting temperature for about 30 min. Starting materials were Eu 99.9 mass%, Co 99.95 mass% and Ge 99.99 mass%. This phase was not observed by Oniskovetz et al. (1985) in the course of phase equilibrium studies in the Eu–Co–Ge system at 670 K.

4.8.4. Eu-Ni-Ge

Phase equilibria in the isothermal sections at 670 K have been determined by Belan (1988) using X-ray powder diffraction of alloys which were synthesized by arc melting ingots of Eu (99.81 mass%), Ni (99.99 mass%) and Ge (99.99 mass%); the alloys were then annealed in evacuated quartz tubes at 670 K for 300 hours. The phase relations are characterized by the formation of six ternary compounds and by the existence of rather extended solid solutions originating at Eu₂Ni₁₇ (up to 18 at.% Ge), EuNi₅ (up to 20 at.% Ge) and Eu₃Ge (up to 12 at.% Ni). The phase equilibria in the isothermal section at 670 K are presented in fig. 83.

The formation and crystal structure of EuNi₂Ge₂ (2) was reported in an early investigation of europium-nickel-germanium combinations by Bodak et al. (1966): CeGa₂Al₂ type, a=0.4086, c=0.9809 (arc melted and annealed at 670 K sample; X-ray powder diffraction data). Belan (1988) confirmed the crystal structure and determined the lattice parameters a=0.4133, c=1.0126.



Fig. 83. Eu–Ni–Ge, isothermal section at 670 K.

According to Oniskovetz et al. (1987), EuNiGe (5) crystallizes with a new structure type, a = 0.6996, b = 0.7581, c = 0.6187, $\gamma = 130.22^{\circ}$ (X-ray single-crystal data). The alloy was obtained by arc melting of the proper amounts of pure components (Eu 99.81 mass%; Ni 99.99 mass%), Ge 99.99 mass%) followed by annealing in an evacuated quartz tube at 670 K for 300 hours.

Crystal structures for four more ternary compounds have been established by Oniskovetz (1984) and Belan (1988) while investigating the Eu–Ni–Ge isothermal section: EuNi₉Ge₄ (1) (CeNi_{8.5}Si_{4.5} type, a=0.7957, c=1.1793); EuNiGe₃ (3) (BaNiSn₃ type, a=0.4437, c=0.9891); EuNiGe₂ (4) (CeNiSi₂ type, a=0.4244, b=1.691, c=0.4228); EuNi_{0.5-0.35}Ge_{1.5-1.65} (6) (AlB₂ type, a=0.4184-0.4169, c=0.4485-0.4480).

4.8.5. Eu-Cu-Ge

A systematic study of the Eu–Cu–Ge system at 670 K was performed by Belan (1988). For sample preparation, see Eu–Ni–Ge. The starting materials were Eu 99.81 mass%, Cu 99.99 mass% and Ge 99.99 mass%. Four ternary compounds were found; two of them are characterized by the formation of extended homogeneity fields (see fig. 84).

Belan (1988) observed and characterized three of the four existing ternary compounds: EuCu_{2.5-1.65}Ge_{1.5-2.35} (1) crystallizes with the CeGa₂Al₂ type, a=0.4187-0.4212, c=1.0116-1.0336; EuCu_{0.8-0.5}Ge_{1.2-1.5} (3) was found to adopt the AlB₂ type, a=0.4217-0.4218, c=0.4432-0.4460; EuCuGe (2) belongs to the TiNiSi type, a=0.7342, b=0.4372, c=0.7550. In contrast, Iandelli (1993) reported a CaCuGe type with a=2.209, b=0.7543, c=0.4453 from X-ray powder diffraction. For the experimental details, see SmCuGe under Sm-Cu-Ge.





The crystal structure for the Eu_2Cu_2Ge (4) compound has not yet been resolved (Belan 1988).

4.8.6. Eu–Zn–Ge

The only information on the interaction of europium with zinc and germanium is due to the work of Pöttgen (1996) who reported the crystal structure of EuZnGe (ZrBeSi type, a=0.4372, c=0.8604; X-ray powder diffraction).

4.8.7. *Eu–Ru–Ge*

EuRu₂Ge₂ was found to crystallize with the CeGa₂Al₂ type structure. The lattice parameters were reported as a=0.4276, c=1.0204 (Francois et al. 1985).

4.8.8. Eu-Rh--Ge

No phase diagram is available for the system Eu-Rh-Ge, and so far, only two ternary compounds have been observed and characterized.

According to Venturini et al. (1985b), the EuRhGe₃ compound crystallizes with the BaNiSn₃ type, a = 0.4410, c = 1.0064 (X-ray powder diffraction analysis). For sample preparation and purity of starting components, see EuCoGe₃ under Eu-Co-Ge.

EuRh₂Ge₂ was found to crystallize with the CeGa₂Al₂ type, a = 0.4164, c = 1.0601 (Francois et al. 1985).

4.8.9. Eu-Pd-Ge

Little information exists on the Eu-Pd-Ge system; two compounds have been observed and characterized so far.

According to Belan (1988), the EuPdGe crystallizes with the EuNiGe type, a = 0.6132, b = 0.7934, c = 0.7441, $\gamma = 132.64^{\circ}$ (X-ray powder diffraction data). The alloy was obtained by arc melting the proper amounts of pure components (Eu 99.81 mass%; Pd 99.99 mass%, Ge 99.99 mass%) followed by annealing in an evacuated quartz tube at 670 K for 300 hours and finally quenching in cold water.

The crystal structure of the compound EuPd₂Ge was found to be of the YPd₂Si type (a=0.7582, b=0.6981, c=0.5834; X-ray powder diffraction) by Jorda et al. (1983). The sample was obtained by induction heating the pressed powder compacts in a levitation coil under an argon atmosphere, pressure 4 atm. After the rapid reaction in the liquid state the molten sample was dropped into a boron nitride crucible. The alloy was annealed in an evacuated quartz tube for 10 days at 1173 K. Starting materials were palladium 99.99 mass%, germanium in specpure quality, and europium 99.9 mass%.

4.8.10. Eu-Ag-Ge

The phase equilibria for Eu–Ag–Ge in the isothermal section at 670 K have been determined by Protsyk (1994) using X-ray powder diffraction analysis of 80 ternary alloys, which were synthesized by arc melting ingots of Eu (98.9 mass%), Ag (99.9 mass%) and Ge (99.99 mass%). The alloys were annealed in evacuated quartz tubes for 400 hours. The total number of compounds observed was three. The EuAg₂ binary compound was observe to dissolve up to 15 at.% Ge. The solubility of the third component in other binary compounds was reported to be negligible. The phase equilibria in the isothermal sections at 670 K are presented in fig. 85.



Fig. 85. Eu–Ag–Ge, isothermal section at 670 K.

The EuAg_{2.00-2.25}Ge_{2.00-1.75} (2) compound was observed and studied by Protsyk (1994). It was found to crystallize with the CeGa₂Al₂ type, lattice parameters a = 0.4300-0.4405, c = 1.0787-1.0835, by X-ray powder diffraction of arc melted alloys annealed at 470 K.

The formation and crystal structure of the EuAgGe (3) compound was investigated by Protsyk (1994): AlB₂ type, a=0.4364, c=0.4373 (arc melted sample annealed at 670 K; X-ray powder diffraction data). Merlo et al. (1996) reported a dependence of the crystal structure of the EuAgGe system on the thermal treatment. According to micrographic and microprobe analyses, the as-cast sample, prepared on the 1:1:1 formula, contained two phases in nearly equal quantities, with approximate compositions EuAg_{1.1}Ge_{0.9} and EuAg_{0.8}Ge_{1.1}. The X-ray powder pattern was completely indexed as a mixture of reflections of the CeCu₂-type cell and an AlB₂-type phase. The same sample, annealed at 970 K, showed a prevailing phase with composition EuAgGe_{0.9}. Nearly all reflections of the powder pattern were indexed on the basis of the CeCu₂-type cell, while some weak lines were ascribed to the AlB₂-type cell. The Ag-rich formulae (EuAg_{1.1}Ge_{0.9}) and Gerich formulae (EuAg_{0.8}Ge_{1.1}) were assigned to the CeCu₂ type (a=0.4675, b=0.7395, c=0.7981) and the AlB₂ type (a=0.4390, c=0.4360), respectively.

The crystal structure of $Eu_{0.166}Ag_{0.654}Ge_{0.18}$ (1) has not been resolved yet (Protsyk 1994).

4.8.11. Eu-Os-Ge

No phase diagram is available at present for the system Eu–Os–Ge, however, one ternary gemanide has been observed and characterized by Segre et al. (1981a). Eu₃Os₄Ge₁₃ was found to crystallize with the Pr₃Rh₄Sn₁₃ type, a = 0.9057 (Segre et al. 1981a). For sample preparation, see Ce₃Ru₄Ge₁₃ under Ce–Ru–Ge.

4.8.12. Eu–Ir–Ge

Phase equilibria for the ternary Eu-Ir-Ge system have not been derived, however, the formation of two compounds has been observed.

The existence of EuIrGe₃ has been established by Venturini et al. (1985b). Crystallographic data reported are BaNiSn₃ type, a = 0.4436, c = 1.0033 (X-ray powder diffraction). For details of the experimental procedure, see LaCoGe₃ under La–Co–Ge.

EuIr₂Ge₂ was found to crystallize with the CeGa₂Al₂ type, a=0.4172, c=1.0543 (Francois et al. 1985).

4.8.13. Eu–Pt–Ge

Information on the interaction of europium and platinum with germanium is due to the work of two research groups who employed X-ray powder as well as single-crystal analyses for the investigation of alloys with specific compositions. The phase diagram of the Eu-Pt-Ge system is not available.

Venturini et al. (1989a) investigated the crystal structure of $EuPt_2Ge_2$ from an arc melted sample annealed at 1273 K for 5 days. The crystal structure was found to

belong to the LaPt₂Ge₂ type, a=0.4417, b=0.4456, c=0.9751, $\beta=91.27^{\circ}$ (X-ray powder diffraction data). The starting materials were Eu (3N), Pt (4N) and Ge (4N).

Pöttgen et al. (1996b) investigated the crystal structure of EuPtGe: ZrOS type, a = 0.65463 (single-crystal X-ray data). The starting materials for the preparation were ingots of europium (Johnson & Matthey), platinum powder (Degussa) and germanium lumps (Wacker), all with stated purity greater than 99.9 mass%. The elements were mixed in the ideal atomic ratio and sealed in a tantalum tube under an argon pressure of about 800 mbar. The tantalum tube was sealed in a quartz ampoule and heated at 1320 K for five days, then cooled to 1170 K and annealed for an additional four weeks.

4.8.14. Eu-Au-Ge

Phase relations have not been established for the ternary system Eu–Au–Ge; only one ternary compound has been reported: EuAuGe crystallizes in a new ternary ordered version of the CeCu₂ type, a=0.4601, b=0.7371, c=0.7881 (single-crystal X-ray data; Pöttgen 1995). For sample preparation, see EuPtGe under Eu–Pt–Ge.

4.9. Gd-d element-Ge systems

4.9.1. *Gd–Mn–Ge*

Phase equilibria in the isothermal section at 970 K have been established by Markiv et al. (1993) using X-ray powder diffraction analysis of 103 ternary alloys which were synthesized by arc melting ingots of Gd (99.85 mass%), Mn (99.9 mass%) and Ge (99.999 mass%); the alloys were then annealed in evacuated quartz tubes for 450–550 hours. In some cases the alloys were preliminary homogenized at 1270 K and 1170 K for 10–30 hours. The phase relations are characterized by the formation of nine ternary compounds and by the existence of a solid solution originating at GdMn₂. Phase equilibria in the isothermal sections at 970 K are presented in fig. 86.

Information concerning the formation of compounds in the ternary Gd-Mn-Ge system is due to the work of several groups of authors; nine ternary compounds have been reported for the various gadolinium-manganese-germanium combinations.

Rossi et al. (1978b) reported on the crystal structure of the GdMn₂Ge₂ (4) compound (CeGa₂Al₂ type, a = 0.4029, c = 1.0895; X-ray powder method). The alloy was obtained by melting under argon in an induction furnace and was annealed at 770 K for one week. The metals used were of purity greater than 99.9 mass% for Gd, and greater than 99.99 mass% for Mn and Ge. The CeGa₂Al₂ structure type was confirmed by Belyavina et al. (1993) from X-ray powder diffraction of an arc melted alloy annealed at 970 K (a = 0.4026, c = 1.0887).

GdMn₆Ge₆ (1) was found to crystallize with the HfFe₆Ge₆-type structure by Venturini et al. (1992), a=0.5242, c=0.8184 (X-ray powder diffraction data). The alloy was synthesized by a powder metallurgical reaction in an evacuated silica tube at 1073 K for 14 days. Belyavina et al. (1993) suggested a new structure type for the GdMn₆Ge₆ compound, which is a derivative from the LiCo₆Ge₆ type but with nearly the same lattice parameters: a=0.52333, c=0.81806.



Fig. 86. Gd-Mn-Ge, isothermal section at 970 K.

Francois et al. (1990) investigated the occurrence of the CeNiSi₂ structure type for several gadolinium-manganese-germanium combinations from alloys annealed at 1173 K: GdMn_{0.26-0.38}Ge₂ (5); a=0.4138-0.4163, b=1.606-1.613, c=0.4000-0.4036. Belyavina et al. (1993) studied the formation and crystal structure for the GdMn_{0.39}Ge₂ compound: CeNiSi₂ type, a=0.41590, b=1.6130, c=0.4039.

Six more ternary compounds were observed and investigated by Belyavina et al. (1993) using X-ray powder diffraction of arc melted alloys annealed at 970 K: GdMn₄Ge₂ (3), ZrFe₄Si₂ type, a=0.76419, c=0.39467; Gd₆Mn₈Ge₈ (6), Gd₆Cu₈Ge₈ type, a=1.4015, b=0.7118, c=0.42027; GdMnGe (7), TiNiSi type, a=0.7138, b=0.41698, c=0.8191; Gd₄Mn_{0.64}Ge₇ (8), Sm₄Co_{0.64}Ge₇ type, a=0.4135, b=0.4045, c=3.0030; GdMn₆Ge₃ (2), unknown structure; and Gd₃Mn₂Ge₃ (9), unknown structure.

4.9.2. Gd–Fe–Ge

Four ternary compounds were found in the Gd-Fe-Ge system.

GdFe₆Ge₆ was reported to be isotypic with the crystal structure of YCo₆Ge₆, with lattice parameters a=0.5118, c=0.4056 (Starodub and Mruz 1983). The sample was prepared by arc melting the proper amounts of the starting components followed by annealing at 870 K for two weeks. At variance with the data presented by Starodub and Mruz (1983), Venturini et al. (1992), using X-ray powder diffraction data, found that GdFe₆Ge₆ crystallized with a new structure type, Pnma space group, a=6.143, b=0.8137, c=7.979. The alloy was obtained by powder metallurgical reaction in an evacuated silica tube at 1173 K for two weeks.

Pecharsky et al. (1989) reported GdFe_{0.33}Ge₂ to crystallize with the CeNiSi₂ type (a= 0.4140, b=1.6017, c=0.4021; X-ray powder analysis). The alloy was arc melted and annealed at 870 K. The purity of the starting materials was greater than 99.9 mass%. Later Francois et al. (1990) investigated the occurrence of the CeNiSi₂ structure type for several gadolinium–iron–germanium combinations from alloys obtained by powder metallurgical reaction which were afterwards annealed at 1173 K: GdFe_{0.25–0.46}Ge₂, CeNiSi₂ type, a= 0.4124–0.4156, b=1.606–1.608, c=0.3998–0.4046.

The GdFe₂Ge₂ compound was investigated by Rossi et al. (1978a) (CeGa₂Al₂ type, a=0.3989, c=1.0485) by means of X-ray diffraction. The alloy was obtained by melting under argon in an induction furnace and annealing at 770 K for one week. The metals used were of purity greater than 99.9 mass% (Gd, Fe) and greater than 99.99 mass% (Ge).

Oleksyn (1990) investigated the crystal structure of $Gd_{117}Fe_{52}Ge_{112}$ by the X-ray powder method ($Tb_{117}Fe_{52}Ge_{112}$ type, a=2.8656). The alloy was synthesized by arc melting followed by annealing at 1070 K for 350 h. The starting materials were Gd 99.83 mass%, Fe 99.9 mass%, Ge 99.99 mass%.

4.9.3. Gd-Co-Ge

The phase diagram of the Gd-Co-Ge system has not been established; nine ternary compounds have been identified for gadolinium-cobalt-germanium combinations.

Méot-Meyer et al. (1985a) reported the crystal structure of $GdCo_{1-x}Ge_2$, x=0.36 (CeNiSi₂ type, a=0.4139, b=1.627, c=0.4062). The sample was prepared by powder metallurgical reaction and annealed in evacuated silica tube at 1173 K. Pecharsky et al. (1989) investigated the formation and crystal structure of the $GdCo_{1-x}Ge_2$ compound by X-ray powder analysis of arc melted alloys annealed at 870 K. The CeNiSi₂-type structure was confirmed, and the existence of an extended homogeneity region was established: 0.3 < x < 0.7 (a=0.4128-0.4165, b=1.6157-1.6398, c=0.4024-0.4077). Francois et al. (1990) confirmed the existence of the homogeneity field with a slight deviation in concentration ratio: $GdCo_{0.24-0.64}Ge_2$, CeNiSi₂ type, a=0.4113-0.4139, b=1.608-1.627, c=0.3986-0.4062. For sample preparation, see GdFe_{0.25-0.46}Ge₂ under Gd-Fe-Ge.

The crystal structure of $Gd_3Co_4Ge_{13}$ (Yb₃Rh₄Sn₁₃ type, a=0.8780; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample which was prepared by heating the a compacted mixture of the starting materials (Gd in pieces, 99.9 mass%; Co and Ge in powder, 99.99 mass%) in an evacuated quartz tube at 1073 K. Bodak et al. (1987) reported the Y₃Co₄Ge₁₃-type structure for the Gd₃Co₄Ge₁₃ compound (a=0.8769; X-ray powder data) from arc melted alloy annealed at 870 K.

Rieger and Parthé (1969b) investigated the formation of the GdCo₂Ge₂ compound (CeGa₂Al₂ type, a = 0.3996, c = 1.0096; X-ray powder diffraction).

From X-ray powder analysis of an alloy obtained by powder metallurgical reaction and annealed at 1173 K, Gd₂Co₃Ge₅ was reported to adopt the Lu₂Co₃Si₅-type structure, a = 0.9683, b = 1.183, c = 0.5750, $\beta = 91.65^{\circ}$ (Venturini et al. 1986b).

The crystal structure of the $GdCo_6Ge_6$ compound was reported by Buchholz and Schuster (1981): YCo_6Ge_6 type, a=0.5016, c=0.3931. The sample was melted under argon in a corundum crucible at 1073–1273 K.

Gorelenko et al. (1984) reported the crystal structure of GdCoGe: TiNiSi type, a = 0.6995, b = 0.4269, c = 0.7253; X-ray powder analysis. The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Gd₃Co₂Ge₄ crystallizes with the Tb₃Co₂Ge₄-type of structure, a = 1.0472, b = 0.8057, c = 0.4177, $\gamma = 107.84^{\circ}$. The sample was prepared by arc melting and annealing at 873 K for 1450 h. The starting materials were Gd >99.9 mass%, Co 99.99 mass%, Ge 99.999 mass% (Mruz et al. 1989).

 Gd_2CoGe_6 is isotypic with Ce_2CuGe_6 , a=0.3952, b=0.4019, c=2.1471 (Oleksyn et al. 1991; X-ray powder diffraction data). The sample was melted in an arc furnace and annealed at 1070 K in an evacuated quartz capsule for 400 h. The purity of the starting materials was greater than 99.9 mass%.

Bodak et al. (1986) reported the crystal structure for Gd_2CoGe_2 (Sc₂CoSi₂ type, a = 1.0647, b = 1.0259, c = 0.4224, $\gamma = 118.48^{\circ}$; X-ray powder diffraction) from an arc melted sample annealed at 870 K.

4.9.4. *Gd–Ni–Ge*

GdNi₅Ge₃ was reported to crystallize with the YNi₅Si₃ type, a=1.9072, b=0.3880, c=0.6792, by Fedyna et al. (1987). The arc melted alloy, annealed at 870 K, was investigated by X-ray powder diffraction analysis. The starting materials were Gd 99.83 mass%, Ni 99.99 mass% and Ge 99.99 mass%.

The GdNi₂Ge₂ compound was found to adopt the CeGa₂Al₂-type structure, a = 0.4063, c = 0.9783 (Rieger and Parthé 1969b).

GdNiGe₃ with the SmNiSi₃-type of structure (a=2.1545, b=0.4079, c=0.4073, X-ray powder diffraction analysis) was reported by Bodak et al. (1985). For details of sample preparation and purity of starting materials, see GdNi₅Ge₃ under Gd–Ni–Ge.

Bodak et al. (1982) reported on the crystal structure of Gd₃NiGe₂ from X-ray powder diffraction (La₃NiGe₂ type, a=1.1450, b=0.4220, c=1.1355). The proper amounts of starting components were arc melted and annealed at 870 K.

 Gd_2NiGe_6 has been found by Oleksyn (1990) from X-ray powder diffraction to be isostructural with Ce_2CuGe_6 (a=0.3976, b=0.4029, c=2.133). The sample was prepared by arc melting ingots of the constituting elements and annealing at 1070 K for 700 h. For the purity of starting materials, see $GdNi_5Ge_3$ under Gd-Ni-Ge.

Pecharsky et al. (1989) investigated the formation and crystal structure of the GdNi_{0.95}Ge₂ compound by X-ray powder analysis of arc melted alloys annealed at 870 K (CeNiSi₂ type, a=0.4128, b=1.674, c=0.4129). For sample preparation, see GdFe_{1-x}Ge₂ under Gd–Fe–Ge. Francois et al. (1990) observed the formation of a homogeneity field for this compound: GdNi_{0.40–0.95}Ge₂, CeNiSi₂ type, a=0.4124–0.4128, b=1.628–1.674, c=0.4009–0.4129.

GdNi_{0.7-0.6}Ge_{1.3-1.4} crystallizes with the AlB₂ type, a=0.4111-0.4101, c=0.4033-0.4053 (Contardi et al. 1977).

Gorelenko et al. (1984) reported the crystal structure of GdNiGe: TiNiSi type, a = 0.7009, b = 0.4280, c = 0.7283; X-ray powder analysis. The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

4.9.5. Gd-Cu-Ge

Five ternary compounds have been found in the Gd-Cu-Ge system.

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented were for a series of alloys GdCu_{1-0.67}Ge_{1-1.33} with a=0.4228-0.4136, c=0.3796-0.4041. Iandelli (1993) confirmed the structure type for a GdCuGe sample (AlB₂ type, a=0.4241, c=0.3755, X-ray powder analysis). The alloy was prepared from turnings or powders of metals (gadolinium 99.7 mass%, copper and germanium 99.99 mass%) which were mixed and sealed in a tantalum crucible under argon, melted by induction heating and annealed for 10 days at 1023 K.

 $Gd_6Cu_8Ge_8$ crystallizes with it own structure type; the lattice parameters are a = 1.4000, b = 0.6655, c = 0.4223 (Rieger 1970).

Konyk et al. (1988) investigated the crystal structure of Gd_2CuGe_6 alloy prepared by arc melting under argon and annealed at 870 K in an evacuated quartz tube for 720 h. From X-ray powder analysis a Ce₂CuGe₆-type was claimed, a=0.4003, b=0.4120, c=2.1096.

Rieger and Parthé (1969b) prepared GdCu₂Ge₂ with the CeGa₂Al₂-type structure, a = 0.4057, c = 1.0248.

Francois et al. (1990) reported the crystal structure of the GdCu_{0.32-0.47}Ge₂ (CeNiSi₂ type, a = 0.4118-4133, b = 1.644-1670, c = 0.3999-0.4005). For sample preparation, see GdFeGe₂ under Gd–Fe–Ge.

4.9.6. Gd-Nb-Ge

The phase diagram of the Gd-Nb-Ge system has not been established.

The existence of a compound $Gd_2Nb_3Ge_5$ with the $Ce_2Sc_3Si_4$ type (a=0.6998, b=1.3552, c=0.7184) was reported by Le Bihan et al. (1996a) from X-ray powder diffraction data of arc melted alloy. The starting materials were: Gd and Nb 99.99 mass%, Ge 99.999 mass%.

4.9.7. Gd–Ru–Ge

Early investigations of the GdRu₂Ge₂ compound determined the CeGa₂Al₂ type with a = 0.4057, c = 0.9895 (Francois et al. 1985) from X-ray powder analysis of alloy obtained by powder metallurgical reaction at 1273 K. The starting components were Gd (3N), Ru (4N) and Ge (4N).

Venturini et al. (1986b) reported that the Gd₂Ru₃Ge₅ compound crystallizes as the U₂Co₃Si₅-type. The lattice parameters were established as a=0.9840, b=1.241, c=0.5767 (X-ray powder diffraction data; for sample preparation, see La₂Ru₃Ge₅ under La-Ru–Ge).

 $Pr_3Rh_4Sn_{13}$ type was announced for the Gd₃Ru₄Ge₁₃ compound (a=0.8995) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Gd (3N), Ru (3N) and Ge (6N).

Francois et al. (1990) reported the crystal structure of GdRu_{0.23-0.36}Ge₂ (CeNiSi₂ type, a = 0.4146-4170, b = 1.606-1613, c = 0.4030-0.4064). For sample preparation, see GdFeGe₂ under Gd–Fe–Ge.

4.9.8. Gd–Rh–Ge

Venturini et al. (1985b) reported an X-ray powder diffraction study of the Gd₃Rh₄Ge₁₃ compound from a sample which was prepared by heating mixture of starting components (La 3N, Ru 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃ type, a=0.8968.

Early investigations of the GdRh₂Ge₂ compound determined it to have the CeGa₂Al₂-type structure: a = 0.4127, c = 1.0142 (Rossi et al. (1979)).

Gd₂Rh₃Ge₅ was found to crystallize with the Lu₂Co₃Si₅ type (a=0.9993, b=1.2062, c=0.5875, $\beta=91.7^{\circ}$; X-ray powder diffraction data) by Venturini et al. (1986b) from a sample prepared by a powder metallurgical reaction at 1173 K. The purity of the starting materials was greater than 99.9 mass%.

Hovestreydt et al. (1982) reported the crystal structure of the GdRhGe compound (TiNiSi type, a=0.6993, b=0.4329, c=0.7511; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. The starting components were Gd (3N), Rh (4N) and Ge (5N).

Gladyshevsky et al. (1991a) reported on the crystal structure for the Gd₃Rh₂Ge₂ compound: La₃Ni₂Ge₂ type, a=0.5589, b=0.7856, c=1.3289 (X-ray powder diffraction data). For the details of sample preparation, see La₃Rh₂Ge₂ under La–Rh–Ge.

Verniere et al. (1995) observed the existence of $Gd_4Rh_{13}Ge_9$ with $Ho_4Ir_{13}Ge_9$ -type structure. No lattice parameters were reported. For details of sample preparation, see La₄Ir₁₃Ge₄ under La–Ir–Ge.

Francois et al. (1990) found a homogeneity field for the compound $GdCo_{0.24-0.37}Ge_2$, CeNiSi₂ type, a = 0.4145-0.4169, b = 1.610-1.622, c = 0.4010-0.4054. For sample preparation, see GdFe_{0.25-0.46}Ge₂ under Gd–Fe–Ge.

Venturini et al. (1984) observed the existence of the $Gd_5Rh_4Ge_{10}$ compound with the $Sc_5Co_4Si_{10}$ type from a sample which was obtained by heating in an evacuated tube at 1073 K.

4.9.9. Gd–Pd–Ge

No systematic study of the Gd–Pd–Ge system has been performed, but the existence of five ternary compounds has been established by different groups of authors.

The existence of the GdPd₂Ge₂ compound (CeGa₂Al₂ type, a=0.4255, c=1.0035) was reported by Rossi et al. (1979). Details of sample preparation are the same as for LaPt₂Ge₂.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Gd_2PdGe_6 compound which was found to crystallize with the Ce_2CuGe_6 type, a=0.40953, b=0.40320, c=2.1624. For the experimental procedure, see La₂PdGe₆ under La-Pd-Ge. The starting materials used were obtained from Johnson & Matthey, UK (99.9 mass%).

The crystal structure of the compound GdPd₂Ge was observed to be of the YPd₂Si type, a=0.7431, b=0.7014, c=0.5607 (X-ray powder diffraction), by Jorda et al. (1983). For the experimental procedure, see LaPd₂Ge under La–Pd–Ge. The starting materials were palladium 99.99 mass%; germanium in specpure quality, and gadolinium 99.9 mass%.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound GdPdGe adopts the KHg₂-type structure, a=0.44406, b=0.7054, c=0.7577. For sample preparation, see LaPdGe under La–Pd–Ge. The starting materials were Gd (3N), Pd (4N) and Ge (5N).

Francois et al. (1990) observed the existence of a homogeneity field for the $GdPd_{0.30-0.43}Ge_2$ compound (CeNiSi₂ type, a=0.4131-0.4154, b=1.630-1.648, c=0.4033-0.4063). For sample preparation, see GdFe_{0.25-0.46}Ge₂ under Gd–Fe–Ge.

4.9.10. Gd-Ag-Ge

No ternary phase diagram has been established for the Gd–Ag–Ge system, however five ternary compounds have been characterized.

GdAgGe₃ was found to crystallize with a new structure type (a=3.478, b=0.8313, c=0.8113; X-ray single-crystal method) by Anisimova et al. (1992). The single crystal was isolated from a sample which was arc melted and annealed at 870 K for two weeks. The purity of the starting materials was greater than 99.9 mass%.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Gd₂AgGe₆ compound which was found to crystallize with the Ce₂CuGe₆ type, a=0.41946, b=0.40583, c=2.1166. For the experimental procedure, see La₂AgGe₆ under La–Ag–Ge. The starting materials used were obtained from Johnson & Matthey, UK (99.9 mass%).

Anisimova et al. (1992, 1995) reported the existence of the $Gd_6Ag_8Ge_8$ ($Gd_6Cu_8Ge_8$ type) and $GdAg_2Ge_2$ ($CeGa_2Al_2$ type) compounds. No lattice parameters were given.

The crystal structure of the GdAgGe compound was first investigated by Zanicchi et al. (1983) by X-ray powder diffraction. It was found to adopt the ZrNiAl type with lattice parameters a=0.7164, c=0.4241. Gibson et al. (1996) reported a single-crystal investigation of this compound. The crystal structure was confirmed and lattice parameters were obtained as a=0.7154, c=0.4237 using a single crystal which was extracted from an arc melted sample annealed at 970 K for 10 days.

4.9.11. Gd-Re-Ge

The only information on the system Gd–Re–Ge is due to Francois et al. (1990) who investigated the occurrence of the compound with a CeNiSi₂ type; no phase diagram is available. The GdRe_{0.25}Ge₂ compound was found to adopt the CeNiSi₂ type with lattice parameters a=0.4162, b=1.607, c=0.4056 (X-ray powder diffraction data). For sample preparation, see GdFe_{0.25–0.46}Ge₂ under Gd–Fe–Ge.

4.9.12. *Gd–Os–Ge*

No phase diagram exists for the ternary Gd–Os–Ge system; one ternary compound has been observed and studied. The $Pr_3Rh_4Sn_{13}$ -type structure was announced for the

 $Gd_3Os_4Ge_{13}$ compound (a=0.9025) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Gd (3N), Os (3N) and Ge (6N).

4.9.13. Gd–Ir–Ge

No ternary phase diagram has been established for the Gd–Ir–Ge system, however seven ternary compounds have been characterized.

Venturini et al. (1984) observed the $Gd_5Ir_4Ge_{10}$ compound with $Sc_5Co_4Si_{10}$ -type structure from a sample obtained by heating a mixture of the starting components in an evacuated silica tube at 1073 K.

Gd₂Ir₃Ge₅ was found to crystallize with the U₂Co₃Si₅ type (a=1.0127, b=1.178, c= 0.5980, X-ray powder diffraction method) by Venturini et al. (1986b) from a sample prepared by a powder metallurgical reaction at 1173 K. The purity of the starting materials was greater than 99.9 mass%.

Venturini et al. (1985b) reported an X-ray powder diffraction study of the $Gd_3Ir_4Ge_{13}$ compound from a sample which was synthesized by heating a mixture of the starting components (Gd 3N, Ir 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃-type structure, a=0.8981.

GdIr₂Ge₂ was found to crystallize in an orthorhombic structure with lattice parameters a=0.4113, b=0.4207, c=1.0167 (Francois et al. 1985).

Hovestreydt et al. (1982) reported the crystal structure of the GdIrGe compound (TiNiSi type, a = 0.6933, b = 0.4308, c = 0.7596; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. The starting components were Gd (3N), Ir (4N) and Ge (5N).

Verniere et al. (1995) have mentioned the existence of $Gd_4Ir_{13}Ge_9$ with $Ho_4Ir_{13}Ge_9$ type. No lattice parameters were given. For the experimental procedure, see $La_4Ir_{13}Ge_9$ under La–Ir–Ge.

Francois et al. (1987) reported the crystal structure of the GdIrGe₂ (YIrGe₂ type, a = 0.4287, b = 1.600, c = 0.8845). The sample was prepared by heating mixture of powders of starting components (Gd 3N, Ir 3N, Ge 3N) in an evacuated silica tube at 1173 K.

4.9.14. Gd–Pt–Ge

No phase diagram has been established for the Gd-Pt-Ge system. Four ternary compounds were observed by different authors.

According to an X-ray powder diffraction analysis Hovestreydt et al. (1982) reported the compound GdPtGe to adopt the TiNiSi-type structure, a=0.7071, b=0.4370, $c \ 0.7571$. For sample preparation, see LaPdGe under La-Pd-Ge.

The existence of the GdPt₂Ge₂ compound (CeGa₂Al₂ type, a=0.436, c=0.977) was reported by Rossi et al. (1979). For sample preparation see LaMn₂Ge₂ under La–Mn–Ge. Venturini et al. (1989a) investigated the crystal structure of GdPt₂Ge₂ from an arc melted sample annealed at 1273 K for 5 days. It was found to belong to the LaPt₂Ge₂ structure type, a=0.4324, b=0.4362, c=0.9717, $\beta=91.13^{\circ}$. The starting materials were Gd (3N), Pt (4N) and Ge (4N). Sologub et al. (1995a) reported an X-ray powder analysis of the Gd₂PtGe₆ compound which was found to crystallize with the Ce₂CuGe₆-type structure, a=0.40693, b=0.40239, c=2.1793. For sample preparation, see La₂PdGe₆ under La–Pd–Ge.

Francois et al. (1987) reported on the existence of the GdPtGe₂ with YIrGe₂-type. No lattice parameters were given. The sample was prepared by heating mixture of powders of starting components (Gd 3N, Pt 3N, Ge 3N) in evacuated silica tube at 1173 K.

4.9.15. Gd-Au-Ge

Information on interaction of gadolinium with gold and germanium is due to the work of two groups of authors (Sologub et al. 1995a, Rossi et al. 1992). The phase diagram of the Gd–Au–Ge system is not yet available; two ternary compounds have been observed and analyzed.

Sologub et al. (1995a) employed X-ray powder diffraction analysis for investigation the crystal structure of the Gd_2AuGe_6 compound from arc melted samples, which was homogenized by annealing at 873 K for 150 hours. The crystal structure was found to be isotypic with Ce₂CuGe₆ compound, a=0.41325, b=0.40234, c=2.1187.

A ternary compound of gadolinium with gold and germanium in the stoichiometric ratio 1:1:1 has been identified and studied by means of X-ray and metallographic analyses by Rossi et al. (1992). GdAuGe was found to adopt the LiGaGe type structure with lattice parameters a = 0.4432, c = 0.7418. The sample was prepared by melting the metals (about 99.9 mass% for gadolinium and 99.99 mass% for gold and germanium) in an induction furnace and annealing at 1070 K for 1 week.

4.10. Tb-d element-Ge systems

4.10.1. *Tb–Cr–Ge*

Brabers et al. (1994) reported the existence of a compound TbCr_6Ge_6 with the HfFe₆Ge₆ type (a=0.5167, c=0.8275; X-ray powder diffraction). The sample was prepared by arc melting and subsequent annealing at 1073 K for three weeks in vacuum.

4.10.2. Tb-Mn-Ge

A systematic study of the Tb–Mn–Ge system at 870 K was performed by Starodub et al. (1996) over the whole concentration region by means of X-ray powder analysis (fig. 87). The samples were prepared by arc melting under argon and annealed in evacuated quartz ampoules at 870 K for 240 hours. The starting materials were Tb 99.99 mass%, Mn 99.98 mass% and Ge 99.999 mass%.

The phase-field distribution in the isothermal section at 870 K is characterized by existence of four ternary compounds and by the formation of a homogeneity field for the $TbMn_{1-x}Ge_2$ (3) compound. Maximum solubility of manganese in the $TbGe_{1.5}$ compound is 5 at.%.

TbMn₆Ge₆ (1) was found to crystallize in the HfFe₆Ge₆-type structure by Venturini et al. (1992) (a=0.5232, c=0.8169; X-ray powder diffraction data). The alloy was



Fig. 87. Tb-Mn-Ge, isothermal section at 870 K.

synthesized by powder metallurgical reaction in evacuated silica tube at 1073 K for 14 days. Starodub et al. (1996) suggested the YCo₆Ge₆ type structure with lattice parameters a = 0.5210, c = 0.4066 (X-ray powder diffraction).

Rossi et al. (1978b) reported on investigation of the crystal structure of the TbMn₂Ge₂ (2) compound (CeGa₂Al₂ type, a = 0.3999, c = 1.0850; X-ray powder method). The alloy was obtained by melting under argon in an induction furnace and was annealed at 770 K for one week. The metals used were of purity greater than 99.9 mass% (Tb) and greater than 99.99 mass% (Mn, Ge). Starodub et al. (1996) confirmed the crystal structure and obtained slightly different lattice parameters: a = 0.3998, c = 1.0775.

TbMn_{0.33}Ge₂ (3) was found to adopt the CeNiSi₂ type with lattice parameters a = 0.4135, b = 1.594, c = 0.4020 by Francois et al. (1990) (X-ray powder diffraction data). For sample preparation, see GdFe_{0.25-0.46}Ge₂ under Gd–Fe–Ge. Starodub et al. (1996) confirmed the structure type and observed a homogeneity region for the compound with the CeNiSi₂ type: TbMn_{0.30-0.35}Ge₂, a = 0.4114-0.4202, b = 1.5890-1.6017, c = 0.3994-0.4160.

One more ternary compound was observed and investigated by Starodub et al. (1996): Tb₉Mn₁₀Ge₁₀ (4). It was found to adopt a Tm₉Fe₁₀Ge₁₀-type structure with lattice parameters a = 0.5398, b = 1.3317, c = 1.3930.

The crystal structures of TbMnGe (TiNiSi type, a=0.7077, b=0.4132, c=0.8166), Tb₃Mn₄Ge₄ (Gd₃Cu₄Ge₄ type, a=1.3901, b=0.7120, c=0.4163), and TbMn₅Ge₃ (YCo₅P₃ type, a=1.3050, b=0.3904, c=1.1408) were derived using a single-crystal method (Venturini and Malaman 1997). Single crystals of TbMnGe and Tb₃Mn₄Ge₄ were extracted from ingots of the corresponding stoichiometry melted in an induction furnace.
The TbMn₅Ge₃ compound was synthesized from a stoichiometry mixture of commercially available high-purity elements compacted into pellets, sealed in a silica tube under argon and annealed at 1223 K for 5 days.

4.10.3. *Tb*–*Fe*–*Ge*

The phase diagram for the Tb–Fe–Ge system (fig. 88) was investigated by Starodub (1988) by means of metallographic and X-ray phase analyses. Alloys were prepared by arc melting followed by annealing at 870 K for 240 hours. The purity of the starting components was greater than 99.9 mass%. Six ternary compounds were observed.

TbFe₆Ge₆ (1) was reported to be isotypic with YCo₆Ge₆ with lattice parameters a = 0.5106, c = 0.4055 (Mruz et al. 1984). The sample was prepared by arc melting the proper amounts of starting components followed by annealing at 870 K for two weeks. At variance with these data, Venturini et al. (1992) using X-ray powder diffraction data found TbFe₆Ge₆ to crystallize with the TbFe₆Sn₆ type, a = 0.8126, b = 1.776, c = 0.5125. The alloy was obtained by powder metallurgical reaction in an evacuated silica tube at 1173 K for two weeks.

Pecharsky et al. (1989) reported TbFe_{0.33}Ge₂ (5) to crystallize with the CeNiSi₂type structure (a=0.4123, b=1.5830, c=0.4006; X-ray powder analysis). The alloy was arc melted and annealed at 870 K. The purity of the starting materials was greater than 99.9 mass%. Francois et al. (1990) confirmed the occurrence of the CeNiSi₂ type for terbium–iron–germanium combinations from the alloys annealed at 1173 K (TbFe_{0.42}Ge₂; a=0.4135, b=1.591, c=0.4026).

Pecharsky et al. (1987) investigated the crystal structure of $Tb_{117}Fe_{52}Ge_{112}$ (6) by the X-ray single-crystal method (own structure type, a = 2.8580). The alloy was synthesized



Fig. 88. Tb-Fe-Ge, isothermal section at 870 K.

by arc melting followed by annealing at 1070 K for 350 h. The starting materials were Tb 99.83 mass%, Fe 99.9 mass%, Ge 99.99 mass%.

According to X-ray powder diffraction data, TbFe₂Ge₂ (3) was found to be isostructural with the CeGa₂Al₂ type, with lattice parameters a=0.3966, c=1.0470 (Bara et al. 1990). The sample was synthesized by direct melting the high-purity constituent elements (Tb 4N, Fe 3N, Ge 5N) in an arc furnace. After melting, the sample was annealed at 1073 K for 1 week.

Two more ternary compounds with an unknown structure type were observed by Starodub (1988) at 870 K: TbFe₄Ge₂ (2) and Tb₂Fe₄Ge₃ (4).

4.10.4. *Tb–Co–Ge*

The isothermal section of the Tb–Co–Ge system at 870 K over the whole concentration region was derived by Starodub (1988) (fig. 89) employing X-ray and microstructural analyses of alloys which were prepared by arc melting the proper amounts of the high-purity constituent elements. The melted buttons were then annealed in evacuated silica tubes at 870 K for 300 hours. Ten ternary compounds were found to exist.

Méot-Meyer et al. (1985a) reported the crystal structure of TbCo_xGe_2 , x=0.57 (7) (CeNiSi₂ type, a=0.4117, b=1.618, c=0.4043). The sample was prepared by powder metallurgical reaction and annealed in an evacuated silica tube at 1173 K. Pecharsky et al. (1989) confirmed the formation and crystal structure of the TbCo_xGe₂ compound from arc melted alloy annealed at 870 K (a=0.4110-0.4122, b=1.5991-1.6209, c=0.3999-0.4050; X-ray powder analysis).

The crystal structure of $Tb_3Co_4Ge_{13}$ (2) (Yb₃Rh₄Sn₁₃ type, a = 0.8764; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample prepared by heating



Fig. 89. Tb-Co-Ge, isothermal section at 870 K.

a compacted mixture of the starting materials (Tb in pieces, 99.9 mass%; Co and Ge in powder, 99.99 mass%) in an evacuated quartz tube at 1073 K. Bodak et al. (1987) reported the $Y_3Co_4Ge_{13}$ type for Tb₃Co₄Ge₁₃, a=0.8779 (X-ray powder data) from arc melted alloy annealed at 870 K.

TbCo₂Ge₂ (3) was found to adopt the CeGa₂Al₂-type structure, a = 0.3984, c = 1.0059 (Starodub 1988; X-ray powder diffraction).

From X-ray powder analysis of an alloy annealed at 1173 K, Tb₂Co₃Ge₅ (4) was reported to adopt the Lu₂Co₃Si₅-type structure, a=0.9649, b=1.183, c=0.5715, $\beta=91.8^{\circ}$ (Venturini et al. 1986b). Starodub (1988) announced the U₂Co₃Si₅-type structure with unknown lattice parameters for the Tb₂Co₃Ge₅ compound.

The crystal structure of the TbCo₆Ge₆ (1) compound was reported by Buchholz and Schuster (1981) (YCo₆Ge₆ structure type, a=0.5106, c 0.4055). The sample was melted under argon in a corundum crucible at 1073–1273 K.

Gorelenko et al. (1984) reported the crystal structure of TbCoGe (8) (TiNiSi type, a = 0.6955, b = 0.4242, c = 0.7271; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Tb₃Co₂Ge₄ (9) crystallizes with a new type of structure, a=1.0692, b=0.8067, c=0.4164, $\gamma=107.72^{\circ}$ (X-ray single-crystal data; Starodub et al. 1986). The sample was prepared by arc melting and annealing at 873 K for 240 h.

Tb₂CoGe₆ is isotypic with Ce₂CuGe₆ (6), a=0.3941, b=0.4003, c=2.1439 (Oleksyn et al. 1991; X-ray powder diffraction data). The sample was melted in an arc furnace and annealed at 1070 K in an evacuated quartz capsule for 400 h. The purity of the starting materials was greater than 99.9 mass%.

Bodak et al. (1986) reported an X-ray single-crystal investigation of the compound Tb₂CoGe₂ (10): Sc₂CoSi₂ type, a=1.0569, b=1.0209, c=0.4212, $\gamma=118.18^{\circ}$.

In the course of isothermal section studies, Starodub (1988) observed a compound $TbCoGe_3$ (5) with unknown structure.

4.10.5. Tb--Ni--Ge

Figure 90 represents the isothermal section of the Tb–Ni–Ge phase diagram at 870 K, which was studied by Starodub (1988). The isothermal section was constructed by means of X-ray powder analysis of 234 alloys which were arc melted and subsequently annealed in evacuated silica tubes for 400 h at 870 K and finally quenched in water. The starting materials were Tb 99.99 mass%, Ni 99.98 mass% and Ge 99.99 mass%.

The ternary phase equilibrium diagram is characterized by the existence of ten ternary compounds and by the formation of a substitutional exchange of Ge/Ni in the solid solutions $Tb_2(Ni_{1-x}Ge_x)_{17}$ and $Tb(Ni_{1-x}Ge_x)_5$ for 0 < x < 0.12. This behavior corresponds to the solid solution range of Ge in nickel. Nonstoichiometry was observed for $TbNi_{1-x}Ge_2$. The binary Tb_2Ge_3 compound dissolves 12 at.% Ni.

TbNi₅Ge₃ (1) was reported to crystallize with the YNi₅Si₃ type, a = 1.9068, b = 0.3871, c = 0.6790 by Koterlyn et al. (1988). The arc melted alloy, annealed at 870 K, was investigated by X-ray powder diffraction analysis. The starting materials were Tb 99.83 mass%, Ni 99.99 mass% and Ge 99.99 mass%.



Fig. 90. Tb-Ni-Ge, isothermal section at 870 K

Tb₃Ni₁₁Ge₄ (2) belongs to the Sc₃Ni₁₁Si₄ type, a = 0.8321, c = 0.8832, after Koterlyn et al. (1988). The alloy was prepared in the same manner as TbNi₅Ge₃.

The TbNi₂Ge₂ (3) compound was found to adopt the CeGa₂Al₂-type structure, a = 0.4044, c = 0.9782 (Rieger and Parthé 1969b).

TbNiGe₃ (4) with the ScNiSi₃-type structure (a=2.1496, b=0.4058, c=0.4054; X-ray powder diffraction analysis) was reported by Bodak et al. (1985). For the details of sample preparation and purity of starting materials, see TbNi₅Ge₃.

Tb₂NiGe₆ (5) has been found by Oleksyn (1990) from X-ray powder diffraction to be isostructural with Ce₂CuGe₆ (a=0.3955, b=2.1224, c=0.4001). The sample was prepared by arc melting ingots of the constituting elements and annealing at 1070 K for 700 h. For the purity of starting materials, see TbNi₅Ge₃.

Pecharsky et al. (1989) investigated the formation and crystal structure of the TbNi_{1-x}Ge₂ (7) compound by X-ray powder analysis of an arc melted alloy annealed at 870 K (CeNiSi₂ type, a=0.4105, b=1.621, c=0.3993). For sample preparation, see TbNi₅Ge₃. Francois et al. (1990) confirmed the structure and reported the composition and lattice parameters as TbNi_{0.94}Ge₂, a=0.4096, b=1.637, c=0.4086 (X-ray powder diffraction) from a sample obtained by a powder metallurgical reaction at 1173 K.

Gorelenko et al. (1984) reported the crystal structure of TbNiGe (8) (TiNiSi type, a = 0.6949, b = 0.4196, c = 0.7303; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Bodak et al. (1982) reported on the crystal structure of Tb₃NiGe₂ (10) from X-ray powder diffraction (La₃NiGe₂ type, a=1.1381, b=0.4222, c=1.1257). The proper amounts of starting components were arc melted and annealed at 870 K.

The crystal structures of two ternary compounds, $TbNiGe_2$ (6) and $Tb_{4.75}NiGe_{4.25}$ (9), have not been evaluated (Starodub 1988).

4.10.6. *Tb–Cu–Ge*

The isothermal section of the Tb–Cu–Ge system at 870 K was constructed by Starodub (1988) (fig. 91) as a result of an X-ray powder analysis of 125 alloys. Samples were obtained by arc melting the proper amounts of constituent elements (purity greater than 99.8 mass%) followed by annealing in evacuated quartz tubes at 870 K for 350 h. Finally samples were quenched in ice water. Phase relations are characterized by formation of four ternary compounds. The binary compound TbCu₂ dissolves about 15 at.% Ge. The existence of an extensive terminal solid solution of TbGe_{1.5} which dissolves ~20 at.% Cu, and then shifts in stoichiometry from 1:1.5 to 1:2 as an additional ~10 at.% Cu is added, was observed during the investigation of the phase relations by Starodub (1988).

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂ type structure by means of X-ray powder diffraction of arc melted alloys. The data presented are TbCu_{1-0.67}Ge_{1-1.33} (4) with a=0.4122-0.4218, c=0.3976-0.3744. At variance with these data, Iandelli (1993) reported that TbCuGe had the CaIn₂-type structure (a=0.4247, c=0.7336, X-ray powder analysis). The alloy was prepared from turnings or powders of the metals (terbium 99.7 mass%, copper and germanium 99.99 mass%), which were mixed and sealed in a tantalum crucible under argon, melted by induction heating and annealed for 10 days at 1023 K. Starodub (1988) observed the AlB₂ type for the compound TbCu_{1.0-1.2}Ge_{1.0-0.8} (4), a=0.4234-0.4225, c=0.3688-0.3658.

Tb₆Cu₈Ge₈ (2) crystallizes with the Gd₆Cu₈Ge₈ type, and the lattice parameters are a = 1.392, b = 0.664, c = 0.420 (Hanel and Nowotny 1970). Starodub (1988) confirmed the



Fig. 91. Tb-Cu-Ge, isothermal section at 870 K.

crystal structure of the Tb₆Cu₈Ge₈ compound (a=1.3900, b=0.6618, c=0.4191; X-ray powder diffraction) from an arc melted sample annealed at 870 K.

Konyk et al. (1988) investigated the crystal structure of Tb₂CuGe₆ (3) alloy prepared by arc melting under argon and annealed at 870 K in an evacuated quartz tube for 720 h. From X-ray powder analysis the authors concluded that this phase has Ce₂CuGe₆-type structure, a = 0.4000, b = 0.4113, c = 2.1010.

Rieger and Parthé (1969b) prepared TbCu₂Ge₂ (1) with the CeGa₂Al₂-type of structure, a=0.4044, c=1.0248. The existence and crystal structure of this compound was confirmed by Starodub (1988) from an arc melted sample annealed at 870 K.

Francois et al. (1990) observed the CeNiSi₂ type for the TbCu_{0.39}Ge₂ compound and reported lattice parameters a = 0.4100, b = 1.648, c = 0.3995 (X-ray powder diffraction) from the sample obtained by the powder metallurgical reaction at 1173 K. Apparently this phase does not exist at 870 K.

4.10.7. Tb-Nb-Ge

The phase diagram of the Tb–Nb–Ge system has not been established. However, the existence of the compound Tb₂Nb₃Ge₄ with the Ce₂Sc₃Si₄-type structure (a = 0.6981, b = 1.3515, c = 0.7156) was reported by Le Bihan et al. (1996a) from X-ray powder diffraction data of an arc melted alloy. Starting materials were Tb and Nb 99.99%, Ge 99.999%.

4.10.8. Tb-Mo-Ge

No phase diagram exists for the Tb-Mo-Ge system; only one compound was observed and investigated. Tb₂Mo₃Ge₄ was reported to crystallize with the Ce₂Sc₃Si₄-type structure (a = 0.6921, b = 1.3149, c = 0.7062) by Le Bihan et al. (1996b) from X-ray powder diffraction of an arc melted alloy. The starting materials were Tb and Mo 99.99 mass%, Ge 99.999 mass%.

4.10.9. *Tb–Ru–Ge*

Early investigations on the TbRu₂Ge₂ compound determined that it had the CeGa₂Al₂type structure with a = 0.4221, c = 0.9879 (Francois et al. 1985) from X-ray powder analysis of an alloy obtained by powder metallurgical reaction at 1273 K. The starting components were Tb (3N), Ru (4N) and Ge (4N).

Venturini et al. (1986b) reported that the Tb₂Ru₃Ge₅ compound crystallizes with the U₂Co₃Si₅-type structure. The lattice parameters were reported as a=0.9793, b=1.241, c=0.5742 (X-ray powder diffraction data). For sample preparation, see La₂Ru₃Ge₅ under La–Ru–Ge.

The $Pr_3Rh_4Sn_{13}$ type was announced for the $Tb_3Ru_4Ge_{13}$ compound (a=0.8965) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Tb (3N), Ru (3N), Ge (6N).

4.10.10. *Tb--Rh--Ge*

Venturini et al. (1985b) reported an X-ray powder diffraction study of the Tb₃Rh₄Ge₁₃ compound from a sample which was prepared by heating a mixture of the starting components (Tb 3N, Rh 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃ type, a=0.8950.

Francois et al. (1985) determined the CeGa₂Al₂ type for the TbRh₂Ge₂ compound, a=0.4118, c=1.0280.

Tb₂Rh₃Ge₅ was found to crystallize with Lu₂Co₃Si₅-type structure (a=0.9951, b=1.2046, c=0.5849, $\beta=91.9^{\circ}$; X-ray powder diffraction data) by Venturini et al. (1986b) from a sample prepared by powder metallurgical reaction at 1173 K. The purity of the starting materials was greater than 99.9 mass%.

Hovestreydt et al. (1982) reported the crystal structure of the TbRhGe compound (TiNiSi type, a=0.6933, b=0.4302, c=0.7506; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. The starting components were Tb (3N), Rh (4N) and Ge (5N).

Gladyshevsky et al. (1991a) reported on the crystal structure for the Tb₃Rh₂Ge₂ compound (La₃Ni₂Ge₂ type, a = 0.55627, b = 0.7808, c = 1.3233; X-ray powder diffraction data). For the details of sample preparation, see La₃Rh₂Ge₂ under La–Rh–Ge.

Verniere et al. (1995) established that the compound $Tb_4Rh_{13}Ge_9$ formed the Ho₄Ir₁₃Ge₉-type structure. No lattice parameters were given. For experimental details, see La₄Ir₁₃Ge₉ under La–Ir–Ge.

Venturini et al. (1984) observed the existence of the Tb₅Rh₄Ge₁₀ compound with $Sc_5Co_4Si_{10}$ -type structure (a=1.2970, c=0.4285; X-ray powder diffraction) from a sample obtained by heating a mixture of powders in an evacuated tube at 1073 K.

4.10.11. Tb-Pd-Ge

No systematic study of the Tb–Pd–Ge system has been performed, but the existence of three ternary compounds has been established by different groups of authors.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Tb₂PdGe₆ compound which was found to crystallize with the Ce₂CuGe₆-type structure, a=0.40830, b=0.40227, c=2.1530. For the experimental procedure, see La₂PdGe₆ under La–Pd–Ge. The starting materials used were obtained from Johnson & Matthey, UK (99.9 mass%).

The crystal structure of the compound TbPd₂Ge was found to be of the YPd₂Si type (a=0.7390, b=0.7028, c=0.5598; X-ray powder diffraction) by Jorda et al. (1983). For the experimental procedure, see LaPd₂Ge under La-Pd-Ge. The starting materials were palladium 99.99 mass%, germanium in specpure quality, and terbium 99.9 mass%.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound TbPdGe adopts the KHg₂-type of structure, a=0.4381, b=0.7000, c=0.7573. For sample preparation, see LaPdGe under La–Pd–Ge. The starting materials were Tb (3N), Pd (4N) and Ge (5N).

4.10.12. Tb-Ag-Ge

No ternary phase diagram has been established for the Tb-Ag-Ge system, however two ternary compounds have been characterized.

The crystal structure of the TbAg_{0.33}Ge_{1.67} compound has been investigated by Protsyk (1994) by means of X-ray analysis from alloy which was arc melted and annealed in an evacuated silica tube for 500 h at 770 K and finally quenched in water. The starting materials were Tb 99.85 mass%, Ag 99.9 mass% and Ge 99.99 mass%. It was found to adopt the α -ThSi₂-type structure with lattice parameters a = 0.4066, c = 1.3783.

Gibson et al. (1996) reported an X-ray single-crystal investigation of the TbAgGe compound. It was found to adopt the ZrNiAl type, a=0.71277, c=0.42103. The single crystal was extracted from an arc melted sample annealed at 970 K for 10 days.

4.10.13. Tb-Os-Ge

No phase diagram exists for the ternary Tb–Os–Ge system, but two ternary compounds have been observed.

 $Pr_3Rh_4Sn_{13}$ -type was announced for the $Tb_3Os_4Ge_{13}$ compound (a=0.9002) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Tb (3N), Os (3N) and Ge (6N).

Venturini et al. (1986b) observed the existence of the $Tb_2Os_3Ge_5$ compound with $Sc_5Co_4Si_{10}$ type structure from a sample obtained by heating a mixture of the starting components in an evacuated quartz tube at 1173 K.

4.10.14. Tb–Ir–Ge

No ternary phase diagram has been established for the Tb-Ir-Ge system, however eight ternary compounds have been characterized.

Venturini et al. (1984) observed the existence of the Tb₅Ir₄Ge₁₀ compound with Sc₅Co₄Si₁₀ type, a=1.2935, c=0.4318, from a sample obtained by heating a mixture of the starting components in an evacuated quartz tube at 1073 K.

Tb₂Ir₃Ge₅ was found to crystallize with U₂Co₃Si₅-type structure (a=1.0122, b=1.276, c=0.5790, X-ray powder diffraction method) by Venturini et al. (1986b) from a sample prepared by powder metallurgical reaction at 1173 K. The purity of the starting materials was greater than 99.9 mass%.

Venturini et al. (1985b) reported on the X-ray powder diffraction study of the Tb₃Ir₄Ge₁₃ compound from an alloy which was synthesized by heating a mixture of the starting components (Tb 3N, Ir 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃ type, a = 0.8962.

TbIr₂Ge₂ was found to adopt a tetragonal structure with lattice parameters a = 0.4144, c = 1.0222 (Francois et al. 1985).

Hovestreydt et al. (1982) reported the crystal structure for the TbIrGe compound (TiNiSi type, a=0.6871, b=0.4280, c=0.7591; X-ray powder data) from an arc melted

sample annealed at 1270 K for 1-2 weeks. The starting components were Tb (3N), Ir (4N) and Ge (5N).

Verniere et al. (1995) announced the $Ho_4Ir_{13}Ge_9$ -type structure for $Tb_4Ir_{13}Ge_9$. No lattice parameters were given. For the experimental procedure, see La₄Ir₁₃Ge₉ under La–Ir–Ge.

Francois et al. (1987) reported the crystal structure of TbIrGe₂ (NdIrGe₂ type, a = 0.4266, b = 1.595, c = 0.8829). The sample was prepared by heating a mixture of powders of the starting components (Tb 3N, Ir 3N and Ge 3N) in an evacuated silica tube at 1173 K.

Tb₄Ir₇Ge₆ was reported to adopt the U₄Re₇Si₆-type structure (a = 0.8345; Francois et al. 1985) from a sample obtained by heating a mixture of powders of the starting materials (Tb 3N, Os and Ge 4N) in an evacuated quartz tube at 1273 K.

4.10.15. *Tb*–*Pt*–*Ge*

No phase diagram has been established for the Tb-Pt-Ge system. Four ternary compounds were observed by different authors.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound TbPtGe adopts the TiNiSi-type of structure, a = 0.7020, b = 0.4354, c = 0.7564. For sample preparation, see LaPdGe under La-Pd-Ge.

The existence of the TbPt₂Ge₂ compound (CeGa₂Al₂ type, a=0.436, c=0.977) was reported by Rossi et al. (1979). For sample preparation see LaMn₂Ge₂ under La–Mn–Ge. Venturini et al. (1989a) investigated the crystal structure of TbPt₂Ge₂ from an arc melted sample annealed at 1273 K for 5 days. The crystal structure was found to belong to the LaPt₂Ge₂ type, a=0.4311, b=0.4351, c=0.9711, $\beta=91.09^{\circ}$. The starting materials were Tb (3N), Pt (4N) and Ge (4N).

Sologub et al. (1995a) reported on the X-ray powder analysis of the Tb₂PtGe₆ compound which was found to crystallize with the Ce₂CuGe₆ type, a=0.40634, b=0.40155, c=2.1648. For sample preparation, see La₂PdGe₆ under La–Pd–Ge.

Francois et al. (1987) mentioned the existence of TbPtGe₂ with $YIrGe_2$ -type structure. No lattice parameters were given. The sample was prepared by heating a mixture of powders of the starting components (Gd 3N, Ir 3N, Ge 3N) in an evacuated silica tube at 1173 K.

4.10.16. Tb--Au--Ge

Information on interaction of terbium with gold and germanium is due to the work of two groups of authors (Sologub et al. 1995a and Rossi et al. 1992). The phase diagram of the Tb–Au–Ge system is not yet available; two ternary compounds have been observed and their structures were determined.

Sologub et al. (1995a) employed X-ray powder diffraction analysis for studying the crystal structure of Tb₂AuGe₆. It was found to be isotypic with Ce₂CuGe₆, a=0.41325, b=0.40234, c=2.1187. For the details of sample preparation, see Gd₂AuGe₆ under Gd-Au-Ge.

A ternary compound of terbium with gold and germanium in the stoichiometric ratio 1:1:1 has been identified and studied by means of X-ray and metallographic analyses by Rossi et al. (1992). TbAuGe was found to adopt the LiGaGe type with lattice parameters a=0.4416, c=0.7335. For the experimental procedure see GdAuGe under Gd–Au–Ge.

4.11. Dy-d element-Ge systems

4.11.1. Dy-Cr-Ge

The only reference on the Dy–Cr–Ge system is due to Brabers et al. (1994) who reported the existence of a compound $DyCr_6Ge_6$ with the HfFe₆Ge₆ type (a=0.5162, c=0.8272; X-ray powder diffraction). The sample was prepared by arc melting and subsequent annealing at 1073 K for three weeks in vacuum.

4.11.2. Dy-Mn-Ge

No ternary phase diagram of the Dy–Mn–Ge system is available. Two ternary compounds have been reported for various dysprosium manganese germanium combinations.

DyMn₆Ge₆ was found to crystallize in the HfFe₆Ge₆-type structure by Venturini et al. (1992), a=0.5228, c=0.8163 (X-ray powder diffraction data). The alloy was synthesized by a powder metallurgical reaction in an evacuated silica tube at 1073 K for 14 days.

Rossi et al. (1978b) reported on the crystal structure of the DyMn₂Ge₂ compound (CeGa₂Al₂ type, a = 0.3980, c = 1.0737; X-ray powder method). The alloy was obtained by melting under argon in an induction furnace and annealing at 770 K for a week. The metals used were of purity greater than 99.9 mass% for Dy, and greater than 99.99 mass% for Mn and Ge.

The DyMn_{0.33}Ge₂ compound was found to adopt the CeNiSi₂-type structure with lattice parameters a = 0.4118, b = 1.583, c = 0.4000 by Francois et al. (1990) (X-ray powder diffraction data). For sample preparation, see GdFe_{0.25-0.46}Ge₂ under Gd–Fe–Ge.

4.11.3. Dy-Fe-Ge

No phase diagram has been constructed for the Dy-Fe-Ge system, but six ternary compounds have been found and characterized by different authors.

DyFe₆Ge₆ was reported to be isotypic with YCo₆Ge₆ with lattice parameters a = 0.5108, c = 0.4044 (Mruz et al. 1984). The sample was prepared by arc melting of the proper amounts of the starting components followed by annealing at 870 K for two weeks. At variance with these data, DyFe₆Ge₆ was found to crystallize with the TbFe₆Sn₆ type, a = 0.8111, b = 1.766, c = 0.5116 by Venturini et al. (1992) from X-ray powder diffraction data. The alloy was obtained by a powder metallurgical reaction in an evacuated silica tube at 1173 K for two weeks.

Pecharsky et al. (1989) reported DyFe_{0.33}Ge₂ to crystallize with the CeNiSi₂-type structure (a=0.4118, b=1.5903, c=0.4002; X-ray powder analysis). The alloy was arc melted and annealed at 870 K. The purity of the starting materials was greater than

99.9 mass%. Francois et al. (1990) confirmed the crystal structure of this compound, a = 0.4121, b = 1.581, c = 0.4011 (X-ray powder diffraction data). For sample preparation, see GdFe_{0.25-0.46}Ge₂ under Gd–Fe–Ge.

DyFe₄Ge₂ is isotypic with the crystal structure of ZrFe₄Si₂; a=0.7303, c=0.3865 according to Fedyna (1988). The alloy was prepared by arc melting the proper amounts of the starting components followed by annealing at 870 K for 400 hours.

Oleksyn (1990) investigated the crystal structure of $Dy_{117}Fe_{52}Ge_{112}$ compound by the X-ray powder method ($Tb_{117}Fe_{52}Ge_{112}$ type, a=2.8382). The alloy was synthesized by arc melting followed by annealing at 1070 K for 350 h. The starting materials were Dy 99.83 mass%, Fe 99.9 mass%, Ge 99.99 mass%.

According to X-ray powder diffraction, $DyFe_2Ge_2$ was found to be isostructural with the CeGa₂Al₂ type, a=0.3957, c=1.0446 (Rossi et al. 1978a).

 $Dy_6Fe_8Ge_8$ has the $Gd_6Cu_8Ge_8$ type structure, a = 1.3528, b = 0.6793, c = 0.4135 (X-ray powder diffraction; Fedyna et al. 1994).

4.11.4. Dy-Co-Ge

The phase diagram for the Dy–Co–Ge system has not been established. Nine ternary compounds have been identified for various dysprosium–cobalt–germanium combinations.

Méot-Meyer et al. (1985a) reported the crystal structure of the $DyCo_{1-x}Ge_2$, x = 0.44 (CeNiSi₂ type, a = 0.4098, b = 1.607, c = 0.4020). Samples were prepared by powder metallurgical reaction and annealed in an evacuated silica tube at 1173 K. Pecharsky et al. (1989) investigated the formation and crystal structure of the $DyCo_{1-x}Ge_2$ compound by X-ray powder analysis of arc melted alloys annealed at 870 K. The CeNiSi₂-type structure was confirmed with lattice parameters a = 0.4130-0.4135, b = 1.6045-1.6057, c = 0.4026-0.4028.

The crystal structure of $Dy_3Co_4Ge_{13}$ (Yb₃Rh₄Sn₁₃ type, a=0.8744; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample which was prepared by heating a compacted mixture of the starting materials (Dy in pieces, 99.9 mass%; Co and Ge in powder, 99.99 mass%) in an evacuated quartz tube at 1073 K. Bodak et al. (1987) reported the Y₃Co₄Ge₁₃ type for the Dy₃Co₄Ge₁₃ compound (a=0.8750; X-ray powder data) from arc melted alloy annealed at 870 K.

From X-ray powder analysis of an alloy annealed at 1173 K, Dy₂Co₃Ge₅ was reported to adopt Lu₂Co₃Si₅-type structure, a=0.9627, b=1.180, c=0.5707, $\beta=91.0^{\circ}$ (Venturini et al. 1986b).

The crystal structure of the DyCo₆Ge₆ compound was reported by Buchholz and Schuster (1981) (YCo₆Ge₆ structure type, a=0.5081, c=0.3918). The sample was melted under argon in a corundum crucible at 1073–1273 K.

Gorelenko et al. (1984) reported the crystal structure of DyCoGe (TiNiSi type, a = 0.6886, b = 0.4204, c = 0.7256; X-ray powder analysis). The alloy was arc melted and annealed in an evacuated quartz tube at 870 K for 350 hours.

Dy₃Co₂Ge₄ crystallizes with the Tb₃Co₂Ge₄ type structure, a = 1.0590, b = 0.8114, c = 0.4135, $\gamma = 107.83^{\circ}$. The sample was prepared by arc melting and annealing at

873 K for 1450 h. The starting materials were: Dy >99.9 mass%, Co 99.99 mass%, Ge 99.999 mass% (Mruz et al. 1989).

 Dy_2CoGe_6 is isotypic with Ce_2CuGe_6 , a=0.3931, b=0.3983, c=2.1341 (Oleksyn et al. 1991, X-ray powder diffraction data). The sample was melted in an arc furnace and annealed at 1070 K in an evacuated quartz capsule for 400 hours. The purity of the starting materials was greater than 99.9 mass%.

Bodak et al. (1986) reported the crystal structure for Dy₂CoGe₂ (Sc₂CoSi₂ type, a = 1.0467, b = 1.0132, c = 0.4178, $\gamma = 117.33^{\circ}$; X-ray powder diffraction) from an arc melted sample annealed at 870 K.

4.11.5. Dy-Ni-Ge

Figure 92 represents the isothermal section of the Dy–Ni–Ge phase diagram at 870 K, which was studied by Koterlyn et al. (1988). The isothermal section was constructed by means of X-ray powder analysis of alloys, which were arc melted, subsequently annealed in evacuated silica tubes for 400 h at 870 K, and finally quenched in ice water. The starting materials were Dy 99.99 mass%, Ni 99.98 mass% and Ge 99.99 mass%.

The ternary phase diagram is characterized by the existence of ten ternary compounds and by the formation of a substitutional exchange of Ge/Ni in the Ni terminal solid solutions $Dy_2(Ni_{1-x}Ge_x)_{17}$ and $Dy(Ni_{1-x}Ge_x)_5$. Nonstoichiometry and a homogeneity range were observed for $DyNi_{1-x}Ge_2$ (7). The binary Dy_2Ge_3 compound dissolves 20 at.% Ni.

DyNi₅Ge₃ (1) was reported to crystallize with the YNi₅Si₃ type, a = 1.9065, b = 0.3864, c = 0.6787, by Fedyna (1988). The arc melted alloy, annealed at 870 K, was investigated



Fig. 92. Dy-Ni-Ge, isothermal section at 870 K.

by X-ray powder diffraction analysis. The starting materials were Dy 99.83 mass%, Ni 99.99 mass%, and Ge 99.99 mass%.

Dy₃Ni₁₁Ge₄ (2) belongs to the Sc₃Ni₁₁Si₄ type, a=0.8317, c=0.8807, after Fedyna (1988). For sample preparation, see DyNi₅Ge₃ under Dy-Ni-Ge.

The DyNi₂Ge₂ (3) compound was found to adopt the CeGa₂Al₂-type structure, a = 0.4035, c = 0.9758 (Rieger and Parthé 1969b).

DyNiGe₃ (4) with the ScNiSi₃-type structure (a=2.1430, b=0.4054, c=0.4042, X-ray powder diffraction analysis) was reported by Bodak et al. (1985). For the details of sample preparation and purity of starting materials, see DyNi₅Ge₃, above.

 Dy_2NiGe_6 (5) has been found by Oleksyn (1990) from X-ray powder diffraction to be isostructural with Ce_2CuGe_6 (a=0.3955, b 2.1170, c=0.4007). Samples were prepared by arc melting ingots of the constituting elements and annealing at 1070 K for 700 h. For the purity of starting materials, see $DyNi_5Ge_3$, above.

Pecharsky et al. (1989) investigated the formation and crystal structure of the DyNi_{1-x}Ge₂ (7) compound by X-ray powder analysis of an arc melted alloy annealed at 870 K (CeNiSi₂ type, a=0.4102, b=1.6216, c=0.4013). For sample preparation, see DyFe_{1-x}Ge₂ under Dy–Fe–Ge. Francois et al. (1990) confirmed the structure and reported the composition and lattice parameters DyNi_{0.80}Ge₂, a=0.4093, b=1.651, c=0.4052 (X-ray powder diffraction) from a sample obtained by a powder metallurgical reaction at 1173 K.

Gorelenko et al. (1984) reported the crystal structure for DyNiGe (8) (TiNiSi type, a=0.6963, b=0.4213, c=0.7285; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Bodak et al. (1982) reported on the crystal structure for the Dy₃NiGe₂ (10) compound from X-ray powder diffraction (La₃NiGe₂-type structure, a=1.1272, b=0.4207, c=1.1218). The proper amounts of starting components were arc melted and annealed at 870 K.

The crystal structure of two ternary compounds $DyNiGe_2$ (6) and $Dy_{4.75}NiGe_{4.25}$ (9) has not been evaluated yet (Koterlyn et al. 1988).

4.11.6. Dy-Cu-Ge

No isothermal section is available for the Dy–Cu–Ge system; four ternary compounds have been found and analyzed by various groups of authors.

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented were $DyCu_{1-0.67}Ge_{1-1.33}$ with a=0.4221-0.4038, c=0.3664-0.3637. At variance with these data, Iandelli (1993) observed DyCuGe with the CaIn₂-type (a=0.4239, c=0.7239, X-ray powder analysis). The alloy was obtained from turnings or powders of metals (Dy 99.7 mass%, Cu and Ge 99.99 mass%), which were mixed and sealed in a tantalum crucible under argon, melted by induction heating and annealed for 10 days at 1023 K.

 $Dy_6Cu_8Ge_8$ crystallizes with the $Gd_6Cu_8Ge_8$ type, lattice parameters a=1.3845, b=0.6618, c=0.4173 (Rieger 1970).

Konyk et al. (1988) investigated the crystal structure of Dy_2CuGe_6 alloy synthesized by arc melting under argon and annealing at 870 K in an evacuated quartz tube for 720 h. From X-ray powder analysis a Ce₂CuGe₆-type structure was claimed for this phase, a = 0.3993, b = 0.4100, c = 2.0939.

Rieger and Parthé (1969b) observed DyCu₂Ge₂ with the CeGa₂Al₂-type structure, a = 0.4029, c = 1.0281.

Francois et al. (1990) observed the CeNiSi₂ type for the DyCu_{0.38}Ge₂ compound and reported lattice parameters a=0.4092, b=1.635, c=0.3968 (X-ray powder diffraction) from a sample obtained by the powder metallurgical reaction at 1173 K.

4.11.7. Dy-Nb-Ge

A phase diagram for the Dy–Nb–Ge system has not been established. However, the existence of a compound Dy₂Nb₃Ge₄ with the Ce₂Sc₃Si₄-type (a=0.6975, b=1.3510, c=0.7154) was reported by Le Bihan et al. (1996a) from X-ray powder diffraction analysis of arc melted alloy. The starting materials were: Dy and Nb 99.99 mass%, Ge 99.999 mass%.

4.11.8. Dy-Mo-Ge

The existence of the Dy₂Mo₃Ge₄ compound with the Ce₂Sc₃Si₄ type (a=0.6892, b=1.3112, c=0.7038) was reported by Le Bihan et al. (1996b). For the sample preparation and purity of starting materials, see Dy–Nb–Ge.

4.11.9. *Dy*-*Ru*(*Rh*, *Pd*)-*Ge*

The ternary Dy-Ru(Rh, Pd)–Ge systems have been studied only with respect to the formation of compounds with specific composition and structure. Their crystallographic characteristics are listed in table 27.

4.11.10. *Dy*-Ag-Ge

No ternary phase diagram has been established for the Dy-Ag-Ge system, however one ternary compound has been characterized.

The crystal structure of the DyAgGe compound was firstly investigated by Zanicchi et al. (1983) using X-ray powder diffraction. It was found to adopt the ZrNiAl type with lattice parameters a=0.7105, c=0.4198. Gibson et al. (1996) reported the single-crystal investigation of this compound. The crystal structure was confirmed and lattice parameters were obtained as a=0.71056, c=0.41960. The single crystal was extracted from an arc melted sample annealed at 970 K for ten days.

4.11.11. *Dy–Os(Ir, Pt)–Ge*

No systematic studies have been performed for the ternary Dy–Os(Ir, Pt)–Ge systems. Interaction of dysprosium with osmium (irridium, platinum) and germanium has been studied only with respect to the formation of compounds with a specific composition and structure. The crystallographic characteristics are listed in table 28.

Compound	Structure	Lattice parameters (nm)			Reference
		a	b	с	-
DyRu ₂ Ge ₂	$CeGa_2Al_2$	0.4219		0.9856	Francois et al. (1985)
Dy ₂ Ru ₃ Ge ₅	U2Co3Si5	0.9783	1.241	0.5723	Venturini et al. (1986b)
$Dy_3Ru_4Ge_{13}$	$Yb_3Rh_4Sn_{13}$	0.895			Segre et al. (1981a)
DyRh ₂ Ge ₂	CeGa ₂ Al ₂	0.4104		1.0253	Francois et al. (1985)
$Dy_2Rh_3Ge_5$	$Lu_2Co_3Si_5$	0.9940	1.2035 $\beta = 92.0^{\circ}$	0.5827	Venturini et al. (1986b)
$Dy_5Rh_4Ge_{10}$	$Sc_5Co_4Si_{10}$				Méot-Meyer et al. (1985b)
Dy ₄ Rh ₇ Ge ₆	$U_4 Re_7 Si_6$	0.8326			Francois et al. (1985)
Dy ₃ Rh ₄ Ge ₁₃	$Yb_3Rh_4Sn_{13}$	0.8928			Venturini et al. (1985b)
Dy ₄ Rh ₁₃ Ge ₉	Ho4Ir13Ge9				Verniere et al. (1995)
DyRhGe	TiNiSi	0.6899	0.4289	0.7521	Hovestreydt et al. (1982)
DyPd ₂ Ge	YPd ₂ Si	0.7355	0.7033	0.5565	Jorda et al. (1983)
Dy ₂ PdGe ₆	Ce ₂ CuGe ₆	0.4073	0.4016	2.1485	Sologub et al. (1995a)
DyPd ₂ Ge ₂	CeGa ₂ Al ₂	0.4035		0.9758	Rossi et al. (1979)
DyPdGe	KHg_2	0.4366	0.6963	0.7556	Hovestreydt et al. (1982)

 Table 27

 Crystallographic data for the ternary Dy-Ru(Rh, Pd)-Ge compounds

Table 28 Crystallographic data for the ternary Dy-Os(Ir, Pt)-Ge compounds

Compound	Structure	Lattice parameters (nm)			Reference	
		a	b	с	-	
$Dy_5Os_4Ge_{10}$	$Sc_5Co_4Si_{10}$				Méot-Meyer et al. (1985b)	
Dy ₃ Os ₄ Ge ₁₃	$Yb_3Rh_4Sn_{13}$	0.8986			Segre et al. (1981a)	
DyIrGe ₂	NdIrGe ₂	0.4256	1.593	0.8815	Francois et al. (1987)	
Dy ₂ Ir ₃ Ge ₅	U2Co3Si5	1.0122	1.171	0.5950	Venturini et al. (1986b)	
Dy ₄ Ir ₇ Ge ₆	$U_4 Re_7 Si_6$	0.8322			Francois et al. (1985)	
$Dy_5Ir_4Ge_{10}$	$Sc_5Co_4Si_{10}$				Méot-Meyer et al. (1985b)	
$Dy_3Ir_4Ge_{13}$	$Yb_3Rh_4Sn_{13}$	0.8937			Venturini et al. (1985b)	
$Dy_4Ir_{13}Ge_9$	Ho ₄ Ir ₁₃ Ge ₉				Verniere et al. (1995)	
DyIrGe	TiNiSi	0.6838	0.4266	0.7597	Hovestreydt et al. (1982)	
DyPtGe ₂	NdIrGe ₂				Francois et al. (1987)	
DyPt ₂ Ge ₂	CeGa ₂ Al ₂	0.434		0.975	Rossi et al. (1979)	
	LaPt ₂ Ge ₂	0.4301	0.4346	0.9682	Venturini et al. (1989a)	
		$\beta = 91.26^{\circ}$				
DyPtGe	TiNiSi	0.6983	0.4340	0.7554	Hovestreydt et al. (1982)	
Dy ₂ PtGe ₆	Ce_2CuGe_6	0.4043	0.4005	2.1672	Sologub et al. (1995a)	

TERNARY RARE-EARTH-GERMANIUM SYSTEMS

4.11.12. Dy-Au-Ge

No ternary phase diagram exists for the Dy–Au–Ge system, however, a ternary compound of dysprosium with gold and germanium in the stoichiometric ratio 1:1:1 has been identified and studied by means of X-ray and metallographic analyses by Rossi et al. (1992). DyAuGe was found to adopt the LiGaGe type with lattice parameters a=0.4411, c=0.7287. The sample was prepared by melting the metals (around 99.9 mass% for dysprosium and 99.99 mass% for gold and germanium) in an induction furnace and annealing at 1070 K for one week.

4.12. Ho-d element-Ge systems

4.12.1. Ho-Cr-Ge

Brabers et al. (1994) reported the existence of the compound $HoCr_6Ge_6$ with the $HfFe_6Ge_6$ type structure (a=0.5158, c=0.8269; X-ray powder diffraction). The sample was prepared by arc melting and subsequent annealing at 1073 K for three weeks in a vacuum.

4.12.2. Ho-Mn-Ge

No phase diagram is available for the ternary Ho-Mn-Ge system; however three ternary compounds have been observed and characterized by different authors.

Venturini et al. (1992) reported the existence of the compound $HoMn_6Ge_6$ with the HfFe₆Ge₆ type (a=0.5230, c=0.8155; X-ray powder diffraction). The sample was synthesized from a mixture of stoichiometric amounts of the elements, which was compacted and sealed in a silica tube under argon followed by annealing at 1073 K for two weeks.

Rossi et al. (1978b) reported an investigation of the crystal structure of the HoMn₂Ge₂ compound (CeGa₂Al₂ type, a=0.3977, c=1.0845; X-ray powder method). The alloy was obtained by melting under argon in an induction furnace and was annealed at 770 K for one week. The metals used were of purity greater than 99.9 mass% for Ho, and greater than 99.99 mass% for Mn and Ge.

HoMn_{0.25}Ge₂ was found to adopt the CeNiSi₂ type structure with lattice parameters a=0.4097, b=1.574, c=0.3983 by Francois et al. (1990) (X-ray powder diffraction data). For sample preparation see GdFe_{0.25-0.46}Ge₂ under Gd–Fe–Ge.

4.12.3. Ho-Fe-Ge

The phase diagram for the Ho–Fe–Ge system was investigated by Salamakha et al. (1996g) by means of X-ray analysis (fig. 93). Alloys for investigation were prepared by arc melting proper amounts of the constituent elements. The starting materials were used in the form of ingots of holmium (99.9 mass%), iron (99.99 mass%) and germanium (99.999 mass%). The samples were annealed at 870 K for two weeks. Six ternary compounds have been observed and characterized.



Fig. 93. Ho–Fe–Ge, isothermal section at 870 K.

HoFe₆Ge₆ (1) was reported to be isotypic with YCo₆Ge₆, lattice parameters a=0.5110, c=0.4056 (Mruz et al. 1984). The sample was prepared by arc melting the proper amounts of the starting components, followed by annealing at 870 K for two weeks and finally quenching in cold water. At variance with these data, HoFe₆Ge₆ was found to crystallize with the TbFe₆Sn₆ type, a=0.8111, b=1.766, c=0.5116 by Venturini et al. (1992) from X-ray powder diffraction data. The alloy was obtained by powder metallurgical reaction in an evacuated silica tube at 1173 K for two weeks. This suggests that HoFe₆Ge₆ may be polymorphic.

Pecharsky et al. (1989) reported HoFe_{0.33}Ge₂ (5) to crystallize with the CeNiSi₂-type (a=0.4102, b=1.5689, c=0.3986; X-ray powder analysis). The alloy was arc melted and annealed at 870 K. The purity of the starting materials was greater than 99.9 mass%. Francois et al. (1990) confirmed the occurrence of CeNiSi₂ type for holmium–iron–germanium combinations from the alloys annealed at 1173 K (HoFe_{0.38}Ge₂; a=0.4105, b=1.572, c=0.3999).

Salamakha et al. (1996g) investigated the crystal structure of Ho₁₁₇Fe₅₂Ge₁₁₂ (6) by X-ray powder diffraction (Tb₁₁₇Fe₅₂Ge₁₁₂ type, a=2.8238). The alloy was synthesized by arc melting and annealing at 870 K for two weeks. The starting materials were Ho 99.9 mass%, Fe 99.9 mass%, and Ge 99.99 mass%.

According to X-ray powder diffraction data, HoFe₂Ge₂ (3) was found to be isostructural with the CeGa₂Al₂ type, with lattice parameters a=0.3949, c=1.0430 (Rossi et al. 1978a).

Fedyna (1988) reported on the X-ray powder investigation of the crystal structure of HoFe₄Ge₂ (2) (ZrFe₄Si₂ type, a=0.7255, c=0.3852) from an arc melted alloy annealed at 870 K alloy.

 $Ho_6Fe_8Ge_8$ (4) belongs to the $Gd_6Cu_8Ge_8$ type, a = 1.3450, b = 0.6781, c = 0.4117, after Fedyna et al. (1994).

4.12.4. Ho-Co-Ge

The isothermal section of the Ho–Co–Ge system at 870 K over the whole concentration region was derived by Aslan (1990) (fig. 94) employing X-ray and microstructural analyses of 212 alloys which were prepared by arc melting the proper amounts of the constituent elements of high purity. The melted buttons were then annealed in evacuated silica tubes at 870 K for 720 hours.

The ternary phase diagram is characterized by the existence of eleven ternary compounds and by the formation of solid solutions based at the Ho_2Co_{17} and $HoCo_5$ binary compounds where the maximum solubility of germanium is 10 at.%. The Ho_5Ge_3 phase dissolves 8 at.% Co.

Méot-Meyer et al. (1985a) reported the crystal structure of $HoCo_xGe_2$ (8), x=0.48 (CeNiSi₂ type, a=0.4094, b=1.595, c=0.4009). The sample was prepared by powder metallurgical reaction and annealed in an evacuated silica tube at 1173 K. Pecharsky et al. (1989) confirmed the formation and crystal structure of the $HoCo_{1-x}Ge_2$ compound and additionally observed the existence of a homogeneity field from arc melted alloys annealed at 870 K (a=0.4080-0.4093, b=1.583-1.592, c=0.3953-0.4008; X-ray powder analysis).

The crystal structure of Ho₃Co₄Ge₁₃ (3) (Yb₃Rh₄Sn₁₃ type, a=0.8735; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample which was prepared by heating a compacted mixture of the starting materials (Ho in pieces, 99.9 mass%; Co and Ge in powder, 99.99 mass%) in an evacuated quartz tube at 1073 K. Bodak et al.



Fig. 94. Ho-Co-Ge, isothermal section at 870 K.

(1987) reported the Y₃Co₄Ge₁₃-type for the Ho₃Co₄Ge₁₃ compound (a=0.8742; X-ray powder data) from arc melted alloy annealed at 870 K.

HoCo₂Ge₂ (5) was found to adopt the CeGa₂Al₂ type, a = 0.3957, c = 1.0077 (Szytuła et al. 1980; X-ray powder diffraction). Aslan (1990) confirmed the crystal structure and observed the existence of a homogeneity field for HoCo_{2.0+x}Ge_{2-x} (x = 0.5).

From an X-ray powder analysis of alloy annealed at 1173 K, Ho₂Co₃Ge₅ (6) was reported to adopt the Lu₂Co₃Si₅-type structure, a=0.9618, b=1.1805, c=0.5691, $\beta=91.9^{\circ}$ (Venturini et al. 1986b).

The crystal structure of the HoCo₆Ge₆ (2) compound was reported by Buchholz and Schuster (1981) (YCo₆Ge₆ structure type, a = 0.5074, $c \ 0.3910$). The sample was melted under argon in a corundum crucible at 1073–1273 K.

Gorelenko et al. (1984) reported the crystal structure of HoCoGe (9) (TiNiSi type, a = 0.6851, b = 0.4198, c = 0.7253; X-ray powder analysis). The alloy was arc melted, and annealed in an evacuated quartz tube at 870 K for 350 hours.

Ho₃Co₂Ge₄ (10) crystallizes with a Tb₃Co₂Ge₄-type of structure, a=1.0523, b=0.7958, c 0.4152, $\gamma=107.36^{\circ}$ (X-ray powder data; Mruz et al. 1989). The sample was prepared by arc melting and annealing at 873 K for 240 h.

Ho₂CoGe₆ (7) is isotypic with Ce₂CuGe₆, a = 0.3923, b = 0.3974, c = 2.131 (Oleksyn et al. 1991; X-ray powder diffraction data). The sample was melted in an arc furnace and annealed at 1070 K in an evacuated quartz capsule for 400 h. The purity of the starting materials was greater than 99.9 mass%.

Bodak et al. (1986) reported on the X-ray powder investigation of the compound Ho₂CoGe₂ (11), Sc₂CoSi₂ type, a=1.0408, b=1.0109, c=0.4166, $\gamma=117.45^{\circ}$.

Investigating the isothermal section, Aslan (1990) observed two compounds with unknown structures: \sim Ho₃Co₆₅Ge₃₂ (1) and \sim HoCo₂Ge₅ (4).

4.12.5. *Ho–Ni–Ge*

Figure 95 represents the isothermal section of the Ho–Ni–Ge phase diagram at 870 K, which was studied by Aslan (1990). The isothermal section was constructed by means of X-ray powder and partly microstructural analyses of 158 alloys which were arc melted, subsequently annealed in evacuated silica tubes for 720 h at 870 K, and finally quenched in cold water. The starting materials were Ho 99.9 mass%, Ni 99.98 mass%, and Ge 99.99 mass%.

The ternary phase diagram is characterized by the existence of ten ternary compounds and by the formation of substitutional solid solutions originating at Ho_2Ni_{17} and $HoNi_5$ binary compounds where the maximum solubility of germanium is 17 at.%. The binary $HoGe_{1.5}$ compound dissolves 15 at.% Ni.

HoNi₅Ge₃ (1) was reported to crystallize with the YNi₅Si₃ type, a=1.9050, b=0.3856, c=0.6785, by Fedyna et al. (1987). The arc melted alloy, annealed at 870 K, was investigated by X-ray powder diffraction analysis. The starting materials were Ho 99.9 mass%, Ni 99.99 mass%, and Ge 99.999 mass%.



Fig. 95. Ho-Ni-Ge, isothermal section at 870 K.

Ho₃Ni₁₁Ge₄ (2) belongs to the Sc₃Ni₁₁Si₄ type, a=0.8292, c=0.8682, after Fedyna et al. (1987). An alloy was prepared in the same manner as HoNi₅Ge₃.

The HoNi₂Ge₂ (4) compound was found to adopt the CeGa₂Al₂-type structure, a = 0.4021, c = 0.9757 (Rieger and Parthé 1969b).

HoNiGe₃ (5) with the SmNiGe₃-type structure (a=2.1476, b=0.4063, c=0.4054, X-ray powder diffraction analysis) was reported by Bodak et al. (1985). For the details of sample preparation and purity of starting materials, see HoNi₅Ge₃, above.

Ho₂NiGe₆ (6) has been found by Oleksyn (1990) from X-ray powder diffraction to be isostructural with Ce₂CuGe₆ (a = 0.3941, b 2.1108, c = 0.3991). The sample was prepared by arc melting ingots of the constituting elements and annealing at 1070 K for 700 h. For the purity of starting materials, see HoNi₅Ge₃, above.

Pecharsky et al. (1989) investigated the formation and crystal structure of the $HoNi_{1-x}Ge_2$ (8) compound by X-ray powder analysis of arc melted alloy annealed at 870 K (CeNiSi₂ type, a=0.4059-0.4079, b=1.5809-1.5796, c=0.3934-0.3952). Francois et al. (1990) confirmed the structure and reported the composition and lattice parameters $HoNi_{0.71}Ge_2$, a=0.4084, b=1.629, c=0.4091 (X-ray powder diffraction) from a sample obtained by powder metallurgical reaction at 1173 K.

Gorelenko et al. (1984) reported the crystal structure of HoNiGe (9) (TiNiSi type, a = 0.6856, b = 0.4204, c = 0.7256; X-ray powder analysis). For the experimental details, see HoCoGe under Ho-Co-Ge.

The crystal structure of HoNiGe₂ (7) was reported by Oleksyn (1990): NdIrGe₂ type, a=0.4136, b=0.8430, c=1.5792 (X-ray powder diffraction). The sample was prepared by arc melting ingots of the constituting elements and annealing at 1070 K for 700 h.

Bodak et al. (1982) reported on the crystal structure of Ho₃NiGe₂ from X-ray powder diffraction (La₃NiGe₂ type, a=1.1195, b=0.4197, c=1.1192). This compound, however, apparently does not exist at 870 K.

The crystal structures of two more ternary compounds \sim HoNi₃Ge₂ (3) and \sim Ho₄NiGe₄ (10) have not yet been evaluated (Aslan 1990).

4.12.6. Ho-Cu-Ge

No phase diagram is available for the Ho-Cu-Ge system; however the crystal structures for five ternary compounds are reported by different groups of authors.

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented are HoCu_{1-0.67}Ge_{1-1.33} with a = 0.4225-0.400, c = 0.3608-0.402. At variance with these data, Iandelli (1993) observed HoCuGe with the CaIn₂-type structure (a = 0.4232, c = 0.7188, X-ray powder analysis). The alloy was prepared from filings or powders of metals (Ho 99.7 mass%, Cu and Ge 99.99 mass%), which were mixed and sealed in a tantalum crucible under argon, melted by induction heating, and annealed for 10 days at 1023 K.

Ho₆Cu₈Ge₈ crystallizes with the Gd₆Cu₈Ge₈ type, lattice parameters a = 1.384, b = 0.662, c = 0.417 (Hanel and Nowotny 1970).

Konyk et al. (1988) investigated the crystal structure of Ho₂CuGe₆ alloy prepared by arc melting under argon and annealing at 870 K in an evacuated quartz tube for 720 h. From X-ray powder analysis a Ce₂CuGe₆-type was claimed, a=0.4011, b=0.4129, c=2.1104.

Rieger and Parthé (1969b) prepared HoCu₂Ge₂ with the CeGa₂Al₂-type structure, a = 0.4016, c = 1.0302.

Francois et al. (1990) observed the CeNiSi₂ type structure for the HoCu_{0.33}Ge₂ compound and reported lattice parameters a = 0.4074, b = 1.618, c = 0.3950 (X-ray powder diffraction) from a sample obtained by powder metallurgical reaction at 1173 K.

4.12.7. Ho-Nb-Ge

The phase diagram of the Ho–Nb–Ge system has not been established, but at least one ternary phase is known. The existence of the compound Ho₂Nb₃Ge₅ with the Ce₂Sc₃Si₄-type structure (a=0.6956, b=1.3479, c=0.7131) was reported by Le Bihan et al. (1996a) from X-ray powder diffraction data of an arc melted alloy. The starting materials were: Ho and Nb 99.99 mass%, Ge 99.999 mass%.

4.12.8. Ho-Mo-Ge

No phase diagram is available for the Ho–Mo–Ge system, and only one compound was observed and investigated. Ho₂Mo₃Ge₄ was reported to crystallize with the Ce₂Sc₃Si₄-type structure (a=0.6868, b=1.3079, c=0.7032) by Le Bihan et al. (1996b) from X-ray powder diffraction of an arc melted alloy. The starting materials were: Ho and Mo 99.99 mass%.



Fig. 96. Ho-Ru-Ge, isothermal section at 870 K.

4.12.9. Ho-Ru-Ge

The isothermal section for Ho–Ru–Ge was constructed by Sologub (1995) at 870 K by means of X-ray diffraction (fig. 96). The samples were prepared by direct arc melting of pieces of high purity components (greater than 99.9 mass%), annealed at 870 K for two weeks in evacuated quartz ampoules and quenched in cold water. The phase-field distribution is characterized by the formation of seven compounds.

Early investigations of the HoRu₂Ge₂ (2) compound showed that it had the CeGa₂Al₂type structure with a=0.4211, c=0.9790 (Francois et al. 1985) from X-ray powder analysis of an alloy obtained by powder metallurgical reaction at 1273 K. The starting components were Ho (3N), Ru (4N), and Ge (4N). Sologub et al. (1995b) confirmed the crystal structure and obtained the lattice parameters a=0.4218, c=0.9805.

Venturini et al. (1986b) reported the structure for the Ho₂Ru₃Ge₅ (3) compound, which crystallizes with the U₂Co₃Si₅-type of structure. The lattice parameters were reported as a=0.9771, b=1.241, c=0.5706 (X-ray powder diffraction data). For sample preparation, see La₂Ru₃Ge₅ under La–Ru–Ge.

The $Pr_3Rh_4Sn_{13}$ -type structure was announced for the $Ho_3Ru_4Ge_{13}$ (1) compound (a = 0.8945) by Segre et al. (1981a) from an X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Ho (3N), Ru (3N), and Ge (6N).

Francois et al. (1990) reported the crystal structure of HoRu_{0.27}Ge₂ (4) (CeNiSi₂ type, a = 0.4116, b = 1.577, c = 0.4007). For sample preparation, see GdFeGe₂ under Gd–Fe–Ge. Sologub et al. (1995b) confirmed the formation and crystal structure for this compound, a = 0.4105, b = 1.5701, c = 0.4008 (X-ray powder diffraction).

Sologub et al. (1994a) reported on a single-crystal investigation of two compounds: HoRuGe (5), TiNiSi type, a=0.6980, b=0.4351, c=0.7281, and Ho₃Ru₂Ge₃ (6), Hf₃Ni₂Si₃ type, a=0.4242, b=1.0731, c=1.3840. The single crystals were obtained from samples which were arc melted and annealed at 870K for 400 h.

Ho₂RuGe₂ (7) was found to crystallize with the Sc₂CoSi₂-type structure, a=1.0643, b=0.4259, c=1.0203, $\beta=118.0^{\circ}$ by Sologub et al. (1995b).

4.12.10. Ho-Rh-Ge

The phase relations in the ternary Ho–Rh–Ge system (0-50 at.% Rh) at 870K were investigated by Sologub (1995) (fig. 97). Fourteen ternary compounds were found to exist within the concentration region investigated. For experimental procedures, see Ho–Ru–Ge.

Venturini et al. (1985b) reported an X-ray powder diffraction study of the Ho₃Rh₄Ge₁₃ (1) compound from a sample prepared by heating a mixture of starting components (Ho 3N, Rh 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to be of the Yb₃Rh₄Sn₁₃ type, a=0.8916.

Francois et al. (1985) determined the CeGa₂Al₂-type structure for the HoRh₂Ge₂ (3) compound, a = 0.4101, c = 1.0196.

Ho₂Rh₃Ge₅ (4) was found to crystallize with Lu₂Co₃Si₅-type structure (a=1.1353, b= 1.1976, c=0.5813, β =119.05°; X-ray single-crystal data) by Venturini et al. (1986b) from a sample synthesized by powder metallurgical reaction at 1173 K. The purity of the starting materials was greater than 99.9 mass%.

Hovestreydt et al. (1982) reported the crystal structure of the HoRhGe (8) compound (TiNiSi type, a=0.6964, b=0.4272, c=0.7516; X-ray powder data) from an arc melted



Fig. 97. Ho–Rh–Ge, partial isothermal section at 870 K (0–50 at.% Rh).

sample annealed at 1270 K for 1-2 weeks. The starting components were Ho (3N), Rh (4N), and Ge (5N).

Salamakha and Sologub (1999) reported on the crystal structure of the Ho₃Rh₂Ge₂ (13) compound (La₃Ni₂Ga₂ type, a = 0.55367, b = 0.7726, c = 1.3165; X-ray powder diffraction data). For the details of sample preparation, see La₃Rh₂Ge₂ under La–Rh–Ge.

Sologub (1995) established the Ho₄Ir₁₃Ge₉-type for the Ho₄Rh₁₃Ge₉ (2) compound, a=0.3962, b=1.1034, c=1.9203. For sample preparation, see Ho–Ru–Ge.

Venturini et al. (1984) observed the existence of the Ho₅Rh₄Ge₁₀ (6) compound with Sc₅Co₄Si₁₀ type (a = 1.2902, c = 0.4242; X-ray powder diffraction) from a sample obtained by heating amixture of powders in an evacuated tube at 1073 K. Salamakha and Sologub (1999) confirmed the Sc₅Co₄Si₁₀-type of structure by a single-crystal method, a = 1.29336, c = 0.42596. The single crystal was taken from an arc melted sample annealed at 870 K.

 $Ho_4Rh_7Ge_6$ (5) was reported to adopt the U₄Re₇Si₆ type structure, a = 0.8305 (Francois et al. 1985) from a sample which was obtained by heating a mixture of powders of the starting materials (Ho 3N, Rh 4N, Ge 4N) in evacuated quartz tubes at 1273 K.

Francois et al. (1990) reported the crystal structure of $\text{HoRh}_{0.28}\text{Ge}_2$ (7) (CeNiSi₂ type, a=0.4107, b=1.584, c=0.3988). For sample preparation, see GdFeGe₂ under Gd–Fe–Ge.

Four more ternary compounds were observed and investigated by Sologub (1995) using an X-ray single-crystal method: Ho₃Rh₂Ge₃ (9), Hf₃Ni₂Si₃ type, a = 0.425, b = 1.026, c = 1.488; ~Ho_{3+x}Rh₂Ge_{3+x} (10), orthorhomb., a = 0.423, b = 1.024, c = 10.2; Ho₂RhGe₂ (11), Sc₂CoSi₂ type, a = 1.0465, b = 0.42670, c = 1.02203, $\beta = 117.2^{\circ}$; ~Ho_{2+x}RhGe_{2+x} (12), monoclinic, a = 1.042, b = 0.428, c = 6.3, $\beta = 117^{\circ}$.

The crystal structure of ~Ho₅Rh₃Ge₂ (14) has not been evaluated (Sologub 1995).

4.12.11. Ho-Pd-Ge

A systematic study of the Ho–Pd–Ge system at 870 K was performed by Sologub (1995) over the whole concentration region by means of X-ray powder analysis (fig. 98). The samples were prepared by arc melting under an argon atmosphere and annealed in evacuated quartz ampoules at 870 K for 500 hours. The starting materials were 99.8 mass% pure or better.

Phase relations are characterized by the existence of ten ternary compounds and by the formation of an extended solid solution originating at the HoPd₃ binary compound. The maximum solubility of Ge in HoPd₃ was observed as 12 at.%. The solubility of the third component in other binary compounds was found to be negligible.

The existence of the HoPd₂Ge₂ (2) compound (CeGa₂Al₂ type, a=0.4220, c=1.0018) was reported by Bodak and Sologub (1991a). The sample was prepared in the same manner as the Ho–Pd–Ge alloys.

Bodak and Sologub (1991a) reported on the X-ray powder analysis of the Ho₂PdGe₆ (3) compound which was found to crystallize with the Ce₂CuGe₆ type, a = 0.4080, b = 0.4007, c = 2.140. For the experimental procedure, see Ho–Pd–Ge.



Fig. 98. Ho–Pd–Ge, isothermal section at 870 K.

The crystal structure of the compound HoPd₂Ge (4) was found to be of the YPd₂Si type (a=0.7318, b=0.6036, c=0.5553; X-ray powder diffraction) by Jorda et al. (1983). For the experimental procedure, see LaPd₂Ge under La–Pd–Ge. The starting materials were Pd 99.99 mass%, Ge specpure quality, and Ho 99.9 mass%. Sologub (1995) confirmed the structure of HoPd₂Ge and reported similar lattice parameters (a=0.7321, b=0.6045, c=0.5563; X-ray powder diffraction).

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound HoPdGe (8) adopts the KHg₂-type of structure, a=0.4360, b=0.6938, c=0.7547. For sample preparation, see LaPdGe under La-Pd-Ge. The starting materials were Ho (3N), Pd (4N), and Ge (5N). Sologub (1995) reported a single-crystal investigation of HoPdGe from an arc melted specimen annealed at 870 K for 500 h (KHg₂ type, a=0.4358, b=0.6922, c=0.7546).

Francois et al. (1990) investigated the crystal structure of the HoPd_{0.33}Ge₂ (7) compound (CeNiSi₂ type, a=0.4118, b=1.593, c=0.4002). In the course of studying the phase equilibria in the Ho–Pd–Ge system at 870 K, Sologub (1995) confirmed the existence of the compound with the CeNiSi₂ type structure and obtained similar lattice parameters: a=0.4107, b=1.5924, c=0.3979.

Sologub (1995) studied the crystal structures of HoPdGe₂ (5) (NdIrGe₂ type, a = 0.4234, b = 1.597, c = 0.8715) and HoPd_{0.8-0.6}Ge_{1.2-1.4} (9) (AlB₂ type, a = 0.4237-0.4276, c = 0.3828-0.3721) by X-ray powder diffraction. The experimental details are given above (Ho-Pde-Ge isothermal section).

 $Ho_6Pd_8Ge_8$ (6) was found to crystallize with the $Gd_6Cu_8Ge_8$ -type structure, a = 0.42348, b = 0.68373, c = 1.4093 (Gladyshevsky et al. 1991b; X-ray single-crystal data).

Sologub et al. (1994b) investigated Ho₂₆Pd₄(Pd, Ge)_{19-x} (10) by an X-ray single-crystal method: own structure type, a = 1.4523, c = 1.0318. The alloy was arc melted and annealed at 870 K for 500 h.

The crystal structure of the \sim HoPd₅Ge₃ (1) compound has not yet been established (Sologub 1995).

4.12.12. Ho-Ag-Ge

The isothermal section of the Ho–Ag–Ge system at 870 K was reported by Sologub and Protsyk (1991) from an X-ray powder analysis of 54 alloys (fig. 99). The samples were obtained by arc melting the components in purified argon and annealing at 870 K for 500 h in evacuated quartz tubes. Finally the alloys were water quenched. The purity of the starting components was Ho 99.8 mass%, Ag 99.9 mass%, and Ge 99.999 mass%. One ternary compound was found to exist in this system at 870 K.

Sologub and Protsyk (1991) reported on the crystal structure of the HoAgGe compound. It was found to adopt the ZrNiAl-type structure, a=0.7084, c=0.41793 (X-ray powder diffraction). Gibson et al. (1996) confirmed the crystal structure from X-ray powder diffraction of an arc melted alloy annealed at 970K for ten days, and presented the lattice parameters a=0.70783, c=0.41826.



Fig. 99. Ho-Ag-Ge, isothermal section at 870 K.

4.12.13. Ho–Re–Ge

The only information on the system Ho–Re–Ge is due to Francois et al. (1990) who investigated the occurrence of the compound with the CeNiSi₂ type; no phase diagram is available. The HoRe_{0.25}Ge₂ compound was found to adopt the CeNiSi₂-type structure with lattice parameters a=0.4128, b=1.578, c=0.4028 by Francois et al. (1990) (X-ray

powder diffraction data). The alloy was prepared from a mixture of the proper amounts of the components with purity 99.9 mass% by metallurgical reaction in a quartz tube at 1173 K.

4.12.14. Ho-Os-Ge

Bodak and Sologub (1991b) were the first to investigate, by X-ray powder diffraction, the phase equilibria within the Ho–Os–Ge system at 870 K over the whole concentration region; samples were prepared as described under Ho–Ru–Ge. The phase relations are characterized by the existence of three ternary compounds (fig. 100).

Bodak et al. (1991) indicated a $Sc_5Co_4Si_{10}$ -type structure for Ho₅Os₄Ge₁₀ (2) from X-ray single-crystal diffraction and reported the lattice parameters a=1.2984, c=0.42820.



Fig. 100. Ho-Os-Ge, isothermal section at 870 K.

Pr₃Rh₄Sn₁₃-type structure was announced for the Ho₃Os₄Ge₁₃ compound (1) (a = 0.8977) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Ho (3N), Os (3N), and Ge (6N). At variance with these data, Bodak and Sologub (1991b) observed the Y₃Co₄Ge₁₃ type for a Ho₃Os₄Ge₁₃ alloy which was arc melted and annealed at 870 K for 500 hours (a = 0.89737; X-ray powder diffraction).

Ho₂OsGe₂ (3) was found to adopt the Sc₂CoSi₂ type structure, a = 1.0691, b = 0.42618, c = 1.0050, $\beta = 118.07^{\circ}$ (X-ray single-crystal analyses; Gladyshevsky et al. 1991b).

4.12.15. Ho-Ir-Ge

The partial isothermal section for the Ho-Ir-Ge system at 870K (0-50 at.% Ir) was established by Sologub (1995) (fig. 101). For sample preparation, see Ho-Ru-Ge. Five



Fig. 101. Ho-Ir-Ge, partial isothermal section at 870 K (0-50 at.% Ir).

ternary compounds were confirmed and eight ternary phases were observed for the first time. No homogeneous ranges were encountered for the ternary compounds.

Venturini et al. (1984) observed the existence of the Ho₅Ir₄Ge₁₀ (5) compound with Sc₅Co₄Si₁₀-type structure from X-ray powder diffraction of a sample obtained by heating the starting components in an evacuated tube at 1073 K, a = 1.2878, c = 0.4286.

Venturini et al. (1985b) reported on an X-ray powder diffraction study of the $Ho_3Ir_4Ge_{13}$ (1) compound from a sample prepared by heating a mixture of the starting components (Ho 3N, Ir 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to adopt the Yb₃Rh₄Sn₁₃ type, a=0.8931.

Hovestreydt et al. (1982) reported the crystal structure of the HoIrGe (7) compound (TiNiSi type, a=0.6801, b=0.4252, c=0.7595; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. The starting components were Ho (3N), Ir (4N), and Ge (5N).

Francois et al. (1987) reported the crystal structure of HoIrGe₂ (4) (NdIrGe₂ type, a = 0.4244, b = 1.595, c = 0.8804). The sample was prepared by heating mixtures of powders of the starting components (Ho 3N, Ir 3N, Ge 3N) in an evacuated silica tube at 1173 K.

HoIr_{0.28}Ge₂ (6) was found to crystallize with a CeNiSi₂ type, a=0.4108, b=1.585, c=0.3988 (X-ray powder diffraction; Sologub 1995). For sample preparation, see Ho-Ru-Ge.

Ho₄Ir₇Ge₆ (3) was reported to adopt the U₄Re₇Si₆ type (a=0.8311; Francois et al. 1985) from a sample obtained by heating a mixture of powders of the starting materials (Ho 3N, Os 4N, Ge 4N) in an evacuated quartz tube at 1273 K.

Five other ternary compounds were observed and characterized by an X-ray singlecrystal method by Sologub et al. (1993) and Sologub (1995): $Ho_4Ir_{13}Ge_9$ (2) belongs to a new structure type, a=0.3954, b=1.1186, c=1.9301 (Sologub et al. 1993); Ho₃Ir₂Ge₃ (8) adopts Hf₃Ni₂Si₃-type structure with a=0.423, b=1.024, c=1.485 (Sologub 1995); \sim Ho_{3+x}Ir₂Ge_{3+x} (9) is orthorhombic, a=0.424, b=1.025, c=10.25 (Sologub 1995); Ho₂IrGe₂ (10) crystallizes with the Sc₂CoSi₂-type structure, a=1.047, b=0.428, c=1.079, $\beta=118^{\circ}$ (Sologub 1995); \sim Ho_{2+x}IrGe_{2+x} (11) is monoclinic, a=1.042, b=0.428, c=6.3, $\beta=117^{\circ}$ (Sologub 1995). The alloys for this investigation were prepared in the same manner as Ho–Ru–Ge.

Two more compounds with unknown structures were observed by Sologub (1995): \sim Ho₅Ir₃Ge₂ (12) and \sim Ho₅Ir₂Ge₃ (13).

4.12.16. Ho-Pt-Ge

The phase equilibria in the Ho–Pt–Ge system (fig. 102) have been investigated by Sologub (1995) by means of an X-ray analysis of 90 alloys which were arc melted and subsequently annealed in evacuated silica tubes for 500 h at 870 K and finally quenched in water. The starting materials were Ho 99.8 mass%, Pt 99.99 mass% and Ge 99.999 mass%. One ternary compound was confirmed and ten ternary phases were observed for the first time.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound HoPtGe (8) adopts the TiNiSi-type structure, a=0.6949, b=0.4328, c=0.7535. For sample preparation, see LaPdGe under La-Pd-Ge.

Sologub et al. (1995a) reported on the X-ray powder analysis of the Ho₂PtGe₆ (3) compound which was found to crystallize with the Ce₂CuGe₆-type structure, a = 0.40441, b = 0.40026, c = 2.1571. For sample preparation, see La₂PdGe₆ under La–Pd–Ge.

X-ray single-crystal analysis was employed to investigate the crystal structure of the



Fig. 102. Ho-Pt-Ge, isothermal section at 870 K.

HoPtGe₂ (6) compound, NdIrGe₂ type, a = 0.4292, b = 0.8702, c = 1.6172 (Salamakha and Sologub 1998). The single crystal was obtained from an arc melted sample annealed at 870 K for 500 h.

Five more ternary compounds in the Ho–Pt–Ge system at 870K were observed and characterized by Sologub (1995) in the course of phase equilibrium studies using X-ray powder diffraction: Ho₂Pt₇Ge₄ (2), Ce₂Pt₇Ge₄-type structure, a=1.984, b=0.4062, c=1.1427; HoPt₂Ge (5), YPd₂Si-type structure, a=0.7218, b=0.6036, c=0.5453; HoPt_{0.22}Ge₂ (7), CeNiSi₂-type structure, a=0.4102, b=1.592, c=0.3951; Ho(Pt,Ge)₂ (10), AlB₂-type structure, a=0.4227, c=0.3822; Ho₂PtGe (11), CrB-type structure, a=0.4022, b=1.0864, c=0.4282.

Three ternary compounds with unknown structure types were observed by X-ray powder diffraction at 870 K: \sim HoPt₅Ge₃ (1), \sim Ho₃Pt₄Ge₆ (4) and \sim Ho₃Pt₂Ge₄ (9) (Sologub 1995).

4.12.17. Ho-Au-Ge

Information on interaction of holmium with gold and germanium is due to the work of two groups of authors (Sologub 1995 and Rossi et al. 1992). A phase diagram of the Ho–Au–Ge system is not available, however, one ternary compound has been observed and characterized.

A ternary compound of holmium with gold and germanium in the stoichiometric ratio 1:1:1 has been identified and studied by means of X-ray and metallographic analyses by Rossi et al. (1992). HoAuGe was found to adopt the LiGaGe type with lattice parameters a=0.4416, c=0.7335. Samples were prepared by melting the metals in an induction furnace, and annealing the resulting alloys at 1070 K for one week. The metal used had a purity of about 99.9 mass% for holmium and 99.99 mass% for gold and germanium. Sologub (1995) confirmed the structure type from X-ray powder diffraction of an alloy with equiatomic composition which was obtained by arc melting the metals and annealing the resulting button at 870 K for 500 h: a=0.44015, b=0.7231.

4.13. Er-d element-Ge systems

4.13.1. Er–Cr–Ge

Brabers et al. (1994) reported the existence of a compound ErCr_6Ge_6 with the HfFe₆Ge₆-type structure (a=0.5150, c=0.8258; X-ray powder diffraction). For sample preparation, see TbCr₆Ge₆ under Tb-Cr-Ge.

4.13.2. Er-Mn-Ge

No systematic study of the Er-Mn-Ge system has been carried out so far; however two ternary compounds were observed and investigated by two groups of authors (Rossi et al. 1978b, Venturini et al. 1992).

ErMn₆Ge₆ was found to crystallize in the HfFe₆Ge₆-type structure by Venturini et al. (1992), a=0.5221, c=0.8142 (X-ray powder diffraction data). For sample preparation, see TbMn₆Ge₆ under Tb-Mn-Ge.

Rossi et al. (1978b) reported an investigation of the crystal structure of the $ErMn_2Ge_2$ compound (CeGa₂Al₂-type structure, a=0.3963, c=1.0835; X-ray powder method). For the experimental details, see TbMn₂Ge₂ under Tb-Mn-Ge.

4.13.3. Er–Fe–Ge

The isothermal section of the Er–Fe–Ge system at 1070 K (fig. 103) was investigated by Oleksyn (1990) by means of metallographic, X-ray and microprobe analyses. Alloys for investigation were prepared by arc melting followed by annealing at 1070 K for 350 hours. The purity of the starting components was Er 99.82 mass%, Fe 99.90 mass%, and Ge 99.99 mass%. Eight ternary compounds were found to exist. The solubility of germanium in iron was established as 18 at.%.

 $ErFe_6Ge_6$ (1) was reported to be isotypic with the crystal structure of YCo₆Ge₆ with lattice parameters a=0.5100, c=0.4041 by Mruz et al. (1984) (X-ray powder diffraction; for sample preparation, see TbFe₆Ge₆ under Tb–Fe–Ge); and a=0.51086, c=0.4048 by Oleksyn (1990) (X-ray powder diffraction). At variance with these data, Venturini et al. (1992) reported the HoFe₆Sn₆-type structure for ErFe₆Ge₆, a=0.8103, b=2.652, c=0.5108 from X-ray powder diffraction data. The alloy was obtained by powder metallurgical reaction in an evacuated silica tube at 1173 K for two weeks.

Pecharsky et al. (1989) reported $\text{ErFe}_x\text{Ge}_{2-x}$ (6) to crystallize with the CeNiSi₂-type structure (a=0.4079-0.4086, b=1.5609-1.5930, c=0.3967-0.3976; X-ray powder analysis). The alloy was arc melted and annealed at 870 K. The purity of the starting materials was greater than 99.9 mass%. Oleksyn (1990) determined the homogeneity region for the ErFe_{0.06-0.30}Ge_{1.94-1.70} (CeNiSi₂-type) compound and obtained lattice parameters a=0.4083-0.4080, b=1.5630-1.5616, c=0.3982-0.3974. Francois et al.



Fig. 103. Er–Fe–Ge, isothermal section at 1070 K.

(1990) confirmed the occurrence of the CeNiSi₂-type structure for erbium-irongermanium combinations from alloys annealed at 1173 K (ErFe_{0.36}Ge₂; a=0.4098, b=1.565, c=0.3987).

According to X-ray powder diffraction data, $ErFe_2Ge_2$ (3) is isostructural with $CeGa_2Al_2$, lattice parameters a=0.3945, c=1.0435 (Bara et al. 1990). For the experimental procedure, see TbFe₂Ge₂ under Tb–Fe–Ge. The crystal structure was also confirmed by Oleksyn (1990) from X-ray powder diffraction, a=0.3932, c=1.0417.

ErFe₄Ge₂ (2) was observed to adopt the ZrFe₄Si₂-type of structure, a=0.7229, c=0.3842, from X-ray powder diffraction of an arc melted sample annealed at 870 K (Fedyna 1988). The crystallographic characteristics obtained by Oleksyn (1990) for ErFe₄Ge₂ are in good agreement: ZrFe₄Si₂ type, a=0.7246, c=0.3864.

Four more ternary compounds were observed for the first time and characterized by Oleksyn (1990): $Er_6Fe_8Ge_8$ (4), $Gd_6Cu_8Ge_8$ type, a=1.3460, b=0.6815, c=0.41057 (X-ray powder diffraction); $Er_9Fe_{10}Ge_{10}$ (5), $Tm_9Fe_{10}Ge_{10}$ type, a=0.5393, b=1.3343, c=1.3949 (X-ray single-crystal data); $Er_3Fe_2Ge_3$ (7), $Hf_3Ni_2Si_3$ type, a=0.41491, b=1.0591, c=1.3758 (X-ray powder diffraction); $Er_{117}Fe_{52}Ge_{112}$ (8), $Tb_{117}Fe_{52}Ge_{112}$ type, a=0.2838 (X-ray powder diffraction).

Two compounds were observed from arc melted samples investigated by Oleksyn (1990) using a single-crystal method: $\text{Er}_{6-x}\text{Fe}_6\text{Ge}_4$, new structure type, a=0.5086, c=0.7851, and $\text{Er}_3\text{Fe}\text{Ge}_3$, $W_3\text{CoB}_3$ type, a=0.4005, b=1.0544, c=1.4135. Apparently these phases are not stable equilibrium phases at 1070 K.

4.13.4. Er–Co–Ge

The isothermal section of the Er–Co–Ge system at 1070 K over the whole concentration region was derived by Oleksyn (1990) (fig. 104) employing X-ray phase and microstructural and microprobe analyses of alloys prepared by arc melting proper amounts of the constituent elements (Er 99.82 mass%, Co 99.90 mass%, Ge 99.99 mass%). The melted buttons were then annealed in evacuated silica tubes at 1070 K for 350 hours. Sixteen ternary compounds were found to exist. Extensive solid solubility regions of Ge in Fe (10 at.%) and in $\text{Er}_2\text{Co}_{17-x}$ (10 at.%) were observed.

The crystal structure of the $ErCo_6Ge_6$ (2) compound was reported by Buchholz and Schuster (1981) (YCo_6Ge_6 structure type, a=0.5074, $c \ 0.3910$). For experimental details see $ErCo_6Ge_6$ under Er-Co-Ge.

Méot-Meyer et al. (1985a) reported the crystal structure of ErCo_xGe_2 (13) (CeNiSi₂ type, a = 0.4078, b = 1.586, c = 0.3985). Samples were prepared by powder metallurgical reaction and annealed in an evacuated silica tube at 1173 K. Pecharsky et al. (1989) confirmed the formation and crystal structure of the ErCo_xGe_2 compound from arc melted alloys annealed at 870 K (a = 0.3983 - 0.4089, b = 1.5706 - 1.5805, c = 0.3955 - 0.3986; X-ray powder analysis). Oleksyn (1990) established the homogeneity region for the compound with CeNiSi₂ type: $\text{ErCo}_{0.09-0.33}\text{Ge}_{1.91-1.67}$, a = 0.4058 - 0.4003, b = 1.5743 - 1.5766, c = 0.3964 - 0.3932 (X-ray powder diffraction).



Fig. 104. Er–Co–Ge, isothermal section at 1070 K.

Fedyna (1988) reported the $ErCo_4Ge_2$ (3) compound to have $ZrFe_4Si_2$ -type structure, a=0.7217, c=0.3743 (X-ray powder diffraction).

The crystal structure of $Er_3Co_4Ge_{13}$ (5) (Yb₃Rh₄Sn₁₃ type, a=0.8726; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample which was prepared by heating a compacted mixture of the starting materials (Er in pieces, 99.9 mass%; Co and Ge in powder, 99.99 mass%) in an evacuated quartz tube at 1073 K. Bodak et al. (1987) reported Y₃Co₄Ge₁₃ type for the Er₃Co₄Ge₁₃ compound (a=0.8731; X-ray powder data) from arc melted alloy annealed at 870 K.

 ErCo_2Ge_2 (6) was found to adopt the CeGa₂Al₂-type structure, a = 0.3959, c = 1.0057 (Oleksyn 1990; X-ray powder diffraction).

From X-ray powder analysis of an alloy annealed at 1173 K, $Er_2Co_3Ge_5$ (7) was reported to adopt $Lu_2Co_3Si_5$ -type structure, a=0.9601, b=1.178, c=0.5680, $\beta=91.9^{\circ}$ (Venturini et al. 1986b).

Gorelenko et al. (1984) reported the crystal structure of ErCoGe (11) (TiNiSi type, a=0.6815, b=0.4181, c=0.7245; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Er₃Co₂Ge₄ (12) crystallizes with the Tb₃Co₂Ge₄-type structure, a = 1.0459, b = 0.7938, c = 0.4148, $\gamma = 107.20^{\circ}$ (X-ray powder diffraction; Mruz et al. 1989).

Bodak et al. (1986) reported an X-ray powder investigation of the compound Er_2CoGe_2 (15): Sc_2CoSi_2 type, a=1.0359, b=1.0181, c=0.4142, $\gamma=116.89^\circ$.

 Er_2CoGe_6 is isotypic with Ce_2CuGe_6 (9), a=0.39777, b=0.39331, c=2.1386 (Oleksyn et al. 1991; X-ray powder diffraction data). The sample was melted in an arc furnace and annealed at 1070 K in an evacuated quartz capsule for 400 h. The purity of the starting materials was greater than 99.9 mass%.

 $Er_5Co_4Ge_{10}$ (10) was found to adopt the $Sc_5Co_4Si_{10}$ -type structure, a = 1.2663, c = 0.41504 (Oleksyn 1990; X-ray powder diffraction).

 $Er_3Co_2Ge_3$ (14) crystallizes with the Hf₃Ni₂Si₃ type structure, a = 0.4145, b = 1.0337, c = 1.3784 (Oleksyn 1990; X-ray powder diffraction).

Four compounds with unknown structures were observed by Oleksyn (1990) in the Er– Co–Ge system at 1070 K: $\sim \text{Er}_{0.03}\text{Co}_{0.65}\text{Ge}_{0.32}$ (1), $\sim \text{Er}_{0.15}\text{Co}_{0.30}\text{Ge}_{0.55}$ (4), $\sim \text{Er}_{0.20}\text{Co}_{0.20}$ Ge_{0.60} (8) and $\sim \text{Er}_{0.42}\text{Co}_{0.10}\text{Ge}_{0.48}$ (16).

One more compound was observed from an arc melted sample and investigated by Oleksyn (1990) using single-crystal method: $\text{Er}_{6-x}\text{Co}_6\text{Ge}_4$, new structure type, a = 0.5091, c = 0.7861.

4.13.5. Er–Ni–Ge

Figure 105 presents the isothermal section of the Er–Ni–Ge phase diagram at 1070 K, studied by Oleksyn (1990). The isothermal section was constructed by means of X-ray powder microprobe and microstructural analyses of 240 alloys which were arc melted, subsequently annealed in evacuated silica tubes for 350 h at 1070 K, and finally quenched in water. The starting materials were Er 99.82 mass%, Ni 99.99 mass%, and Ge 99.99 mass%.

The ternary phase diagram is characterized by the existence of fourteen ternary compounds and by the formation of substitutional solid solutions originating at $\text{Er}_2\text{Ni}_{17}$ and ErNi_5 (10 at.% Ge) as well as Er_5Ge_3 (13 at.% Ni). Nonstoichiometry was observed for $\text{ErNi}_{1-x}\text{Ge}_2$.



Fig. 105. Er-Ni-Ge, isothermal section at 1070 K.

ErNi₅Ge₃ (1) was reported to crystallize with the YNi₅Si₃ type, a=1.903, b=0.3847, c=0.6783 by Fedyna et al. (1987). The arc melted alloy, annealed at 1070 K, was investigated by X-ray powder diffraction analysis. The starting materials were Er 99.82 mass%, Ni 99.99 mass%, and Ge 99.99 mass%.

 $Er_3Ni_{11}Ge_4$ (2) belongs to the Sc₃Ni₁₁Si₄-type family of compounds, a=0.8273, c=0.8680, after Fedyna et al. (1987). For the preparation of the alloy, see $ErNi_5Ge_3$.

Oleksyn and Bodak (1994) used X-ray powder diffraction to investigate the crystal structure of ErNi_3Ge_2 (3) which forms a new structure type, a = 1.79662, c = 0.379410. For alloy synthesis, see Er-Ni-Ge.

The ErNi₂Ge₂ (4) compound was found to adopt the CeGa₂Al₂-type structure, a = 0.4016, c = 0.9733 (Rieger and Parthé 1969b).

ErNiGe₃ (5) with the SmNiGe₃-type structure (a = 0.4013, b = 0.4031, c = 2.1396, X-ray powder diffraction analysis) was reported by Bodak et al. (1985). For the details of sample preparation and purity of starting materials, see SmNiGe₃ under Sm–Ni–Ge.

 Er_2NiGe_6 (6) was found to be isostructural with the Ce_2CuGe_6 -type structure (a = 0.39492, b = 2.1148, c = 0.39957) by Oleksyn (1990) from X-ray powder diffraction. The sample was prepared by arc melting ingots of the constituting elements and annealing the resulting button at 1070 K for 700 h.

The crystal structure of the ErNiGe₂ (7) compound was investigated by Oleksyn (1990) from X-ray powder diffraction of arc melted alloys annealed at 1070 K for 350 h. It was found to adopt a NdIrGe₂-type structure with lattice parameters a=0.4125, b=0.8451, c=1.5792.

Gorelenko et al. (1984) reported the crystal structure of ErNiGe (8) (TiNiSi type, a = 0.6818, b = 0.4188, c = 0.7239; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

 $\text{ErNi}_{0.4}\text{Ge}_{1.6}$ (10) was said to crystallize with the AlB₂ type structure, a = 0.40737, c = 0.39284 (Oleksyn 1990; X-ray powder diffraction).

Pecharsky et al. (1989) investigated the formation and crystal structure of the $\text{ErNi}_{1-x}\text{Ge}_2$ (11) compound by X-ray powder analysis of arc melted alloy annealed at 870 K (CeNiSi₂ type, a=0.3970, b=1.5938, c=0.3980). Francois et al. (1990) confirmed the structure and reported the composition and lattice parameters $\text{ErNi}_{0.65}\text{Ge}_2$, a=0.4068, b=1.612, c=0.3922 (X-ray powder diffraction) from a sample obtained by powder metallurgical reaction at 1173 K. Oleksyn (1990) described the limits of the homogeneity field for the compound with the CeNiSi₂ type structure with the formula $\text{ErNi}_{0.12-0.36}\text{Ge}_{1.88-1.64}$, a=0.4078-0.4052, b=1.621-1.578, c=0.4000-0.3924.

 $Er_3Ni_2Ge_3$ (12) belongs to the $Hf_3Ni_2Si_3$ type, a=0.41435, b=1.0266, c=1.3863 (Oleksyn 1990; X-ray powder diffraction).

Bodak et al. (1982) reported on the crystal structure of the Er₃NiGe₂ (13) compound from X-ray powder diffraction (La₃NiGe₂ type, a = 1.1180, b = 0.4181, c = 1.1124). The proper amounts of starting components were arc melted and annealed at 870 K.

The crystal structures of two ternary compounds have not been evaluated (Oleksyn 1990): $Er_{0.333}Ni_{0.25}Ge_{0.417}$ (9), $Er_{0.48}Ni_{0.10}Ge_{0.42}$ (14).

4.13.6. Er-Cu-Ge

No phase diagram is available for the ternary Er–Cu–Ge system, however five ternary compounds were observed and characterized by different groups of authors.

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented are $ErCu_{0.67}Ge_{1.33}$ with a=0.398, c=0.404. Iandelli (1993) observed ErCuGe with the CaIn₂ type (a=0.4227, c=0.7108, X-ray powder analysis). The alloy was prepared from filings or powders of metals (Er 99.7%, Cu and Ge 99.99%), which were mixed and sealed in a tantalum crucible under argon, melted by induction heating, and annealed for 10 days at 1023 K.

 $Er_6Cu_8Ge_8$ crystallizes with the $Gd_6Cu_8Ge_8$ -type structure, lattice parameters a = 1.3790, b = 0.6617, c = 0.4153 (Rieger 1970).

Konyk et al. (1988) investigated the crystal structure of Er_2CuGe_6 alloy prepared by arc melting under argon and annealing at 870 K in an evacuated quartz tube for 720 h. From X-ray powder analysis the compound was claimed to have the Ce₂CuGe₆-type structure, a=0.3977, b=0.4080, c=2.0837.

Rieger and Parthé (1969b) observed $ErCu_2Ge_2$ with the CeGa₂Al₂-type of structure, a=0.4003, c=1.0317.

Francois et al. (1990) observed the CeNiSi₂ type for the ErCu_{0.39}Ge₂ compound and reported the lattice parameters a = 0.4066, b = 1.602, c = 0.3941 (X-ray powder diffraction) from a sample obtained by a powder metallurgical reaction at 1173 K.

4.13.7. Er-Nb-Ge

The phase diagram of the Er–Nb–Ge system has not been yet established. The existence of the compound $\text{Er}_2\text{Nb}_3\text{Ge}_4$ with the $\text{Ce}_2\text{Sc}_3\text{Si}_4$ -type structure (a=0.6927, b=1.3465, c=0.7116) was reported by Le Bihan et al. (1996a) from X-ray powder diffraction data of an arc melted alloy. The starting materials were: Er and Nb 99.99 mass%, Ge 99.999 mass%.

4.13.8. *Er–Mo–Ge*

No phase diagram is available for the Er–Mo–Ge system; only one compound was observed and characterized. $\text{Er}_2\text{Mo}_3\text{Ge}_4$ was reported to crystallize with the $\text{Ce}_2\text{Sc}_3\text{Si}_4$ -type structure (a=0.6863, b=1.3070, c=0.7028) by Le Bihan et al. (1996b) from X-ray powder diffraction of an arc melted alloy. The starting materials were: Er and Mo 99.99 mass%, Ge 99.999 mass%.

4.13.9. Er–Ru–Ge

Early investigations of the ErRu₂Ge₂ compound determined that it had the CeGa₂Al₂-type structure with a = 0.4211, c = 0.9801 (Francois et al. 1985) from X-ray powder analysis of an alloy obtained by a powder metallurgical reaction at 1273 K. The starting components were Er (3N), Ru (4N), and Ge (4N).
Venturini et al. (1986b) reported the $\text{Er}_2\text{Ru}_3\text{Ge}_5$ compound to crystallize with the U₂Co₃Si₅-type structure, lattice parameters a=0.9752, b=1.240, c=0.5696 (X-ray powder diffraction data). For sample preparation, see La₂Ru₃Ge₅ under La–Ru–Ge.

 $Pr_3Rh_4Sn_{13}$ type was announced for the $Er_3Ru_4Ge_{13}$ compound (a=0.8945) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Er (3N), Ru (3N), and Ge (6N).

4.13.10. Er-Rh-Ge

Venturini et al. (1985b) reported an X-ray powder diffraction study of the $\text{Er}_3\text{Rh}_4\text{Ge}_{13}$ compound from a sample prepared by heating a mixture of the starting components (Er 3N, Rh 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found be of the Yb₃Rh₄Sn₁₃ type, a = 0.8904.

Er₂Rh₃Ge₅ was found to crystallize with Lu₂Co₃Si₅-type (a=0.9933, b=1.2025, c=0.5808, $\beta=92.1^{\circ}$; X-ray powder diffraction data) by Venturini et al. (1986b) from an alloy which was synthesized by a powder metallurgical reaction at 1173 K. The purity of the starting materials was greater than 99.9 mass%.

 $Er_4Rh_7Ge_6$ was reported to adopt $U_4Re_7Si_6$ -type structure (a=0.8296; Francois et al. 1985) from a sample which was obtained by heating a mixture of powders of the starting materials (Er 3N, Rh 4N, Ge 4N) in an evacuated quartz tube at 1273 K.

Gladyshevsky et al. (1991a) reported on the crystal structure of the $\text{Er}_3\text{Rh}_2\text{Ge}_2$ compound (La₃Ni₂Ge₂ type, a = 0.55207, b = 0.7683, c = 1.3138; X-ray powder diffraction data). For the details of sample preparation, see La₃Rh₂Ge₂ under La–Rh–Ge.

Verniere et al. (1995) established that the compound $Er_4Rh_{13}Ge_9$ is of the $Ho_4Ir_{13}Ge_9$ type. No lattice parameters were given. For sample preparation, see $La_4Ir_{13}Ge_9$ under La–Ir–Ge.

 Er_2Rh_3Ge crystallizes with the Y₂Rh₃Ge-type of structure, lattice parameters a = 0.5523, c = 1.1762 (Cenzual et al. 1987). The sample was obtained by arc melting under argon and annealing at 1273 K for 7 days.

Méot-Meyer et al. (1985b) reported the existence of the $Er_5Rh_4Ge_{10}$ compound with $Sc_5Co_4Si_{10}$ -type structure, but no lattice parameters were given.

Francois et al. (1985) determined the CeGa₂Al₂ type for the ErRh₂Ge₂ compound, a=0.4094, c=1.0170.

Hovestreydt et al. (1982) reported the crystal structure of the ErRhGe compound (TiNiSi type, a=0.6827, b=0.4257, c=0.7507; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. The starting components were Er (3N), Rh (4N), and Ge (5N).

4.13.11. *Er–Pd–Ge*

No systematic study of the Er-Pd-Ge system has been performed; the existence of three ternary compounds has been observed by different groups of authors.

Sologub et al. (1995a) reported an X-ray powder analysis of the Er₂PdGe₆ compound which was found to crystallize with the Ce₂CuGe₆-type structure, a=0.40574, b=0.40051, c=2.1402. For the experimental procedure, see La₂PdGe₆ under La-Pd-Ge. The starting materials used were obtained from Johnson & Matthey, UK (99.9%).

The crystal structure of the compound ErPd_2Ge was found to be of the YPd₂Si type (a=0.7296, b=0.7038, c=0.5551; X-ray powder diffraction) by Jorda et al. (1983). For the experimental procedure, see LaPd₂Ge under La-Pd-Ge. The starting materials were Pd 99.99 mass%, Ge specpure quality, and Er 99.9 mass%.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound ErPdGe adopts the KHg₂-type structure, a=0.4348 b=0.6900, c=0.7536. For sample preparation, see LaPdGe under La-Pd-Ge. The starting materials were Er (3N), Pd (4N), and Ge (5N).

4.13.12. Er–Ag–Ge

No ternary phase diagram has been established for the Er–Ag–Ge system, however one ternary compound has been characterized. Gibson et al. (1996) reported an X-ray single-crystal investigation of the ErAgGe compound. It was found to adopt the ZrNiAl type, a = 0.70649, c = 0.41665. The single crystal was isolated from an arc melted sample annealed at 970 K for ten days.

4.13.13. Er-Os-Ge

No phase diagram exists for the ternary Er–Os–Ge system; four ternary compounds have been observed and studied. The $Pr_3Rh_4Sn_{13}$ -type was announced for the $Er_3Os_4Ge_{13}$ compound (a=0.8973) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Er (3N), Os (3N), and Ge (6N).

Méot-Meyer et al. (1985b) observed the existence of the $Er_5Os_4Ge_{10}$ compound with $Sc_5Co_4Si_{10}$ -type structure from X-ray powder diffraction of a sample obtained by heating in an evacuated tube at 1073 K. However, no lattice parameters were reported.

 $Er_4Os_7Ge_6$ was reported to adopt the U₄Re₇Si₆-type structure (a=0.8314; Francois et al. 1985) from a sample obtained by heating a mixture of powders of the starting materials (Er 3N, Os 4N, Ge 4N) in an evacuated quartz tube at 1273 K.

ErOsGe₂ belongs to the TiMnSi₂-type, a=0.957, b=1.055, c=0.829 (Venturini et al. 1985b; X-ray powder diffraction). The alloy was synthesized by a powder metallurgical reaction and annealed at 1073 K.

4.13.14. Er–Ir–Ge

No ternary phase diagram has been established for the Er-Ir-Ge system, however six ternary compounds have been characterized.

Venturini et al. (1985b) reported an X-ray powder diffraction study of the $Er_3Ir_4Ge_{13}$ compound from a sample which was prepared by heating a mixture of the starting

components (Er 3N, Ir 4N, Gea 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to be of the Yb₃Rh₄Sn₁₃ type, a = 0.8923.

Verniere et al. (1995) reported the $Ho_4Ir_{13}Ge_9$ -type structure for the $Er_4Ir_{13}Ge_9$ compound. No lattice parameters were given. For the experimental procedure, see $La_4Ir_{13}Ge_9$ under La–Ir–Ge.

Hovestreydt et al. (1982) reported the crystal structure of the ErIrGe compound (TiNiSi type, a = 0.6766, b = 0.4238, c = 0.7593; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. The starting components were Er (3N), Ir (4N), and Ge (5N).

Francois et al. (1987) reported the crystal structure of ErIrGe₂ (NdIrGe₂ type, a = 0.4227, b = 1.594, c = 0.8783). The sample was prepared by heating a mixture of powders of the starting components (Er 3N, Ir 3N, Ge 3N) in an evacuated silica tube at 1173 K.

Méot-Meyer et al. (1985b) observed the existence of the $Er_5Ir_4Ge_{10}$ compound with $Sc_5Co_4Si_{10}$ type from a sample obtained by heating in an evacuated tube at 1073 K. However, no lattice parameters were given.

 $Er_4Ir_7Ge_6$ was reported to adopt $U_4Re_7Si_6$ -type structure (a=0.8295; Francois et al. 1985) from a sample which was obtained by heating a mixture of powders of the starting materials (Er 3N, Ir 4N, Ge 4N) in an evacuated quartz tube at 1273 K.

4.13.15. Er-Pt-Ge

No phase diagram has been established for the Er-Pt-Ge system. Two ternary compounds were observed by different authors.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound ErPtGe adopts the TiNiSi-type structure, a=0.6917, b=0.4319, c=0.7527. For sample preparation, see LaPdGe under La–Pd–Ge.

Sologub et al. (1995a) reported an X-ray powder analysis of the Er_2PtGe_6 compound which was found to crystallize with the Ce_2CuGe_6 -type structure, a=0.40315, b=0.39977, c=2.1573. For sample preparation, see La_2PdGe_6 under La–Pd–Ge.

4.13.16. Er-Au-Ge

Information on interaction of erbium with gold and germanium is due to Rossi et al. 1992). The phase diagram of the Er–Au–Ge system is not available. A ternary compound of erbium with gold and germanium of the stoichiometric 1:1:1 ratio has been identified and studied by means of X-ray and metallographic analyses by Rossi et al. (1992). ErAuGe was found to adopt the LiGaGe type with lattice parameters a=0.4397, c=0.7203. For the experimental procedure, see GdAuGe under Gd–Au–Ge.

4.14. Tm-d element-Ge systems

4.14.1. *Tm*–*Mn*–*Ge*

No systematic study has been performed for the Tm-Mn-Ge system; however, the formation of two ternary compounds has been reported so far.

TmMn₆Ge₆ was found to crystallize in the HfFe₆Ge₆-type structure by Venturini et al. (1992), a=0.5219, c=0.8139 (X-ray powder diffraction data). The alloy was synthesized by a powder metallurgical reaction in an evacuated silica tube at 1073 K for 14 days.

TmMn_{0.25}Ge₂ compound was found to adopt the CeNiSi₂-type structure with lattice parameters a = 0.4073, b = 1.557, c = 0.3966 by Francois et al. (1990) (X-ray powder diffraction data). For sample preparation, see GdFe_{0.25-0.46}Ge₂ under Gd–Fe–Ge.

4.14.2. Tm-Fe-Ge

The phase diagram of the Tm–Fe–Ge system was investigated by Fedyna (1988) by means of metallographic and X-ray phase analyses (fig. 106). Alloys for investigation were prepared by arc melting followed by annealing at 870 K for 500 hours. The purity of the starting components was greater than 99.9 mass%. Ten ternary compounds were observed.

TmFe₆Ge₆ (1) was reported to be isotypic with the crystal structure of YCo₆Ge₆, lattice parameters a=0.5143, c=0.4098 (Mruz et al. 1984). The sample was prepared by arc melting the proper amounts of the starting components followed by annealing at 870 K for two weeks. At variance with these data, TmFe₆Ge₆ was found to crystallize with the HoFe₆Sn₆-type structure, a=0.8095, b=2.653, c=0.5107, by Venturini et al. (1992) from X-ray powder diffraction data. The alloy was obtained by powder metallurgical reaction in an evacuated silica tube at 1173 K for two weeks. These results suggest that TmFe₆Ge₆ may be polymorphic.

TmFe₄Ge₂ (2) was found to crystallize in the ZrFe₄Si₂-type structure, a = 0.72228, c = 0.37456, by Fedyna (1988) in the course of a phase diagram investigation employing X-ray powder diffraction.

According to X-ray powder diffraction data, TmFe₂Ge₂ (4) is isostructural with



Fig. 106. Tm-Fe-Ge, isothermal section at 870 K.

CeGa₂Al₂, lattice parameters a = 0.39301, c = 1.04184 (Fedyna 1988; X-ray powder diffraction).

Fedyna (1988) investigated the crystal structure of $\text{Tm}_9\text{Fe}_{10}\text{Ge}_{10}$ (8) by a single-crystal method. It was found to crystallize with a new structure type, a=0.5386, b=1.3306, c=1.3913. The single crystal was isolated from an alloy which was arc melted and annealed at 870 K.

Pecharsky et al. (1989) reported $\text{TmFe}_{1-x}\text{Ge}_2$ (9) to crystallize with the CeNiSi₂-type structure (a=0.4061-0.4066, b=1.5532-1.5610, c=0.3959-0.3961; X-ray powder analysis). The alloy was arc melted and annealed at 870 K. The purity of the starting materials was greater than 99.9 mass%. Francois et al. (1990) confirmed the occurrence of the CeNiSi₂ type for thulium-iron-germanium combinations from alloys annealed at 1173 K (TmFe_{0.35}Ge₂; a=0.4082, b=1.558, c=0.3973).

Fedyna (1988) investigated the crystal structure of the $Tm_{117}Fe_{52}Ge_{112}$ (10) compound by X-ray powder diffraction ($Tb_{117}Fe_{52}Ge_{112}$ structure type, a=2.7964). The alloy was synthesized by arc melting and annealing a melted button at 870 K for 350 h. The starting materials were Tm 99.83 mass%, Fe 99.9 mass%, and Ge 99.99 mass%.

Four more ternary compounds with unknown structure were observed by Fedyna (1988) at 870 K: $\sim Tm_{0.20}Fe_{0.53}Ge_{0.27}$ (3), $\sim Tm_{0.225}Fe_{0.55}Ge_{0.225}$ (5), $\sim Tm_{0.275}Fe_{0.375}Ge_{0.35}$ (6) and $\sim Tm_{0.30}Fe_{0.40}Ge_{0.30}$ (7).

4,14.3. *Tm*-*Co*-*Ge*

Isothermal sections of the Tm–Co–Ge system at 870 K (33–100 at.% Tm) and at 1070 K (0–33 at.% Tm) were derived by Fedyna (1988) (fig. 107) employing X-ray phase and



Fig. 107. Tm–Co–Ge, isothermal sections at 1070 K (0–33 at.% Tm) and at 670 K (33–100 at.% Tm).

microstructural analyses of 145 alloys prepared by arc melting the proper amounts of the constituent elements of high purity. The melted buttons were then annealed in evacuated silica tubes for 500 hours. Fifteen ternary compounds were found to exist.

The crystal structure of the TmCo₆Ge₆ (2) compound was reported by Buchholz and Schuster (1981) (YCo₆Ge₆ structure type, a = 0.5098, $c \ 0.3912$). The sample was melted under argon in a corundum crucible at 1073–1273 K.

TmCo₄Ge₂ (4) was found to form the ZrFe₄Si₂-type structure, a = 0.72285, c = 0.37456, by Fedyna (1988) employing X-ray powder diffraction.

Méot-Meyer et al. (1985a) reported the crystal structure of TmCo_xGe_2 (11), x = 0.42 (CeNiSi₂ type, a = 0.4070, b = 1.578, c = 0.3988). The sample was prepared by a powder metallurgical reaction and annealed in an evacuated silica tube at 1173 K. Pecharsky et al. (1989) confirmed the formation and crystal structure of the TmCo_xGe_2 compound from arc melted alloys annealed at 870 K (a = 0.4062 - 0.4079, b = 1.5613 - 1.5760, c = 0.3965 - 0.3977; X-ray powder analysis).

The crystal structure of $Tm_3Co_4Ge_{13}$ (6) (Yb₃Rh₄Sn₁₃ type, a = 0.8715; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample which was prepared by heating a compacted mixture of the starting materials (Tm in pieces, 99.9 mass%; Co and Ge in powder, 99.99 mass%) in an evacuated quartz tube at 1073 K. Bodak et al. (1987) reported the Y₃Co₄Ge₁₃-type structure for the Tm₃Co₄Ge₁₃ compound (a = 0.87156; X-ray powder data) from an arc melted alloy annealed at 870 K.

TmCo₂Ge₂ (7) was found to adopt the CeGa₂Al₂-type structure, a = 0.4259, c = 1.1060 (Fedyna 1988; X-ray powder diffraction).

Tm₂CoGe₆ is isotypic with Ce₂CuGe₆ (9), a=0.3909, b=0.3951, c=2.1252 (Oleksyn et al. 1991; X-ray powder diffraction data). The sample was melted in an arc furnace and annealed at 1070 K in an evacuated quartz capsule for 400 h. The purity of the starting materials was greater than 99.9 mass%.

 $Tm_5Co_4Ge_{10}$ (10) has the $Sc_5Co_4Si_{10}$ -type structure, a=1.2622, c=0.4139, after Venturini et al. (1984).

Gorelenko et al. (1984) reported the crystal structure of TmCoGe (12) (TiNiSi type, a=0.6775, b=0.4168, c=0.7224; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Tm₃Co₂Ge₄ (13) crystallizes with the Tb₃Co₂Ge₄-type structure, a = 1.0410, b = 0.7904, c = 0.4143, $\gamma = 107.04^{\circ}$ (X-ray powder diffraction data; Mruz et al. (1989). The sample was prepared by arc melting and annealing at 873 K for 240 h.

Bodak et al. (1986) reported an X-ray powder investigation of the compound Tm_2CoGe_2 (15): Sc_2CoSi_2 -type structure, a = 1.0326, b = 1.0125, c = 0.4119, $\gamma = 117.00^\circ$.

In the course of phase diagram studies, Fedyna (1988) observed five more ternary compounds with unknown structures: $\sim Tm_{0.03}Co_{0.65}Ge_{0.32}$ (1), $\sim Tm_{0.07}Co_{0.33}Ge_{0.60}$ (3), $\sim Tm_{0.15}Co_{0.30}Ge_{0.55}$ (5), $\sim Tm_{0.20}Co_{0.30}Ge_{0.50}$ (8) and $\sim Tm_{0.33}Co_{0.17}Ge_{0.50}$ (14).

4.14.4. Tm-Ni-Ge

Figure 108 represents the isothermal sections of the Tm–Ni–Ge system at 870 K (0–50 at.% Tm) and at 670 K (50–100 at.% Tm), studied by Fedyna (1988). The isothermal



Fig. 108. Tm-Ni-Ge, isothermal sections at 870 K (0-50 at.% Tm) and at 670 K (50-100 at.% Tm).

sections were constructed by means of X-ray powder and metallographic analyses of 200 alloys which were arc melted, subsequently annealed in evacuated silica tubes for 900 h, and finally quenched in water. The starting materials were Tm 99.82 mass%, Ni 99.98 mass% and Ge 99.99 mass%.

The ternary phase diagram is characterized by the existence of twelve ternary compounds and by the formation of substitutional solid solutions based at Tm_2Ni_{17} (10 at.% Ge) and $TmNi_5$ (15 at.% Ge). The binary compounds Tm_5Ge_3 and $Tm_{11}Ge_{10}$ dissolve 13 and 8 at.% Ni, respectively.

TmNi₅Ge₃ (1) was reported to crystallize with the YNi₅Si₃ type, a=1.90183, b=0.38398, c=0.67867, by Fedyna (1988). The arc melted alloy, annealed at 870 K, was investigated by X-ray powder diffraction analysis. The starting materials were Tm 99.82 mass%, Ni 99.99 mass%, and Ge 99.99 mass%.

Tm₃Ni₁₁Ge₄ (2) belongs to the Sc₃Ni₁₁Si₄-type structure group of compounds, a = 0.8279, c = 0.8690, after Fedyna et al. (1987). The alloy was prepared in the same manner as TmNi₅Ge₃.

The TmNi_{2-1.56}Ge_{2-2.20} (4) compound was found to adopt the CeGa₂Al₂-type structure, a = 0.4003 - 0.3985, c = 0.9724 - 0.9596 (Fedyna 1988).

TmNiGe₃ (5) with the ScNiSi₃-type structure (a=2.1372, b=0.4019, c=0.4003, X-ray powder diffraction analysis) was reported by Bodak et al. (1985). For the details of sample preparation and the purity of the starting materials, see TmNi₅Ge₃.

 Tm_2NiGe_6 (6) has been found by Oleksyn (1990) from X-ray powder diffraction to be isostructural with Ce₂CuGe₆-type structure (a=0.3931, b=2.1031, c=0.3979). The

sample was prepared by arc melting ingots of the constituting elements and annealing at 1070 K for 700 h. For the purity of starting materials, see TmNi₅Ge₃.

Oleksyn (1990) reported the crystal structure of the TmNiGe₂ (7) compound, NdIrGe₂ type, a = 0.4095, b = 0.8405, c = 1.5779, from X-ray powder diffraction analysis. For the experimental procedure, see Tm₂NiGe₆.

Gorelenko et al. (1984) investigated the crystal structure of TmNiGe (9) (TiNiSi type, a=0.6790, b=0.4183, c=0.7235; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours. According to DTA, this phase exhibits polymorphism at 1630 K (Koterlyn et al. 1994).

Tm(Ni_{0.23-0.165}Ge_{0.60-0.665})_{2-x} (11), x=0.34, was said to form an AlB₂ type, a=0.40795-0.40706, c=0.39238-0.40084 (Fedyna 1988; X-ray powder diffraction).

Four more ternary compounds with unknown structures were observed by Fedyna (1988) in the Tm-Ni-Ge system: $\sim Tm_{0.17}Ni_{0.53}Ge_{0.30}$ (3), $\sim Tm_{0.27}Ni_{0.28}Ge_{0.45}$ (8), $\sim Tm_{0.33}Ni_{0.27}Ge_{0.40}$ (10) and $\sim Tm_{0.50}Ni_{0.32}Ge_{0.18}$ (12).

Pecharsky et al. (1989) investigated the formation and crystal structure of the TmNi_{1-x}Ge₂ compound by X-ray powder analysis of arc melted alloy annealed at 870 K (CeNiSi₂ type, a=0.4015-0.4071, b=1.5728-1.6023, c=0.3881-0.3979). For sample preparation, see TmNi₅Ge₃. Francois et al. (1990) confirmed the structure and reported the composition and lattice parameters TmNi_{0.42}Ge₂, a=0.4070, b=1.578, c=0.3988 (X-ray powder diffraction) from a sample obtained by powder metallurgical reaction at 1173 K.

4.14.5. Tm-Cu-Ge

No isothermal section is available for the ternary Tm-Cu-Ge system; however five ternary compounds were observed and characterized by different groups of authors.

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented were TmCu_{1-0.67}Ge_{1-1.33} with a=0.4220-0.397, c=0.3545-0.397. At variance with the data of Rieger and Parthé (1969a), Iandelli (1993) observed TmCuGe with the CaIn₂-type (a=0.4225, c=0.7045, X-ray powder analysis). The alloy was prepared from turnings or powders of metals (thulium 99.7 mass%, copper and germanium 99.99 mass%), which were mixed and sealed in a tantalum crucible under argon, melted by induction heating, and annealed for 10 days at 1023 K.

Tm₆Cu₈Ge₈ crystallizes with the Gd₆Cu₈Ge₈-type structure, lattice parameters a = 1.374, b = 0.660, c = 0.413 (Hanel and Nowotny 1970).

Konyk et al. (1988) investigated the crystal structure of Tm_2CuGe_6 which had been prepared by arc melting the starting components under argon and annealing at 870 K in an evacuated quartz tube for 720 h. From X-ray powder analysis the Ce₂CuGe₆-type structure was claimed for this compound, a=0.4065, b=0.3963, c=2.0767.

Rieger and Parthé (1969b) prepared TmCu₂Ge₂ with the CeGa₂Al₂-type structure, a = 0.3994, c = 1.0307.

Francois et al. (1990) observed the CeNiSi₂-type structure for the TmCu_{0.20}Ge₂ compound and reported the lattice parameters a=0.4055, b=1.585, c=0.3931 (X-ray

powder diffraction) from a sample obtained by a powder metallurgical reaction at 1173 K.

4.14.6. Tm-Nb-Ge

The phase diagram of the Tm–Nb–Ge system has not been established. The existence of the compound $\text{Tm}_2\text{Nb}_3\text{Ge}_4$ with the Ce₂Sc₃Si₄ type (a=0.6917, b=1.3416, c=0.7092) was reported by Le Bihan et al. (1996a) from X-ray powder diffraction data of arc melted alloy. Starting materials were: Tm and Nb 99.99 mass%, Ge 99.999 mass%.

4.14.7. *Tm*–*Mo*–*Ge*

No phase diagram is available for the Tm–Mo–Ge system, and only one compound was observed and investigated. Tm₂Mo₃Ge₄ was reported to crystallize with the Ce₂Sc₃Si₄-type structure (a=0.6840, b=1.3041, c=0.7009) by Le Bihan et al. (1996b) from X-ray powder diffraction of an arc melted alloy. The starting materials were: Tm and Mo 99.99 mass%, Ge 99.999 mass%.

4.14.8. Tm–Ru–Ge

X-ray powder analysis of an alloy with the TmRu₂Ge₂ composition showed that it had the CeGa₂Al₂-type structure with a=0.4202, c=0.9797 (Francois et al. 1985). The sample was obtained by a powder metallurgical reaction at 1273 K. The starting components were Tm (3N), Ru (4N), and Ge (4N).

Venturini et al. (1986b) reported on Tm₂Ru₃Ge₅ crystallizing with the U₂Co₃Si₅ type. Lattice parameters were reported as a=0.9725, b=1.239, c=0.5676 (X-ray powder diffraction data). For sample preparation, see La₂Ru₃Ge₅ under La-Ru-Ge.

Yb₃Rh₄Sn₁₃ type was reported for the Tm₃Ru₄Ge₁₃ compound (a=0.8925) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Tm (3N), Ru (3N), and Ge (6N).

4.14.9. Tm–Rh–Ge

Venturini et al. (1985b) reported an X-ray powder diffraction study of the crystal structure of $Tm_3Rh_4Ge_{13}$ from an alloy which was prepared by heating a mixture of the starting components (Tm 3N, Rh 4N, Ge 4N) in an evacuated quartz tube at 1073 K. It was found to adopt the Yb₃Rh₄Sn₁₃-type structure, a=0.8899.

Francois et al. (1985) determined the CeGa₂Al₂ type for the TmRh₂Ge₂ compound, a=0.4062, c=1.0129.

Tm₂Rh₃Ge₅ was found to crystallize with Lu₂Co₃Si₅-type structure (a=0.9903, b=1.2009, c=0.5781, $\beta=92.4^{\circ}$; X-ray powder diffraction data) by Venturini et al. (1986b) from a sample prepared by a powder metallurgical reaction at 1173 K. The purity of the starting materials was greater than 99.9 mass%.

Gladyshevsky et al. (1991a) reported on the crystal structure of the $Tm_3Rh_2Ge_2$ compound (La₃Ni₂Ge₂ type, a=0.550897, b=0.7654, c=1.3097; X-ray powder diffraction data). For the details of sample preparation, see La₃Rh₂Ge₂ under La–Rh–Ge.

Verniere et al. (1995) observed that the compound $Tm_4Rh_{13}Ge_9$ belonged to the $Ho_4Ir_{13}Ge_9$ -type structure. No lattice parameters were reported. For sample preparation, see $La_4Ir_{13}Ge_9$ under La-Ir-Ge.

Venturini et al. (1984) established the existence of the Tm₅Rh₄Ge₁₀ compound with Sc₅Co₄Si₁₀-type structure, a=1.2868, c=0.4230, from X-ray powder analysis of a sample obtained by heating a mixture of powders in an evacuated tube at 1073 K.

Tm₄Rh₇Ge₆ belongs to the U₄Re₇Si₆-type structure group, a=0.8276 (Francois et al. 1985; X-ray powder diffraction). The alloy was synthesized by heating a mixture of powders of the constituent elements in an evacuated quartz tube at 1273 K. The starting components were Tm (3N), Rh (4N), and Ge (4N).

4.14.10. Tm-Pd-Ge

No systematic study of the Tm-Pd-Ge system has been performed, but the existence of three ternary compounds has been observed by different groups of authors.

Sologub et al. (1995a) reported an X-ray powder analysis of the Tm₂PdGe₆ compound which was found to crystallize with the Ce₂CuGe₆-type structure, a=0.4047, b=0.3995, c=2.1346. For the experimental procedure, see La₂PdGe₆ under La–Pd–Ge. The purity of the starting materials used was 99.9 mass%.

The crystal structure of the compound TmPd_2Ge was found to be of the YPd_2Si type (a=0.7254, b=0.7045, c=0.5523; X-ray powder diffraction) by Jorda et al. (1983). For the experimental procedure, see LaPd₂Ge under La-Pd-Ge. The starting materials were Pd 99.99 mass%, Ge specpure quality, and Tm 99.9 mass%.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound TmPdGe adopts the KHg₂-type structure, a=0.4337, b=0.6855, c=0.7524. For sample preparation, see LaPdGe under La-Pd-Ge. The starting metals were Tm (3N), Pd (4N), and Ge (5N).

4.14.11. Tm-Ag-Ge

No ternary phase diagram has been established for the Tm–Ag–Ge system, however one ternary compound has been characterized. Gibson et al. (1996) reported an X-ray powder investigation of the TmAgGe compound. It was found to adopt the ZrNiAl-type structure, a=0.70415, c=0.41570. The sample was arc melted and annealed at 970 K for ten days.

4.14.12. Tm-Os-Ge

No phase diagram is available for the ternary Tm–Os–Ge system; four ternary compounds have been observed. Tm₄Os₇Ge₆ belongs to the U₄Re₇Si₆-type structure group of compounds, a=0.8297 (Francois et al. 1985; X-ray powder diffraction). The alloy was synthesized by heating a mixture of powders of the constituent elements in an evacuated quartz tube at 1273 K. The starting components were Tm (3N), Os (4N), and Ge (4N).

The $Pr_3Rh_4Sn_{13}$ -type structure was reported for the $Tm_3Os_4Ge_{13}$ compound (a= 0.8955) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Tm (3N), Os (3N), and Ge (6N).

Venturini et al. (1984) observed the existence of the $Tm_5Os_4Ge_{10}$ compound with $Sc_5Co_4Si_{10}$ -type structure, a=1.2929, c=0.4253, from a sample obtained by heating a compacted mixture of powders of the starting metals in an evacuated tube at 1073 K.

TmOsGe₂ is isostructural with TiMnSi₂, a=0.953, b=1.052, c=0.827 (Venturini et al. 1985b; X-ray powder diffraction). The alloy was obtained by a powder metallurgical reaction and annealed at 1073 K.

4.14.13. Tm--Ir-Ge

No ternary phase diagram has been established for the Tm-Ir-Ge system, however five ternary compounds have been characterized.

Méot-Meyer et al. (1985b) observed the existence of the $Tm_5Ir_4Ge_{10}$ compound with $Sc_5Co_4Si_{10}$ -type structure from samples obtained by heating compacted mixtures of the proper amounts of the starting metals in evacuated tubes at 1073 K.

Venturini et al. (1985b) reported an X-ray powder diffraction study of the $Tm_3Ir_4Ge_{13}$ compound from a sample which was prepared in the same way as $Tm_5Ir_4Ge_{10}$. The starting components were Tm (3N), Ir (4N), and Ge (4N). The crystal structure was found to be of the Yb₃Rh₄Sn₁₃ type, a = 0.8912.

Hovestreydt et al. (1982) reported the crystal structure of the TmIrGe compound (TiNiSi type, a=0.6736, b=0.4227, c=0.7591; X-ray powder data) from an arc melted sample annealed at 1270 K for 1–2 weeks. The starting components were Tm (3N), Ir (4N), and Ge (5N).

Verniere et al. (1995) suggested the $Ho_4Ir_{13}Ge_9$ -type structure for the $Tm_4Ir_{13}Ge_9$ compound. No lattice parameters were given. For the experimental procedure, see $La_4Ir_{13}Ge_9$ under La–Ir–Ge.

Tm₄Ir₇Ge₆ was reported to adopt the U₄Re₇Si₆-type structure (a = 0.8273; Francois et al. 1985) from a sample which was obtained by heating a mixture of powders of the starting materials (Tm 3N, Ir 3N, Ge 4N) in an evacuated quartz tube at 1273 K.

4.14.14. Tm-Pt-Ge

No phase diagram has been established for the Tm-Pt-Ge system. Three ternary compounds were observed by different scientific groups.

According to an X-ray powder diffraction analysis reported by Hovestreydt et al. (1982), the compound TmPtGe adopts the TiNiSi-type structure, a=0.6880, b=0.4306, c=0.7517. For sample preparation, see LaPdGe under La–Pd–Ge.

Sologub et al. (1995a) reported an X-ray powder analysis of the Tm₂PtGe₆ compound which was found to crystallize with the Ce₂CuGe₆-type structure, a = 0.4048, b = 0.3993, c = 2.1539. For sample preparation, see La₂PdGe₆ under La–Pd–Ge.

Francois et al. (1987) observed the existence of TmPtGe₂ with the NdIrGe₂-type structure. The lattice parameters were measured as a = 0.4263, b = 1.620, c = 0.8657. The sample was prepared by heating a mixture of powders of the starting components (Tm 3N, Pt 3N, Ge 3N) in an evacuated silica tube at 1173 K.

4.14.15. Tm-Au-Ge

The only information on the interaction of components in the ternary Tm–Au–Ge system is due to Pöttgen et al. (1996a) who observed and characterized the TmAuGe compound. The LiGaGe-type structure was claimed with lattice parameters a=0.43907, c=0.71659 (X-ray single-crystal data). The sample was obtained by melting a mixture of the metals in an arc furnace and annealing at 1070 K for one week.

4.15. Yb-d element-Ge systems

4.15.1. Yb-Mn-Ge

The isothermal section for the Yb–Mn–Ge system at 670 K was established by Dzianii (1995) who employed X-ray powder analysis of 84 samples obtained by arc melting the proper amounts of starting components and annealing at 670 K for twenty days. The phase-field relations are characterized by the existence of three ternary compounds (fig. 109). The solubility of a third component in the binary compounds was found to be negligible.

YbMn₆Ge₆ (1) was found to crystallize with the HfFe₆Ge₆-type structure by Venturini et al. (1992), a=0.5212, c=0.8132 (X-ray powder diffraction data). The alloy was synthesized by powder metallurgical reaction in an evacuated silica tube at 1073 K for 14 days.



Fig. 109. Yb-Mn-Ge, isothermal section at 670 K.

Dzianii (1995) reported on the existence of the YbMn_{0.52}Ge₂ (2) compound: CeNiSi₂ type, a = 0.4071, b = 1.5503, c = 0.3964 (X-ray powder diffraction).

One more ternary compound with an unknown structure was observed by Dzianii (1995) in the course of studying the phase equilibria in the Yb-Mn-Ge system at 670 K; \sim Yb₉Mn₁₀Ge₁₀ (3).

Rossi et al. (1978b) investigated the crystal structure of the YbMn₂Ge₂ compound by X-ray powder diffraction. The CeGa₂Al₂-type structure was announced for this phase with lattice parameters a = 0.4067, c = 1.0871. For sample preparation, see TbMn₂Ge₂ under Tb-Mn-Ge. Apparently this phase does not exist at 670 K.

4.15.2. Yb-Fe-Ge

The phase diagram of the Yb-Fe-Ge system (fig. 110) was investigated by Dzianii (1995) by means of X-ray phase analysis of 90 samples. The alloys for investigation were prepared by arc melting. The samples were homogenized by annealing at 670 K for 480 hours. The purity of the starting components was Yb 99.8 mass%. Fe 99.9 mass%, and Ge 99.99 mass%. Five ternary compounds were observed.

YbFe₆Ge₆ (1) was found to crystallize with the HfFe₆Ge₆-type structure, a = 0.5097, c=0.8092, by Venturini et al. (1992) from X-ray powder diffraction data. The alloy was obtained by a powder metallurgical reaction in an evacuated silica tube at 1173 K for two weeks. At variance with these data, YbFe₆Ge₆ was reported to be isotypic with the crystal structure of YCo₆Ge₆ with lattice parameters a = 0.5098, c = 0.4049 (Dzianii et al. 1995a). The sample was prepared by arc melting the proper amounts of starting components followed by annealing at 670 K for two weeks.

YbFe₄Ge₂ (2) was found to crystallize with the ZrFe₄Si₂ type structure, a=0.72279, c = 0.38764, by Dzianii et al. (1995b). For the experimental procedure, see Yb-Fe-Ge.



Yb2Fe17 Yb6Fe23

Fig. 110. Yb-Fe-Ge, isothermal section at 670 K.

According to X-ray powder diffraction data, YbFe₂Ge₂ (3) is isostructural with the CeGa₂Al₂ type, lattice parameters a=0.3924, c=1.0503 (Rossi et al. 1978a; X-ray powder diffraction).

Dzianii (1995) reported Yb(Fe_{0.43-0.25}Ge_{0.25-0.39})Ge₂ (4) to crystallize with the CeNiSi₂-type structure (a=0.4070, b=1.5475, c=0.3961; X-ray powder analysis).

One more ternary compound with an unknown structure was observed in the course of phase equilibrium studies of the ternary Yb–Fe–Ge system at 670 K by Dzianii (1995) employing X-ray powder diffraction: \sim Yb₉Fe₁₀Ge₁₀ (5).

4.15.3. Yb-Co-Ge

The isothermal section of the Yb–Co–Ge system at 670 K was derived by Dzianii et al. (1995c) (fig. 111) using X-ray analysis of 99 alloys prepared by arc melting the proper amounts of high-purity constituent elements. The melted buttons were then annealed in evacuated silica tubes for 500 hours. Seven ternary compounds were found to exist.

The crystal structure of the YbCo₆Ge₆ (1) compound was reported by Buchholz and Schuster (1981): YCo₆Ge₆ structure type, a=0.5078, c=0.3910. The sample was melted under argon in a corundum crucible at 1073–1273 K.

YbCo₄Ge₂ (2) was found to adopt the ZrFe₄Si₂-type structure, a=0.7236, c=0.3716, by Fedyna (1988) employing X-ray powder diffraction method. For sample preparation, see Pr-Fe-Ge.

The crystal structure of the Yb₃Co₄Ge₁₃ (3) compound (Yb₃Rh₄Sn₁₃ type, a=0.8705; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample which was prepared by heating a compacted mixture of the starting materials (Yb in pieces, 99.9 mass%; Co and Ge in powder, 99.99 mass%) in an evacuated quartz tube



Fig. 111. Yb–Co–Ge, isothermal section at 670 K.

at 1073 K. Bodak et al. (1987) reported the $Y_3Co_4Ge_{13}$ -type structure for the $Yb_3Co_4Ge_{13}$ compound (a = 0.8725; X-ray powder data) from an arc melted alloy annealed at 870 K.

YbCo₂Ge₂ (4) was found to adopt the CeGa₂Al₂-type structure, a = 0.3996, c = 1.0123 (Dzianii 1995; X-ray powder diffraction).

Méot-Meyer et al. (1985a) reported the crystal structure of YbCo_xGe₂ (5), x=0.37 (CeNiSi₂ type, a=0.4077, b=1.563, c=0.3967). The sample was prepared by a powder metallurgical reaction and annealed in an evacuated silica tube at 1173 K. Pecharsky et al. (1989) confirmed the formation and crystal structure of the YbCo_xGe₂ compound from arc melted alloys annealed at 870 K (a=0.4045, b=1.5512, c=0.3948; X-ray powder analysis).

In the course of phase diagram studies, two more ternary compounds with unknown structures were observed by Dzianii (1995): ~YbCoGe (6) and ~Yb₂CoGe₂ (7).

Yb₅Co₄Ge₁₀ was observed to crystallize with the Sc₅Co₄Si₁₀-type structure by Méot-Meyer et al. (1985b). For experimental details, see YbCo_xGe₂ under Yb–Co–Ge. Apparently this phase does not exist at 670 K.

4.15.4. Yb–Ni–Ge

Figure 112 represents the isothermal section of the Yb–Ni–Ge system at 670 K, studied by Dzianii (1995). The isothermal section was constructed by means of X-ray powder analysis of 110 alloys which were arc melted and subsequently annealed in evacuated silica tubes for 480 h and finally quenched in water. The starting materials were Yb 99.8 mass%, Ni 99.9 mass%, and Ge 99.99 mass%.



Fig. 112. Yb–Ni–Ge, isothermal section at 670 K.

The ternary phase diagram is characterized by the existence of twelve ternary compounds and by the formation of substitutional solid solutions based at Tm_2Ni_{17} and $TmNi_5$, which dissolve 15 at.% Ge.

YbNi₅Ge₃ (1) was reported to crystallize with the YNi₅Si₃- type structure, a = 1.8892, b = 0.3830, c = 0.6779, by Fedyna et al. (1987). The arc melted alloy, annealed at 870 K, was investigated by X-ray powder diffraction analysis. The starting materials were Yb 99.8 mass%, Ni 99.99 mass%, and Ge 99.99 mass%.

Yb₃Ni₁₁Ge₄ (2) belongs to the Sc₃Ni₁₁Si₄-type structure group, a = 0.8259, c = 0.8648, after Fedyna et al. (1987). The alloy was prepared in the same manner as TmNi₅Ge₃.

The YbNi₂Ge₂ (4) compound was found to adopt the CeGa₂Al₂-type structure, a = 0.4001, c = 0.9733 (Rieger and Parthé 1969b).

YbNiGe₃ (5) with the ScNiSi₃-type structure (a=0.4067, b=2.1548, c=0.4067, X-ray powder diffraction analysis) was reported by Dzianii (1995). For the details of sample preparation and the purity of starting materials, see Yb–Ni–Ge.

Yb₂NiGe₆ (6) has been found by Dzianii (1995) from X-ray powder diffraction to be isostructural with Ce₂CuGe₆ (a=0.3948, b 2.100, c=0.3960). The sample was prepared by arc melting ingots of the constituting elements and annealing the resulting button at 670 K for 480 h. For the purity of starting materials, see Yb–Ni–Ge.

Gorelenko et al. (1984) investigated the crystal structure of YbNiGe (9) (TiNiSi type, a=0.6740, b=0.4162, c=0.7217; X-ray powder analysis). The proper amounts of starting materials were arc melted, and the resulting alloy was annealed in an evacuated quartz tube at 870 K for 350 hours.

YbNi_{0.6}Ge_{1.4} (12) was said to adopt the AlB₂-type structure, a=0.4193, c=0.3965 (Contardi et al. 1977; X-ray powder diffraction). Dzianii (1995) observed a homogeneity field for the compound with AlB₂ structure and obtained significantly different lattice parameters: Yb₂(Ni, Ge)₃, a=0.3405-0.3764, c=0.3942-0.4009 (X-ray powder diffraction).

Five more ternary compounds with unknown structure were observed by Dzianii (1995) in the Yb–Ni–Ge system: \sim Yb_{0.17}Ni_{0.53}Ge_{0.30} (3), \sim Yb_{0.25}Ni_{0.25}Ge_{0.50} (7), \sim Yb_{0.27}Ni_{0.28}Ge_{0.45} (8), \sim Yb_{0.33}Ni_{0.27}Ge_{0.40} (10), \sim Yb_{0.33}Ni_{0.17}Ge_{0.50} (11).

4.15.5. Yb--Cu-Ge

The isothermal section for the ternary Yb–Cu–Ge system over the whole concentration region (fig. 113) was established by Salamakha et al. (1996a). Four ternary compounds were observed and characterized by employing X-ray powder analysis of arc melted alloys annealed at 670 K. The starting materials were used in the form of ingots of high-purity elements: Yb 99.9 mass%, Cu 99.99 mass%, and Ge 99.999 mass%.

Iandelli (1993) observed YbCuGe (4) with the CaIn₂-type structure (a=0.4213, c=0.7036, X-ray powder analysis). The alloy was prepared from filings or powders of the metals (Yb 99.7 mass%, Cu and and Ge 99.99 mass%), which were mixed, sealed in a tantalum crucible under argon, melted by induction heating, and annealed for 10 days at



Fig. 113. Yb-Cu-Ge, isothermal section at 670 K.

1023 K. The crystal structure of this compound was confirmed by Dzianii et al. (1995d), a=0.4186, c=0.6988. For the experimental details, see the preceding paragraph.

Yb₆Cu₈Ge₈ (3) crystallizes with the Gd₆Cu₈Ge₈-type structure, lattice parameters a=1.371, b=0.659, c=0.413 (Hanel and Nowotny 1970). The crystal structure was confirmed for the Yb₆Cu₈Ge₈ compound by Dzianii (1995) from X-ray powder diffraction data, a=1.414, b=0.6637, c=0.4201.

Konyk et al. (1988) investigated the crystal structure of Yb₂CuGe₆ (2), which was prepared by arc melting under argon and annealing at 870 K in an evacuated quartz tube for 720 h. From X-ray powder analysis, the Ce₂CuGe₆-type structure was claimed, a = 0.3994, b = 0.4082, c = 2.1018.

Rieger and Parthé (1969b) prepared YbCu₂Ge₂ (1) with the CeGa₂Al₂-type structure, a=0.4045, c=1.0228.

4.15.6. Yb-Nb-Ge

The phase diagram of the Yb–Nb–Ge system has not been established yet. However, the existence of a compound Yb₂Nb₃Ge₄ with the Ce₂Sc₃Si₄-type structure (a=0.6937, b=1.3449, c=0.7109) was reported by Le Bihan et al. (1996a) from X-ray powder diffraction data of an arc melted alloy. The starting materials were: Yb and Nb 99.99 mass%, Ge 99.999 mass%.

4.15.7. Yb-Ru-Ge

X-ray powder analysis of an alloy of the YbRu₂Ge₂ composition indicated that it had the CeGa₂Al₂-type structure with a=0.4203, c=0.9763 (Francois et al. 1985). The sample

was obtained by a powder metallurgical reaction at 1273 K. The starting components were Yb (3N), Ru (4N), and Ge (4N).

Yb₃Rh₄Sn₁₃-type structure was reported for the Yb₃Ru₄Ge₁₃ compound (a=0.8911) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days. The starting materials were Yb (3N), Ru (3N), and Ge (6N).

4.15.8. Yb-Rh-Ge

Venturini et al. (1985b) reported an X-ray powder diffraction study of the Yb₃Rh₄Ge₁₃ compound from a sample which was prepared by heating a mixture of the starting components (Yb 3N, Rh 4N, Ge 4N) in an evacuated quartz tube at 1073 K. The crystal structure was found to be of the Yb₃Rh₄Sn₁₃ type, a=0.8941.

Francois et al. (1985) determined the CeGa₂Al₂-type structure for the YbRh₂Ge₂ compound, a = 0.4062, c = 1.0065.

Venturini et al. (1984) established the existence of the Yb₅Rh₄Ge₁₀ compound with Sc₅Co₄Si₁₀-type structure and lattice parameters a = 1.2886, c = 0.4234 from X-ray powder analysis of a sample obtained by heating a mixture of powders in an evacuated tube at 1073 K.

Yb₄Rh₇Ge₆ belongs to the U₄Re₇Si₆-type structure family, a=0.8254, according to Francois et al. 1985 (X-ray powder diffraction). The alloy was synthesized by heating a mixture of powders of the constituent elements in an evacuated quartz tube at 1273 K. Starting components were Yb (3N), Rh (4N), and Ge (4N).

4.15.9. Yb-Pd-Ge

A systematic study of the Yb–Pd–Ge system (fig. 114) has been performed by Seropegin et al. (1994) employing X-ray phase analysis, microstructural and local X-ray spectral analyses of 152 samples which were arc melted and annealed at 870 K for 600 h. The existence of one ternary compound was confirmed and formation of nine other ternary phases was observed for the first time. The purity of the metals used for the synthesis of the alloys was Yb 99.98 mass%, Pd and Ge 99.99 mass%.

According to X-ray powder diffraction analysis, YbPd₂Ge₂ (3) was reported to adopt the CeGa₂Al₂-type structure, a = 0.4287, c = 1.0020 (Rossi et al. 1979). Seropegin et al. (1994) confirmed the existence and structure of this compound with a = 0.42841, c = 1.0001.

Seropegin et al. (1994) reported an X-ray powder analysis of the Yb₂PdGe₆ (4) compound which was found to crystallize with the Ce₂CuGe₆-type structure, a = 0.3974, b = 2.1834, c = 0.40689. For the experimental procedure, see the Yb–Pd–Ge isothermal section. Sologub et al. (1995a) confirmed the formation of Yb₂PdGe₆ with the Ce₂CuGe₆-type structure and obtained a = 0.40755, b = 0.39934, c = 2.1851. For the experimental procedure, see La₂PdGe₆ under La–Pd–Ge. The starting materials used were of purity 99.9 mass%.



Fig. 114. Yb-Pd-Ge, isothermal section at 870 K.

In the course of the phase equilibria investigation, three more compounds were observed and characterized: YbPdGe₂ (5), NdIrGe₂ type, a = 0.4336, b = 0.8626, c = 1.6071 (X-ray powder diffraction); YbPd_{0.5-0.62}Ge_{1.5-1.38} (7), AlB₂ type, a = 0.42276-0.42263, c = 0.40686-0.40649 (X-ray powder diffraction); YbPdGe (9), KHg₂ type, a = 0.4344, b = 0.6839, c = 0.7522 (X-ray powder diffraction).

The crystal structures of the compounds \sim Yb₁₀Pd₇₅Ge₁₅ (1) (Seropegin et al. 1994), \sim Yb₂₀Pd₂₀Ge₆₀ (2) (Seropegin et al. 1994), \sim YbPd₂Ge (6) (Jorda et al. 1983), \sim Yb_{33.3}Pd₂₈Ge_{38.7} (8) (Seropegin et al. 1994) and \sim Yb₄₂Pd₁₃Ge₄₅ (10) (Seropegin et al. 1994) have not been determined.

4.15.10. Yb-Ag-Ge

No ternary phase diagram has been established for the Yb–Ag–Ge system, however one ternary compound has been characterized. Gibson et al. (1996) reported an X-ray powder investigation of the YbAgGe compound. It was found to adopt the ZrNiAl-type structure, a = 0.70524, c = 0.41387. The sample was arc melted and annealed at 970 K for ten days.

4.15.11. Yb-Os-Ge

No phase diagram is available for the ternary Yb-Os-Ge system, but two ternary compounds have been observed.

Yb₄Os₇Ge₆ belongs to the U₄Re₇Si₆-type structure family, a=0.8288 (Francois et al. 1985; X-ray powder diffraction). The alloy was synthesized by heating a mixture of powders of the constituent elements in an evacuated quartz tube at 1273 K. The starting components were Yb (3N), Os (4N), and Ge (4N).

The $Pr_3Rh_4Sn_{13}$ -type structure was announced for the $Yb_3Os_4Ge_{13}$ compound (a = 0.8941) by Segre et al. (1981a) from X-ray powder analysis of an arc melted sample annealed at 1523 K for 1 day and at 1273 K for 7 days sample. The starting materials were Yb (3N), Os (3N), and Ge (6N).

4.15.12. Yb–Ir–Ge

No ternary phase diagram has been established for the Yb–Ir–Ge system, however three ternary compounds have been characterized.

Méot-Meyer et al. (1985b) observed the $Yb_5Ir_4Ge_{10}$ compound with $Sc_5Co_4Si_{10}$ -type structure from a sample which was obtained by heating a compacted mixture of powders in evacuated tube at 1073 K. No lattice parameters were given.

Venturini et al. (1985b) reported an X-ray powder diffraction study of the Yb₃Ir₄Ge₁₃ compound from a sample which was prepared from the pure components (Yb 3N, Ir 4N, Ge 4N) by a powder metallurgical reaction at 1073 K. The crystal structure was found to be of the Yb₃Rh₄Sn₁₃ type, a=0.8936.

Yb₄Ir₇Ge₆ was reported to adopt U₄Re₇Si₆-type structure (a=0.8262; Francois et al. 1985) from a sample which was obtained by heating a mixture of powders of the starting materials (Yb 3N, Ir 4N, Ge 4N) in an evacuated quartz tube at 1273 K.

4.15.13. *Yb–Pt–Ge*

A systematic study of the Yb–Pt–Ge system (fig. 115) has been performed by Borisenko (1993) employing X-ray phase analysis as well as microstructural and local X-ray spectral analyses of 72 samples which were arc melted and annealed at 870K for 600h. The



Fig. 115. Yb-Pt-Ge, isothermal section at 870 K.

existence of three ternary compounds was observed. The purity of the metals used for the synthesis of the alloys was Yb 99.98 mass%, Pt and Ge 99.99 mass%.

Borisenko (1993) reported an X-ray powder analysis of the Yb₂PtGe₆ (1) compound which was found to crystallize with the Ce₂CuGe₆-type structure, a=0.3949, b=2.186, c=0.4091. For the experimental procedure, see the preceding paragraph. Sologub et al. (1995a) confirmed the formation of Yb₂PtGe₆ with the Ce₂CuGe₆-type structure and obtained a=0.40482, b=0.39771, c=2.1940. For the experimental procedure, see La₂PdGe₆ under La–Pd–Ge. The purity of the starting materials used was 99.9 mass%.

In the course of phase equilibrium studies, two more compounds were observed and characterized by X-ray powder diffraction: YbPtGe₂ (2), NdIrGe₂ type, a=0.4337, b=0.8734, c=1.6134; and YbPtGe (3), TiNiSi type, a=0.6897, b=0.4325, c=0.7542.

4.15.14. Yb-Au-Ge

Only one report exists on the interaction of components in the ternary Yb–Au–Ge system: Rossi et al. (1992) observed and characterized the YbAuGe compound as having the LiGaGe-type structure with lattice parameters a=0.4475, c=0.7163 (X-ray powder diffraction). The sample was obtained by melting the metals in an induction furnace and annealing at 1070 K for one week. The metals used had a purity of around 99.9 mass.% for Yb and 99.99 mass.% for Au and Ge.

4.16. Lu–d element–Ge systems

4.16.1. Lu-Mn-Ge

No ternary phase diagram for the Lu–Mn–Ge system is available. Three ternary compounds have been reported for various luthetium–manganese–germanium combinations.

LuMn₆Ge₆ was found to crystallize in the HfFe₆Ge₆-type structure by Venturini et al. (1992), a=0.5211, c=0.8134 (X-ray powder diffraction data). The alloy was synthesized by a powder metallurgical reaction in an evacuated silica tube at 1073 K for 14 days.

LuMn_{0.27-0.12}Ge₂ was found by Francois et al. (1990) to adopt the CeNiSi₂-type structure with lattice parameters a=0.4053-0.4028, b=1.543-1.558, c=0.3956-0.3897 (X-ray powder diffraction data). For sample preparation, see GdFe_{0.25-0.46}Ge₂ under Gd–Fe–Ge.

Meyer et al. (1983) investigated the crystal structure of the LuMnGe₂ compound, and found it had a new structure type, a=0.5466, b=1.8519, c=0.8173 (X-ray single-crystal method) from an alloy obtained by heating the proper amounts of the metals in a quartz tube under argon and annealing at 1173 K.

4.16.2. Lu-Fe-Ge

No phase diagram has been constructed for the Lu–Fe–Ge system; six ternary compounds have been found and characterized by different groups of authors.

LuFe₆Ge₆ was reported to be isotypic with YCo₆Ge₆, lattice parameters a = 0.5087, c = 0.4034 (Mruz et al. 1984). The sample was prepared by arc melting the proper amounts

of the starting components followed by annealing at 870 K for two weeks. At variance with these data, LuFe₆Ge₆ was found to crystallize with the HfFe₆Ge₆-type structure, a=0.5096, c=0.8081, by Venturini et al. (1992) from X-ray powder diffraction data. The alloy was obtained by a powder metallurgical reaction in an evacuated silica tube at 1173 K for two weeks.

Pecharsky et al. (1989) reported LuFe_xGe₂ to crystallize with the CeNiSi₂-type structure (a = 0.4042, b = 1.5431, c = 0.3947; X-ray powder analysis). The alloy was arc melted and annealed at 870 K. The purity of the starting materials was greater than 99.9 mass%. Francois et al. (1990) confirmed the structure of this compound and established the composition as LuFe_{0.33-0.11}Ge₂, a = 0.4121, b = 1.581, c = 0.4011 (X-ray powder diffraction data). For sample preparation, see GdFe_{0.25-0.46}Ge₂ under Gd–Fe–Ge.

LuFe₄Ge₂ is isotypic with ZrFe₄Si₂, lattice parameters a = 0.7200, c = 0.3854, after Fedyna (1988). The alloy was prepared by arc melting the proper amounts of the starting components followed by annealing at 870 K for 400 hours.

Oleksyn (1990) investigated the crystal structure of the Lu₁₁₇Fe₅₂Ge₁₁₂ compound by the X-ray powder method (Tb₁₁₇Fe₅₂Ge₁₁₂ type, a=2.792). The alloy was synthesized by arc melting and annealing at 1070 K for 350 h. The starting materials were Lu 99.83 mass%, Fe 99.9 mass%, and Ge 99.99 mass%.

Lu₆Fe₈Ge₈ belongs to the Gd₆Cu₈Ge₈-type structure family, a = 1.3280, b = 0.6805, c = 0.4038 (X-ray powder diffraction; Fedyna et al. 1994).

Fedyna and Zavodnik (1988) reported a single-crystal investigation of the Lu₃Fe₂Ge₃ compound, showing that it had the Hf₃Ni₂Si₃-type structure, a=0.41272, b=1.047, c=1.3611. The single crystal was isolated from an arc melted alloy.

4.16.3. Lu-Co-Ge

The phase diagram of the Lu–Co–Ge system has not yet been established; seven ternary compounds have been identified and characterized for various lutetium–cobalt–germanium combinations.

Méot-Meyer et al. (1985a) reported that $LuCo_{1-x}Ge_2$, x=0.34, has the CeNiSi₂-type structure with a=0.4038, b=1.554, c=0.3939. The sample was prepared by a powder metallurgical reaction and annealed in an evacuated silica tube at 1173 K. Pecharsky et al. (1989) also investigated the formation and crystal structure of the $LuCo_{1-x}Ge_2$ compound by X-ray powder analysis of an arc melted alloy annealed at 870 K: CeNiSi₂ type, a=0.4038-0.4040, b=1.5512-1.5551, c=0.3948-0.3949).

The crystal structure of Lu₃Co₄Ge₁₃ (Yb₃Rh₄Sn₁₃ type, a=0.8700; X-ray powder diffraction) was investigated by Venturini et al. (1985b) from a sample which was prepared by heating a compacted mixture of the starting materials (Lu in pieces, 99.9 mass%; Co and Ge in powder, 99.99 mass%) in an evacuated quartz tube at 1073 K. Bodak et al. (1987) reported the Y₃Co₄Ge₁₃ type for the Lu₃Co₄Ge₁₃ compound (a=0.8694; X-ray powder data) from an arc melted alloy annealed at 870 K.

Gorelenko et al. (1984) reported the crystal structure of LuCoGe (TiNiSi type, a = 0.6720, b = 0.4140, c = 0.7226; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours.

Lu₂CoGe₆ is isotypic with Ce₂CuGe₆, a = 0.3904, b = 0.3936, c = 2.1192 (Oleksyn et al. 1991; X-ray powder diffraction data). The sample was melted in an arc furnace and annealed at 1070 K in evacuated quartz capsule for 400 h. The purity of the starting materials was greater than 99.9 mass%.

Koterlyn (1996) investigated the crystal structure of the LuCo_{3.8}Ge_{1.2} compound which belongs to the CaCu₅-type structure, a = 0.48823, c = 0.40301 (X-ray powder diffraction).

Bodak et al. (1986) reported the crystal structure for Lu₂CoGe₂ (Sc₂CoSi₂ type, a = 1.0234, b = 1.0049, c = 0.4109, $\gamma = 117.31^{\circ}$; X-ray powder diffraction) from an arc melted sample annealed at 870 K.

LuCo₄Ge₂ is isotypic with ZrFe₄Si₂, lattice parameters a = 0.7199, c = 0.3735, after Fedyna (1988). The alloy was prepared by arc melting the proper amounts of the starting components and annealing at 870 K for 400 hours.

4.16.4. *Lu–Ni–Ge*

No isothermal section for the Lu-Ni-Ge system is available; eight ternary compounds were observed and characterized by different groups of authors.

LuNi₅Ge₃ was reported to crystallize with the YNi₅Si₃-type structure, a = 1.8973, b = 0.3826, c = 0.6775, by Fedyna et al. (1987). An arc melted alloy, annealed at 870 K, was investigated by X-ray powder diffraction analysis. The starting materials were Lu 99.83 mass%, Ni 99.99 mass%, and Ge 99.99 mass%.

Lu₃Ni₁₁Ge₄ belongs to the Sc₃Ni₁₁Si₃-type structure, a=0.8249, c=0.8641, after Fedyna et al. (1987). For sample preparation, see the preceding paragraph.

The LuNi₂Ge₂ compound was found to adopt the CeGa₂Al₂-type structure, a = 0.39975, c = 0.97538 (Bodak and Koterlyn 1995).

LuNiGe₃ with the SmNiGe₃-type structure (a=2.1305, b=0.3932, c=0.3982, X-ray powder diffraction analysis) was reported by Bodak et al. (1985). For the details of sample preparation and the purity of the starting materials, see LuNi₅Ge₃.

Lu₂NiGe₆ has been found by Oleksyn (1990) from X-ray powder diffraction to be isostructural with Ce₂CuGe₆ (a = 0.3908, b = 0.4007, c = 2.1265). The sample was prepared by arc melting ingots of the constituting elements and annealing at 1070 K for 700 h. For the purity of starting materials, see LuNi₅Ge₃.

Pecharsky et al. (1989) investigated the formation and crystal structure of the LuNi_{1-x}Ge₂ compound by X-ray powder analysis of an arc melted alloy annealed at 870 K (CeNiSi₂ type, a=0.3993-0.4045, b=1.5566-1.5690, c=0.3852-0.3929). For sample preparation, see LuFe_{1-x}Ge₂ under Lu–Fe–Ge. Francois et al. (1990) confirmed the structure and reported the composition and lattice parameters LuNi_{0.48-0.19}Ge₂, a=0.4037-0.4015, b=1.535-1.558, c=0.3945-0.3898 (X-ray powder diffraction) from a sample obtained by a powder metallurgical reaction at 1173 K.

Gorelenko et al. (1984) reported the crystal structure of LuNiGe (TiNiSi type, a = 0.6727, b = 0.4147, c = 0.7229; X-ray powder analysis). The alloy was obtained by arc melting and annealing in an evacuated quartz tube at 870 K for 350 hours. Koterlyn et al. (1994) investigated a single crystal which was extracted from an arc melted LuNiGe alloy. A new structure type was observed, a = 0.4116, b = 0.9194, c = 2.2334. According to DTA, this phase exists above 1570 K.

Oleksyn (1990) reported on the crystal structure of LuNiGe₂ from X-ray powder diffraction (NdIrGe₂ type, a = 0.4082, b = 0.8893, c = 1.5795). The proper amounts of the starting components were arc melted and annealed at 1070 K.

4.16.5. Lu-Cu-Ge

No isothermal section is available for the Lu–Cu–Ge system; four ternary compounds have been found and analyzed by various groups of authors.

Rieger and Parthé (1969a) investigated the occurrence of the AlB₂-type structure by means of X-ray powder diffraction of arc melted alloys. The data presented indicated a compound of LuCu_{0.67}Ge_{1.33} stoichiometry with a = 0.383, c = 0.405.

Iandelli (1993) observed LuCuGe with the CaIn₂ type (a=0.4212, c=0.6962, X-ray powder analysis). The alloy was prepared from turnings or powders of the metals (lutetium 99.7 mass%, copper and germanium 99.99 mass%), which were mixed and sealed in a tantalum crucible under argon, melted by induction heating, and annealed for 10 days at 1023 K.

Lu₆Cu₈Ge₈ crystallizes with the Gd₆Cu₈Ge₈-type structure, lattice parameters a = 1.3661, b = 0.6581, c = 0.4113 (Rieger 1970).

Francois et al. (1990) observed the CeNiSi₂-type structure for the LuCu_{0.14}Ge₂ compound and reported lattice parameters a = 0.4029, b = 1.567, c = 0.3903 (X-ray powder diffraction) from a sample obtained by a powder metallurgical reaction at 1173 K.

4.16.6. *Lu–Nb–Ge*

The phase diagram of the Lu–Nb–Ge system has not been established yet. The existence of the compound Lu₂Nb₃Ge₄ with the Ce₂Sc₃Si₄-type structure (a=0.6895, b=1.3392, c=0.7071) was reported by Le Bihan et al. (1996a) from X-ray powder diffraction data of an arc melted alloy. The starting materials were: Lu and Nb 99.99 mass%, Ge 99.999 mass%.

4.16.7. Lu-Mo-Ge

The existence of Lu₂Mo₃Ge₄ with the Ce₂Sc₃Si₄-type structure (a = 0.6789, b = 1.3012, c = 0.6990) was reported by Le Bihan et al. (1996b). For sample preparation and purity of starting materials, see Lu–Nb–Ge.

Compound	Structure	Lattice	paramet	ers (nm)	Reference		
		a	b	с	-		
Lu ₄ Ru ₇ Ge ₆	U ₄ Re ₇ Si ₆	0.8256		0.9856	Francois et al. (1985)		
LuRu _{0.25} Ge ₂	CeNiSi ₂	0.4076	1.549	0.3980	Francois et al. (1990)		
LuRuGe ₂	TiMnSi ₂	0.953	1.049	0.823	Venturini et al. (1985a)		
Lu ₃ Ru ₄ Ge ₁₃	$Yb_3Rh_4Sn_{13}$	0.8911			Segre et al. (1981a)		
Lu ₅ Rh ₄ Ge ₁₀	$Sc_5Co_4Si_{10}$				Méot-Meyer et al. (1985b)		
Lu ₃ Rh ₂ Ge ₂	La ₃ Ni ₂ Ga ₂	0.54917	0.7593	1.3051	Gladyshevsky et al. (1991a)		
Lu ₄ Rh ₇ Ge ₆	$U_4 Re_7 Si_6$	0.8243			Francois et al. (1985)		
Lu ₃ Rh ₄ Ge ₁₃	$Yb_3Rh_4Sn_{13}$	0.8900			Venturini et al. (1985b)		
Lu ₄ Rh ₁₃ Ge ₉	Ho ₄ Ir ₁₃ Ge ₉				Verniere et al. (1995)		
LuRh ₀₂₃ Ge ₂	CeNiSi ₂	0.4054	1.555	0.3962	Francois et al. (1990)		
LuPd ₂ Ge	YPd ₂ Si	0.7189	0.7049	0.5512	Jorda et al. (1983)		
$LuPd_{0.16}Ge_2$	CeNiSi ₂	0.4059	1.561	0.3934	Francois et al. (1990)		

Table 29 Crystallographic data for the ternary Lu-Ru(Rh, Pd)-Ge compounds

4.16.8. Lu-Ru(Rh, Pd)-Ge

The ternary Lu-Ru(Rh, Pd)-Ge systems have been studied only with respect to the formation of compounds with specific compositions and structures. Their crystallographic characteristics are listed in table 29.

4.16.9. Lu-Ag-Ge

Protsyk (1994) constructed the equilibrium phase diagram for the Lu–Ag–Ge system at 770K (fig. 116) by means of X-ray powder phase analysis of 65 alloys. The samples



Fig. 116. Lu-Ag-Ge, isothermal section at 770 K.

were arc melted and annealed for 500 h. Two ternary compounds were observed. LuAg₂ dissolves 20 at.% Ge.

The crystal structure of the LuAgGe (1) compound was investigated by Protsyk (1994) by X-ray powder diffraction method. It was found to adopt the ZrNiAl-type structure with lattice parameters a = 0.7006, c = 0.4129. The crystal structure was confirmed by Gibson et al. (1996), with lattice parameters a = 0.71025, c = 0.41337 (X-ray powder diffraction).

The crystal structure of $\sim Lu_5(Ag,Ge)_4$ (2) was not resolved (Protsyk 1994).

4.16.10. Lu-Re-Ge

The only information on the system Lu-Re-Ge is due to Francois et al. (1990) who investigated the occurrence of the compound with a CeNiSi₂ type; no phase diagram is available.

LuRe_{0.12}Ge₂ was found by Francois et al. (1990) to crystallize with the CeNiSi₂type structure with lattice parameters a=0.4085, b=1.551, c=0.3991 (X-ray powder diffraction data). The alloy was prepared from a mixture of the proper amounts of the components with purity of 99.9 mass% by a metallurgical reaction in a quartz tube at 1173 K.

4.16.11. Lu–Os(Ir)–Ge

The ternary Lu–Os(Ir)–Ge systems have been studied only with respect to the formation of compounds with specific compositions and structures. Their crystallographic characteristics are listed in table 30.

Compound	Crystallographic data for Structure	the ternary Lattice	Lu–Os(I	r, Pt)–Ge c ters (nm)	compounds Reference
		a	b	с	-
LuOsGe ₂	TiMnSi ₂	0.951	1.048	0.827	Venturini et al. (1985a)
Lu ₃ Os ₄ Ge ₁₃	Yb ₃ Rh ₄ Sn ₁₃	0.8941			Segre et al. (1981a)
Lu ₄ Os ₇ Ge ₆	$U_4 Re_7 Si_6$	0.8276			Francois et al. (1985)
Lu ₄ Ir ₇ Ge ₆	$U_4 Re_7 Si_6$	0.8258			Francois et al. (1985)
$Lu_5Ir_4Ge_{10}$	$Sc_5Co_4Si_{10}$				Méot-Meyer et al. (1985b)
Lu ₃ Ir ₄ Ge ₁₃	$Yb_3Rh_4Sn_{13}\\$	0.8898			Venturini et al. (1985b)

Table 20

4.16.12. Lu-Au-Ge

No ternary phase diagram exists for the Lu-Au-Ge system, however, a ternary compound of luthetium with gold and germanium in the stoichiometric ratio 1:1:1 has been identified and studied by means of X-ray analysis by Pöttgen et al. (1996a). LuAuGe was found to adopt the LiGaGe type with lattice parameters a = 0.43775, c = 0.71138. The sample was prepared by melting a mixture of the metals in an arc furnace and annealing at 1070 K.

5. Rare earth-f element-germanium systems

5.1. Sc-R'-Ge systems

5.1.1. Sc-Y-Ge

The phase equilibria in the Sc–Y–Ge system (fig. 117) were investigated by Shpyrka and Mokra (1991) by means of X-ray phase and microstructural analyses of alloys which were arc melted and subsequently annealed in evacuated silica tubes for 350 h at 870 K and finally quenched in water. The starting materials were Sc 99.92 mass%, Y 99.90 mass%, and Ge 99.99 mass%. The phase relations are characterized by the existence of three ternary compounds and the formation of a continuous solid solution (Sc, Y)₅Ge₃ originating at the isotypic binary compounds. The binary compounds ScGe₂, Y₂Ge₃ and Sc₁₁Ge₁₀ dissolve 18, 10 and 8 at.% of third component, respectively.



Fig. 117. Sc-Y-Ge, isothermal section at 870 K.

In the course of a phase equilibrium study, three ternary compounds were observed by Shpyrka and Mokra (1991): $Sc_{2.7}Y_{2.3}Ge_4$ (1) was found to be isotypic with Sm_5Ge_4 , a = 0.7283, b = 1.418, c = 0.7461; $Sc_{1.35}Y_{3.65}Ge_4$ (3) belongs to the Sm_5Ge_4 -type structure family, a = 0.7440, b = 1.431, c = 0.7578; and $\sim Sc_{0.3}Y_{0.7}Ge_2$ (2) crystallizes with an unknown structure type.

5.1.2. Sc-La-Ge

No phase diagram is available for the Sc–La–Ge system; however two ternary compounds were observed and characterized in the course of searching for isostructural series of compounds.

 $Sc_3La_{1.22}Ge_4$ was found to be isotypic with $Sc_3Ce_2Si_4$, a=0.7252, b=1.4350, c=0.7652 (X-ray powder diffraction; Shpyrka et al. 1990). ScLaGe belongs to the

ScCeSi type, a=0.4351, c=1.6067 (X-ray powder diffraction; Shpyrka 1990). For the experimental details, see Sc-Y-Ge.

Shpyrka (1990) investigated the phase formation in the section $ScGe_2$ -LaGe₂, and no ternary compounds were observed.

5.1.3. Sc-Ce-Ge

Phase relations in the isothermal section of the Sc–Ce–Ge system at 870K (fig. 118) were determined by Bodak and Kokhan (1983) from X-ray powder diffraction and microstructural analyses of 120 alloys prepared by arc melting Sc (99.92 mass%), Ce (99.56 mass%) and Ge (99.99 mass%) ingots. The melted buttons were then annealed at 870 K for 400 h in evacuated silica tubes. Four ternary compounds were found to exist. Up to 4 at.% Sc and 8 at.% Sc dissolve in CeGe_{2–1.78} and CeGe_{1.6–1.56}. The solubilities of third component in other binary compounds were reported to be negligible.

The crystal structures of $Sc_3Ce_{1.22}Ge_4$ (2) ($Sc_3Ce_2Si_4$ type; a=0.7188, b=1.339, c=0.7416) and ScCeGe (3) (ScCeSi type; a=0.4314, c=1.5913) were investigated by Shpyrka et al. (1990) and Shpyrka (1990), respectively, employing an X-ray single-crystal method. The samples were prepared in the same manner as for the investigation of the isothermal section of this system.

The crystal structures of ~Sc₅Ce_{0.5}Ge_{4.5} (1) and ~Sc₂Ce₅Ge₆ (4) are not determined.



Fig. 118. Sc--Ce--Ge, isothermal section at 870 K.

5.1.4. Sc-Pr-Ge

At present, the phase relations are unknown for the system Sc–Pr–Ge. The formation of two ternary germanides was observed in the course of searching for isostructural series of compounds.

Sc₃Pr_{1.22}Ge₄ was found to be isotypic with Sc₃Ce₂Si₄, a=0.7116, b=1.4059, c=0.7576 (X-ray powder diffraction; Shpyrka et al. 1990). ScPrGe belongs to the ScCeSi type, a=0.4325, c=1.5874 (X-ray powder diffraction; Shpyrka 1990). For the experimental details, see Sc-Y-Ge.

5.1.5. Sc--Nd-Ge

The isothermal section for the Sc–Nd–Ge system at 870 K (fig. 119) was constructed by Shpyrka (1990) employing X-ray phase and microstructural analyses of 112 alloys which were arc melted and annealed for 400 h in sealed quartz ampoules. The phase relations within the Sc–Nd–Ge system at 870 K are characterized by the existence of three ternary compounds and by the formation of substitutional solid solutions originating at Nd₅Ge₃





(dissolves 12.5 at.% Sc), Nd₅Ge₄ (10 at.% Sc), NdGe (5 at.% Sc), NdGe_{2-x} (8 at.% Sc), Sc₁₁Ge₁₀ (8 at.% Nd), and Sc₅Ge₃ (5 at.% Nd). The purity of the starting metals was Sc 99.92 mass%, Nd 99.44 mass%, and Ge 99.99 mass%. The solubilities of third component in other binary compounds were reported to be <5 at.%.

The crystal structures of $Sc_3Nd_{1.22}Ge_4$ (1) ($Sc_3Ce_2Ge_4$ type; a=0.7119, b=1.4065, c=0.7574) and ScNdGe (2) (ScCeSi type; a=0.43106, c=1.5823) were investigated by Shpyrka et al. (1990) and Shpyrka (1990), respectively, employing X-ray powder diffraction. For experimental details, see Sc-Nd-Ge, isothermal section.

The crystal structure of \sim Sc₂Nd₅Ge₆ (3) was not investigated.

5.1.6. Sc-Sm-Ge

No phase diagram is available for the Sc-Sm-Ge system; however two ternary compounds were observed and characterized.

 $Sc_3Sm_{1.22}Ge_4$ was found to be isotypic with $Sc_3Ce_2Si_4$, a=0.7102, b=1.4020, c=0.7546 (X-ray powder diffraction; Shpyrka et al. 1990). ScSmGe belongs to the ScCeSi type, a=0.4264, c=1.5623 (X-ray powder diffraction; Shpyrka 1990). For the experimental details, see Sc-Y-Ge.

The phase relations along the section $ScGe_2$ -SmGe₂ were investigated by Shpyrka (1990); the formation of a ternary compound $Sc_{0.12}Sm_{0.22}Ge_{0.66}$ with an unknown structure type was observed.

5.1.7. Sc-Eu-Ge

Little information exists about the Sc–Eu–Ge system; only one ternary germanide was characterized. ScEuGe was found to be isotypic with a ScCeSi type, a = 0.4270, c = 1.5636 (X-ray powder diffraction; Shpyrka 1990). For the experimental details, see Sc–Y–Ge.

5.1.8. *Sc*–*Gd*–*Ge*

No complete phase diagram is available for the Sc–Gd–Ge system; phase relations along ScGe₂–GdGe₂ were studied by Shpyrka (1990). From X-ray powder diffraction data for arc melted alloys annealed at 870 K, the solubility of ScGe₂ in GdGe₂ was found to extend up to 8 at.% Sc.

5.1.9. Sc-Tb-Ge

The only phase diagram information on the system Sc–Tb–Ge is due to Shpyrka (1990) who investigated ternary arc melted alloys annealed at 870 K in the ScGe₂–TbGe₂ quasibinary system by means of X-ray powder diffraction. The solubility of ScGe₂ in TbGe₂ extends to 6 at.% Sc.

5.1.10. Sc-Dy-Ge

The phase equilibria in the Sc–Dy–Ge system (fig. 120) were investigated by Shpyrka and Mokra (1991) using X-ray phase and microstructural analyses of alloys which were arc melted and subsequently annealed in evacuated silica tubes for 350 h at 870 K and finally quenched in water. The starting materials were Sc 99.92 mass%, Dy 99.90 mass% and Ge 99.99 mass%. The phase relations are characterized by the existence of three ternary compounds and the formation of continuous solid solution (Sc, Dy)₅Ge₃ originating at the isotypic binary compounds. The binary compounds DyGe_{1.33}, ScGe₂, Sc₁₁Ge₁₀ and Dy₁₁Ge₁₀ dissolve 20, 18, 8 and 8 at.% of the third component, respectively.

The three compounds observed by Shpyrka and Mokra (1991) were $Sc_{1.8}Dy_{3.2}Ge_4$ (1) (Sm₅Ge₄ type, a=0.7346, b=1.4295, c=0.7555); $Sc_{2.7}Dy_{2.3}Ge_4$ (3) (isotypic with Sm₅Ge₄, a=0.7260, b=1.4151, c=0.7477); and \sim ScDy₂Ge₆ (2) which crystallizes with an unknown structure type.



Fig. 120. Sc–Dy–Ge, isothermal section at 870 K.

5.2. Y-R'-Ge systems

5.2.1. *Y*–*Ce*–*Ge*

The isothermal section of the Y–Ce–Ge phase diagram at 870 K (fig. 121) was constructed by Shpyrka (1990) using X-ray powder diffraction data of 163 arc melted alloys annealed for 400 h. The purity of the starting components was Y 99.90 mass%, Ce 99.56 mass%, and Ge 99.99 mass%. The phase relations are characterized by the existence of two ternary compounds and by the formation of two continuous solid solutions between binary



Fig. 121. Y-Ce-Ge, isothermal section at 870 K.

200

 RGe_{2-x} and R_5Ge_3 compounds. Three solid solution ranges were found to exist within the Y-Ce-Ge system at 870 K: Ce in Y₂Ge₃ (up to 20 at.%), Ce in Y₁₁Ge₁₀ (up to 18 at.%) and Y in Ce₅Ge₄ (up to 20 at.%).

 $Y_{0.2}$ Ce_{0.8}Ge (1) was said to crystallize with CrB type structure, a = 0.447, b = 1.1095, c = 0.4064 (Shpyrka 1990; X-ray powder diffraction).

 $Y_{3.2}Ce_{1.8}Ge_4$ (2) belongs to the Sm₅Ge₄ type structure, a = 0.760, b = 1.463, c = 0.756 (Shpyrka 1990; X-ray powder diffraction).

5.3. La-R'-Ge systems

5.3.1. La-Ce-Ge

The phase equilibria in the La–Ce–Ge system at 870 K (fig. 122) were investigated by Shpyrka (1988) by means of X-ray phase analysis and partly microstructural analysis of alloys which were arc melted and subsequently annealed in evacuated silica tubes for 350 h and finally quenched in water. The starting materials were La 99.79 mass%, Ce 99.56 mass%, and Ge 99.99 mass%. The phase relations are characterized by the formation of continuous solid solutions originating at the isotypic binary compounds.



5.3.2. La-Gd-Ge

The phase relations in the La–Gd–Ge ternary system at 873 K within 40–100 at.% Ge were investigated by Stetskiv et al. (1995) using X-ray powder and partly microstructural analyses. Samples were obtained by arc melting, and homogenized at 873 K for 500 h. The formation of the continuous solid solution (La, Gd)Ge_{2-x} (α -ThSi₂ structure type) was found and solubility of Gd (~10 at.%) in LaGe_{2-x} (α -GdSi₂ structure type) was determined.

5.4. Ce-R'-Ge systems

5.4.1. *Ce–Gd–Ge*

The phase equilibria in the Ce–Gd–Ge system (fig. 123) were investigated by Shpyrka et al. (1986) by means of X-ray phase analysis of 170 alloys which were arc melted and subsequently annealed in evacuated silica tubes for 350 h at 870 K and finally quenched in water. The starting materials were Ce 99.56 mass%, Gd 99.85 mass%, and Ge 99.99 mass%. The phase relations are characterized by the formation of three continuous solid solutions between isotypic binary compounds: (Ce, Gd)Ge_{2-x}, (Ce, Gd)₅Ge₄ and (Ce, Gd)₅Ge₃. The binary compounds GdGe, Ce₃Ge and Gd_{1.04}Ge_{1.56} dissolve 40, 20 and 16 at.% of the third component, respectively.



Fig. 123. Ce–Gd–Ge, isothermal section at 870 K.

5.4.2. Ce-Dy-Ge

Little information exists about the Ce–Dy–Ge system; only one ternary germanide was characterized. Ce_{0.8}Dy_{0.2}Ge was found to be isotypic with CrB, a=0.4465, b=1.1064, c=0.4050 (X-ray powder diffraction; Shpyrka 1990). For the experimental details, see Y–Ce–Ge.

5.4.3. Ce-Ho-Ge

No phase diagram is available for the Ce–Ho–Ge system; however one ternary compound was observed and characterized in the course of searching for isostructural series of compounds. Ce_{0.8}Ho_{0.2}Ge was reported to be isotypic with CrB, a=0.4475, b=1.1092, c=0.4063 (X-ray powder diffraction; Shpyrka et al. 1990). For the experimental details, see Y–Ce–Ge.

TERNARY RARE-EARTH-GERMANIUM SYSTEMS

5.4.4. *Ce–Er–Ge*

At present, phase relations are unknown for the system Ce–Er–Ge; the formation of one ternary germanide was observed. Shpyrka (1990) reported the crystallographic characteristics for Ce_{0.8}Er_{0.2}Ge: CrB-type structure, a=0.4470, b=1.1104, c=0.4072 (X-ray powder diffraction). For experimental details, see Y–Ce–Ge.

5.4.5. Ce-Tm-Ge

No phase diagram is available for the Ce–Tm–Ge system; however one ternary compound was observed and characterized by Shpyrka (1990): Ce_{0.8}Tm_{0.2}Ge, CrB-type structure, a = 0.4485, b = 1.1110, c = 0.4073 (X-ray powder diffraction). For experimental details, see Y–Ce–Ge.

5.4.6. Ce-Lu-Ge

The phase equilibria in the Ce–Lu–Ge system at 870 K (fig. 124) were investigated by Shpyrka (1990) by means of X-ray phase and microstructural analyses of 143 alloys which were arc melted and subsequently annealed in evacuated silica tubes for 350 h and finally quenched in water. The starting materials were Ce 99.56 mass%, Lu 99.98 mass%, and Ge 99.99 mass%. The phase relations are characterized by the existence of two ternary compounds and the formation of continuous solid solution (Ce, Lu)₅Ge₃ between the isotypic binary compounds. The binary compounds Ce₃Ge, Lu_{0.9}Ge₂ and LuGe_{1.5} dissolve 12.5, 10 and 10 at.% of third component, respectively.

The two ternary compounds observed by Shpyrka (1990) were $Ce_{0.45-1.35}Lu_{4.55-3.65}Ge_4$ (1) (*a*=0.7389-0.7469, *b*=1.4305-1.4436, *c*=0.7607-0.7649) and $Ce_{3.25}Lu_{1.75}Ge_4$ (2) (*a*=0.7666, *b*=1.4925, *c*=0.7649). Both phases are isotypic with Sm₅Ge₄.



Fig. 124. Ce-Lu-Ge, isothermal section at 870 K.

5.5. Sm-R'-Ge systems

5.5.1. Sm-Lu-Ge

Shpyrka investigated the phase formation within the SmGe₂-LuGe₂ section at 870 K; three ternary phases were observed: \sim Sm₂₆Lu₈Ge₆₆ (unknown type), \sim Sm₂₄Lu₁₀Ge₆₆ (DyGe_{1.85} type) and \sim Sm₂₂Lu₁₂Ge₆₆ (HoGe₂ type). For sample preparation, see Ce-Lu-Ge.

5.6. Dy-R'-Ge systems

5.6.1. *Dy–Ho–Ge*

The only information on the phase relations in the Dy–Ho–Ge system is due to Shpyrka (1990) who investigated the DyGe₂–HoGe₂ section by means of X-ray powder diffraction. The samples were prepared by arc melting followed by annealing at 870 K for 400 h. The purity of the starting materials was Dy 99.83 at.%, Ho 99.50 at.%, and Ge 99.99 at.%. The solubility of HoGe₂ in DyGe₂ extends to 15 at.% Ho. One ternary compound Dy_{0.19-0.17}Ho_{0.19-0.21}Ge_{0.66} with unknown structure was observed. The solubility of DyGe₂ in HoGe₂ extends to 8.5 at.% Ho.

5.7. Er-R'-Ge systems

5.7.1. Er-Tm-Ge

No ternary phase diagram exists for the Er–Tm–Ge system; however the formation of a ternary compound \sim Er_{0.24}Tm_{0.12}Ge_{0.66} with an unknown structure was reported from an X-ray investigation of the ErGe₂–TmGe₂ section. The solubility of TmGe₂ in ErGe₂ extends to 3 at.% Tm, whereas the solubility of ErGe₂ in TmGe₂ extends to 20 at.% Er.

6. Discussion

6.1. Peculiarities of the interactions in the R-s element-Ge systems

6.1.1. R-Li-Ge systems

From 16 rare-earth ternary systems with lithium and germanium the isothermal sections for 10 systems have been established over the whole concentration region.

The main peculiarity of all ternary systems with rare-earth metals concerns the influence which the component interaction in the terminal binary systems has on the ternary systems. The binary immiscibility region R–Li always extends into the ternaries up to a maximum content of 17–26 at.% Ge. As a consequence, a small number of ternary compounds is formed, with a maximum observed for the Ho–Li–Ge system (7 intermetallics). All ternary compounds, as a rule, have a narrow homogeneity range, which is connected with the pronounced difference in characteristic alloying parameters of the interacting components.

Structure type	La	Ce	Pr	Nd	Sm	Eu	Gđ	Tb	Dy	Но	Er	Tm	Yb	Lu	Y	_
Ce ₂ Li ₂ Ge ₃	+	+	+	+	+		_			_	_	_	_	-		
Ce ₂ MnGe ₅		+	+	+	+					-	_	~		~		
AlCr ₂ C	÷	+	+	+	_		_			-	-	-	-	-		
Pr ₂ LiGe ₆		+	+	-	-		-			-	-	~	-	-		
CaLiSi ₂	+	$^+$	+	+	+	+	+			-	-	-				
ZrNiAl		~	+	+	+		+	+	+	+	+	+	+	+	+	
Tm ₄ LiGe ₄		~	_	-	-		+	+	+	+	+	+	+	+	+	
$Hf_3Ni_2Si_3$		-		-	-		-	+	+	+	+	+	-	+	+	
TmLi _{1-x} Ge ₂			_	-	_		_			+	+	+	-	+		

 Table 31

 Isotypic compounds of the ternary R–Li–Ge systems^a

^aAn empty cell means that the alloy of this composition was not investigated; a plus sign means that the compound exists, a minus sign that it was not observed.

Analysis of the compositions and crystal structures of the experimentally observed ternary intermetallics established a sharp differentiation between systems belonging to the ceric or to the yttric subgroup. This situation is illustrated by table 31.

From the investigated series of isostructural compounds, intermetallics of equiatomic composition with ZrNiAl structure are typical for both the ceric and the yttric subgroups. Other series exist either in the ceric subgroup (RLi_2Ge , R_2LiGe_6 , R_2LiGe_5 , $R_2Li_2Ge_3$) or in the yttric subgroup (R_4LiGe_4 , $R_3Li_2Ge_3$, $RLi_{1-x}Ge_2$). The system Gd–Li–Ge occupies the intermediate position with compounds crystallizing in structural types typical for the ceric subgroup (CaLiSi₂), as well as types typical for the yttric subgroup (Tm_4LiGe_4) or for both subgroups (ZrNiAl). However the systems of a particular subgroup are not complete analogues. For example, in the Ce–Li–Ge system, a compound of composition Ce₂₆Li₅Ge₂₂ exists which has not been found in the corresponding systems of this subgroup. Also the intermetallic of equiatomic composition with the ZrNiAl structure does not form with cerium. In the systems with Nd and Sm the homologous compounds with Pr₂LiGe₆ structure, which are formed with cerium and praseodymium, have not been found. Also, in the Sm–Li–Ge system there is no compound with AlCr₂C structure.

For the yttric subgroup the biggest differences are observed for the Yb–Li–Ge system. The formation of two compounds (Yb₈LiGe₁₃ and Yb₅Li₄Ge₄) with new structure types which do not occur within any other system of this subgroup has been found for the ytterbium–lithium–germanium combinations. This is probably due to the tendency of ytterbium to be divalent or mixed-valent.

Compounds of equiatomic composition with rare-earth metals of the yttric and cerium subgroups crystallize with the ZrNiAl type whereas scandium germanide of equiatomic composition forms the MgAgAs type.

Due to a noticeable lack of information on ternary R-Li-Ge systems, it is still difficult to establish a relation between the number of compounds formed per individual system
and the chemical nature of the interacting elements. From the data available, one can distinguish some established regularities:

- the number of compounds formed per system increases with increasing differences (i) in atom size, electronegativity, electronic structure and thermodynamic properties;
- (ii) a separation of systems into ceric and yttric subgroups is observed; the Gd-Li-Ge system occupies an intermediate position between these subgroups;
- (iii) binary immiscibility always extends into the corresponding ternary system.

6.1.2. *R*-*Mg*-*Ge*

Interaction of rare earths with magnesium and germanium has not been studied sufficiently; few ternary compounds were observed and investigated (EuMgGe, YbMgGe and EuMg₃Ge₃). Therefore it is impossible to draw any conclusions with respect to the alloying behavior of these metals.

6.2. Peculiarities of the interactions in the R-p element-Ge systems

6.2.1. *R*–*B*–*Ge systems*

The characteristic features of the interaction of boron and germanium with the rare earths is the absence of ternary compounds and the lack of solid solubility of the third component in the binary phases.

6.2.2. R-Al-Ge systems

In spite of the fact that the partial isothermal sections (0–33 at.% R) have been investigated only for four ternary systems, it is possible to draw some conclusions on the interaction of components in these systems (see table 32). Similarly to the ternary R-Li-Ge combinations, a differentiation exists between ternary systems containing light and heavy lanthanides; the Gd-Al-Ge system occupies an intermediate position between ceric and vttric subgroups:

			Isc	otypic	compc	unds	of the	ternar	y R–A	Al-Ge	syster	ns				
Structure type	La	Ce	Pr	Nd	Sm	Eu	Gd	Tb	Dy	Но	Er	Tm	Yb	Lu	Y	Sc
CaAl ₂ Si ₂	+	+	+	+	+	+	+	+	+	+	+	+	+	+	+	_
Ba ₂ Cd ₃ Bi ₄	+	+	+	+	+		+	+	+	4	+	-	-	-	-	—
La ₂ AlGe ₆	+	+	+	+	+	-	+					_		-	_	-
α -ThSi ₂	+	+	+	+	$^+$	+	+	-	-		-	-	—	_	-	-
YAlGe	_	_	~	-	-	_	+	+	+	+	+	÷	+	+	+	+
AlB_2	+	+		+			-								-	

Table 32

^aAn empty cell means that the alloy of this composition was not investigated; a plus sign means that the compound exists, a minus sign that it was not observed.

- (i) the R_2AlGe_6 and α -ThSi₂ structures are typical for the ceric subgroup, and the Gdcontaining compounds are the ending members of these isotypic series;
- (ii) the YAlGe structure is typical for the yttric subgroup, and the Gd-containing compound is the first member of this isostructural series;
- (iii) the CaAl₂Si₂ type occurs in all systems except of for scandium;
- (iv) the GdAlGe compound has two polymorphic modifications, α -ThSi₂ and YAlGe.

6.2.3. R-Ga(In, C)-Ge systems

Little information exists on the interaction of gallium (indium, carbon) with germanium and the rare earths. From the available data, one notices that for the gallium-containing compounds the most typical structures are the AlB₂-, ThSi₂- and Ce₂GaGe₆-types. Only one series of isotypic compounds was observed both for the rare-earth-indiumgermanium combinations (Mo₂NiB₂) and for the carbon-containing ternary alloys (R_5CGe_3).

6.2.4. R-Si-Ge systems

The R-Si-Ge systems are characterized by the presence of two components with similar crystallochemical behavior. This is the main reason why limited or continuous solid solutions are formed between the isotypic binary compounds. These solid solutions often show various deviations from linearity in the unit cell volume versus concentration plots.

Two ternary compounds were found only in the Y–Si–Ge system. They have the crystal structures of binary YSi₂ and YGe₂ compounds.

6.3. Peculiarities of the interactions in the R-d element-Ge systems

The majority of experimental investigations deals with Fe, Co, Ni and Cu. Therefore, our discussion will be based on the interaction peculiarities of rare earths and germanium with the above-mentioned elements and their electronic analogues.

6.3.1. R-Fe-Ge systems

From the results reviewed in this chapter, some common regularities of the interaction of rare-earth metals with iron and germanium can be drawn. The number of ternary compounds formed with light rare-earth elements, iron and germanium monotonously increases from lanthanum to samarium. No ternary compounds were found with europium, which is probably due to its divalent nature, compared to trivalency for the other rare earths. Among the heavy lanthanides, Tm forms the largest number of ternary compounds with iron and germanium.

The ternary systems R–Fe–Ge are characterized by various stoichiometries and crystal structures of the existing ternary compounds, depending on the rare-earth metal (table 33). As one can see, the most prevailing structure types are $CeGa_2Al_2$ and $CeNiSi_2$. Compounds with AlB₂-, BaNiSn₃-, Nd₆Fe₁₃Si- and Sm₄Co_{1-x}Ge₇-type structures were observed in ternary systems containing light lanthanides; compounds with CeGa₂Al₂-,

				21					,		,					
Structure type	La	Ce	Pr	Nd	Sm	Eu	Gd	Tb	Dy	Но	Er	Tm	Yb	Lu	Y	Sc
CeGa ₂ Al ₂	+	+	+	+	+	-	+	+	+	+	+	+	+	+	+	_
CeNiSi ₂	_	+	+	+	+		+	+	+	+	+	+	+	+	+	-
YCo ₆ Ge ₆	_		+	+	+	_	+	+	+	+	+	+	+	+	+	
Tb ₁₁₇ Fe ₅₂ Ge ₁₁₂			+	-	+	-		+	+	+	+	+	-	+	+	-
ZrFe ₄ Si ₂			-			-	-	+	+	+	+	+	+	+	+	
Gd ₆ Cu ₈ Ge ₈		~	-		_	-	-	_	+	+	+	+	_	+	_	_
$Hf_3Ni_2Si_3$			-	_		_		-		-	+	_	-	+		-
$Tm_9Fe_{10}Ge_{10}$			_	_	-			-		-	+	+	+			_
BaNiSn ₃		+	+	_	-	-		_			-	_	-			_
AlB ₂	+	-	_	+	+			_		-	-	-	-			-
Nd ₆ Fe ₁₃ Si		~	+	+	_	-		-		_		-	_			_
Sm ₄ Co _{1-x} Ge ₇		-	+	+	+			-		-	-	-	_			-

Table 33 Isotypic compounds in the ternary R-Fe-Ge systems^a

^aAn empty cell means that the alloy of this composition was not investigated; a plus sign means that the compound exists, a minus sign that it was not observed.

CeNiSi₂-, YCo₆Ge₆- and Tb₁₁₇Fe₅₂Ge₁₁₂-type structures are found for both the light and heavy rare-earth elements; and ZrFe₄Si₂-, Gd₆Cu₈Ge₈-, Tm₉Fe₁₀Ge₁₀- and Hf₃Ni₂Si₃-type structures are typical only for the heavy lanthanides.

The range of formation of ternary R–Fe–Ge compounds is restricted to concentrations of less than ~42 at.% rare-earth metal; $R_{117}Fe_{52}Ge_{112}$ (Tb₁₁₇Fe₅₂Ge₁₁₂ type) is the terminal R-rich phase. Ternary compounds with light lanthanides are found predominantly in the range 40–70 at.% Ge, whereas the heavy rare-earth elements form compounds primarily in the concentration region from 28 to 50 at.% Ge.

6.3.2. R-Co-Ge systems

Interactions of R with cobalt and germanium have been sufficiently studied to draw some conclusions, i.e. the phase diagrams for 12 ternary R–Co–Ge systems have been established. Most of them are characterized by a large number of ternary compounds. Substitution of an R element essentially affects the alloying behaviour of elements that is displayed in the number of compounds formed. The maximum number of ternary phases (20) has been observed for the samarium-containing system. The Eu–Co–Ge system strongly differs from all other R–Co–Ge systems by the number of ternary compounds. The isotypic series of compounds which are observed in these systems are listed in table 34.

Dimorphism phenomena are characteristic for the $R_2Co_3Ge_5$ compounds (Lu₂Co₃Si₅-type $\leftrightarrow U_2Co_3Si_5$ -type) (R = Ce–Sm, Gd). Morphotropic transformation was noticed for

			100	opic c	ompo		1 1110	-	,	0.00	e jocen					
<u></u>	La	Ce	Pr	Nd	Sm	Eu	Gd	ТЪ	Dy	Но	Er	Tm	Yb	Lu	Y	Sc
CeGa ₂ Al ₂	+	+	+	+	+	+	+	+	+	+	+	+	+		+	_
CeNiSi ₂	+	+	+	+	+	-	+	+	+	+	+	+	+	+	+	—
Sc_2CoSi_2		-	-	$^+$	+	-	+	$^+$	+	+	+	+	+	+	+	+
Tb ₃ Co ₂ Ge ₄		-		-	+	-	+	+	+	+	+	+	-		+	-
TiNiSi		-	-	-	+	-	+	+	+	+	+	+	+	+	+	+
Y ₃ Co ₄ Ge ₁₃		_	_	_	_	_	+	+	+	+	+	+	+	+	+	-
YCo ₆ Ge ₆		-		-	-	_	+	+	+	+	+	+	+	+	+	-
Ce ₂ CuGe ₆		-	-	_	-	_	+	+	+	+	+	+		+	+	-
$ZrFe_4Si_2$		-			-	_		-		-	+	+	+	+		-
$\mathrm{Sc}_5\mathrm{Co}_4\mathrm{Si}_{10}$		-	-			-				-	+	$^+$	+		+	_
$BaNiSn_3$		+	+	+	+	+				-	-	_				_
AlB_2		+	+	+				-			_	_				-
PbFC1		+	+	+				-		-	_	_				-
La ₃ NiGe ₂		+	+	+							-	_				
Tb ₁₁₇ Fe ₅₂ Ge ₁₁	2	-	+	+	+	_				_	-	_				_
$U_2 Co_3 Si_5$		+	+	+	-	_		+					-	_	+	-
$\mathrm{Lu}_2\mathrm{Co}_3\mathrm{Si}_5$		+	+	+	+		+		+	+	+		_	_		-

Table 34 Isotypic compounds of the ternary R–Co–Ge systems^a

^aAn empty cell means that the alloy of this composition was not investigated; a plus sign means that the compound exists, a minus sign that it was not observed.

the RCoGe compounds: from structure type PbFCl (CeCoGe, PrCoGe, NdCoGe) to structure type TiNiSi (SmCoGe, GdCoGe). No compound of equiatomic composition was observed within the Eu–Co–Ge system.

The maximum number of ternary compounds in the R-3d element-Ge systems with Pr, Nd, Sm, Tb, Ho, Er, Tm is formed with cobalt.

6.3.3. R-Ni-Ge systems

The primary intention of this section is to discuss and compare the interaction of the components in the R-Ni-Ge systems. According to sect. 4, the phase equilibria have been investigated for 12 ternary systems.

Concerning the number and the composition of compounds formed, the interaction of the components in the ternary systems R-Ni-Ge is rather complicated and varies considerably.

In this respect the most significant differences are observed in the light rare-earth group, between Ce and Eu. The ternary nickel germanides with cerium (20 compounds) exist within a wide concentration region from 7.5 to 62.5 at.% Ce, whereas the ternary phases in the Eu–Ni–Ge system (six compounds) occur between 7.5 and 33.3 at.% Eu.

				21	.1.						- ,					
Structure type	La	Ce	Pr	Nd	Sm	Eu	Gd	Y	Tb	Dy	Но	Er	Tm	Yb	Lu	Sc
CeGa ₂ Al ₂	+	+	+	+	+	+	+	+	+	+	+	+	+	+	+	
CeNiSi ₂	+	+	+	+	+	+	+	+	+	+	+	+-	+		+	_
AlB ₂	+	+	+	+	+	+	+	+	+	+	+	+	+	+		—
SmNiGe ₃		+	+	+	+	-	+	+	+	+	+	+-	+	_	+	-
TiNiSi		+	+	+	+	-	+	+	+	+	+	+	+	+	+	+
Ce ₂ CuGe ₆		+	+	+	+	_	+	+	+	+	+	+	+	+	+	_
La ₃ NiGe ₂	+	+	+	+	+	-	+	+	+	+	+	+	_	_	_	
YNi_5Si_3		-	_	~	+	—	+	+	+	+	+	+	+	+	+	-
$\mathrm{Se}_3\mathrm{Ni}_{11}\mathrm{Si}_4$		-	_	~	-	-		+	+	+	+	+	+	+	+	+
NdIrGe ₂	_	-	-			_		?	?	?	+	+	+	?	+	_
LuNiGe		-	-	~	-	-		-	_	-	-		+	_	+	-
La ₁₁ NiGe ₆	+	+	~		-	-		_	-	-	_		-	_		_
$\rm U_3Ni_4Si_4$	+	+	+	~	-	_		-		-	-	~	_	_		_
$U_2 Co_3 Si_5$		+	+	?	?	-		-	-	-	-	-	_	-		
CeNi _{8.5} Si _{4.5}	-	+	÷	+		+		-	_	-	-	*****		-		-

Table 35 Isotypic compounds of the ternary R-Ni-Ge systems^a

^aAn empty cell means that the alloy of this composition was not investigated; a plus sign means that the compound exists, a minus sign that it was not observed.

The maximum rare-earth concentration in the ternary nickel germanides of Pr (Nd, Sm) is approximately 50 at.%.

The formation of ternary phases with the rare-earth elements from Tb through Tm (including Y) exhibits a close resemblance between systems. Moreover, the Y(Tb,Dy)–Ni–Ge systems are identical. This is also true for the Ho(Er,Tm)–Ni–Ge systems.

It should be noted, that the concentration region spanned by the compounds formed for the R elements from Tb through Tm (including Y) is somewhat narrower in comparison with R-Ni-Ge systems, where R=Ce, Pr, Nd, Sm, Eu (from 11 to 50 at.% R). The maximum Ge concentration in the ternary nickel germanides of the light rare-earth elements as well as of the heavy rare earths is 66.6 at.% (in the R₂NiGe₆ compounds).

Another interesting feature of the R–Ni–Ge systems is the solubility of Ge in the Nirich binary compounds R_2Ni_{17} and RNi_5 .

Table 35 gives a survey of the isotypic series of the compounds in the R–Ni–Ge systems. The compounds of the CeGa₂Al₂-, CeNiSi₂-, AlB₂-, Ce₂CuGe₆-, La₃NiGe₂-, TiNiSi- and SmNiGe₃-type structures are found for both the light and the heavy rare-earth elements. The compounds of the CeNi_{8.5}Si_{4.5}-, U₂Co₃Si₅-, U₃Ni₄Si₄- and La₁₁Ni₄Ge₆-type structures are observed in ternary systems containing light lanthanides. The Sc₃Ni₁₁Si₄-, NdIrGe₂- and LuNiGe-type structures occur typically only for the

heavy lanthanides. The RNi₅Ge₃ compounds of YNi₅Si₃ structure type, unexpectedly, occur solely with samarium and with the heavy rare-earth elements. In addition to the compounds listed in table 35, the crystal structure has been solved for the following germanides: La₂NiGe (space group I4/mcm), La₈NiGe₅ (space group Pmmn), La(Ni, Ge)₁₃ (space group Fm3c), Ce₅NiGe₂ (space group P4/ncc), SmNi₃Ge₃ (space group I4/mmm), EuNiGe (space group P2₁/b), EuNiGe₃ (space group I4mm) and Er₃Ni₂Ge₃ (space group Cmcm). All these compounds are the unique representatives of the indicated structure types in the R–Ni–Ge systems.

As one can see from table 35, a few morphotropic transformations have been observed in the systems under discussion. A brief description follows:

- (i) The RNiGe₂ compounds. The compounds with 1:1:2 composition when R is a light rare-earth element crystallize in the CeNiSi₂-type structure. The compounds of the same structure type for the heavy rare-earth elements have been found to form with a nonstoichiometric composition and are defective of Ni atoms. Furthermore, the compounds of stoichiometric composition with Ho, Er, Tm and Lu have been found to crystallize with the NdIrGe₂-type structure.
- (ii) The R(Ni, Ge)₁₃ compounds. The following morphotropic transformation has been observed for the light rare-earth elements: from La(Ni, Ge)₁₃ (NaZn₁₃ type, space group Fm3c) to R(Ni, Ge)₁₃ (R = Ce–Nd, Eu, CeNi_{8.5}Si_{4.5} type, space group I4/mcm).
- (iii) The RNiGe₃ compounds. In this series the SmNiGe₃ structure type (space group Cmmm) was observed for the compounds of the lanthanides except Eu and Yb. The EuNiGe₃ compound crystallizes in the BaNiSn₃ type (space group I4mm).
- (iv) The RNiGe compounds. A similar transformation, which also is caused, probably, by the peculiar behavior of the Eu atom has been observed in the RNiGe series of compounds: Ce(Pr-Sm)NiGe (TiNiSi-type) to EuNiGe (own structure type) \rightarrow Gd(Tb-Lu)NiGe (TiNiSi-type).

The TmNiGe and LuNiGe compounds exhibit dimorphism. The TiNiSi type \leftrightarrow LuNiGe type transition temperature is 1630 K for TmNiGe and 1570 K for LuNiGe.

The compound Ce_5NiGe_2 also occurs in two modifications: the compound in its own structure type (high-temperature modification) transforms into a compound of unknown structure type (low-temperature modification).

Thus, the comparison of the R–Ni–Ge systems, carried out above, shows a similarity in the interaction of rare-earth metals with nickel and germanium with the exception of europium, which forms a considerably smaller number of compounds. This is consistent with europium's divalent character, and its similar behavior observed in the other Eu–3d element–Ge systems. At the same time, the type of interaction and the crystal structures of compounds formed are different for the elements of the light and heavy lanthanides. The only two ternary germanides of scandium, which are isotypic with lanthanide-containing compounds, are ScNiGe (structure type TiNiSi) and $Sc_3Ni_{11}Ge_4$ (structure type $Sc_3Ni_{11}Ge_4$).

6.3.4. R-Cu(Ag, Au)-Ge systems

In contradiction to earlier reviewed R-Fe(Co, Ni)-Ge systems with a brightly pronounced distinction between systems containing light rare earths and systems containing heavy rare earths, the alloying behavior in R-Cu(Ag, Au)-Ge systems is of an analogous type.

The predominant majority of ternary compounds exists within the narrow concentration region from 20 to 33 at.% R.

Table 36 lists the isotypic series of the compounds in the R-Cu(Ag, Au)-Ge systems. Ternary phases of Ce₂Cu₃Ge₃- and CeNiSi₂-type structures are found only in the R-Cu-Ge system and are not included in table 36.

		I	sotypi	c con	npoun	ds of	the te	rnary	R–Cu	ı(Ag, A	Au)–G	e sys	tems ^a				
Structure type		La	Ce	Pr	Nd	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu	Y	Sc
CeGa ₂ Al ₂	Cu Ag Au	+ +	+ +	+ +	+ + +	+ +	+ +	++	+	+	+	+	+	+		+	-
Ce ₂ CuGe ₆	Cu Ag Au	+ + +	+ + +	+ + +	+ + +	+ + +	-	+ + +	+	+	+ - -	+	+	+	_	+	-
AlB ₂	Cu Ag Au	+ +	+ +	+ +	+ + +	+	+	+	+	+	+ - -	+	÷	-	-	+	_
CaIn ₂ or LiGaGe	Cu Ag Au	- + +	~ + +	- + +	- - +	- +	_ -	- - +	+ - +	+ +	+ +	+ - +	+ ~- +	+ ~ +	+ +	+ +	- - +
Fe ₂ P or ZrNiAl	Cu Ag Au	-		+	+ -	+ -	+ -	-	+ -	+ -	+ -	+	+	+~	+ -	+ -	+ + -
Gd ₆ Cu ₈ Ge ₈	Cu Ag Au	-	-	+ +	+ + _	+ +	_	+ +	+	+	+ -	+	+	+	+ 	+	+

	Table 36
sotypic compounds of the	ternary R-Cu(Ag, Au)-Ge systems

^aAn empty cell means that the alloy of this composition was not investigated; a plus sign means that the compound exists, a minus sign that it was not observed.

The compounds of equiatomic composition are found to crystallize mainly in hexagonal basis. The following morphotropic transformation was observed in the RCuGe compounds: (La–Sm, Gd)CuGe (AlB₂ structure type) \rightarrow (Y, Tb–Lu)CuGe (CaIn₂ structure type) -> ScCuGe (ZrNiAl structure type). For the ternary RAgGe compounds the following structure types are characteristic: (La, Ce, Pr)AgGe (LiGaGe structure type) \rightarrow EuAgGe (AlB₂ structure type) \rightarrow (Gd-Lu, Sc)AgGe (ZrNiAl structure type). The RAuGe compounds crystallize with the LiGaGe structure type.

Unlike other lanthanides, europium forms equiatomic compounds with an orthorhombic structure: EuCuGe (structure types TiNiSi and CaCuGe), EuAgGe (structure type KHg₂) and EuAuGe (own structure type).

6.3.5. R-platinum metals-Ge systems

Although the isothermal sections are completely or partly constructed only for 18 ternary systems from 96 possible R–platinum metals–Ge combinations, one can see that with respect to the formation of compounds in the ternary R–M–Ge systems, Ru and Os show behavior similar to Rh and Ir (see table 37). Analysis of the compositions and crystal structures of the experimentally observed ternary germanides of platinum metals established a likeness between platinum- and palladium-containing systems (see table 38). Since information on the systematic investigations of the R–Pt–Ge systems is still lacking, only some regularities on the interaction of these components are observed.

		15		com		5 01 1			· 100(<u> </u>	.,,						
Structure type	La	Ce	Pr	Nd	Sm	Eu	Gd	Tb	Dy	Но	Er	Tm	Yb	Lu	Y	Sc	
Yb ₃ Rh ₄ Sn ₁₃	Ru	-	+	+	+	+	_	+	+	+	+	+	+	+	+	+	-
	Os	-	+	+	+	+	+	+	+	+	+	+	+	+	+	+	
	Rh	-	÷		+	+		+	+	+	+	+	+	+	+	+	
	Ir	-	+	+	+	+	-	+	+	+	+	+	+	+	+	+	-
CeGa ₂ Al ₂	Ru	+	+	+	+	+	+	+	+	+	+	+	+	+	+	+	
	Rh	+	+	+	+	+	+	+	+	+	+	+	+	+	+	+	-
$CaBe_2Ge_2$	Ir	+	+	+	+	+	+	+	+		-		-			_	
U2C03Si5 or	Ru	+	+	+	+	+	-	+	+	+	+	+	+	+	+	+	
Lu2Co3Si5	Rh	+	+	+	÷	+	_	+	+	+	+	+	+	+	+	+	
	Ir	+	+	+	+	+	-	+	+	+		_	-		-	_	
U4Re7Si6	Rh			-		-	-		-	+	+	$^+$	+	+	+	+	+
	Ir	-	_	-		-		-	+	+	+	+	+	+	+	+	+
	Os	-	-	-		-	-		-	—	-	+	+	+	+	+	+
NdIrGe ₂	Ir		-	+	+	+	-	+	+	+	+	+	-		-	+	-
$Sc_5Co_4Si_{10}$	Rh	-		-		-	-	+	+	+	+	+	+	+	+	+	_
	Ir	-	-	_	-		-	-		+	+	+	+	_		+	
	Os	-		-		-		+	+	+	+	+	+	+	+	+	_
TiNiSi	Rh	+	+	+	+	+	-	+	+	+	+	+	+	+	+	+	+
	Ir	+	+	+	+	+		+	+	+	+	+	+	+	+	+	+
$La_3Ni_2Ga_2$	Ru	+	+	+	+	+	-	_	_	_	_	_	-	_	-	_	
	Rh	+	+	+	+	+	-	+	+	+	+	+	$^+$		+	+	-
Ho ₄ Ir ₁₃ Ge ₉	Rh	+	+	+	+	+	_	+	+	+	$^+$	+	+	+	+	+	_
	Ir	+	+	+	+	+	-	+	+	+	+	+	+	+	+	+	-

Table 37 Isotypic compounds of the ternary R-Ru(Os, Rh, Ir)-Ge systems^a

^aAn empty cell means that the alloy of this composition was not investigated; a plus sign means that the compound exists, a minus sign that it was not observed.

P.S. SALAMAKHA et al.

As one can see from table 37, the most prevailing structure type among the compounds within R-Ru(Os, Rh, Ir)-Ge systems is the Yb₃Rh₄Sn₁₃ type. In addition to the compounds listed in table 37, the crystal structure has been solved for a few germanides with the TiMnSi₂-, Sc₂CoSi₂-, Hf₃Ni₂Si₃-, CeNiSi₂- and BaNiSn₃-types of structure. Morphotropic transformations were observed for the RRuGe compounds: (La-Sm)RuGe (PbFCl structure type) \rightarrow HoRuGe (TiNiSi structure type) \rightarrow ScRuGe (ZrNiAl structure type).

			ISOT	ypic c	ompo	inds (51 the	terna	ry R	Pa(Pt)	-Ge	system	15 "				
Structure type	La	Ce	Pr	Nd	Sm	Eu	Gd	Tb	Dy	Но	Er	Τm	Чb	Lu	Y	Sc	
KHg ₂	Pd Pt	+	+ +	+ +	+ +	+	-	+	+	+	+	+	+ -	+	+	+	_
TiNiSi	Pt	_	_	-	-	+	-	+	+	+	+	+	+	+		+	+
YPd ₂ Si	Pd	+	+	+	+	+	_	+	+	+	+	+	+	+	+	+	-
CeGa ₂ Al ₂	Pd Pt	+ +	+ -	+ +	+ 	+ -	+ -	+ +									
LaPt ₂ Ge ₂	Pt	+	+	$^+$	+	+	+	+	+	+	_	-	-	-	_	+	
CeCuGe ₆	Pd Pt	+ +	+ +	+ +	+ +	+ +		+ +		+ +							
NdIrGe ₂	Pt		+	+	+	+		+	+	+	+	+	+	+	-	+	-

Table 38 sotypic compounds of the ternary R–Pd(Pt)–Ge systems^a

^aAn empty cell means that the alloy of this composition was not investigated; a plus sign means that the compound exists, a minus sign that it was not observed.

The RPt₂Ge₂ compounds crystallizes with two structure types, CeGa₂Al₂ and LaPt₂Ge₂ (see table 38). The CePt₂Ge₂ compound has three polymorphic modifications, CeGa₂Al₂, CaBe₂Ge₂ and LaPt₂Ge₂. Compounds of equiatomic composition with platinum crystallize with the following structure types: LaPtGe (LaPtSi structure type) \rightarrow (Ce–Nd) PtGe (KHg₂ structure type) \rightarrow SmPtGe (TiNiSi structure type) \rightarrow EuPtGe (ZrOS structure type) \rightarrow (Gd-Yb,Sc)PtGe (TiNiSi structure type).

6.4. Peculiarities of the interactions in the R-R'-Ge systems

An analysis of the interaction of the components in the ternary systems R-R'-Ge for which the isothermal sections have been constructed showed that they can be divided into three groups: (a) systems which are characterized by formation of ternary compounds; (b) systems which are characterized by formation of continuous solid solutions and limited solid solutions between binary germanides; (c) systems in which both ternary compounds and continuous and limited solutions are formed.

(a) The Sc-Ce(Nd)-Ge ternary systems are characterized by the formation of ternary compounds, comparatively small solubility of the third component in the binary

compounds, and the absence of continuous solid solutions. These are connected with the significant differences in the rare-earth metal atom structure (absence of 4f electron shell in Sc atom) and in atom size ($r_{Sc} = 0.164 \text{ nm}$, $r_{Ce} = 0.183 \text{ nm}$, $r_{Nd} = 0.182 \text{ nm}$).

In comparing the considered systems with one another, it is necessary to indicate that at the transition from cerium to neodymium the number of ternary compounds decreases from 4 to 3 and the homogeneity range of the solid solutions on the base of the binary phases increases from 8 to 12.5 at.% Sc.

Concerning the formation of compounds, a common feature of these systems is the formation of the ternary phase with Ge content 33.3 at.% (ScRGe).

The $Ce_{0.5}Sc_{4.5}Ge_4$ compound has no equivalent in the Nd–Sc–Ge system. The $R_{1.25}Sc_3Ge_4$ compound exists with all the rare-earth metals of the cerium subgroup (La, Ce, Pr, Nd, Sm, Eu).

Considering the crystal structures of the compounds it is possible to conclude that the presence of scandium leads to the formation of various kinds of superstructures to the structure types of the binary compounds (Sm₅Ge₄, Ca₂As). RScGe ternary germanides are isostructural and are formed with the elements of the cerium subgroup (La, Ce, Pr, Nd, Sm, Eu), i.e. at the ratio $r_{\rm R}/r_{\rm Sc}$ 1.1; for R = Y, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu the compounds of this composition are not observed.

- (b) The existence of two components with close crystal chemical properties and a similar structure for most of the binary compounds determines the character of the interaction of the components in the Ce–La–Ge and Ce–Gd–Ge systems (absence of ternary compounds, formation of continuous and limited solid solutions between the isotypic binary compounds). As a consequence of the similar structure of all of the binary germanides, the Ce–La–Ge system is characterized by the formation of continuous solid solutions only (ratio $r_{\rm Ce}/r_{\rm La} = 0.997$). In the Ce–Gd–Ge system, the isotypic compounds were found to form continuous solid solutions as well, and on the basis of compounds which belong to different structure types, limited substitutional solid solution of different extension were observed. Extension of the solid solutions by the substitution of one rare-earth element by another is determined by the size of substituting atoms.
- (c) The Sc-Y(Dy)-Ge and Ce-Y(Lu)-Ge systems occupy a special position among the R-R'-Ge systems. Both ternary compounds and continuous and limited solid solutions on the basis of binary compounds are found to exist. The peculiarity of the systems considered is the formation of continuous solid solutions between isostructural germanides with the composition R₅Ge₃ (Mn₅Si₃ structure type). One more continuous solid solution was observed in the system Ce-Y-Ge.

Another feature of the systems of this subgroup is the large extent of the limited solid solutions. Differences in the crystal chemistry characteristics of the rare-earth metals in the systems considered are insignificant, but they influence composition, structure and the number of ternary compounds. Ternary compounds with the composition $Sc_{0.3}R_{0.7}Ge_2$ (R = Y, Dy) were found to exist for the Sc and Ge ternaries with Y and Dy on the digermanide section. They have no equivalent in other

R-R'-Ge systems. The formation of compounds with the Ce_{0.8} $R_{0.2}$ Ge composition (structure type CrB) is characteristic of elements of the yttric subgroup (Y, Dy, Ho, Er, Tm). An increase in the volume of the unit cell in the series of the isostructural compounds is connected with the ability of the cerium atoms to adopt an intermediate state.

As one can see from the present review, rare-earth metals show very similar crystal chemistry that is displayed in the formation of continuous solid solutions as well as substitutional solid solutions. On the other hand, differences in electron configuration of the rare-earth atoms influence the interactions in the ternary systems, as shown by different compositions, structures and the number of ternary compounds.

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Chapter 174

CRYSTAL STRUCTURES AND CRYSTAL CHEMISTRY OF TERNARY RARE-EARTH GERMANIDES

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Contents

	Symbols and abbreviations	227
1.	Introduction	227
2.	Influence of a third component on the fields	
	of formation of ternary germanides	228
3.	Structure types of ternary rare-earth	
	germanides	230
	3.1. $R(M,Ge)_{13}$ compounds	230
	3.1.1. NaZn ₁₃ structure type	230
	3.1.2. CeNi _{8.5} Si _{4.5} structure type	230
	3.2. $R(M, Ge)_{12}$ compounds	231
	3.2.1. YCo_6Ge_6 structure type	231
	3.2.2. MgFe ₆ Ge ₆ (or HfFe ₆ Ge ₆)	
	structure type	231
	3.2.3. $GdMn_6Ge_6$ structure type	232
	3.2.4. $ScNi_6Ge_6$ structure type	233
	3.2.5. $GdFe_6Ge_6$ structure type	233
	3.2.6. $TbFe_6Sn_6$ structure type	234
	3.2.7. $HoFe_6Sn_6$ structure type	234
	3.3. $R_3(M, Ge)_{34}$ and $R_3(M, Ge)_{26}$	
	compounds	234
	3.3.1. $Ce_3Pt_{23}Ge_{11}$ structure type	234
	3.3.2. $Ce_3Pd_{20}Ge_6$ structure type	235
	3.4. $R_2(M,Ge)_{17}$ compounds	236
	3.4.1. Th_2Zn_{17} structure type	236
	3.4.2. $Ce_2Al_2Co_{15}$ structure type	236
	3.4.3. $Nd_2Cr_9Ge_8$ structure type	236
	3.5. $R(M, Ge)_8$ compounds	238
	3.5.1. YNi_5Si_3 structure type	238
	3.5.2. YCo_5P_3 structure type	239
	3.6. $R(M, Ge)_6$ compounds	239
	3.6.1. $ZrFe_4Si_2$ structure type	239
	3.6.2. $SmNi_3Ge_3$ structure type	240
	3.6.3. $EuMg_3Ge_3$ structure type	241

3.7. $R_3(M, Ge)_{17}$ compounds	242
3.7.1. $Yb_3Rh_4Sn_{13}$ structure type	242
3.7.2. $Y_3Co_4Ge_{13}$ structure type	243
3.8. $R_2(M, Ge)_{11}$ compounds	244
3.8.1. $Ce_2Pt_7Ge_4$ structure type	244
3.8.2. $Ho_4Ir_{13}Ge_9$ structure type	246
3.9. $R(M, Ge)_5$ compounds	247
3.9.1. $CaCu_5$ structure type	247
3.9.2. $Sc_3Ni_{11}Si_4$ structure type	247
3.9.3. $Sc_3Ni_{11}Ge_4$ structure type	248
3.9.4. $ErNi_3Ge_2$ structure type	248
3.9.5. $ErCo_3Ge_2$ structure type	250
3.10. $R(M,Ge)_{-4.5}$ compounds	251
3.10.1. $Sc_6Ni_{18}Si_{11}$ structure type	251
3.10.2. $Nb_2Cr_4Si_5$ structure type	251
3.11. R(M, Ge) ₄ compounds	252
3.11.1. $CeGa_2Al_2$ structure type	252
3.11.2. $CaBe_2Ge_2$ structure type	253
3.11.3. $LaPt_2Ge_2$ structure type	254
3.11.4. $CaAl_2Si_2$ structure type	254
3.11.5. $U_2Co_3Si_5$ structure type	255
3.11.6. $Lu_2Co_3Si_5$ structure type	256
3.11.7. SmNiGe ₃ structure type	257
3.11.8. BaNiSn ₃ structure type	258
3.12. $R_2(M, Ge)_7$ compounds	258
3.12.1. $Ba_2Cd_3Bi_4$ structure type	258
3.12.2. $Ce_2Sc_3Si_4$ structure type	260
3.12.3. Ce_2CuGe_6 structure type	260
3.12.4. Pr_2LiGe_6 structure type	261
3.12.5. $Ce_2(Ga, Ge)_7$ structure type	262
3.12.6. La_2AlGe_6 structure type	263
3.13. $R_3(M, Ge)_{10}$ and $R_4(M, Ge)_{13}$	
compounds	264

3.13.1. $Ce_3Pt_4Ge_6$ structure type	264
3.13.2. $Y_3Pt_4Ge_6$ stucture type	265
3.13.3. $U_4 Re_7 Si_6$ structure type	266
3.14. R(M, Ge) ₃ compounds	267
3.14.1. YPd ₂ Si structure type	267
3.14.2, AlCr ₂ C structure type	267
3.14.3. ZrAl ₂ structure type	268
3.14.4. TiAl, structure type	268
3.14.5. Ce ₂ Cu ₂ Ge ₂ structure type	268
3.14.6. CeNiSi ₂ structure type	269
3 14.7. YIrGe, structure type	270
3 14.8 LuMnGe, structure type	271
3 14 9 ZrCrSi ₂ (or TiMnSi ₂) structu	пе
fyne	272
3 14 10 TmJ i. Ge. structure type	273
3.14.11 Cal isi structure type	273
3.14.17 CaPh Ga structure type	275
2.14.12. Us Co Sp structure type	274
2.14.14 Ca MaGa structure type	275
3.14.14. Ce ₂ Milde ₅ structure type	270
3.15. $R_5(M, Ge)_{14}$ and $R_4(M, Ge)_{11}$	277
compounds	277
3.15.1. $\text{Sc}_5\text{Co}_4\text{Si}_{10}$ structure type	277
3.15.2. $Zr_4Co_4Ge_7$ structure type	278
3.15.3. $La_4Ga_4Ge_7$ structure type	279
3.16. $R_3(M, Ge)_8$ compounds	279
3.16.1. $Gd_3Cu_4Ge_4$ structure type	279
3.16.2. $U_3Ni_4Si_4$ structure type	280
3.17. $R_2(M, Ge)_5$ compounds	281
3.17.1. $Ce_2Li_2Ge_3$ structure type	281
3.17.2. $\text{Tm}_2\text{Ga}_{0.5}\text{Ge}_{4.5}$ structure type	282
3.18. $R_3(M, Ge)_7$ and $R_9(M, Ge)_{20}$	
compounds	283
3.18.1. $Nd_6Fe_{13}Si$ structure type	283
3.18.2. $Tm_9Fe_{10}Ge_{10}$ structure type	283
3.19. $R(M,Ge)_2$ compounds	285
3.19.1. $ZrSi_2$ structure type	285
3.19.2. $MgZn_2$ structure type	285
3.19.3. MgCu ₂ structure type	285
3.19.4. Y ₂ Rh ₃ Ge structure type	285
3.19.5. PbFCl structure type	286
3.19.6. CeScSi structure type	287
3.19.7. AlB ₂ structure type	287
3.19.8. CaIn ₂ structure type	288
3.19.9. LiGaGe (or NdPtSb) structu	ire
type	289
3.19.10. KHg ₂ structure type	289
3.19.11. TiNiSi structure type	290
3.19,12. ZrNiAl structure type	291
3.19,13. LaPtSi structure type	291
3.19.14. ZrOS (or LaIrSi) structure t	ype 292
3.19.15. EuNiGe structure type	292

3.19.16. DyAlGe structure type	293
3.19.17. YAlGe structure type	294
3.19.18. EuAuGe structure type	294
3.19.19. CaCuGe structure type	295
3.19.20. α-YbAuGe structure type	295
3.19.21. β-YbAuGe structure type	296
3.19,22. LuNiGe structure type	296
3.19.23. ZrBeSi structure type	297
3.19.24. α -ThSi ₂ structure type	298
3.19.25. α -GdSi ₂ structure type	298
3.19.26. $CeSi_{1-x}Ge_{1-x}$ structure type	298
3.19.27. Te ₂ Ag ₃ Tl structure type	298
3.19.28. Tb ₃ Co ₂ Ge ₄ structure type	299
3.19.29. $Sc_7Cr_{4+x}Si_{10-x}$ structure type	300
3.19.30. $\text{Sm}_4\text{Co}_{1-x}\text{Ge}_7$ structure type	300
3.20. $R_7(M, Ge)_{13}$ and $R_4(M, Ge)_7$	
compounds	301
3.20.1. Yb ₂ Al ₅ Ge ₈ structure type	301
3.20.2. $Nd_4Rh_4Ge_3$ structure type	302
3.20.3. Yb ₈ LiGe ₁₃ structure type	303
3.21. R ₃ (M,Ge) ₅ and R ₅ (M,Ge) ₈ compounds	304
3.21.1. La ₃ In₄Ge structure type	304
3.21.2. Hf ₃ Ni ₂ Si ₃ structure type	304
3.21.3. $Tm_3(Ga_{0.5}Ge_{0.5})_5$ structure type	305
3,21.4. U ₃ Sb ₃ Cu ₂ structure type	305
3.21.5. Nb ₅ Cu ₄ Si ₄ structure type	306
3.22. $R_2(M, Ge)_3$ compounds	306
3.22.1. Nd ₅ Co ₅ Ge ₄ structure type	306
3.22.2. Sc_2CoSi_2 structure type	307
3.22.3. Mo_2FeB_2 structure type	308
3.23. $R_{9}(M, Ge)_{13-11}$ compounds	309
3.23.1. $Tb_{117}Fe_{s2}Ge_{112}$ structure type	309
3.23.2. Tm_4LiGe_4 structure type	311
3.23.3. La ₃ Ni ₂ Ga ₂ structure type	311
3.23.4. Sc _o Ni _s Ge _s structure type	312
3.24. R(M, Ge) compounds	313
3.24.1. CrB structure type	313
3.24.2. FeB structure type	313
3.24.3. La ₂ NiGe structure type	313
3.24.4. Gd ₃ NiSi ₂ structure type	314
3.25. $R_{11}(M, Ge)_{10}$ compounds	315
3.25.1. Sc ₁₁ Al ₂ Ge ₈ structure type	315
3.25.2. $La_{11}Ni_4Ge_6$ structure type	316
3.26. R ₂₆ (M, Ge) ₂₃ compounds	317
3.26.1. Ho ₂₆ Pd ₄ (Pd, Ge) ₁₉ structure	
type	317
3.26.2. $Ce_{26}Li_5Ge_{23-v}$ structure type	318
3.27. $R_7(M, Ge)_6$ and $R_5(M, Ge)_4$ compounds	319
3.27.1. $Ce_7Pd_4Ge_2$ structure type	319
3.27.2. Sm_5Ge_4 structure type	320
3.27.3. Gd ₅ Si ₂ Ge ₂ structure type	321

Unit cell dimensions (in nm)		R, R' Y,	Sc, and the lanthanides	
ols and abbreviations				
types of the germanides	328			
. Classification of the ternary structure				
cussion	327			
4.3.1. Y ₃ NiAl ₃ Ge ₂ structure type	327	References		335
$R(M, M'Ge)_2$ compounds	327	Acknowledge	ment	335
4.2.2. LaTmIr ₂ Ge ₄ structure type	327	5.3. Analysi	s of some new structure types	333
4.2.1. TbFeSi ₂ structure type	326		germanides	331
$R(M, M', Ge)_2$ compounds	326		of the binary rare-earth	
4.1.1. LaPt: 22Pd. 66 structure type	326	5.2.1	Formation of superstructures	550
R(M,M'Ge), compounds	325	5.2 Formati	ion of superstructures	330
nanides	325		smallest atoms	329
structure type cture types of quaternary rare-earth	525	5.1.5.	prismatic coordination of the	
3.29.2. Ce ₅ NiGe ₂ structure type 3.29.3 Cr B structure type	324	513	Structure types with trigonal	329
3.29.1. Y_2 HfS ₅ structure type	324		antiprismatic coordination of	220
$R_5(M, Ge)_3$ compounds	324	5.1.2.	Structure types with tetragonal	
3.28.2. La ₃ InGe structure type	323		the smallest atoms	328
3.28.1. La_8NiGe_5 structure type	322		icosahedral coordination of	
. $R_4(M,Ge)_3$ and $R_3(M,Ge)_2$ compounds	322	5.1.1.	Structure types with	
	. $R_4(M, Ge)_3$ and $R_3(M, Ge)_2$ compounds 3.28.1. La_8NiGe_5 structure type 3.28.2. La_3InGe structure type	$R_4(M, Ge)_3$ and $R_3(M, Ge)_2$ compounds 322 $3.28.1.$ La_8NiGe_5 structure type 322 $3.28.2.$ La_3InGe structure type 323	$R_4(M, Ge)_3$ and $R_3(M, Ge)_2$ compounds 322 5.1.1. $3.28.1.$ La_8NiGe_5 structure type 322 $3.28.2.$ La_3InGe structure type 323	$R_4(M,Ge)_3$ and $R_3(M,Ge)_2$ compounds 3225.1.1. Structure types with3.28.1. La_8NiGe_5 structure type322icosahedral coordination of3.28.2. La_3InGe structure type323the smallest atoms

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1. Introduction

The ternary systems of rare-earth metals with metallic and semimetallic components have been studied intensively during the last 20 years. Among them, the systems containing germanium are most completely investigated.

The preceding chapter (173) of this volume (Salamakha et al. 1999) is a review of ternary R-M-Ge systems which have been studied over the entire concentration region and which have been only partly investigated. The character of interaction in these systems varies, and major differences are seen in the number of ternary germanides observed within the investigated concentration range. This chapter is devoted to the description of the structure types and the crystal chemistry of the ternary (quaternary) germanides of the rare-earth metals.

The known structures of the germanides belong to 135 structure types. For each structure type the following information is presented:

- (i) chemical formula of the prototype;
- (ii) space group symbol and the number of formula units in the unit cell;
- (iii) lattice parameters (in nm) for the germanide (prototype or isotypic compound) on which the structure determination has been made and the appropriate reference;
- (iv) atomic positions and refined atomic coordinates; for compounds where statistical occupations of structure sites are observed, the various atoms are expressed as X, X1 etc. and additional data are presented;
- (v) projection of the structure and coordination polyhedra of the atoms;
- (vi) list of isotypic germanides; the unit cell dimensions and references for the isostructural compounds are presented in the preceding chapter (173) of this volume (Salamakha et al. 1999).

2. Influence of a third component on the fields of formation of ternary germanides

As R and Ge are components with much different crystallochemical properties (atomic size, electronic structure, electronegativity, etc.), the deciding factor that affects the formation, composition and structure, is the nature of the third component in the systems.

The ternary systems with two rare-earth metals and germanium are characterized by the formation of compounds with compositions $(R, R')_5$ Ge₄, $(R, R')_{11}$ Ge₁₀, (R, R')Ge and $(R, R')_2$ Ge which crystallize with the structure types of binary compounds and their superstructures. This is caused by the similarities in the electronic structure of R elements.

When the third component is a p element (Al, Ga, In, Si, Sn, Sb, Bi), the trends in formation of compounds are found to be maintained in the same R to Ge ratio as in the binary compounds. The compounds are characterized by a variable composition at constant R content, but in contrast to the R-R'-Ge systems, the compositions of compounds are more varied (fig. 1).

The main reason for the formation of a large number of ternary compounds in the R-M-Ge systems (M=s or d element) is the presence of components with significantly different crystallochemical properties (fig. 2).

Figures 1 and 2 presents only the compositions of compounds in which the crystal structure has been determined. In many cases, the substitution of a M component or a change in temperature leads to the formation of another structure (these compositions are marked with a square). In spite of the variety of compositions, one can see from fig. 2 that the predominant number of compounds are arranged on the lines connecting the elements with the binary phases of simple compositions (R–MGe, R–MGe₂ etc.).

The most favourable concentration for the formation of intermetallic compounds is 33 at.% of R (RM₂-RGe₂), particularly the composition RMGe. The compounds of equatomic composition crystallize in 20 structure types. The morphotropic transformation within the RMGe series occurs both if R is replaced by another R', and when the M component is changed.



Fig. 1. Composition triangle showing the existence of ternary compounds in the R–M–Ge systems when M is p-element.

Fig. 2. Composition triangle showing the existence of ternary compounds in the R-M-Ge systems when M is s- and d-element.

For a better demonstration of the influence of the R component on the formation of ternary germanides and their crystal chemistry, and for the improvement and simplification of the presentation of the crystallographic data of the compounds, we have characterised the composition of a given phase according to its R/(M, Ge) ratio, and arranged the structure types according to increasing rare-earth content in the next section of this chapter.

The same approach is used for the description of the quaternary germanides (sect. 4 of the present review). However, the literature data on the crystal structures of quaternary germanides are quite sparse.

3. Structure types of ternary rare-earth germanides

3.1. $R(M,Ge)_{13}$ compounds

3.1.1.	$NaZn_{13}$	structure	type

<u>50 rm</u>	50 mise, 2 = 6, u = 1.1571 for La(140.82000.18)(3)(maskov 1764)								
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)				
La	8(a)	1/4	1/4	1/4	100				
X1	8(b)	0	0	0	100				
X2	96(i)	0	0.1782	0.1151	100				

SG Fm3c, Z = 8, a = 1.1371 for La(Ni_{0.82}Ge_{0.18})₁₃ (Bruskov 1984)

X = 0.82Ni+0.18Ge

No isotypic compounds are known.

3.1.2. CeNi_{8.5}Si_{4.5} structure type

SG	I4/mcm.	Z=4.	a = 0.7932.	$c \approx 1.1817$	for Pr ₁	- CooGe	(Fedvna	et al.	1987)
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Wyckoff notation	x/a	y/b	z/c	G (%)	_
4(a)	0	0	1/4	69.3	
16(l)	0.1815	0.6815	0.1284	100	
16(l)	0.6273	0.1273	0.1668	100	
4(d)	0	1/2	0	100	
16(k)	0.0633	0.2002	0	100	
	Wyckoff notation 4(a) 16(l) 16(l) 4(d) 16(k)	Wyckoff notation         x/a           4(a)         0           16(l)         0.1815           16(l)         0.6273           4(d)         0           16(k)         0.0633	Wyckoff notationx/ay/b4(a)0016(l)0.18150.681516(l)0.62730.12734(d)01/216(k)0.06330.2002	Wyckoff notationx/ay/bz/c4(a)001/416(l)0.18150.68150.128416(l)0.62730.12730.16684(d)01/2016(k)0.06330.20020	Wyckoff notationx/ay/bz/cG (%)4(a)001/469.316(1)0.18150.68150.128410016(1)0.62730.12730.16681004(d)01/2010016(k)0.06330.20020100

Isotypic compounds:

 $RNi_{8.5}Ge_{4.5}^*$ : R = Ce, Pr, Nd, Sm, Eu

* In the  $RNi_{8.5}Ge_{4.5}$  compounds the site in Wyckoff position 4(d) is occupied by a statistical mixture  $Ni_{0.5}Ge_{0.5}$ .

The praseodymium atoms have coordination number 24 (fig. 3a). Coordination polyhedra for cobalt and germanium are the icosahedra and their derivatives (fig. 3b–e).



Fig. 3. Projection of the  $Pr_{1-x}Co_9Ge_4$  unit cell and coordination polyhedra of the atoms: (a) Pr, (b-e) Co, Ge.

3.2.  $R(M, Ge)_{12}$  compounds

3.2.1. $YCo_6Ge_6$ structure type	
SG P6/mmm, $Z = 1$ , $a = 0.5074$ , $c = 0.3908$ for YCo ₆ Ge ₆ (Buchholz and Schuster 1981)	I

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Y	1(a)	0	0	0	45	
Со	3(g)	1/2	0	1/2	100	
Ge1	2(e)	0	0	0.307	50	
Ge2	2(c)	1/3	2/3	0	100	

Isotypic compounds:

 $RMn_6Ge_6: R = Nd, Sm$ 

 $RFe_6Ge_6$ : R = Y, Pr-Sm, Gd-Lu

 $RCo_6Ge_6$ : R = Y, Sc, Gd–Lu

For yttrium atoms, polyhedra with 20 apexes are typical (fig. 4a). Those for cobalt and germanium atoms are the icosahedra and their derivatives (fig. 4b–d).

#### 3.2.2. $MgFe_6Ge_6$ (or $HfFe_6Ge_6$ ) structure type

SG P6/mmm, Z=1, a=0.52262, c=0.81653 for DyMn₆Ge₆ (Schöbinger-Papamantellos et al. 1994)

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)
Dy	1(a)	0	0	0	100



Fig. 4. Projection of the  $YCo_6Ge_6$  unit cell and coordination polyhedra of the atoms: (a) Y, (b-d) Co and Ge.

Mn	6(i)	1/2	0	0.2504	100
Gel	2(e)	0	0	0.3453	100
Ge2	2(d)	1/3	2/3	1/2	100
Ge3	2(c)	1/3	2/3	0	100

Isotypic compounds:

 $RCr_6Ge_6$ : R = Sc, Y, Tb-Er

 $RMn_6Ge_6$ : R = Sc, Y, Gd-Lu

 $RFe_6Ge_6$ : R = Sc, Yb, Lu

The coordination polyhedra for dysprosium atoms have 20 apexes (fig. 5a). For manganese and germanium atoms, icosahedra and their derivatives are typical (fig. 5b-e).

SG P6/mmm, $Z = 1$ , $a = 0.52333$ , $c = 0.81806$ (Belyavina et al. 1993)							
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)		
Gd1	1(a)	0	0	0	70		
Gd2	1(b)	0	0	1/2	30		
Mn	6(i)	1/2	0	0.25	100		
Gel	2(e)	0	0	0.3465	100		
Ge2	2(d)	1/3	2/3	1/2	100		
Ge3	2(c)	1/3	2/3	0	100		

3.2.3.  $GdMn_6Ge_6$  structure type

No isotypic compounds are observed.



Fig. 5. Projection of the  $DyMn_6Ge_6$ unit cell and coordination polyhedra of the atoms: (a) Dy, (b–e) Mn and Ge.

3.2.4. ScNi₆Ge₆ structure type

SG P6/mmm, $Z = 4$ , $a =$	1.0152, c = 0.7813	for ScNi ₆ Ge ₆	(Buchholz and a	Schuster 1981)	)
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Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)
Sc1	3(g)	1/2	0	1/2	100
Sc2	1(a)	0	0	0	100
Ni1	12(o)	0.247	0.494	0.250	100
Ni2	12(n)	0.238	0	0.258	100
Ge1	6(m)	0.162	0.324	1/2	100
Ge2	6(1)	0.160	0.320	0	100
Ge3	6(i)	1/2	0	0.158	100
Ge4	2(e)	0	0	0.340	100
Ge5	2(d)	1/3	2/3	1/2	100
Ge6	2(c)	1/3	2/3	0	100

No isotypic compounds are observed.

3.2.5. GdFe₆Ge₆ structure type

SG Pnma, a = 6.143, b = 0.8137, c = 7.979 (Venturini et al. 1992)

Atomic coordinates have not been determined.

# 3.2.6. TbFe₆Sn₆ structure type

SG Cmcm, Z=4, a=0.8116, b=1.7672, c=0.5120 for YFe₆Ge₆ (Venturini et al. 1992) Atomic coordinates for the germanides of this structure type have not been determined.

Isotypic compounds:  $RFe_6Ge_6$ : R = Tb-Ho

# 3.2.7. HoFe₆Sn₆ structure type

SG Immm, Z=6, a=0.8103, b=2.652, c=0.5108 for  $ErFe_6Ge_6$  (Venturini et al. 1992) Atomic coordinates for the germanides of this structure type have not been deter-

mined. Isotypic compound: RFe₆Ge₆: R=Tm

#### 3.3. $R_3(M, Ge)_{34}$ and $R_3(M, Ge)_{26}$ compounds

3.3.1. Ce₃Pt₂₃Ge₁₁ structure type

SG F $\overline{4}$ 3m, Z = 8, a = 1.71833 for Ce₃Pt₂₃Ge₁₁ (Gribanov et al. 1993a). See fig. 6.

Atom	Wyckoff notation	<i>x/a</i>	y/b	<i>z/c</i>	G (%)
Ce	24(g)	0.0018	1/4	1/4	100
Pt1	48(h)	0.0841	0.0841	0.2479	100
Pt2	24(f)	0.1281	0	0	100
Pt3	16(e)	0.1927	0.1927	0.1927	100
Pt4	16(e)	0.4139	0.4139	0.4139	100
Pt5	16(e)	0.5787	0.5787	0.5787	100
Pt6	16(e)	0.8098	0.8098	0.8098	100
Ge1	24(f)	0.3285	0	0	100
Ge2	16(e)	0.1075	0.1075	0.1075	100
Ge3	16(e)	0.3357	0.3357	0.3357	100
Ge4	16(e)	0.6672	0.6672	0.6672	100
Xa	48(h)	0.0847	0.0847	0.7541	100
Xb	16(e)	0.8962	0.8962	0.8962	100

Xa = 0.78Pt+0.22Ge, Xb = 0.20Pt+0.80Ge

No isotypic compounds are observed.

234



Fig. 6. Projection of the  $Ce_3Pt_{23}Ge_{11}$  unit cell and coordination polyhedra of the atoms: (a) Ce, (b-g) Pt, (h-k) Ge, (l) Xa, (m) Xb.

3.3.2.	$Ce_3Pd_{20}Ge_6$	structure type						
SG Fn	a3m, Z=4, a	= 1.24453 for	$Ce_3Pd_{20}Ge_6$	(Gribanov	et al.	1994).	See fig.	7.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Ce1	4(0)	0	0	0	100
Ce2	8(c)	1/4	1/4	1/4	100
Pd1	32(f)	0.38390	0.38390	0.38390	100



Fig. 7. Projection of the  $Ce_3Pd_{20}Ge_6$  unit cell and coordination polyhedra of the atoms: (a, b) Ce, (c, d) Pd, (e) Ge.

Pd2	48(h)	0	0.17479	0.17479	100
Ge	24(e)	0.2325	0	0	100

Isotypic compounds:  $R_3Pd_{20}Ge_6$ : R = Nd, Sm

#### 3.4. $R_2(M,Ge)_{17}$ compounds

#### 3.4.1. $Th_2Zn_{17}$ structure type

SG R $\overline{3}$ m, Z=3, a=0.8425–0.8433, c=1.2336–1.2368 for Sm₂Co_{15.1–14.1}Ge_{1.9–2.9} (Mruz 1988).

Atomic coordinates for this compound have not been determined.

#### 3.4.2. Ce₂Al₂Co₁₅ structure type

SG R $\overline{3}$ m, Z = 3, a = 0.9021, c = 1.3787 for Ce₂Zn₁₅Ge₂ (Opainych 1996) Atomic coordinates for this compound have not been determined.

3.4.3. SG Pm	3.4.3. $Nd_2Cr_9Ge_8$ structure type SG Pmma, $Z=2$ , $a=0.9388$ , $b=0.4046$ , $c=0.8045$ (Bodak et al. 1989a)									
Atom	Atom Wyckoff notation $x/a$ $y/b$ $z/c$ G (%)									
Nd	2(e)	1/4	0	0.6680	100	,m				

Crl	4(i)	0.1064	0	0.2973	100
Cr2	2(f)	1/4	1/2	0.0516	50
Cr3	2(d)	0	1/2	1/2	100
Cr4	2(a)	0	0	0	100
Ge1	4(k)	1/4	0.1587	0.0419	50
Ge2	4(j)	0.5387	1/2	0.1787	100
Ge3	<b>2</b> (f)	1/4	1/2	0.3780	100

No isotypic compounds are observed.



Fig. 8. Projection of the  $Nd_2Cr_9Ge_8$  unit cell and coordination polyhedra of the atoms: (a) Nd, (b-e) Cr, (f-h) Ge.

For neodymium atoms, polyhedra with 18 apexes are typical (fig. 8a). The chromium atom polyhedra are distorted cubo-octahedra and pentagonal prisms with additional atoms (fig. 8b–e). Those for germanium atoms are polyhedra with 11 apexes and pentagonal prisms with additional atoms (fig. 8f–h).

# 3.5. $R(M, Ge)_8$ compounds

3.5.1. YNi ₅ Si ₃	structure	type
-----------------------------------------	-----------	------

SG Pnma, Z = 4, a = 1.90183, b = 0.38398, c = 0.67867 for TmNi₅Ge₃ (Fedyna 1988)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Tm	4(c)	0.3542	1/4	0.878	100	
Ni1	4(c)	0.0021	1/4	0.390	100	
Ni2	4(c)	0.2070	1/4	0.067	100	
Ni3	4(c)	0.2008	1/4	0.691	100	
Ni4	4(c)	0.3854	1/4	0.365	100	
Ni5	4(c)	0.4864	1/4	0.591	100	
Ge1	4(c)	0.0765	1/4	0.645	100	
Ge2	4(c)	0.0884	1/4	0.090	100	
Ge3	4(c)	0.2598	1/4	0.380	100	

Isotypic compounds:

 $RNi_5Ge_3$ : R = Y, Gd-Lu

The coordination polyhedra for thulium atoms have 20 apexes (fig. 9a). The nickel atoms are situated inside polyhedra with 12 and 15 apexes (fig. 9b–f). For germanium atoms, trigonal prisms with three additional atoms are typical (fig. 9g–i).



Fig. 9. Projection of the TmNi₅Ge₃ unit cell and coordination polyhedra of the atoms: (a) Tm, (b-f)Ni, (g-i) Ge.

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)	
Tb	4(c)	0.2068	1/4	0.9131	100	
Mnl	4(c)	0.4807	1/4	0.7923	100	
Mn2	4(c)	0.9986	1/4	0.0888	100	
Mn3	4(c)	0.6852	1/4	0.2941	100	
Mn4	4(c)	0.1879	1/4	0.6180	100	
Mn5	4(c)	0.4366	1/4	0.0338	100	
Gel	4(c)	0.6211	1/4	0.0887	100	
Ge2	4(c)	0.3766	1/4	0.2406	100	
Ge3	4(c)	0.8796	1/4	0.9125	100	

3.5.2.  $YCo_5P_3$  structure type

SG Pnma, Z=4, a=1.3050, b=0.3904, c=1.1408 for TbMn₅Ge₃ (Venturini and Malaman 1997)

No isotypic compounds are observed.

# 3.6. $R(M, Ge)_6$ compounds

# 3.6.1. ZrFe₄Si₂ structure type

SG P4₂/mnm, Z = 2, a = 0.72472, c = 0.38705 for TmFe₄Ge₂ (Fedyna 1988)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Tm	2(a)	0	0	0	100
Fe	8(i)	0.086	0.353	0	100
Ge	4(f)	0.215	0.215	1/2	100

Isotypic compounds:

 $RFe_4Ge_2$ : R = Y, Dy-Lu

 $RCo_4Ge_2$ : R = Er-Lu

Thulium atoms are situated inside the polyhedra with 20 apexes (fig. 10a). The coordination polyhedra of iron atoms are deformed cubo-octahedra (fig. 10b). The germanium atoms have an environment in a form of trigonal prism with three additional atoms (fig. 10c).



Fig. 10. Projection of the  $TmFe_4Ge_2$  unit cell and coordination polyhedra of the atoms: (a) Tm, (b) Fe, (c) Ge.

3.6.2.  $SmNi_3Ge_3$  structure type SG I4/mmm, Z=4, a=0.40659, c=2.5137 (Mruz et al. 1990)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Sm	4(e)	0	0	0.3465	100
Ni1	8(g)	0	1/2	0.0553	100
Ni2	4(e)	0	0	0.1999	100
Ge1	4(e)	0	0	0.1063	100
Ge2	4(d)	0	1/2	1/4	100
Ge3	2(b)	0	0	1/2	100
Ge4	2(a)	0	0	0	100

No isotypic compounds are observed.

The coordination numbers for the Sm atoms are 22 (fig. 11a). The coordination polyhedra for the Ni atoms are tetragonal antiprisms with one additional atom and distorted cubo-octahedra with one additional apex (fig. 11b, c); those for Ge atoms are tetragonal antiprisms with two additional atoms and distorted cubo-octahedra with two additional atoms and distorted cubo-octahedra with two additional apexes (fig. 11d–g).



Fig. 11. Projection of the  $SmNi_3Ge_3$  unit cell and coordination polyhedra of the atoms: (a) Sm, (b–c) Ni, (d–g) Ge.

) Atom Wyckoff notation x/ay/bz/cG (%) Eu 4(c) 0 0.442 1/4 100 Mg1 4(c) 0 0.650 1/4100 Mg2 4(c) 0.750 1/4 100 0 Mg3 4(c) 0.855 1/4 100 0 Ge1 4(c) 0 0.017 1/4100 Ge2 4(c) 0.098 1/4 100 0 Ge3 4(c)0 0.303 1/4 100

3.6.	$3. EuMg_3Ge_3$	structure ty	pe				
SG	Cmcm, $Z = 4$ ,	a=0.4485,	<i>b</i> = 3.060,	c = 0.4485	(Zmii	et al.	1973)

No isotypic compounds are observed.



Fig. 12. Projection of the  $EuMg_3Ge_3$  unit cell and coordination polyhedra of the atoms: (a) Eu, (b–d) Mg, (e–g) Ge.

The coordination polyhedra for europium atoms have 20 apexes (fig. 12a). Magnesium atoms are situated in the centre of the tetragonal prisms with additional atoms (fig. 12b, c)

and trigonal prisms with additional atoms (fig. 12d). Coordination polyhedra in the form of trigonal prism, tetragonal antiprism and cubo-octahedra are typical for the germanium atoms (fig. 12e–g).

#### 3.7. $R_3(M, Ge)_{17}$ compounds

3.7.1.  $Yb_3Rh_4Sn_{13}$  structure type SG Pm3n, Z=2, a=0.8962 for Y₃Ru₄Ge₁₃ (Segre et al. 1981). See fig. 13.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Y	6(c)	1/4	0	1/2	100
Ru	8(e)	1/4	1/4	1/4	100
Gel	24(k)	0	0.15333	0.30570	100
Ge2	2(a)	0	0	0	100

Isotypic compounds:

 $R_3Co_4Ge_{13}$ : R = Y, Sm, Gd–Lu

 $R_3Ru_4Ge_{13}$ : R = Y, Ce–Sm, Gd–Lu

 $R_3Rh_4Ge_{13}$ : R = Y, Nd, Sm, Gd–Lu

 $R_3Os_4Ge_{13}$ : R = Y, Ce–Sm, Gd–Lu

 $R_3Ir_4Ge_{13}$ : R = Y, Ce–Sm, Gd–Lu



Fig. 13. Projection of the Y₃Ru₄Ge₁₃ unit cell and coordination polyhedra of the atoms: (a) Y, (b) Ru, (c, d) Ge.
243



Fig. 14. Two types of unit cells in the  $Y_3Co_4Ge_{13}$  structure and coordination polyhedra of the atoms.

d

3.7.2. $Y_3Co_4Ge_{13}$ structure type SG Pm3n, Z = 2, a = 0.8769 (Bruskov et al. 1986). See fig. 14.									
Atom Wyckoff notation $x/a$ $y/b$ $z/c$ G (%)									
Y	6(c)	1/4	0	1/2	100				
Co	8(e)	1/4	1/4	1/4	100				

244		P.S	5. SALAMAKHA		
Ge1	24(k)	0	0.142	0.273	42
Ge2	24(k)	0	0.161	0.327	58
Ge3	2(a)	0	0	0	100

This structure type differs from the Yb₃Rh₄Sn₁₃ type by the splitting of the site in Wyckoff position 24(k). Isotypic compounds:  $R_3Co_4Ge_{13}$ : R = Y, Gd-Lu  $R_3Ru_4Ge_{13}$ : R = Ce, Nd  $R_3Os_4Ge_{13}$ : R = Nd, Ho

### 3.8. $R_2(M, Ge)_{11}$ compounds

3.8.1.  $Ce_2Pt_7Ge_4$  structure type SG Pnma, Z=4, a=1.9866, b=0.4089, c=1.1439 (Gribanov et al. 1992a)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Cel	4(c)	0.0281	1/4	0.7437	100
Ce2	4(c)	0.2199	1/4	0.5122	100
Pt1	4(c)	0.0351	1/4	0.0604	100
Pt2	4(c)	0.0412	1/4	0.4534	100
Pt3	4(c)	0.2139	1/4	0.1836	100
Pt4	4(c)	0.3465	1/4	0.2449	100
Pt5	4(c)	0.3664	1/4	0.8671	100
Pt6	4(c)	0.3707	1/4	0.6198	100
Pt7	4(c)	0.6610	1/4	0.5527	100
Ge1	4(c)	0.0942	1/4	0.2534	100
Ge2	4(c)	0.2440	1/4	0.7935	100
Ge3	4(c)	0.4123	1/4	0.0631	100
Ge4	4(c)	0.4144	1/4	0.4225	100

No isotypic compounds have been observed.

For cerium atoms, polyhedra with 22 and 21 apexes are typical (fig. 15a,b). The platinum atom polyhedra are distorted cubo-octahedra (fig. 15c-i). Trigonal prisms with additional atoms are typical for germanium atoms (fig. 15j-m).





3.8.2. E	$Ho_4 Ir_{13} Ge_9$	structure	type
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SG Pmmn, Z = 2, a = 0.3954, b = 1.1186, c = 1.9301 (Sologub et al. 1993)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Hol	4(e)	1/4	0.5591	0.70745	100
Ho2	2(b)	1/4	3/4	0.5216	100
Ho3	2(a)	1/4	1/4	0.0194	100
Ir1	4(e)	1/4	0.0497	0.54578	100
Ir2	4(e)	1/4	0.0673	0.16441	100
Ir3	4(e)	1/4	0.1227	0.85460	100
Ir4	4( <i>e</i> )	1/4	0.5589	0.04021	100
Ir5	4(e)	1/4	0.6265	0.35825	100
Ir6	2(b)	1/4	3/4	0.84250	100
Ir7	2(a)	1/4	1/4	0.3585	100
Ir8	2(a)	1/4	1/4	0.72724	100
Ge6	2(a)	1/4	1/4	0.5998	100
Ge1	4(e)	1/4	0.0646	0.4183	100
Ge2	4(e)	1/4	0.5705	0.9160	100
Ge3	4(e)	1/4	0.6195	0.2314	100
Ge4	2(b)	1/4	3/4	0.1012	100
Ge5	2(a)	1/4	1/4	0.2352	100

 $R_4Rh_{13}Ge_9:R=Y, La-Sm, Gd-Lu$ 

 $R_4Ir_{13}Ge_9:R=Y, La-Sm, Gd-Lu$ 

The coordination polyhedra of the holmium atoms have 20 apexes (fig. 16a-c). Those of iridium are tetragonal prisms with five additional atoms and distorted cubo-octahedra (fig. 16d-k). The coordination polyhedra of germanium atoms are trigonal prisms with three additional atoms (fig. 161-q).



Fig. 16. Projection of the  $Ho_4Ir_{13}Ge_9$  unit cell and coordination polyhedra of the atoms: (a–c) Ho, (d–k) Ir, (l-q) Ge.

### 3.9. $R(M, Ge)_5$ compounds

## 3.9.1. CaCu₅ structure type

SG P6/mmm, Z=1, a=0.5296, c=0.4413 for SmPt_{4.4}Ge_{0.6} (Barakatova 1994) Atomic coordinates for this compound have not been determined.

# 3.9.2. $Sc_3Ni_{11}Si_4$ structure type

SG P6 ₃ /mmc, $Z = 2$ , $a = 0.8321$ , $c =$	$0.8832 \text{ for } Tm_3Ni_{11}Ge_4$	(Fedyna 1988)	. See fig. 17.
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Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Tm	6(h)	0.1883	0.3766	1/4	100	
Ni1	12(k)	0.1719	0.344	0.594	100	
Ni2	6(h)	0.537	0.075	1/4	100	
Ni3	<b>4</b> (f)	1/3	2/3	0.073	100	
Ge1	6(g)	1/2	0	0	100	
Ge2	2(b)	0	0	1/4	72	

Isotypic compounds:

 $R_3Ni_{11}Ge_4$ : R = Tb-Lu, Y



Fig. 17. Projection of the  $Tm_3Ni_{11}Ge_4$  unit cell and coordination polyhedra of the atoms: (a) Tm, (b-d) Ni, (e, f) Ge.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)			
Sc	6(h)	0.190	0.380	1/4	100			
Ni1	12(k)	0.162	0.324	0.581	100			
Ni2	6(h)	0.555	0.110	1/4	100			
Ni3	4(f)	1/3	2/3	0.008	100			
Ge1	6(g)	1/2	0	0	100			
Ge2	2(b)	0	0	1/4	72			
Ge3	2(a)	0	0	0	28			

3.9.3.  $Sc_3Ni_{11}Ge_4$  structure type SG P6₃/mmc, Z=2, a=0.8130, c=0.8505 (Andrusyak 1988)

No isotypic compounds are observed.

The 2(a) atomic position, which is partly occupied in this structure, is vacant in the previous structure type.

## 3.9.4. ErNi₃Ge₂ structure type

SG P $\overline{6}$ , Z = 12, a = 1.79662, c = 0.37941 (Oleksyn and Bodak 1994). See fig. 18.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Er1	3(k)	0.0088	0.5756	1/2	100	
Er2	3(k)	0.0969	0.3366	1/2	100	
Er3	3(k)	0.3345	0.1678	1/2	100	





P.S. SALAMAKHA

Er4	1(e)	2/3	1/3	0	100
Er5	1(d)	1/3	2/3	1/2	100
Er6	1(a)	0	0	0	100
Ni1	3(k)	0.0906	0.1590	1/2	100
Ni2	3(k)	0.2404	0.2725	1/2	100
Ni3	3(k)	0.4229	0.0487	1/2	100
Ni4	3(k)	0.5817	0.1831	1/2	100
Ni5	3(j)	0.0571	0.4509	0	100
Ni6	3(j)	0.1759	0.6205	0	100
Ni7	3(j)	0.1918	0.0037	0	100
Ni8	3(j)	0.1962	0.1541	0	100
Ni9	3(j)	0.2168	0.4970	0	100
Ni10	3(j)	0.2602	0.3850	0	100
Ni11	3(j)	0.4650	0.1803	0	100
Ni12	3(j)	0.4747	0.3216	0	100
Ge1	3(k)	0.1405	0.5176	1/2	100
Ge2	3(k)	0.1480	0.0690	1/2	100
Ge3	3(k)	0.2827	0.4804	1/2	100
Ge4	3(k)	0.5217	0.2772	1/2	100
Ge5	3(j)	0.1457	0.2482	0	100
Ge6	3(j)	0.3272	0.2933	0	100
Ge7	3(j)	0.3363	0.0410	0	100
Ge8	3(j)	0.5241	0.0859	0	100

No isotypic compounds are observed.

# 3.9.5. ErCo₃Ge₂ structure type

SG P6₃/mcm, Z=2, a=0.5091, c=0.7861 for  $Er_{6-x}Co_6Ge_4$  (x=3.94) (Bodak et al. 1990)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Er1	4(e)	0	0	0.1533	27	-
Er2	2(b)	0	0	0	48	
Co	6(g)	0.4813	0	1/4	100	
Ge	4(d)	1/3	2/3	0	100	

Isotypic compound:  $\operatorname{Er}_{6-x}\operatorname{Fe}_6\operatorname{Ge}_4(x=4.17)$ 

250

### 3.10. $R(M, Ge)_{\sim 4.5}$ compounds

3.10.1. Sc₆Ni₁₈Si₁₁ structure type

SG Immm, Z=4, a=1.8322, b=1.2461, c=0.8191 for Sc₆Ni₁₈Ge₁₁ (Andrusyak and Kotur 1987)

Atom	Wyckoff notation	<i>x/a</i>	<i>y/b</i>	z/c	G (%)
Sc1	8(n)	0	0.1828	0.2036	100
Sc2	8(1)	0	0.1820	0.2804	100
Sc3	4(i)	0	1/2	0.1280	100
Sc4	4(i)	0	1/2	0.3079	100
Ni1	16(o)	0.1664	0.3471	0.21772	100
Ni2	16(o)	0.2169	0.1499	0.41399	100
Ni3	8(m)	0.8372	0	0.7916	100
Ni4	8(m)	0.7325	0	0.9237	100
Ni5	8(1)	0	0.3326	0.4230	100
Ni6	8(1)	0	0.0988	0.1139	100
Ni7	4(j)	0	0	0.4321	100
Ni8	4(h)	0	0.3798	0	100
Ge1	16(o)	0.2647	0.16866	0.15669	100
Ge2	8(m)	0.1810	0	0.33157	100
Ge3	8(1)	0	0.2864	0.11457	100
Ge4	4(g)	0	0.6772	1/2	100
Ge5	4(f)	0.7290	0	1/2	100
Ge6	2(b)	1/2	1/2	0	100
Ge7	2(a)	0	0	0	100

No isotypic compounds have been observed.

# 3.10.2. Nb₂Cr₄Si₅ structure type

SG Ibam, Z=4, a=0.7821, b=1.6662, c=0.5146 for the Sc₂Cr₄Ge₅ compound (Andrusyak 1988)

Atomic coordinates have not been determined.

3.1	1.1.	CeGa2Al	₂ structure	type
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SG I4/mmm, Z = 2, a = 0.4042, c = 1.0183 for NdCo₂Ge₂ (Salamakha 1989)

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Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)	
Nd	2(a)	0	0	0	100	
Со	4(d)	0	1/2	1/4	100	
Ge	4(e)	0	0	0.387	100	

Isotypic compounds:  $RMn_2Ge_2$ : R=Y, La-Sm, Gd-Yb  $RFe_2Ge_2$ : R=Y, La-Sm, Gd-Lu  $RCo_2Ge_2$ : R=Y, La-Yb  $RNi_2Ge_2$ : R=Y, La-Lu  $RCu_2Ge_2$ : R=Y, La-Lu  $RRu_2Ge_2$ : R=Y, La-Lu  $RRh_2Ge_2$ : R=Y, La-Lu  $RPd_2Ge_2$ : R=Y, La-Lu  $RAg_2Ge_2$ : R=La-Gd  $RPt_2Ge_2$ : R=Y, La-Dy, Er  $RAu_2Ge_2$ : R=Ce, Nd

For neodymium atoms, polyhedra with 22 apexes are typical (fig. 19a). The cobalt atom polyhedra are distorted cubo-octahedra (fig. 19b). Tetragonal antiprisms with one additional atom are typical for germanium atoms (fig. 19c).



Fig. 19. Projection of the NdCo₂Ge₂ unit cell and coordination polyhedra of the atoms: (a) Nd, (b) Co, (c) Ge.

SG P4/	SG P4/nmm, $Z=2$ , $a=0.4246$ , $c=1.0098$ for CeIr ₂ Ge ₂ (Mathur and Frost 1994)							
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)			
Ce	2(c)	1/4	1/4	0.749	100			
Ir1	2(c)	1/4	1/4	0.368	100			
Ir2	2(a)	3/4	1/4	0	100			
Ge1	2(c)	1/4	1/4	0.108	100			
Ge2	2(b)	3/4	1/4	1/2	100			

3.11.2.  $CaBe_2Ge_2$  structure type

Isotypic compounds:

 $RIr_2Ge_2$ : R = La - Tb

For the cerium atoms, coordination polyhedra have 22 apexes (fig. 20a). Iridium and germanium atoms have an environment in the form of distorted cubo-octahedra and tetragonal antiprisms with one additional atom (fig. 20b-e).



Fig. 20. Projection of the CeIr₂Ge₂ unit cell and coordination polyhedra of the atoms: (a) Ce, (b-e) Ir and Ge.

	, , , ,	,	× 1			,
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
La	2(a)	0.2631	0.0151	0.7449	100	
Pt1	2(a)	02559	0.0483	0.3790	100	
Pt2	2(a)	0.2680	0.4650	0.0016	100	
Ge1	2(a)	0.2647	0.0000	0.1267	100	
Ge2	2(a)	0.2727	0.5687	0.5049	100	

3.11.3. LaPt₂Ge₂ structure type

SG P2₁, Z = 2, a = 0.4404, b = 0.4421, c = 0.9851,  $\beta = 90.50^{\circ}$  (Venturini et al. 1989a)

 $RPt_2Ge_2$ : R = La - Dy

The coordination polyhedra of the lanthanum atoms have 22 apexes (fig. 21a). Those of platinum and germanium are tetragonal antiprisms with one additional atom and distorted cubo-octahedra (fig. 21b-e).



Fig. 21. Projection of the LaPt₂Ge₂ unit cell and coordination polyhedra of the atoms: (a) Ce, (b-e) Ir and Ge.

### 3.11.4. CaAl₂Si₂ structure type

SG P3m1, Z=1, a=0.4271, c=0.6947 for CeAl₂Ge₂ (Zarechnyuk et al. 1970). See fig. 22.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Ce	1(a)	0	0	0	100	
Al	2(d)	1/3	2/3	0.63	100	



Isotypic compounds:  $RAl_2Ge_2$ : R = Y, La-Lu



Fig. 22. Projection of the  $CeAl_2Ge_2$ unit cell and coordination polyhedra of the atoms: (a) Ce, (b) Al, (c) Ge.

3.11.5.  $U_2Co_3Si_5$  structure type

SG Ibam, Z=4, a=0.9783, b=1.1896, c=0.5831 for  $Pr_2Co_3Ge_5$  (Fedyna et al. 1987). See fig. 23.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Pr	8(j)	0.2726	0.3602	0	100
Co1	8(j)	0.114	0.120	0	100
Co2	4(b)	1/2	0	1/4	100
Gel	8(j)	0.3467	0.096	0	100
Ge2	8(g)	0	0.250	1/4	100
Ge3	4(a)	0	0	1/4	100

Isotypic compounds:

 $R_2Co_3Ge_5$ : R = Y, Ce–Nd, Tb  $R_2Ni_3Ge_5$ : R = Ce, Pr  $R_2Ru_3Ge_5$ : R = La–Sm, Gd–Tm  $R_2Rh_3Ge_5$ : R = La–Pr  $R_2Ir_3Ge_5$ : R = La–Sm, Gd–Dy



Fig. 23. Projection of the  $Pr_2Co_3Ge_5$  unit cell and coordination polyhedra of the atoms: (a) Pr, (b,c) Co, (d-f) Ge.

3.11.6.  $Lu_2Co_3Si_5$  structure type SG C2/c, Z=4, a=1.1353, b=1.1976, c=0.5813  $\beta$ =119.05° for Ho₂Rh₃Ge₅ (Venturini et al. 1986). See fig. 24.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Но	8(f)	0.2695	0.1370	0.2664	100
Rh1	8(f)	0.1001	0.3576	0.1172	100
Rh2	4(e)	0	0.0013	1/4	100
Ge1	8(f)	0.3313	0.4041	0.3319	100
Ge2	4(e)	0	0.2114	1/4	100
Ge3	4(e)	0	0.5071	1/4	100
Ge4	4(e)	0	0.7796	1/4	100

 $R_2Co_3Ge_5$ : R = Pr-Sm, Gd-Er

 $R_2Rh_3Ge_5$ : R = Nd–Sm, Gd–Tm



Fig. 24. Projection of the  $Ho_2Rh_3Ge_5$  unit cell and coordination polyhedra of the atoms: (a) Ho, (b,c) Rh, (d-g) Ge.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Sm	4(j)	0	0.3318	1/2	100
Ni	4(i)	0	0.1092	0	100
Gel	4(j)	0	0.0568	1/2	100
Ge2	4(i)	0	0.2164	0	100
Ge3	4(i)	0	0.4433	0	100

3.11.7. SmNiGe₃ structure type

SG Cmmm, Z = 4, a = 0.4102, b = 2.1657, c = 0.4092 (Bodak et al. 1985)

RNiGe₃: R = Y, Ce–Sm, Gd–Tm

RGaGe₃: R = Y, Gd

The coordination polyhedra with 20 apexes are typical for samarium atoms (fig. 25a). Those for nickel atoms are tetragonal antiprisms (fig. 25b). The germanium coordination polyhedra are trigonal prisms (fig. 25c-e).



Fig. 25. Projection of the SmNiGe₃ unit cell and coordination polyhedra of the atoms: (a) Sm, (b) Ni, (c-e) Ge.

3.11.8.  $BaNiSn_3$  structure type SG I4mm, Z=2, a=0.4350, c=0.9865 for LaCoGe₃ (Venturini et al. 1985)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
La	2(a)	0	0	0.5759	100	
Co	2(a)	0	0	0.2313	100	
Ge1	2(a)	0	0	0.0000	100	
Ge2	4(b)	0	1/2	0.3253	100	

RCoGe₃: R = Ce-Eu, Yb

RRhGe₃: R = La - Pr, Eu

RIrGe₃: R = La, Eu

RRuGe₃: R = La

 $ROsGe_3: R = La$ 

The coordination number of lanthanum atoms is 21 (fig. 26a). Cobalt atoms have the coordination polyhedra in a form of tetragonal antiprisms (fig. 26b). Germanium atoms are situated inside the tetragonal antiprisms and distorted cubo-octahedra (fig. 26c, d).

### 3.12. $R_2(M, Ge)_7$ compounds

### 3.12.1. Ba₂Cd₃Bi₄ structure type

SG Cmca, Z=4, a=0.6143, b=1.5193, c=0.8035 for La₂Al₃Ge₄ (Zhao and Parthé 1991c). See fig. 27.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
La	8(f)	0	0.11389	0.4170	100	
Al1	8(e)	1/4	0.2842	1/4	100	



Fig. 26. Projection of the LaCoGe₃ unit cell and coordination polyhedra of the atoms: (a) La, (b) Co, (c-d) Ge.



Fig. 27. Projection of the  $La_2Al_3Ge_4$  unit cell and coordination polyhedra of the atoms: (a) La, (b,c) Al, (d,e) Ge.

Al2	4(a)	0	0	0	100
Ge1	8(f)	0	0.1873	0.0531	100
Ge2	8(e)	1/4	0.4512	1/4	100

Isotypic compounds:  $R_2Al_3Ge_4$ : R = Ce-Sm, Gd-Er

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Ce	8(d)	0.0039	0.5949	0.1767	61
Sc1	8(d)	0.157	0.3757	0.333	100
Sc2	4(c)	0.183	3/4	0.499	100
Ge1	8(d)	0.3153	0.4593	0.0395	100
Ge2	4(c)	0.9556	3/4	0.8754	100
Ge3	4(c)	0.310	3/4	0.139	100

3.12.2.  $Ce_2Sc_3Si_4$  structure type

SG Pnma, Z = 4, a = 0.7188, b = 1.339, c = 0.7416 Ce_{1.22}Sc₃Ge₄ (Shpyrka 1990)

 $R_{2-x}Sc_3Ge_4$ : R = La-Sm

 $R_2Nb_3Ge_4$ : R = Sc, Y, Gd–Lu

 $R_2Mo_3Ge_4$ : R = Sc, Y, Tb-Tm, Lu

Sc₂V₃Ge₄

3.12.3. Ce₂CuGe₆ structure type

SG Amm2, Z=2, a=0.40756, b=0.42152, c=2.15408 (Konyk et al. 1988)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Cel	2(b)	1/2	0	0.218	100	
Ce2	2(b)	1/2	0	0.885	100	
Cu	2(a)	0	0	0.451	100	
Ge1	2(b)	1/2	0	0.498	100	
Ge2	2(b)	1/2	0	0.610	100	
Ge3	2(a)	0	0	0.000	100	
Ge4	2(a)	0	0	0.115	100	
Ge5	2(a)	0	0	0.344	100	
Ge6	2(a)	0	0	0.772	100	

Isotypic compounds:

 $R_2CoGe_6$ : R = Y, Gd–Tm, Lu

 $R_2NiGe_6$ : R = Y, Ce-Sm, Gd-Lu

 $R_2PdGe_6$ : R = Y, La–Sm, Gd–Yb

 $R_2PtGe_6: R = Y, La-Sm, Gd-Yb$ 

 $R_2CuGe_6$ : R = Ce-Sm, Gd-Yb

 $R_2AgGe_6$ : R = La–Sm, Gd

 $R_2AuGe_6$ : R = Ce-Sm, Gd-Dy

Polyhedra with 16 and 20 apexes are typical for the cerium atoms (fig. 28a, b). Atoms of cooper are situated inside the tetragonal antiprisms, formed by the atoms of cerium and

260

germanium (fig. 28c). The germanium coordination polyhedra are trigonal prisms with two and three additional atoms, tetragonal antiprisms with additional atoms, distorted cubo-octahedra and polyhedra with 7 apexes (fig. 28d–i).



Fig. 28. Projection of the  $Ce_2CuGe_6$  unit cell and coordination polyhedra of the atoms: (a,b) Ce, (c) Cu, (d-i) Ge.



Fig. 29. Projection of the  $Pr_2LiGe_6$  unit cell and coordination polyhedra of the atoms: (a) Pr, (b) Li, (c-e) Ge.

## 3.12.4. $Pr_2LiGe_6$ structure type

SG Cmmm, Z=2, a=0.41268, b=2.10520, c=0.43455 (Pavlyuk et al. 1988a). See fig. 29.

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)
Pr	4(i)	0	0.1657	0	100
Li	2(a)	0	0	0	100

262		P.S. SA	LAMAKHA		
Gel	4(j)	0	0.0579	1/2	100
Ge2	4(j)	0	0.2861	1/2	100
Ge3	4(i)	0	0.4431	0	100

Ce2LiGe6, Y2.25Ga0.67Ge6.08

### 3.12.5. $Ce_2(Ga, Ge)_7$ structure type

SG Cmca, Z = 8, a = 0.86373, b = 0.82697, c = 2.1451 for Ce₂Ga_{0.7}Ge_{6.3} (Yarmolyuk et al. 1989). See fig. 30.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Ce	16(g)	0.2511	0.3780	0.08185	100
X1	16(g)	0.2843	0.1240	0.19385	100
X2	8(f)	0	0.1186	0.4591	100
X3	8(f)	0	0.1231	0.1478	100
X4	8(f)	0	0.1309	0.0298	100
X5	8(f)	0	0.3357	0.3057	100
X6	8(f)	0	0.4123	0.1935	100

X = 0.1Ga + 0.9Ge

Isotypic compound: Nd₂(Ga, Ge)₇



Fig. 30. Projection of the  $Ce_2Ga_{0.7}Ge_{6.3}$  unit cell and coordination polyhedra of the atoms: (a) Ce, (b–g) X.



Fig. 31. Projection of the La₂AlGe₆ unit cell and coordination polyhedra of the atoms: (a) La, (b) Al, (c-g) X1, X2, X3, Ge1 and Ge2.

3.12.6.  $La_2AlGe_6$  structure type SG C2/m, Z=4, a=0.8373, b=0.8833, c=1.0887,  $\beta$ =101.34° (Zhao et al. 1991). See fig. 31.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
La	8(j)	0.08527	0.24828	0.33612	100
Al	4(i)	0.8006	0	0.1952	100
<b>X</b> 1	4(i)	0.0694	0	0.1123	100
X2	8(j)	0.2783	0.2131	0.1125	100
X3	4(i)	0.4869	0	0.1133	100
Ge1	4(i)	0.1460	0	0.5640	100
Ge2	4(i)	0.3597	0	0.4195	100

X1=0.23Al+0.77Ge; X2=0.09Al+0.91Ge; X3=0.19Al+0.81Ge

Isotypic compounds:

 $R_2AlGe_6: R = Ce-Sm, Gd$ 

 $R_2(Ga, Ge)_7$ : R = Y, Gd

3.13.  $R_3(M, Ge)_{10}$  and  $R_4(M, Ge)_{13}$  compounds

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Ce1	4(c)	0	0.1575	1/4	100	
Ce2	4(c)	0	0.5292	1/4	50	
Pt1	4(c)	0	0.29577	1/4	100	
Pt2	4(c)	0	0.93714	1/4	100	
Ge1	8(g)	0.201	0.0356	1/4	50	
Ge2	4(c)	0	0.3898	1/4	100	
Ge3	4(c)	0	0.7505	1/4	100	

3.13.1.  $Ce_3Pt_4Ge_6$  structure type

SG Cmcm, Z=2, a=0.4419, b=2.6222, c=0.4422 (Gribanov et al. 1992b)

Isotypic compound: Sm₃Pt₄Ge₆

For the cerium atoms, polyhedra with 21 and 19 apexes are typical (fig. 32a,b). The polyhedra for platinum atoms are trigonal prisms with four additional atoms and tetragonal antiprisms with two additional atoms (fig. 32c, d). The germanium coordination polyhedra are deformed cubooctahedra and trigonal prisms with three additional atoms (fig. 32e-g).



Fig. 32. Projection of the  $Ce_3Pt_4Ge_6$  unit cell and coordination polyhedra of the atoms: (a,b) Ce, (c,d) Pt, (e-g) Ge.



Fig. 33. Projection of the  $Y_3Pt_4Ge_6$  unit cell and coordination polyhedra of the atoms: (a-c) Y, (d-g) Pt, (h-m) Ge.

3.13.2.  $Y_3Pt_4Ge_6$  stucture type SG P2₁/m, Z=2, a=0.86922, b=0.43062, c=1.31615,  $\beta$ =99.45° (Venturini and Malaman 1990). See fig. 33.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Y1	2(e)	0.0673	1/4	0.8128	100	
Y2	2(e)	0.5889	1/4	0.8135	100	
Y3	2(e)	0.7653	1/4	0.5604	100	
Pt1	2(e)	0.1496	1/4	0.0883	100	
Pt2	2(e)	0.4672	1/4	0.3751	100	
Pt3	2(e)	0.6473	1/4	0.1008	100	
Pt4	2(e)	0.9703	1/4	0.3747	100	
Ge1	2(e)	0.1191	1/4	0.5685	100	
Ge2	2(e)	0.1945	1/4	0.2782	100	
Ge3	2(e)	0.3777	1/4	0.9999	100	

266		P.S. SA	LAMAKHA		
Ge4	2(e)	0.4145	1/4	0.5691	100
Ge5	2(e)	0.6957	1/4	0.2823	100
Ge6	2(e)	0.8738	1/4	0.0042	100

No isotypic compounds have been observed.

# 3.13.3. $U_4Re_7Si_6$ structure type

SG Im $\overline{3}$ m, Z=2, a=0.81255 for Sc₄Rh₇Ge₆ (Engel et al. 1984). See fig. 34.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Sc	8(c)	1/4	1/4	1/4	100
Rh1	12(d)	1/4	0	1/2	100
Rh2	2(a)	0	0	0	100
Ge	12(e)	0.3128	0	0	100

Isotypic compounds:  $Sc_4M_7Ge_6$ : M = Co, Ru, Ir, Os  $R_4Rh_7Ge_6$ : R = Y, Dy-Lu  $R_4Ir_7Ge_6$ : R = Y, Tb-Lu  $R_4Os_7Ge_6$ : R = Y, Er-Lu



Fig. 34. Projection of the  $Sc_4Rh_7Ge_6$  unit cell and coordination polyhedra of the atoms: (a) Sc, (b, c) Rh, (d) Ge.



Fig. 35. Projection of the  $HoPd_2Ge$  unit cell and coordination polyhedra of the atoms: (a) Ho, (b) Pd, (c) Ge.

#### 3.14. $R(M, Ge)_3$ compounds

### 3.14.1. YPd₂Si structure type

SG Pnma, Z=4, a=0.7321, b=0.7045, c=0.5563 for HoPd₂Ge (Sologub 1995). See fig. 35.

Atom	Wyckoff notation	<i>x/a</i>	<i>y/b</i>	z/c	G (%)
Ho	4(c)	0.6472	1/4	0.0324	100
Pd	8(d)	0.0948	0.0537	0.1789	100
Ge	4(c)	0.3560	1/4	0.3646	100

Isotypic compounds:

 $RPd_2Ge: R = Y, La-Sm, Gd-Tm, Lu$ 

# 3.14.2. AlCr₂C structure type

SG P6₃/mmc, Z=2, a=0.4537, c=0.7568 for CeLi₂Ge (Pavlyuk 1993)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Ce	2(a)	0	0	0	100	
Li	4(f)	1/3	2/3	0.625	100	
Ge	2(c)	1/3	2/3	1/4	100	

Isotypic compounds:

 $RLi_2Ge: R = La-Nd$ 



Fig. 36. Projection of the  $CeSn_{3-x}$ Ge unit cell and coordination polyhedra of the atoms: (a) Ce, (b) Sn, (c) X, (d) Ge.

3.14.3. ZrAl₃ structure type

SG I4/mmm, Z = 4, a = 0.4014, c = 1.7320 for  $\text{CeSn}_{3-x}\text{Ge}_x$  (Stetskiv 1999). See fig. 36.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Ce	4(e)	0	0	0.1284	100	
Sn	4(d)	0	1/2	1/2	100	
Х	4(c)	0	1/2	0	100	
Ge	4(e)	0	0	0.3695	100	

X = 0.90Sn+0.10GeIsotypic compounds:  $RSn_{3-x}Ge_x$ : R = La, Pr, Sm  $CeBi_2Ge$ 

#### 3.14.4. TiAl₃ structure type

SG I4/mmm, Z=2, a=0.4619, c=0.9233 for  $PrSn_{3-x}Ge_x$  (HT modification) (Stetskiv 1999)

Atomic coordinates have not been determined for this germanide.

3.14.5. Ce₂Cu₃Ge₃ structure type

$SU \subseteq MZIII, Z \sim Z, u = 0.41060, v = 1.7407, c = 0.42106 (KOIIVK 1766). SUC J$
-------------------------------------------------------------------------------------------

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Cel	2(a)	0	0.000	0	100	
Ce2	2(b)	0	0.779	1/2	100	
Cu1	2(a)	0	0.618	0	100	
Cu2	2(a)	0	0.212	0	100	



Fig. 37. Projection of the  $Ce_2Cu_3Ge_3$  unit cell and coordination polyhedra of the atoms: (a, b) Ce, (c-e) Cu, (f-h) Ge.

Cu3	2(b)	0	0.420	1/2	100
Ge1	2(a)	0	0.361	0	100
Ge2	2(b)	0	0.129	1/2	100
Ge3	2(b)	0	0.563	1/2	100

Isotypic compounds:  $R_2Cu_3Ge_3$ : R = Pr, Nd

#### 3.14.6. CeNiSi₂ structure type

SG Cmcm, Z = 4, a = 0.4199, b = 1.6765, c = 0.4174 for NdNiGe₂ (Salamakha 1989)

Wyckoff notation	x/a	y/b	z/c	G (%)	
4(c)	0	0.397	1/4	100	
4(c)	0	0.100	1/4	100	
4(c)	0	0.034	1/4	100	
4(c)	0	0.751	1/4	100	
	Wyckoff notation 4(c) 4(c) 4(c) 4(c)	Wyckoff notation x/a   4(c) 0   4(c) 0   4(c) 0   4(c) 0   4(c) 0	Wyckoff notation x/a y/b   4(c) 0 0.397   4(c) 0 0.100   4(c) 0 0.034   4(c) 0 0.751	Wyckoff notation $x/a$ $y/b$ $z/c$ 4(c)00.3971/44(c)00.1001/44(c)00.0341/44(c)00.7511/4	Wyckoff notation $x/a$ $y/b$ $z/c$ G (%)4(c)00.3971/41004(c)00.1001/41004(c)00.0341/41004(c)00.7511/4100

Isotypic compounds:

 $RMn_{1-x}Ge_2$ : R = Nd, Sm, Gd–Tm, Lu

 $RFe_{1-x}Ge_2$ : R = Y, La–Sm, Gd–Lu



Fig. 38. Projection of the NdNiGe₂ unit cell and coordination polyhedra of the atoms: (a) Nd, (b) Ni, (c, d) Ge.

 $RCo_{1-x}Ge_2$ : R=Y, La–Sm, Gd–Lu  $RNi_{1-x}Ge_2$ : R=Y, La–Lu  $RCu_{1-x}Ge_2$ : R=La–Sm, Gd–Tm, Lu  $RRu_{1-x}Ge_2$ : R=Gd, Ho, Lu  $RRh_{1-x}Ge_2$ : R=Nd, Gd, Ho, Lu  $RPd_{1-x}Ge_2$ : R=La–Nd, Gd, Ho, Lu  $RIr_{1-x}Ge_2$ : R=Cd, Ho, Lu  $RIr_{1-x}Ge_2$ : R=La, Ho  $RPt_{1-x}Ge_2$ : R=La, Ho

The coordination number of neodymium atoms is 21 (fig. 38a). Nickel atoms have the coordination polyhedra in the form of tetragonal antiprisms with one additional atom (fig. 38b). Germanium atoms are situated inside the trigonal prisms and distorted cubooctahedra (fig. 38c, d).

Wyckoff notation	x/a	y/b	z/c	G (%)			
4(i)	0	0	0.2057	100			
4(g)	0	0.2393	0	100			
8(1)	0	0.2494	0.3541	100			
8(1)	0	0.3474	0.2002	100			
4(j)	1/2	0	0.0770	100			
4(i)	0	0	0.4215	100			
	Wyckoff notation 4(i) 4(g) 8(1) 8(1) 4(j) 4(i)	Wyckoff notation x/a   4(i) 0   4(g) 0   8(l) 0   4(j) 1/2   4(i) 0	Wyckoff notation x/a y/b   4(i) 0 0   4(g) 0 0.2393   8(1) 0 0.2494   8(1) 0 0.3474   4(j) 1/2 0   4(i) 0 0	Wyckoff notation $x/a$ $y/b$ $z/c$ 4(i)000.20574(g)00.239308(1)00.24940.35418(1)00.34740.20024(j)1/200.07704(i)000.4215			

3.14.7. YIrGe₂ structure type

SG Immm, Z = 8, a = 0.4358, b = 0.8909, c = 1.6153 for NdIrGe₂ (Salamakha et al. 1989)

Isotypic compounds:

RIrGe₂: R = Y, Pr-Sm, Gd-Er

RPtGe₂: R = Y, Ce–Sm, Gd–Yb

 $RPdGe_2$ : R = Y, Sm, Gd–Ho, Yb



Fig. 39. Projection of the NdIrGe2 unit cell and coordination polyhedra of the atoms: (a, b) Nd, (c) Ir, (d-f) Ge.

Polyhedra with 19 and 20 apexes are typical for the neodymium atoms (fig. 39a,b). Atoms of iridium are situated inside the trigonal prisms (fig. 39c). The germanium coordination polyhedra are trigonal prisms, distorted cubo-octahedra and distorted tetragonal prisms (fig. 39d-f).

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)
Lul	8(n)	0	0.40571	0.2481	100
Lu2	4(i)	0	0.1394	0	100
Mnl	8(m)	1/4	1/4	0.2476	100
Mn2	4(k)	0	0	0.2535	100
Ge1	8(n)	0	0.1383	0.3464	100
Ge2	4(j)	0	0.2905	1/2	100
Ge3	4(i)	0	0.2977	0	100
Ge4	4(h)	0.2624	0	1/2	100
Ge5	4(g)	0.2577	0	0	100

3.14.8. *LuMnGe*₂ *structure type* SG Cmmm, *Z* = 12, *a* = 0.5466, *c* = 1.8519, *c* = 0.8173 (Meyer et al. 1983)

No isotypic compounds are observed.

3.14.9. ZrCrSi₂ (or TiMnSi₂) structure type

SG Pbam, Z = 12, a = 1.0148, b = 0.9355, c = 0.8141 for ScCrGe₂ (Andrusyak 1988). See fig. 40.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Sc1	8(i)	0.32742	0.04765	0.24668	100
Sc2	4(g)	0.33143	0.32009	0	100
Cr1	8(i)	0.08009	0.24822	0.24960	100
Cr2	4(e)	0	0	0.24469	100
Ge1	8(i)	0.32908	0.31885	0.35089	100
Ge2	4(h)	0.03891	0.37798	1/2	100
Ge3	4(h)	0.11388	0.09815	1/2	100
Ge4	4(g)	0.03886	0.38121	0	100
Ge5	4(g)	0.12715	0.10435	0	100

Isotypic compounds:

ScMGe₂: M=Mn, Fe, Co, Ru, Rh, Os ROsGe₂: R=Er, Tm, Lu LuRuGe₂



Fig. 40. Projection of the  $ScCrGe_2$  unit cell and coordination polyhedra of the atoms: (a,b) Sc, (c,d) Cr, (e-i) Ge.



Fig. 41. Projection of the  $TmLi_{1-x}Ge_2$  unit cell and coordination polyhedra of the atoms: (a) Tm, (b) Li, (c, d) Ge.

3.14.10.  $TmLi_{1-x}Ge_2$  structure type

SG P2₁/m, Z = 2, a = 0.4008, b = 0.3875, c = 0.8123,  $\beta = 104.24^{\circ}$  (Pavlyuk et al. 1991). See fig. 41.

Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)
2(e)	0.3967	1/4	0.7927	100
2(e)	0.24	1/4	0.38	50
2(e)	0.0526	1/4	0.1059	100
2(e)	0.7531	1/4	0.5057	100
	Wyckoff notation 2(e) 2(e) 2(e) 2(e)	Wyckoff notation x/a   2(e) 0.3967   2(e) 0.24   2(e) 0.0526   2(e) 0.7531	Wyckoff notation x/a y/b   2(e) 0.3967 1/4   2(e) 0.24 1/4   2(e) 0.0526 1/4   2(e) 0.7531 1/4	Wyckoff notationx/ay/bz/c2(e)0.39671/40.79272(e)0.241/40.382(e)0.05261/40.10592(e)0.75311/40.5057

 $RLi_{1-x}Ge_2$ : R = Ho, Er, Lu

### 3.14.11. CaLiSi₂ structure type

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SG Pnma, Z = 4, a = 0.7815, b = 0.3965, c = 1.0748 for CeLiGe<sub>2</sub> (Pavlyuk et al. 1986)
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Atom	Wyckoff notation	<i>x/a</i>	y/b	z/c	G (%)	
Ce	4(c)	0.142	1/4	0.364	100	
Li	4(c)	0.498	1/4	0.613	100	
Gel	4(c)	0.160	1/4	0.683	100	
Ge2	4(c)	0.217	1/4	0.072	100	

Isotypic compounds:

RLiGe₂: R = La - Gd



Fig. 42. Projection of the CeLiGe₂ unit cell and coordination polyhedra of the atoms: (a) Ce, (b) Li, (c, d) Ge.

The coordination number of cerium atoms is 18 (fig. 42a). Lithium atoms have the coordination polyhedra in the form of deformed cubo-octahedra (fig. 42b). Germanium atoms are situated inside the trigonal prisms with three additional atoms (fig. 42c, d).

		-		· •	,	
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Cel	2(b)	1/4	3/4	0.3633	100	
Ce2	2(a)	1/4	1/4	0.8514	100	
Rh	2(b)	1/4	3/4	0.5753	100	
Ge1	2(b)	1/4	3/4	0.0070	100	
Ge2	2(b)	1/4	3/4	0.716	100	
Х	2(a)	1/4	1/4	0.0631	100	
Ge3	2(a)	1/4	1/4	0.205	100	
Ge4	2(a)	1/4	1/4	0.4937	100	

3.14.12.  $CeRh_{1-x}Ge_{2+x}$  structure type SG Pmmn, Z=2, a=0.4322, b=0.4339, c=1.7101 (Shapiev et al. 1991)

X = 0.35Rh + 0.65Ge

Isotypic compound:  $SmRh_{1-x}Ge_{2+x}$ 

The coordination polyhedra with 21 apexes are typical for the cerium atoms (fig. 43a, b). The atoms of rhodium, statistical mixture X (X=0.35Rh+0.65Ge) and germanium are placed inside of trigonal prisms with additional atoms and distorted cubo-octahedra (fig. 43c-h).



Fig. 43. Projection of the  $CeRh_{1-x}Ge_{2+x}$  unit cell and coordination polyhedra of the atoms: (a) Ce, (c-h) Rh, X and Ge.

See Children, 2 - 2, u 0.4245, b 2.5756, c 0.4267 for CC3142CC7 (Konyk 1780)								
Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)			
Ce1	4(j)	0	0.3151	1/2	100			
Ce2	2(a)	0	0	0	100			
Ni	4(i)	0	0.1272	0	100			
Ge1	4(j)	0	0.090	1/2	100			
Ge2	4(i)	0	0.222	0	100			
Ge3	4(i)	0	0.4137	0	100			
Ge4	2(c)	1/2	0	1/2	100			

3.14.13.  $La_3Co_2Sn_7$  structure type SG Cmmm Z=2, a=0.4243, b=2.5758, c=0.4289 for Ce₂Ni₂Ge₇ (Konvk 1986).

Isotypic compound: Sm₃Co₂Ge₇

For cerium atoms, polyhedra with 18 and 20 apexes are typical (fig. 44a,b). The nickel atom polyhedra are tetragonal antiprisms with one additional atom (fig. 44c). Those for germanium atoms are trigonal prisms, tetragonal antiprisms and distorted cubo-octahedra (fig. 44d–g).



Fig. 44. Projection of the  $Ce_3Ni_2Ge_7$  unit cell and coordination polyhedra of the atoms: (a,b) Ce, (c) Ni, (d-g) Ge.

Atom	Wyckoff notation	<i>x/a</i>	y/b	z/c	G (%)
Ce	4(k)	0	1/2	0.1661	100
Ge1	4(1)	1/2	1/2	0.2898	100
Ge2	4(k)	0	1/2	0.4470	100
Х	4(1)	1/2	1/2	0.0540	100

3.14.14.  $Ce_2MnGe_5$  structure type

SG Ammm, Z=2, a=0.4308, b=0.4170, c=2.1134 (Konyk 1989)

_____

X=0.5Mn+0.5Ge Isotypic compounds:

 $R_2LiGe_5$ : R = Ce–Sm

 $R_2 LIGe_5$ . R = Ce = Sin

The coordination polyhedra for the cerium atoms have 18 apexes (fig. 45a). For Ge1 atoms, the coordination polyhedra in the form of trigonal prisms with two additional atoms are typical (fig. 45b). Ge2 and the statistical mixture X (X = 0.5Mn+0.5Ge) are situated in the centres of trigonal prisms with one additional atoms (fig. 45c, d).



Fig. 45. Projection of the  $Ce_2MnGe_5$  unit cell and coordination polyhedra of the atoms: (a) Ce, (b) Ge1, (c, d) Ge2 and X.

### 3.15. $R_5(M, Ge)_{14}$ and $R_4(M, Ge)_{11}$ compounds

3.15.1.  $Sc_5Co_4Si_{10}$  structure type

SG P4/mbm, Z=2, a=1.29336, c=0.42596 for Ho₅Rh₄Ge₁₀ (Gladyshevsky et al. 1992a)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Hol	4(h)	0.17458	0.67458	1/2	100
Ho2	4(h)	0.61279	0.11279	1/2	100
Ho3	2(a)	0	0	0	100
Rh	8(i)	0.2455	0.0210	0	100
Ge1	8(j)	0.1586	0.0027	1/2	100
Ge2	8(i)	0.1615	0.1997	0	100
Ge3	4(g)	0.0669	0.5669	0	100

Isotypic compounds:

 $R_5Co_4Ge_{10}$ : R = Tm-Lu

 $R_5Rh_4Ge_{10}$ : R = Y, Gd–Lu

 $R_5Os_4Ge_{10}$ : R = Y, Dy-Tm

The coordination numbers for holmium atoms are 17, 18 and 20 (fig. 46a–c). Rhodium atoms have coordination polyhedra in the form of trigonal prisms with four additional atoms (fig. 46d). Germanium atoms are situated inside the trigonal prisms with three additional atoms and deformed cubo-octahedra (fig. 46e–g).



Fig. 46. Projection of the  $Ho_5Rh_4Ge_{10}$  unit cell and coordination polyhedra of the atoms: (a-c) Ho, (d) Rh, (e-g) Ge.

3.15.2.  $Zr_4Co_4Ge_7$  structure type SG I4/mmm, Z=4, a=1.3215, c=0.5229 for Sc₄Co₄Ge_{7-x} (Andrusyak 1988). See fig. 47.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Sc1	8(i)	0.1966	0	0	100	
Sc2	8(h)	0.3608	0.3608	0	100	
Со	16(k)	0.1483	0.6483	1/4	100	
Ge1	8(j)	0.2080	1/2	0	100	
Ge2	8(i)	0.4071	0	0	100	
Ge3	8(h)	0.2069	0.2069	0	100	
Ge4	4(e)	0	0	0.250	100	

 $Sc_4M_4Ge_{7-x}$ : M=Fe, Ni


Fig. 47. Projection of the  $Sc_4Co_4Ge_7$  unit cell and coordination polyhedra of the atoms: (a,b) Sc, (c) Co, (d-g) Ge.

#### 3.15.3. La₄Ga₄Ge₇ structure type

SG Pmmm, a = 0.8414, b = 0.8620, c = 3.109 for Ce₄Ga₄Ge₇ (Gryniv et al. 1989)

Atomic coordinates for the germanides of this structure type were not presented. Isotypic compounds:

 $R_4Ga_4Ge_7$ : R = La, Nd

### 3.16. $R_3(M, Ge)_8$ compounds

3.	16.1.	$Gd_3Cu_4C$	∃e₄ struc	ture type
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SG	Immm	, Z = 2,	a = 0.4223	, <i>b</i> =0.6655	, c = 1.4000	(Rieger	1970)
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Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)
Gd1	4(j)	1/2	0	0.36884	100
Gd2	2(a)	0	0	0	100
Cu	8(1)	0	0.31067	0.33048	100

P.S. SALAMAKHA

Ge1	4(i)	0	0	0.21567	100
Ge2	4(h)	0	0.18902	1/2	100

Isotypic compounds:  $R_3Mn_4Ge_4$ : R = Gd, Tb  $R_3Fe_4Ge_4$ : R = Dy-Tm, Lu  $Sc_3Ni_4Ge_4$   $R_3Cu_4Ge_4$ : R = Sc, Y, Pr-Sm, Gd-Lu  $R_3Ag_4Ge_4$ : R = Pr-Sm, Gd  $R_3Pd_4Ge_4$ : R = Y, Gd-Tm

The coordination numbers for the Gd atoms are 20 and 19 (fig. 48a, b). The coordination polyhedra for the Cu atoms are distorted cubo-octahedra (fig. 48c); those for Ge atoms are trigonal prisms with additional atoms (fig. 48d, e).



Fig. 48. Projection of the  $Gd_3Cu_4Ge_4$  unit cell and coordination polyhedra of the atoms: (a,b) Gd, (c) Cu, (d,e) Ge.

3.16.2.  $U_3Ni_4Si_4$  structure type SG Immm, Z = 2, a = 0.42234, b = 0.42295, c = 2.4156 for La₃Ni₄Ge₄ (Bruskov 1984)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Lal	4(j)	1/2	0	0.3494	100	
La2	2(a)	0	0	0	100	
Ni1	4(j)	1/2	0	0.0989	100	

280

Ni2	4(i)	0	0	0.2490	100
Ge1	4(j)	1/2	0	0.2000	100
Ge2	4(i)	0	0	0.446	100

Isotypic compounds:

 $R_3Ni_4Ge_4$ : R = Ce, Pr

 $R_3Rh_4Ge_4$ : R = La

The coordination polyhedra for the lanthanum atoms have 20 and 21 apexes (fig. 49a, b). For nickel atoms, the coordination polyhedra are typically trigonal prisms and distorted cubo-octahedra (fig. 49c, d). Germanium atoms are situated in the centres of trigonal prisms and tetragonal antiprism (fig. 49e, f).



Fig. 49. Projection of the  $La_3Ni_4Ge_4$  unit cell and coordination polyhedra of the atoms: (a,b) La, (c,d) Ni, (e,f) Ge.

### 3.17. $R_2(M, Ge)_5$ compounds

# 3.17.1. Ce₂Li₂Ge₃ structure type

SO C (10,11, 2 - 7, 4 - 0.77/55, 0 - 1.0070, 0 - 0.05570 (1 aviyuk cl al. 17000), Sec 11g.	G Cmcm, $Z = 4$ , $a = 0.44795$ , $b = 1.8846$ , $c = 0.69570$ (Pav	vlyuk et al. 1988b). See fi	ig. 50.
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Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Cel	4(c)	0	0.4484	1/4	100
Ce2	4(c)	0	0.6583	1/4	100
Li	8(f)	0	0.1910	0.559	100

P.S. SALAMAKHA

Ge1	8(f)	0	0.0611	0.0688	100
Ge2	4(c)	0	0.2801	1/4	100

Isotypic compounds:  $R_2Li_2Ge_3$ : R=La-Sm



Fig. 50. Projection of the  $Ce_2Li_2Ge_3$  unit cell and coordination polyhedra of the atoms: (a,b) Ce, (c) Li, (d,e) Ge.

Atom	Wyckoff notation		/a		G (%)
		<i>x/u</i>	<i>yib</i>	2/0	G (70)
Tml	2(b)	1/4	3/4	0.6920	100
Tm2	2(a)	1/4	1/4	0.1275	100
Х	2(b)	1/4	3/4	0.2626	100
Х	2(b)	1/4	3/4	0.8000	100
Х	2(a)	1/4	1/4	0.8381	100
Х	2(a)	1/4	1/4	0.5675	100
Х	2(a)	1/4	1/4	0.4287	100

3.17.2.  $Tm_2Ga_{0.5}Ge_{4.5}$  structure type

SG Pmmm, Z = 2, a = 0.3915, b = 0.4048, c = 1.8209 (Gryniv and Myakush 1989)

X = 0.9Ge + 0.1Ga

No isotypic compounds are observed.

282

# 3.18. $R_3(M, Ge)_7$ and $R_9(M, Ge)_{20}$ compounds

3.18.1. Nd₆Fe₁₃Si structure type

SG 14/mcm, Z = 4, a = 0.80710, c = 2.3085 for Pr₆Fe₁₃Ge (Fedyna and Pecharsky 1989). See fig. 51.

Atom	Wyckoff notation	<i>x/a</i>	y/b	<i>z</i> / <i>c</i>	G (%)
Pr1	16(1)	0.1658	0.6658	0.1900	100
Pr2	8(f)	0	0	0.1094	100
Fe1	16(l)	0.1780	0.6780	0.0597	100
Fe2	16(l)	0.616	0.116	0.0955	100
Fe3	16(k)	0.065	0.212	0	100
Fe4	4(d)	0	1/2	0	100
Ge	4(a)	0	0	1/4	100

Isotypic compound: Nd₆Fe₁₃Ge



Fig. 51. Projection of the Pr₆Fe₁₃Ge unit cell and coordination polyhedra of the atoms: (a, b) Pr, (c-f) Fe, (g) Ge.

# 3.18.2. $Tm_9Fe_{10}Ge_{10}$ structure type

SG Immm, $Z = 2$ , $a = 0.5386$ ,	b = 1.3306	c = 1.3916 (	Pecharsk	y et al.	1987	). See fig	g. 52.
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Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Tm1	8(1)	0.1462	0.3644	0	100	
Tm2	4(j)	0	0.3052	1/2	100	
Tm3	4(g)	0.2836	0	0	100	

284		P.S. SA	LAMAKHA		
Tm4	2(a)	0	0	0	100
Fe1	16(o)	0.1438	0.1541	0.2522	100
Fe2	4(j)	0	0.0904	1/2	100
Ge1	8(1)	0.2905	0.2049	0	100
Ge2	4(i)	0	0.2099	0	100
Ge3	4(h)	0.3252	1/2	0	100
Ge4	4(f)	1/2	0	0.249	100

Isotypic compounds:  $R_9Fe_{10}Ge_{10}$ : R = Er, Yb



Fig. 52. Projection of the  $Tm_9Fe_{10}Ge_{10}$  unit cell and coordination polyhedra of the atoms: (a–d) Tm, (e, f) Fe, (g--j) Ge.



Fig. 53. Projection of the  $SmSn_{1.5}Ge_{0.5}$  unit cell and coordination polyhedra of the atoms: (a) Sm, (b, c) X.

3.19.  $R(M, Ge)_2$  compounds

3.19.1. ZrSi₂ structure type

SG Cmcm, Z = 4, a = 0.4502, b = 1.5367, c = 0.4502 for SmSn_{1.5}Ge_{0.5} (Stetskiv 1999). See fig. 53.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Sm	4(c)	0	0.0811	1/4	100
Х	4(c)	0	0.4280	1/4	100
Х	4(c)	0	0.7579	1/4	100

X = 0.25Ge+0.75SnIsotypic compounds:  $RSn_{1.5}Ge_{0.5}$ : R = La-Pr

#### 3.19.2. $MgZn_2$ structure type

SG P6₃/mmc, Z=4, a=0.5006, c=0.8150 for Sc₂Fe₃Ge (Andrusyak 1988) Atomic coordinates have not been determined.

# 3.19.3. MgCu₂ structure type

SG Fd3m, Z=8, a=0.7063 for Sc(Sc, Fe, Ge)₂ (Andrusyak 1988) Atomic coordinates have not been determined.

5.15.1. I florg Ge Sti acture type	3.19.4.	$Y_2Rh_3Ge$	structure	type
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SG R3	m, $Z = 3$ , $a = 0.5552$ ,	<i>c</i> = 1.182	for Y2Rh3Ge	(Cenzual et	al. 1987)
Atom	Wheelroff notation	/~	a./L	-/-	C(0/)

Awin	wyckon notation	x/a	<i>yib</i>	2/0	G (%)
Y	6(c)	0	0	0.3718	100

286		P.	S. SALAMAKI	HA				
Rh	9(d)	1/2	0	1/2	100			
Ge	3(a)	0	0	0	100			
Isotyp	Isotypic compounds:							

 $R_2Rh_3Ge: R = Pr, Er$ 

# 3.19.5. PbFCl structure type

SG P4/nmm, Z=2, a=0.4170, c=0.6865 for CeCoGe (Welter et al. 1993)

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)	
Ce	2(c)	1/4	1/4	0.67	100	
Co	2(a)	3/4	1/4	0	100	
Ge	2(c)	1/4	1/4	0.19	100	

Isotypic compounds: RTiGe: R=Y, Gd−Tm RMnGe: R=La-Sm CeFeGe RCoGe: R=La-Nd RRuGe: R=La-Sm

For cerium atoms, polyhedra with 18 apexes are typical (fig. 54a). The cobalt atom polyhedra are distorted cubo-octahedra (fig. 54b). Those for germanium atoms are tetragonal antiprisms with one additional atom (fig. 54c).



Fig. 54. Projection of the CeCoGe unit cell and coordination polyhedra of the atoms: (a) Ce, (b) Co, (c) Ge.

SG I4/mmm, $Z = 4$ , $a = 0.4314$ , $c = 1.5913$ for CeScGe (Shpyrka 1990)							
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)		
Ce	4(e)	0	0	0.326	100		
Sc	4(c)	0	1/2	0	100		
Ge	2(e)	0	0	0.124	100		

3.19.6. CeScSi structure type

Isotypic compounds: RScGe: R = La - Eu



Fig. 55. Projection of the CeScGe unit cell and coordination polyhedra of the atoms: (a) Ce, (b) Sc, (c) Ge.

The coordination polyhedra for cerium atoms have 17 apexes (fig. 55a). Scandium atoms are situated in the centres of the cubo-octahedra (fig. 55b). The coordination polyhedra in the form of tetragonal antiprism with one additional atom are typical for the germanium atoms (fig. 55c).

SG P6/mmm, $Z = 1$ , $a = 0.4277$ , $c = 0.3881$ for NdCuGe (Salamakha 1986)								
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)			
Nd	1(a)	0	0	0	100			
Х	2(d)	1/3	2/3	1/2	100			

1000

0 0001 0

3.19.7.  $AlB_2$  structure type SC DG/m ~ ~ 4

X = 0.5Cu + 0.5Ge

Isotypic compounds:  $RFe_{0.67}Ge_{1.33}$ : R = La, Nd, Sm  $RCo_{0.5}Ge_{1.5}$ : R = Ce-Nd  $RNi_{0.6}Ge_{1.4}$ : R = La-Yb  $RCu_{0.7}Ge_{1.3}$ : R = Y, La-Sm, Gd-Tm RCuGe:R = La-Gd  $RZn_{1.5}Ge_{0.5}$ : R = La-Sm  $RRh_{0.5}Ge_{1.5}$ : R = Ce, Nd, Sm  $RPd_{0.6}Ge_{1.4}$ : R = Ce, Nd, Sm, Ho, Yb  $RAg_{0.7}Ge_{1.3}$ : R = Ce-Nd  $RIr_{0.5}Ge_{1.5}$ : R = Nd  $RPt_{0.6}Ge_{1.4}$ : R = Ce, Nd, Sm, Ho  $RAu_{0.7}Ge_{1.3}$ , R = Ce, Nd, Sm, Ho

The coordination polyhedra of the neodymium atoms have 18 apexes (fig. 56a). Those of the statistical mixture X (X=0.5Cu+0.5Ge) are trigonal prisms with three additional atoms (fig. 56b).



Fig. 56. Projection of the NdCuGe unit cell and coordination polyhedra of the atoms: (a) Nd, (b) X.

3.19.8. CaIn₂ structure type

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Tb	2(b)	0	0	1/4	100
X	4(f)	1/3	2/3	0.0212	100

X=0.5Cu+0.5Ge Isotypic compounds: RCuGe: R=Tb-Er

288

SG P6 ₃ mc, $Z=2$ , $a=0.45587$ , $c=0.78969$ for LaAgGe (Pecharsky et al. 1991)							
Wyckoff notation	x/a	y/b	z/c	G (%)			
2(a)	0	0	0.000	100			
2(b)	1/3	2/3	0.2514	100			
2(b)	1/3	2/3	0.7082	100			
	mc, $Z=2$ , $a=0.455$ Wyckoff notation 2(a) 2(b) 2(b)	mc, $Z = 2$ , $a = 0.45587$ , $c = 0.7$ Wyckoff notation $x/a$ 2(a) 0   2(b) 1/3   2(b) 1/3	mc, $Z = 2$ , $a = 0.45587$ , $c = 0.78969$ for LaAWyckoff notation $x/a$ $y/b$ 2(a)002(b) $1/3$ $2/3$ 2(b) $1/3$ $2/3$	mc, $Z=2$ , $a=0.45587$ , $c=0.78969$ for LaAgGe (PecharskWyckoff notation $x/a$ $y/b$ $z/c$ 2(a)000.0002(b)1/32/30.25142(b)1/32/30.7082	mc, $Z=2$ , $a=0.45587$ , $c=0.78969$ for LaAgGe (Pecharsky et al. 1991)Wyckoff notation $x/a$ $y/b$ $z/c$ G (%)2(a)000.0001002(b)1/32/30.25141002(b)1/32/30.7082100		

3.19.9. LiGaGe (or NdPtSb) structure type SG P6 ma 7=2 a=0.45587 a=0.78960 for LaAaGa (Pacharalay et a

Isotypic compounds:

RAgGe: R = Ce, Pr

RAuGe: R = Sc, Y, La-Sm, Gd-Lu

The coordination polyhedra of the lanthanum atoms have 14 apexes (fig. 57a). Those for silver and germanium atoms are trigonal prisms with additional atoms (fig. 57b, c).



Fig. 57. Projection of the LaAgGe unit cell and coordination polyhedra of the atoms: (a) La, (b, c) Ag and Ge.

# 3.19.10. KHg₂ structure type

SG Imma, Z = 4, a = 0.4366, b = 0.6956, c = 0.7596 for HoPdGe (Sologub and Salamakha 1999)

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	<i>y/b</i>	z/c	G (%)	
Но	4(e)	0	1/4	0.5402	100	
Х	8(h)	0	0.0473	0.1651	100	

X=0.5Pd+0.5Ge Isotypic compounds: RPdGe: R=Y, La-Sm, Gd-Tm RPtGe: R=Ce-Nd The coordination polyhedra for holmium atoms have 18 apexes (fig. 58a). The statistical mixture X (X=0.5Pd+0.5Ge) occupies the centre of trigonal prism with four additional atoms (fig. 58b).





Fig. 58. Projection of the HoPdGe unit cell and coordination polyhedra of the atoms: (a) Ho, (b) X.

Fig. 59. Projection of the HoRuGe unit cell and coordination polyhedra of the atoms: (a) Ho, (b) Ru, (c) Ge.

# 3.19.11. TiNiSi structure type

SG Pnma, Z = 4, a = 0.6980, b = 0.4351, c = 0.7281 for HoRuGe (Sologub et al. 1993)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Но	4(c)	0.00850	1/4	0.69089	100	
Ru	4(c)	0.1562	1/4	0.0638	100	
Ge	4(c)	0.2042	1/4	0.3771	100	

Isotypic compounds:

RCoGe: R = Sc, Y, Sm, Gd-Lu

RNiGe: R = Sc, Y, Ce-Sm, Gd-Lu

RRuGe: R = Gd-Tm

RRhGe: R = Sc, Y, Ce–Sm, Gd–Tm

RIrGe: R = Sc, Y, Ce–Sm, Gd–Tm

RPtGe: R = Sc, Y, Sm, Gd-Tm

The polyhedra with 18 apexes are typical for the holmium atoms (fig. 59a). The polyhedra for ruthenium atoms are deformed cubo-octahedra (fig. 59b). The germanium coordination polyhedra are trigonal prisms with four additional atoms (fig. 59c).



Fig. 60. Projection of the HoAgGe unit cell and coordination polyhedra of the atoms: (a) Ho, (b) Ag, (c, d) Ge.

3.19.12. ZrNiAl structure type SG P $\overline{6}$ 2m, Z = 3, a = 0.7084, c = 0.4179 for HoAgGe (Sologub and Protsyk 1991)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Но	3(f)	0.5883	0	0	100	
Ag	3(g)	0.255	0	1/2	100	
Ge1	2(d)	1/3	2/3	1/2	100	
Ge2	1(a)	0	0	0	100	

Isotypic compounds:

RLiGe: R = Y, Pr-Sm, Gd-Lu

RAgGe: R = Sc, Y, Sm, Gd-Lu

 $RAg_{1+x}Ge_{1-x}$ : R = Pr, Nd

ScMGe: M=Cu, Ru, Rh, Pd, Os

For holmium atoms, polyhedra with 17 apexes are typical (fig. 60a). The silver atom polyhedra are distorted cubo-octahedra (fig. 60b). The trigonal prisms with three additional atoms are the polyhedra for germanium atoms (fig. 60c, d).

3.19.13. LaPtSi structure ty	pe
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SG I4₁md, Z = 4, a = 0.42663, c = 1.4970 for LaPtGe (Hovestreydt et al. 1982)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
La	4(a)	0	0	0.581	100	
Pt	4(a)	0	0	0.1660	100	
Ge	4(a)	0	0	0.000	100	



Fig. 61. Projection of the LaPtGe unit cell and coordination polyhedra of the atoms: (a) La, (b,c) Pt and Ge.

Isotypic compound: LaIrGe

The coordination polyhedra of lanthanum have 20 apexes (fig. 61a). The trigonal prisms with three additional atoms are the polyhedra for platinum and germanium atoms (fig. 61b, c).

3.19.14. ZrOS (or LaIrSi) structure type SG P2₁3, Z=4, a=0.65463 for EuPtGe (Pöttgen et al. 1996)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Eu	4(a)	0.13207	0.13207	0.13207	100
Pt	4(a)	0.41819	0.41819	0.41819	100
Ge	4(a)	0.83351	0.83351	0.83351	100

No isotypic compounds are observed.

For europium atoms, polyhedra with 20 apexes are typical (fig. 62a). The platinum and germanium atoms polyhedra have 10 apexes (fig. 62b, c).

#### 3.19.15. EuNiGe structure type

SG P2₁/c, Z = 4, a = 0.6158, b = 0.6187, c = 0.7581,  $\beta = 119.83^{\circ}$  (Oniskovetz et al. 1987). See fig. 63.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Eu	4(e)	0.3014	0.6394	0.1071	100	
Ni	4(e)	0.1115	0.0957	0.1755	100	
Ge	4(e)	0.2285	0.3564	0.4268	100	

Isotypic compound: EuPdGe



Fig. 62. Projection of the EuPtGe unit cell and coordination polyhedra of the atoms: (a) Eu, (b, c) Pt and Ge.



Fig. 63. Projection of the EuNiGe unit cell and coordination polyhedra of the atoms: (a) Eu, (b) Ni, (c) Ge.

3.19.16. *DyAlGe structure type* SG Cmc2₁, *Z* = 4, *a* = 0.4091, *b* = 1.046, *c* = 0.5874 (Yanson 1975)

Atom	Wyckoff notation	<i>x/a</i>	y/b	z/c	G (%)
Dy	4(a)	0	0.0189	0.0000	100
Al	4(a)	0	0.4525	0.1470	100
Ge	4(a)	0	0.2524	0.4500	100



Fig. 64. Projection of the YAlGe unit cell and coordination polyhedra of the atoms: (a) Y, (b) Al, (c) Ge.

SG Cmcm, $Z = 4$ , $a = 0.40504$ , $b = 1.0440$ , $c = 0.57646$ (Zhao and Parthé 1990b)							
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)		
Y	4(c)	0	0.3099	1/4	100		
Al	4(a)	0	0	0	100		
Ge	4(c)	0	0.6058	1/4	100		

Isotypic compounds:

RAlGe: R = Gd-Tm

Polyhedra with 17 apexes are typical for the yttrium atoms (fig. 64a). Atoms of aluminium are situated inside the distorted cubo-octahedra (fig. 64b). The germanium atoms coordination polyhedra are trigonal prisms with three additional atoms (fig. 64c).

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Eu1	2(a)	0	0	0.62735	100
Eu2	2(b)	0	1/2	0.70640	100
Au	4(d)	0	0.21432	0.00243	100
Ge	4(d)	0	0.31235	0.33353	100

3.19.18. EuAuGe structure type

3.19.17. YAlGe structure type

SG Imm2, Z=4, a=0.4601, b=0.7371, c=0.7888 (Pöttgen 1995a)

Isotypic compound: YbAu_{1.24}Ge_{0.76}



Fig. 65. Projection of the EuAuGe unit cell and coordination polyhedra of the atoms: (a, b) Eu, (c, d) Au and Ge.

For europium atoms, polyhedra with 18 apexes are typical (fig. 65a, b). The atoms of gold and germanium are situated inside the trigonal prisms with additional atoms (fig. 65c, d).

3.19.19. CaCuGe structure type

SG Pna2₁, a = 2.209, b = 0.7543, c = 0.4453 for EuCuGe (Iandelli 1993)

Atomic coordinates for the rare-earth germanides of this structure type were not presented.

3.19.20. α-YbAuGe structure	type	
SG Pnma, $Z = 12$ , $a = 2.1332$ ,	b = 0.4485, c = 0.7708 (Merlo et al.	1998)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Yb1	4(c)	0.0005	1/4	0.7094	100	
Yb2	4(c)	0.1663	1/4	0.7842	100	
Yb3	4(c)	0.3331	1/4	0.7132	100	
Au1	4(c)	0.0936	1/4	0.4153	100	
Au2	4(c)	0.2380	1/4	0.4138	100	
Au3	4(c)	0.4317	1/4	0.4186	100	
Gel	4(c)	0.0703	1/4	0.083	100	
Ge2	4(c)	0.2714	1/4	0.082	100	
Ge3	4(c)	0.3990	1/4	0.096	100	

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3.19.21.	$\beta$ -YbAuGe	structure	type

SG Pnma, Z = 12, a = 2.1311, b = 0.4481, c = 0.7704 for YbAu_{1.03}Ge_{0.97} (Merlo et al. 1998)

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)	
Yb1	4(c)	0.0005	1/4	0.7127	100	
Yb2	4(c)	0.1663	1/4	0.7864	100	
Yb3	4(c)	0.3336	1/4	0.7126	100	
Au	4(c)	0.2379	1/4	0.4172	100	
Ge	4(c)	0.2701	1/4	0.083	100	
<b>X</b> 1	4(c)	0.0941	1/4	0.4162	100	
X2	4(c)	0.4309	1/4	0.4123	100	
X3	4(c)	0.0705	1/4	0.086	100	
X4	4(c)	0.3983	1/4	0.0843	100	

X1=0.69Au+0.31Ge; X2=0.56Au+0.44Ge; X3=X4=0.43Au+0.57Ge

3.19.22.	LuNiGe	structure	type
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SG	Cmcm,	Z = 16,	a = 0.4116,	<i>b</i> =2.2334,	c = 0.9194	(Koterlyn et a	ıl. 1994)
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Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Lul	8(f)	0	0.58908	0.0645	100	
Lu2	4(c)	0	0.72747	1/4	100	
Lu3	4(c)	0	0.88557	1/4	100	
Ni1	8(f)	0	0.1957	0.0184	100	
Ni2	4(c)	0	0.0305	1/4	100	
Ni3	4(a)	0	0	0	100	
Ge1	8(f)	0	0.3020	0.1061	100	
Ge2	4(c)	0	0.1399	1/4	100	
Ge3	4(c)	0	0.4757	1/4	100	

Isotypic compound: TmNiGe

For luthetium atoms, polyhedra with 18 and 19 apexes are typical (fig. 66a–c). Those for nickel and germanium atoms are trigonal prisms with additional atoms and distorted cubo-octahedra (fig. 66d–i).



Fig. 66. Projection of the LuNiGe unit cell and coordination polyhedra of the atoms: (a-c) Lu, (d-i) Ni, Ge.

3.19.23. ZrBeSi structure type SG P6₃/mmc, Z=2, a=0.4372, c=0.8604 for EuZnGe (Pöttgen 1995b)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Eu	2(a)	0	0	0	100	
Zn	2(c)	1/3	2/3	1/4	100	
Ge	2(d)	1/3	2/3	3/4	100	

For europium atoms, polyhedra with 20 apexes are typical (fig. 67a). The atoms of zinc and germanium are situated inside the trigonal prisms with three additional atoms (fig. 67b, c).



Fig. 67. Projection of the EuZnGe unit cell and coordination polyhedra of the atoms: (a) Eu, (b,c) Zn and Ge.

SG I41	SG I4 ₁ /amd, $Z = 4$ , $a = 0.4231$ , $c = 1.4219$ for CeZn _{0.7} Ge _{1.3} (Opainych 1996)							
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)			
Ce	4(a)	0	3/4	1/8	100			
Х	8(e)	0	1/4	0.4589	100			

3.19.24.  $\alpha$ -ThSi₂ structure type

X = 0.35Zn + 0.65GeIsotypic compounds: RAIGe: R = La-Gd

3.19.25.  $\alpha$ -GdSi₂ structure type

SG Imma, Z = 4, a = 0.4044, b = 0.3988, c = 1.348 for YSi_{1.4}Ge_{0.6} (Muratova 1976) Atomic coordinates were not determined for a germanide of this structure type.

3.19.26.  $CeSi_{1-y}Ge_{1-x}$  structure type

SG I $\overline{4}$ m2, Z=4, a=0.4198, b=1.4004 for CeSi_{0.92}Ge_{0.66} (Boutarek et al. 1992)

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)	
Ce1	2(c)	0	1/2	1/4	100	
Ce2	2(a)	0	0	0	100	
Si	4(f)	0	1/2	0.6743	95	
Ge	4(e)	0	0	0.4124	66	

No isotypic compounds have been observed.

## 3.19.27. Te₂Ag₃Tl structure type

SG Cmmm, Z = 2, a = 1.8894, b = 0.4650, c = 0.4299 for Ce₂Sb₃Ge (Stetskiv et al. 1998). See fig. 68.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Ce	4(g)	0.1406	0	0	100	
Sb1	2(b)	1/2	0	0	100	
Sb2	4(h)	0.3047	0	1/2	100	
Ge	2(d)	0	0	1/2	100	

Isotypic compounds:

 $R_2Sb_3Ge: R = La, Pr, Sm$ 



Fig. 68. Projection of the Ce₂Sb₃Ge unit cell and coordination polyhedra of the atoms: (a) Ce, (b, c) Sb, (d) Ge.

3.19.28.  $Tb_3Co_2Ge_4$  structure type

SG C2/m, Z=2, a=1.0692, b=0.4164, c=0.8067,  $\beta=107.72^{\circ}$  (Starodub et al. 1986). See fig. 69.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Tb1	4(i)	0.3771	0	0.3076	100
Tb2	2(a)	0	0	0	100
Co	4(i)	0.3096	0	0.6312	100
Ge1	4(i)	0.0964	0	0.3998	100
Ge2	4(i)	0.7105	0	0.0796	100

Isotypic compounds:



Fig. 69. Projection of the  $Tb_3Co_2Ge_4$  unit cell and coordination polyhedra of the atoms: (a,b) Tb, (c) Co, (d,e) Ge.

3.19.29.  $Sc_7Cr_{4+x}Si_{10-x}$  structure type

SG I4/mmm, Z=4, a=0.9995, c=1.4168 for  $Sc_7Mn_{4+x}Ge_{10-x}$ , x=1.3 (Kotur et al. 1988)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Sc1	16(n)	0	0.2520	0.3119	100
Sc2	8(h)	0.3253	0.3253	0	100
Sc3	4(e)	0	0	0.1621	100
Mn	16(n)	0	0.3283	0.1014	100
Ge4	16(m)	0.2055	0.2055	0.1670	100
Ge3	8(j)	0.8714	1/2	0	100
Ge2	4(e)	0	0	0.3891	100
Ge1	4(d)	0	1/2	1/4	100
Х	8(h)	0.1238	0.1238	0	25

X = 0.64Mn + 0.36Ge

Isotypic compound:  $Sc_7Cr_{4+x}Ge_{10-x}$ , x = 1.3

3.19.30.  $Sm_4Co_{1-x}Ge_7$  structure type

	. 1987)
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Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Sm1	2(b)	1/2	0	0.5284	100	
Sm2	2(b)	1/2	0	0.9165	100	
Sm3	2(a)	0	0	0.1832	100	
Sm4	2(a)	0	0	0.7966	100	
Co	2(a)	0	0	0.0745	64	
Ge1	2(b)	1/2	0	0.1048	100	
Ge2	2(b)	1/2	0	0.2665	100	
Ge3	2(b)	1/2	0	0.7130	100	
Ge4	2(a)	0	0	0.0000	100	
Ge5	2(a)	0	0	0.3680	100	
Ge6	2(a)	0	0	0.4521	100	
Ge7	2(a)	0	0	0.6038	100	

Isotypic compounds:

 $R_4Fe_{1-x}Ge_7$ : R = Pr, Nd, Sm



Fig. 70. Projection of the  $Sm_4Co_{1-x}Ge_7$  unit cell and coordination polyhedra of the atoms: (a-d) Sm, (e) Co, (f-l) Ge.

For samarium atoms, polyhedra with 16, 17, 18 and 20 apexes are typical (fig. 70a–d). The cobalt atoms polyhedra are tetragonal antiprisms with two additional atoms (fig. 70e). The trigonal prisms and distorted cubo-octahedra are the polyhedra for germanium atoms (fig. 70f–l).

#### 3.20. $R_7(M, Ge)_{13}$ and $R_4(M, Ge)_7$ compounds

3.20.1. Yb₇Al₅Ge₈ structure type

SG C2/m, Z = 2, a = 1.5958, b = 0.42871, c = 1.2611,  $\beta = 95.78^{\circ}$  (Zhao and Parthé 1991a). See fig. 71.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Yb1	4(i)	0.01782	0	0.2983	100
Yb2	4(i)	0.15884	0	0.54329	100
Yb3	4(i)	0.81087	0	0.1358	100
Yb4	2(a)	0	0	0	100
A11	4(i)	0.2242	0	0.3052	100
A12	4(i)	0.6087	0	0.1671	100
A13	2(d)	0	1/2	1/2	100
Ge1	4(i)	0.1751	0	0.1050	100
Ge2	4(i)	0.3484	0	0.6203	100
Ge3	4(i)	0.3877	0	0.3150	100
Ge4	4(i)	0.4468	0	0.1345	100

No isotypic compounds have been observed.



Fig. 71. Projection of the Yb₇Al₅Ge₈ unit cell and coordination polyhedra of the atoms: (a-d) Yb, (e-g) Al, (h-k) Ge.

3.20	).2.	$Nd_4Rh_4$	Ge ₃ structure	e type					
SG	C2/c	c, $Z = 4$ ,	a=2.1021,	<i>b</i> =0.5652,	c = 0.7941,	$\beta = 110.08^{\circ}$	(Salamakha	1989).	See
fig.	72.								

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Nd1	8(f)	0.17058	0.1154	0.3993	100	
Nd2	8(f)	0.43350	0.1479	0.3317	100	
Rh1	8(f)	0.06212	0.1340	0.01774	100	
Rh2	8(f)	0.27848	0.1509	0.1849	100	
Gel	8(f)	0.17147	0.3813	0.0582	100	
Ge2	4(e)	0	0.1493	1/4	100	

No isotypic compounds have been observed.



Fig. 72. Projection of the Nd₄Rh₄Ge₃ unit cell and coordination polyhedra of the atoms: (a, b) Nd, (c-f) Rh and Ge.

5012	[/ <b>c</b> , <b>Z</b> +, <b>a</b> 1.1517	, 0 1.0017	, c 1.5577, p	100.10 (1	aviyak et al. 1967a)
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Yb1	4(e)	0.0946	0.7707	0.0684	100
Yb2	4(e)	0.1199	0.3541	0.3026	100
Yb3	4(e)	0.1285	0.0178	0.4334	100
Yb4	4(e)	0.1421	0.0634	0.1732	100
Yb5	4(e)	0.3548	0.5124	0.5419	100
Yb6	4(e)	0.3814	0.3122	0.1812	100
Yb7	4(e)	0.5947	0.1431	0.3996	100
Yb8	4(e)	0.6667	0.1094	0.1958	100
Li	4(e)	0.16	0.425	0.129	100
Ge1	4(e)	0.0507	0.6229	0.2303	100
Ge2	4(e)	0.0704	0.3144	0.1029	100
Ge3	4(e)	0.0863	0.4928	0.4615	100
Ge4	4(e)	0.1540	0.8291	0.2786	100
Ge5	4(e)	0.1773	0.5207	0.1364	100
Ge6	4(e)	0.1946	0.2165	0.0060	100
Ge7	4(e)	0.3115	0.1519	0.3381	100
Ge8	4(e)	0.4018	0.3691	0.3801	100

3.20.3.  $Yb_8LiGe_{13}$  structure type SG P2₁/c, Z=4, a=1.1317, b=1.0817, c=1.5577,  $\beta$ =106.40° (Pavlyuk et al. 1987a)

304		P.S. S			
Ge9	4(e)	0.4064	0.4221	0.0007	100
Ge10	4(e)	0.4361	0.0435	0.2393	100
Ge11	4(e)	0.5108	0.2117	0.0386	100
Ge12	4(e)	0.6685	0.3362	0.2992	100
Ge13	4(e)	0.7530	0.2474	0.0586	100

No isotypic compounds have been observed.

## 3.21. $R_3(M, Ge)_5$ and $R_5(M, Ge)_8$ compounds

3.21.1.	La₃In₄Ge	structure	type
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SG I4/mcm, Z = 4, a = 0.8516, c = 1.1902 (Guloy and Corbett 1996)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
La1	4(a)	0	0	0.25	100	
La2	8(h)	0.3354	0.8354	0	100	
In	16(l)	0.1428	0.6428	0.1863	100	
Ge	4(c)	0	0	0	100	

No isotypic compounds have been observed.

# 3.21.2. *Hf*₃Ni₂Si₃ structure type

SG Cmcm, Z=4, a=0.42730, b=1.0403, c=1.4128 for Ho₃Ir₂Ge₃ (Salamakha et al. 1996)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Ho1	4(c)	0	0.6407	1/4	100	
Ho2	8(f)	1/2	0.5839	0.1107	100	
Ir	8(f)	1/2	0.7016	0.1008	100	
Ge1	8(f)	0	0.6224	0.0357	100	
Ge2	4(c)	0	0.3431	1/4	100	

Isotypic compounds:  $R_3Li_2Ge_3$ : R = Y, Tb–Tm, Lu  $R_3Fe_2Ge_3$ : R = Er, Lu  $Sc_3Co_2Ge_3$  $Er_3Ni_2Ge_3$ 



Fig. 73. Projection of the  $Ho_3Ir_2Ge_3$  unit cell and coordination polyhedra of the atoms: (a, b) Ho, (c-e) Ir and Ge.

The coordination numbers of holmium are 17 and 18 (fig. 73a,b). The iridium and germanium atoms are situated in the centres of trigonal prisms with additional atoms (fig. 73c-e).

#### 3.21.3. $Tm_3(Ga_{0.5}Ge_{0.5})_5$ structure type

SG I4/mcm, Z = 4, a = 0.7748, c = 1.0836 (Gryniv and Myakush 1989)

Atomic coordinates were not presented.

### 3.21.4. $U_3Sb_3Cu_2$ structure type

SG P6₃/mmc, Z=2, a=0.4142, c=2.2315 for Ce₃Sn₃Ge₂ (Stetskiv 1999). See fig. 74.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Ce1	4(f)	1/3	2/3	0.0788	100	
Ce2	2(c)	1/3	2/3	1/4	100	
Sn1	4(f)	1/3	2/3	0.6580	100	
Sn2	2(a)	0	0	0	100	
Ge	4(e)	0	0	1/6	100	

Isotypic compounds:

 $R_3Sn_3Ge_2$ : R = La, Pr, Sm



Fig. 74. Projection of the  $Ce_3Sn_3Ge_2$  unit cell and coordination polyhedra of the atoms: (a, b) Ce, (c, d) Sn, (e) Ge.

$3.21.5. Nb_50$	Cu ₄ Si ₄ structur	e type			
SG I4/m, $Z =$	=2, a=1.1210	c = 0.43698 f	for Yb ₅ Li ₄ Ge ₄	(Pavlyuk et al.	1989)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Yb1	2(a)	0	0	0	100	
Yb2	8(h)	0.1957	0.1188	0	100	
Li	8(h)	0.079	0.400	0	100	
Ge	8(h)	0.4307	0.2456	0	100	

No isotypic compounds have been observed.

# 3.22. $R_2(M, Ge)_3$ compounds

3.22.1. Nd₆Co₅Ge₄ structure type

SG P $\overline{6}$ m2, Z=1, a=0.9272, c=0.4188 for Nd₆Co₅Ge_{2.2} (Salamakha et al. 1986)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Nd1	3(k)	0.8696	0.1304	1/2	100	
Nd2	3(j)	0.5179	0.4821	0	100	
Co1	3(j)	0.1519	0.8481	0	100	
Co2	1(c)	1/3	2/3	0	100	
Co3	1(a)	0	0	0	100	

Ge1	3(k)	0.2359	0.7641	1/2	40
Ge2	1(f)	2/3	1/3	1/2	100

No isotypic compounds have been observed.

For the neodymium atoms, polyhedra with 17 and 15 apexes are typical (fig. 75a,b). The polyhedra for cobalt atoms are trigonal prisms and icosahedra (fig. 75c–e). The germanium coordination polyhedra are trigonal prisms and deformed cubo-octahedra (fig. 75f, g).



Fig. 75. Projection of the  $Nd_6Co_5Ge_{2,2}$  unit cell and coordination polyhedra of the atoms: (a, b) Nd, (c-e) Co, (f, g) Ge.

#### 3.22.2. Sc₂CoSi₂ structure type

SG C2/m, Z = 4, a = 1.0691, b = 0.42618, c = 1.0050,  $\beta = 118.07^{\circ}$  for Ho₂OsGe₂ (Glady-shevsky et al. 1991b)

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)	
Ho1	4(i)	0.9968	0	0.3253	100	
Ho2	4(i)	0.1848	0	0.1130	100	

308		P.S. SA	LAMAKHA		
Os	4(i)	0.2710	0	0.6320	100
Ge1	4(i)	0.3585	0	0.4386	100
Ge2	4(i)	0.4876	0	0.1251	100

Isotypic compounds:

 $R_2CoGe_2$ : R = Sc, Y, Nd-Tm

 $R_2RuGe_2$ : R=Nd, Sm, Ho

 $R_2RhGe_2$ : R = Nd, Sm, Ho

 $R_2$ IrGe₂: R=Nd, Ho

For holmium atoms, polyhedra with 17 and 18 apexes are typical (fig. 76a,b). The atoms of osmium are situated inside the distorted cubo-octahedra (fig. 76c). The coordination polyhedra for the germanium atoms are trigonal prisms with additional atoms (fig. 76d, e).



Fig. 76. Projection of the  $Ho_2OsGe_2$ unit cell and coordination polyhedra of the atoms: (a, b) Ho, (c) Os, (d, e) Ge.

3.22.3. Mo₂FeB₂ structure type

SG	P4/mbm,	Z = 2,	a = 0.7205,	c = 0.4294	for Y	Yb ₂ InGe ₂	(Zaremba e	t al.	1997)
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Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Yb	4(g)	0.32492	0.82492	0	100	
In	2(b)	0	0	1/2	100	
Ge	4(h)	0.1229	0.6229	1/2	100	

Isotypic compounds:

 $R_2InGe_2$ : R = Y, La–Sm, Gd–Ho



Fig. 77. Projection of the 1/8 of the  $Tb_{117}Fe_{52}Ge_{112}$  unit cell.

# 3.23. $R_9(M, Ge)_{13-11}$ compounds

3.23.1.  $Tb_{117}Fe_{52}Ge_{112}$  structure type SG Fm-3m, Z = 4, a = 2.8580 (Pecharsky et al. 1987). See figs. 77 and 78.

			/1	-/	$C(\theta/)$
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Tb1	96(k)	0.0681	0.0681	0.1557	100
Tb2	96(k)	0.1793	0.1793	0.4084	100
Tb3	96(k)	0.1995	0.1995	0.0663	100
Tb4	96(j)	0	0.1036	0.2550	100
Tb5	48(i)	1/2	0.1158	0.1158	100
Tb6	24(e)	0.3384	0	0	100
Tb7	8(c)	1/4	1/4	1/4	100
Tb8	4(a)	0	0	0	100
Fe1	96(k)	0.1676	0.1676	0.2302	100
Fe2	48(h)	0	0.0723	0.0723	100
Fe3	32(f)	0.3983	0.3983	0.3983	100
Fe4	32(f)	0.4503	0.4503	0.4503	100
Gel	96(k)	0.0738	0.0738	0.3228	100

310	0 P.S. SALAMAKHA						
Ge2	96(k)	0.1071	0.1071	0.2423	100		
Ge3	48(i)	1/2	0.2094	0.2094	100		
Ge4	48(h)	0	0.1447	0.1447	100		
Ge5	48(g)	0,1395	1/4	1/4	100		
Ge6	32(f)	0.1464	0.1464	0.1464	100		
Ge7	32(f)	0.3088	0.3088	0.3088	100		
Ge8	24(e)	0.1152	0	0	100		
Ge9	24(e)	0.2150	0	0	100		

Isotypic compounds:  $Nd_{117}Cr_{52}Ge_{112}$   $R_{117}Fe_{52}Ge_{112}$ : R = Y, Pr, Sm, Dy–Tm, Lu  $R_{117}Co_{52}Ge_{112}$ : R = Pr, Sm



Fig. 78. Coordination polyhedra of the atoms in the  $Tb_{117}Fe_{52}Ge_{112}$  structure: (a-h) Tb, (i-l) Fe, (m-u) Ge.

SG Pnma, $Z=4$ , $a=0.7013$ , $b=1.4429$ , $c=0.7573$ (Pavlyuk et al. 1990)						
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Tm1	8(d)	0.828	0.127	0.676	100	
Tm2	8(d)	0.476	0.096	0.317	100	
Li	4(c)	0.158	1/4	0.479	100	
Ge1	8(d)	0.165	0.037	0.533	100	
Ge2	4(c)	0.784	1/4	0.363	100	
Ge3	4(c)	0.517	1/4	0.588	100	

3.23.2.  $Tm_4LiGe_4$  structure type

Isotypic compounds:  $R_4LiGe_4$ : R = Y, Gd-Lu

3.23.3. La₃Ni₂Ga₂ structure type

SG Pbcm, Z = 4, a = 0.5658, b = 0.7863, c = 1.3581 for Nd₃Ru₂Ge₂ (Bodak et al. 1989b). See fig. 79.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Nd1	8(e)	0.1509	0.4021	0.0981	100	
Nd2	4(d)	0.6282	0.2379	1/4	100	
Ru	8(e)	0.3572	0.0318	0.0902	100	
Gel	4(d)	0.1353	0.1102	1/4	100	
Ge2	4(c)	0.6223	1/4	0	100	

Isotypic compounds:

 $R_3Ru_2Ge_2$ : R=La-Sm

R₃Rh₂Ge₂: R=Y, La-Sm, Gd-Tm, Lu



Fig. 79. Projection of the  $Nd_3Ru_2Ge_2$  unit cell and coordination polyhedra of the atoms: (a,b) Nd, (c) Ru, (d,e) Ge.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Sc1	8(1)	0	0.31373	0.08338	100
Sc2	4(j)	1/2	0	0.10743	100
Sc3	4(j)	1/2	0	0.27270	100
Sc4	2(c)	1/2	1/2	0	100
Ni1	8(1)	0	0.22699	0.30457	100
Ni2	2(a)	0	0	0	100
Ge1	8(1)	0	0.13854	0.19132	100
Ge2	4(i)	0	0	0.36590	100
Ge3	4(g)	0	0.20724	0	100

3.23.4.  $Sc_9Ni_5Ge_8$  structure type SG Immm, Z=2, a=0.39822, b=0.9129, c=2.0426 (Kotur et al. 1989)

No isotypic compounds have been observed.

3.24. R(M, Ge) compounds

3.24.1. CrB structure type

SG Cmcm, Z = 4, a = 0.4033, b = 1.0884, c = 0.4287 for Sm₂PtGe (Barakatova 1994)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Sm	4(c)	0	0.1392	1/4	100	
Х	4(c)	0	0.4200	1/4	100	

X = 0.5Pt+0.5Ge

Isotypic compounds:

 $Ce_{0.8}R_{0.2}Ge: R = Y, Dy-Tm$ 

3.24.2. FeB structure type

SG Pnma, Z=4, a=0.8453, b=0.3732, c=0.5582 for Sm₂PdGe (Barakatova 1994) Atomic coordinates have not been determined.

3.24.3.  $La_2NiGe$  structure type

SG I4/mcm, Z=8, a=0.7947, c=1.4262 (Bruskov et al. 1983). See fig. 80.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
La	16(l)	0.1678	0.6678	0.1457	100
Ni	8(h)	0.6151	0.1151	0	100
Ge1	4(c)	0	0	0	100
Ge2	4(a)	0	0	1/4	100

No isotypic compounds have been found.



Fig. 80. Projection of the La₂NiGe unit cell and coordination polyhedra of the atoms: (a) La, (b) Ni, (c, d) Ge.

# 3.24.4. Gd₃NiSi₂ structure type

SG Pnma, Z=4, a=1.20401, b=0.4358, c=1.1871 for La₃NiGe₂ (Bodak et al. 1982). See fig. 81.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
La1	4(c)	0.0576	1/4	0.12471	100
La2	4(c)	0.21649	1/4	0.80142	100
La3	4(c)	0.38309	1/4	0.05697	100
Ni	4(c)	0.12757	1/4	0.36719	100
Ge1	4(c)	0.30183	1/4	0.49409	100
Ge2	4(c)	0.47464	1/4	0.81216	100

Isotypic compounds:

 $R_3CoGe_2$ : R = Ce-Sm

 $R_3NiGe_2$ : R=Y, Ce-Sm, Gd-Er



Fig. 81. Projection of the La₃NiGe₂ unit cell and coordination polyhedra of the atoms: (a-c) La, (d) Ni, (e, f) Ge.
# 3.25. $R_{11}(M, Ge)_{10}$ compounds

	, ,		(		, 0	
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Sc1	16(n)	0	0.2507	0.3102	100	
Sc2	16(n)	0	0.3356	0.1024	100	
Sc3	8(h)	0.3272	0.3272	0	100	
Sc4	4(e)	0	0	0.1688	100	
Al	8(h)	0.1270	0.1270	0	100	
Ge1	16(m)	0.2047	0.2047	0.1711	100	
Ge2	8(j)	0.1470	1/2	0	100	
Ge3	4(e)	0	0	0.3815	100	
Ge4	4(d)	0	1/2	1/4	100	
						_

3.25.1. Sc₁₁Al₂Ge₈ structure type

SG I4/mmm, Z=4, a=1.0419, c=1.4974 (Zhao and Parthé 1991b). See fig. 82.

No isotypic compounds have been observed.



Fig. 82. Projection of the  $Sc_{11}Al_2Ge_8$  unit cell and coordination polyhedra of the atoms: (a-d) Sc, (e) Al, (f-i) Ge.

SG C2/	$2/m$ , $Z = 2$ , $a = 1.8637$ , $b = 0.4384$ , $c = 1.4191$ , $\beta = 106.13^{\circ}$ (Pecharsky et al. 1986)					
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
La1	4(i)	0.0957	0	0.2840	100	
La2	4(i)	0.1422	0	0.8494	100	
La3	4(i)	0.2160	0	0.5999	100	
La4	4(i)	0.4515	0	0.3738	100	
La5	4(i)	0.6601	0	0.0935	100	
La6	2(a)	0	0	0	100	
Ni1	4(i)	0.0594	0	0.4752	100	
Ni2	4(i)	0.2477	0	0.0503	100	
Ge1	4(i)	0.2614	0	0.2345	100	



d

b



Fig. 83. Projection of the  $La_{11}Ni_4Ge_6$  unit cell and coordination polyhedra of the atoms: (a-f) La, (g-k) Ni and Ge.

3.25.2. La₁₁Ni₄Ge₆ structure type

Ge2	4(i)	0.3713	0	0.5490	100
Ge3	4(i)	0.4864	0	0.1512	100

No isotypic compounds have been found.

The coordination polyhedra for the lanthanum atoms have 17 and 18 apexes (fig. 83a– f). For nickel and germanium atoms, the coordination polyhedra as trigonal prisms with additional atoms are typical (fig. 83g–k).

3.26.  $R_{26}(M, Ge)_{23}$  compounds

SG P4/	nmm, Z = 2, a = 1.45	z = 2, a = 1.4523, c = 1.0318 (Sologub et al. 1994)				
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Ho1	4(f)	3/4	1/4	0.2690	100	
Ho2	8(h)	0.3688	0.6312	1/2	100	
Ho3	8(i)	1/4	0.0709	0.9446	100	
Ho4	8(i)	1/4	0.0665	0.3844	100	
Ho5	8(j)	0.3922	0.3922	0.6647	100	
Ho6	16(k)	0.3805	0.57087	0.1745	100	
Pd1	2(c)	1/4	1/4	0.184	50	
Pd2	8(j)	0.3682	0.3682	0.1729	100	
Ge1	2(c)	1/4	1/4	0.7904	100	
Ge2	8(i)	1/4	0.5379	0.6926	100	
Ge3	8(j)	0.4538	0.4538	0.3880	100	
Ge4	8(j)	0.4420	0.4420	0.9597	100	
<b>X</b> 1	2(c)	1/4	1/4	0.5396	100	
X2	8(i)	1/4	0.6300	0.9716	100	

3.26.1.  $Ho_{26}Pd_4(Pd, Ge)_{19}$  structure type SG P4/nmm, Z=2, a=1.4523, c=1.0318 (Sologub et al. 1994)

X1 = 0.21Pd+0.79Ge; X2 = 0.27Pd+0.73Ge

No isotypic compounds have been observed.

The coordination polyhedra of the holmium atoms have 14–17 apexes (fig. 84a–f). Those of the palladium atoms are cubes with four additional atoms (fig. 84g) and distorted trigonal prisms with additional atoms (fig. 84h). The germanium and X atoms occupy the centres of tetragonal antiprisms with additional atoms and distorted trigonal prisms with additional atoms (fig. 84i–m).



Fig. 84. Projection of the  $Ho_{26}Pd_4(Pd,Ge)_{19}$  unit cell and coordination polyhedra of the atoms: (a-f) Ho, (g,h) Pd, (i-m) Ge.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
Ce1	16(k)	0.0786	0.6170	0.1796	100	
Ce2	8(j)	0.1115	0.1115	0.3409	100	
Ce3	8(i)	1/4	0.0634	0.6321	100	
Ce4	8(i)	1/4	0.0651	0.0929	100	
Ce5	8(h)	0.3674	0.6326	1/2	100	
Ce6	4(f)	3/4	1/4	0.2652	100	
Lil	8(i)	1/4	0.600	0.649	100	
Li2	2(b)	3/4	1/4	1/2	100	
Ge1	8(j)	0.0382	0.0382	0.5998	100	

3.26.2.  $Ce_{26}Li_5Ge_{23-y}$  structure type SG P4/nmm, Z = 2, a = 1.5402, c = 1.0900 (Pavlyuk et al. 1987b)

Ge2	8(j)	0.0550	0.0550	0.0353	100
Ge3	8(j)	0.1239	0.1239	0.8456	100
Ge4	8(i)	1/4	0.5322	0.3170	100
Ge5	8(i)	1/4	0.6325	0.0149	100
Ge6	2(c)	1/4	1/4	0.204	100
Ge7	2(c)	1/4	1/4	0.470	100
Ge8	2(c)	1/4	1/4	0.853	37

No isotypic compounds have been observed.

3.27.  $R_7(M, Ge)_6$  and  $R_5(M, Ge)_4$  compounds

3.27.1. Ce₇Pd₄Ge₂ structure type

SG P2₁/c, Z = 4, a = 0.9315, b = 1.2277, c = 1.2273,  $\beta = 109.46^{\circ}$  (Gribanov et al. 1993b). See fig. 85.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Ce1	4(e)	0.0003	0.6613	0.3803	100
Ce2	4(e)	0.0017	0.5898	0.0992	100
Ce3	4(e)	0.0021	0.3799	0.3395	100
Ce4	4(e)	0.3535	0.0014	0.3363	100
Ce5	4(e)	0.3624	0.2482	0.0895	100
Ce6	4(e)	0.6321	0.0011	0.1545	100
Ce7	4(e)	0.6374	0.2532	0.4076	100
Pd1	4(e)	0.2508	0.0007	0.0605	100
Pd2	4(e)	0.2759	0.2489	0.3204	100
Pd3	4(e)	0.2989	0.4997	0.0749	100
Pd4	4(e)	0.7276	0.2464	0.1861	100
Gel	4(e)	0.1441	0.3801	0.1574	100
Ge2	4(e)	0.8561	0.3772	0.0826	100

No isotypic compounds have been found.



Fig. 85. Projection of the  $Ce_7Pd_4Ge_2$  unit cell and coordination polyhedra of the atoms: (a–g) Ce, (i–l) Pd, (m, n) Ge.

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
X1	8(d)	0.0253	0.1004	0.6781	100	
X2	8(d)	0.3795	0.1157	0.3388	100	
X3	4(c)	0.2120	1/4	0.0024	100	
Ge1	8(d)	0.2206	0.0449	0.0312	100	
Ge2	4(c)	0.0868	1/4	0.3885	100	
Ge3	4(c)	0.3239	1/4	0.6333	100	

3.27.2. *Sm*₅*Ge*₄ *structure type* SG Pnma, *Z* = 4, *a* = 0.7666, *b* = 1.4925, *c* = 0.7649 for Ce_{3.25}Lu_{1.75}Ge₄ (Shpyrka 1990)

X1 = X2 = X3 = 0.65Ce + 0.35Lu

Isotypic compounds:

 $Sc_{2.7}Y_{2.3}Ge_4$ ,  $Sc_{1.35}Y_{3.65}Ge_4$ ,  $Sc_{2.7}Dy_{2.3}Ge_4$ ,  $Sc_{1.8}Dy_{3.2}Ge_4$ 

 $Ce_{1.8}Y_{3.2}Ge_4,\ Ce_{0.45-1.35}Lu_{4.55-3.65}Ge_4$ 

Rare-earth atoms are surrounded by 14–17 neighbours (fig. 86a–c). Trigonal prisms with additional atoms are typical as coordination polyhedra for germanium atoms (fig. 86d–f).



Fig. 86. Projection of the Ce_{3.25}Lu_{1.75}Ge₄ unit cell and coordination polyhedra of the atoms: (a-c) R, (d-f) Ge.

$3.27.3. Gd_{5}$	$Si_2Ge_2 s$	tructure type					
SG P112 ₁ /a	, Z = 4,	a = 0.75808,	<i>b</i> =1.4802,	c = 0.77799,	$\gamma = 93.190^{\circ}$	(Pecharsky	and
Gschneidner	1997)						

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)	
Gd1	4(e)	0.325	0.2509	0.003	100	
Gd2	4(e)	-0.008	0.1010	0.180	100	
Gd3	4(e)	0.016	0.4012	0.188	100	
Gd4	4(e)	0.360	0.8817	0.161	100	
Gd5	4(e)	0.333	0.6209	0.176	100	
<b>X</b> 1	4(e)	0.189	0.245	0.360	100	
X2	4(e)	0.945	0.254	0.898	100	
X3	4(e)	0.201	0.959	0.460	100	
X4	4(e)	0.152	0.547	0.467	100	

X = 0.5Si + 0.5Ge

No isotypic compounds have been observed.

# 3.28. $R_4(M, Ge)_3$ and $R_3(M, Ge)_2$ compounds

3.28.1.  $La_8NiGe_5$  structure type SG Pmmn, Z=8, a=1.5586, b=1.8384, c=1.1351 (Bruskov et al. 1984)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)
Lal	8(g)	0.1111	0.1439	0.3842	100
La2	8(g)	0.1198	0.5753	0.2274	100
La3	8(g)	0.6003	0.5510	0.1028	100
La4	8(g)	0.6042	0.0641	0.4219	100
La5	8(g)	0.6186	0.1570	0.1031	100
La6	4(f)	0.1039	1/4	0.0799	100
La7	4(f)	0.1155	1/4	0.7273	100
La8	4(f)	0.5804	1/4	0.5926	100
La9	4(e)	1/4	0.0883	0.1425	100
La10	4(e)	1/4	0.0928	0.6394	100
La11	2(b)	1/4	3/4	0.1419	100
La12	2(b)	1/4	3/4	0.6598	100
Ni1	4(f)	0.5515	1/4	0.8855	100
Ni2	4(e)	1/4	0.5585	0.0105	100
Gel	8(g)	0.0435	0.0742	0.1547	100
Ge2	8(g)	0.0445	0.1007	0.6233	100
Ge3	4(f)	0.5494	1/4	0.3207	100
Ge4	4(e)	1/4	0.0079	0.3914	100
Ge5	4(e)	1/4	0.1736	0.9011	100
Ge6	4(e)	1/4	0.5543	0.7714	100
Ge7	4(e)	1/4	0.6537	0.4091	100
Ge8	2(a)	1/4	1/4	0.2678	100
Ge9	2(a)	1/4	1/4	0.5124	100

No isotypic compounds have been observed.

322

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)
Ce1	32(m)	0.1999	0.0668	0.1357	100
Ce2	8(g)	1/2	0	0.1439	100
Ce3	8(h)	0.1674	0.6674	1/2	100
Sn1	4(c)	0	0	0	100
Gel	8(h)	0.1199	0.6199	0	100
Ge2	4(a)	0	0	1/4	100
X	16(l)	0.1752	0.6752	0.2976	100

## 3.28.2. La₃InGe structure type

SG I4/mcm, Z=16, a=1.2423, c=1.5662 for Ce₃SnGe (Stetskiv 1999). See fig. 87.

X = 0.75Sn+0.25Ge Isotypic compounds:  $R_3$ SnGe: R = La-Sm  $Ce_3$ MGe: M =Sb, Bi



Fig. 87. Projection of the Ce₃SnGe unit cell and coordination polyhedra of the atoms: (a-c) Ce, (d) Sn, (e, f) Ge, (g) X.

## 3.29. $R_5(M, Ge)_3$ compounds

3.29.1.  $Y_2HfS_5$  structure type

SG Pnma, Z=4, a=1.2255, b=0.8898, c=0.8008 Ce₅RuGe₂ (Gladyshevsky et al. 1992b). See fig. 88.

Atom	Wyckoff notation	<i>x</i> / <i>a</i>	y/b	z/c	G (%)
Cel	8(d)	0.0703	0.5309	0.3156	100
Ce2	4(c)	0.0016	1/4	0.0343	100
Ce3	4(c)	0.2051	1/4	0.6420	100
Ce4	4(c)	0.2866	1/4	0.1630	100
Ru	4(c)	0.0188	1/4	0.4234	100
Ge	8(d)	0.3287	0.5050	0.4331	100

No isotypic compounds have been found.



Fig. 88. Projection of the Ce₅RuGe₂ unit cell and coordination polyhedra of the atoms: (a-d) Ce, (e) Ru, (f) Ge.

SG P4/ncc, $Z = 4$ , $a = 1.1760$ , $c = 0.6429$ (Belsky et al. 1987). See fig. 89.							
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)		
Ce1	16(g)	0.0358	0.1636	0.3372	100		
Ce2	4(b)	3/4	1/4	0	100		

3.29.2. Ce₅NiGe₂ structure type

Ni	4(c)	1/4	1/4	0.082	100
Ge	8(f)	0.4095	0.5905	1/4	100

No isotypic compounds have been observed.



Fig. 89. Projection of the Ce₅NiGe₂ unit cell and coordination polyhedra of the atoms: (a, b) Ce, (c) Ni, (d) Ge.

## 3.29.3. $Cr_5B_3$ structure type

SG I4/mcm, Z=4, a=0.7939, c=1.3908 for Nd₅(Ga, Ge)₃ (Opainych et al. 1992) Atomic coordinates have not been determined.

Isotypic compound: Ce₅Ga₂Ge

## 4. Structure types of quaternary rare-earth germanides

## 4.1. $R(M, M'Ge)_4$ compounds

Investigation of the quaternary alloys has been carried out mainly between two isotypic compounds, gradually substituting one of the components in the initial compounds. Thus, as typical for the ternary phases, the CeGa₂Al₂ structure type also occurs in the quaternary compounds  $Y_xR_{1-x}Mn_2Ge_2$  (R=La, Lu) (Venturini 1996),  $Sm_xR_{1-x}Mn_2Ge_2$  (R=Y, Gd)

(Duraj et al. 1989),  $Nd_xU_{1-x}M_2Ge_2$  (M=Mn, Co, Ni, Cu) (Sologub and Salamakha 1998),  $LaMn_{2-x}M_xGe_2$  (M=Fe, Cu) (Venturini and Malaman 1996),  $LaRu_xRh_{2-x}Ge_2$  (Venturini et al. 1989b). The same authors show, that when the  $LaM_2Ge_2$  ternary compounds crystallize with the structure types of CeGa₂Al₂ (for M=Ru, Rh, Pd) and of CaBe₂Ge₂ (for M=Ir), solid solutions originating from the ternary compounds are found to exist.

The formation of compounds with four individual components with the  $CaBe_2Ge_2$  structure becomes possible when the initial ternary compounds crystallize with the  $ClGa_2Al_2$  (SG I4/mmm) and  $LaPt_2Ge_2$  (SG P2₁) types of structure:  $LaPt_{1.2}Ru_{0.8}Ge_2$ ,  $LaPt_{1.1}Rh_{0.9}Ge_2$ , and  $LaPt_{0.7-1.4}Pd_{1.3-0.6}Ge_2$ . The compound  $LaPt_{1.42}Pd_{0.58}Ge_2$ , however, forms a unique structure type which is a superstructure to the  $CaBe_2Ge_2$  type. Atomic coordinates for this type are presented below.

SG P4/	SG P4/nmm, $Z = 2$ , $a = 0.4373$ , $c = 0.9914$ for La Pt _{1.48} Pd _{0.52} Ge ₂ (Venturini et al. 1989b)							
Atom	Wyckoff notation	x/a	y/b	z/c	G (%)			
La	2(c)	1/4	1/4	0.7539	100			
Pt	2(c)	1/4	1/4	0.1218	100			
Ge1	2(c)	1/4	1/4	0.3713	100			
Ge2	2(a)	3/4	1/4	0	100			
Х	2(b)	3/4	1/4	1/2	100			

4.1.1.  $LaPt_{1.42}Pd_{0.58}Ge_2$  structure type

X = 0.48Pt+0.52Pd

### 4.2. $R(M, M', Ge)_3$ compounds

### 4.2.1. *TbFeSi₂* structure type

SG Cmcm, Z = 4, a = 0.4203, b = 1.8266, c = 0.4229 for LaMnCu_{0.5}Ge_{1.5} (Norlidah et al. 1998)

Atom	Wyckoff notation	x/a	y/b	z/c	G (%)	
La	4(c)	0	0.1015	1/4	100	
Mn	4(c)	0	0.7494	1/4	100	
Ge	4(c)	0	0.3306	1/4	100	
X	4(c)	0	0.4680	1/4	100	

X = 0.5Cu+0.5GeIsotypic compounds:  $RMnCu_{0.5}Ge_{1.5}$ : R = Ce-Sm RMnNi_{0.5}Ge_{1.5}: R = La-NdRMnPd_{0.5}Ge_{1.5}: R = La-NdRRhCu_{0.5}Ge_{1.5}: R = La-NdLaMnPt_{0.5}Ge_{1.5}

4.2.2.  $LaTmIr_2Ge_4$  structure type SG Immm, Z = 4, a = 0.43230, b = 0.8825, c = 1.6101 (Malaman et al. 1989)

Atom	Wyckoff notation	<i>x/a</i>	y/b	z/c	G (%)	
La	4(g)	0	0.2399	0	100	
Tm	4(i)	0	0	0.2067	100	
Ir	8(1)	0	0.2486	0.3513	100	
Ge1	8(1)	0	0.3484	0.2002	100	
Ge2	4(j)	1/2	0	0.0796	100	
Ge3	4(i)	0	0	0.4206	100	

## 4.3. $R(M, M'Ge)_2$ compounds

4.3.1. Y₃NiAl₃Ge₂ structure type

SG P $\overline{6}$ 2m, Z=1, a=0.69481, c=0.41565 (Zhao and Parthé 1990a)

Wyckoff notation	x/a	y/b	z/c	G (%)	
3(f)	0.5963	0	0	100	
1(a)	0	0	0	100	
3(g)	0.2261	0	1/2	100	
2(d)	1/3	2/3	1/2	100	
	Wyckoff notation 3(f) 1(a) 3(g) 2(d)	Wyckoff notation         x/a           3(f)         0.5963           1(a)         0           3(g)         0.2261           2(d)         1/3	Wyckoff notation         x/a         y/b           3(f)         0.5963         0           1(a)         0         0           3(g)         0.2261         0           2(d)         1/3         2/3	Wyckoff notationx/ay/bz/c3(f)0.5963001(a)0003(g)0.226101/22(d)1/32/31/2	Wyckoff notationx/ay/bz/cG (%)3(f)0.5963001001(a)0001003(g)0.226101/21002(d)1/32/31/2100

## 5. Discussion

In many cases, ternary germanides of rare-earth metals crystallize with the structure types characteristic for the compounds with silicon which have been discussed extensively in the reviews of Gladyshevsky and Bodak (1982) and Parthé and Chabot (1984). The analysis of many structure types of germanium containing compounds was presented by Gladyshevsky et al. (1990). Our discussion will not be concerned with those types that have been considered in these three surveys.

#### P.S. SALAMAKHA

## 5.1. Classification of the ternary structure types of the germanides

The rare-earth atoms in the above described compounds are generally the largest atoms in the unit cells. Therefore their structure types can be categorized as definite classes in the classification scheme of Kripyakevich (1977), by the coordination number and coordination polyhedra of the atoms of other components with the smaller radii.

Among the R-M-Ge compounds, the most important three classes of structure types are: (1) class 5 with a coordination number equal to 12, and the icosahedron coordination polyhedron; (2) class 9 with coordination numbers of 8–10 and a tetragonal antiprism coordination polyhedron; (3) class 10 with coordination numbers of 6+n (n=1, 2, 3 or 5) and a trigonal prism coordination polyhedron and its derivatives.

## 5.1.1. Structure types with icosahedral coordination of the smallest atoms

The compound  $Nd_2Cr_9Ge_8$  is the first representative of a novel structure type. The coordination polyhedra for the smallest atoms (Cr and Ge) have the form of an icosahedron and its derivatives. The  $Nd_2Cr_9Ge_8$  structure can be considered as a linear stacking of the CaCu₅ segments and hypothetical RX₁₂ slabs (fig. 90).

The ErCo₃Ge₂ (or Er_{6-x}Co₆Ge₄) structure is a defected derivative from CaCu₅ and differs from the present structure by a slight shift of the x coordinate of Co atoms from the site 3(g),  $\frac{1}{2}0\frac{1}{2}$ . As result, the symmetry is changed, and the c lattice parameter is doubled.

A part of the same atomic positions from the CaCu₅ structure are retained in YCo₆Ge₆, which is formed by the substitution of R atoms by pairs of M atoms. The RM₆Ge₆ compounds crystallize with different structure types, and in most cases polymorphism is observed in these compounds. All of these structure types are related with the YCo₆Ge₆ type. The lattice parameters for the RM₆Ge₆ structures expressed as the lattice parameters of YCo₆Ge₆ ( $a_1$ ,  $c_1$ ) are presented in table 1.



Fig. 90. Structure type  $Nd_2Cr_9Ge_8$  as a linear hybrid of CaCu₅ and hypothetical RX₁₂ structure.

Structure type	Space group	Representatives	Lattice parameters		
			а	b	с
YCo ₆ Ge ₆	P6/mmm	$RCo_6Ge_6$ (R=Gd-Lu)	$a_1$	$a_1$	$c_1$
MgFe ₆ Ge ₆	P6/mmm	$RCr_6Ge_6(R = Y, Tb-Er)$	$a_1$	$a_1$	$2c_1$
GdMn ₆ Ge ₆	P6/mmm	GdMn ₆ Ge ₆	$a_1$	$a_1$	$2c_1$
ScNi ₆ Ge ₆	P6/mmm	ScNi ₆ Ge ₆	$2a_1$	$2a_1$	$2c_1$
TbFe ₆ Sn ₆	Cmcm	$RFe_6Ge_6(R = Tb-Ho)$	$2c_1$	$2\sqrt{3}a_1$	$a_1$
HoFe ₆ Sn ₆	Immm	TmFe ₆ Ge ₆	$2c_1$	$3\sqrt{3}a_1$	$a_1$
GdFe ₆ Ge ₆	Pnma	GdFe ₆ Ge ₆	$12a_1$	$c_1$	9√3

Table 1 Structure times of cormanides related with VCo Ge time

5.1.2. Structure types with tetragonal antiprismatic coordination of the smallest atoms An example of the tetragonal antiprism polyhedron  $(R_4M_4)$  is a fragment typical for the BaAl₄ structure. The structure types with tetragonal antiprismatic coordination generally occur at a rare-earth concentration of R  $\approx 20\%$ . The structures which are built from BaAl₄ fragments are presented in table 2.

Table 2 Distorted and substited derivatives of BaAl₄ in ternary rare-earth germanides					
Structure type	Space group	Representatives			
CeAl ₂ Ga ₂	I4/mmm	RMn(Fe, Co, Ni, Cu, Ru, Rh, Pd, Ag, Pt, Au) ₂ Ge ₂			
CaBe ₂ Ge ₂	P4/nmm	$RIr_2Ge_2, R = La - Tb$			
LaPt ₂ Ge ₂	P2 ₁	$RPt_2Ge_2, R = La - Dy$			
BaNiSn ₃	I4mm	$RCoGe_3$ , $R=Ce-Eu$			
$U_2Co_3Si_5$	Ibam	$R_2Ru_3Ge_5$ , $R = La$ -Sm, Gd-Tm; $R_2Rh_3Ge_5$ , $R = La$ -Pr; $R_2Ir_3Ge_5$ , $R = La$ -Sm, Gd-Dy			
Lu ₂ Co ₃ Si ₅	C2/c	$R_2Co_3Ge_5$ , $R = Pr-Sm$ , $Gd-Er$ ; $R_2Rh_3Ge_5$ , $R = Nd-Sm$ , $Gd-Tm$			
$LaPt_{1.42}Pd_{0.58}Ge_2$	P4/nmm	$LaPt_{1.42}Pd_{0.58}Ge_2$			

## 5.1.3. Structure types with trigonal prismatic coordination of the smallest atoms

Among ternary germanides of rare earths, the most widespread are the structure types which belong to the trigonal prismatic category. In these structures, the trigonal prisms can completely occupy the space without gaps to form columns, walls and stacks, or to connect the peaks (edges). This fragment which is formed by the six large (R) atoms at the corners, and the small seventh one (M or X) inside it gives the AlB₂ type. The

#### P.S. SALAMAKHA

Structure type Space group		Representatives		
AlB ₂	P6/mmm	RCuGe, R=La–Sm		
CaIn ₂	P6 ₃ /mmc	RCuGe, $R = Gd - Yb$		
KHg ₂	Imma	$R(Pd,Ge)_2$ , $R = Gd-Yb$ ; YbAuGe		
ZrBeSi	P6 ₃ /mmc	EuZnGe		
LiGaGe	P6 ₃ mc	RAgGe, R=La-Pr; RAuGe, R=Sc, Y, La-Sm, Gd-Yb		
DyAlGe	$Cmc2_1$	DyAlGe		
YAlGe	Cmcm	RAIGe, $R = Y, Gd-Tm$		
TiNiSi	Pnma	RCoGe, R=Sc, Y, Sm, Gd-Yb; RNi(Pt)Ge, R=Sc, Y, Ce-Sm, Gd-Yb		
Tb ₃ Co ₂ Ge ₄	C2/m	$R_3Co_2Ge_4$ , $R = Sm$ , $Gd-Tm$		
CaCuGe	Pna2 ₁	EuCuGe		
α-YbAuGe	Pnma	YbAuGe		
β-YbAuGe	Pnma	YbAuGe		
EuAuGe	Imm2	EuAuGe, YbAu _{1.24} Ge _{0.76}		

Table 3 Distorted, substituted and vacancy derivatives of  $AlB_2$  in ternary rare-earth germanides

structure types related with the farther structure type  $AlB_2$  by various deformations are presented in table 3.

The new structural types YAlGe, and  $\alpha$ -YbAuGe and  $\beta$ -YbAuGe are the centrosymmetric variants of the earlier observed DyAlGe type and CaCuGe type, respectively. EuAuGe is a superstructure to the KHg₂ type.

Mutual rotation of plane segments by 90° in the AlB₂ structure leads to the formation of  $\alpha$ -ThSi₂,  $\alpha$ -GdSi₂, LaPtSi and CeGe_{0.66}Si_{0.92} types.

## 5.2. Formation of superstructures

Structure types may have the same positions of atoms, but differ by the number of components substituting at these positions. Simultaneously, the symmetry and outline of the unit cell may be changed. An ordered substitution of the atom positions by different atoms leads to the formation of superstructures. An increase of the number of components in a compound enhances the number of possible variants of their distribution over the atom positions of the parent structure.

Table 4 demonstrates the superstructures which are formed as a result of an ordered substitution of the smallest atoms in the initial binary structure type by the other small atoms.

The structure type  $Y_3NiAl_3Ge_2$  is an example of a quaternary substitution variant of a binary structure type:  $Fe_2P \rightarrow ZrNiAl \rightarrow Y_3NiAl_3Ge_2$  (SG P62m). The partly ordered occupation of the atomic positions of Be in the CaBe₂Ge₂ structure by the transition metal atoms leads to the formation of the LaPt_{1.42}Pd_{0.58}Ge₂ superstructure.

Structure type	Space group	Structure type	Space group
Yb ₅ Sb ₃	Pnma	Ce ₅ RuGe ₂	Pnma
Nd ₅ Ir ₃	P4/ncc	Ce ₅ NiGe ₂	P4/ncc
EuMg ₅	P6 ₃ /mmc	Sc ₃ Ni ₁₁ Si ₄	P6 ₃ /mmc
ZrGa ₂	Cmmm	Te ₂ Ag ₃ Al	Cmmm
BaAl ₄	I4/mmm	CeGa ₂ Al ₂	I4/mmm
UPt ₂	Cmcm	YAlGa	Cmcm
$\alpha$ -ThSi ₂	I4 ₁ /amd	LaPtSi	$I4_1md$
CaIn ₂	P6 ₃ /mmc	LiGaGe	P6 ₃ mc
Fe ₂ P	P62m	ZrNiAl	P62m
Eu ₃ Ga ₈	Immm	U ₃ Ni ₄ Si ₄	Immm
Ni ₂ In	P6 ₃ /mmc	ZrBeSi	P6 ₃ /mmc
PbCl ₂	Pnma	TiNiSi	Pnma
SrSi ₂	<b>P2</b> ₁ 3	ZrOS	P2 ₁ 3

 Table 4

 Formation of superstructures by ordered substitution of smaller atoms

The LaTmIrGe₂ structure is a superstructure of  $YIrGe_2$  and is formed as a consequence of an ordered occupation of large atoms in the initial structure by rare-earth atoms with different sizes.

The occupation of the atomic positions of Cr in the  $Cr_{23}C_6$  structure by the large Ce atoms and the small Pd atoms gives the new  $Ce_3Pd_{20}Ge_6$  structure type, i.e. a superstructure of the  $Cr_{23}C_6$  type.

A new structure type EuAuGe was derived from the binary  $KHg_2$  structure by an ordered arrangement of the Eu(1) and Eu(2) atoms substituting on the K positions, and the Au and Ge atoms on the Hg positions of  $KHg_2$ . Thus, EuAuGe is a superstructure of the binary intermetallic  $KHg_2$ .

## 5.2.1. Formation of superstructures of the binary rare-earth germanides

The crystal structure of  $Ho_{26}Pd_4(Pd, Ge)_{19-x}$  represents a substitutional variant of the  $Er_{26}Ge_{23-x}$  structure type. The difference between the two structures lies only in the replacement of germanium atoms by palladium atoms in positions 2(c) and 8(j) and the presence of a statistical distribution of Ce and Pd atoms in positions 2(c) and 8(i). Other isotypical ternary phases are not known. Only the compound  $Ce_{26}Li_5Ge_{23-y}$ , where the Li atoms occupy the 2(b) and 8(i) positions which are vacant in the previous phases, has a similar structure (table 5).

The formation of superstructures from the  $Sm_5Ge_4$  type originates from an ordered occupation of the Sm atomic positions by other atoms (table 6). The symmetry of the structures remains unchanged.

Site	$\mathrm{Er}_{26}\mathrm{Ge}_{23-x}$	$\operatorname{Ho}_{26}\operatorname{Pd}_4(\operatorname{Pd},\operatorname{Ge})_{19-x}$	$Ce_{26}Li_5Ge_{23-y}$	
4(f)	Er	Но	Ce	
8(h)	Er	Но	Ce	
8(I)	Er	Но	Ce	
8(I)	Er	Но	Ce	
8(j)	Er	Но	Ce	
16(k)	Er	Но	Ce	
2(c)	Ge	Pd	Ge	
2(c)	Ge	Ge	Ge	
2(c)	Ge	$Pd_{0.21}Ge_{0.79}$	Ge	
8(I)	Ge	Ge	Ge	
8(I)	Ge	$Pd_{0.27}Ge_{0.73}$	Ge	
8(j)	Ge	Pd	Ge	
8(j)	Ge	Ge	Ge	
8(j)	Ge	Ge	Ge	
2(b)			Li	
8(I)			Li	

 $\label{eq:Table 5} Table 5 \\ Site occupancies in Er_{26}Ge_{23-x}, Ho_{26}Pd_4(Pd,Ge)_{19-x} \mbox{ and } Ce_{26}Li_5Ge_{23-y} \mbox{ (SG P4/nmm)} \\$ 

 $\label{eq:Table 6} Table \ 6 \\ Site occupancies in \ Sm_5Ge_4, \ Ce_2Sc_3Ge_4, \ Sc_2V_3Ge_4 \ and \ Tm_4LiGe_4 \ (SG \ Pnma) \\$ 

Site	Sm₅Ge₄	$Ce_2Sc_3Ge_4$	$Sc_2V_3Ge_4$	Tm ₄ LiGe ₄
4(c)	Sm	Sc	v	Li
8(d)	Sm	Sc	V	Tm
8(d)	Sm	Ce	Sc	Tm
4(c)	Ge	Ge	Ge	Ge
4(c)	Ge	Ge	Ge	Ge
8(d)	Ge	Ge	Ge	Ge

The compound  $Gd_5Si_2Ge_2$  occurs between two isotypic binary compounds,  $Gd_5Si_4$  and  $Gd_5Ge_4$  (structure type  $Sm_5Ge_4$ ). An internal deformation in the structure leads to the exterior one. The initial orthorhombic structure transforms to a monoclinic structure.

In contrast to the previously described examples, the formation of three types of superstructures of the  $Ho_{11}Ge_{10}$  type is possible (table 7):

- (i) an ordered substitution of the site originally occupied by the large atom  $16(n) Sc_{11-x}Yb_xGe_{10}$ ;
- (ii) an ordered substitution of the site originally occupied by the small atom  $8(h) Sc_{11}Al_2Ge_8$ .
- (iii) an  $Sc_7Mn_{4-x}Ge_{10-x}$  structure: the Mn atom occupies the 16(n) position, and the statistical mixture (Mn,Ge) fills the 8(h) position.

She becupations in $10_{11}0_{10}$ , $50_{11}M_20_{8}$ , $50_{7}M_{4+-}0_{10-x}$ (x = 1.5) and $50_{11-x}$ 10, $50_{10}$ (x ~ 5) (50 14/10000)									
Site	Ho ₁₁ Ge ₁₀	$Sc_{11}Al_2Ge_8$	$\mathrm{Sc}_{7}\mathrm{Mn}_{4+x}\mathrm{Ge}_{10-x}$	$\operatorname{Sc}_{11-x}\operatorname{Yb}_{x}\operatorname{Ge}_{10}$					
4(e)	Но	Sc	Sc	Sc _{0.22} Yb _{0.78}					
8(h)	Ho	Sc	Sc	$Sc_{0.29}Yb_{0.71}$					
16(n)	Ho	Sc	Sc	$Sc_{0.32}Yb_{0.68}$					
16(n)	Ho	Sc	Mn	Sc					
4(d)	Ge	Ge	Ge	Ge					
4(e)	Ge	Ge	Ge	Ge					
8(h)	Ge	Al	$Mn_{0.64}Ge_{0.36}$	Ge					
8(I)	Ge	Ge	Ge	Ge					
16(m)	Ge	Ge	Ge	Ge					

Table 7 Site occupancies in Ho₁₁Ge₁₀, Sc₁₁Al₂Ge₂, Sc₇Mn₄, Ge₁₀, (x = 1.3) and Sc₁₁, Yb, Ge₁₀  $(x \approx 5)$  (SG I4/mmm)

### 5.3. Analysis of some new structure types

The atoms in the Ho₄Ir₁₃Ge₉ structure are located in two planes with  $x = \frac{1}{4}$  and  $x = \frac{3}{4}$ . The metal atoms form trigonal prisms with their axes parallel to one another. The prisms centered by germanium atoms form two types of blocks: HoIr₆Ge₃ and Ho₃Ir₁₀Ge₆ which are mutually connected through empty trigonal prisms formed by iridium atoms. The blocks are shifted with respect to each other by a half translation along the shortest (*a*) axis (fig. 91). A survey of the literature of known structure types revealed that these blocks are typical for compounds such as YNi₅Si₃ (fig. 91, a) and Y₆Ni₂₀P₁₃ (fig. 91, b).

The unit cell dimensions of the Ce₂Pt₇Ge₄ structure correspond to the lattice parameters of the previous one. The atoms of cerium and platinum produce trigonal prisms in which the germanium atoms are located. Three trigonal prisms combine with each other owing to a common edge to give a typical "star". The fourth prism has a common edge with one of these prisms. This fragment corresponds to the composition Ce₂Pt₇Ge₄. The packing arrangement of the prisms in the Ce₂Pt₇Ge₄ structure are shown in fig. 92. The distance between two similarly oriented "star" fragments in terms of the lattice parameter *a* is 1/2a. The crystal structure of Ce₂Pt₇Ge₄ (I) is similar to that of the compound Nd₂Ni₇P₄ (II) (space group Pmn2₁) ( $a_{\rm I} \approx 2b_{\rm II}$ ,  $b_{\rm I} \approx a_{\rm II}$ ,  $c_{\rm I} \approx c_{\rm II}$ ) in which the packing of the same "stars" is observed.

In the ternary cross section of the Ce–Pt–Ge system the compound Ce₃Pt₄Ge₆ is located between CePt₂Ge₂ and CePtGe₂. Analysis of the crystal structures shows Ce₃Pt₄Ge₆ to be a combination of the two structures. The relationship between the CePt₂Ge₂, Ce₃Pt₄Ge₆ and CePtGe₂ structures is shown in fig. 93. The marked fragment in CePtGe₂ (structural type NdIrGe₂) has the composition Ce₂Pt₂Ge₄. The composition 2Ce₃Pt₄Ge₆ is the result of the following fragment packing:  $\frac{1}{2}$ Ce₂Pt₂Ge₄ + CePt₂Ge₂ + Ce₂Pt₂Ge₄ + CePt₂Ge₂ +  $\frac{1}{2}$ Ce₂Pt₂Ge₄.





Fig. 92. The interrelation between  $Ce_2Pt_7Ge_4$  and  $Nd_2Ni_7P_4$  structures.

Fig. 91. Blocks of atoms, typical for the structures related to the  $Ho_4Ir_{13}Ge_9$  type: (a)  $YNi_5Si_3$  and (b)  $Y_6Ni_{20}P_{13}$ .

The structural type Y₃Pt₄Ge₆ is monoclinically deformed Ce₃Pt₄Ge₆ with  $a \approx 2a$ ,  $b \approx b$  and  $c \approx \frac{1}{2}c$ . The structure of Y₃Pt₄Ge₆ is a stacking variant of the monoclinic structures LaPt₂Ge₂ and NdIrGe₂.

The  $Nd_4Rh_4Ge_3$  structure type can be described as a stacking of fragments typical for the YPd₂Si and La₃Ni₂Ga₂ structures (fig. 94). In turn, the La₃Ni₂Ga₂ structure consists of YAIGe and CrB fragments.

The structure types  $Ce_2(Ga_{0.9}Ge_{0.1})_7$  and  $La_2Al_{1+x}Ge_{6-x}$  are the vacancy variant of the orthorhombic SmNiGe₃ and can be considered as an intergrowth of AlB₂-, deformed Po- and partially vacant BaAl₄-type slabs.

The Yb₇Al₅Ge₈ structure type can be considered as an intergrowth of TiNiSi-, AlB₂and CsCl-type columns.

The new structure types  $CeRh_{1-x}Ge_{2+x}$  and  $Ce_2Cu_3Ge_3$  are formed as a result of an internal deformation of the CeNiSi₂ structure; the unit cell dimensions, however, remain unchanged. The  $TmLi_{1-x}Ge_2$  structure is a monoclinically deformed derivative of the CeNiSi₂ structure and it can be described as a result of an inclusion of Li atoms into the empty tetragonal prisms which are typical for the CaSb₂ structure.

The TmLi_{1-x}Ge₂, CeRh_{1-x}Ge_{2+x} and Ce₂Cu₃Ge₃ structures together with CeNiSi₂, TbFeSi₂ and U₃Ni₄Si₄ are the members of the homological series of compounds with the common formulae  $R_{m+0.5n}M_{2m}X_{2n}$  where *m* is the number of AlB₂ fragments and *n* is the number of BaAl₄ fragments. For TmLi_{1-x}Ge₂, *m*=1 and *n*=2; for the CeRh_{1-x}Ge_{2+x}, Ce₂Cu₃Ge₃, CeNiSi₂ and TbFeSi₂ structures *m*=2 and *n*=4; and for U₃Ni₄Si₄, *m*=*n*=4.



Fig. 93. The interrelation between  $CePt_2Ge_2$ ,  $Ce_3Pt_4Ge_6$  and  $CePtGe_2$  structures.



Fig. 94. The  $Nd_4Rh_4Ge_3$  as a stacking of (I)  $YPd_2Si$  and (II)  $La_3Ni_2Ga_2$  fragments.

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# Chapter 175

# SCANDIUM ALLOY SYSTEMS AND INTERMETALLICS

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## Contents

	List of symbols	341	3.1.10. Sc-Rh-B	385
1.	Introduction	342	3.1.11. Sc- $M$ -B (M = Os, Ir)	386
2.	Binary systems containing scandium	343	3.2. Sc-M-Al ternary systems	386
	2.1. Sc-M (M = 1A element) systems	345	3.2.1. Sc-Li-Al	386
	2.2. Sc-M ( $M = 2A$ element) systems	345	3.2.2. Sc-Mg-Al	386
	2.3. Sc-M (M=RE) systems	347	3.2.3. ScCa-Al	387
	2.4. Sc-M (M=actinide element) systems	349	3.2.4. ScSr-Al	387
	2.5. Sc-M (M=4A element) systems	351	3.2.5. Sc-Ba-Al	387
	2.6. Sc-M (M=5A, 6A element) systems	351	3.2.6. Sc-R-Al (R=La, Ce, Yb)	387
	2.7. Sc-M (M=Mn, Tc, Re) systems	353	3.2.7. Sc-R-A1 (R = Y, Sm, Gd, Tb,	
	2.8. Sc-M (M=Fe, Co, Ni) systems	354	Dy, Ho, Er, Tm, Lu)	388
	2.9. Sc-M (M=platinum group element)		3.2.8. Sc-M-Al (M=Ti, Zr, Hf)	390
	systems	357	3.2.9. Sc-Nb-Al	391
	2.10. Sc-M (M=1B element) systems	361	3.2.10. ScCr-Al	391
	2.11. Sc-M (M=2B element) systems	363	3.2.11. Sc-Mo-Al	391
	2.12. Sc–X (X=3B element) systems	365	3.2.12. Sc-Mn-Al	392
	2.13. Sc-X (X=4B element) systems	371	3.2.13. Sc-Fe-Al	392
	2.14. Sc-X (X=P, As, Sb, Bi) systems	376	3.2.14. ScCo-Al	393
	2.15. Sc-X (X=Se, Te, Po) systems	377	3.2.15. Sc-Ni-Al	393
3.	Ternary systems containing scandium	379	3.2.16. ScRuAl	393
	3.1. Sc-M-B ternary systems	379	3.2.17. Sc- $M$ -Al (M = Rh, Os, Ir, Pt)	394
	3.1.1. Sc-La-B	379	3.2.18. Sc-Pd-A1	394
	3.1.2. ScCrB	379	3.2.19. Sc-Cu-Al	395
	3.1.3. Sc-W-B	382	3.2.20. Sc- $M$ -Al (M = Ag, Au)	396
	3.1.4. Sc-Mn-B	382	3.3. Sc-M-Ga ternary systems	396
	3.1.5. Sc-Re-B	382	3.3.1. Sc-Y-Ga	396
	3.1.6. Sc-Fe-B	383	3.3.2. Sc-Ti-Ga	400
	3.1.7. ScСо-В	384	3.3.3. Sc-Zr-Ga	400
	3.1.8. Sc-Ni-B	384	3.3.4. Sc-Hf-Ga	401
	3.1.9. Sc-Ru-B	385	3.3.5. Sc-V-Ga	401

	3.3.6.	Sc–Nb–Ga	402
	3.3.7.	Sc–Cr–Ga	402
	3.3.8.	ScMnGa	402
	3.3.9.	Sc-Fe-Ga	404
	3.3.10.	Sc–Co–Ga	405
	3.3.11.	Sc–Ni–Ga	406
	3.3.12.	Sc-M-Ga (M=Ru, Rh, Pd,	
		Os, Ir, Pt)	407
	3.3.13.	Sc–Cu–Ga	407
3.4.	Sc-M-In	n ternary systems	408
	3.4.1.	Sc–Ni–In	408
	3.4.2.	Sc-Pd-In	408
	3.4.3.	Sc-Pt-In	409
	3.4.4.	Sc-M-In (M=Cu, Ag, Au)	409
3.5.	Sc-M-C	ternary systems	409
	3.5.1.	Sc-Th-C	409
	3.5.2.	Sc-Ti-C	410
	3.5.3.	Sc-M-C (M = Zr, Hf, V, Nb,	
		Ta)	410
	3.5.4.	Sc-Cr-C	410
	3.5.5.	Sc-Mo-C	411
	3.5.6.	$S_{c-M-C}$ (M = W. Re. Tc)	411
	3.5.7	Sc-Fe-C	412
	3.5.8.	Sc-Co-C	412
	3.5.9	Sc-Ni-C	414
	3.5.10	$S_{C-M-C}$ (M = Ru, Rh, Pd)	414
	3.5.11	Sc-Ir-C	415
3.6.	Sc-M-S	i ternary systems	416
2.0.	361	Sc-Y-Si	416
	362	Sc-La-Si	416
	363	Sc-Ce-Si	416
	364	Sc-Pr-Si	422
	365	Sc-Nd-Si	42.2
	366	Sc-Sm-Si	423
	367	Sc-Dy-Si	423
	3.6.8	Sc-Er-Si	423
	369	Sc-Lu-Si	424
	3610	Sc-Ti-Si Sc-7r-Si	425
	3611	Sc-Hf-Si	426
	3612	Sc-V-Si	426
	3613	Sc-Nb-Si	426
	3614	Sc-Ta-Si	428
	3615	Sc-Cr-Si	428
	3.6.16	Sc-Mo-Si	428
	3617	Sc_W_Si	428
	3618	Sc-Mn-Si	430
	3610	Sc_Re_Si	430
	3670	Sc-Fe-Si	431
	3621	Sc-Co-Si	432
	3677	Sc_Ni_Si	427
	3672	Sc-Ru-Si	433
	5.0.23.	00 IAU-01	-55

	3.6.24.	ScRhSi	433
	3.6.25.	Sc-Pd(Os, Ir, Pt)-Si	434
	3.6.26.	ScCuSi	434
	3.6.27.	ScAg-Si	436
	3.6.28.	Sc-Au-Si	436
3.7.	ScMG	e ternary systems	437
	3.7.1.	Sc-Li-Ge	437
	3.7.2.	ScY-Ge	437
	3.7.3.	ScLa–Ge	437
	3.7.4.	Sc-Ce-Ge	437
	3.7.5.	ScPr(Sm)-Ge	441
	3.7.6.	Sc-Nd-Ge	442
	3.7.7.	ScEuGe	442
	3.7.8.	ScDyGe	442
	3.7.9.	Sc-Yb-Ge	442
	3.7.10.	ScHfGe	444
	3.7.11.	Sc–V–Ge	444
	3.7,12.	ScNbGe	445
	3.7.13.	ScTaGe	445
	3.7.14.	ScCrGe	445
	3.7.15.	ScMoGe	446
	3.7.16.	ScW-Ge	447
	3.7.17.	ScMnGe	447
	3.7.18.	ScReGe	448
	3.7.19.	Sc–Fe–Ge	448
	3.7.20.	ScCoGe	448
	3.7.21.	Sc-Ni-Ge	450
	3.7.22.	ScRu(Rh, Pd, Os, Ir)Ge	450
	3.7.23.	Sc-Cu-Ge	451
	3.7.24.	Sc-Ag-Ge	451
3.8.	ScMS	n ternary systems	451
	3.8.1.	Sc-Li-Sn	451
	3.8.2.	Sc-Mn-Sn	453
	3.8.3.	ScFeSn	453
	3.8.4.	ScCoSn	453
	3.8.5.	Sc-Ni-Sn	453
	3.8.6.	Sc-Ru(Rh, Pd, Os, Ir, Pt)-Sn	453
	3.8.7.	ScCuSn	454
	3.8.8.	Sc–Au–Sn	454
3.9.	Sc-M-P	(As, Sb, Bi) ternary systems	454
	3.9.1.	Sc-Gd-P	454
	3.9.2.	Sc-Mn(Fe, Co)-P	454
	3.9.3.	Sc-Ru-P	455
	3.9.4.	Sc–Ni–As	455
	3.9.5.	Sc-Ni(Pt, Au)-Sb	455
	3.9.6.	Sc-Ni(Pd)-Bi	456
3.10.	ScMS	e ternary systems	456
	3.10.1.	Sc-Mg(Eu, Mn, Cu, Ag, Cd)-	
		Se	456
3.11.	Sc-X-X	' ternary systems	456
	3.11.1.	Sc-Ga-Al	456

3.11.2. Sc-C-B(Al)	457	4.13. Sc-Re-Ni-Si	468
3.11.3. Sc-In(Tl, Sn, Pb)-B	457	4.14. ScCaPtP	468
3.11.4. Sc-In(Tl, Sn, Pb)-C	457	4.15. Sc-Y-Ti-Co	468
3.11.5. Sc–Si–C	458	5. Generalisation of the data on scandium metal	
3.11.6. Sc-Al-Si	458	systems and intermetallics	468
3.11.7. Sc-Ge-Si	458	5.1. Regularities found in binary scandium	
3.11.8. Sc-Al-Ge	459	phase diagrams	469
3.11.9. Sc-As-P	459	5.2. Regularities found in ternary scandium	
3.11.10. Sc-Te-Se	459	phase diagrams	473
3.12. Sc-M-M' ternary systems	460	5.3. Atomic size factor and its influence on	
3.12.1. Sc-Mg-Mn	460	the nature of scandium intermetallics	479
3.12.2. Sc-Y-Gd	460	5.4. Relations between compositions	
3.12.3. Sc-Tb-Mn	460	and crystal structures of scandium	
3.12.4. Sc-Y-Fe	460	intermetallics	482
3.12.5. Sc-Ce-Fe	460	6. Physical properties of scandium based	
3.12.6. Sc-U-Pd	460	intermetallics	492
3.12.7. Sc-Ti-Fe	462	6.1. Compounds with non-magnetic and	
3.12.8. Sc-Ti-Ni	462	non-superconducting ground state	494
3.12.9. Sc-Ti-Pt	462	6.1.1. RAuGe ( $R=Sc$ , Y and Lu)	494
3.12.10. Sc-Hf-Ir	462	6.1.2. Crystal field parameters of	
3.12.11. Sc-V-Nb	462	lanthanides diluted in ScAl ₂ ,	
3.12.12. Sc-Cr-Ni	463	$YAl_2$ and $LuAl_2$	496
3.12.13. Sc-Mn-Fe	463	6.1.3. Spin fluctuations in $RCo_2$	
3.12.14. Sc-Re-Ni	463	compounds $(R = Sc, Y, Lu)$	497
3.12.15. Sc-Ru-Rh	463	6.2. Compounds with magnetic ground state	501
3.12.16. Sc-Ni-Au	463	6.2.1. $Sc_3In$	501
3.12.17. ScCuZn	464	6.2.2. $ScFe_2$ and related compounds	503
4. Multicomponent systems containing		6.2.2.1. $Sc(M_{1-x}Si_x)_2$	
scandium	464	(M = Fe, Co, Ni)	505
4.1. Sc-Mg-Mn-Li(Ca, Y, Ce, Nd, Zr,		6.2.2.2. $(Sc_{1-x}Ti_x)Fe_2$	507
Ni, Cd, Zn, Al, In, Si, Ge, Sn)	464	6.2.3. Sc substitution in $YMn_2$	508
4.2. Sc–Ca–Rh–B	464	6.3. Compounds with superconducting	
4.3. Sc-Ce(Pr, Nd, Sm, Gd, Tb, Dy, Ho,		ground state	509
Er, Tm)–Rh–B	464	6.3.1. $Sc_{1-x}M_x$ alloys (M=Co, Rh,	
4.4. Sc-Y(Nd, Dy, Er, Lu)-Fe-B	465	Ir, Pd, Pt)	509
4.5. Sc–Lu–Ru–B	466	6.3.2. $Sc_5M_4Si_{10}$ (M=Co, Rh, Ir)	
4.6. $Sc-U-Pd-B$	466	and $R_2Fe_3Si_5$ (R = Sc, Y, Lu)	510
4.7. Sc–Th–Rh–B	466	6.3.3. $RRu_4B_4$	512
4.8. Sc-Y(Lu)-Ir-Si	466	6.3.4. $ScNi_2B_2C$	513
4.9. Sc-Dy-Ir-Si	466	Acknowledgement	513
4.10. Sc-Ni-C-B, Sc-Lu-Ni-C-B	467	Appendix 1. Structure types of intermetallic	
4.11. Sc-Y-Ge-Si	467	compounds of scandium	513
4.12. Sc-Rh-Os-Si	467	References	521

# List of symbols

A	Coefficient of resistivity ( $\rho_{mag} = AT^2$ )	bec	Body centered cubic
$A_4, A_6$	Crystal field parameters	С	Curie constant
a, b, c	Lattice parameters	с	Total heat capacity
В	Magnetic induction	CF	Crystal field

CN	Coordination number	$W_{\rm e.0}$	Residual thermal resistivity
CP	Coordination polyhedron	$W_{e.ph}$	Thermal resistivity due to phonon
C _m	Magnetic heat capacity	•	scattering
$\Delta c$	Difference in the heat capacity at $T_s$	$W_{\rm e.sf}$	Thermal resistivity due to spin
cub	Cubic symmetry		fluctuation scattering
dhcp	Double hexagonal close packed	x, W	Crystal field parameters of cubic
DOS	Density of states		systems
Ε	Eutectic transition	Χ, Χ΄	p-element
Ed	Eutectoid transition	α	Thermal expansion coefficient
fcc	Face centered cubic	$\alpha, \beta, \gamma$	Lattice parameters
hcp	Hexagonal close packed	$\alpha_{n}, \beta_{n}, \gamma_{n}$	Specific heat coefficients in the normal
hex	Hexagonal symmetry		state
HT	High temperature	$\alpha_{\rm s}, \beta_{\rm s}, \gamma_{\rm s}$	Specific heat coefficients in
iL	Immiscibility gap in liquid	0	superconducting state
L	Congruently melting compound; liquid	β	Lattice specific heat coefficient
LT	Low temperature	χ	Magnetic susceptibility
М	Magnetization	$\chi_0$	Temperature independent magnetic susceptibility
M, M′	Metallic element (s-, d-, f-element)	v	Electronic specific heat coefficient
Mt	Metatectic transition	r F	Fermi energy
$N(\varepsilon_{\rm F})$	Density of states at the Fermi level	2 _F	Total thermal conductivity
orthorh	Orthorhombic symmetry	2	Lattice thermal conductivity
Р	Peritectic transition	2	Electronic thermal conductivity
Pd	Peritectoid transition	λ _e	Pohr magnaton
$p_{\rm S}$	Saturation moment	$\mu_{\rm B}$	Bohr magneton per Ee stem
S	Polymorphic transition	$\mu_{\text{Fe}}$	Effective magnetic memory
$S, S_{tot}$	Total thermopower	$\mu_{\rm eff}$	Effective magnetic moment
$S_{\rm diff}$	Diffusion thermopower	$ ho, ho_{ m ges}$	Pari had alertrical resistivity
$S_{drag}$	Thermopower due to drag effects	$ ho_0$	Residual electrical resistivity
SG	Space group	$ ho_{ m sf}$	Electrical resistivity due to spin
ST	Structure type		Electrical registivity due to magnetic
s,p,d,f	Band index	$ ho_{ m mag}$	scattering
tetr	Tetragonal symmetry	0.	Electrical resistivity due to phonon
$T_{\rm sf}$	Spin fluctuation temperature	Pph	scattering
T _c	Curie temperature	$\Delta \rho / \rho$	Magnetoresistance
$T_{\rm N}$	Néel temperature	~	Precedes the composition formula of a
rs	Superconducting transition temperature		compound to indicate that the
W	Total thermal resistivity		composition is given tentatively

## 1. Introduction

The last comprehensive treatment of scandium as an element and of its alloys and compounds was given in the book *Scandium*. Its occurrence, chemistry, physics, metallurgy, biology and technology in 1975 (Gschneidner 1975). Meanwhile numerous

342

structural investigations have been published in the literature mainly concerning structural properties. It seems that the time is ready to summarise the new results with the aim to give an overview over the last most significant and relevant results. Since one of us (B.K.) has been working for more than twenty years in the field of structural and chemical investigations of scandium-based alloys and compounds, it is obvious that problems such as phase stability and the phase diagrams represent the main part of the chapter. Many investigations of ternary scandium-based phase diagrams have been investigated and published since 1975. However, there are also numerous new investigations of binary compounds and their phase diagrams are now known, and these are included in this chapter. The aim is to give an overview of the newly published data up to the beginning of 1997. In sections 2 and 3 the binary and ternary scandium containing systems are treated, whereas sect. 4 is dedicated to multicomponent systems.

At the beginning of each section an explanation is given of how the information is subdivided in the subsequent text. Each phase diagram is accompanied by a brief statement about what seems to be necessary for understanding the phase relationships and where the data have been published. Also included are the crystal structure data of binary, ternary and multinary phases as far as they are given in the literature.

Since in some cases the published data are controversial, we have tried to make objective and critical comments to the best of our abilities.

Section 5 presents general trends among the binary and ternary Sc-based intermetallics, since this information may be interesting for the syntheses of new Sc compounds for both basic research as well as for technical applications.

In the last section the physical properties of several selected intermetallic compounds containing scandium are discussed and some of their physical properties are depicted in diagrams. In most of the cases the physical properties of the Sc-containing compounds and those of the isostructural Y, La or Lu compounds are compared.

## 2. Binary systems containing scandium

The phase diagrams of the Sc–E (E=element) binary systems have been investigated in the entire or partial concentration region for majority of elements. These data are presented in summarised form in table 1. The data have been obtained primarily from the original papers, supplemented by data from the 2nd edition of *Binary Alloy Phase Diagrams* by Massalski (1990) and from the 2nd edition of *Pearson's Handbook of Crystallographic Data for Intermetallic Phases* by Villars and Calvert (1991).

There are no data for about 24 Sc–E binary systems out of 89 possible. Among them there are 10 systems with the transuranium elements with atomic numbers higher than 95. The phase diagrams of 54 Sc–E binary systems have been investigated for the entire or partial concentration region up to the beginning of 1997. The figures of the phase diagrams of binary systems presented and discussed by Gschneidner (1975) are not shown in this section if no additional controversial literature data appeared in the meantime. In these cases a brief summary and references are given. 23 binary phase diagrams have been

	1A	2A	3A	4A	5A	6A	7A		8A		1B	2B	3B	4B	5B	6B
2	Li	Be 3											B ∎2 ➡	C ∎3 +		
3	Na	Mg ⊠ 1		-									A1 ∎4	Si 3	Р 4	
4	ĸ	$\overline{Ca}$ $\blacksquare 0$ iL	Sc	Ti ∎0 ∞	$\mathbf{V}$ $\mathbf{I}_0$ E	Cr = 0	Mn □1 -•	Fe ∎3	Co ∎4	Ni ∎5	Cu ∎3	Zn ⊠5	Ga ∎8	Ge ∎5	As 4	Se 2
5	Rb	$\frac{\mathrm{Sr}}{\mathrm{IL}}$	Y ∎0	Zr ∎0 ∞	$\mathbb{N}^{N}_{\mathbb{D}}$		Tc 5	Ru ∎4	Rh ∎5	Pd ∎5	Ag ∎3	Cd ⊠3	In ∎6	Sn Ø4	Sb 3	Te 2
6	Ċs	Ba ∎0 <i>iL</i>	La ∎0 ∞	Hf ∎0 ∞	$Ta \\ \Box 0 \\ E$	$\mathbf{W} = 0 \\ E$	Re ∎2	Os 3	Ir ∎7	Pt Ø4	Au ∐4	Hg 2	T1 ∎ 7	Pb Ø2	Bi 1	Po 1
7	Fr	Ra	Ac	Ku	Ns											

Table 1 Summary of information known about the Sc–E binary phase diagrams^a

6	Ce ∎0 ∞	Pr	Nd ∎0 ∞	Pm	Sm □0	Eu ∏0 iL	Gd ∎0 ∞	Tb □0 ∞	Dy □0 ∞	Ho □0 ∞	Er ∎0 ∞	Tm	Yb □0 <i>iL</i>	Lu □0 ∞
7	Th ∎0 ∞	Pa	U ∎0 iL	Np	Pu ∎ 1 ∞	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr

^a The squares indicate the concentration range in which the phase diagram of the Sc-E binary system was investigated: black square, 75–100%; grey square, 25–75%; open square, less than 25%; no square, not investigated.

The number of binary compounds found is listed next to the square.

The character of the mutual solubility of Sc and E is indicated as follows:

iL, miscibility gap in the liquid state;

E, mutual solubility in the solid state <1 at.% (simple eutectic, no binary compound occurs);

 $\rightarrow$  , solubility of Sc in solid E >1 at.%;

 $\leftarrow$  , solubility of E in solid Sc >1 at.%;

 $\infty$ , at least one continuous solid solution of Sc and E occurs.

published after Gschneidner's review article in 1975. These diagrams will be discussed in more detail. All controversial data about the systems will be analysed and discussed. In some cases necessary corrections are made and the revised phase diagrams are presented, whereas in other cases diverging results in the literature are only mentioned. The data in the section are arranged according to the stretched form of the periodic table of elements. Within one group of elements the systems are given according to increasing atomic number of the elements. The data about all scandium binary intermetallics including their composition, melting temperature (in °C) and crystallographic data (structure type (ST) or symmetry and lattice parameters) are presented. The reference source of the crystallographic data is presented first followed by the references in which these data appeared. The reference source with data of the melting temperature of compound is printed in italics. The following abbreviations are used for compounds' formation and decomposition:

L, congruently melting compound;

P, peritectically melting compound;

Pd, compound is formed according to peritectoid reaction;

S, polymorphic transition;

Ed, compound decomposes according to eutectoid reaction;

Mt, metatectic transition.

2.1. Sc-M (M = 1A element) systems

There are no data about the interaction of scandium with the alkaline metals. Taking into consideration the large differences in the melting temperatures of Sc and 1A elements the occurrence of immiscibility gaps in liquid and solid binary alloys are possible as they occur in the Sc–E (E = alkaline-earth element) alloys (see sect. 2.2). The absence of binary compounds in these systems is very likely.

2.2. Sc-M (M = 2A element) systems

Occurrence of three scandium-beryllium intermetallic compounds and their crystal structures are the only data existing about the Sc–Be binary system. Their characteristics are presented in table 2. Gschneidner and Calderwood (1987) reviewed all available papers on scandium-beryllium binary alloys.

Beaudry and Daane (1969) established the Sc-Mg phase diagram in the range of 0– 60 at.% Sc.  $\beta$ Sc dissolves up to 80 at.% Mg and magnesium dissolves up to 15 at.% Sc. The latter data was refined by Sviderskaya and Nikitina (1972), who established the

Table 2Intermetallic compounds in the Sc-M (M=Be, Mg) binary systems a											
Compound	Melting	Structure type	Lattice p	arameters	Reference						
	temperature (°C)	or symmetry	a (Å)	c (Å)	-						
ScBe ₁₃	?	NaZn ₁₃	10.102		Laube and Nowotny (1962)						
$Sc_2Be_{17}$	?	hex	7.6I	7.50	Gladyshevsky et al. (1964)						
$ScBe_5$	?	CaCu ₅	4.55	3.50	Protasov and Gladyshevsky (1964)						
ScMg(\beta')	Pd, 520	CsCl	3.597		Schob and Parthé (1965), Beaudry and Daane (1969)						

^a References in italics contain data about a compound's melting temperature.



temperature dependence of the solubility of Sc in Mg. One binary compound ScMg with a broad homogeneity range, isotypic with CsCl, occurs in the system (table 2). Reviews of the papers on Sc–Mg alloys have been given by Gschneidner (1975) and by Nayeb-Hashemi and Clark (1986). The latter authors presented the assessed phase diagram of the system with only few small corrections of the earlier data of Beaudry and Daane (1969). New data concerning the phase diagram are not known.

Dzuraev and Altynbaev (1986) determined the solubility of Sc in  $\beta$ Ca,  $\beta$ Sr and Ca and Sr in  $\beta$ Sc and  $\alpha$ Sc as well as the temperatures of the monotectic and eutectic reactions



in the Sc-Ca and Sc-Sr systems. The Sc-Ca and Sc-Sr phase diagrams constructed on the base of these data are presented in figs. 1 and 2, respectively.

The phase diagram of Sc–Ba system has been reported by Altynbaev et al. (1988). The allotropic transition  $\beta$ Sc  $\leftrightarrow \alpha$ Sc, which was not shown by these authors, has been added to the phase diagram presented in fig. 3. The melting temperature for Sc has been corrected for the now accepted value.

The interaction of scandium with the earth alkaline elements is similar. An immiscibility gap occurs in the liquid alloys and no binary compound exists in any of these systems.

## 2.3. Sc-M (M = RE) systems

The majority of the data concerning binary Sc-RE systems have been obtained between 1960 and 1970. Since that time practically no new information has been published on the Sc-RE phase diagrams.

The Sc–Y phase diagram was investigated by Beaudry and Daane (1963). The HT and LT modifications of scandium and yttrium are completely miscible in each other. The list of references concerning this system and the phase diagram with the corrected temperatures of phase transitions can be found in the reviews of Gschneidner (1975) and Gschneidner and Calderwood (1983e, 1986a).

Naumkin et al. (1970) investigated the Sc–La phase diagram.  $\gamma$ La and  $\beta$ Sc form continuous series of solid solutions, while  $\beta$ La,  $\alpha$ La and  $\alpha$ Sc dissolve from 12 to 16 at.% of the second component. The phase diagram and the reference list are given by Gschneidner (1975) and Gschneidner and Calderwood (1982a, 1986a).

The Sc–Ce phase diagram has been determined by Naumkin et al. (1964). Gschneidner (1975) and Gschneidner and Calderwood (1982b, 1986a) corrected only the values of the melting and allotropic transition temperatures of the pure components to conform with the accepted values. The bcc phases of Sc and Ce are completely miscible in each other. The LT modifications of Sc and Ce dissolve about 12 and about 17 at.% of Ce and Sc, respectively.

There are no available data about the phase diagram of the Sc–Pr system. Taking into consideration the data on the Sc–Ce system it is possible to predict a complete mutual miscibility of the components in each other in liquid and in bcc solid phases.  $\alpha$ Sc and  $\alpha$ Pr have different crystal structures (hcp and dhcp respectively), therefore, they probably form limited solid solutions.

Beaudry et al. (1965) investigated the Sc–Nd phase diagram. Pairs of HT and LT phases of these components are completely miscible in each other. The attempts of the authors to find two phase region between the hcp phase of Sc and double hcp phase of Nd failed. This continuous solid solution decomposes beginning at 700°C by forming an immiscibility gap. The phase diagram has been analysed earlier by Gschneidner (1975) and Gschneidner and Calderwood (1982c, 1986a).

There are no data known about investigations of Sc-Pm system.

The only data about interaction between Sc and Sm are those published by Kotur et al. (1991). It was found that at 600°C samarium dissolves about 18 at.% Sc. From a comparison of the phase diagrams of other light RE (La, Ce and Nd) it is possible to predict a complete miscibility of the components in each other in the liquid and solid bcc phases.

Massalski (1990) presented the hypothetical Sc–Eu phase diagram based on thermodynamic calculations of Miedema (1976). They predict the occurrence of a broad immiscibility gap in liquid and solid alloys and the absence of binary compounds in this system.

The phase diagram of Sc–Gd system has been established by Beaudry and Daane (1964). The figure of the phase diagram is also presented in the reviews of Gschneidner (1975) and Gschneidner and Calderwood (1983c, 1986a) who corrected only the values of melting and the bcc  $\leftrightarrow$  hcp transitions temperatures of the components with their new values. One liquid and two solid continuous solutions exist in this system.

The lattice parameters of several Sc–Tb alloys have been measured indicating a complete solubility of  $\alpha$ Tb and  $\alpha$ Sc. These data were reviewed and analysed by Gschneidner (1975) and Gschneidner and Calderwood (1983d, 1986a).

The phase diagram of the Sc–Dy binary system has not been investigated. Kotur et al. (1991) reported about a complete solubility of the components at 600°C. The a and c lattice spacing of the hcp solid solution appear to follow Vegard's rule within the experimental error.

Considering the above presented data it is possible to predict the existence of one liquid and two solid rows of continuous solutions in the Sc–Tb and Sc–Dy systems like in the Sc–Gd system. The occurrence of two of these solid solutions ( $\alpha$ Sc,  $\alpha$ Tb) and ( $\alpha$ Sc,  $\alpha$ Dy) has been already confirmed experimentally. Cavin et al. (1967) reported the lattice spacings of five binary Sc-Ho alloys. Their data were also presented and analysed by Gschneidner (1975) and Gschneidner and Calderwood (1983b, 1986a).  $\beta$ Sc forms a continuous series of solid solutions with holmium.

The Sc–Er phase diagram has been investigated by Naumkin et al. (1964). Gschneidner (1975) and Gschneidner and Calderwood (1983a, 1986a) critically revised and corrected the values of temperatures of all phase transitions presented in the original paper. Er and  $\alpha$ Sc are completely soluble in each other.  $\beta$ Sc dissolves about 24 at.% Er.

There are no known data about the Sc-Tm system in the literature.

Since Ho, Er and Tm have only one solid phase (hcp); it appears that these three binary systems will have similar phase diagrams, i.e. occurrence of one liquid and one solid continuous solutions and a limited solubility in bcc Sc phase. One of such solutions, namely ( $\alpha$ Sc, Ho), has already been determined experimentally.

The hypothetical Sc–Yb phase diagram has been constructed by Massalski (1990) on the basis of thermodynamic calculations of de Boer et al. (1979). Immiscibility gaps in liquid and solid alloys and the absence of binary compounds are predicted for that system. This is in agreement with the data of Kotur (1995) who prepared several binary alloys and observed immiscibility of liquid components and two separate layers in solid alloys.

Kotur and Mokra (1994) reported the complete solubility of scandium and lutetium at 800°C. These are the only available experimental data about the Sc–Lu system. It is possible to predict the complete miscibility of the components in the liquid and a limited solubility of lutetium in  $\beta$ Sc.

## 2.4. Sc-M (M = actinide element) systems

Among the family of the actinide elements data concerning binary systems with scandium only exists for the three elements thorium, uranium and plutonium.

Terekhov and Sinyakova (1990) reported on the Sc–Th phase diagram (fig. 4). Their results are an improvement on the data of Badaeva and Kuznetsova (1969) who were the first to investigate the phase diagram on the basis of thermal analysis of 8 alloys. A continuous series of solid solutions occur between the HT phases of the components.  $\alpha$ Th dissolves up to 66 at.% Sc and  $\alpha$ Sc dissolves up to 20 at.% Th. With decreasing temperature the mutual solubility of the components also decreases. The authors presented a plot of lattice spacing *a* vs. Sc content of the fcc Th_{1-x}Sc_x solid solution at 950°C. As estimated from the plot *a*=5.095 Å for pure  $\alpha$ Th; *a* does not change out to about 7–8 at.% Sc content. In the concentration range 0.08 < *x* ≤ 0.61, *a* follows Vegard's rule with *a*=4.937 Å at *x*=0.61. There is a considerable discrepancy between the values of the melting point of Sc (1530°C) and the  $\alpha$ Sc  $\leftrightarrow \beta$ Sc transition temperature (1415°C) as obtained by Terekhov and Sinyakova (1990) and the now accepted values. For that reason we present in fig. 4 the corrected values for the temperatures of the phase transitions of the pure components.

Figure 5 displays the Sc–U phase diagram established by Terekhov and Sinyakova (1992). No binary compounds and an immiscibility gap in the liquid alloys occur in



the system. Okamoto (1993) indicated the necessity of further confirmation of the  $(\beta Sc)/(\beta Sc) + (\alpha Sc)$  boundary since it is too steep and does not follow the van't Hoff relation.

The Sc–Pu phase diagram has been investigated by Kutaitsev et al. (1967), Ellinger et al. (1968, 1972) and Ballagny et al. (1970). These and other papers concerning this system have been analysed in the review of Gschneidner (1975). The diagrams reported by Ellinger et al. (1968, 1972) and Ballagny et al. (1970) are very similar and are the accepted version. HT bcc phases of the components ( $\beta$ Sc,  $\epsilon$ Pu) are completely miscible in each other. The other phases of Sc ( $\beta$ ) and Pu ( $\delta$ ,  $\delta'$ ,  $\gamma$ ,  $\beta$ ,  $\alpha$ ) form limited solid solutions. One
The intermetallic compound in the Sc-Pu binary system								
Compound	Melting	Structure type	Lattice p	arameters	Reference			
	temperature (°C)	or symmetry	a (Å)	c (Å)	-			
~Sc ₂ Pu ₃	Pd, 753	αLa	3.308– 3.310 °	10.709– 10.717	Ellinger et al. (1968)	-		

Table 3

^a The first and second values of lattice spacings are for the Sc-rich and Pu-rich side of the homogeneity range, respectively.

binary compound of the approximate composition  $Sc_2Pu_3$  occurs in the system (table 3). Different authors, however, give different values for the homogeneity limits of Sc₂Pu₃, and additional investigations are necessary. Massalski (1990) indicated that the diagram cannot be modelled with a reasonable set of thermodynamic functions and therefore some phase boundaries need further refinement.

### 2.5. Sc-M (M = 4A element) systems

Two variants of the Sc-Ti phase diagram have been reported by Savitskii and Burkhanov (1961) and Beaudry and Daane (1962). Gschneidner (1975) and Murray (1987) analysed them and showed that the Beaudry and Daane one is probably more correct. In these reviews one can find the figure of the phase diagram and the list of references concerning the properties of the Sc-Ti allovs. There are no binary compounds in the system. The bcc HT phases of these components form a continuous series of solid solutions. The hcp LT phases of Sc and Ti dissolve up to 6.9 and 12.8 at.% of the other component, respectively.

Beaudry and Daane (1963) investigated the phase diagram of the Sc-Zr system. The two solid phases of the components are completely miscible in each other. The components also form a continuous liquid solution. These data and the data of other publications on Sc-Zr alloys are presented and reviewed by Gschneidner (1975) and Palenzona and Cirafici (1993).

The Sc-Hf phase diagram is similar to that of Sc-Zr. It was established by Naumkin et al. (1967). Gschneidner (1975) presented the figure of the phase diagram. He corrected only the values of phase transition temperatures of the pure components to the now accepted values. In the review one can find also the list of references concerning the physical properties of Sc-Hf alloys.

## 2.6. Sc-M (M = 5A, 6A element) systems

The character of interaction of scandium with 5A elements, vanadium, niobium and tantalum and the 6A elements, chromium, molybdenum and tungsten is similar. No binary compounds occur in any of these systems. The components are completely miscible in each other in the liquid state and form simple eutectics.

Savitskii et al. (1970, 1971a) reported on the Sc–V phase diagram. The figure of the phase diagram is also presented in the review of Gschneidner (1975) who corrected the temperatures of phase transitions of pure components to the now accepted values.  $\beta$ Sc and  $\alpha$ Sc dissolve <2 and <0.5 at.% V, respectively. The solubility of Sc in V is <2 at.%. Smith and Lee (1989) noticed an inconsistency of the original phase diagram with van't Hoff's thermodynamic functions. They presented the calculated phase diagram and predicted the occurrence of an immiscibility gap in liquid state in the temperature range from 1593°C to 1459°C and a monotectic reaction occurring at 1459°C. The validity of this theoretical phase diagram needs to be experimentally examined.

The phase diagram of the Sc–Nb system has been reported by Savitskii et al. (1970) and Savitskii and Efimov (1972). The figure of the phase diagram is also presented by Gschneidner (1975). The mutual solubility of the components is as follows: <0.4 at.% Nb in  $\beta$ Sc, <0.3 at.% Nb in  $\alpha$ Sc, and <0.1 at.% Sc in Nb.

Dennison et al. (1966a) established part of the Sc–Ta phase diagram in the high Sc concentration range (0 to 6 at.% Ta). The solubility of Ta in liquid Sc is very low (about 0.2 to 0.5 at.%) but was not determined accurately. According to the data of Taylor et al. (1965) solid Ta dissolves <0.0001 at.% Sc at  $1625^{\circ}$ C.

Two variants of the Sc–Cr phase diagram have been reported, by Savitskii et al. (1970) and Svechnikov et al. (1972). As was stated by Gschneidner (1975), who preferred the data of Savitskii et al. (1970), the major difference between the two diagrams is that Savitskii et al. found that chromium has insignificant effect on the  $\beta$ Sc  $\leftrightarrow \alpha$ Sc transformation, while Svechnikov et al. (1972) established the transformation to be lowered from 1340 to 990°C by means of an eutectoid reaction. Contrary to Gschneidner (1975), Venkatraman and Neumann (1985) preferred the diagram of Svechnikov et al. and presented the phase diagram based on these data correcting only the phase transition temperatures of the components. Thus, additional experimental investigation of the system is necessary to clarify the situation. Taylor et al. (1965) determined the solubility of Sc in solid Cr to be <0.1 at.%. The value of solubility of Cr in solid Sc is <1 at.% according to the data of Svechnikov et al. and needs, perhaps, to be refined too.

Brewer and Lamoreaux (1980) reported on the calculated Sc–Mo phase diagram based on the assumed thermodynamic functions. They predicted an eutectic  $L \leftrightarrow \beta$ Sc+Mo reaction at 1370±50°C and an eutectoid  $\beta$ Sc  $\leftrightarrow \alpha$ Sc+Mo reaction at ~1337°C in this system. The mutual solubility of the components in the solid phases is very low according to their calculation. These data have been partially confirmed by Kotur and Bodak (1988) who investigated several Sc–Mo alloys at 800°C and observed the immiscibility of the components and no binary compounds.

The solubility of tungsten in liquid scandium in the temperature range 1647–2045°C has been determined by Dennison et al. (1966b). They established it to be 2.4–7.9 at.%. The extrapolation of these data towards the melting temperature of Sc, 1541°C, revealed a 1.3 at.% solubility of W. Taylor et al. (1965) determined the solubility of scandium in

solid tungsten as <0.004 at.% at 1625°C. Pandian et al. (1988) used these data to evaluate the hypothetical Sc-W phase diagram. They assumed a temperature of 1510°C for the eutectic reaction  $L \leftrightarrow \beta Sc + W$ . The immiscibility of the components in the solid state and absence of binary compounds at 800°C have been confirmed by Kotur et al. (1989a).

## 2.7. Sc-M (M = Mn, Tc, Re) systems

The Mn-rich part of the Sc-Mn phase diagram in the range 0-5 at.% Sc has been established by Hellawell (1962). This phase diagram is shown in the review of Gschneidner (1975). The limit of solubility of scandium in  $\beta$ Mn and  $\delta$ Mn is about 1 at.%, in yMn it is only 0.4 at.%. Dwight (1961a) reported the existence of one binary compound in the system, namely ScMn₂ (table 4). His data were confirmed by Kripyakevich et al. (1964). From that time no new data concerning the phase diagram appeared in the literature.

The Sc-Tc phase diagram is still unknown. Darby et al. (1962) synthesised five binary compounds and determined the crystal structure of two of them (table 4). ScTc7 was observed in the cast alloy and  $ScTc_2$  in an alloy annealed at 700°C. Gschneidner (1975) doubted the composition of the ScTc₇ phase. His reason is that binary compounds isotypic with  $\alpha$ Mn have in general the 5:24 stoichiometry, i.e. the true composition of the phase must be Sc5Tc24. This statement needs experimental verification. During the last two decades no new data concerning Sc-Tc phase diagram appeared in the literature.

Savitskii et al. (1966) reported on the Sc-Re phase diagram. It follows from the figure in their paper that the liquidus curve in the phase diagram and the boundaries of some phase fields need additional refinement. Two binary compounds occur in this system (table 4).  $\beta$ Sc dissolves <1 at.% Re, and the solubility of scandium in solid rhenium does not exceed ~5-6 at.%. Gschneidner (1975) presented the data of Savitskii et al., however he corrected in the figure of the phase diagram the temperatures of some phase transitions with the accepted values.

	Intermetallic	Intermetallic compounds in the Sc-M (M=Mn, Tc, Re) binary systems								
Compound	Melting	Structure type or symmetry	Lattice pa	arameters	Reference					
	temperature (°C)		a (Å)	c (Å)	-					
ScMn ₂	?	MgZn ₂	5.033	8.278	Dwight (1961a)					
ScTc ₇	?	αMn	9.509		Darby et al. (1962)					
~ScTc ₃	?	?			Darby et al. (1962)					
ScTc ₂	?	MgZn ₂	5.223	8.571	Darby et al. (1962)					
~Sc ₃ Tc ₂	?	?			Darby et al. (1962)					
~Sc ₄ Tc	?	?			Darby et al. (1962)					
$Sc_5Re_{24}$	P, 2570	αMn	9.6448		Savitskii et al. (1966)					
ScRe ₂	P, 2030	MgZn ₂	5.270	8.590	Savitskii et al. (1966)					

Table /



## 2.8. Sc-M (M = Fe, Co, Ni) systems

Naumkin et al. (1969) reported on the Sc-Fe phase diagram. They established the occurrence of two binary compounds ScFe₂ (*L*, 1600°C) and Sc₃Fe (*Pd*, 800°C) but did not investigate their crystal structures. The existence of ScFe₂ is consistent with the earlier data of Dwight (1961a) and Gladyshevsky et al. (1964). Dwight synthesised the ScFe₂ compound and established it to be isotypic with MgNi₂,SG *P*6₃/*mmc*, with the lattice spacings a=4.972, c=16.278 Å. Gladyshevsky et al. obtained an ScFe₂ sample which was isotypic with MgZn₂, SG *P*6₃/*mmc*, with the lattice spacings a=4.92, c=7.90 Å, and in cast alloys with the content of iron less than 50 at.% they observed the occurrence of the cubic MgCu₂-type structure, SG *Fd*3*m*, with the lattice spacing a=7.09 Å.

Taking these data into consideration Bodak et al. (1978) reinvestigated the Sc–Fe phase diagram in the concentration range 0–90 at.% Sc. They confirmed the polymorphism of ScFe₂ (HT phase of MgNi₂ type [given as  $\lambda_3$  in fig. 6] and LT phase of MgZn₂ type [ $\lambda_1$ ]) and discovered a new binary phase ScFe_{1.74} ( $\lambda_2$ ) with the MgCu₂ type structure. Their lattice spacings are given in table 5. The stoichiometry of the scandium richest binary phase was shown to be about 7:1, not in agreement with the 3:1 stoichiometry found by Naumkin et al. Consequently Kotur et al. (1986a) established the structure and the composition of that phase being Sc₂₉Fe₆ in their single-crystal investigation (table 5).

Kubashewski (1982) presented a revised phase diagram of this system. The only changes which were introduced to the phase diagram of Naumkin et al. were a schematical indication of three polymorphic modifications for ScFe₂.

The revised phase diagram is shown in fig. 6. The temperatures of the majority of phase transitions are the data of Naumkin et al. since they investigated a larger number of samples, 39 vs. 24 by Bodak et al. The compositions of binary phases, temperatures of phase transitions of the ScFe_{1.74} and ScFe₂ compounds are the data taken from Bodak

	mermeane									
Compound	Melting	Structure type	Latti	ce paran	neters	Reference				
_	temperature (°C)	or symmetry	a (Å)	b (Å)	c (Å)					
$ScFe_2(\lambda_3)$	<i>L</i> , ~1600– <i>S</i> , >1200	MgNi ₂	4.974		16.29	Bodak et al. (1978)				
$ScFe_2(\lambda_1)$	<i>S</i> , >1200	MgZn ₂	4.977		8.146	Bodak et al. (1978)				
$ScFe_{1.74}(\lambda_2)$	P, 1525– Mt, 1295	MgCu ₂	7.039			Bodak et al. (1978)				
Sc ₂₉ Fe ₆	Pd, 800	$Sc_{29}Fe_6$	14.361			Kotur et al. (1986a), Naumkin et al. (1969)				
ScCo ₂	L, 1520	MgCu ₂	6.921			Dwight (1961a), Markiv et al. (1978)				
ScCo	P, 1050	CsCl	3.145			Aldred (1962), Markiv et al. (1978)				
Sc ₂ Co	L, 840	Al ₂ Cu	6.370		5.618	Kotur et al. (1977a), Markiv et al. (1978)				
Sc ₃ Co	P, 870	Sc ₃ Co	13.102	8.624	5.829	Chabot and Parthé (1978), Markiv et al. (1978)				
ScNi ₅ (HT)	P, 1180–	CaCu ₅	4.69		3.887	Braslavskaya and Maslenkov (1987)				
	S, 800		4.74		3.76	Goebel and Rosen (1968)				
ScNi ₅ (LT)	S, 800	?				Braslavskaya and Maslenkov (1987)				
$Sc_2Ni_7$	L, ~1295	Ce ₂ Ni ₇	4.761		22.395	Braslavskaya and Maslenkov (1987)				
			4.98		24.52	Goebel and Rosen (1968)				
ScNi ₂	L, 1310	MgCu ₂	6.921			Dwight (1961a), <i>Markiv et al. (1978)</i>				
ScNi	L, 1270	CsCl	3.171			Aldred (1962), Markiv et al. (1978)				
Sc ₂ Ni	L, 1000	Ti ₂ Ni	12.120			Aldred (1962), Markiv et al. (1978)				

Table 5 Intermetallic compounds in the Sc-M (M = Fe, Co, Ni) binary systems

et al. The now accepted temperatures of the phase transitions of the pure components are indicated in the phase diagram shown in fig. 6.

The Sc–Co phase diagram, which is shown in fig. 7 is based primarily on the results reported by Markiv et al. (1978). The authors confirmed the occurrence of the compounds ScCo₂, ScCo, Sc₂Co (table 5) and discovered a new one, Sc₃Co with an orthorhombic unit cell. Chabot and Parthé (1978) established its crystal structure (table 5). There were controversial data about the crystal structure of the Sc₂Co compound. Gladyshevsky et al. (1964) reported it to be of Ti₂Ni type, however, these data were not confirmed by Aldred



Fig. 7. The Sc-Co phase diagram in the range 0-90 at.% Sc.

(1962), Kotur et al. (1977a) and Markiv et al. (1978) (table 5). Kotur (1977a) determined the homogeneity range of ScCo₂ phase at 800°C. The lattice spacing increases linearly from a = 6.892 to a = 6.921 Å within its homogeneity range from 30 to 34.5 at.% Sc. These data are in agreement with the data of Markiv et al.

Markiv et al. (1978) published also the Sc–Ni phase diagram in the range 0–80 at.% Sc. These authors confirmed the five binary compounds ScNi₅, Sc₂Ni₇, ScNi₂, ScNi and Sc₂Ni, which were earlier synthesised and structurally determined (table 5). There was a disagreement between the data of Goebel and Rosen (1968) and Markiv et al. concerning the homogeneity range of the ScNi₂ phase. Goebel and Rosen reported it from 27.2 to 33.4 at.% Sc at 1000°C, while Markiv et al. fixed the lower and upper limits at 30 and 36 at.% Sc (a = 6.866 - 6.938 Å), respectively.

Maslenkov and Braslavskaya (1984) reinvestigated part of the Sc–Ni phase diagram in the range 0–36 at.% Sc. Their data are in excellent agreement with the data of Markiv et al. The temperatures of the phase transitions differ no more than 5–10°C at temperatures >1000°C, which is within the experimental error limits. ScNi₂ forms a homogeneous solid solution in the range of 31–35 at.% Sc as reported by Maslenkov and Braslavskaya. The lattice spacing displays a positive deviation from Vegard's rule and changes from a=6.871 to a=6.920 Å as determined from a plot of a vs. concentration. Finally, the same authors, Braslavskaya and Maslenkov (1987), established the occurrence of polymorphism for ScNi₅ and reinvestigated the crystal structure of ScNi₅ and Sc₂Ni₇ phases (table 5). The data of Braslavskaya and Maslenkov for lattice spacings of ScNi₅ (HT) and especially of Sc₂Ni₇ differ remarkably from the data of Goebel and Rosen (table 5). The reason for that is unknown.

The revised Sc–Ni phase diagram is presented in fig. 8. This figure includes the data of Markiv et al. in the range >36 at.% Sc and the data of Maslenkov and Braslavskaya, and Braslavskaya and Maslenkov in the range 0–36 at.% Sc. The temperatures of phase transitions of pure components are in agreement with the accepted values.



Fig. 8. The Sc-Ni phase diagram in the range 0-80 at.% Sc.

## 2.9. Sc-M (M = platinum group element) systems

The Sc–Ru phase diagram has been investigated by Savitskii et al. (1971b). They confirmed the existence of the two binary compounds  $ScRu_2$  and ScRu (table 6) and synthesised a third one with an unknown structure. Chabot et al. (1980a) determined the composition of the latter phase as  $Sc_{11}Ru_4$  as well as its structure (table 6). The same group of authors, Chabot et al. (1980b), synthesised a fourth binary compound in the system with an approximate composition  $Sc_6Ru$  and a cubic structure. Finally five years later Cenzual et al. (1985) established its real composition,  $Sc_{57}Ru_{13}$ , and the crystal structure (table 6). Other data, which also support the reinvestigation of this phase diagram, are the two reported sets of values for the lattice spacings of the  $ScRu_2$  compound (table 6). They indicate that  $ScRu_2$  has, perhaps, a homogeneity range.

Khorujaya et al. (1995) reported on the Sc–Rh phase diagram which is presented in fig. 9. These authors found extended homogeneity ranges for ScRh and ScRh₃ compounds which explained the different values of the lattice spacings for these phases reported earlier by different authors (table 6). However, it is unknown to which composition these published values belong. Three other binary compounds  $Sc_2Rh$ ,  $Sc_3Rh$  and  $Sc_{57}Rh_{13}$  exist in this system (table 6).

The Sc-Pd phase diagram was established by Savitskii et al. (1971c,d). Gschneidner (1975) presented a revised phase diagram, based primarily on these data. He corrected the composition of earlier known  $Sc_2Pd$  phase, which was shown in the original diagram at the composition "Sc₃Pd₂" and changed the temperatures of phase transitions for pure components to the presently accepted values. Gschneidner presented also the arguments in favour of occurrence of the broad homogeneity range for ScPd₃ (see values of lattice spacing in table 6) and the much higher solubility of scandium in solid palladium. The different values of the lattice spacing reported for Sc₂Pd (see table 6) may also indicate the existence of a homogeneity range of that phase too. Finally, Savitskii et al. established very

Compound	Melting	Structure type	Lattic	e param	Reference	
	temperature (°C)	or symmetry	a (Å)	b (Å)	c (Å)	
ScRu ₂	P, 1840	MgZn ₂	5.119		8.542	Compton and Matthias (1959), Savitskii et al. (1971b)
			5.135		8.525	Dwight (1961a)
ScRu	<i>L</i> , 2210	CsCl	3.203			Aldred (1962), Savitskii et al. (1971b)
$Sc_{11}Ru_4$	P, 1510	$\mathbf{Sc}_{11}\mathbf{Ir}_4$	13.367			Chabot et al. (1980a), Savitskii et al. (1971b)
Sc577Ru13	?	$Sc_{57}Rh_{13}$	14.394			Cenzual et al. (1985)
ScRh ₃	P, 1650	AuCu ₃	3.900			Dwight et al. (1961), Khorujaya et al. (1995)
			3.898			Geballe et al. (1965)
			3.909			Erdmann and Keller (1973)
ScRh	L, 1990	CsCl	3.206			Gschneidner (1961), Khorujaya et al. (1995)
			3.204			Dwight et al. (1965)
Sc ₂ Rh	P, 1080 - Ed, 980	?				Khorujaya et al. (1995)
$Sc_3Rh$	L, 1110 - Ed. 930	?				Khorujaya et al. (1995)
$Sc_{57}Rh_{13}$	L, 1150	$\mathrm{Sc}_{57}\mathrm{Rh}_{13}$	14.4051			Cenzual et al. (1985), Khorujaya et al. (1995)
ScPd ₃	<i>P</i> , 1450	AuCu ₃	3.981			Dwight et al. (1961), Savitskii et al. (1971c)
			3.969			Erdmann and Keller (1973), Norman and Harris (1969)
ScPd ₂	P, 1430	MgCu ₂ (?)				Savitskii et al. (1971c)
ScPd	L, 1570	CsCl	3.283			Aldred (1962), Savitskii et al. (1971c)
$Sc_2Pd$	L, 1200	Ti ₂ Ni	12.427			Aldred (1962), Savitskii et al. (1971c)
			12.441			Geballe et al. (1965)
~Sc ₄ Pd	P, 1040	?				Savitskii et al. (1971c)
ScOs ₂	?	MgZn ₂	5.179		8.484	Compton and Matthias (1959), Gschneidner (1961)
			5.188		8.505	Dwight et al. (1966)
$Sc_{11}Os_4$	?	$Sc_{11}Ir_4$	13.344			Chabot et al. (1980a)
$Sc_{44}Os_7$	?	$Mg_{44}Rh_7$	20.771			Chabot et al. (1980b)
ScIr ₃	P, 1980	AuCu ₃	3.900			Eremenko et al. (1994)

Table 6 Intermetallic compounds in the Sc–M (M=Ru, Rh, Pd, Os, Ir, Pt) binary systems

continued on next page

	Table 6, continued								
Compound	Melting	Structure type	Latti	ce paran	neters	Reference			
	temperature (°C)	or symmetry	a (Å)	b (Å)	c (Å)				
ScIr ₂	L, 2150	MgCu ₂	7.345			Eremenko et al. (1994)			
			7.348			Compton and Matthias (1959)			
ScIr	L, 2100	CsCl	3.205			Eremenko et al. (1994)			
			3.206			Aldred (1962)			
Sc ₂ Ir	P, 1420	Ti ₂ Ni	12.290			Eremenko et al. (1994)			
$Sc_{11}Ir_4$	L, 1410	$Sc_{11}Ir_4$	13.430			Eremenko et al. (1994)			
			13.350			Chabot et al. (1980a)			
$Sc_{57}Ir_{13}$	L, 1480	Sc577Rh13	14.350			Eremenko et al. (1994)			
			14.364			Cenzual et al. (1985)			
$Sc_{44}Ir_7$	P, 1420	Mg44Rh7	20.750			Eremenko et al. (1994)			
			20.755			Chabot et al. (1980b)			
ScPt ₃	P, 1850(?)	AuCu ₃	3.958			Dwight et al. (1961),			
						Savitskii et al. (1978a)			
			3.954			Bronger (1967)			
			3.953			Erdmann and Keller (1973)			
ScPt	L, 2200(?)	CsCl	3.270			Aldred (1962),			
						Savitskii et al. (1978a)			
$Sc_2Pt$	?	Co ₂ Si	6.592	4.491	8.206	Chabot and Parthé (1979)			
Sc ₅₇ Pt ₁₃	?	Sc57Rh13	14.350			Cenzual et al. (1985)			

approximately the whole liquidus curve except in the concentration range 90-100 at.% Sc. Thus, a reinvestigation of phase diagram would be necessary. Altogether there exist five binary compounds in this system. Their characteristics are presented in table 6.

As yet no phase diagram is known for the Sc–Os system. However there are data for three binary compounds; these data are presented in table 6. Various values reported for the lattice spacings of  $ScOs_2$  suggest a homogeneity range for that phase.

The Sc–Ir phase diagram, which is shown in fig. 10, is based on the results reported by Eremenko et al. (1994). Five of seven binary compounds have been confirmed, and two new compounds  $Sc_2Ir$  and  $ScIr_3$  have been synthesised by the authors. The crystal structures of all of them are known and given in table 6. The lattice spacings of several of these compounds reported by Eremenko et al. are in excellent agreement with the earlier reported data (see table 6). However in the case of the compound  $Sc_{11}Ir_4$  with a constant composition there is remarkably large difference in the values of lattice spacing, which is not understood.

Four intermetallic scandium-platinum compounds have been prepared and their crystal structures were determined (table 6). Only a few of the phase equilibria in the Sc–Pt phase diagram up to 50 at.% Sc were determined by Savitskii et al. (1978a). The solubility of



scandium in solid platinum is about 10 at.%. In the single invariant phase transformation shown in the original diagram at  $1850\pm25^{\circ}$ C, four phases, namely *L*, Pt(Sc), ScPt₃ and ScPt, are involved, which is in contradiction with the Gibbs phase rule. The slight variations of lattice spacing for ScPt₃ (see table 6) may be due to the result of a homogeneity range similar to that in the cases of ScRh₃ and ScIr₃. However, in the figure of the phase diagram presented by Savitsky et al. ScPt₃ has a constant composition. Thus, the Sc–Pt phase diagram is too tentative and needs additional investigation.

## 2.10. Sc-M (M = 1B element) systems

Savitskii et al. (1970) and Naumkin et al. (1971) were the first to study the Sc-Cu phase diagram. Two binary compounds ScCu and ScCu₂ which were known earlier were confirmed, and a third one, ScCu₄, was reported for the first time. Markiv et al. (1978) reinvestigated the phase diagram in the range 0-80 at.% Sc. In general the data presented in these three papers are in good agreement with each other except for the way of formation of the ScCu₂ compound and its melting temperature, and the homogeneity range of the ScCu₄ phase. Savitskii et al. and Naumkin et al. established the peritectic formation of ScCu₂ at 890°C, while Markiv et al. reported that it is congruently melting at 990°C. The RCu₂ compounds with the heavy rare earths Gd, Dy or Y are also congruently melting phases (Massalski 1990). It is known that scandium resembles the alloying behaviour of these rare earths. For that reason we prefer the data of Markiv et al. concerning the way and temperature of formation of the ScCu₂ compound. We think that the data of Markiv et al. who reported the homogeneity range for ScCu₄ compound from 19 to 23 at.% Sc are more correct. The Cu-rich side of the ScCu₄ phase was determined by microprobe analysis as 18.6 at.% Sc (see Kotur et al. 1996a). Its crystal structure is unknown (table 7). All attempts to solve its structure using powder or single-crystal methods were unsuccessful since the phase is terribly sensitive to mechanical grinding (see Kotur et al. 1996a). The Sc-Cu phase diagram is presented in fig. 11. It is based primarily on the data of Savitskii et al. and Naumkin et al., and in some regions, as mentioned above, on the data of Markiv et al. However, there are also indications that the melting temperature of ScCu₄ is higher than 1000°C (Kotur et al. 1996a). Thus, the phase diagram needs an additional investigation in the range 15-35 at.% Sc as well as in the Sc-rich region (>80 at.% Sc). An extended list of references on this system can be found in the paper by Subramanian et al. (1988).

The solubility of scandium in silver was investigated by Gschneidner et al. (1970) who presented the part of Sc–Ag phase diagram in the range 0–12 at.% Sc. The phase diagram in the concentration region 0–85 at.% Sc has been established by Stapf et al. (1975). Three earlier known binary compounds have been confirmed. Their characteristics are presented in table 7. Stapf et al. reported the eutectic temperature of 910°C between the Ag solid solution and ScAg₄, and the composition of the melt at that temperature containing 10 at.% Sc. These data do not agree with the data of Gschneidner et al. who reported a maximum solubility of 10.5 at.% Sc in solid Ag at the eutectic temperature of 926°C. We prefer these latter data since they were obtained from a larger number of samples.

		-		-	
Compound	Melting	Structure type or symmetry	Lattice pa	arameters	Reference
	temperature (°C)		a (Å)	c (Å)	-
ScCu ₄	L, 925	?			Savitskii et al. (1970)
ScCu ₂	L, 990	MoSi ₂	3.290	8.388	Dwight et al. (1967), Markiv et al. (1978)
ScCu	L, 1125	CsCl	3.256		Aldred (1962), Savitskii et al. (1970)
ScAg ₄	P, ~936	MoNi ₄	6.5740	4.0686	McMasters et al. (1970), Stapf et al. (1975)
			6.575	4.067	Reule et al. (1971)
ScAg ₂	L, 1155	MoSi ₂	3.519	8.922	Dwight et al. (1967), Stapf et al. (1975)
			3.517	8.923	Reule et al. (1971)
ScAg	L, 1230	CsCl	3.412		Aldred (1962), Stapf et al. (1975)
ScAu ₄	?	MoNi ₄	6.536	4.031	Reule et al. (1971)
ScAu ₂	?	MoSi ₂	3.508	8.725	Dwight et al. (1967)
			3.504	8.720	Reule et al. (1971)
ScAu	?	CsCl	3.370		Aldred (1962)
Sc ₂ Au	?	?			Aldred (1962)

Table 7 Intermetallic compounds in the Sc-M (M=Cu, Ag, Au) binary systems



This assumption required the shifting of the  $L + ScAg_2 \leftrightarrow ScAg_4$  peritectic temperature by 16°C of the data of Stapf et al. as well as the shifting of the composition of the eutectic.



The Sc-Ag phase diagram presented in fig. 12 is based primarily on the data of Stapf et al. and the above mentioned modification based on the data of Gschneidner et al. The temperatures of the Sc phase transitions are indicated too, although the Sc-rich part of

The 0–14 at.% Sc part of the Sc–Au phase diagram was reported over three decades ago (Rider et al. 1965). The figure is also presented by Gschneidner (1975). The maximum solubility of scandium (8.8 at.%) in solid gold occurs at the eutectic temperature of 1040°C. Four binary compounds have been synthesised in the system. Their crystal structure data are presented in table 7.

## 2.11. Sc-M (M = 2B element) systems

the phase diagram needs to be determined.

The Sc–Zn phase diagram in the range 0–60 at.% Sc has been recently reported by Palenzona and Manfrinetti (1997); it is presented in fig. 13. Four of the earlier known binary compounds have been confirmed by them and a new one,  $Sc_{13}Zn_{58}$  has been added. The crystal structure data are given in table 8. Earlier, Kripyakevich et al. (1966) reported the existence of a cubic compound with the lattice spacing 13.79 Å and the approximate composition  $Sc_2Zn_7$ . The authors identified the structure to be closely related to the  $Ru_3Be_{17}$  type. Andrusyak et al. (1989) using single-crystal structure investigation corrected its composition to  $Sc_3Zn_{17}$  and established that it belongs to the  $Ru_3Be_{17}$  structure type (table 8).

Palenzona and Manfrinetti (1996) investigated the Sc–Cd phase diagram in the range 0–70 at.% Sc, which is shown in fig. 14. The Sc-rich part of the phase diagram is drawn schematically since it has not been investigated experimentally and further investigations are necessary. Scandium is practically insoluble in solid cadmium. The solubility of cadmium in  $\beta$ Sc is comparatively high, as can be established from the change of the variation of the lattice parameter which varies from 3.73 Å for pure Sc to 3.58 Å in



Fig. 13. The Sc-Zn phase diagram in the range 0-60 at.% Sc.



Fig. 14. The Sc-Cd phase diagram in the range 0-70 at.% Sc.

a quenched two-phase alloy containing 30 at.% Cd (Palenzona and Manfrinetti). These authors confirmed the existence of two known binary compounds, namely ScCd and ScCd₂, and synthesised a third one, ScCd₇. The crystal structures of all these compounds have been determined and are given in table 8. The data given by the different authors for the lattice spacings of these compounds are in good agreement (see table 8). The ScCd phase is characterised by the homogeneity region ranging from 50 to about 62 at.% Sc. The lattice spacing changes from a=3.510 Å for the equiatomic composition to a=3.524 Å for the Sc-rich composition (Palenzona and Manfrinetti).

Only two binary compounds, ScHg and ScHg₃, are known in the Sc–Hg phase diagram. Their crystal structures have been determined by Laube and Nowotny (1963b) (table 8).

Compound	Melting	Structure type	Latti	ce paran	neters	Reference			
	temperature (°C)	or symmetry	a (Å)	b (Å)	c (Å)				
ScZn ₁₂	P, 475	ThMn ₁₂	8.814		5.140	Kripyakevich et al. (1966), Palenzona and Manfrinetti (1997)			
Sc ₃ Zn ₁₇	P, 815	$Ru_3Be_{17}$	13.852			Andrusyak et al. (1989), Palenzona and Manfrinetti (1997)			
$\mathrm{Sc}_{13}\mathrm{Zn}_{58}$	P, 820	$Gd_{13}Zn_{58}$	13.741		13.632	Palenzona and Manfrinetti (1997)			
ScZn ₂	P, 1025	$AlB_2$	4.363		3.196	Kripyakevich et al. (1965), Palenzona and Manfrinetti (1997)			
ScZn	<i>L</i> , 1230	CsCl	3.350			Laube and Nowotny (1963a), Palenzona and Manfrinetti (1997)			
ScCd ₇	P, 415	ScCd ₇	7.306	9.998	9.318	Palenzona and Manfrinetti (1996), Pani et al. (1995)			
ScCd ₃	P, 760	$Ni_3Sn$	6.332		4.854	Palenzona and Manfrinetti (1996)			
			6.330		4.853	Schablaske et al. (1964)			
SeCd	L, 1255	CsCl	3.513			Schablaske et al. (1964), Palenzona and Manfrinetti (1996)			
			3.507			Laube and Nowotny (1963a)			
ScHg ₃	?	Ni ₃ Sn	6.369		4.762	Laube and Nowotny (1963b)			
ScHg	?	CsCl	3.480			Laube and Nowotny (1963b)			

Table 8 termetallic compounds in the Sc–M (M=Zn, Cd, Hg) binary systems

## 2.12. Sc-X (X = 3B element) systems

The Sc–B phase diagram has been published by Spear (1976, 1977). Figure 15 presents the Sc–B phase diagram based on these papers. Two binary compounds occur in this system, namely ScB₁₂ and ScB₂. Earlier it was claimed that there exist two other B-rich compounds ScB₄ and ScB₆, however already Peshev et al. (1970) could not confirm the existence of these two phases. The published data for the crystal structure of ScB₂ phase and its lattice spacings are in good agreement with each other (see table 9). However, two different crystal structures have been reported for the ScB₁₂ compound. Przybylska et al. (1963) found its structure to be isotypic with the cubic UB₁₂. A single-crystal investigation by Matkovich et al. (1965) revealed however that the ScB₁₂ structure is tetragonal, isotypic with ThMn₁₂ (SG *I4/mmm*, a=5.22, c=7.35 Å). Its pseudocubic



Fig. 15. The Sc-B phase diagram.

tetragonal structure was confirmed also by Peshev et al. (1970) and by Callmer (1978) (a = 5.2347, c = 7.3583 Å). However a recent single-crystal investigation of ScB₁₂ by Bruskov et al. (1988) confirmed the cubic  $UB_{12}$ -type structure (table 9). It seems that this question needs additional investigation. Perhaps ScB₁₂ occurs in two polymorphic modifications, but this does not agree with the presented phase diagram.

A detailed reference list on the scandium-boron alloys and their properties can be found in the reviews of Gschneidner (1975) and Spear and Liao (1990).

The Sc-Al phase diagram has been established by Naumkin et al. (1965). The Al-rich region was later refined by Drits et al. (1973). A phase diagram based on these papers is presented in the review of Gschneidner and Calderwood (1989a). In this paper and in the review of Gschneidner (1975) an extended list of references has been given. The solubility of scandium in solid aluminium does not exceed 0.22 at.% (Drits et al.), whereas Sc dissolves about 4 at.% Al (Naumkin et al.). Four binary compounds of constant composition occur in the system. Their compositions and characteristics are given in table 9. Schob and Parthé (1965) reported the CsCl structure type (SG Pm3m) for ScAl (a=3.450 Å) and noticed several extra lines in its X-ray patterns. Schuster and Bauer (1985) during an investigation of the Sc-Al-N ternary system determined that pure ScAl had the CrB-type structure. These authors claimed that either oxygen or nitrogen (or both) can stabilize the CsCl structure in the Sc-Al alloys.

There exist two variants of the Sc-Ga phase diagram in the literature. The first one was reported by Markiv et al. (1977) who investigated only 13 binary alloys within

Compound	Melting	Structure type	Latti	ce param	eters	Reference
*	temperature (°C)	or symmetry	a (Å)	b (Å)	c (Å)	
ScB ₁₂	L, 2040	UB ₁₂	7.402			Bruskov et al. (1988), Spear (1976)
$ScB_2$	L, 2250	AlB ₂	3.148		3.516	Peshev et al. (1970), Spear (1976)
			3.146		3.517	Zhuravlev and Stepanova (1958)
ScAl ₃	P, 1320	AuCu ₃	4.101			Schuster and Bauer (1985), Naumkin et al. (1965)
			4.105			Zalutskii and Kripyakevich (1967)
ScAl ₂	L, 1420	MgCu ₂	7.5748			Schuster and Bauer (1985), Naumkin et al. (1965)
			7.580			Rechkin et al. (1965)
ScAl	<i>L</i> , ~1300	CrB	5.0299	9.8945	3.1263	Schuster and Bauer (1985), Naumkin et al. (1965)
Sc ₂ Al	P, 1195	Ni ₂ In	4.8813		6.167	Schuster and Bauer (1985), Naumkin et al. (1965)
			4.888		6.166	Eymond and Parthé (1969)
ScGa ₃	P, 1030	AuCu ₃	4.095			Yatsenko et al. (1979)
			4.096			Markiv et al. (1977)
ScGa ₂	L, 1140	KHg ₂	4.140	6.614	7.914	Belyavina and Markiv (1980a), Yatsenko et al. (1979)
$Sc_3Ga_5$	L, 1130(?)	$\mathrm{Tm}_3\mathrm{Ga}_5$	10.910	9.231	5.695	Markiv et al. (1981), <i>Markiv et al. (1977)</i>
ScGa	P, 1090	CrB	4.023	10.212	3.894	Yatsenko et al. (1979)
			4.022	10.205	3.895	Schob and Parthé (1965)
$Sc_5Ga_4$	P, 1230	$\mathrm{Ho}_{11}\mathrm{Ge}_{10}$	10.366		15.305	Markiv et al. (1989), Yatsenko et al. (1979)
$Sc_3Ga_2$	?	$Gd_3Ga_2$	10.767		14.045	Markiv et al. (1987)
$Sc_5Ga_3$	L, 1430	$Mn_5Si_3$	8.067		6.036	Yatsenko et al. (1979)
			8.074		5.951	Schob and Parthé (1964a)
Sc ₂ Ga	P, 1065(?)	$Sc_2Ga$	8.085	5.933	14.014	Belyavina and Markiv (1992), Markiv et al. (1977)
			$\gamma = 90.9$	5°		
ScIn ₃	P, 930	AuCu ₃	4.479			Palenzona and Manfrinetti (1996), Vatamba et al. (1982)
			4 477			raisenko et al. $(1983)$
C -T-	B 070	7-0-	4.477	12 571	4 450	Parme et al. (1905)
Scin ₂	P, 970		4.440	13.371	4.459	raienzona and Manfrinetti (1996)

Table 9 Intermetallic compounds in the Sc-X (X=B, Al, Ga, In, Tl) binary system

continued on next page

Compound	Melting	Structure type	Lattic	се рагаг	neters	Reference
	temperature (°C)	or symmetry	a (Å)	b (Å)	c (Å)	
ScIn	P, 1125	AuCu	4.539		4.326	Palenzona and Manfrinetti (1996)
ScIn _{1-x}	P, 1280	CsCl	3.564			Palenzona and Manfrinetti (1996)
Sc ₂ In	<i>L</i> , 1400	Ni ₂ In	5.024		6.276	Palenzona and Manfrinetti (1996), Yatsenko et al. (1983)
			5.0260		6.2771	Hines and Harris (1971)
Sc ₃ In	P, 1340	Ni ₃ Sn	6.43		5.17	Yatsenko et al. (1983), Palenzona and Manfrinetti (1996)
			6.421		5.183	Compton and Matthias (1962)
~ScTl ₂	P, 967	?				Sabirzyanov (1988)
$Sc_3Tl_5$	P, 987– Ed, 477	Pu ₃ Pd ₅	9.970	7.948	10.235	Sabirzyanov (1988)
ScT1	P, 1152– Ed, 367	cub	13.382			Sabirzyanov (1988)
Sc ₅ Tl ₄	P, 1262	Ti₅Ga₄	8.590		6.356	Sabirzyanov (1988)
$Sc_{5}Tl_{3-3.85}$	L, 1372	$Mn_5Si_3$	8.396– 8.432		6.160– 6.465	Sabirzyanov (1988)
Sc ₂ Tl	P, 1287	Ni ₂ In	4.984		6.255	Sabirzyanov (1988)
~Sc ₃ Tl	P, 1262– Ed, 1117	?				Sabirzyanov (1988)

Table 9, continued

the concentration range of 35–68 at.% Ga, which is only half of the number of alloys investigated by Yatsenko et al. (1979) (see below). From this investigation Markiv et al. (1977) concluded that there exist seven binary compounds. Three of them,  $Sc_5Ga_3$ ,  $Sc_2Ga_3$  and  $ScGa_3$ , were reported to melt congruently at temperatures 1380, 1130 and 1090°C, respectively. The others,  $Sc_2Ga_3$ ,  $Sc_5Ga_4$ , ScGa and  $ScGa_2$ , are formed by peritectic reactions at 1065, 1240, 1080 and 1070°C, respectively. In this paper and in the following papers (Belyavina and Markiv 1980a, 1992, Markiv et al. 1981, 1987, 1989), the same group of scientists presented results of crystal structure investigations of the above mentioned gallides and also reported about the synthesis of an extra binary compound  $Sc_3Ga_2$ . Markiv et al. (1981) corrected the composition of the earlier reported " $Sc_2Ga_3$ " compound which they subsequently found to be  $Sc_3Ga_5$ . The crystal structure data are given in table 9. Belyavina and Markiv (1992) reinvestigated the structure of the Sc–Ga alloys in the range 30–38.5 at.% Ga. The  $Sc_2Ga$  compound has a narrow homogeneity range from 33 to 35 at.% Ga. Its monoclinic crystal structure is related to  $Mn_5Si_3$  type.



In the alloys with the content 36-8.5 at.% Ga they observed two hexagonal phases which they presented as h-Sc₅Ga₃ and r-Sc₅Ga₃ with the lattice spacings a=8.048-8.062 and c=6.112-6.073 Å, and a=8.084 and c=5.958 Å respectively. The pure r-Sc₅Ga₃ was observed in a specimen with 36 at.% Ga and heat treated at 800°C. Thus, the composition of the phase is shifted from stoichiometry 5:3 (37.5 at.% Ga). This compound appears at temperatures lower than 1000°C, and its structure was determined to be of the Mn₅Si₃ type. The crystal structure of the h-Sc₅Si₃ phase, which is observed at high temperatures with the content of about 38 at.% Ga, has not been established and needs additional investigation. The structure of another compound isotypic with h-R₅Ga₃ (R=Y, Tm, Lu) reported by Markiv and Belyavina (1992) is also unknown, however, as stated by Markiv and Belyavina the structure of these compounds should closely be related to the Mn₅Si₃ type structure.

A second variant of the Sc–Ga phase diagram was presented by Yatsenko et al. (1979). These authors investigated 28 alloys over the whole concentration region of the system. Figure 16 presents the Sc–Ga phase diagram based on the data of Yatsenko et al. The two variants of the Sc–Ga phase diagram considerably differ from each other. Yatsenko et al. observed only five binary compounds in the system (see fig. 16). For three of them, ScGa₃, Sc₅Ga₃ and ScGa, they determined the crystal structure. These data perfectly agree with the data of Markiv et al. But in general the disagreement between the two reported versions is drastic. Such disagreement is hard to explain as the two groups of scientist used practically the same experimental methods: differential thermal, X-ray and microscopic analyses. Markiv et al. used also the microprobe analysis and Yatsenko et al. performed also microhardness measurements on their samples. These diverging results strongly suggest that the Sc–Ga phase diagram needs to be reinvestigated.

The Sc–In phase diagram was determined by Yatsenko et al. (1983). Earlier the part of the phase diagram in the range 0–40 at.% In was proposed by Gardner et al. (1968), but their data were tentative. Yatsenko et al. confirmed the compositions and crystal structures



of three binary scandium indides,  $ScIn_3$ ,  $Sc_2In$  and  $Sc_3In$ , which had been synthesised earlier, and observed three new compounds of the tentative compositions  $Sc_3In_5$ , ScIn and  $Sc_5In_3$  with unknown structures.

Recently Palenzona et al. (1996) reinvestigated the Sc–In phase diagram in the range 30-100 at.% In. The compounds Sc₃In₅ and Sc₅In₃ could not be confirmed and were replaced by ScIn₂ and ScIn_{1-x}, respectively. In addition four other binary phases have been confirmed. Their characteristics are given in table 9. The temperatures of the phases transitions reported by Palenzona et al. are in average 5 to 20°C higher than those reported by Yatsenko et al. with the exception of the temperature for the peritectic formation of ScIn_{1-x} which is 50°C lower than that of the corresponding "Sc₅In₃" phase reported by Yatsenko et al. Figure 17 presents the phase diagram based on the data of Palenzona et al. (1996) (in the range 0–70 at%. Sc) and those of Yatsenko et al. (1983) (in the range 70–100 at.% Sc). Gschneidner (1975) reviewed the physical properties of Sc–In compounds. Sc₃In is a well known weak ferromagnetic compound with a Curie temperature near 6 K. Since it has been considered as a prototype of an intermetallic compound where spin fluctuations play an important role its physical properties are discussed in sect. 6.

Sabirzyanov (1988) was the only scientist who investigated the interaction of scandium with thallium. He established the phase diagram shown in fig. 18. The investigation was carried out by means of thermal, X-ray and microscopic analyses. He also measured the magnetic susceptibility of the alloys. Seven binary compounds occur in the system. Sabirzyanov determined the crystal structure of five of them (table 9). For two phases with unknown structures the compositions of  $Sc_3T1$  and  $ScTl_2$  are given as the most likely ones. The homogeneity range for  $Sc_5Tl_{3-3.85}$  reaches 6 at.% at 1262°C. The limits of solubility of thallium in  $\beta$ Sc and  $\alpha$ Sc are  $18\pm1$  at.% and  $11\pm1$  at.%, respectively. The data concerning the temperatures of the phase transitions, the compositions and crystal structures of the compounds (except lattice spacings) were also presented by Sabirzyanov (1989); however, the phase diagram was not shown.



Fig. 19. The Sc-C phase diagram in the range 20-100 at.% Sc.

## 2.13. Sc-X (X = 4B element) systems

Many papers have been dedicated to the investigation of interaction of scandium with carbon. The early papers which appeared before 1973 have been reviewed by Gschneidner (1975) and Gschneidner and Calderwood (1986c). In total seven compounds have been reported to occur in this system, however, the majority of them were not confirmed. Gordijchuk et al. (1981) first reported on the Sc–C phase diagram in the range 20–100 at.% Sc and refined it afterwards (Gordijchuk 1987). The phase diagram presented in fig. 19 is based mainly on the latter data; there are only three binary compounds. Their

crystal structure data are presented in table 10. One of the phases,  $Sc_4C_3$ , exists in two polymorphic modifications. The data of Gorgijchuk agree with the results of Krikorian et al. (1969a) who also observed that  $Sc_4C_3$  (ST anti-Th₃P₄, SG I43d, a = 7.207 Å) remained stable when heated to 1500°C. Its X-ray pattern changed when heating the sample up to 1600°C. Krikorian et al. (1969b) reported also about a bcc phase with the approximate composition  $Sc_{13}C_{10}$  (~56.5 at.% Sc, a = 8.5268 Å). It was synthesised after annealing the  $Sc_4C_3$  sample with an addition of germanium. However the Ge atoms are not involved into the structure of this scandium carbide. Possibly Krikorian et al. obtained the high temperature phase of  $Sc_4C_3$  ( $\beta$ ) reported by Gordijchuk. Jedlichka et al. (1971) were the first to determine the composition and the crystal structure of the scandium carbide with the highest Sc content, which was earlier reported by Krikorian et al. (1969a) as "ScC_{1,2-1,3}". Jedlichka et al. (1971) determined its composition as  $Sc_{15}C_{19}$  (ST  $Sc_{15}C_{19}$ , SG  $P42_1c$ , a=7.50, c=15.00 Å). Recently Pöttgen and Jeitschko (1991) reinvestigated the structure of  $Sc_{15}C_{19}$  using a single crystal and reported its composition as  $Sc_3C_4$ . The tetragonal unit cell of  $Sc_3C_4$  contains two additional carbon atoms in comparison to the Sc₁₅C₁₉ structure. Its lattice spacings are given in table 10. Maybe that these two investigated single crystals Sc₃C₄ (42.9 at.% Sc) and Sc₁₅C₁₉ (44.1 at.% Sc) can be treated in favour of occurrence of homogeneity range of this compound reported by Gordijchuk (see fig. 19). Gordijchuk determined its homogeneity range from 43.5 to 45.7 at.% Sc and the lattice spacings changing from a = 7.53, c = 15.04 Å to a = 7.51, c = 15.51 Å. Thus, to clarify the conflicting data additional investigations of the system, particularly in the range 40-80 at.% Sc, have to be carried out.

Although three binary scandium silicides, Sc₅Si₃, ScSi and Sc₃Si₅, were obtained and structurally investigated already in the early 1960s (table 10), a Sc-Si phase diagram was only presented in 1988. It is shown in fig. 20. The data are taken from Eremenko et al. (1988) with corrections for the phase transition temperatures of pure components to the presently accepted values. For scandium the difference between the reported melting temperature (1615°C) and the  $\beta$ Sc  $\leftrightarrow \alpha$ Sc transition temperature (1430°C) and the corresponding present temperatures 1541 and 1337°C is rather large. In the case of silicon the difference in the melting temperature (1412°C reported and 1414°C accepted) was within the experimental error. Eremenko et al. confirmed the data of Bodak et al. (1976) and Kotur (1977a) that the binary phase with the highest Si content exists only at high temperature (see fig. 20). Bodak et al. and Kotur observed that phase only in the as cast alloys. After heat treatment at 800°C for 340 h this phase totally decomposed to Si and ScSi. There is a disagreement between the data about the composition of the highest silicon-containing scandium silicide. Gladyshevsky and Emes-Misenko (1963) reported it as Sc₃Si₅ (62.5 at.% Si), Schob and Parthé (1964b) found it to have the homogeneity range from 60 (composition Sc₂Si₃ or ScSi_{1.5}) to 62.5 at.% Si (composition Sc₃Si₅ or ScSi_{1.67}), whereas Eremenko et al. claimed a constant composition ScSi_{1.5}. For the reported lattice spacings for this phase, it is given as  $ScSi_{2-x}$  in table 10.

Recently Kotroczo and McColm (1994) established the phase equilibria for rapidly cooled Sc-Si alloys (cooling rate 150-200°C/s). Their phase diagram shows many similarities with that of Eremenko et al. But in general the liquid boundaries and

Compound	Melting	Structure type or symmetry	Latti	ce paran	neters	Reference
-	temperature (°C)		a (Å)	b (Å)	c (Å)	
$Sc_3C_4$	P, 1794	Sc ₃ C ₄	7.5138		14.704	Pöttgen and Jeitschko (1991), Gordijchuk (1987)
Sc ₁₅ C ₁₉		Sc ₁₅ C ₁₉	7.50		15.00	Jedlichka et al. (1971)
$Sc_4C_3$ ( $\beta$ )	P, 1864 – S, 1504	?				Gordijchuk (1987)
$Sc_4C_3(\alpha)$	S, 1504 – Ed, ~950	anti-Th ₃ P ₄	7.2078			Gordijchuk (1987)
$ScC_{1-x}$	L, 2270	NaCl	4.67-4.	.72		Gordijchuk (1987)
			4.509			Nowotny and Auer-Welsbach (1961), Auer-Welsbach and Nowotny (1961)
$ScSi_{2-x}(\beta)$	P, 1260 –	AlB ₂	3.66		3.87	Gladyshevsky and
	S, 1070		3.664-		3.877-	Emes-Misenko (1963),
			3.646		3.881	Eremenko et al. (1988), Schob and Parthé (1964b)
$\mathrm{ScSi}_{2-x}(\alpha)$	S, 1070– Ed, 925	?				Eremenko et al. (1988)
ScSi	P, 1785	CrB	3.988	9.882	3.659	Schob and Parthé (1965), Eremenko et al. (1988)
$Sc_5Si_3$	L, 2060	$Mn_5Si_3$	7.861		5.812	Arbuckle and Parthé (1962), Eremenko et al. (1988)
ScGe ₂	P, 1116	ZrSi ₂	3.889	14.866	3.796	Eremenko et al. (1981)
			3.888	14.873	3.793	Schob and Parthé (1964b)
ScGe	P, 1192	CrB	3.98	10.08	3.763	Eremenko et al. (1981)
			4.007	10.06	3.762	Schob and Parthé (1965)
$Sc_{11}Ge_{10}$	P, 1675	$Ho_{11}Ge_{10}$	10.12		15.54	Eremenko et al. (1981)
			10.285		15.54	Kotur (1991)
$Sc_5Ge_4$	P, 1870	$Sm_5Ge_4$	7.269	13.980	7.152	Eremenko et al. (1981)
			7.118	13.79	7.140	Kotur (1991)
$Sc_5Ge_3$	L, 2065	$Mn_5Si_3$	7.921		5.881	Eremenko et al. (1981)
			7.939		5.883	Arbuckle and Parthé (1962)
$ScSn_2$	P, 895	$ScSn_2$	4.238		31.073	Palenzona and Manfrinetti (1995)
ScSn	P, 945	CsCl	3.666			Kotur and Derkach (1994), Palenzona and Manfrinetti (1995)
$Sc_6Sn_5$	P, 1455	Ti ₆ Ge₅	8.830	19.045	6.057	Palenzona and Manfrinetti (1995)

Table 10 Intermetallic compounds in the Sc-X (X=C, Si, Ge, Sn, Pb) binary systems

continued on next page

Table 10 continued

	Tuble To, commute							
Compound	Melting	Structure type or symmetry	Latt	ice paran	neters	Reference		
	temperature (°C)		a (Å)	b (Å)	c (Å)	-		
Sc ₅ Sn ₃	<i>L</i> , ~1800	Mn ₅ Sn ₃	8.401		6.073	Palenzona and Manfrinetti (1995)		
			8.408		6.081	Jeitschko and Parthé (1965)		
Sc ₆ Pb ₅	P, 1290	${\rm Ti}_6{\rm Ge}_5$	8.889	19.274	6.177	Palenzona and Manfrinetti (1995)		
Sc ₅ Pb ₃	<i>L</i> , ~1700	$Mn_5Si_3$	8.473		6.162	Palenzona and Manfrinetti (1995)		
			8.467		6.158	Jeitschko and Parthé (1965)		



the nonvariant reactions were 10 to 110°C and in one case (for peritectic reaction  $L + \text{ScSi} \leftrightarrow \beta \text{ScSi}_{2-x}$ ) even 525°C higher than those reported by Eremenko et al. Kotroczo and McColm reported the highest silicon-containing silicide as having the homogeneity range  $\text{ScSi}_{1.22-1.67}$  (55–62.5 at.% Si), a polymorphic transition in the temperature range 1325–1350°C, and being stable down to the room temperature. Neither Kotroczo and McColm nor Eremenko et al. obtained pure AlB₂-type structure specimens of this silicide. They observed in the X-ray patterns the presence of a nonstoichiometric AlB₂-type



structure, however, together with extra weak lines. Eremenko et al. determined the lattice spacings of this AlB₂-type phase as a=3.654, c=3.87 Å. Kotroczo and McColm observed an increase of the lattice parameters from a=3.656, c=3.872 Å to a=3.665, c=3.880 Å as the silicon content increases. An indexing of almost all lines of the patterns was possible assuming an orthorhombic unit cell with a=8.27(9), b=8.69(7), c=9.98(9) Å. The fourth binary silicide Sc₅Si₄ (P, 1920°C) was observed by Kotroczo and McColm in rapidly cooled alloys. Its X-ray pattern was indexed as an orthorhombic cell with a=6.78(2), b=13.11(4), c=7.03(1) Å. In our opinion these data indicate that the Sm₅Ge₄ structure type as a possible structure for Sc₅Si₄, which is structure for the corresponding scandium germanide Sc₅Ge₄ (see table 10).

Okamoto (1992) mentioned the thermodynamical inconsistency of the liquidus curve in the Sc–Si phase diagram of Eremenko et al. (see fig. 20, between 30 and 45 at.% Si). Therefore a new investigation of the Sc–Si phase diagram in the range 40–65 at.% Si is advisable.

The Sc–Ge system was experimentally investigated by Eremenko et al. (1981). Figure 21 displays the Sc–Ge phase diagram based on these data. The solubility of germanium in  $\beta$ Sc is less than 0.5 at.% whereas in solid  $\alpha$ Sc it is more than 1 at.% but this value is not yet exactly determined. The solubility of scandium in germanium is less than 1 at.%. Three germanides, namely Sc₅Ge₃, ScGe and ScGe₂ were known before Eremenko et al. synthesised two others, Sc₅Ge₄ and Sc₁₁Ge₁₀. The data from different authors about the crystal structure of scandium germanides are in general agreement (see table 10). Only in



Fig. 22. The Sc-Sn phase diagram in the range 0-70 at.% Sc.

the case of  $Sc_{11}Ge_{10}$  is there a considerable difference in the reported *a* lattice spacings, while the *c* values are identical.

Palenzona and Manfrinetti (1995) published the Sc–Sn phase diagram in the range 0– 70 at.% Sc which is presented in fig. 22. Earlier only the experimental data by Eremenko et al. (1990) existed, and they reported that  $Sc_5Sn_3$  melts congruently at 1775°C. These data were confirmed by Palenzona and Manfrinetti (1995). Four binary stannides occur in the system. Two of them,  $ScSn_2$  and  $Sc_6Sn_5$  have been prepared and structurally investigated by Palenzona and Manfrinetti for the first time. These authors did not mention the data of Kotur and Derkach (1994) who reported that ScSn has the CsCl structure type. Since scandium–tin alloys are extremely oxidizable the ScSn phase could not be obtained in pure state. Palenzona and Manfrinetti did not determine the crystal structure of ScSn, however they mentioned the rather simple character of its powder X-ray pattern. The crystal structure characteristics of scandium stannides are presented in table 10.

The Sc–Pb phase diagram has been determined by Palenzona and Manfrinetti (1995) in the range 0–70 at.% Sc (see fig. 23). The Sc-rich part of this system (as well as the Sc–Sn system, discussed above) has not been investigated because of the high melting temperatures of the corresponding alloys and contamination of them by molybdenum which was used as container material during preparation of the samples. Two binary compounds occur in the system (table 10), one of them, Sc₅Pb₃ was known before the investigation of Palenzona and Manfrinetti.

## 2.14. Sc-X (X = P, As, Sb, Bi) systems

There is no information in the literature about the binary phase diagrams of scandium with the 5B elements (P, As, Sb, Bi). Although in each of the systems from one to four binary



Fig. 23. The Sc-Pb phase diagram in the range 0-70 at.% Sc.

compounds have been synthesised and their crystal structures have been determined, there is no information about their melting temperatures and the way of formation (see table 11). The only exception are the data of Komissarova et al. (1965) who found that ScP has a melting temperature higher than 2000°C. Evidently some phases occur in two (Sc₃P₂) or three (Sc₃As₂) polymorphic modifications, but nothing is known about the temperatures of their phases transitions. Different values of lattice spacings observed for NaCl-type compounds (see table 11) may be originating from the homogeneity ranges of these phases or from scandium of different purity used by different groups of scientists. Additional investigations are necessary to clarify these data. Additional literature can be found in Gschneidner (1975), and Gschneidner and Calderwood (1986b, 1989b).

### 2.15. Sc-X (X = Se, Te, Po) systems

Only a little information exists about the interaction of scandium with the elements of selenium subgroup (Se, Te and Po). No phase diagrams are available for any of these binary systems.

Two binary compounds have been synthesised in the Sc–Se system by different groups of scientists. The results presented in table 12 indicate the possibility of homogeneity ranges of these phases.

Men'kov et al. (1959, 1961) synthesised two scandium tellurides and determined their crystal structures. The data of Men'kov et al. (1959) about the cubic  $\gamma'$ -Al₂O₃-type structure for the compound Sc₂Te₃ had not been confirmed by a single-crystal structure investigation of that phase performed by White and Dismukes (1965) (see table 12). The latter authors obtained also a specimen of Sc_{2.3}Te₃ composition isotypic with Sc₂Te₃ with the lattice parameters a = 4.113, c = 4.051 Å. This result seems to indicate the occurrence

Compound	Melting	Structure type or symmetry	Lattic	e paran	neters	Reference
	temperature (°C)		a (Å)	b (Å)	c (Å)	
ScP	?	NaCl	5.312			Parthé and Parthé (1963)
			5.3088			Yim et al. (1972)
$Sc_3P_2$ (I)	?	Cr ₃ C ₂	6.9781	3.7570	14.3655	Berger (1980a)
$Sc_3P_2$ (II)	?	$S_3Sb_2$	10.1075	3.6944	10.1793	Berger (1980a)
Se ₇ P ₃	?	$Th_7Fe_3$	8.9340		5.7349	Berger (1981)
Sc ₃ P	?	Fe ₃ C	6.7540	8.4449	5.7662	Berger (1981)
ScAs	?	NaCl	5.4638			Yim et al. (1972)
			5.4687			Brixner (1960)
Sc ₃ As ₂ (I)	?	$Cr_3C_2$	7.1423	3.8698	14.7073	Berger (1980a)
Sc ₃ As ₂ (II)	?	$S_3Sb_2$	10.3754	3.8063	10.3754	Berger (1980a,b)
Sc ₃ As ₂ (III)	?	V ₃ As ₂	10.3755		3.8064	Berger (1977)
Sc ₅ As ₃	?	βYb₅Sb₃	10.7038	8.1418	7.2272	Berger (1980a)
Sc ₇ As ₃	?	$Sc_7As_3$	14.3751		8.0281	Berger et al. (1981), Berger (1977)
ScSb	?	NaCl	5,8517			Berger (1977)
			5.859			Brixner (1960)
Sc ₅ Sb ₃	?	βYb ₅ Sb ₃	11.0792	8.7126	7.6272	Berger (1977)
Sc ₂ Sb	?	Cu ₂ Sb	4.2049		7.7902	Berger (1977)
ScBi	?	NaCl	5.954			Zhuravlev and Smirnova (1962)

Table 11 Intermetallic compounds in the Sc–X (X=P, As, Sb, Bi) binary systems

Table 12 Intermetallic compounds in the Sc-X (X = Se, Te, Po) binary systems

Compound	Melting temperature (°C)	Structure type or symmetry	Lattice parameters			Reference
			a (Å)	b (Å)	c (Å)	-
Sc ₂ Se ₃	?	Sc ₂ S ₃	10.836	7.673	22.95	Dismukes and White (1965)
			10.846	7.668	23.004	Brozek et al. (1974)
ScSe	?	NaCl	5.398			Hulliger and Hull (1970)
			5.434			Brozek et al. (1974)
Sc ₂ Te ₃	?	$Ti_7S_{12}$	4.109		4.059	White and Dismukes (1965)
ScTe	?	NiAs	4.120		6.749	Men'kov et al. (1961)
ScPo	?	NiAs	4.206		6.92	Prokin et al. (1977)

of a homogeneity range of this phase. There is a disagreement between the data reported about the crystal structure of another phase, namely ScTe. Brixner (1960) determined it as

hexagonal with the lattice spacings a = 6.728, c = 8.360 Å, however, Men'kov et al. (1961) reported it as isotypic with NiAs (see table 12). We consider the data of Men'kov et al. to be more reliable since the neighbouring scandium telluride, Sc₂Te₃, contains NiAs-type fragments in its structure.

In the literature there is information only about one binary compound occurring in the Sc–Po system. Its crystal structure data are given in table 12.

#### 3. Ternary systems containing scandium

At the beginning of 1997 there was information on about 110 scandium ternary systems. Of these systems the phase equilibria have been investigated either for the entire concentration region of an isothermal section (or sometimes several sections), or for only in part of it. Selected alloys have been investigated in 85 of these ternary systems. A compilation of these data are given in table 13. As can be seen from that table, there is a considerable amount of data concerning the Sc-M-X ternaries, where M is a metal and X stands for a p-element. In this section we have arranged the data in the following subsections: Sc-M-B, Sc-M-Al, Sc-M-Ga, Sc-M-In, Sc-M-C, Sc-M-Si, Sc-M-Ge, Sc-M-Sn, and Sc-M-X with X=P, As, Sb, Bi and with X=Se, Te, Po. Since there is only a small amount of data available for the latter two cases, these subsections have not been subdivided. The last two subsections of the ternary systems include either two p-elements (Sc-X-X'), or two s-, d-, or f-metals (Sc-M-M'). If the isothermal section of a system is known from the literature it is shown in a figure together with a brief comment. If these isothermals have already been treated in one of the previous chapters of the Handbook on the Physics and Chemistry of Rare Earths then they are omitted. As in the previous section controversial data are mentioned separately and are critically evaluated as best we are able to do so.

Since there is only a small amount of data concerning the melting temperatures and the way of formation of ternary scandium intermetallics given in the literature, these data are not included in the tables which list the compositions and lattice parameters of ternary compounds. The reference from which the lattice parameters have been taken is listed first, and is followed by other references. The reference where the corresponding atomic coordinates of the structure have been published (if it is available) is italicized.

#### 3.1. Sc-M-B ternary systems

## 3.1.1. Sc-La-B

The phase diagram of the Sc–La–B system is unknown. The solubility of scandium in LaB₆ has been investigated by Tsolovski and Peshev (1972). It has been reported that the solubility reaches 0.5 mole fraction Sc, but according to the data of Kondrashov (1978) and Samsonov et al. (1979) the solubility is considerably lower. The limiting composition of the solid solution is La_{0.9}Sc_{0.1}B₆, and there is practically no change of the lattice parameter within this homogeneity range (La_{0.9}Sc_{0.1}B₆ to LaB₆).

#### 3.1.2. Sc--Cr--B

Zavalii and Mikhalenko (1989) reported about an investigation of the phase equilibria in the Sc-Cr-B system at 800°C (0-33.3 at.% Sc) and at 600°C (33.3-100 at.% Sc) but





these authors did not present figures of these isothermal sections.  $CrB_2$  dissolves up to 7 at.% Sc. One ternary compound ScCrB₄, which is isotypic with YCrB₄, occurs in the system, but the lattice spacings have not been reported (table 14).

Compound	Structure type	Lattice parameters			Reference	
	or symmetry	a (Å) b (Å)		c (Å)		
ScCrB ₄	YCrB ₄	?	?	?	Zavalii and Mikhalenko (1989)	
$ScMnB_4$	YCrB ₄	?	?	?	Zavalii and Mikhalenko (1989)	
Sc ₂ ReB ₆	Y ₂ ReB ₆	8.856	11.169	3.4937	Mikhalenko et al. (1991)	
$ScFeB_4$	YCrB ₄	5.884	11.318	3.3424	Zavalii et al. (1988), Stepanchikova and Kuz'ma (1981)	
$Sc_2Co_{21}B_6$	$W_2Cr_{21}C_6$	10.546			Gangleberger et al. (1966), Stepanchikova (1979)	
		10.537			Kuz'ma and Voroshilov (1967)	
$ScCo_4B_4$	CeCo ₄ B ₄	4.902		6.961	Stepanchikova (1979)	
$ScCo_3B_2$	$CeCo_3B_2$	4.889		2.977	Kuz'ma et al. (1969), Stepanchikova (1979)	
ScCoB ₄	YCrB ₄	5.762	11.172	3.250	Zavalii et al. (1988), Stepanchikova (1979)	
$Sc_{3-4}Ni_{20-19}B_6$	$W_2Cr_{21}C_6$	10.585			Kuz'ma and Voroshilov (1967), Stepanchikova and Kuz'ma (1981)	
$Sc_4Ni_{29}B_{10}$	$Sc_4Ni_{29}B_{10}$	7.680		15.380	Kuz'ma et al. (1988), Stepanchikova and Kuz'ma (1981)	
$\sim$ Sc ₄ Ni ₁₅ B ₆	?	5.7853	11.208	3.2737	Stepanchikova and Kuz'ma (1981)	
$ScNiB_4$	YCrB ₄	5.7853	11.208	3.2737	Zavalii et al. (1988), Stepanchikova and Kuz'ma (1981)	
ScNi ₃ B	CaTiO ₃	3.776			Stepanchikova and Kuz'ma (1981)	
ScRu ₄ B ₄	LuRu ₄ B ₄	7.346		14.895	Ku et al. (1979)	
$Sc_2Ru_5B_4$	$Sc_5Ru_2B_4$	9.9833	8.4859 $\beta = 90.01^{\circ}$	3.0001	Rogl (1984a)	
ScRuB ₄	?				Ku et al. (1979)	
$Sc_2Os_5B_4$	$Sc_2Ru_5B_4$	10.0477	8.5499 $\beta = 90.03^{\circ}$	3.0216	Rogl (1984a)	
ScOsB ₂	LuRuB ₂	5.647	5.178	6.184	Shelton and Ku (1980)	
$ScIr_3B_4$	ZrIr ₃ B ₄	7.576		3.442	Rogl and Nowotny (1979)	
$ScIr_3B_2$	ErIr ₃ B ₂	5.344	9.307 $\beta = 92.1^{\circ}$	3.062	Ku and Meissner (1981)	
$ScIr_3B_{1-x}$	CaTiO ₃	3.999			Holleck (1977)	

Table 14 Ternary intermetallic compounds in the Sc-M-B systems



Fig. 24. Sc-W-B, isothermal section at 1000°C.

# 3.1.3. Sc-W-B

Zavalii and Mikhalenko (1989) briefly reported about an investigation of the phase equilibria in the Sc–W–B system at 1000°C (0–33.3 at.% Sc) and at 600°C (33.3–100 at.% Sc) without presenting the illustrations. The isothermal section at 1000°C, which is shown in fig. 24, is based on the data of Mikhalenko et al. (1991). Binary compound ScB₂ dissolves up to 10 at.% W. No ternary compounds were found.

### 3.1.4. Sc-Mn-B

The phase equilibria in the Sc–Mn–B system at 800°C (0–33.3 at.% Sc) and at 500°C (33.3–100 at.% Sc) have been investigated by Zavalii and Mikhalenko (1989). Figures of these isothermal sections were not presented in the original paper. Scandium stabilises the high temperature binary phase MnB₂ at 800°C (ST AlB₂). In the binary system it is stable in the temperature range 1827–1100°C. This solid solution has the homogeneity range of about 4–8 at.% Sc. One ternary compound, namely ScMnB₄ occurs in the system, but its lattice spacings have not been reported (table 14).

### 3.1.5. Sc-Re-B

Zavalii and Mikhalenko (1989) have investigated the phase equilibria in the Sc-Re-B system at 1000°C (0–33.3 at.% Sc) and at 600°C (33.3–100 at.% Sc), but they did not show figures in their publication. The isothermal section of the phase diagram at 1000°C for the whole concentration region, which is shown in fig. 25, is based on the data of Mikhalenko et al. (1991). Scandium diboride dissolves up to 7 at.% Re. One ternary compound,  $Sc_2ReB_6$ , occurs in the system. Its characteristics are shown in table 14.



Fig. 25. Sc-Re-B, isothermal section at 1000°C. Ternary compound: (1) Sc₂ReB₆.

### 3.1.6. Sc-Fe-B

Stepanchikova and Kuz'ma (1981) studied isothermal sections of the Sc-Fe-B phase diagram at 700°C (0-50 at.% B) and at 1000°C (50-100 at.% B). In fig. 26 we corrected



Fig. 26. Sc-Fe-B, isothermal sections at 700°C (0-50 at.% B) and at 1000°C (50-100 at.% B). Ternary compound: (1) ScFeB₄.

the composition of the binary compound, earlier known as  $\sim$ Sc₇Fe, to Sc₂₉Fe₆ (see sect. 2.8). One ternary compound was observed in this system, the data are given in table 14.

#### 3.1.7. Sc-Co-B

The phase equilibria at 800 and 600°C in the Sc–Co–B system have been investigated by Stepanchikova (1979). The isothermal sections (depicted in fig. 27) are corrected for the homogeneity range of the binary compound ScCo₂, which was found to exist from 30 to 34.5 at.% Sc at 800°C (see sect. 2.8). Stepanchikova confirmed two ternary compounds which were known earlier and synthesized two new ternaries, namely ScCo₄B₄ and ScCoB₄ (table 14).



Fig. 27. Sc-Co-B, isothermal sections at 800°C (0-33.3 at.% Sc) and at 600°C (33.3-100 at.% Sc). Ternary compounds: (1) Sc₂Co₂₁B₆; (2) ScCo₄B₄; (3) ScCo₃B₂; (4) ScCoB₄.

### 3.1.8. Sc-Ni-B

The isothermal section of Sc–Ni–B at 800°C has been established by Stepanchikova and Kuz'ma (1981). The occurrence of an earlier known ternary compound,  $Sc_3Ni_{20}B_6$  has been confirmed and four new ternary borides have been added (table 14). Zavalii et al. (1988) used a single crystal investigation for the refinement of the composition of the ~ScNi₄B₄ compound reported by Stepanchikova and Kuz'ma. According to the results of



Fig. 28. Sc-Ni-B, isothermal section at 800°C. Ternary compounds: (1)  $Sc_{3-4}Ni_{20-19}B_6$ ; (2)  $Sc_4Ni_{29}B_{10}$ ; (3)  $\sim Sc_4Ni_{15}B_6$ ; (4)  $ScNiB_4$ ; (5)  $ScNi_3B$ .

Zavalii et al. it is  $Sc_4Ni_{29}B_{10}$ . Figure 28 displays the isothermal section of the Sc–Ni–B phase diagram, based on the data of Stepanchikova and Kuz'ma with corrected data of Zavalii et al. and the recently observed homogeneity range for ScNi₂ at 800°C (see sect. 2.8).

#### 3.1.9. Sc-Ru-B

Ku et al. (1979) investigated part of the Sc–Ru–B phase diagram. Based on an X-ray analysis of the as-cast alloys, these authors observed the occurrence of the following two-phase equilibria: RuB–ScRuB₄, "ScRu₂B₂"–ScRuB₄ and "ScRu₂B₂"–Ru₇B₃, as well as the metastable equilibria of ScRu₄B₄ with ScRuB₄, "ScRu₂B₂", Ru₇B₃ and RuB. The metastable ScRu₄B₄ ternary phase decays during the homogenisation of alloys at temperatures between 800 and 1300°C. Later Rogl (1984a) refined the composition of "ScRu₂B₂" and showed that the actual composition is Sc₂Ru₅B₄. The crystal structure data for all these ternary compounds are given in table 14.

#### 3.1.10. Sc-Rh-B

In the study of the Rh-rich end of the Sc–Rh–B system Holleck (1977) established the existence of the solid solution of boron in the binary compound ScRh₃ at 1300°C: ScRh₃B_{0-0.8}(ST AuCu₃, a=3.900-4.075 Å). Evidently that solid solution can reach the composition ScRh₃B (ST CaTiO₃).

# 3.1.11. Sc-M-B (M = Os, Ir)

There are no data yet available concerning the phase equilibria in the Sc–Os–B and Sc–Ir–B systems. Two ternary compounds in the Os system and three ternary compounds with Ir have been synthesized and their crystal structures determined (see table 14). The boron content in the compound  $ScIr_3B_{1-x}$  was not accurately determined because of the loss of some of the components during arc melting.

# 3.2. Sc-M-Al ternary systems

## 3.2.1. *Sc–Li–Al*

Berezina et al. (1986) investigated binary Al–(2.75-3) wt.% Li specimens alloyed with 0.1 to 0.7 wt.% Sc, which have been quenched from 580°C and subsequently homogenized at 175°C for 16 h. Their data indicate that a three-phase region Al+Al₃Li + Al₃Sc exists in the ternary system at 175°C.

## 3.2.2. Sc-Mg-Al

The part of the Sc–Mg–Al isothermal section (0-33.3 at.% Sc) at 400°C reported by Odinaev et al. (1989) is presented in fig. 29. No ternary compounds were observed. Turkina and Kuzmina (1976) investigated also the phase equilibria at 430°C and two polythermal sections in the Al-rich part of the phase diagram (alloys containing up to 26 wt.% Mg and up to 3 wt.% Sc). Three other quasibinary polythermal sections ScAl₂–Mg, ScAl₂–Mg₂Al₃ and ScAl₂–Mg₁₇Al₁₂ of the eutectic type, have been reported by Odinaev et al. (1991). All of the data are in good agreement with each other.



Fig. 29. Sc-Mg-Al, part of the isothermal section at 400°C (0-33.3 at.% Sc).

386
#### 3.2.3. *Sc–Ca–Al*

Iandelli and Olcese (1985) investigated the alloys of the ScAl₂–CaAl₂ section in the Sc– Ca–Al ternary system. Between 800 and 900°C CaAl₂ (ST MgCu₂) dissolves 0.14 mole fraction of ScAl₂, whereas ScAl₂ (ST MgCu₂) dissolves 0.08 mole fraction of CaAl₂. These limited solid solutions are in two phase equilibria with each other. No ternary compounds were observed.

#### 3.2.4. Sc-Sr-Al

The isothermal section of the Al corner of the Sc–Sr–Al phase diagram at 500°C (fig. 30) has been published by Trubniakova et al. (1987). The same group of scientists (Trubniakova and Ganiev 1989) reported on the polythermal section  $SrAl_4$ – $ScAl_3$ . The section is of eutectic type with a limited mutual solubility of the components. No ternary compounds occur in the investigated part of the system.



Fig. 30. Sc–Sr–Al, part of the isothermal section at 500°C (66.7–100 at.% Al).

# 3.2.5. Sc-Ba-Al

The isothermal section of Sc–Ba–Al at 500°C, which is based on the data of Altynbaev et al. (1987), is presented in fig. 31. The immiscibility gap observed in the binary Sc–Ba system spreads deeply into the ternary system up to 56 at.% Al (dashed line in fig. 31). Six additional polythermal sections of the Sc–Ba–Al phase diagram, namely ScAl₂–BaAl₄, ScAl₂–Ba, ScAl–Ba, ScAl₃–BaAl₄, ScAl₂–BaAl₂, ScAl₂–BaAl have been investigated by the same group (Altynbaev et al., 1990). No ternary compounds were observed.

### 3.2.6. Sc-R-Al (R = La, Ce, Yb)

Iandelli and Olcese (1985) ivestigated the alloys of the sections  $ScAl_2-RAl_2$ . No ternary compounds were found in any of the three systems. At 800–900°C the mutual solubility of scandium in LaAl₂ and lanthanum in ScAl₂ is low. The boundary compositions of these solid solutions are:  $Sc_{0.04}La_{0.96}Al_2$  and  $La_{0.96}Sc_{0.04}Al_2$ .

In as-cast alloys  $ScAl_2$  and  $CeAl_2$  (ST MgCu₂) are completely miscible in each other. The miscibility at 800°C decreases to about 0.15 mole fraction of  $ScAl_2$  in  $CeAl_2$  and about 0.19 mole fraction of  $CeAl_2$  in  $ScAl_2$ .

A continuous series of solid solutions have been observed in the as-cast alloys between isotypic  $ScAl_2$  and  $YbAl_2$ .



Fig. 31. Sc-Ba-Al, isothermal section at 500°C. The dashed line shows the extent of the Sc-Ba liquid immiscibility region.

## 3.2.7. Sc-R-Al (R = Y, Sm, Gd, Tb, Dy, Ho, Er, Tm, Lu)

The phase equilibria at 500°C and 800°C between ScAl₃ and RAl₃ been investigated by Zalutska et al. (1969) (systems with R=Y, Tb, Dy, Ho and Er), Zalutska et al. (1970) (the system with R = Gd), and Zalutska et al. (1974) (systems with R = Sm, Tm and Lu). The terminal binary compounds have different stacking variants of cubic and hexagonal atomic layers: hexagonal,  $\gamma_2$  (ST Ni₃Sn or Mg₃Cd, 100% hexagonal stacking, for the compound GdAl₃), cubic, y₃ (ST AuCu₃, 0% hexagonal stacking, for the compounds ScAl₃, ErAl₃, TmAl₃, LuAl₃) and mixed variants  $\gamma_9$  (ST BaPb₃, 66.7% hexagonal stacking, for the compounds Yal₃, TbAl₃), γ₄ (ST TiNi₃, 50% hexagonal stacking, for the compound DyAl₃) and  $\gamma_{15}$  (ST HoAl₃, 40% hexagonal stacking, for the compounds HoAl₃ and DyAl₃). Isotypic trialuminides are completely miscible in each other: Sc-Er-Al, Sc-Tm-Al and Sc-Lu-Al. In other ternary systems trialuminides form limited solid solutions. ScAl₃ dissolves 10, 3, 3.75, 10.75, 15 and 18 at.% of Y, Sm, Gd, Tb, Dy and Ho, respectively. The solubility of Sc is 3.25, 2.5, 0.5, 2.5, 7.5 and 5.5 at.% in YAl₃, SmAl₃, GdAl₃, TbAl₃, DyAl₃ (in both polymorphic modifications  $\gamma_4$  and  $\gamma_{15}$ ) and HoAl₃, respectively. The values of the lattice spacings of these solid solutions and figures of parts of the isothermal sections of the phase diagrams of these systems are available in the original papers and (except for the systems with Sm, Tm and Lu) in the review by Gschneidner (1975). Ternary compounds isotypic with TiNi₃ ( $\gamma_4$ ) occur only in the Sc-Y-Al and Sc-Tb-Al systems. Their lattice spacings are presented in table 15. Visible differences between the phase equilibria occurring at 500 and 800°C have not been observed.

Compound	Structure type	Latt	ice parame	ters	Reference
	or symmetry	<i>a</i> (Å)	b (Å)	c (Å)	
$Sc_{0.18-0.50}Y_{0.82-0.50}Al_3$	TiNi ₃	6.077– 6.053		9.508– 9.480	Zalutska et al. (1969)
$Sc_{0.15-0.45}Tb_{0.85-0.55}Al_{3}$	TiNi ₃	6.084– 6.060		9.526– 9.480	Zalutska et al. (1969)
$ScFe_{4.0-7.1}Al_{8.0-4.9}$	ThMn ₁₂	8.70– 8.68		4.81– 4.77	Zarechnyuk et al. (1970)
ScFe _{0.30-1.35} Al _{1.70-0.65}	MgZn ₂	5.301– 5.108		8.587– 8.319	Zarechnyuk et al. (1970)
$\sim$ Sc ₆ Co ₈ Al ₁₅	$Mg_6Cu_{16}Si_7$	12.09			Markiv and Burnashova (1969), Markiv and Storozhenko (1973)
ScCoAl	MgZn ₂	5.12		8.20	Teslyuk and Protasov (1965a)
Sc ₂ Co ₃ Al ₉	Y ₂ Co ₃ Ga ₉	12.57	7.337	9.216	Markiv and Belyavina (1987a)
~ScNiAl ₄	?				Zarechnyuk and Rykhal (1977)
$\sim$ Sc ₆ Ni ₇ Al ₁₆	$Mg_6Cu_{16}\mathrm{Si}_7$	12.16			Markiv and Burnashova (1969), Markiv and Storozhenko (1973)
~ScNiAl ₂	?				Zarechnyuk and Rykhal (1977)
$ScNi_{1-0.6}Al_{1-1.4}$	MgZn ₂	5.12ª		8.20	Teslyuk and Protasov (1965a), Zarechnyuk and Rykhal (1977)
ScNi ₂ Al	MnCu ₂ Al	5.990			Dwight and Kimball (1987), Goebel and Rosen (1968)
~ScRu _{2.3} Al _{3.9}	?				Raevskaya and Sokolovskaya (1979)
~ScRu _{0.8} Al _{3.7}	?				Raevskaya and Sokolovskaya (1979)
$Sc_6Ru_7Al_{16}$	Mg ₆ Cu ₁₆ Si ₇	12.38			Markiv and Storozhenko (1973)
~ScRuAl ₂	MnCuAl ₂	6.175			Raevskaya and Sokolovskaya (1979)
~ScRu _{1.1-1.04} Al _{0.9-0.96}	?				Raevskaya and Sokolovskaya (1979)
$\sim$ ScRu _{0.9-0.8} Al _{1.1-1.2}	?				Raevskaya and Sokolovskaya (1979)
$ScRu_{0.68-0.26}Al_{1.32-1.74}$	MgZn ₂	5.25– 5.33		8.46– 8.58	Raevskaya and Sokolovskaya (1979), Karatygina et al. (1974b)
Sc. Rh-Al.	Mg.Cu.Sia	12.34			Markiv and Storozhenko (1973)
~ScPdi - Alcar	?				Karatyoina et al. (1974b)
~ScPdAl	?				Karatyoina et al. $(1974b)$
ScPdo as a - Al	MgZna	5 51b		8 62	Karatygina et al. (1974b)
Sc. Pd- A1.	Ma Cu Si	12 34		0.02	Markiv and Storozbarka (1072)
ScPd. 41	$M_{\rm pCu} = A_1$	6 3 27			Dwight and Kimball (1987)
Ser u ₂ AI	MINU u2/M	0.327			Dwight and Kiniball (1987)

Table 15 Ternary intermetallic compounds in the Sc-M-Al systems

389

Table 15, commacu							
Compound	Structure type	Latt	ice parame	ters	Reference		
	or symmetry	<i>a</i> (Å)	b (Å)	<i>c</i> (Å)			
Sc ₆ Os ₇ Al ₁₆	Mg ₆ Cu ₁₆ Si ₇	12.41			Markiv and Storozhenko (1973)		
$Sc_6Ir_7Al_{16}$	$Mg_6Cu_{16}Si_7$	12.31			Markiv and Storozhenko (1973)		
$ScCu_{4.0-6.15}Al_{8.0-5.85}$	ThMn ₁₂	8.656– 8.570		5.000– 4.947	Kotur (1989), Prevarskii et al. (1976)		
~ScCu ₄ Al ₃	?				Prevarskii et al. (1976)		
Sc ₂ Cu _{7.5} Al _{3.5}	hex	4.913		8.420	Gladyshevsky et al. (1992)		
Sc ₃ Cu ₉ Al ₇	orthorh	21.88	8.292	8.344	Gladyshevsky et al. (1992)		
Sc ₆ Cu _{16.4} Al _{13.9}	hex	8.493		8.870	Gladyshevsky et al. (1992)		
$ScCu_2Al_2$	orthorh	8.46	8.88	14.65	Gladyshevsky et al. (1992)		
ScCu ₂ Al	MnCu ₂ Al	6.199			Dwight and Kimball (1987)		
		6.203			Nakonechna and Shpyrka (1996)		
~ScCu _{1.4} Al _{0.6}	?				Prevarskii et al. (1976)		
ScCuA1	MgZn ₂	5.04		8.24	Teslyuk and Protasov (1965b)		
$ScCu_{0.6}Al_{1.4}$	MgNi ₂	5.252		17.113	Gladyshevsky et al. (1992), Nakonechna and Shpyrka (1996)		
ScAg ₂ Al	MnCu ₂ Al	6.564			Dwight and Kimball (1987)		
ScAu ₂ Al	$MnCu_2Al$	6.536			Dwight and Kimball (1987)		

Table 15, continued

^a For the composition ScNiAl.

^b For an unknown composition.

## 3.2.8. Sc-M-Al (M = Ti, Zr, Hf)

Parts of the isothermal sections at 500°C of the Sc-M-Al (M = Ti, Zr, Hf) phase diagrams (66.7–100 at.% Al) reported by Kotur et al. (1989b) are presented in fig. 32. No ternary compounds were found. Binary scandium aluminides dissolve different quantities (in at.%) of the third element: ScAl₃ – 6 Ti, 10 Zr, 15 Hf; ScAl₂ – 5 Ti, 8 Zr, 13 Hf. The solubility of Sc in the aluminides of the 4A-elements does not exceed 5 at.%. These data are in good agreement with the data of Toropova et al. (1990) who reported on the phase equilibria in the Sc–Zr–Al system at 600°C. ScAl₃ and ZrAl₃ dissolve 10 at.% Zr and



Fig. 32. (a) Sc-Ti-Al, (b) Sc-Zr-Al, and (c) Sc-Hf-Al parts of the isothermal sections at 500°C (66.7–100 at.% Al).

5 at.% Sc, respectively. A two-phase region  $(Sc_{1-x}Zr_xAl_3 + Zr_{1-y}Sc_yAl_3)$  and a threephase region  $(Al + Sc_{1-x}Zr_xAl_3 + Zr_{1-y}Sc_yAl_3)$  have been confirmed too.

### 3.2.9. Sc-Nb-Al

Shamrai et al. (1988) reported on the phase equilibria in the Sc–Nb–Al system at 200–800°C (fig. 33). Their data, which indicate a solubility of about 1 at.% Al in  $\alpha$ Sc, are in disagreement with the data of Naumkin et al. (1965) who report a solubility of about 4 at.% Al. There are no ternary compounds in the system. Binary aluminides dissolve less than 1 at.% of the third component.



#### 3.2.10. Sc-Cr-Al

Part of the Sc–Cr–Al isothermal section at 500°C (30–100 at.% Al), which is shown in fig. 34, has been investigated by Sokolovskaya et al. (1989). No ternary compounds were found. ScAl₃ dissolves up to 11 at.% Cr. Other binary aluminides also dissolve large amounts of the third element, but there are no data available about lattice parameters of these solid solutions.

#### 3.2.11. Sc-Mo-Al

Only a little information concerning the Sc-Mo-Al system is available. Cheldieva et al. (1989) investigated an isothermal section of the Al-rich part of the phase diagram at 500°C, and the polythermal sections between aluminides ScAl₃ and MoAl₁₂ and from the Al corner along the atomic ratio Mo:Sc=2:1 line, however no figure was given.



Fig. 34. Sc--Cr-Al, part of the isothermal section at 500°C (30-100 at.% Al).

They found that the binary scandium and molybdenum aluminides dissolve very small quantities of a third component. Ternary compounds have not been observed.

#### 3.2.12. Sc-Mn-Al

Drits et al. (1984) reported about investigations of the Al-rich parts (96–100 at.% Al) of the Sc–Mn–Al isothermal sections at 500 and 600°C, and on the polythermal sections (Al+0.8 wt.% Sc)–Mn and Sc–(Al+0.8 wt.% Mn) in the regions 0–2.8 wt.% Mn and Sc, respectively. A three-phase area ( $\alpha$  solid solution (Al)+ScAl₃+MnAl₆) was found; however, no ternary compounds have been observed. Al dissolves less than 0.2 at.% Sc and 0.3 at.% Mn. Scandium appreciably decreases the solubility of manganese in aluminium.

## 3.2.13. Sc-Fe-Al

Part of the Sc–Fe–Al isothermal section (0–33.3 at.% Sc) at 500°C has been investigated by Zarechnyuk et al. (1970). This isothermal section is included in the review of Gladyshevsky et al. (1990). There are two ternary compounds with wide homogeneity ranges observed in the investigated part of the system (table 15). It is interesting to note that two isostructural compounds, ScFe₂ and ScFe_{1.35–0.30}Al_{0.65–1.70} (ST MgZn₂), are in two-phase equilibrium with each other. Alloys of the ScAl₂–ScFe₂ section at 800°C were also examined by Dwight et al. (1975). From the figure shown there it follows that ScAl₂ dissolves up to 6 at.% Fe whereas ScFe₂ dissolves only about 1 at.% Al. Dwight et al. also observed two ternary compounds ScFe_{1.96–1.4}Al_{0.04–0.6} (ST MgCu₂) and ScFe_{1.37–0.2}Al_{0.63–1.8} (ST MgZn₂) along the ScFe₂–ScAl₂ pseudo-binary line. These data are in agreement with the results of Sankar and Wallace (1976) who investigated the alloys of this section too. In addition Sankar and Wallace reported the composition ranges for these two ternary compounds at 1000°C:  $ScFe_{1.87-1.42}Al_{0.13-0.88}$  (ST MgCu₂) and  $ScFe_{1.31-0.15}Al_{0.69-1.85}$  (ST MgZn₂). However, no lattice spacings of these compounds are given in the papers of Dwight et al. (1975) and Sankar and Wallace (1976).

### 3.2.14. Sc-Co-Al

Three ternary compounds have been synthesized and their crystal structures were determined (see table 15). Phase equilibria in this system have not been completely investigated.

## 3.2.15. Sc-Ni-Al

Parts of two isothermal sections of the Sc–Ni–Al system have been studied by Goebel and Rosen (1968) (Ni corner at 1000°C) and Zarechnyuk and Rykhal (1977) (0–33.3 at.% Sc at 600°C). Their figures are presented in the review of Gladyshevsky et al. (1990). The data of Goebel and Rosen need to be completed in the region close to Sc₂Ni₇ compound. Goebel and Rosen confirmed the ScNiAl ternary compound known from an earlier investigation by Teslyuk and Protasov (1965a) (ST MgZn₂, a=5.12, c=8.12 Å), and they observed a new one, ScNi₂Al (ST MnCu₂Al, a=6.02 Å). Zarechnyuk and Rykhal synthesized the two ternary compounds ~ ScNiAl₄, ~ ScNiAl₂ and confirmed an extended homogeneity range for ScNiAl (see table 15). There are also the data of Markiv and Burnashova (1969) and Markiv and Storozhenko (1973) who reported an aluminide with the following composition ~ Sc₆Ni₇Al₁₆ (ST Th₆Mn₂₃ or Mg₆Cu₁₆Si₇, a=12.16 Å). Maybe this compound and the compound ~ ScNiAl₂ identified by Zarechnyuk and Rykhal are the same.

#### 3.2.16. Sc-Ru-Al

Karatygina et al. (1974a) investigated part of the Sc–Ru–Al isothermal section at 600°C. One ternary compound ScRu_{0.92–0.32}Al_{1.08–1.68} with the MgZn₂ structure type was found (a=5.27, c=8.57 Å for the composition ScRu_{0.5}Al_{1.5}). A continuous series of solid solutions occur between the isotypic binary compounds ScRu and ScAl (ST CsCl) whereas a two-phase region exists between ScRu and RuAl (ST CsCl). In our opinion these data need additional verification if one takes into account the later data of Schuster and Bauer (1985) who observed the CrB structure type for pure ScAl (see sect. 2.12).

Karatygina et al. (1974b) reported the phase equilibria at 800°C in the region 0–85 at.% Al; later the same scientific group (Raevskaya and Sokolovskaya 1979) refined their earlier data. In addition to the earlier reported ternary compound, five other compounds were observed (see table 15). Of these, the crystal structure of ~ScRuAl₂ was determined to be of the MnCu₂Al type. Markiv and Storozhenko (1973) also synthesized a cubic ternary compound with a similar composition, namely Sc₆Ru₇Al₁₆ crystallising in the Mg₆Cu₁₆Si₇ structure type. To clarify these contradictory data additional work needs to be done. In our opinion, the data of Markiv and Storozhenko seem to be more reliable,

which is based on analysis of the data of related systems. Figures of the two isothermal sections mentioned above can be found in the review of Gladyshevsky et al. (1990).

## 3.2.17. Sc-M-Al (M = Rh, Os, Ir, Pt)

There is information in the literature about a ternary compound of the composition  $Sc_6M_7Al_{16}$  in each of the Sc-M-Al (M=Rh, Os, Ir) ternary systems. Their lattice parameters are presented in table 15. Phase equilibria were not investigated. According to the investigation of Markiv and Storozhenko (1973) the compound of the 6:7:16 stoichiometry does not occur in the Sc-Pt-Al ternary system.

## 3.2.18. Sc-Pd-Al

Part of the Sc–Pd–Al isothermal section at 800°C shown in fig. 35 is based mainly on the data of Karatygina et al. (1974b). An extended solid solution is formed on the basis of the ScPd binary compound where the atoms of the initial components can substitute by each other in the structure. The binary compounds  $Sc_2Pd$  and  $Sc_4Pd$  dissolve about 13 and 8 at.% Al, whereas  $ScAl_2$  dissolves about 7 at.% Pd. Karatygina et al. synthesized three ternary compounds (see fig. 35); the existence of two other ternary compounds, namely  $Sc_6Pd_7Al_{16}$  and  $ScPd_2Al$  was reported by other authors (see table 15). The composition of the latter one occurs within the homogeneity range of the (Sc, Al)Pd solid solution observed by Karatygina et al. These conflicting data need additional refinement.



Fig. 35. Sc-Pd-A1, part of the isothermal section at 800°C (0-80 at.% Al). Ternary compounds: (1) ~ScPd_{1.73}Al_{6.36}; (2) ~ScPdAl₃; (3) ScPd_{0.30-0.57}Al_{1.70-1.43}.



Fig. 36. Sc-Cu-Al, part of the isothermal section at 500°C (0-33.3 at.% Sc). Ternary compounds: (1)  $ScCu_{4,0-6,15}Al_{8,0-5,85}$ ; (2)  $\sim ScCu_4Al_3$ ; (3)  $Sc_2Cu_{7,7}Al_{3,5}$ ; (4)  $Sc_3Cu_9Al_{17}$ ; (5)  $Sc_6Cu_{16,4}Al_{13,9}$ ; (6)  $ScCu_2Al_2$ ; (7)  $ScCu_2Al$ ; (8)  $\sim ScCu_{1,4}Al_{0,6}$ ; (9) ScCuAl; (10)  $ScCu_{0,6}Al_{1,4}$ .

### 3.2.19. Sc-Cu-Al

Many investigations of the Sc-Cu-Al system have been reported. The phase equilibria in the range 0-33.3 at.% Sc at 500°C were first reported in the paper of Prevarskii et al. (1976). Nine ternary compounds were obtained: (1)  $ScCu_{4-6.6}Al_{8-5.4}$  (ST ThMn₁₂, a = 8.66 - 8.63, c = 4.43 - 5.10 Å), (2) ~ScCu₄Al₃, (3) ~ScCu_{4.3}Al_{1.3}, (4) ~ScCu_{2.6}Al_{2.3}, (5) ~ScCu₃Al₂, (6) ~ScCu₂Al₂, (7) ScCu₂Al (8) ~ScCu_{1.4}Al_{0.6}and (9) ScCuAl. Two of them, (9) ScCuAl (ST MgZn₂) and (7) ScCu₂Al (ST CsCl), were synthesized earlier (Teslyuk and Protasov 1965b). Toropova et al. (1989) and Kharakterova (1991) reinvestigated the Al corner of the system at 450 and 500°C. They did not confirm the two phase equilibria between CuAl₂ and ScAl₃, however they established the two phase equilibrium between Al and ternary compound (1). Kotur (1989) refined the homogeneity range and the lattice parameters of compound (1) (see table 15). Kharakterova determined the solubility of Sc and Cu in solid Al (about 1.5 at.% Cu and about 0.1 at.% Sc at 500°C). Gladyshevsky et al. (1992), who conducted a crystal structure investigation of four of the ternary compounds reported earlier by Prevarskii et al., refined their compositions to (3)  $Sc_2Cu_{7,5}Al_{3,5}$ , (4)  $Sc_3Cu_9Al_7$ , (5)  $Sc_6Cu_{16,4}Al_{13,9}$ , (6)  $ScCu_2Al_2$ , discovered an additional ternary compound (10)  $ScCu_{0.6}Al_{1.4}$ , and determined the crystal structures of all five compositions. These data are presented in table 15. The revised isothermal section at 500°C based on the above mentioned papers is shown in fig. 36. There is some controversy concerning the published data for the crystal structure of the ScCu₂Al compound. Teslyuk and Protasov (1965b) investigated an as-cast sample and a sample homogenized at 800°C of the ScCu₂Al composition, and they obtained identical X-ray patterns for both samples. Between the two possible structure types (MnCu₂Al and CsCl) they preferred the latter one (a=3.10 Å), however, there were two weak extra lines which could be indexed assuming MnCu₂Al type. The MnCu₂Al structure for this phase was reported by Dwight and Kimball (1987). Recently Nakonechna and Shpyrka (1996) confirmed the MnCu₂Al type structure by single-crystal investigation (see table 15).

#### 3.2.20. Sc - M - Al (M = Ag, Au)

Dwight and Kimball (1987) prepared the Heusler phases  $ScAg_2Al$  and  $ScAu_2Al$  and determined their lattice parameters (see table 15). Data about phase equilibria in these systems are not available in the literature.

#### 3.3. Sc-M-Ga ternary systems

### 3.3.1. Sc-Y-Ga

Markiv et al. (1981) reported on the isothermal section of the Sc–Y–Ga system at 800°C in the range 0–75 at.% Sc (fig. 37). The gallides  $ScGa_2$  and  $ScGa_3$  dissolve about 9 at.% Y,  $Sc_3Ga_5$  (in the original paper " $Sc_2Ga_3$ ") dissolves about 36 at.% Y. One ternary compound with an extended homogeneity range along 44.5 at.% Ga isoconcentrate occurs in the system, however its crystal structure is unknown (table 16). Markiv et al. found the solubility of gallium in solid scandium at 800°C to be about 1 at.%. This value differs from those (between about 4 and 6 at.% Ga) reported in other papers on the Sc–M–Ga



Fig. 37. Sc-Y-Ga, part of the isothermal section at 800°C (0–75 at.% Sc). Ternary compound: (1)  $Sc_{1.26-3.82}Y_{3.74-1.18}Ga_4$ .

Compound	Structure type	Latt	ice parame	ters	Reference
	or symmetry	a (Å)	b (Å)	c (Å)	
Sc _{1,26-3.82} Y _{3,74-1,18} Ga ₄	?				Markiv et al. (1981)
Sc1-4Ti4-1Ga3	?				Gavrilenko and Markiv (1978a)
ScTi ₂ Ga ₄	YbMo ₂ Al ₄	6.578		5.475	Grin' et al. (1980), Gavrilenko and Markiv (1978a)
$Sc_{6.8-9.4}Ti_{4.2-1.8}Ga_{10}$	$\mathrm{Ho}_{11}\mathrm{Ge}_{10}$	10.23– 10.343		14.68 14.98	Markiv et al. (1989), Gavrilenko and Markiv (1978a)
$Sc_{3.2-4.7}Zr_{7.8-6.3}Ga_{10}$	$\mathrm{Ho}_{11}\mathrm{Ge}_{10}$	10.401– 10.399		14.98– 15.01	Markiv et al. (1989), Markiv et al. (1979)
$Sc_{0.2}Hf_{0.8}Ga_3$	ZrAl ₃	3.948		17.35	Markiv and Belyavina (1981)
Sc _{0.2-0.9} Hf _{0.8-0.1} Ga	αΜοΒ	3.851ª		20.27	Markiv and Belyavina (1981)
$ScV_2Ga_4$	YbMo ₂ Al ₄	6.482		5.216	Grin' et al. (1980)
~ScNbGa₄	?				Savitskii et al. (1980a)
$Sc_{8.4-9.4}Nb_{2.6-1.6}Ga_{10}$	$\mathrm{Ho}_{11}\mathrm{Ge}_{10}$	10.378– 10.385		15.07 15.24	Markiv et al. (1989)
~Sc ₄ Cr ₄ Ga ₃	?				Gavrilenko and Markiv (1978a)
$Sc_3Mn_2Ga_6$	$\mathrm{Sc_3Mn_2Ga_6}$	8.051	8.533	10.607	Markiv and Belyavina (1987b), Gavrilenko and Markiv (1978b)
$ScMn_{0.33}Ga_{1.67}$	$CaIn_2$	4.354		6.418	<i>Kuzmenko et al. (1983),</i> Gavrilenko and Markiv (1978b)
$Sc_{8.5}Mn_{1.2}Ga$	$Sc_{8.5}Mn_{1.2}Ga$	14.284	14.284	14.840	Markiv and Belyavina (1989a), Gavrilenko and Markiv (1978b)
$ScFe_{6-4.73}Ga_{6-7.27}$	$ScFe_6Ga_6$	8.431– 8.507	8.613– 8.585	5.009– 5.040	Belyavina and Markiv (1982a)
Sc ₂ Fe _{8.83} Ga _{8.17}	$Th_2Zn_{17}$	8.695		12.641	Belyavina and Markiv (1982a)
ScFeGa₅	HoCoGa₅	4.145		6.623	Belyavina and Markiv (1980b), Gavrilenko and Markiv (1978b)
$Sc_3Fe_2Ga_6$	$Sc_3Mn_2Ga_6$	8.081	8.425	10.457	<i>Markiv and Belyavina (1987b)</i> , Gavrilenko and Markiv (1978b)
$ScFe_{1.82-1.44}Ga_{0.18-0.56}$	MgCu ₂	7.03– 7.15			Gavrilenko and Markiv (1978b)
$ScFe_{1.37-0.71}Ga_{0.63-1.29}$	MgZn ₂	5.053 5.156		8.287– 8.386	Gavrilenko and Markiv (1978b)
ScFe _{0.33} Ga _{1.67}	$KHg_2$	4.304	6.498	7.433	Kuzmenko et al. (1983)
ScFe _{0.14} Ga _{1.86}	CaIn ₂	4.294		6.578	Kuzmenko et al. (1983), Gavrilenko and Markiv (1978b)
Sc _{8.5} Fe _{1.2} Ga	$Sc_{8.5}Mn_{1.2}Ga$	14.213	14.213	14.785	<i>Markiv and Belyavina (1989a)</i> , Gavrilenko and Markiv (1978b)
ScFe _{4.73} Ga _{7.27}	ThMn ₁₂	8.567		5.060	Belyavina and Markiv (1982a)
ScCo _{5.8} Ga _{6.2}	ThMn ₁₂	8.345		5.048	Belyavina and Markiv (1982a), Gavrilenko and Markiv (1979)

 Table 16

 Ternary intermetallic compounds in the Sc-M-Ga systems

		Tuore	10, 00,000	icu	
Compound	Structure type	Lattice parameters			Reference
	or symmetry	a (Å)	b (Å)	c (Å)	
ScCo _{4.5} Ga _{4.1}	TbCu ₇	5.007		4.044	Markiv and Belyavina (1987a), Gavrilenko and Markiv (1979)
Sc ₂ Co ₃ Ga ₉	$Y_2Co_3Ga_9$	12.58	7.272	9.216	<i>Markiv and Belyavina (1987a)</i> , Gavrilenko and Markiv (1979)
ScCoGa ₅	HoCoGa ₅	4.135		6.642	<i>Belyavina and Markiv (1980b),</i> Gavrilenko and Markiv (1979)
~Sc ₁₇ Co ₆₄₋₆₂ Ga ₁₉₋₂₁	?				Gavrilenko and Markiv (1979)
Sc ₂ Co ₇ Ga ₄	$Mg_2Zn_{11}$	8.074			<i>Markiv and Belyavina (1987a),</i> Gavrilenko and Markiv (1979)
Sc ₂ CoGa ₈	Ho ₂ CoGa ₈	4.126		10.68	Belyavina and Markiv (1980b), Gavrilenko and Markiv (1979)
Sc ₆ Co _{7.2-6.3} Ga _{15.8-16.7}	$\mathrm{Th}_{6}\mathrm{Mn}_{23}$	12.14 ^b			Markiv and Burnashova (1969), Gavrilenko and Markiv (1979)
~Sc ₂₂ Co ₆₃₋₆₀ Ga ₁₅₋₁₈	?				Gavrilenko and Markiv (1979)
~Sc ₂₂ Co ₅₃₋₄₉ Ga ₂₅₋₂₉	?				Gavrilenko and Markiv (1979)
ScCo _{1.2} Ga _{1.8}	$ScCo_{1.2}Ga_{1.8}$	12.255		8.223	<i>Belyavina and Markiv (1989),</i> Gavrilenko and Markiv (1979)
Sc29-34Co48-24Ga29-42	$MgZn_2$	5.021 <u>°</u>		8.137-	Gavrilenko and Markiv (1979)
		5.170		8.175	
ScCo _{0.35} Ga _{1.65}	TiFeSi	8.070	11.46	6.618	Belyavina and Markiv (1982b), Gavrilenko and Markiv (1979)
~Sc ₃₇ Co ₁₄ Ga ₄₉	?				Gavrilenko and Markiv (1979)
Sc ₅ Co _{0.925} Ga _{0.925}	$\mathrm{Sc}_5\mathrm{Ni}_{1-x}\mathrm{Ga}_{1-x}$	8.769		8.639	Markiv and Belyavina (1989b), Gavrilenko and Markiv (1979)
ScCo _{0.5} Ga _{1.5}	$KHg_2$	4.267	6,419	7.400	Kuzmenko et al. (1983)
ScCo _{0.14} Ga _{1.86}	CaIn ₂	4.283		6.594	Kuzmenko et al. (1983)
ScNiGa₅	HoCoGa₅	4.140		6.477	Belyavina and Markiv (1980b), Gavrilenko and Markiv (1979)
ScNi _{2.36} Ga _{3.64}	$Ru_3Be_{17}$	13.440			Markiv and Belyavina (1990b), Gavrilenko and Markiv (1979)
$Sc_2Ni_{7-5.5}Ga_{4-5.5}$	$Hf_2Ni_{6.5}Ga_{4.5}$	17.800 17.997		8.197– 8.288	Markiv and Belyavina (1990a), Gavrilenko and Markiv (1979)
~Sc ₁₇ Ni ₆₄₋₅₉ Ga ₁₉₋₂₄	?				Gavrilenko and Markiv (1979)
$\sim$ Sc ₂₂ Ni ₅₈ Ga ₂₀	?				Gavrilenko and Markiv (1979)
~Sc ₂₃ Ni ₆₁ Ga ₁₆	?				Gavrilenko and Markiv (1979)
Sc ₂ NiGa ₈	Ho ₂ CoGa ₈	4.127		10.56	Belyavina and Markiv (1980b), Gavrilenko and Markiv (1979)
ScNi ₂ Ga	MnCu ₂ Al	6.001			Gavrilenko and Markiv (1979)
ScNi _{1.2} Ga _{1.8}	$ScCo_{1.2}Ga_{1.8}$	12.217		8.155	Belyavina and Markiv (1989), Gavrilenko and Markiv (1979)

Table 16, continued

			,		
Compound	Structure type	Latt	ice paramet	ers	Reference
	or symmetry	a (Å)	b (Å)	<i>c</i> (Å)	
ScNiGa ₂	MgCuAl ₂	4.037	9.552	6.467	Markiv and Belyavina (1983), Gavrilenko and Markiv (1979)
Sc30-36Ni55-39Ga15-25	MgZn ₂	5.054 ^d		8.002	Gavrilenko and Markiv (1979)
ScNi _{0.35} Ga _{1.65}	TiFeSi	8.042	11.44	6.602	Belyavina and Markiv (1982b), Gavrilenko and Markiv (1979)
$ScNi_{1-0.67}Ga_{1-1.33}$	KHg ₂	4.166– 4.210	6.309– 6.419	7.216– 7.291	Kuzmenko et al. (1983)
ScNiGa	TiNiSi	6.309	4.166	7.216	Kuzmenko et al. (1983)
ScNi _{0.14} Ga _{1.86}	CaIn ₂	4.283		6.587	Kuzmenko et al. (1983)
$Sc_5Ni_{0.963}Ga_{0.963}$	$\mathrm{Sc}_{5}\mathrm{Ni}_{1-x}\mathrm{Ga}_{1-x}$	8.819		8.600	<i>Markiv and Belyavina (1989b)</i> , Gavrilenko and Markiv (1979)
$Sc_6Ru_7Ga_{16}$	$Mg_6Cu_{16}Si_7$	12.44			Markiv and Storozhenko (1973)
$Sc_6Rh_7Ga_{16}$	$Mg_6Cu_{16}Si_7$	12.38			Markiv and Storozhenko (1973)
ScPd ₂ Ga	MnCu ₂ Al	6.346			Dwight and Kimball (1987)
ScPdGa	TiNiSi	6.281	4.3582	7.5520	Hovestreydt et al. (1982)
Sc ₆ Os ₇ Ga ₁₆	$Mg_6Cu_{16}Si_7$	12.49			Markiv and Storozhenko (1973)
$Sc_6Ir_7Ga_{16}$	$Mg_6Cu_{16}Si_7$	12.43			Markiv and Storozhenko (1973)
ScPtGa	TiNiSi	6.454	4.342	7.479	Hovestreydt et al. (1982)
$ScCu_{5.49-4.85}Ga_{6.51-7.15}$	ThMn ₁₂	8.62°		4.78	Gavrilenko and Markiv (1979)
$ScCu_{3.7}Ga_{2.3}$	$\operatorname{Ru}_3\operatorname{Be}_{17}$	13.545			Markiv and Belyavina (1990b), Gavrilenko and Markiv (1979)
~ScCu _{3.6} Ga _{1.4}	?				Gavrilenko and Markiv (1979)
~ScCu _{3.2} Ga _{1.6}	?				Gavrilenko and Markiv (1979)
$Sc_{14}Cu_{37}Ga_{14}$	$\mathrm{Gd}_{14}\mathrm{Ag}_{51}$	11.438		8.352	<i>Markiv et al. (1984),</i> Gavrilenko and Markiv (1979)
ScCu ₂ Ga	MnCu ₂ Al	6.158			Gavrilenko and Markiv (1979)
$ScCu_{0.77-0.26}Ga_{1.23-1.74}$	CaIn ₂	4.248 ^f		6.588	Gavrilenko and Markiv (1979), Markiv et al. (1984)
$ScCu_{1.40-0.86}Ga_{0.60-1.14}$	$\mathrm{KHg}_2$	4.229 ^g	6.450	7.325	Markiv et al. (1984)

Table	16.	continued
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^a For the composition  $Sc_{0.34}Hf_{0.66}Ga$ . ^b For the composition  $Sc_6Co_7Ga_{16}$ . ^c For the composition  $Sc_{33}Co_{38-25}Ga_{29-42}$ . ^d For the composition  $Sc_{33,3}Ni_{43,7}Ga_{23}$ .

^e for the composition ScCu_{5.5}Ga_{6.5}. ^f For the composition ScCu_{0.26}Ga_{1.74}. ^g For the composition ScCu_{0.95}Ga_{1.05}.

system (see figs. 38–46). This is an additional reason for a reinvestigation of the Sc–Ga binary system which we mentioned in sect. 2.12. Complete miscibility between  $Sc_5Ga_3$  and  $Y_5Ga_3$  is observed (fig. 37).

## 3.3.2. Sc-Ti-Ga

The Sc–Ti–Ga isothermal section at 800°C (0–75 at.% Ga) has been investigated by Gavrilenko and Markiv (1978a); three ternary compounds were observed. Markiv et al. (1989) determined the solubility of titanium in Sc₅Ga₄ (5 at.%) together with the composition and the crystal structure of another ternary compound, reported in the original paper as "Sc_{2–2.37}TiGa_{3–2.63}" [compound (3) in the modified isothermal section presented in fig. 38]. The characteristic data of the ternary compounds are given in table 16.



Fig. 38. Sc-Ti-Ga, part of the isothermal section at 800°C (0-75 at.% Sc). Ternary compounds: (1)  $Sc_{1-4}Ti_{4-1}Ga_3$ ; (2)  $ScTi_2Ga_4$ ; (3)  $Sc_{6.8-9.4}Ti_{4.2-1.6}Ga_{10}$ .

#### 3.3.3. Sc-Zr-Ga

The revised isothermal section of the Sc–Zr–Ga system at 800°C (0–75 at.% Ga) presented in fig. 39 is based mainly on the data of Markiv et al. (1979). They observed one ternary compound "Sc_{1.8–2.7}Zr_{3.2–2.3}Ga₄". Its composition and crystal structure, as well as the solubility of zirconium in Sc₅Ga₄ (10 at.%), were determined by Markiv et al. (1989) (see table 16). The other binary gallides Sc₃Ga₅, Zr₃Ga₂ and ZrGa dissolve about 15 at.% Zr, about 12 and 46 at.% Sc, respectively (see fig. 39). Zr₅Ga₃–Sc₅Ga₃ form a continuous series of solid solutions between the two binary end members.



Fig. 39. Sc–Zr–Ga, part of the isothermal section at 800°C (0–75 at.% Sc). Ternary compound: (1)  $Sc_{3.2-4.7}Zr_{7.8-6.3}Ga_{10}$ .

### 3.3.4. Sc-Hf-Ga

Investigations of the Sc-Hf–Ga phase equilibria at 800°C in the range 0–63 at.% Ga have been reported by Belyavina et al. (1981), and by Markiv and Belyavina (1981) in the range 0–75 at.% Ga. The data of both papers are identical in the concentration range 0–50 at.% Ga. Sc₅Ga₄ dissolves up to 15 at.% Hf. The hafnium gallide "Hf₅Ga₄" dissolves up to 20 at.% Sc. Later the same scientific group (Markiv et al., 1989) refined the composition of this compound to Hf₁₁Ga₁₀ and found its solubility of Sc to be 30 at.%. Other binary gallides, such as Sc₅Ga₃ (in the original paper "Sc₂Ga₃") and HfGa₂ also dissolve rather large amounts of the third component: 30 at.% Hf and 10 at.% Sc, respectively. Two ternary compounds have been synthesized by Markiv and Belyavina who also established their crystal structure (see table 16). Sc₅Ga₃ and Hf₅Ga₃ mutually dissolve 100% of each other. The revised isothermal section at 800°C is shown in fig. 40.

### 3.3.5. Sc-V-Ga

Savitskii et al. (1978b) studied the Sc–V–Ga phase equilibria at 800°C. The figure of the isothermal section is available in the review of Gladyshevsky et al. (1990). One ternary compound ScV₂Ga₄ occurs in this system, its crystal structure was determined by Grin' et al. (1980) (see table 16). The solubility of V in Sc(Ga) solid solution slightly increases with increase temperature, but it does not exceed 2 at.%. In as-cast alloys the solid solution based on vanadium spreads up to about 20 at.% Sc with increasing gallium content. The solubility of V in Sc₅Ga₃ also increases with the increasing temperature and reaches about 10–12 at.% V.



Fig. 40. Sc-Hf-Ga, part of the isothermal section at 800°C (0–75 at.% Sc). Ternary compounds: (1)  $Sc_{0.2}Hf_{0.8}Ga_3$ ; (2)  $Sc_{0.2-0.9}Hf_{0.8-0.1}Ga$ .

### 3.3.6. Sc-Nb-Ga

During the investigation of the Sc–Nb–Ga alloys by Savitskii et al. (1980a) part of the phase equilibria at 800°C were established (0–75 at.% Sc) and two ternary compounds were observed (see fig. 41). One of the compounds, ~ScNbGa₂, is formed after long-term homogenization of the alloys at 800°C. The composition of the second reported compound, "Sc_{3.8–4.2}Nb_{1.2–0.4}Ga₄", was refined to Sc_{8.4–9.4}Nb_{2.6–1.6}Ga₁₀ by Markiv et al. (1989) who also determined its crystal structure (see table 16).

#### 3.3.7. Sc--Cr--Ga

Gavrilenko and Markiv (1978a) investigated part of the Sc–Cr–Ga isothermal section at 800°C, and its figure is presented in the review of Gladyshevsky et al. (1990). One ternary compound  $\sim$ Sc₄Cr₂Ga₃ occurs in this system, but its crystal structure is unknown (table 16).

## 3.3.8. Sc-Mn-Ga

Gavrilenko and Markiv (1978b) investigated part of the Sc-Mn-Ga isothermal section at 500°C (0–80 at.% Ga). Among the binary compounds of the Sc-Mn, Sc-Ga and Mn-Ga binary systems only ScMn₂ (ST MgZn₂) dissolves a large amount of the third component: up to 40 at.% Ga. The lattice parameters increase from a=5.03, c=8.19 (for ScMn₂) to a=5.22, c=8.52 Å for ScMn_{0.8}Ga_{1.2}. Three ternary compounds were synthesized in the system and their compositions and the crystal structures were published in subsequent papers of the same scientific group: compound (1) "Sc₂₅Mn₂₅Ga₅₀" by Markiv and Belyavina (1987b), compound (2) "Sc₃₆Mn₁₀Ga₅₄" by Belyavina (1983), compound (3)



Fig. 41. Sc–Nb–Ga, part of the isothermal section at 800°C (0–75 at.% Sc). Ternary compounds: (1) ~ScNbGa₄; (2)  $Sc_{84-94}Nb_{2.6-1.6}Ga_{10}$ .

" $Sc_{77}Mn_{13}Ga_{10}$ " by Markiv and Belyavina (1989a). The refined compositions of these compounds are presented in a modified isothermal section, which is shown in fig. 42.



Fig. 42. Sc-Mn–Ga, part of the isothermal section at 500°C (0–80 at.% Sc). Ternary compounds: (1)  $Sc_3Mn_2Ga_6$ ; (2)  $ScMn_{0.33}Ga_{1.67}$ ; (3)  $Sc_{8.5}Mn_{1.2}Ga$ .

The characteristics of their crystal structures are summarised in table 16.

#### 3.3.9. Sc-Fe-Ga

The Sc-Fe-Ga isothermal section at 800°C in the range 0-75 at.% Ga had been reported by Gavrilenko and Markiv (1978b). They established seven ternary compounds, for four of them a complete or partially investigated crystal structure was given. Belyavina and Markiv (1982a) reinvestigated the alloys of 7.7 at.% Sc isoconcentrate with the Ga content from 38 to 62 at.%. They did not confirm the data of Gavrilenko and Markiv about the crystal structure of "ScFe_{6.75-4.96}Ga_{5.25-7.04}" at 800°C (ST ThMn₁₂). A phase isotypic with ThMn₁₂ was found to occur at 600°C in an alloy with the composition  $ScFe_{4,73}Ga_{7,27}$ (its lattice spacings are given in table 16). At 800°C an orthorhombic phase occurs closely related to ThMn₁₂ type structure (see table 16). At 800°C a new compound, namely Sc₂Fe_{8.83}Ga_{8.17} was found; it is in equilibrium with the above-mentioned ternary phase and the  $\alpha$ (Fe, Ga) solid solution. Kuzmenko et al. (1983) reported about another ternary compound: ScFe0.14Ga1.86 (ST CaIn2) which was found in an as-cast alloy as well as in alloys annealed at 800°C. In other publications the compositions and the crystal structures of four other ternary compounds observed by Gavrilenko and Markiv were determined: (3) "ScFe_{1-0.8}Ga_{5-5.2}" (Belyavina and Markiv 1980b), (7) "Sc₃₆Fe₉Ga₅₅" (Kuzmenko et al., 1983), (4) "Sc₂₈Fe_{26.5-22.5}Ga_{45.4-49.4}" (Markiv and Belyavina 1987b), (9) "Sc₈₀Fe₁₂Ga₈" (Markiv and Belyavina 1989a). The modified isothermal section at 800°C based on these papers is presented in fig. 43. The composition of the " $Sc_7Fe$ "



Fig. 43. Sc-Fe-Ga, part of the isothermal section at 800°C (0-75 at.% Sc). Ternary compounds: (1)  $ScFe_{6-4,73}Ga_{6-7,27}$ ; (2)  $ScFe_{8,83}Ga_{8,17}$ ; (3)  $ScFeGa_5$ ; (4)  $Sc_3Fe_2Ga_6$ ; (5)  $ScFe_{1.82-1.44}Ga_{0.18-0.56}$ ; (6)  $ScFe_{1.37-0.71}$  $Ga_{0.63-1.29}$ ; (7)  $ScFe_{0.33}Ga_{1.67}$ ; (8)  $ScFe_{0.14}Ga_{0.86}$ ; (9)  $Sc_{8.5}Fe_{1.2}Ga$ .

binary compound has been corrected in this figure too (see also sect. 2.8). The crystal structure characteristics of all observed Sc–Fe–Ga ternary compounds are presented in table 16.

## 3.3.10. Sc-Co-Ga

A number of papers dealing with investigations of Sc–Co–Ga alloys and compounds have been published. Figure 44 presents a revised isothermal section at 800°C. Gavrilenko and Markiv (1979) reported on the isothermal section at 800°C in the range 0–75 at.% Ga. Sc–Co binary compounds dissolve large quantities of Ga: from 8 at.% (Sc₃Co) to 37 at.% (ScCo). The solubility of Co in Sc₅Ga₃ is about 11 at.%. Fifteen ternary compounds were reported to occur in the system at 800°C. Gavrilenko and Markiv confirmed the data of Markiv and Burnashova (1969) concerning Sc₆Co₇Ga₁₆ and determined its homogeneity range at 800°C: (8) Sc₆Co_{7.2–6.3}Ga_{15.8–16.7}. They also established the crystal structure of the phase (12) Sc_{29–34}Co_{40–24}Ga_{29–42} (see table 16). In later publications of Markiv and co-workers data about the crystal structure and proper compositions of other nine ternary compounds are given: (4) "ScCo_{1–0.75}Ga_{4–4.25}" and (7) "Sc₁₉Co₁₂Ga₆₉" by Belyavina and Markiv (1980b), (1) "Sc₂O₄₅Ga₄₆" by Belyavina and Markiv (1982a), (13) "ScCo_{0.35–0.20}Ga_{1.65–1.80}" by Belyavina and Markiv (1982b), (2) "ScCo_{3.96–3.72}Ga_{3.04–3.28}", (3) "ScCo₂Ga₅" and (6) "ScCo₃Ga₂" by Markiv and Belyavina (1987a), (15) "Sc₇₄Co₁₃Ga₁₃" by Markiv and Belyavina (1989b), and



Fig. 44. Sc–Co–Ga, part of the isothermal section at 800°C (0–75 at.% Sc). Ternary compounds: (1) ScCo_{5.8}Ga_{6.2}; (2) ScCo_{4.5}Ga_{4.1}; (3) Sc₂Co₃Ga₉; (4) ScCoGa₅; (5) ~Sc₁₇Co₆₄₋₆₂Ga₁₉₋₂₁; (6) Sc₂Co₇Ga₄; (7) Sc₂CoGa₈; (8) Sc₆Co_{7.2-6.3}Ga_{15.8-16.7}; (9) ~Sc₂₂Co₆₃₋₆₀Ga₁₅₋₁₈; (10) ~Sc₂₂Co₅₃₋₄₉Ga₂₅₋₂₉; (11) ScCo_{1.2}Ga_{1.8}; (12) Sc₂₉₋₃₄Co₄₈₋₂₄Ga₂₉₋₄₂; (13) ScCo_{0.35}Ga_{1.65}; (14) ~Sc₃₇Co₁₄Ga₄₉; (15) Sc₅Co_{0.925}Ga_{0.925}.

(11) "Sc₂₇Co₂₆Ga₄₇" by Belyavina and Markiv (1989). The refined compositions and the crystal structure data of these compounds are presented in fig. 44 and in table 16. The crystal structures of four Sc–Co–Ga ternary compounds are still unknown (see table 16). Kuzmenko et al. (1983) reinvestigated the alloys of the ScCu₂–ScGa₂ section and identified two other ternary compounds, namely ScCo_{0.14}Ga_{1.86} (ST CaIn₂) and ScCo_{0.5}Ga_{1.5} (ST KHg₂), which were observed only in the as-cast alloys (for their lattice spacings see table 16). The latter compound disintegrates into the ternary phases (12) and (13) during homogenization at 800°C.

### 3.3.11. Sc-Ni-Ga

Gavrilenko and Markiv (1979) presented data about the phase equilibria in the Sc-Ni-Ga system at 800°C in the range 0–75at.% Ga. They synthesized fourteen ternary compounds, but for only three of them [ScNi₂Ga (ST MnCu₂Al), Sc₃₀₋₃₆Ni₅₅₋₃₉Ga₁₅₋₂₅(ST MgZn₂), Sc₃₃₋₃₈Ni₃₅₋₁₈Ga₃₂₋₄₄ (ST CaIn₂)] has the crystal structure data been given. The compositions of the other eleven compounds were determined tentatively. For eight of them the crystal structure investigations were performed afterwards, this also led to a refinement of their compositions: (1) "ScNi_{1-0.85}Ga_{4-4.15}" and (7) "Sc_{20}Ni_{12}Ga_{68}" by Belyavina and Markiv (1980b), (12) "ScNi_{0.50.26}Ga_{1.5-1.74}" by Belyavina and Markiv (1982b), (10) ScNiGa₂ by Markiv and Belyavina (1983), (9) "Sc₂₇Ni₂₆Ga₄₇" by Belyavina and Markiv (1989), (14) "Sc70-73Ni20-12Ga10-15" by Markiv and Belyavina (1989b), (3) "Sc₁₇Ni₅₄₋₄₁Ga₂₉₋₄₂" by Markiv and Belyavina (1990a), and (2) "ScNi_{2.60}Ga_{4.03}" by Markiv and Belyavina (1990b). The refined compositions, the structure data of these compounds and the compositions of three other ternary compounds with unknown structures are given in table 16. Figure 45 shows the corrected isothermal section at 800°C based on all these publications. The solubility of Ga in ScNi₅, Sc₂Ni₇, ScNi₂ and ScNi is 11.5, 8.0, 12.2 and 30 at.%, respectively. Kuzmenko et al. (1983) reinvestigated the alloys of the ScNi₂-ScGa₂ section. They rejected the data of Gavrilenko and Markiv (1979) concerning the crystal structure of the  $Sc_{33-38}Ni_{35-18}Ga_{32-44}$  compound (ST CaIn₂, a = 4.184-4.240, c = 6.387-6.584 Å). Kuzmenko et al. observed the ternary compound of  $CaIn_2$  type only in the as-cast alloy at the composition of  $ScNi_{0,14}Ga_{1.86}$  (see table 16). For a compound of composition  $ScNi_{1-0.67}Ga_{1-1.33}$  at 800°C they found a structure of KHg₂ type. For the alloy of the equiatomic composition, ScNiGa, the ordered structure of the TiNiSi type was preferred by Kuzmenko et al. (see table 16). Earlier, Dwight (1968) reported about the ScNiGa compound crystallising in the KHg₂ type structure; the lattice parameters reported by Dwight for that phase, a = 4.164, b = 6.306, c = 7.230 Å are in good agreement with the parameters found by Kuzmenko et al. (see table 16). There are no further data in the paper of Kuzmenko et al. whether the  $ScNi_{1-0.67}Ga_{1-1.33}$  compound has variable content of scandium or not. For that reason we have drawn a broad homogeneity range for that compound (13) in fig. 45 according to the earlier data of Gavrilenko and Markiv (1979).



Fig. 45. Sc–Ni–Ga, part of the isothermal section at 800°C (0–75 at.% Sc). Ternary compounds: (1) ScNiGa₅; (2) ScNi_{2,36}Ga_{3,64}; (3) Sc₂Ni_{7-5,5}Ga_{4-5,5}; (4)  $\sim$ Sc₁₇Ni₆₄₋₅₉Ga₁₉₋₂₄; (5)  $\sim$ Sc₂₂Ni₅₈Ga₂₀; (6)  $\sim$ Sc₂₃Ni₆₁Ga₁₆; (7) Sc₂NiGa₈; (8) ScNi₂Ga; (9) ScNi_{1,2}Ga_{1,8}; (10) ScNiGa₂; (11) Sc₃₀₋₃₆Ni₅₅₋₃₉Ga₁₅₋₂₅; (12) ScNi_{0,35}Ga_{1,65}; (13) Sc₃₃₋₃₈Ni₃₅₋₁₈Ga₃₂₋₄₄; (14) Sc₅Ni_{0,963}Ga_{0,963}.

### 3.3.12. Sc-M-Ga (M = Ru, Rh, Pd, Os, Ir, Pt)

No data are available about phase equilibria in the six Sc–M–Ge (M=Ru, Rh, Pd, Os, Ir, Pt) ternary systems. Only occasional alloys were examined in each of these systems. As a result, in the Sc–Pd–Ga system two ternary compounds were synthesized and structurally characterised: ScPd₂Ga and ScPdGa (see table 16). In each of the remaining five systems one ternary compound was observed: their compositions are Sc₆M₇Ga₁₆ (M=Ru, Rh, Os, Ir) and ScPtGa. The crystal structure data are given in table 16. According to the data of Markiv and Storozhenko (1973) Sc₆M₇Ga₁₆ (M=Pd, Pt) ternary compounds do not occur in either the as-cast alloys or the alloys homogenised at 800°C.

### 3.3.13. Sc-Cu-Ga

Gavrilenko and Markiv (1979) investigated a part of the Sc–Cu–Ga isothermal section at 800°C (0–75 at.% Ga), however without showing a figure. The isothermal section shown in fig. 46 is mainly based on the figure presented by Gavrilenko (1982). Eight ternary compounds occur in the investigated part of the system. The crystal structure was determined for six of them (see table 16). The compositions of two of these compounds, (2) "Sc₁₅Cu₅₂Ga₃₃" and (5) "Sc₂₂Cu₅₅Ga₂₃", were refined as part of the crystal structure investigations by Markiv and Belyavina (1990b, 1989a). The compound (1) ScCu_{5.49–4.85}Ga_{6.51–7.15}was observed by Gavrilenko and Markiv in the as-cast alloy and in a sample homogenised at 600°C. At 800°C the alloys of this concentration region of the



Fig. 46. Sc–Cu–Ga, part of the isothermal section at 800°C (0–75 at.% Sc). Ternary compounds: (1) ScCu_{5,49–4,85}Ga_{6,51–7.15} (at 600°C); (2) ScCu_{3.7}Ga_{2.3}; (3)  $\sim$ ScCu_{3.6}Ga_{1.4}; (4)  $\sim$ ScCu_{3.2}Ga_{1.6}; (5) Sc₁₄Cu₃₇Ga₁₄; (6) ScCu₂Ga; (7) ScCu_{1.40–0.86}Ga_{0.60–1.14}; (8) ScCu_{0.77–0.26}Ga_{1.23–1.74}.

system are in the liquid state. Gavrilenko and Markiv (1979) reported about one ternary compound in the ScCu₂–ScGa₂ section: ScCu_{1.4–0.26}Ga_{0.6–1.74} (ST CaIn₂, a = 4.211-4.248, c = 6.459-6.588 Å). In a later paper Markiv et al. (1984) examined again the alloys of that section and reported the existence of two ternary phases within that composition region, namely (7) ScCu_{1.40–0.86}Ga_{0.60–1.14} (ST KHg₂) and (8) ScCu_{0.77–0.26}Ga_{1.23–1.74} (ST CaIn₂) (for their lattice parameters see table 16). Dwight (1968) also reported about the existence of a hexagonal compound ScCu_{0.5}Ga_{1.5} (ST Ni₂In, a = 4.254, c = 6.612), with a composition within the homogeneity range of the hexagonal compound (8) observed by Markiv et al. (1984), however, the values of the lattice spacings of the Dwight phase are higher than those reported by Gavrilenko and Markiv (1979) and Markiv et al. (1984).

#### 3.4. Sc-M-In ternary systems

#### 3.4.1. Sc-Ni-In

There are no data about the phase equilibria in the Sc–Ni–In system. Three ternary compounds  $ScNi_4In$ ,  $ScNi_2In$  and  $Sc_2Ni_2In$  have been synthesized and their crystal structure determined (see table 17).

### 3.4.2. Sc–Pd–In

Savitskii et al. (1980b) investigated the polythermal PdIn-PdSc section of the Sc-Pd-In ternary system. They observed a complete miscibility between the isotypic binary

Compound	Structure type	Lattice pa	rameters	Reference
	or symmetry	a (Å)	c (Å)	
ScNi ₄ In	MgCu ₄ Sn	6.872		Zaremba et al. (1984)
ScNi ₂ In	MnCu ₂ Al	6.256		Zaremba et al. (1984)
Sc ₂ Ni ₂ In	$Mo_2FeB_2$	7.1679	3.33154	4 Pöttgen and Dronskowski (1996)
$Sc_{0.76-1.44}Pd_2In_{1.24-0.56}$	MnCu ₂ A1	6.496ª		Dwight and Kimball (1987), Urvachev et al. (1983)
ScPt ₂ In	MnCu ₂ Al	6.512		Dwight and Kimball (1987)
ScCu ₂ In	MnCu ₂ Al	6.378		Dwight and Kimball (1987)
ScAg ₂ In	MnCu ₂ Al	6.720		Dwight and Kimball (1987)
ScAu ₂ In	MnCu ₂ Al	6.692		Dwight and Kimball (1987)

Table 17 Intermetallic compounds in the Sc-M-In ternary systems

^a For the ScPd₂In composition.

compounds PdIn and PdSc (ST CsCl). After a reinvestigation of the same section Urvachev et al. (1983) established the occurrence of one ternary compound with an extended homogeneity range:  $Sc_{0.76-1.44}Pd_2In_{1.24-0.56}$ , which is formed as the result of an atomic ordering of the observed earlier  $Pd(In_xSc_{1-x})$  solid solution. Dwight and Kimball (1987) reported about a ScPd₂In compound crystallizing in the MnCu₂Al type structure (see table 17) which is, obviously, the ordered type for the compound observed by Urvachev et al. (1983).

### 3.4.3. Sc-Pt-In

Dwight and Kimball (1987) identified a ternary compound of  $MnCu_2Al$  type structure in the Sc–Pt–In alloy with the ScPt₂In composition, homogenized at 700°C (see table 17). No information is available about other compounds or alloys of this system.

## 3.4.4. Sc-M-In (M = Cu, Ag, Au)

The occurrence of a Heusler type ternary compound,  $ScM_2In$ , in each of the three Sc-M-In (M=Cu, Ag, Au) ternary systems has been reported by Dwight and Kimball (1987). Their lattice spacings are given in table 17. The alloys were homogenized at 700°C. No phase equilibria in these systems were investigated.

## 3.5. Sc-M-C ternary systems

### 3.5.1. Sc-Th-C

Krupka et al. (1973) observed the occurrence of a solid solution of scandium in the cubic thorium carbide,  $Th_2C_3$  (ST  $Pu_2C_3$ ). The lattice parameter changes within the homogeneity range of  $Th_{2-0.6}Sc_{0-1.4}C_3$  from a=8.556 to a=8.563 Å, the value for  $Th_{1.4}Sc_{0.6}C_3$  is a=8.530 Å.

## 3.5.2. Sc-Ti-C

Nowotny and Auer-Welsbach (1961) synthesized the ternary compound  $ScTi_3C_4$  isotypic with NaCl (a=4.5 Å). Velikanova et al. (1989) evaluated the hypothetical projection of the solidus surfaces of the phase diagram. A wide range of continuous solid solutions between the isotypic binary carbides  $ScC_{1-x}$  and  $TiC_{1-x}$  (ST NaCl) was predicted by them. It might be that the ternary phase observed by Nowotny and Auer-Welsbach is a part of this solid solution, and possibly not an individual ternary compound. Recently this prediction was confirmed experimentally by Ilyenko et al. (1996) who confirmed a complete mutual solubility of  $ScC_{1-x}$  and  $TiC_{1-x}$ . These authors reported also that the  $ScC_{1-x}$  phase is in equilibrium with all the phases of the solidus surface. However, the paper by Ilyenko et al. does not contain a figure of the phase equilibria.

## 3.5.3. Sc-M-C (M = Zr; Hf, V, Nb, Ta)

Hypothetical projections of the solidus surfaces of the Sc-M-C (M=Zr, Hf, V, Nb, Ta) phase diagrams are proposed in a paper of Velikanova et al. (1989). A complete miscibility of the binary carbides  $ScC_{1-x}$  and  $MC_{1-x}$  (M=Zr, Hf, V, Nb, Ta) crystallizing in the NaCl type structure, and the absence of ternary compounds in each of these ternary systems is predicted. However, these data need to be confirmed experimentally. Recently llyenko et al. (1996) reported the existence of continuous solid solutions between  $ScC_{1-x}$  and  $MC_{1-x}$  (M=Zr, Hf), and accordingly these solid solutions are in equilibria with all the phases of the solidus surface. The same authors reported that the  $VC_{1-x}$  binary carbidedissolves at least 15 at.% Sc while the V solubility in  $ScC_{1-x}$  is at least 17 at.%. These data reject the earlier prediction of a complete miscibility of the NaCl-type binary carbides in the system Sc–V–C. However, no figures of the phase equilibria are presented in the brief communication of Ilyenko et al.

### 3.5.4. Sc-Cr-C

A hypothetical projection of the solidus surfaces of the Sc–Cr–C phase diagram has been proposed and experimentally confirmed in the range 0–30 at.% C by Velikanova et al. (1989) and Artyukh et al. (1989) (see fig. 47a). At high carbon content one ternary compound Sc₂CrC₃ occurs in the system (Artyukh et al.). Its melting temperature does not exceed 1600°C. Pecharskaya et al. (1990) established its crystal structure (see table 18). A second ternary compound ScCrC₂, occurring in two very closely related modifications  $\beta$  (HT) and  $\alpha$  (LT), has been reported by Pöttgen et al. (1995) (see table 18). Recently Artyukh et al. (1997) presented the phase equilibria over the whole concentration region of the system. In the carbon-rich range ScC_{1-x}–C–Cr₃C₂ all the phases are in equilibria with the ternary compound Sc₂CrC₃. Scandium and chromium binary carbides dissolve no more than 1 to 1.5 at.% of the third component. However, the ScCrC₂ ternary compound was not mentioned. Thus, an additional investigation of the system in the >40 at.% C region is necessary.



Fig. 47. (a) Sc-Cr-C, and (b) Sc-Mo-C parts of the projections of solidus surfaces (a, 0-30 at.% C; b, 0-42 at.% C).

#### 3.5.5. Sc-Mo-C

Velikanova et al. (1989) evaluated hypothetical projection of solidus surfaces of the Sc-Mo-C phase diagram and confirmed it, at least partially, by experiment in 0–42 at.% C concentration region (see fig. 47b). The forecasted and the experimental data are in good agreement. No ternary compounds were observed. In the diagram presented by Velikanova et al. it is shown that about 8 at.% Sc is soluble in Mo at 1200°C. These data are in disagreement with the prediction of Brewer and Lamoreaux (1980) and the experimentally determined Sc–M (M=5A, 6A element) binary phase diagrams (see sect. 2.6). The solubility of scandium in these elements is very low (<0.1 at.%). The diagram presented in fig. 47b has been modified by taking this into account.

# 3.5.6. Sc-M-C (M = W, Re, Tc)

Hypothetical projections of solidus surfaces of the Sc-M-C (M=W, Re, Tc) phase diagrams have been proposed: Sc-W-C by Velikanova et al. (1989), Sc-Re-C by Velikanova et al. and by Eremenko et al. (1989a), and Sc-Tc-C by Eremenko et al. (1989b). However, all these results need an experimental verification. No ternary compounds were predicted. Pöttgen and Jeitschko (1992) synthesized a ternary carbide  $Sc_5Re_2C_7$  and investigated its crystal structure (see table 18); these data do not confirm the predictions mentioned above.

Compound Struc	ture type	Latt	ice parame	ters	Reference			
or sy	mmetry	a (Å)	b (Å)	c (Å)				
$Sc_2CrC_3$ $Sc_2C$	rC ₃	14.110	5.809	3.271	Pecharskaya et al. (1990), Artyukh et al. (1989)			
$ScCrC_2$ ( $\beta$ ) ScCr	C ₂ (β)	3.237		9.149	Pöttgen et al. (1995)			
$ScCrC_2(\alpha)$ ScCr	$C_2(\alpha)$	3.2434	9.1502	5.6148	Pöttgen et al. (1995)			
$Sc_5Re_2C_7$ $Sc_5R$	.e ₂ C ₇	7.7926	13.620	3.2062	Pöttgen and Jeitschko (1992)			
ScFeC ₂ ScCo	$C_2$	3.293		7.487	Marusin et al. (1985), Pecharskaya (1989)			
Sc ₃ FeC ₄ Sc ₃ C	$OC_4$	3.3636	4.3748	12.087	Tsokol' et al. (1986a), Pecharskaya (1989)			
ScCo ₃ C CaTi	O ₃	3.8291			Pecharskaya (1989)			
5		3.827			Holleck (1977)			
ScCoC ₂ ScCo	$C_2$	3.3344		7.292	<i>Marusin et al. (1985)</i> , Pecharskaya (1989)			
$Sc_3CoC_4$ $Sc_3C$	oC ₄	3.3933	4.3727	11.989	<i>Tsokol' et al. (1986a)</i> , Pecharskaya (1989)			
ScNiC ₂ ScCo	$C_2$	3.325		7.368	Marusin et al. (1985), Pecharskaya (1989)			
Sc ₃ NiC ₄ Sc ₃ C	CoC ₄	3.4118	4.3772	11.916	Tsokol' et al. (1986a), Pecharskaya (1989)			
ScRu ₃ C CaTi	O ₃	4.031			Holleck (1977)			
ScIr ₃ C _{1-x} CaTi	O ₃	3.994			Holleck (1977)			

Table 18 Intermetallic compounds in the Sc–M–C ternary systems

### 3.5.7. Sc-Fe-C

The isothermal section of the Sc-Fe-C system at 600°C has been investigated by Pecharskaya (1989). The phase diagram presented in fig. 48 is mainly based on these data. The data concerning the binary Sc-C system are not in agreement with the Sc-C phase diagram presented by Gordijchuk (1987) (see sect. 2.14). Two ternary compounds ScFeC₂ and Sc₃FeC₄ occur in this system. Their crystal structures were studied earlier by Marusin et al. (1985) and Tsokol' et al. (1986a) (see table 18).

### 3.5.8. Sc--Co--C

The Sc–Co–C phase equilibria at 600°C have been established by Pecharskaya (1989) and are shown in fig. 49. The data about the existence at 600°C of  $Sc_4C_3$  binary carbide are not in agreement with the other literature sources (see sect. 2.14). Earlier the existence of three ternary compounds were reported in the system. Their compositions and the crystal structure data are given in table 18.



Fig. 48. Sc-Fe-C, isothermal section at 600°C. Ternary compounds: (1) ScFeC₂; (2) Sc₃FeC₄.



Fig. 49. Sc-Co-C, isothermal section at 600°C. Ternary compounds: (1) ScCo₃C; (2) ScCoC₂; (3) Sc₃CoC₄.

3.5.9. Sc-Ni-C

Two ternary compounds  $ScNiC_2$  and  $Sc_3NiC_4$  were synthesized and their crystal structure determined (see table 18). Later, Pecharskaya (1989) presented isothermal section at 600°C (see fig. 50). However, the existence of a  $Sc_4C_3$  binary compound at 600°C does not agree with the Sc–C phase diagram published by Gordijchuk (1987) (see sect. 2.13); this discrepancy needs to be cleared-up by a new investigation.



Fig. 50. Sc-Ni-C, isothermal section at 600°C. Ternary compounds: (1) ScNiC₂; (2) Sc₃NiC₄.

## 3.5.10. Sc-M-C (M = Ru, Rh, Pd)

Holleck (1977) investigated the phase equilibria of the Sc-M-C (M=Ru, Rh, Pd) systems at 1300°C in the ranges 0–40 (for M=Ru), 0–50 (for M=Rh) and 0–25 (for M=Pd) at.% Sc. The isothermal sections presented in fig. 51 are modified by taking into account the newest data concerning the Sc-M (M=Ru, Rh, Pd) phase diagrams. The compositions and their homogeneity ranges of the binary compounds at 1300°C were corrected (see sect. 2.9). One ternary compound occurs in the Sc-Ru-C system (see table 18). In the Sc-Rh-C system the solid solution due to the inclusion of carbon atoms into the lattice of the ScRh₃ compound (ST AuCu₃) was observed: ScRh₃C_{0-0.75}. Its lattice parameter varies from a = 3.900 up to a = 4.025 Å. Possibly this solid solution may reach the ScRh₃C composition.



Fig. 51. (a) Sc-Ru-C, (b) Sc-Rh-C, and (c) Sc-Pd-C parts of the isothermal sections at 1300°C (a, 0-40; b, 0-50; c, 0-25 at.% Sc). Ternary compound: (1) ScRu₃C.

# 3.5.11. Sc-Ir-C

One ternary compound  $ScIr_3C_{1-x}$  of the perovskite type structure has been synthesized by Holleck (1977) (see table 18), however the proper carbon content is unknown because of the loss of some of the component during its preparation. The compound is in the two phase equilibria with  $ScIr_2$  and C.

## 3.6. Sc-M--Si ternary systems

## 3.6.1. *Sc*-*Y*-*Si*

Kotroczo and McColm (1987) investigated the quasibinary section  $Sc_5Si_3-Y_5Si_3$  of the Sc–Y–Si ternary system and found a limited solid solutions  $Y_{5-x}Sc_xSi_3$  ( $0 \le x \le 0.75$ ) and  $Sc_{5-y}Y_ySi_3$  ( $0 \le y \le 1$ ) during an examination of as-cast alloys. Later Kotur and Mokra (1994) during an investigation of the isothermal section of the ternary system at 800°C observed a complete miscibility of these isotypic binary silicides (see fig. 52). Another continuous solid solution occurs between the isotypic monosilicides of scandium and yttrium. The highest yttrium silicide, YSi₂, dissolves 20 at.% Sc. One ternary compound with a variable composition occurs in this system (see table 19).



Fig. 52. Sc-Y-Si, isothermal section at 800°C. Ternary compound: (1) Sc_{0.95-0.52}Y_{0.05-0.48}Si_{1.67}.

## 3.6.2. Sc-La-Si

There are two ternary compounds known in the Sc–La–Si system: ScLaSi (Mokra and Bodak 1979) and  $\sim$ ScLa₂Si₂ (Mokra 1979), however, the lattice parameters have been reported only for the first compound (see table 19).

#### 3.6.3. Sc--Ce--Si

An isothermal section of the Sc–Ce–Si phase diagram at 600°C has been investigated by Mokra (1979) and Bodak et al. (1981). Its figure was presented in the review of Rogl (1984b). Binary silicides of cerium and scandium do not dissolve more than 5 at.% of Sc and Ce respectively. All eight ternary compounds known in this system have variable

Compound	Structure type	Latt	ice param	eters	Reference
	or symmetry	a (Å)	b (Å)	c (Å)	-
Sc _{0.95-0.52} Y _{0.05-0.48} Si _{1.67}	AlB ₂	3.687–		3.935-	Kotur and Mokra (1994)
		3.735		4.033	
$ScLa_2Si_2$	$Mo_2FeB_2$				Mokra (1979)
ScLaSi	ScCeSi	4.344		15.98	Mokra and Bodak (1979)
$\sim$ Sc ₃ Ce ₁₁ Si ₆	?				Mokra (1979)
~Sc ₃ Ce ₈ Si ₉	?				Mokra (1979)
ScCe ₂ Si ₂	$Mo_2FeB_2$	7.61		4.402	Mokra (1979)
		7.518		4.393	Kotur et al. (1989c)
~Sc ₄ Ce ₇ Si ₉	?				Mokra (1979)
~Sc ₅ Ce ₆ Si ₉	?				Mokra (1979)
ScCeSi	ScCeSi	4.300		15.80	<i>Mokra and Bodak (1979),</i> Mokra (1979)
		4.302		15.768	Kotur et al. (1989c)
$Sc_3Ce_2Si_4$	$\mathrm{Ce}_2\mathrm{Sc}_3\mathrm{Si}_4$	7.248	14.255	7.551	<i>Mokra et al. (1979),</i> Mokra (1979)
~Sc ₇ Ce ₃ Si ₁₀	?				Mokra (1979)
~ScPr ₄ Si ₃	?				Banakh and Kotur (1997)
$Sc_{1.26}Pr_{3.74}Si_4$	$\mathrm{Sm}_{5}\mathrm{Ge}_{4}$	7.453	14.842	7.825	<i>Kotur et al. (1997a),</i> Banakh and Kotur (1997)
$\sim$ Sc ₂ Pr ₅ Si ₃	?				Banakh and Kotur (1997)
ScPr ₂ Si ₂	$Mo_2FeB_2$	7.585		4.328	Banakh and Kotur (1997), Mokra (1979)
$\sim Sc_2Pr_3Si_4$	?				Banakh and Kotur (1997)
ScPrSi	ScCeSi	4.292		15.78	Mokra and Bodak (1979)
		4.301		15.810	Banakh and Kotur (1997)
$Sc_3Pr_2Si_4$	$Ce_2Sc_3Si_4$	7.196	14.150	7.495	<i>Kotur et al. (1997a),</i> Banakh and Kotur (1997)
Sc _{0.89} Pr _{0.11} Si _{1.53}	AlB ₂	3.6648		3.8876	Banakh and Kotur (1997)
~ScNd ₄ Si ₃	?				Banakh and Kotur (1998)
ScNd ₂ Si ₂	$Mo_2FeB_2$	7.307		4.323	Banakh and Kotur (1998), Mokra (1979)
ScNdSi	ScCeSi	4.224		15.567	Kotur et al. (1992), Banakh and Kotur (1998)
		4.248		15.73	Mokra and Bodak (1979)
$Sc_{0.85-0.95}Nd_{0.15-0.05}Si_{1.67}$	AlB ₂	3.6644– 3.6596		3.8896- 3.8860	-Kotur et al. (1992), Banakh and Kotur (1998)
Sc ₄ NdSi ₄	$\mathrm{Sm}_5\mathrm{Ge}_4$	7.058	13.912	7.361	Kotur et al. (1997a), Kotur et al. (1992)
Sc _{0.2-0.4} Sm _{0.8-0.6} Si	CrB	4.193– 4.200	10.51– 10.50	3.846– 3.817	Kotur et al. (1991)

Table 19 Intermetallic compounds in the Sc-M-Si ternary systems

Compound	Structure type or symmetry	Lat	tice parame	eters	Reference
		a (Å)	b (Å)	c (Å)	-
Sc _{0.3} Sm _{0.7} Si ₂	aThSi2	4.049		13.388	Kotur et al. (1991)
$ScSm_2Si_2$	$Mo_2FeB_2$	7.420		4.350	Kotur et al. (1991)
ScSmSi	ScCeSi	4.255		15.56	<i>Kotur et al. (1991),</i> Mokra and Bodak (1979)
$Sc_3Sm_2Si_4$	$Ce_2Sc_3Si_4$	7.42	14.21	7.51	Kotur et al. (1991)
$Sc_{0.3}Dy_{0.7}Si_2$	$\alpha ThSi_2$	3.943		13.188	Kotur et al. (1991)
$Sc_{0.4-0.7}Dy_{0.6-0.3}Si_{1.67}$	$AlB_2$	3.762– 3.688		4.048– 3.929	Kotur et al. (1991)
ScV ₅ Si ₅	Ti ₆ Ge ₅	7.644	16.223	4.971	Kotur (1987)
$Sc_2V_3Si_4$	$Sc_2Re_3Si_4$	6.644		12.270	Kotur et al. (1986b), Kotur (1987)
$Sc_2V_3Si_3$	$Mn_5Si_3$	7.360		4.997	Kotur et al. (1983a), Kotur (1987)
$Sc_{0.4}Nb_{4.6}Si_3$	$W_5Si_3$	10.046		5.076	Kotur (1986)
$Sc_2Nb_3Si_4$	$Ce_2Sc_3Si_4$	6.684	13.11	7.010	Kotur (1986)
$Sc_2Cr_4Si_5$	$Nb_2Cr_4Si_5$	7.585	16.138	4.932	Kotur and Sikirica (1982a), Kotur and Bodak (1987)
$Sc_2Cr_3Si_4$	$Sc_2Re_3Si_4$	6.559		12.150	Kotur et al. (1986b), Kotur and Bodak (1987)
$Sc_7Cr_{4.8}Si_{9.2}$	$\mathrm{Sc}_{7}\mathrm{Cr}_{4+x}\mathrm{Si}_{10-x}$	9.757		13.884	<i>Kotur et al. (1985a),</i> Kotur and Bodak (1987)
$Sc_2Mo_3Si_4$	$Ce_2Sc_3Si_4$	6.536	12.641	6.784	Kotur et al. (1986c), Kotur and Bodak (1988)
$Sc_{2-3}W_{3-2}Si_4$	$\mathrm{Sm}_5\mathrm{Ge}_4$	6.537 6.568	12.645– 12.734	6.786- 6.793	Kotur et al. (1989a)
ScMnSi ₂	ZrCrSi ₂	9.077	9.854	7.928	Kotur et al. (1977b, 1980)
$Sc_4Mn_4Si_7$	$Zr_4Co_4Ge_7$	13.06		5.227	Kotur et al. (1977b), <i>Kotur et al. (1980)</i>
ScMnSi	ZrNiAl	6.551		3.861	<i>Kotur et al. (1980)</i> , Kotur et al. (1977b)
ScMn _{0.25} Si _{1.75}	$ZrSi_2$	3.878	14.46	3.776	Kotur and Bodak (1977), Kotur et al. (1980)
Sc ₅ Re ₈ Si ₁₂	Sc ₅ Re ₈ Si ₁₂	14.475	19.66	5.237	Chabot and Parthé (1987)
$Sc_2Re_3Si_4$	$Sc_2Re_3Si_4$	6.619		12.36	Pecharsky et al. (1978), Pecharsky (1979)
~ScReSi ₂	?				Pecharsky (1979)
$Sc_3Re_2Si_4$	$Sc_3Re_2Si_4$	19.567	15.336 $\beta = 125.76$	13.705 8°	Chabot and Parthé (1985)
Sc7Re3.35Si10.65	$Sc_7Re_{4-x}Si_{10+x}$	9.8123		14.274	Zhao et al. (1988)
$Sc_{0.35}Fe_{4.65}Si_3$	$Mn_5Si_3$	6.763		4.718	Gladyshevsky et al. (1977)

Table 19, continued

Compound	Structure type	Lat	tice paramete	ers	Reference
	or symmetry	a (Å)	b (Å)	c (Å)	
ScFe ₁₀ Si ₂	ThMn ₁₂	8.280		4.706	Bodak et al. (1995), Gladyshevsky et al. (1977)
$\mathrm{Sc}_{1.2}\mathrm{Fe}_{4}\mathrm{Si}_{9.8}$	$\mathrm{Sc}_{1,2}\mathrm{Fe}_{4}\mathrm{Si}_{9,8}$	3.897		15.160	Kotur and Bruvo (1991), Gladyshevsky et al. (1977)
~ScFe ₅ Si ₃	?				Gladyshevsky et al. (1977)
ScFe ₄ Si ₂	$ZrFe_4Si_2$	6.947		3.796	Gladyshevsky et al. (1977)
ScFe ₂ Si ₂	$HfFe_2Si_2$	7.5002	7.1375	5.0224	Kotur et al. (1997b), Gladyshevsky et al. (1977)
Sc ₂ Fe ₃ Si ₅	$Sc_2Fe_3Si_5$	10.05		5.313	Bodak et al. (1977), Gladyshevsky et al. (1977)
		10.225		5.275	Braun (1980)
ScFeSi ₂ (I)	ZrCrSi ₂	8.984	9.739	7.795	Gladyshevsky et al. (1977)
ScFeSi ₂ (II)	ScFeSi ₂	5.115	18.929	14.298	Yarmolyuk et al. (1980), Gladyshevsky et al. (1977)
$Sc_4Fe_4Si_7$	$Zr_4Co_4Ge_7$	13.099		5.075	<i>Chabot et al. (1984),</i> Kotur (1983)
$Sc_{1-1.09}Fe_{1.97-1.82}$ $Si_{0.06-0.12}$	$MgCu_2$	7.038 ^a			Gladyshevsky et al. (1977)
$ScFe_{1.5-1.42}Si_{0.5-0.58}$	$MgZn_2$	4.962 -		8.079-	Kotur (1977b), Gladyshevsky et al. (1977)
		4.974		8.060	Kotur et al. (1998)
ScFe _{0.25} Si _{1.75}	$ZrSi_2$	3.861	14.48	3.762	Kotur and Bodak (1977), Gladyshevsky et al. (1977)
$Sc_2FeSi_2$	$Sc_2CoSi_2$	9.917	3.984 $\beta = 123.48^{\circ}$	9.944	Kotur and Sikirica (1983), Gladyshevsky et al. (1977)
ScFeSi	TiNiSi	6.512	3.8391	7.298	Chabot et al. (1984)
$Sc_3Fe_2Si_3$	$Hf_3Ni_2Si_3$	3.959	9.960	12.941	Chabot et al. (1984)
$Sc_6Co_{30}Si_{19}$	$\mathrm{Sc}_6\mathrm{Co}_{30}\mathrm{Si}_{19}$	14.776		3.613	Kotur and Sikirica (1991), Kotur et al. (1977a)
$\sim Sc_4Co_{14}Si_9$	hex	10.16		3.614	Kotur et al. (1977a)
$Sc_6Co_{16}Si_7$	$Mg_6Cu_{16}Si_7$	11.438			Dwight et al. (1963a), Kotur et al. (1977a)
$ScCo_2Si_2$	$CeGa_2Al_2$	3.7756		9.598	Kotur et al. (1977a, 1989c)
		3.72		9.51	Voroshilov et al. (1967)
$Sc_2Co_3Si_5$	$U_2Co_3Si_5$	9.206	11.26	5.320	Kotur et al. (1977a), <i>Kotur (1977a)</i>
$Sc_5Co_4Si_{10}$	$Sc_5Co_4Si_{10}$	12.01		3.936	Kotur et al. (1977a)
		12.041		3.936	Braun et al. (1980)

Table 19, continued

Compound	Structure type or symmetry	Lat	tice paramet	ters	Reference
		a (Å)	b (Å)	c (Å)	
ScCo _{1.52-1.46} Si _{0.48-0.54}	MgZn ₂	4.934-		7.918–	Kotur (1977b), Kotur et al. (1977a)
		4.973		7.830	Kotur et al. (1998)
ScCoSi	TiNiSi	6.419	3.953	6.896	Kotur and Bodak (1977), Kotur et al. (1977a)
ScCo _{0.25} Si _{1.75}	ZrSi ₂	3.856	14.54	3.744	Kotur and Bodak (1977), Kotur et al. (1977a)
Sc ₃ Co ₂ Si ₃	$Hf_3Ni_2Si_3$	3.996	9.815	12.67	Gladyshevsky and Kotur (1978), Kotur et al. (1977a)
$Sc_2CoSi_2$	$Sc_2CoSi_2$	9.74	3.954 $\beta = 122.6^{\circ}$	9.82	Gladyshevsky and Kotur (1978), Kotur et al. (1977a)
Sc ₂ Co _{0.85} Si _{0.15}	Ti ₂ Ni	12.099			Kotur et al. (1977a)
~Sc ₂ Ni ₉ Si ₉	?				Bodak et al. (1976)
$Sc_3Ni_{11}Si_4$	$\mathbf{Sc}_{3}\mathbf{Ni}_{11}\mathbf{Si}_{4}$	8.024		8.429	Kotur et al. (1983b), Bodak et al. (1976)
ScNi ₂ Si ₃	$ScNi_2Si_3$	3.830		23.50	Kotur et al. (1978), Bodak et al. (1976)
$\mathbf{Sc_6Ni_{18}Si_{11}}$	$\mathbf{Sc}_{6}\mathbf{Ni}_{18}\mathbf{Si}_{11}$	17.945	12.223	8.029	Kotur et al. (1986d), Bodak et al. (1976)
$Sc_6Ni_{16}Si_{7m}$	$\mathrm{Mg}_{6}\mathrm{Cu}_{16}\mathrm{Si}_{7}$	11.46			Gladyshevsky et al. (1962), Bodak et al. (1976)
		11.429			Dwight et al. (1963a)
~Sc ₂ Ni ₅ Si ₃	?				Bodak et al. (1976)
$scNi_2Si_2$	$CeGa_2Al_2$	3.8018		9.567	Kotur et al. (1989c), Bodak et al. (1976)
		3.72		9.50	Voroshilov et al. (1967)
ScNiSi ₃	ScNiSi ₃	3.815	3.825	20.62	Kotur et al. (1977c), Bodak et al. (1976)
Sc3Ni4Si4	Gd ₆ Cu ₈ Ge ₈	12.68	6.38	3.89	Bodak et al. (1976)
$ScNi_{1.52-1.49}Si_{0.48-0.51}$	MgZn ₂	4.989–		7.730-	Kotur (1977b), Bodak et al. (1976)
		5.000		7.719	Kotur et al. (1998)
ScNiSi	TiNiSi	6.383	4.011	6.868	Kotur and Bodak (1977), Bodak et al. (1976)
$\mathrm{Sc}_3\mathrm{Ni}_2\mathrm{Si}_4$	$Sc_3Ni_2Si_4$	11.678	3.976	11.940	Zhao and Parthé (1989a), Bodak et al. (1976)
$ScNi_{0.25}Si_{1.75}$	ZrSi ₂	3.843	14.68	3.727	Kotur and Bodak (1977), Bodak et al. (1976)
$Sc_3Ni_2Si_3$	$\mathrm{Hf}_3\mathrm{Ni}_2\mathrm{Si}_3$	3.9812	9.688	13.111	Zhao and Parthé (1989b), Bodak et al. (1976)

Table 19, continued

Compound	Structure type or symmetry	Lattice parameters			Reference
		<i>a</i> (Å)	b (Å)	c (Å)	
Sc ₃ NiSi ₃	$Sc_3NiSi_3$	9.801	3.974 $\beta = 114.16^{\circ}$	13.193	Kotur and Gladyshevsky (1983), Bodak et al. (1976)
$\sim Sc_3Ru_2Si_6$	orthorh	8.939	9.061	4.175	Braun and Segre (1980)
ScRuSi	ZrNiAl	6.851		3.423	Hovestreydt et al. (1982)
ScRh ₃ Si ₇	$ScRh_3Si_7$	7.5056		19.691	<i>Chabot et al. (1981b),</i> Braun et al. (1979)
~Sc ₃ Rh ₂ Si ₉	?				Braun et al. (1979)
$\sim$ Sc ₂ Rh ₃ Si ₄	?				Braun et al. (1979)
ScRhSi ₂	$ScRhSi_2$	6.292	4.025	9.517	<i>Chabot et al. (1981a),</i> Braun et al. (1979)
$Sc_5Rh_4Si_{10}$	$Sc_5Co_4Si_{10}$	12.325		4.032	Braun et al. (1980), Braun et al. (1979)
~Sc ₃ Rh ₃ Si ₅	?				Braun et al. (1979)
~Sc ₄ RhSi ₈	?				Braun et al. (1979)
~Sc ₆ Rh ₄ Si ₉	?				Braun et al. (1979)
ScRhSi	TiNiSi	6.4736	4.0500	7.2483	Hovestreydt et al. (1982)
$\sim Sc_3Rh_2Si_4$	?	6.543	4.069	7.396	Braun et al. (1979)
ScPdSi	TiNiSi	6.543	4.069	7.396	Hovestreydt et al. (1982)
~Sc ₃ Os ₂ Si ₆	orthorh	8.963	9.044	4.195	Braun and Segre (1980)
ScIr ₃ Si ₇	$ScRh_3Si_7$	7.5010		19.909	Chabot et al. (1981b)
$Sc_5Ir_4Si_{10}$	$Sc_5Co_4Si_{10}$	12.316		4.076	Braun et al. (1980)
ScIrSi	TiNiSi	6.418	4.036	7.299	Hovestreydt et al. (1982)
Sc ₄ Ir ₇ Si ₆	$U_4 Re_7 Si_6$	8.003			Engel et al. (1984)
ScPtSi	TiNiSi	6.566	4.130	7.275	Hovestreydt et al. (1982)
ScCu ₂ Si ₂	$CeGa_2Al_2$	3.810		10.091	<i>Kotur (1984),</i> Kotur et al. (1985b)
$Sc_3Cu_4Si_4$	$Gd_6Cu_8Ge_8$	13.096	6.411	3.945	Kotur and Bodak (1980), Kotur et al. (1985b)
		13.09	6.42	3.94	Hanel and Nowotny (1970)
ScCuSi (h)	ZrNiAl	6.426		3.922	Kotur et al. (1981), Kotur et al. (1985b)
		6.44		3.92	Dwight et al. (1973)
ScCuSi (r)	TiNiSi	6.566	3.976	7.224	<i>Kotur et al. (1981),</i> Kotur et al. (1985b)
Sc2Cu0.8Si0.2	Ti ₂ Ni	12.290			Kotur et al. (1985b)
ScAuSi	ScAuSi	4.212		6.803	Fornasini et al. (1992)

Table 19, continued

^a For the composition  $Sc_{1.05}Fe_{1.89}Si_{0.06}$ .

content of Ce and Sc within 2 to 4 at.%. These results were partially confirmed by Kotur et al. (1989c) who reported slightly different values for the lattice spacings for two of the ternary compounds,  $ScCe_2Si_2$  and ScCeSi (see table 19). The crystal structures of five ternary compounds are still unknown.

#### 3.6.4. Sc-Pr-Si

Banakh and Kotur (1997) reported about the Sc–Pr–Si isothermal section at 600°C. However, a figure of the section was not presented in that short communication. Eight ternary compounds occur in the system. Two of them, ScPrSi and ~ScPr₂Si₂, had been synthesized earlier by Mokra and Bodak (1979) and Mokra (1979). The crystal structure has been determined for five of these compounds (see table 19).

### 3.6.5. Sc-Nd-Si

Figure 53 shows the isothermal section of the Sc–Nd–Si system at 600°C which was determined by Banakh and Kotur (1998). The binary silicides  $NdSi_{2-x}$  and NdSi dissolve 15 and 7 at.% Sc, respectively. The solubility of the third component in other neodymium and scandium binary silicides does not exceed 2 at.%. Five ternary compounds exist in this system (see table 19). One of them, (4) in fig. 53, has variable composition of Sc and Nd. Four other have practically constant composition.



Fig. 53. Sc–Nd–Si, isothermal section at 600°C. Ternary compounds: (1)  $\sim$ ScNd₄Si₃; (2) ScNd₂Si₂; (3) ScNdSi; (4) Sc_{0.85–0.95}Nd_{0.15–0.05}Si_{1.67}; (5) Sc₄NdSi₄.


Fig. 54. Sc–Sm–Si, part of the isothermal section at 600°C (0–80 at.% Sc). Ternary compounds: (1)  $Sc_{0.3}Sm_{0.7}Si_2$ ; (2)  $Sc_{0.2-0.4}Sm_{0.8-0.6}Si$ ; (3)  $ScSm_2Si_2$ ; (4) ScSmSi; (5)  $Sc_3Sm_2Si_4$ .

#### 3.6.6. Sc-Sm-Si

Kotur et al. (1991) reported on part of the Sc–Sm–Si isothermal section at 600°C which is shown in fig. 54. All the samarium and scandium binary silicides dissolve different amounts of the third component, from 2 at.% Sm (ScSi compound) up to 13 at.% Sc (Sm₅Si₃ compound). Five ternary compounds exist in the system, and the crystal structure is known for all of them (see table 19).

#### 3.6.7. Sc–Dy–Si

The Sc–Dy–Si phase equilibria at 600°C have been investigated by Kotur et al. (1991) (fig. 55). Solid solutions of substitution of Sc and Dy of different extent on the basis of binary silicides occur in the system. DySi dissolve only 1 at.% Sc while the isotypic silicides  $Sc_5Si_3$  and  $Dy_5Si_3$  are completely miscible. The variations of the lattice spacings vs. composition of solid solutions obey Vegard's rule in case of  $Sc_{1-x}Dy_xSi$ , or show slight deviations from this rule ( $Dy_{5-x}Sc_xSi_3$ ,  $Dy_{5-x}Sc_xSi_4$ ). Two ternary compounds occur in this system (see table 19). One of them also has a variable composition of Sc and Dy.

#### 3.6.8. Sc-Er-Si

Kotur and Parasiuk (1994) investigated the Sc–Er–Si isothermal section at 600°C which is depicted in fig. 56. Ternary compounds do not exist in this system. Pairs of isotypic binary silicides, namely ScSi and ErSi,  $Sc_5Si_3$  and  $Er_5Si_3$ , form continuous series of solid solutions.  $ErSi_{1.67}$  dissolves 32 at.% Sc.



 $\label{eq:solution} Fig. 55. \ Sc-Dy-Si, isothermal section at 600^{\circ}C. \ Ternary \ compounds: (1) \ Sc_{0.3}Dy_{0.7}Si_2; (2) \ Sc_{0.4-0.7}Dy_{0.6-0.3}Si_{1.67}.$ 



Fig. 56. Sc-Er-Si, isothermal section at 600°C.

# 3.6.9. Sc–Lu–Si

The Sc-Lu-Si isothermal section at 800°C, published by Kotur and Mokra (1994) (see fig. 57), is similar to that of the Sc-Er-Si system.  $LuSi_{2-x}$  dissolves 35 at.% Sc.



Fig. 57. Sc-Lu-Si, isothermal section at 800°C.

## 3.6.10. Sc-Ti-Si, Sc-Zr-Si

Parts of the isothermal sections of the Sc–Ti–Si and Sc–Zr–Si systems at 800°C were investigated by Kotur et al. (1989b) and are displayed in fig. 58. The phase equilibria are quite similar in both systems; no ternary compounds were observed. The binary silicides TiSi, TiSi₂, ZrSi and ZrSi₂ dissolve 12, 10, 22 and 11 at.% Sc, respectively. Scandium monosilicide dissolves 9 at.% Ti or 15 at.% Zr.



Fig. 58. (a) Sc-Ti-Si, and (b) Sc-Zr-Si parts of the isothermal sections at 800°C (50-100 at.% Si).



Fig. 59. Sc-Hf-Si, isothermal section at 800°C.

## 3.6.11. Sc-Hf-Si

Kotur et al. (1989b) reported on a part of the Sc–Hf–Si isothermal section at 800°C (50–100 at.% Si). Later Kotur and Ratush (1991) investigated the isothermal section over the whole concentration region (see fig. 59). No ternary compounds exist in this system. The hafnium silicides Hf₂Si, Hf₃Si₂, Hf₅Si₄, HfSi and HfSi₂ dissolve 25, 10, 33, 10 and 24 at.% Sc, respectively. ScSi dissolves 33 at.% Hf. Continuous series of solid solutions occur between the isotypic silicides Hf₅Si₃ and Sc₅Si₃. The variations of the lattice spacings of these solid solutions were measured by Kotur and Ratush.

#### 3.6.12. Sc-V-Si

Kotur et al. (1983a) investigated alloys of the section  $Sc_5Si_3-V_5Si_3$ , and later Kotur (1987) published the phase equilibria at 800°C for the whole concentration range (fig. 60). Three ternary compounds were synthesized and their crystal structures determined (see table 19). One of the compounds, namely  $ScV_5Si_5$ , has variable content of Sc and V within 2 at.%.

#### 3.6.13. Sc-Nb-Si

The Sc–Nb–Si isothermal section at 800°C presented in fig. 61 has been reported by Kotur (1986). Solid solution of substitution  $Sc_{5-1.5}Nb_{0-3.5}Si_3$  occurs in the system. The variation of the lattice parameters show negative deviation from Vegard's rule. Other binary scandium and niobium silicides do not dissolve the third component. Two ternary compounds exist in the system. Probably  $Sc_{0.4}Nb_{4.6}Si_3$  is a solid solution of the binary



Fig. 60. Sc-V-Si, isothermal section at 800°C. Ternary compounds: (1) ScV₅Si₅; (2) Sc₂V₃Si₄; (3) Sc₂V₃Si₃.



Fig. 61. Sc-Nb-Si, isothermal section at 800°C. Ternary compounds: (1) Sc_{0.4}Nb_{4.6}Si₃; (2) Sc₂Nb₃Si₄.

 $\beta Nb_5Si_3$  compound (which occurs in the Nb–Si system in the temperature range 2480–2000°C) stabilized by scandium.



Fig. 62. Sc-Ta-Si, isothermal section at 800°C.

# 3.6.14. Sc-Ta-Si

Figure 62 displays the isothermal section of the Sc–Ta–Si system at 800°C reported by Kotur and Bodak (1990). Binary tantalum and scandium silicides (except  $Sc_5Si_3$ ) practically do not dissolve the third component.  $Sc_5Si_3$ dissolves less than 2 at.% Ta. No ternary compounds were observed.

## 3.6.15. Sc-Cr-Si

Kotur and Bodak (1987) investigated the Sc-Cr-Si isothermal section at 800°C (see fig. 63). The scandium silicide  $Sc_5Si_3$  dissolves up to 2 at.% Cr. Three ternary compounds were synthesized and their crystal structures determined, the data are given in table 19.

## 3.6.16. Sc-Mo-Si

The Sc-Mo-Si isothermal section at 800°C, which is based on the data of Kotur and Bodak (1988), is displayed in fig. 64. Only one binary compound, namely  $Sc_5Si_3$ , dissolves the third component: 25 at.% Mo. The lattice spacings change linearly within the homogeneity range of the solid solution. One ternary compound exists in this system, its crystal structure data are given in table 19.

### 3.6.17. Sc-W-Si

The phase equilibria of the Sc–W–Si system at 800°C presented in fig. 65 are similar to those of Sc–Mo–Si system (Kotur et al., 1989a). The solubility of W in  $Sc_5Si_3$  is about



4 at.%. The single ternary compound has variable content of Sc and W; it is isotypic with Sm₅Ge₄ (table 19).

Fig. 64. Sc-Mo-Si, isothermal section at 800°C. Ternary compound: (1) Sc₂Mo₃Si₄.

Mo₃Si

Мо

Sc₅Si₃

Sc



Fig. 65. Sc-W-Si, isothermal section at 800°C. Ternary compound: (1) Sc₂₋₃W₃₋₂Si₄.

## 3.6.18. Sc-Mn-Si

Kotur et al. (1977b, 1980) reported on a part of the Sc–Mn–Si isothermal section at 800°C. A figure of this section is available in the review of Rogl (1984b). Among the binary compounds only  $ScMn_2$  dissolves up to 20 at.% Si; the lattice parameters of this solid solution obey Vegard's rule within the homogeneity range. Four ternary compounds of constant compositions occur in this system, the crystal structures of all of them are known (see table 19).

### 3.6.19. Sc-Re-Si

Pecharsky (1979) and Bodak et al. (1981) each reported about parts of the phase equilibria of the Sc–Re–Si system at 800°C namely in the ranges 0–66.7 at.% Sc and 0–33.3 at.% Sc, respectively. ScRe₂ dissolves about 21 at.% Si. The lattice parameters of the solid solution decrease linearly (from a=5.28, c=8.58 to a=5.17, c=8.39 Å) within the homogeneity range. Five ternary compounds were synthesized and the crystal structures of three of them: Sc₂Re₃Si₄, ScRe₂Si₃ and Sc₃Re₂Si₃ were determined by Pecharsky et al. (1978, 1979). The structures of the two other ScReSi₂ and ~Sc₈Re₃Si₉ were not reported. The single crystal investigation of Chabot and Parthé (1985) did not confirm the existence of compound "Sc₃Re₂Si₃" at 800°C, it revealed a composition of Sc₃Re₂Si₄. As a result of precised single crystal investigations the compositions and crystal structures of two other compounds were refined: "ScRe₂Si₃" to Sc₅Re₈Si₁₂ (Chabot and Parthé, 1987) and "Sc₈Re₃Si₉" to Sc₇Re_{3.35}Si_{10.65} (Zhao et al., 1988). The crystal structure data of these compounds are presented in table 19. A modified isothermal section at 800°C with the



Fig. 66. Sc–Re–Si, part of the isothermal section at 800°C (0–66.7 at.% Sc). Ternary compounds: (1)  $Sc_5Re_8Si_{12}$ ; (2)  $Sc_2Re_3Si_4$ ; (3) ~ScReSi₂; (4)  $Sc_3Re_2Si_4$ ; (5)  $Sc_7Re_{3.35}Si_{10.65}$ .

corrected compositions of the ternary compounds and corrections concerning the binary Re-Si system (according to the data of Massalski 1990) is shown in fig. 66.

#### 3.6.20. Sc-Fe-Si

The isothermal section at 800°C presented in fig. 67 has been investigated by Gladyshevsky et al. (1977). Fourteen ternary compounds occur at that temperature in the system. Twelve of them have a constant composition. The composition of three compounds were refined afterwards: "Sc₃Fe₂Si₆" to ScFeSi₂(II) (Yarmolyuk et al., 1980), "Sc₃Fe₃Si₄" to Sc₄Fe₄Si₇ (Chabot et al. (1984) and Kotur (1983) independently), and "ScFe₃Si₆" to  $Sc_{1,2}Fe_4Si_{9,8}$  (Kotur and Bruvo 1991). It is interesting to mention the existence of the ternary compound ScFeSi₂(I), which is in two-phase equilibria at 800°C with the ternary compounds ScFeSi₂(II), Sc₂Fe₃Si₅ and Sc₄Fe₄Si₇. Possibly the composition of the silicide  $ScFeSi_2(I)$  is slightly shifted from the ideal stoichiometry; additional investigations are necessary to clarify this. Chabot et al. (1984) also found two other ternary compounds Sc₃Fe₂Si₃ and ScFeSi in the as-cast alloys and confirmed the results published by Kotur and Sikirica (1983) concerning the Sc₂FeSi₂ compound. The phase equilibria presented in fig. 67 include all the corrections mentioned above. The crystal structure data of the ternary compounds are summarized in table 19. A recently performed X-ray structure analysis of compound 12 in fig. 67 conducted by Kotur et al. (1998) revealed that this compound does not crystallize in a superstructure of the Mg₂Cu₃Si-type as reported earlier by Gladyshevsky et al. (1977) and Kotur (1977b), but shows a random distribution



Fig. 67. Sc-Fe-Si, isothermal section at 800°C. Ternary compounds: (1)  $Sc_{0.35}Fe_{4.65}Si_3$ ; (2)  $ScFe_{10}Si_2$ ; (3)  $Sc_{1.2}Fe_4Si_{9.8}$ ; (4)  $\sim$ ScFe_5Si_3; (5) ScFe_4Si_2; (6) ScFe_2Si_2; (7) Sc_2Fe_3Si_5; (8) ScFeSi_2(I); (9) ScFeSi_2(II); (10) Sc_4Fe_4Si_7; (11) Sc_{1-1.09}Fe_{1.97-1.82}Si_{0.06-0.12}; (12) ScFe_{1.5-1.42}Si_{0.5-0.58}; (13) ScFe_{0.25}Si_{1.75}; (14) Sc_2FeSi_2; (15) ScFeSi; (16) Sc_3Fe_2Si_3.

of Fe and Si atoms on the two crystallographic sites in the MgZn₂-type structure. For that reason the composition is  $ScFe_{1.5}Si_{0.5}$ , and not  $Sc_2Fe_3Si$  as in the earlier publications.

# 3.6.21. Sc-Co-Si

Figure 68 presents the Sc–Co–Si isothermal section at 800°C (and a part of it at 700°C) investigated by Kotur et al. (1977a). ScCo₂ dissolves 6 at.% Si. The lattice parameter *a* of this solid solution increases linearly from 6.911 to 6.920 Å within the alloys on the isoconcentrate of 33.3 at.% Sc (Kotur 1977a). Kotur et al. confirmed the occurrence of two ternary compounds  $ScCo_2Si_2$  and  $Sc_6Co_{16}Si_7$  and synthesized ten new ternary silicides (see table 19). In the later papers the compositions of two ternary compounds have been refined: "ScCo₇Si₄" to  $Sc_6Co_{30}Si_{19}$  (Kotur and Sikirica 1991), and "Sc₃Co₂Si₅" to  $Sc_5Co_4Si_{10}$  (Braun et al. 1980). The phase equilibria shown in fig. 68 include all these refinements. Kotur et al. (1998) corrected the crystal structure of compound 7 in fig. 68 to the MgZn₂-type instead of the superstructure Mg₂Cu₃Si-type as reported earlier (see Kotur 1977b). The compound  $Sc_2Co_{0.85}Si_{0.15}$  exists only in alloys annealed at 800°C; perhaps it is formed by a solid-state phase reaction.

#### 3.6.22. Sc-Ni-Si

In a systematic investigation of the Sc-Ni-Si phase equilibria at 800°C in the range 0-70 at.% Sc performed by Bodak et al. (1976) fifteen ternary compounds have been



Fig. 68. Sc–Co–Si, part of the isothermal sections at 800°C and at 700°C (0–70 at.% Sc). Ternary compounds: (1)  $Sc_6Co_{30}Si_{19}$ ; (2)  $\sim$ Sc_4Co₁₄Si₉; (3)  $Sc_6Co_{16}Si_7$ ; (4)  $ScCo_2Si_2$ ; (5)  $Sc_2Co_3Si_5$ ; (6)  $Sc_5Co_4Si_{10}$ ; (7)  $ScCo_{1.52-1.46}Si_{0.48-0.54}$ ; (8) ScCoSi; (9)  $ScCo_{0.25}Si_{1.75}$ ; (10)  $Sc_3Co_2Si_3$ ; (11)  $Sc_2CoSi_2$ ; (12)  $Sc_2Co_{0.85}Si_{0.15}$ .

synthesized (fig. 69); two of these ternary compounds, namely  $ScNi_2Si_2$  and  $Sc_6Ni_16Si_7$ had been known earlier (see table 19). Further investigations revealed a change of the compositions of six ternary compounds observed by Bodak et al.: (2) " $Sc_{15}Ni_{62.5}Si_{22.5}$ " (Kotur et al. 1983b), (3) " $Sc_{17.5}Ni_{30}Si_{52.5}$ " (Kotur et al. 1978), (4) " $Sc_{15}Ni_{50}Si_{35}$ " (Kotur et al. 1986d), (12) " $Sc_{35}Ni_{20}Si_{45}$ " (Zhao and Parthé 1989a,b), (13) " $Sc_{32}Ni_8Si_{60}$ " (Kotur and Bodak 1977), (15) " $Sc_{44}Ni_{12}Si_{44}$ " (Kotur and Gladyshevsky 1983). Their crystal structure data can be found in table 19. The phase equilibria at 800°C are presented in fig. 69 assuming these refinements. The binary  $ScNi_2$  compound dissolves a large amount of the third component: about 7 at.% Si. The lattice spacing of the solid solution increases linearly from a = 6.901 to 6.909 Å (Kotur 1977a). Other Sc–Ni binary compounds dissolve less than 2 to 3 at.% Si.

#### 3.6.23. Sc-Ru-Si

No data are known about the phase equilibria occurring in the Sc-Ru-Si system. Only two ternary compounds have been synthesized and their crystal structures investigated (see table 19).

## 3.6.24. Sc-Rh-Si

Braun et al. (1979) investigated a part of the Sc-Rh-Si isothermal section at 1000°C (44-100 at.% Si); the figure can be found in Rogl (1984b). Nine ternary compounds



Fig. 69. Sc–Ni–Si, part of the isothermal section at 800°C (0–70 at.% Sc). Ternary compounds: (1)  $\sim$ Sc₂Ni₃Si₃; (2) Sc₃Ni₁₁Si₄; (3) ScNi₂Si₃; (4) Sc₆Ni₁₈Si₁₁; (5) Sc₆Ni₁₆Si₇; (6)  $\sim$ Sc₂Ni₅Si₃; (7) ScNi₂Si₂; (8) ScNiSi₃; (9) Sc₃Ni₄Si₄; (10) ScNi_{1.52–1.49}Si_{0.48–0.51}; (11) ScNiSi; (12) Sc₃Ni₂Si₄; (13) ScNi_{0.25}Si_{1.75}; (14) Sc₃Ni₂Si₃; (15) Sc₃NiSi₃.

were observed. Hovestreydt et al. (1982) reported about the existence of another one, ScRhSi. Chabot et al. (1981b) refined the composition of the "ScRh₃Si₆" compound to ScRh₃Si₇ and determined its crystal structure. But the proper compositions and the crystal structures of six other ternary compounds remain still unknown (see table 19). Braun et al. also investigated a part of the phase equilibria at 800 and 1150°C. These investigations revealed that ScRhSi₂ is not in equilibrium with Si at 1150°C, and the ternary compound Sc₅Rh₄Si₁₀ does not exist at 800°C; furthermore it is shown that the silicides Sc₄RhSi₈ and ScRhSi₂ are in equilibrium.

## 3.6.25. Sc-Pd(Os, Ir, Pt)-Si

There are no literature data about the phase equilibria of the Sc–Pd(Os, Ir, Pt)–Si systems. Only one ternary compound within each system (except Sc–Ir–Si) were observed by the examination of separate alloys for isotypic compounds existing in related ternary systems. In the Sc–Ir–Si system four ternary compounds were obtained. Their compositions and the crystal structure data are collected in table 19.

## 3.6.26. Sc-Cu-Si

According to the investigation of Kotur et al. (1985b) there are insignificant differences in the phase equilibria at 600 and 800°C of the Sc–Cu–Si system (see fig. 70). Five ternary compounds occur in the system. Two of them, Sc₃Cu₄Si₄ and ScCuSi(h), had been known



Fig. 70. Sc–Cu–Si, isothermal sections at (a) 600°C and (b) 800°C. Ternary compounds: (1) ScCu₂Si₂; (2)  $Sc_3Cu_4Si_4$ ; (3) ScCuSi(h); (4) ScCuSi(r); (5) Sc₂Cu_{0.8}Si_{0.2}.

earlier. The crystal structures are established for all compounds (see table 19). Two ternary phases ScCuSi(h) and  $Sc_2Cu_{0.8}Si_{0.2}$  appear only after a long-term homogenization of alloys, whereas three other ternary silicides were observed also in the as-cast alloys. Two ternary compounds with compositions close to equiatomic coexist in the system (Kotur et al. 1981). They are separated by a narrow two-phase region, thus a detailed investigation is necessary to find out their proper compositions.

# 3.6.27. Sc-Ag-Si

No ternary compound was observed by Kotur and Boichuk (1988) in the Sc–Ag–Si isothermal section at 600°C, which is shown in fig. 71. These results agree with those of Iandelli (1985), who investigated the alloy of equiatomic composition and established the existence of two phases.



# 3.6.28. Sc-Au-Si

One ternary compound ScAuSi has been synthesized and its crystal structure was determined by Fornasini et al. (1992) (see table 19). There are no data about the phase equilibria in this system.

### 3.7. Sc-M-Ge ternary systems

# 3.7.1. Sc-Li-Ge

The only data about the Sc-Li-Ge system concerns the ScLiGe ternary compound. Its crystal structure is presented in table 20 (overleaf). The phase diagram is unknown.

#### 3.7.2. Sc-Y-Ge

Shpyrka and Mokra (1991) published the isothermal section of the Sc–Y–Ge system at 600°C, which is shown in fig. 72. A continuous series of solid solutions occur between the isotypic binary compounds  $Sc_5Si_3$  and  $Y_5Si_3$ . Other binary germanides  $ScGe_2$ ,  $Sc_{11}Ge_{10}$ ,  $Y_2Ge_3$  dissolve 18, 8, and 10 at.% Y or Sc, respectively. Three ternary compounds have been found. The crystal structures were determined for two compounds (see table 20).



Fig. 72. Sc–Y–Ge, isothermal section at 600°C. Ternary compounds: (1)  $Sc_{0.3}Y_{0.7}Ge_2$ ; (2)  $Sc_{1.35}Y_{3.65}Ge_4$ ; (3)  $Sc_{2.7}Y_{2.3}Ge_4$ .

#### 3.7.3. Sc-La-Ge

Two Sc-La-Ge ternary compounds were synthesized, and their crystal structure data are given in table 20. There are no published data concerning the phase equilibria in this system.

# 3.7.4. Sc-Ce-Ge

Bodak and Kokhan (1983) investigated the Sc–Ce–Ge isothermal section at 600°C; fig. 73 is based on these data. Four ternary compounds exist in this system; the crystal structures

Compound	Structure type	Latt	ice parame	ters	Reference
	or symmetry	<i>a</i> (Å)	b (Å)	<i>c</i> (Å)	
ScLiGe	MgAgAs	6.407			Grund (1985)
$\sim Sc_{0.3}Y_{0.7}Ge_2$	?				Shpyrka and Mokra (1991)
$Sc_{1.35}Y_{3.65}Ge_4$	Sm₅Ge₄	7.440	14.31	7.578	Shpyrka and Mokra (1991)
Sc _{2.7} Y _{2.3} Ge ₄	$Sm_5Ge_4$	7.283	14.18	7.461	Shpyrka and Mokra (1991)
ScLaGe	ScCeSi	4.351		16.067	Bodak and Kokhan (1983)
$Sc_3La_{1.22}Ge_4$	$Ce_2Sc_3Si_4$	7.252	14.350	7.652	Shpyrka (1990)
~Sc ₂ Ce ₅ Ge ₆	?				Bodak and Kokhan (1983)
ScCeGe	ScCeSi	4.314		15.91	Bodak and Kokhan (1983)
$Sc_3Ce_{1.22}Ge_4$	$Ce_2Sc_3Si_4$	7.188	13.99	7.416	Shpyrka (1990),
					Bodak and Kokhan (1983)
$\sim$ Sc _{4.5} Ce _{0.5} Ge ₄	?				Bodak and Kokhan (1983)
ScPrGe	ScCeSi	4.325		15.874	Bodak and Kokhan (1983)
$Sc_3Pr_{1.22}Ge_4$	$Ce_2Sc_3Si_3$	7.116	14.059	7.576	Shpyrka (1990)
$\sim Sc_2Nd_5Ge_6$	?				Shpyrka (1990)
ScNdGe	ScCeSi	4.3106		15.823	Bodak and Kokhan (1983), Shpyrka (1990)
		4.3022		15.788	Bodak et al. (1997)
$Sc_3Nd_{1.22}Ge_4$	$Ce_2Sc_3Si_4$	7.119	14.065	7.574	Shpyrka (1990)
		7.204	13.925	7,474	Bodak et al. (1997)
ScSmGe	ScCeSi	4.264		15.623	Bodak and Kokhan (1983)
Sc ₃ Sm _{1.22} Ge ₄	$Ce_2Sc_3Si_4$	7.102	14.020	7.546	Shpyrka (1990)
ScEuGe	ScCeSi	4.270		15.636	Shpyrka (1990)
~Sc _{0.3} Dy _{0.7} Ge ₂	?				Shpyrka and Mokra (1991)
Sc _{1.8} Dy _{3.2} Ge ₄	$Sm_5Ge_4$	7.346	14.295	7.555	Shpyrka and Mokra (1991)
Sc _{2.7} Dy _{2.3} Ge ₄	Sm ₅ Ge ₄	7.260	14.151	7.477	Shpyrka and Mokra (1991)
$\sim$ Sc _{0.3} Yb _{0.7} Ge ₂	?				Kotur and Mokra (1995)
$Sc_6Yb_5Ge_{10}$	$Ho_{11}Ge_{10}$	10.505		15.87	Kotur et al. (1996b)b*; Kotur and Mokra (1995)
Sc _{1-1.8} V _{5-4.2} Ge ₅	Ti ₆ Ge ₅	7.782-	16.59-	5.091-	Kotur (1987)
		7.890	16.73	5.157	
$Sc_2V_3Ge_4$	$Ce_2Sc_3Si_4$	6.614	12.774	6.776	<i>Kotur et al. (1986c),</i> Kotur (1987)
Sc ₂ Nb ₃ Ge ₄	$Ce_2Sc_3Si_4$	6.860	13.39	7.160	Kotur (1986)
$Sc_{2-3}Ta_{3-2}Ge_4$	$\mathrm{Sm}_5\mathrm{Ge}_4$	6.823– 6.855	13.177– 13.230	6.977– 6.993	Kotur and Bodak (1990)
$ScCr_6Ge_6$	HfFe ₆ Ge ₆	5.101		8.229	Andrusyak (1986), Kotur et al. (1988b)
$Sc_2Cr_4Ge_5$	$Nb_2Cr_4Si_5$	7.821	16.662	5.146	Kotur et al. (1988b)

Table 20 Intermetallic compounds in the Sc-M-Ge ternary systems

continued on next page

		Table	20, comini	<i>ieu</i>	
Compound	Structure type	Latt	ice parame	ters	Reference
	or symmetry	a (Å)	b (Å)	c (Å)	-
ScCrGe ₂	ZrCrSi ₂	9.390	10.142	8.135	Kotur et al. (1988b)
		9.37	10.09	8.13	Venturini et al. (1985)
Sc ₇ Cr _{5.2} Ge _{8.8}	$Sc_7Cr_{4+x}Si_{10-x}$	10.150		14.352	Kotur et al. (1988a,b)
$Sc_{2\!-\!4}Mo_{3\!-\!1}Ge_4$	$\mathrm{Sm}_5\mathrm{Ge}_4$	6.691- 6.813	12.872– 13.285	6.905– 7.027	Kotur and Bodak (1988)
$ScMn_6Ge_6$	HfFe ₆ Ge ₆	5.176		8.099	Andrusyak (1986), Andrusyak and Kotur (1991)
$ScMn_6Ge_4$	$ZrFe_6Ge_4$	5.066		20.013	Kotur (1995), Andrusyak and Kotur (1991)
$\sim Sc_5 Mn_7 Ge_8$	?				Andrusyak and Kotur (1991)
ScMnGe ₂	ZrCrSi ₂	9.342	10.191	8.083	Andrusyak and Kotur (1991)
-	-	9.30	10.13	8.06	Meyer et al. (1983)
ScMnGe	ZrNiAl	6.677		3.946	Kotur and Andrusyak (1984a), Andrusyak and Kotur (1991)
$Sc_7Mn_{5.3}Ge_{8.7}$	$\mathrm{Sc}_7\mathrm{Cr}_{4+x}\mathrm{Si}_{10-x}$	9.951		14.168	Kotur et al. (1988a), Andrusyak and Kotur (1991)
ScReGe ₂	ZrCrSi ₂	9.385	10.173	8.323	Kotur (1995)
2	-	9.39	10.17	8.32	Venturini et al. (1985)
ScFe ₆ Ge ₆	HfFe ₆ Ge ₆	5.062		8.056	Andrusyak (1986)
	• •	5.069		8.077	Andrusyak and Kotur (1991)
ScFe ₆ Ge₅	$ScFe_6Ge_5$	5.0631		44.11	Kotur (1995), Andrusyak and Kotur (1991)
$ScFe_6Ge_4$	$ZrFe_6Ge_4$	5.066		20.013	Kotur (1995), Andrusyak and Kotur (1991)
ScFeGe ₂	ZrCrSi ₂	9.227	10.098	8.263	Andrusyak and Kotur (1991)
		9.22	10.09	8.00	Venturini et al. (1985)
$\mathrm{Sc}_{4}\mathrm{Fe}_{4}\mathrm{Ge}_{6.6}$	$Zr_4Co_4Ge_7$	13.296		5.235	Andrusyak and Kotur (1989), Andrusyak and Kotur (1991)
$Sc_{1-1.17}Fe_{1.94-1.70}$ $Ge_{0.06-0.30}$	MgCu ₂	7.060ª			Andrusyak and Kotur (1991)
ScFe _{1.5} Ge _{0.5}	MgZn ₂	5.006		8.147	Andrusyak and Kotur (1991)
ScFeGe	ZrNiAl	6.547		3.895	Kotur and Andrusyak (1984a), Andrusyak and Kotur (1991)
$ScCo_6Ge_6$	HfFe ₆ Ge ₆	5.064		7.778	Andrusyak (1986), Kotur and Andrusyak (1991)
		5.056		7.799	Buchholz and Schuster (1981)
$\sim$ Sc ₄ Co ₁₁ Ge ₅	?				Kotur and Andrusyak (1991)
$Sc_4Co_7Ge_6$	$U_4 Re_7 Si_6$	7.850			Kotur and Andrusyak (1991)

Table 20, continued

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		Tuole	20, continu		
Compound	Structure type	Lattice parameters			Reference
	or symmetry	<i>a</i> (Å)	b (Å)	c (Å)	
ScCoGe ₂	ZrCrSi ₂	9.186	10.102	7.958	Kotur and Andrusyak (1991)
		9.19	10.09	7.96	Venturini et al. (1985)
$Sc_4Co_4Ge_6$	$Zr_4Co_4Ge_7$	13.215		5.229	Andrusyak and Kotur (1989), Kotur and Andrusyak (1991)
ScCoGe	TiNiSi	6.495	4.000	7.072	Kotur and Andrusyak (1984a), Kotur and Andrusyak (1991)
$Sc_2CoGe_2$	$Sc_2CoSi_2$	9.595	9.828 $\gamma = 123.2^{\circ}$	3.914	Kotur and Andrusyak (1991)
Sc ₃ Co ₂ Ge ₃	$Hf_3Ni_2Si_3$	4.078	9.930	13.243	Kotur and Andrusyak (1991)
ScNi ₆ Ge ₆	$ScNi_6Ge_6$	10.158		7.816	Andrusyak (1986), Kotur and Andrusyak (1991)
		10.152		7.813	Buchholz and Schuster (1981)
$Sc_{12.3}Ni_{40.7}Ge_{31}$	$Sc_{12.3}Ni_{40.7}Ge_{31}$	17.865		8.220	<i>Bodak et al. (1990),</i> Kotur and Andrusyak (1991)
$Sc_3Ni_{11}Ge_4$	$Sc_3Ni_{11}Ge_4$	8.130		8.505	<i>Andrusyak (1988),</i> Kotur and Andrusyak (1991)
$Sc_6Ni_{18}Ge_{11}$	$\mathbf{Sc}_{6}\mathbf{Ni}_{18}\mathbf{Si}_{11}$	18.322	12.461	8.191	Andrusyak and Kotur (1987), Kotur and Andrusyak (1991)
$Sc_6Ni_{16}Ge_7$	$\mathbf{Mg}_{6}\mathbf{Cu}_{16}\mathbf{Si}_{7}$	11.654			GIMK, 62; Kotur and Andrusyak (1991)
		11.663			Dwight et al. (1963a)
$Sc_3Ni_4Ge_4$	Gd ₆ Cu ₈ Ge ₈	12.910	6.598	3.908	Kotur and Sikirica (1982b), Kotur and Andrusyak (1991)
ScNiGe	TiNiSi	6.454	4.071	7.068	Kotur and Andrusyak (1984a), Kotur and Andrusyak (1991)
~Sc ₁₃ Ni ₆ Ge ₁₅	?				Kotur and Andrusyak (1991)
Sc ₄ Ni ₄ Ge ₆₂	$Zr_4Co_4Ge_7$	13.276		5.225	Andrusyak and Kotur (1989)
Sc ₉ Ni ₅ Ge ₈	Sc ₉ Ni ₅ Ge ₈	20.426	9.129	3.9822	Kotur et al. (1989d)
Sc ₄ Ru ₇ Ge ₆	U ₄ Re ₇ Si ₆	8.129			Engel et al. (1984)
ScRuGe ₂	ZrCrSi ₂	9.28	10.32	8.12	Venturini et al. (1985)
ScRuGe	ZrNiAl	6.962		3.4683	Hovestreydt et al. (1982)
Sc₄Rh ₇ Ge ₆	U4Re7Si6	8.1255			Engel et al. (1984)
ScRhGe,	ZrCrSi ₂	9.302	10.359	8.146	Parthé and Chabot (1984)
ScRhGe (I)	TiNiSi	6.497	4.112	7.385	Hovestreydt et al. (1982)
ScRhGe (II)	ZrNiAl	6.672		3.794	Hovestreydt et al. (1982)
ScPdGe	ZrNiAl	6.7153		3.9250	Hovestreydt et al. (1982)
Sc ₄ Os ₇ Ge ₆	$U_4 Re_7 Si_6$	8.146			Engel et al. (1984)
ScOsGe,	ZrCrSi ₂	9.29	10.33	8.17	Venturini et al. (1985)
ScOsGe	ZrNiAl	6.928		3.467	Hovestreydt et al. (1982)
					_

Table 20, continued

continued on next page

Table 20, continued						
Compound	Structure type	Latt	ice parame	ters	Reference	
	or symmetry	a (Å)	b (Å)	c (Å)	-	
Sc ₄ Ir ₇ Ge ₆	U ₄ Re ₇ Si ₆	8.136			Engel et al. (1984)	
ScIrGe	TiNiSi	6.446	4.107	7.482	Hovestreydt et al. (1982)	
Sc ₃ Cu ₄ Ge ₄	Gd ₆ Cu ₈ Ge ₈	13.32	6.523	4.004	Kotur and Andrusyak (1984b)	
		13.30	6.516	3.996	Thirion et al. (1983)	
ScCuGe	ZrNiAl	6.510		3.998	Kotur and Andrusyak (1984b)	
		6.514		3.972	Dwight (1968)	
ScAgGe	ZrNiAl	6.882		4.026	Kotur and Bodak (1988)	

^a For the composition  $ScFe_{1.79}Ge_{0.21}$ .



Fig. 73. Sc–Ce–Ge, isothermal section at 600°C. Ternary compounds: (1)  $\sim$ Sc₂Ce₅Ge₆; (2) ScCeGe; (3) Sc₃Ce_{1.22}Ge₄; (4)  $\sim$ Sc_{4.5}Ce_{0.5}Ge₄.

are known for two of them (see table 20). Shpyrka (1990) refined the composition of compound "Sc₂CeGe₃" to Sc₃Ce_{1.22}Ge₄. This correction has been taken into account in fig. 73.

# 3.7.5. Sc-Pr(Sm)-Ge

In both the Sc–Pr–Ge and Sc–Sm–Ge ternary systems two ternary compounds of the same compositions and crystal structures occur (table 20). The phase equilibria have not been investigated.

#### 3.7.6. Sc-Nd-Ge

The Sc–Nd–Ge phase equilibria at 600°C investigated by Bodak and Kokhan (1983) (presented in fig. 74), are similar to those of the system with cerium. However, the mutual solubility of Sc and Nd in the binary germanides reaches 10 at.% which is considerably higher than the solubility of Sc and Ce in binary germanides. Three ternary compounds are known in this system. The crystal structure data for two of them are given in table 20. However, the same group of authors reported different values for the lattice parameters for these compounds in different papers (see table 20).



Fig. 74. Sc-Nd-Ge, isothermal section at 600°C. Ternary compounds: (1)  $\sim$ Sc₂Nd₅Ge₆; (2) ScNdGe; (3) Sc₃Nd_{1.22}Ge₄.

# 3.7.7. Sc-Eu-Ge

The only ternary compound synthesized in the system, ScEuGe, belongs to the ScCeSi structure type (Shpyrka 1990) (see table 20). The phase diagram is still unknown.

#### 3.7.8. Sc--Dy-Ge

As can be seen from fig. 75 which shows the phase equilibria in the Sc–Dy–Ge system at 600°C, there are many similarities with the Sc–Y–Ge system. Three ternary compounds of similar compositions and crystal structures occur in both systems (see table 20); these data were taken from Shpyrka and Mokra (1991).

## 3.7.9. Sc-Yb-Ge

The Sc-Yb-Ge isothermal section at 400°C investigated by Kotur and Mokra (1995) is presented in fig. 76. The immiscibility gap occurring in the Sc-Yb binary system spreads



Fig. 75. Sc–Dy–Ge, isothermal section at 600°C. Ternary compounds: (1)  $Sc_{0.3}Dy_{0.7}Ge_2$ ; (2)  $Sc_{1.8}Dy_{3.2}Ge_4$ ; (3)  $Sc_{2.7}Dy_{2.3}Ge_4$ .



Fig. 76. Sc–Yb–Ge, isothermal section at 400°C. Ternary compounds: (1)  $\sim$ Sc_{0.3}Yb_{0.7}Ge₂; (2) Sc₆Yb₅Ge₁₀.

into the ternary system up to about 30 at.% Ge. The  $Yb_3Ge_5$  (Th₃Pd₅ type) germanide dissolves about 6 at.% Sc. Large amounts of Yb (8 and 20 at.%) dissolve in the ScGe₂

and the  $Sc_5Ge_3$  compounds, respectively. Two ternary compounds were observed in this system (table 20). For one of them,  $Sc_6Yb_5Ge_{10}$  the crystal structure has been determined by Kotur et al. (1996b), it crystallizes in the  $Ho_{11}Ge_{10}$  type of structure, the same as  $Sc_{11}Ge_{10}$ , however with a partial disorder of the Sc and the Yb atoms on the rare-earth sites.

#### 3.7.10. Sc-Hf-Ge

Kotur (1991) studied the Sc-Hf-Ge isothermal section at 800°C, which is shown in fig. 77. Ternary compounds do not occur. Isotypic pairs of binary germanides  $ScGe_2$ -HfGe_2,  $Sc_5Ge_4$ -Hf_5Ge_4 and  $Sc_5Ge_3$ -Hf_5Ge_3 are completely miscible. Other Sc and Hf binary germanides dissolve appreciable quantities of the third component.



Fig. 77. Sc--Hf--Ge, isothermal section at 800°C.

## 3.7.11. Sc-V-Ge

The isothermal section at 800°C, which was determined by Kotur (1987), can be found in the review of Gladyshevsky et al. (1990). In contrast to the previous system the mutual solubility of Sc and V in the binary germanides is low and does not exceed 1 to 3 at.%. Kotur et al. (1983a) found a single crystal isotypic with Sc₅Ge₃ in one of the ternary as-cast alloys. Its lattice spacings are a = 7.43, c = 5.02 Å, but the proper composition is unknown. These data (Kotur 1987, Kotur et al. 1983a) indicate the large solubility of Sc in V₅Ge₃ and V in Sc₅Ge₃ at elevated temperatures. Two ternary compounds occur in the system. Their crystal structure data are in table 20.

## 3.7.12. Sc-Nb-Ge

The isothermal section at 800°C of the Sc–Nb–Ge system has been studied by Kotur (1986). The figure is presented also in Gladyshevsky et al. (1990). A solid solution of Nb in Sc₅Ge₃ has been observed, Sc_{5–1.2}Nb_{0–3.8}Ge₃. The lattice parameters vary nonlinearly within the homogeneity range reaching the values of a = 7.752, c = 5.365Å at Sc_{1.2}Nb_{3.8}Ge₃. One ternary compound, Sc₂Nb₃Ge₄, which is isotypic with Sc₃Ce₂Si₄, exists in this system (table 20).

# 3.7.13. Sc-Ta-Ge

Kotur and Bodak (1990) investigated the Sc–Ta–Ge isothermal section at 800°C which is displayed in fig. 78. The system is similar to the Nb-based one, however the solubility of Ta in Sc₅Ge₃ is lower. The variation of the lattice parameters vs. composition of the solid solution  $Sc_{5-3.25}Ta_{0-1.75}Ge_3$  does not obey Vegard's rule, exhibiting a negative deviation. The only ternary compound, isotypic with Sm₅Ge₄ has a variable Sc and Ta content. Its lattice spacings display a positive deviation from Vegard's rule. The limiting values of the lattice parameters are given in table 20.



Fig. 78. Sc-Ta-Ge, isothermal section at 800°C. Ternary compound: (1) Sc₂₋₃Ta₃₋₂Ge₄.

#### 3.7.14. Sc-Cr-Ge

The isothermal section at 800°C of the Sc–Cr–Ge system has been studied by Kotur et al. (1988b) (fig. 79). The binary  $Sc_5Ge_3$  germanide dissolves 7.5 at.% Cr. A positive deviation from Vegard's rule is observed for the lattice parameters of this solid solution. Four ternary compounds exist in this system, their crystal structure data are shown in table 20. The compound ScCrGe₂ (3) has been synthesized independently by Kotur et al. (1988b) and Venturini et al. (1985).



Fig. 79. Sc–Cr–Ge, isothermal section at 800°C. Ternary compounds: (1) ScCr₆Ge₆; (2) Sc₂Cr₄Ge₅; (3) ScCrGe₂; (4) Sc₇Cr_{5.2}Ge_{8.8}.

3.7.15. Sc-Mo-Ge Figure 80 displays the Sc-Mo-Ge isothermal section at 800°C according to the



Fig. 80. Sc-Mo-Ge, isothermal section at 800°C. Ternary compound: (1) Sc₂₋₄Mo₃₋₁Ge₄.

data of Kotur and Bodak (1988). The binary scandium and molybdenum germanides practically do not dissolve the third component at 800°C. Only  $Sc_5Ge_3$  forms a solid solution,  $Sc_{5-4.92}Mo_{0-0.08}Ge_3$ . One ternary compound isotypic with  $Sm_5Ge_4$  occurs:  $Sc_{2-4}Mo_{3-1}Ge_4$  with a variable content of Sc and Mo (table 20). It is separated by a two-phase region from the binary  $Sc_5Ge_4$  compound which crystallizes in the same structure.

## 3.7.16. Sc-W-Ge

The solubility of W in binary scandium germanides is not worth mentioning, except for  $Sc_5Ge_3$ , where a solid solution of up to 3 at.% W exists:  $Sc_{5-4.76}W_{0-0.24}Ge_3$ . No ternary compounds were observed in the ternary Sc–W–Ge system (fig. 81, Kotur et al. 1989a).



Fig. 81. Sc-W-Ge, isothermal section at 800°C.

# 3.7.17. Sc-Mn-Ge

Andrusyak and Kotur (1991) investigated a part of the Sc–Mn–Ge isothermal section at 600°C, which is presented in fig. 82. One ternary compound known earlier, ScMnGe₂ (Meyer et al. 1983), has been confirmed, and five new ternary compounds have been obtained by Andrusyak and Kotur (see table 20). Later Kotur (1995) refined the composition of one compound, "ScMn₅Ge₃" to ScMn₆Ge₄. This refinement was taken into account in fig. 82. The binary scandium germanides ScGe₂, Sc₁₁Ge₁₀ and Sc₅Ge₄ dissolve 4, 2 and 3 at.% Mn, respectively. The other binary germanides do not dissolve appreciable quantities of the third component.



Fig. 82. Sc-Mn-Ge, isothermal section at 600°C. Ternary compounds: (1) ScMn₆Ge₆; (2) ScMn₆Ge₄; (3)  $\sim$ Sc₅Mn₇Ge₈; (4) ScMnGe₂; (5) ScMnGe; (6) Sc₇Mn₅₃Ge₈₇.

## 3.7.18. Sc-Re-Ge

Venturini et al. (1985) reported about the ternary compound  $ScReGe_2$  isotypic with  $ZrCrSi_2$ . These data were confirmed by Kotur (1995). The lattice parameters reported in the two publications are in good agreement (table 20).

#### 3.7.19. Sc-Fe-Ge

The Sc–Fe–Ge isothermal section at 600°C has been published by Andrusyak and Kotur (1991). All together eight ternary compounds were observed. Two of them, ScFe₆Ge₆ and ScFeGe₂ were synthesized earlier by Olenych et al. (1981) and Venturini et al. (1985), respectively. Using X-ray diffraction Kotur (1995) refined the compositions of two ternary compounds reported by Andrusyak and Kotur: "ScFe₅Ge₃" to ScFe₆Ge₄ and "ScFe₅Ge₄" to ScFe₆Ge₅. The crystal structure data of the ternary compounds are given in table 20. Figure 83 shows an isothermal section at 600°C with the refined compositions of the ternary phases. Among binary scandium germanides only ScGe₂ and Sc₅Ge₃ dissolve a somewhat large amount of Fe: 6 at.%.

#### 3.7.20. Sc-Co-Ge

The first data about this system were reported by Buchholz and Schuster (1981) and later by Venturini et al. (1985) who synthesized the following ternary compounds,  $ScCo_6Ge_6$ and  $ScCoGe_2$ , respectively. Kotur and Andrusyak (1991) investigated the isothermal section at 600°C which is shown in fig. 84. Seven ternary compounds were observed,



Fig. 83. Sc-Fe-Ge, isothermal section at 600°C. Ternary compounds: (1) ScFe₆Ge₆; (2) ScFe₆Ge₅; (3) ScFe₆Ge₄; (4) ScFeGe₂; (5) Sc₄Fe₄Ge₆₆; (6) Sc_{1-1.17}Fe_{1.94-1.70}Ge_{0.06-0.30}; (7) ScFe_{1.5}Ge_{0.5}; (8) ScFeGe.



Fig. 84. Sc–Co–Ge, isothermal section at 600°C. Ternary compounds: (1)  $ScCo_6Ge_6$ ; (2)  $\sim Sc_4Co_{11}Ge_5$ ; (3)  $Sc_4Co_7Ge_6$ ; (4)  $ScCoGe_2$ ; (5)  $Sc_4Co_4Ge_6$ ; (6) ScCoGe; (7)  $Sc_2CoGe_2$ .

449

five of them for the first time (table 20). Single crystals of a new ternary compound,  $Sc_3Co_2Ge_3$  were extracted from the alloy cooled at a rate of 10–20°C/min (Kotur and Andrusyak). Maybe this germanide exists over a narrow temperature range, which was not determined. The binary compounds  $ScCo_2$ ,  $ScGe_2$ ,  $Sc_{11}Ge_{10}$ ,  $Sc_5Ge_4$ ,  $Sc_5Ge_3$  dissolve 11.5 at.% Ge, and 6, 4, 4, and 3 at.% Co, respectively. The lattice parameter *a* of the solid solution  $ScCo_{2-1.65}Ge_{0-0.35}$  varies linearly from 6.902 to 6.984 Å (Kotur and Andrusyak 1991). The lattice spacings of the  $ScCo_{0-0.18}Ge_{2-1.82}$  solid solution also obey Vegard's rule.

#### 3.7.21. Sc-Ni-Ge

The phase equilibria in the Sc–Ni–Ge system at 600°C have been investigated by Kotur and Andrusyak (1991) (see fig. 85). Eight ternary compounds occur at that temperature (table 20). From the as-cast samples single crystals of two other ternary compounds  $Sc_4Ni_4Ge_{6,2}$  and  $Sc_9Ni_5Ge_8$  have been extracted and their crystal structures have been determined by Andrusyak and Kotur (1989) and Kotur et al. (1989d), respectively (table 20). The binary scandium germanides dissolve from 2 to 8 at.% Ni, ScNi₂ dissolves about 3.5 at.% Ge.



Fig. 85. Sc-Ni-Ge, isothermal section at 600°C. Ternary compounds: (1) ScNi₆Ge₆; (2) Sc_{12.3}Ni_{40.7}Ge₃₁; (3) Sc₃Ni₁₁Ge₄; (4) Sc₆Ni₁₈Ge₁₁; (5) Sc₆Ni₁₆Ge₇; (6) Sc₃Ni₄Ge₄; (7) ScNiGe; (8)  $\sim$ Sc₁₃Ni₆Ge₁₅.

## 3.7.22. Sc-Ru(Rh, Pd, Os, Ir)-Ge

There are no literature data concerning the phase diagrams of Sc–M–Ge for M=Ru, Rh, Pd, Os, or Ir. From one to three ternary compounds have been synthesized in each of these

systems. Their crystal structure data are presented in table 20. The ScRhGe compound, possibly, occurs in two polymorphic modifications. The temperature of the phase transition is unknown.

#### 3.7.23. Sc-Cu-Ge

Kotur and Andrusyak (1984b) investigated the Sc–Cu–Ge isothermal section at 600°C; the figure is also shown in the review of Gladyshevsky et al. (1990). Two ternary compounds have been found (table 20). Dwight (1968) was the first to report on the ScCuGe compound. Another germanide,  $Sc_3Cu_4Ge_4$  was synthesized independently by Thirion et al. (1983) and Kotur and Andrusyak (1984b). The data on the lattice spacings of these ternaries obtained by different authors are in good agreement (table 20).

#### 3.7.24. Sc-Ag-Ge

One ternary compound, ScAgGe, exists at 600°C according to the data of Kotur and Boichuk (1988) (fig. 86, table 20). The mutual solubility of the components in Sc-Ag and Sc-Ge binary compounds is practically zero.



Fig. 86. Sc-Ag-Ge, isothermal section at 600°C. Ternary compound: (1) ScAgGe.

#### 3.8. Sc-M-Sn ternary systems

#### 3.8.1. *Sc–Li–Sn*

The data published by Grund (1985) about the ternary compound, ScLiSn, which is isotypic with MgAgAs (table 21) are the only data known for the Sc–Li–Sn system.

Compound	Structure type	Latt	ice parame	ters	Reference
	or symmetry	a (Å)	b (Å)	c (Å)	
ScLiSn	MgAgAs	6.748			Grund (1985)
ScMn ₆ Sn ₆	HfFe ₆ Ge ₆	5.474		8.973	Malaman et al. (1988)
ScFe ₆ Sn ₆	HfFe ₆ Ge ₆	5.330		8.845	Malaman et al. (1988)
$ScCo_6Sn_6$	YCo ₆ Ge ₆	5.3048		4.2734	Derkach and Kotur (1996)
ScCo _{1.1} Sn _{3.6}	tetr (?)	13.324ª			Espinosa et al. (1982)
ScCo ₂ Sn	MnCu ₂ Al	6.188			Kotur and Klyuchka (1989)
		6.187			Dwight and Kimball (1987)
ScCoSn	TiNiSi	6.773	4.402	7.339	Kotur and Klyuchka (1989)
ScNi ₄ Sn	$MgCu_4Sn$	6.897			Kotur and Klyuchka (1989)
ScNi ₂ Sn	MnCu ₂ Al	6.228			Kotur and Klyuchka (1989)
		6.214			Dwight and Kimball (1987)
ScNiSn	TiNiSi	6.625	4.333	7.536	Kotur and Klyuchka (1989)
Sc ₂ Ni ₂ Sn	$Mo_2FeB_2$	7.0928		3.3800	Derkach and Kotur (1994)
ScRu _{1.1} Sn _{3.6}	tetr (?)	13.567ª			Espinosa et al. (1982)
$ScRh_{1.1}Sn_{3.6}$	tetr (?)	13.567°			Espinosa et al. (1982), Cooper (1980)
ScPd ₂ Sn	MnCu ₂ Al	6.509			Johnson and Shelton (1984)
-		6.503			Malik et al. (1985)
ScPdSn (I)	ZrNiAl	7.471		3.537	Dwight et al. (1973)
ScPdSn (II)	TiNiSi	6.543	4.069	7.396	Hovestreydt et al. (1982)
ScOs ₁₁ Sn _{3.6}	cub	13.606			Espinosa et al. (1982)
$ScIr_{1.1}Sn_{3.6}$	tetr (?)	13.575ª			Espinosa et al. (1982), Cooper (1980)
ScPt ₂ Sn	MnCu ₂ Al	6.514			Dwight and Kimball (1987)
ScPtSn (I)	ZrNiAl	7.41		3.62	Dwight et al. (1973)
ScPtSn (II)	AlLiSi	6.352			Eberz et al. (1980)
ScPtSn (III)	TiNiSi	6.566	4.130	7.275	Hovestreydt et al. (1982)
ScCu ₄ Sn	$\mathrm{MgCu}_4\mathrm{Sn}$	6.997			Kotur and Klyuchka (1989), Kotur and Derkach (1994)
ScCuSn	CaIn ₂	4.384		6.827	Kotur and Klyuchka (1989), Kotur and Derkach (1994)
		4.39		6.82	Dwight (1976)
~Sc ₆ CuSn ₂	?				Kotur and Derkach (1994)
ScAuSn (I)	MgAgAs	6.422			Dwight (1976)
ScAuSn (II)	AlLiSi	6.422			Eberz et al. (1980)

Table 21 Intermetallic compounds in the Sc-M-Sn ternary systems

^a lattice parameter of pseudocubic cell.

## 3.8.2. Sc-Mn-Sn

The Sc–Mn–Sn phase diagram is unknown, but one ternary compound,  $ScMn_6Sn_6$  has been synthesized and its crystal structure determined (Malaman et al. 1988) (table 21).

# 3.8.3. Sc-Fe-Sn

Kotur and Klyuchka (1989) investigated alloys of the compositions ScFeSn, ScFe₂Sn and ScFe₄Sn, but no ternary compounds of such stoichiometries were found. Malaman et al. (1988) reported the existence and the crystal structure of the ternary compound ScFe₆Sn₆ (table 21). There are no data in the literature about the phase equilibria in this system.

# 3.8.4. Sc-Co-Sn

There are data in the literature about four ternary Sc–Co–Sn compounds (see table 21). Espinosa et al. (1982) reported the lattice parameter of a pseudocubic unit cell for a compound with the tentative composition  $ScCo_{1.1}Sn_{3.6}$ . Rare earths form numerous groups of closely related ternary compounds of such a stoichiometry which crystallize in different cubic and tetragonal structure types. A single-crystal investigation is necessary to determine the actual crystal structure of  $ScCo_{1.1}Sn_{3.6}$ . The data of Kotur and Klyuchka (1989) and Dwight and Kimball (1987) concerning  $ScCo_2Sn$  are in good agreement with each other (table 21). According to the data of Kotur and Klyuchka this ternary compound is in equilibrium with Co at 400°C.

# 3.8.5. Sc-Ni-Sn

Four ternary compounds in the Sc–Ni–Sn system have been synthesized and structurally investigated (table 21). However, there are only few data known about the phase equilibria. Kotur and Klyuchka (1989) reported that at 400°C the ScNi₄Sn stannide is in equilibria with Ni and ScNi₂Sn. The latter compound is also in equilibrium with ScNiSn. Derkach and Kotur (1994) also found that at 400°C the Sc₂Ni₂Sn ternary compound is in equilibria with the ternary phase ScNiSn and also with the binary phases ScNi₂, ScNi and Sc₅Sn₃.

# 3.8.6. Sc-Ru(Rh, Pd, Os, Ir, Pt)-Sn

The phase equilibria of the Sc–M–Sn (where M=Ru, Rh, Pd, Os, Ir, or Pt) systems are not known. One or two ternary compounds have been synthesized in each of the systems. These data are shown in table 21. Espinosa et al. (1982) reported on the tetragonal ternary compounds of a tentative composition ScM_{1.1}Sn_{3.6} (M=Ru, Rh, Ir) giving their pseudocubic cell parameters (table 21). Probably, these compounds are isotypic with  $Er_{5-x}Rh_6Sn_{18+x}$  found by Hodeau and Marezio (1984), however, additional investigations are necessary to determine the proper composition and structure of these stannides. Two and three different crystal structure types have been reported for ScPdSn and ScPtSn, respectively (see table 21). This might be an indication for a polymophism of these compounds.



Fig. 87. Sc-Cu-Sn, isothermal section at 400°C. Ternary compounds: (1) ScCu₄Sn; (2) ScCuSn; (3) ~Sc₆CuSn₂.

# 3.8.7. Sc-Cu-Sn

The Sc–Cu–Sn system is the only one of the Sc–M–Sn series for which an isothermal section at 400°C has been reported (fig. 87, Kotur and Derkach 1994). Three ternary compounds occur, and for two of the compounds the crystal structure is known (table 21).

#### 3.8.8. Sc-Au-Sn

The existence of a cubic ternary compound of equiatomic composition (ScAuSn) has been reported by Dwight (1976) and by Eberz et al. (1980). In both publications the same lattice parameter a=6.422 Å is mentioned, however for different structure types, MgAgAs (Dwight) and AlLiSi (Eberz et al.) (table 21).

# 3.9. Sc-M-P(As, Sb, Bi) ternary systems

#### 3.9.1. Sc-Gd-P

Jansen and Sperlich (1975) reported about a continuous series of solid solutions between isotypic binary phosphides ScP and GdP, these are the only data known about this system.

#### 3.9.2. Sc-Mn(Fe, Co)-P

No data exist for the Sc–M–P (M=Mn, Fe and Co) phase equilibria. Jeitschko et al. (1993, 1990), Reinbold and Jeitschko (1987) and Jeitschko and Reinbold (1985) reported

Compound	Structure type	Latti	ice parame	ters	Reference
	or symmetry	a (Å)	b (Å)	c (Å)	
Sc ₂ Mn ₁₂ P ₇	$Zr_2Fe_{12}P_7$	9.392		3.562	Jeitschko et al. (1993)
ScFe ₄ P ₂	$ZrFe_4Si_2$	6.962		3.622	Jeitschko et al. (1990)
$Sc_2Fe_{12}P_7$	$Zr_2Fe_{12}P_7$	?		?	Reinbold and Jeitschko (1987)
ScFe ₅ P ₃	YCo ₅ P ₃	?	?	?	Reinbold and Jeitschko (1987)
$Sc_2Co_{12}P_7$	$Zr_2Fe_{12}P_7$	8.973		3.531	Jeitschko and Reinbold (1985)
ScCo ₅ P ₃	YCo ₅ P ₃	11.691	3.583	10.206	Jeitschko and Reinbold (1985)
$Sc_5Co_{19}P_{12}$	$Sc_5Co_{19}P_{12}$	12.124		3.633	Jeitschko and Reinbold (1985)
ScCoP	TiNiSi	6.268	3.750	7.050	Jeitschko and Reinbold (1985)
$Sc_2Ru_{12}P_7$	$Zr_2Fe_{12}P_7$	9.318		3.87	Ghetta et al. (1986)
ScRuP	ZrNiAl	6.524		3.610	Ghetta et al. (1986)
ScNi ₄ As ₂	ZrFe ₄ Si ₂	7.077		3.738	Jeitschko et al. (1990)
ScNiSb	MgAgAs	6,062			Dwight (1974)
		6.055			Pecharsky et al. (1983)
ScPtSb	MgAgAs	6.312			Dwight (1974)
ScNiBi	MgAgAs	6.191			Dwight (1974)
ScPdBi	MgAgAs	6.4353			Block et al. (1990)

 Table 22

 Intermetallic compounds in the Sc-M-P(As, Sb, Bi) ternary systems

on one, three and four ternary compounds and their crystal structures in the Mn, Fe and Co systems, respectively. These data are shown in table 22.

## 3.9.3. Sc-Ru-P

Ghetta et al. (1986) synthesized two ternary compounds,  $Sc_2Ru_{12}P_7$  and ScRuP, and established their crystal structure (table 22). The phase equilibria for Sc-Ru-P alloys are unknown.

# 3.9.4. Sc-Ni-As

One ternary compound  $ScNi_4As_2$  has been synthesized by Jeitschko et al. (1990) (table 22). This paper is the only one about ternary alloys with scandium and arsenic.

# 3.9.5. Sc-Ni(Pt, Au)-Sb

Isothermal sections of the Sc–M–Sb (M=Ni, Pt and Au) systems have not been investigated. Only a few alloys were examined, among them the compounds ScNiSb and ScPtSb have been synthesized by Dwight (1974) and Pecharsky et al. (1983) (table 22). Later Dwight (1977) reported that no compound of  $Sc_3Au_3Sb_4$  composition exists.

#### 3.9.6. *Sc–Ni(Pd)–Bi*

In both the Sc-Ni-Bi and Sc-Pd-Bi systems the compounds with the equiatomic composition have been obtained by Dwight (1974) and Block et al. (1990). Their crystal structure data are given in table 22. There are no literature data for the phase equilibria in any of the Sc-M-Bi ternary system.

#### 3.10. Sc-M-Se ternary systems

#### 3.10.1. Sc-Mg(Eu, Mn, Cu, Ag, Cd)-Se

None of the Sc–M–Se (M=Mg, Eu, Mn, Cu, Ag and Cd) ternary systems was investigated systematically. Only separate alloys have been examined with respect to the occurrence of ternary compounds known to exist in other related ternary systems. As a result one ternary compound in the six systems has been reported. These data are given in table 23.

T-11- 02

Intermetallic compounds in the Sc-M-Se ternary systems						
Compound	Structure type	Latt	ice parame	ters	Reference	
	or symmetry	a (Å)	b (Å)	c (Å)		
Sc ₂ MgSe ₄	Al ₂ MgO ₄	11.12			Guittard et al. (1964)	
$Sc_2EuSe_4$	$Fe_2CaO_4$	12.128	14.243	3.932	Hulliger and Vogt (1966)	
Sc ₂ MnSe ₄	Al ₂ MgO ₄	11.11			Guittard et al. (1964)	
$Sc_{1-0.67}Cu_{1-2}Se_2$	ErCuSe ₂	3.889– 3.898		6.265– 6.267	Julien-Pouzol et al. (1968)	
ScAgSe ₂	ErAgSe ₂	4.25	6.73	13.52	Julien-Pouzol and Guittard (1969)	
$Sc_2CdSe_2$	$\mathrm{Al}_{2}\mathrm{MgO}_{4}$	11.208			Pawlak et al. (1981)	

# 3.11. Sc-X-X' ternary systems

## 3.11.1. Sc-Ga-Al

Markiv et al. (1987) reported about a part of the Sc–Ga–Al isothermal section at 900°C (25–100 at.% Sc), which is depicted in fig. 88. Four ternary compounds were observed and for two of them (Nos. 1 and 4 in fig. 88) the crystal structure has been determined (table 24). The binary compound ScGa₂ (ST KHg₂) dissolves 22 at.% Al. The lattice spacings of the solid solution ScGa_{2-x}Al_x increase from a = 4.140, b = 6.614, c = 7.914 to a = 4.143, b = 6.618, c = 7.922 Å. Another binary gallide, Sc₅Ga₄ (ST Ho₁₁Ge₁₀) dissolves about 12 at.% Al. The lattice parameters *a* and *c* vary within the limits 10.366–10.395 and 15.305–15.305 Å. Sc₅Ga₃ (ST Mn₅Si₃) dissolves about 20 at.% Al: a = 8.07-8.162, c = 5.951-5.923 Å, respectively. The solubility of Al in Sc₃Ga₂ (ST Gd₃Ga₂) is about 13 at.%, the lattice parameters of the solid solution vary from a = 10.767, c = 14.045 to a = 10.781, c = 14.131 Å. A large amount of Ga (about 15 at.%) can be dissolved by ScAl₂



Fig. 88. Sc–Ga–Al, part of the isothermal section at 900°C (25–100 at.% Si). Ternary compounds: (1) ScGa_{0.75–1.23}Al_{1.25–0.77}; (2)  $\sim$ Sc₄Ga₄Al; (3)  $\sim$ ScGa_{0.56–0.64}Al_{0.44–0.36}; (4) ScGa_{0.4}Al_{0.6}.

(ST MgCu₂): a = 7.580-7.552 Å. A compound of the approximate ScAl composition (55 at.% Al) dissolves up to 7 at.% Ga. The isotypic binary compounds ScGa₃ and ScAl₃ (ST AuCu₃) are completely miscible.

#### 3.11.2. Sc-C-B(Al)

No data are known about phase equilibria in the Sc–C–B and Sc–C–Al systems. However, three and two ternary compounds have been synthesized and structurally investigated in the boron and aluminium systems, respectively. These data are presented in table 24. Bauer (1982) observed also a solid solution of C in ScB₂: ScB_{2–1.9}C_{0–0.1}.

# 3.11.3. Sc-In(Tl, Sn, Pb)-B

Holleck (1977) reported the existence of a ternary compound of the tentative composition  $Sc_3XB_{1-x}$  of the perovskite type structure in the Sc–X–B (X = In, Tl, Sn and Pb) systems (table 24). The actual composition, however, is unknown due to the evaporation of the components during the synthesis procedure. The alloys were homogenized at 800°C.

#### 3.11.4. Sc-In(Tl, Sn, Pb)-C

Holleck (1977) synthesized the ternary  $Sc_3XC_x$  (X=In, Tl, Sn and Pb) compounds which are isotypic with CaTiO₃ (table 24). However, the exact content of carbon in these compounds is unknown.

Compound	Structure type	Lat	ice parame	ters	Reference
	or symmetry	a (Å)	b (Å)	c (Å)	
ScGa _{0.75-1.23} Al _{1.25-0.77}	AlB ₂	4.362-		3.230-	Markiv et al. (1987)
		4.396		3.256	
$\sim Sc_4Ga_4Al$	?				Markiv et al. (1987)
~ScGa _{0.56-0.64} Al _{0.44-0.36}	?				Markiv et al. (1987)
ScGa _{0.4} Al _{0.6}	DyAl	5.494	10.674	5.343	Markiv et al. (1987)
$ScB_2C_2$	$ScB_2C_2$	5.175	10.075	3.440	Smith et al. (1965)
$ScB_2C$	$YB_2C$	6.651		6.673	Bauer (1982)
$Sc_2BC_2$	$Sc_2BC_2$	3.300		10.691	Halet et al. (1990)
ScAl ₃ C ₃	ScAl ₃ C ₃	3.355		16.766	Tsokol' et al. (1986b)
Sc ₃ AlC	CaTiO ₃	4.48			Rosen and Sprang (1965)
$Sc_3InB_{1-x}$	CaTiO ₃	4.560			Holleck (1977)
$Sc_3TlB_{1-x}$	CaTiO ₃	4.520			Holleck (1977)
$Sc_3SnB_{1-x}$	CaTiO₃	4.571			Holleck (1977)
$Sc_3PbB_{1-x}$	CaTiO ₃	4.528			Holleck (1977)
$Sc_3InC_x$	CaTiO ₃	4.533			Holleck (1977)
Sc ₃ TlC _x	CaTiO ₃	4.517			Holleck (1977)
$Sc_3SnC_x$	CaTiO ₃	4.516			Holleck (1977)
Sc ₃ PbC _x	CaTiO ₃	4.528			Holleck (1977)
Sc ₂ AlSi ₂	Mo ₂ FeB ₂	6.597		3.994	Tyvanchuk et al. (1988)
$Sc_{11}Al_2Ge_8$	$Sc_{11}Al_2Ge_8$	10.419		14.974	Zhao and Parthé (1991)

Table 24 Intermetallic compounds in the Sc-X-X' ternary systems

#### 3.11.5. Sc-Si-C

Kotroczo and McColm (1987) investigated solubility of carbon in Sc₅Si₃ (ST Mn₅Si₃) and observed a solid solution, Sc₅Si₃C_{0-0.8}. The lattice parameters vary nonlinearly within the homogeneity range: a = 7.876 - 7.877, c = 5.821 - 5.902 Å.

# 3.11.6. Sc-Al-Si

Toropova et al. (1985) established part of the polythermal section of the Sc–Al–Si system at a constant content of 2 at.% Al. They observed a ternary phase of unknown composition. Its crystal structure was determined in a detailed structural investigation which showed that it had the Sc₂AlSi₂ composition (Tyvanchuk et al. 1988) (table 24). These authors published also the isothermal section at 500°C, which is shown in fig. 89.

#### 3.11.7. Sc-Ge-Si

Muratova (1978) studied the Sc–Ge–Si isothermal section at 600°C, however, no figure was presented in her paper. A continuous series of solid solutions exist between pairs of isotypic binary compounds  $Sc_5Ge_3$  and  $Sc_5Si_3$ , ScGe and ScSi. The scandium germanide


Fig. 89. Sc-Al-Si, isothermal section at 500°C. Ternary compound: (1) Sc₂AlSi₂.

with the highest Ge content, ScGe₂, dissolves 35 at.% Si. The lattice spacings of these solid solutions vary linearly within their homogeneity ranges. Ternary compounds have not been observed.

#### 3.11.8. Sc-Al-Ge

The ternary compound  $Sc_{11}Al_2Ge_8$  with one of the superstructures of the  $Ho_{11}Ge_{10}$  type has been synthesized and investigated by Zhao and Parthé (1991). The lattice parameters are given in table 24. Phase equilibria are unknown.

## 3.11.9. Sc-As-P

Yim et al. (1972) found a continuous series of solid solutions between the isotypic binary compounds ScP and AsP. These are the only data known about this system.

# 3.11.10. Sc-Te-Se

Dismukes and White (1965) obtained the alloy  $Sc_2Te_{0.33}Se_{2.67}at 950-1000^{\circ}C$  with the structure of  $Sc_2Se_3$  and the lattice parameters a = 10.915, b = 7.729 and c = 23.12 Å. These data indicate the occurrence of a solid solution  $Sc_2Te_xSe_{2-x}$  ( $0 \le x \le 0.33$ ). A substitution of Te for Se leads to an increase of the lattice constants.

# 3.12. Sc-M-M' ternary systems

## 3.12.1. Sc-Mg-Mn

Drits et al. (1977) reported on the isothermal sections at 500 and 300°C in the magnesium corner of this system. The solubility of Sc and Mn decrease as a result of their alloying with Mg. Four phases in a peritectic nonvariant equilibrium  $L+\beta \leftrightarrow \alpha + Mn$  ( $\beta$ : solid solution of Mg in  $\beta$ Sc) at 700°C have been detected.

# 3.12.2. *Sc*–*Y*–*Gd*

A single crystal with the composition  $Sc_{0.075}Y_{0.175}Gd_{0.75}$  with the hcp structure has been prepared and its magnetic properties investigated by Ito et al. (1988), however, no data about the lattice parameters were presented in this paper. These data indicate a complete miscibility of the components in the ternary system, similar to what occurs in the binary Sc–Y and Sc–Gd systems (see sect. 2.3).

## 3.12.3. Sc-Tb-Mn

Lelievre-Berna et al. (1993) prepared two alloys of the solid solution  $Tb_{1-x}Sc_xMn_2$  (x = 0.00, 0.01 and 0.03) (ST MgCu₂) and investigated their magnetic structures. The alloys, annealed at 730°C, were essentially single phase according to the X-ray powder diffraction analysis, however, a small amount of pure Tb metal was detected by neutron scattering. These data indicate the occurrence of a limited solid solution of Sc in TbMn₂. No data about variation of lattice parameter are available.

## 3.12.4. Sc-Y-Fe

The isothermal section of the Sc–Y–Fe system at 600°C, which is presented in fig. 90, has been established by Koshel' et al. (1984). The phase equilibria at 800°C are the same. Ternary compounds were not observed. The highest solubility of Sc, 30 at.%, occurs in the binary YFe₂ (ST MgCu₂) compound. The lattice parameter *a* changes within the limits 7.358–7.037 Å. Other Y–Fe binary compounds do not dissolve more than 5 at.% Sc.

# 3.12.5. Sc-Ce-Fe

Figure 91 displays the Sc–Ce–Fe isothermal section at 600°C, which was investigated by Koshel' et al. (1984). This system is similar to the previous Y-based one. CeFe₂ (ST MgCu₂) dissolves about 22 at.% Sc. The lattice parameter *a* of the solid solution  $Ce_{1-0.33}Sc_{0-0.67}Fe_2$  changes within the limits 7.272–7.159 Å. ScFe₂ dissolves less than 5 at.% Ce. Ternary compounds have not been reported. The same phase equilibria were observed at 800°C.

## 3.12.6. Sc-U-Pd

Maple et al. (1996) reported about a solid solution of Sc in the binary compound UPd₃ (ST AuCu₃),  $U_{1-x}Sc_xPd_3$  ( $0 \le x \le 0.5$ ). Data concerning the variation of the lattice parameter with the composition were not presented. Dhar et al. (1996) reported about an alloy





with the composition  $Sc_{0.8}U_{0.2}Pd_3$  crystallizing in the cubic AuCu₃ type structure with the lattice parameter a=3.980 Å. These data support the occurrence of the  $Sc_{1-x}U_xPd_3$  ( $0 \le x \le ?$ ) solid solution.

# 3.12.7. Sc-Ti-Fe

Nishihara and Yamaguchi (1985, 1986) reported the occurrence of the complete miscibility of the isotypic binary compounds  $ScFe_2$  and  $TiFe_2$  (ST MgZn₂). However, no data about lattice parameters of the solid solution were presented. The  $ScFe_2$ -TiFe₂ magnetic phase diagram has been studied in detail, see sect. 6.

# 3.12.8. Sc-Ti-Ni

The melting diagram of the Sc–Ti–Ni system in the range of 50–100 at.% Ni has been investigated by Semenova et al. (1996b). Two ternary eutectics and two ternary peritectics occur at 1110 and 980°C, and 1210 and 1130°C, respectively. Semenova et al. (1996a) investigated the system for the same concentration range at the subsolidus temperatures. No ternary compounds were observed. The solid solubility limits of the phases based on the binary compounds were determined. The polythermal section TiNi–ScNi was shown to be quasibinary.

# 3.12.9. Sc-Ti-Pt

Dwight (1961b) investigated the alloys of the section  $ScPt_3$ -TiPt₃ at 900°C. The isotypic binary compounds of the AuCu₃ structure type are completely miscible. Other regions of the diagram were not investigated.

# 3.12.10. Sc-Hf-Ir

Dwight et al. (1963b) synthesized one ternary compound,  $Sc_{0.2}Hf_{0.8}Ir$  and showed that it crystallizes in the  $\gamma$ TiCu type structure (table 25). These are the only data known about this system.

	Intermetallic of	compounds in the	e Sc-M-M' tern	ary systems	_
Compound	Structure type	Lattice pa	arameters	Reference	
	or symmetry	a (Å)	c (Å)	-	
Sc _{0.2} Hf _{0.8} Ir	γTiCu	3.32	6.22	Dwight et al. (1963b)	
ScNi ₄ Au	MgCu ₄ Sn	6.828		Dwight (1975)	
ScCuZn (I)	MgZn ₂	5.164	8.364	Dwight (1968)	
ScCuZn (II)	CaIn ₂	4.39	6.82	Dwight (1968)	

Table 25		
etallic compounds in the Sc-M-M'	ternary	sv

# 3.12.11. Sc-V-Nb

According to the investigations of Savitskii et al. (1975) ternary compounds do not exist in this system. A narrow region of continuous series of solid solutions adjoining the V–Nb binary system was observed in the ternary system. The solubility of scandium in V(Nb) solid solution decrease from 2 at.% in binary Sc–V alloys to 0.1 at.% in binary Sc–Nb alloys. The lowest solubility of scandium occurs in the  $V_{20}Nb_{80}$  alloy.

#### 3.12.12. Sc--Cr-Ni

Maslenkov and Braslavskaya (1986a) reported on the Sc–Cr–Ni phase diagram in the temperature range 1100–1860°C. The quasibinary sections Cr–ScNi₂ and Cr–Sc₂Ni₇ are of eutectic type. The isothermal section at 1300°C and the projection of a part of the liquidus surface (Ni–Cr–ScNi₂) are presented in the paper too. The lowest ternary eutectic  $L \leftrightarrow \gamma_{Ni} + \langle ScNi_5 \rangle + \langle Sc_2Ni_7 \rangle$  occurs at 1125°C. The same authors (Maslenkov and Braslavskaya 1986b) presented parts (Ni–Cr–ScNi₂) of isothermal sections at 800 and 1050°C. The figure of the latter is shown in the review of Gladyshevsky et al. (1990). These isothermal sections differ from one another due to the rapid decrease of the solubility of scandium in the Ni(Cr) solid solution ( $\gamma_{Ni}$  phase), which is 0.27 and 0.1 at.% at 1050 and 800°C, respectively. Ternary compounds were not observed. Part of the alloys of the three-phase region ScNi₅–Ni–Cr were inhomogeneous.

## 3.12.13. Sc-Mn-Fe

Kyrchiv (1983) reported about an investigation of part of the Sc-Mn-Fe isothermal section at 600°C (0-33.3 at.% Sc), however, no figure was presented. Isotypic binary compounds  $ScMn_2$  and  $ScFe_2$  (ST MgZn₂) are completely miscible. No ternary compounds were observed.

#### 3.12.14. Sc-Re-Ni

Part of the Sc-Re-Ni isothermal section at 1000°C (Ni corner) has been studied by Arskaya et al. (1970) and Savitskii et al. (1972). Ternary compounds do not occur. The solubility of Sc in Ni is about 0.2 wt.%, and it decreases rapidly with increasing rhenium content. Nickel dissolves up to 40 wt.% Re.

## 3.12.15. Sc-Ru-Rh

Khorujaya and Korniyenko (1996, 1997) reported on part of the projection of the liquidus surface (0–50 at.% Sc). The projection of the solidus surfaces in the same concentration region has been determined by Eremenko et al. (1996). Ternary compounds do not exist. The liquidus surface consists of five surfaces of primary crystallization of Ru and Rh solid solutions as well as of the phases based on ScRu₂, ScRh₃ and on a continuous series of solid solutions between the isotypic compounds ScRu and ScRh ( $\delta$  phase). The highest temperature on the surface is 2334°C (Ru melting point) and the lowest one is 1520°C (ternary eutectic  $L(E_1) \leftrightarrow \delta + \langle ScRh_3 \rangle + \langle Ru \rangle$ ).

## 3.12.16. Sc-Ni-Au

One ternary compound  $ScNi_4Au$  has been synthesized and structurally investigated by Dwight (1975) (table 25). These are the only data reported about this system.

# 3.12.17. Sc-Cu-Zn

Dwight (1968) reported that the ternary compound ScCuZn exists in two polymorphic modifications. Their crystal structure data are presented in table 25. Phase equilibria have not been investigated.

# 4. Multicomponent systems containing scandium

Little information has been published in the literature concerning four-component systems containing scandium. The starting material for the preparation of multicomponent (four-component) alloys is normally a pair of ternary compounds. Multicomponent systems are frequently prepared if one (or both) ternary system show outstanding physical properties, such as superconductivity with high transition temperatures, a possible coexistence of superconductivity and magnetism, or if the multicomponent system can be used for hard magnetic materials. In that cases the effect of alloying on the properties of ternary compound is examined in a four-component system. Data about five-component systems containing scandium are even more rare.

# 4.1. Sc-Mg-Mn-Li(Ca, Y, Ce, Nd, Zr, Ni, Cd, Zn, Al, In, Si, Ge, Sn)

Drits et al. (1971) investigated the effect of alloying on the properties (tensile and yield strengths, elongation and hardness) at ambient and elevated ( $300-350^{\circ}$ C) temperatures of multiphase Mg-based ternary alloys Mg + 11%Sc + 1.0%Mn and Mg + 11%Sc + 0.6%Mn (composition in wt.%). The quantities of the alloyed elements did not exceed 2 wt.%. Additions of 0.5–1.0% Ca, Cd, Si, Y and Zn increase the strength of Mg + 11%Sc + 0.6%Mn alloy at ambient temperature. Additions of 0.5–1.0% rare earths, Zn and Sn had the same effect on the strength at 350°C. Additions of Li, Al and Sn (in larger amounts) have a negative influence. This improvement in the mechanical properties is attributed to the appearance of noticeable amounts of second phase intermetallic compounds, especially in the case of Al. Additions of Zr, Ni, In and Ge practically do not have an effect on the strength of these ternary Mg–Sc–Mn alloys.

# 4.2. Sc--Ca--Rh--B

Matthias et al. (1978) obtained the compound  $Sc_{0.3}Ca_{0.7}Rh_4B_4$  occurring in two polymophic modifications. However, their structures and lattice spacings were not reported. One of the phases, probably HT, is of  $CeCo_4B_4$  type structure (Vandenberg and Matthias 1977).

# 4.3. Sc-Ce(Pr, Nd, Sm, Gd, Tb, Dy, Ho, Er, Tm)-Rh-B

Matthias et al. (1978) prepared the alloys with the compositions  $Sc_xR_{1-x}Rh_4B_4$  (x = 0.2, 0.3, 0.4). Compositions of single phases alloys for different R are presented in

464

Composition of alloy	Modification	Composition of alloy	Modification
$Sc_{0.3}Ce_{0.7}Rh_4B_4$	HT	Sc _{0.3} Dy _{0.7} Rh ₄ B ₄	HT
$Sc_{0.3}Pr_{0.7}Rh_4B_4$	HT	$Sc_{0.3}Ho_{0.7}Rh_4B_4$	LT
$Sc_{0.3}Nd_{0.7}Rh_4B_4$	HT	$Sc_{0.4}Ho_{0.6}Rh_4B_4$	HT
$Sc_{0.3}Sm_{0.7}Rh_4B_4$	HT+LT	$Sc_{0.2}Er_{0.8}Rh_4B_4$	HT
$Sc_{0.3}Gd_{0.7}Rh_4B_4$	LT	$Sc_{0.3}Er_{0.7}Rh_4B_4$	?
$Sc_{0.3}Tb_{0.7}Rh_4B_4$	HT	$Sc_{0.3}Tm_{0.7}Rh_4B_4$	HT

Table 26 Compositions of single phase alloys prepared in the Sc-R-Rh-B systems (R=Ce, Pr, Nd, Sm, Gd, Tb, Dy, Ho, Er, Tm)^a

^a Source: Matthias et al. (1978).

table 26. One of the two modifications of compounds is tetragonal. However, the original paper does not indicate which of them, and neither gives the data about their lattice spacings. Taking into account the data of Vandenberg and Matthias (1977) about the occurrence of ternary compounds RRh₄B₄ (R=Nd, Sm, Gd, Tb, Dy, Ho, Er, Tm) with the tetragonal structure of the CeCo₄B₄ type (SG  $P4_2/nmc$ ), it is possible to state that the formation of solid solutions occur when R is substituted for Sc in these ternary compounds, Sc_xR_{1-x}Rh₄B₄. These solutions are metastable (Matthias et al. 1978). Additional investigation is necessary to establish their homogeneity regions. Possibly, Sc_{0.3}Ce_{0.7}Rh₄B₄ and Sc_{0.3}Pr_{0.7}Rh₄B₄ are individual quaternary compounds; however there is no data about the occurrence of ternary compounds CeRh₄B₄ and PrRh₄B₄.

### 4.4. Sc-Y(Nd, Dy, Er, Lu)-Fe-B

Chen and Duh (1988) reported the occurrence of the solid solution  $(Sc_{0-0.2}R_{1-0.8})_2Fe_{14}B$  at 1000°C and variations of the lattice spacings within its homogeneity range (see table 27). The alloys are ferromagnetic. The Curie temperature of the alloys monotonically decrease with the increasing scandium content (see table 27).

Solid solution	Lattice par	rameters (Å)	$T_{C}$
	a	С	
$(Sc_{0-0.2}Y_{1-0.8})_2Fe_{14}B$	8.767-8.750	12.037-11.988	564-557
$(Sc_{0-0.2}Nd_{1-0.8})_2Fe_{14}B$	8.792-8.769	12.190-12.186	589-585
$(Sc_{0-0.2}Dy_{1-0.8})_2Fe_{14}B$	8.762-8.756	12.022-11.977	592-583
$(Sc_{0-0.2}Er_{1-0.8})_2Fe_{14}B$	8.738-8.730	11.964-11.917	553–544
$(Sc_{0-0.2}Lu_{1-0.8})_2Fe_{14}B$	8.703-8.656	11.876-11.893	535-528

 Table 27

 Variations of lattice parameters and Curie temperature  $(T_c)$  within the homogeneity ranges of the solid solutions  $(Sc_{n-0}, R_{1-0,8})_2$ Fe₁₄B (R=Y, Nd, Dy, Er, Lu) which are isotypic with Nd₂Fe₁₄B

# 4.5. Sc-Lu-Ru-B

The as-cast and homogenized at 1150°C Sc–Lu–Ru–B alloys of the section "ScRu₄B₄"–LuRu₄B₄ have been examined by Ku et al. (1979). The boundary ternary compound LuRu₄B₄ (ST LuRu₄B₄, SG *I*4₁/*acd*) is thermodynamically stable while the compound "ScRu₄B₄" is metastable and decomposes after homogenization at 800–1300°C. A metastable continuous series of solid solutions Sc₀₋₁Lu₁₋₀Ru₄B₄ occur. The lattice parameters vary within the limits a = 7.419-7.346 and c = 14.955-14.895 Å. All the alloys are superconducting. More details are given in sect. 6.

## 4.6. Sc-U-Pd-B

Five alloys  $Sc_{0.8}U_{0.2}Pd_3B_x$  (x=0, 0.1, 0.2, 0.3, 0.5) have been prepared by Dhar et al. (1996). An X-ray phase examination shows the occurrence of the  $Sc_{0.8}U_{0.2}Pd_3B_x$  ( $0 \le x \le 0.3$ ) solid solution of AuCu₃ type structure with the lattice constants 3.980, 3.999 and 4.017 Å for x=0, 0.1 and 0.3, respectively. The non-Fermi liquid behaviour reported in the literature for x=0 alloy (Gajewski et al. 1994) persists in x=0.1, but is absent in x=0.2 and 0.3 alloys at least down to 1.4 K.

# 4.7. Sc-Th-Rh-B

Vandenberg and Matthias (1977) presented the crystal structure data of two alloys:  $Sc_{0.5}Th_{0.5}Rh_4B_4$  (ST CeCo₄B₄, SG  $P4_2/nmc$ ), lattice parameters a = 5.322, c = 7.453 Å, and  $Sc_{0.65}Th_{0.35}Rh_4B_4$  (ST CeCo₄B₄), a = 5.317, c = 7.422 Å. These data indicate the existence of the limited solid solution of substitution of Sc for Th in the ternary compound ThRh₄B₄.

# 4.8. Sc-Y(Lu)-Ir-Si

Venturini et al. (1989) reported about the occurrence of continuous series of solid solutions between the isotypic ternary compounds  $Sc_5Ir_4Si_{10}-Lu_5Ir_4Si_{10}$  (ST  $Sc_5Co_4Si_{10}$ ) at 900°C. They investigated the variation of the lattice parameters with composition and the distribution of Sc and Lu atoms in the structure using four single crystals obtained from the solid solution region. The tetragonal lattice spacings of the solid solution  $Sc_{5-0}Lu_{0-5}Ir_4Si_{10}$  change within the limits a=12.314-12.475 and c=4.076-4.171 Å. A negative deviation from Vegard's rule is observed. An isotypic single crystal  $Sc_{2.5}Y_{2.5}Ir_4Si_{10}$  with the lattice parameters a=12.3926, c=4.1292 Å has been investigated too. These data indicate the formation of a solid solution  $Sc_{5-x}Y_xIr_4Si_{10}$  ( $0 \le x \le ?$ ). The alloys of the both four component systems are superconducting.

## 4.9. Sc–Dy–Ir–Si

Another pseudobinary section  $Sc_5Ir_4Si_{10}-Dy_5Ir_4Si_{10}$  has been investigated by Ramakrishnan et al. (1992). These isotypic ternaries form a solid solution  $Sc_{5-x}Dy_xIr_4Si_{10}$ 

 $(0 \le x \le 5)$  with the linear dependence of both tetragonal lattice parameters *a* and *c* with *x*. Within this series superconductivity has been found for  $0 \le x < 1.5$  and antiferromagnetic ordering for x > 1.5. The coexistence of superconductivity and magnetism is reported for x=1.5. The superconducting transition temperature decreases rapidly with increasing *x* from  $T_c = 8.45$  K for x = 0 down to about 4 K for the x = 1.5 sample where the coexistence of superconductivity and magnetic order is observed. The magnetic ordering temperature  $T_N$  increases linearly from 3.5 to 5.0 K in the concentration range  $2 \le x \le 5$ . The temperature dependence of the resistivity of alloys is typical for a metal in the investigated temperature range up to 300 K.

4.10. Sc-Ni-C-B, Sc-Lu-Ni-C-B

A superconducting transition was reported for metastable as-cast alloy of composition  $ScNi_2B_2C$  by Ku et al. (1994). The major phase has been indexed as the tetragonal LuNi₂B₂C-type structure (SG *I4/mmm*) with the lattice parameters a=3.34, c=10.2 Å. Annealing of the alloy at 1050°C for 24 h led to the disappearance of the tetragonal phase and superconductivity.

The same authors reported on the pseudoquaternary system  $(Lu_{1-x}Sc_x)Ni_2B_2C$ . The unstable boundary is near the Sc-rich region (x > 0.5). All the alloys are superconducting.

4.11. Sc-Y-Ge-Si

Three alloys with the compositions  $Sc_{0.48}Y_{4.52}Ge_{0.29}Si_{2.71}$ ,  $Sc_{0.72}Y_{4.28}Ge_{0.43}Si_{2.57}$  and  $Sc_{4.25}Y_{0.75}Ge_{0.45}Si_{2.55}$  with the Mn₅Si₃ type structure (SG *P6*₃/*mcm*) have been prepared and examined by McColm and Kotroczo (1987). Taking into account the existence of isotypic binary compounds  $Sc_5Si_3$ ,  $Sc_5Ge_3$ ,  $Y_5Si_3$  and  $Y_5Ge_3$  it is possible to forecast the occurrence of continuous series of solid solutions between these binary phases with complete mutual substitution of Sc and Y and Si and Ge as well. Hydrogenation of the above mentioned alloys has been investigated.

#### 4.12. Sc-Rh-Os-Si

Braun and Segre (1980) investigated the phase composition at 1000°C of alloys within the section  $Sc_3Os_2Si_6$ —"Sc_3Rh₂Si₆". One of the components of this section, the compound of the tentative composition,  $Sc_3Os_2Si_6$ , is orthorhombic (see table 19, above). The second component, "Sc₃Rh₂Si₆", is a two-phase alloy containing the ternary compounds  $Sc_5Rh_4Si_{10}$  (ST  $Sc_5Co_4Si_{10}$ , see table 19) and  $\sim$ Sc₄RhSi₈ (structure unknown, see table 19). The silicide  $Sc_3Os_2Si_6$  dissolves about 5.5 at.% Rh as deducted from the data presented in the table of the original paper. However, this value is not in agreement with the value given in the text, where a solubility of about 30 at.% Rh is mentioned. Variation of the lattice parameters vs. composition of the solid solution is not presented. Judging from the phase composition of the section, the Sc₃Rh_xOs_{2-x}Si₆ solid solution is

in two-phase equilibrium with  $Sc_5Rh_4Si_6$  and in three-phase equilibrium with the phases  $Sc_5Rh_4Si_{10}$  and  $\sim Sc_4RhSi_8$ . The alloys of the section are superconducting.

# 4.13. Sc-Re-Ni-Si

Zhao and Parthé (1989a) obtained a single crystal  $Sc_3(Ni_{0.96}Re_{0.04})_2Si_4$  and investigated its crystal structure: ST  $Sc_3Ni_2Si_4$ , SG *Pnma*, a=11.679, b=3.985, c=11.991 Å. These data are indicative of the formation of a limited solid solution of the substitution of Re for Ni in the ternary compound  $Sc_3Ni_2Si_4$ . However, these data are not complete and an additional investigation is necessary to define the limits of the solid solution.

## 4.14. Sc-Ca-Pt-P

The only data about the Sc–Ca–Pt–P system concerns the ScCa₂Pt₇P_{$\sim$ 3} quaternary compound, which has been reported by Lux et al. (1991). It is isotypic with Eu₂Pt₇AlP_{$\sim$ 3}, SG *I*4/*mmm*, *a*=4.038, *c*=27.027.

# 4.15. Sc-Y-Ti-Co

The alloy with the composition  $Sc_{0.4}Y_{0.4}Ti_{0.2}Co_2$  is a single phase. It crystallizes in the cubic MgCu₂-type structure, a = 6.962 Å. It was established by Burnashova et al. (1981) who also investigated the hydrogenation of the alloy. These data and the data about the binary compounds ScCo₂, YCo₂ and TiCo₂ which also crystallize with the same structure indicate that there is possibly a complete solubility of these binary compounds, or a limited solubility of Ti in  $(Y_{1-x}Sc_x)Co_2$ .

## 5. Generalisation of the data on scandium metal systems and intermetallics

Phase diagrams give a fundamental insight into how two or more elements behave when they are combined in a system. An understanding of the interaction mechanism between the elements which results in different types of phase diagrams is one of the aims of physical and chemical investigations. The responsible physical parameters (factors) which determine this interaction are: the size, electrochemical, valence-electron, cohesiveenergy and atomic number factors (Villars 1995). A review of the methods (usually semiempirical) proposed for the explanation and prediction of the constitution of phase diagrams, and the occurrence and crystal structure of intermediate compounds in the systems has been written by Villars (1995). The best semiempirical method for the calculation of the enthalpy of binary alloys based on the first three of the above-mentioned factors has been deducted by Miedema (1976). The prediction based on Miedema's model is in agreement with many experimental data. However, the attempts to apply this model to ternary systems failed. Villars (1995) introduced a new model using two additional factors (cohesive energy and atomic number) in order to explain the stability of ternary compounds of proper structure types. Of course, each of these five factors used in Villars's model is related to the position of the corresponding element in the periodic table; however, it is impossible to replace them by only one.

Besides these semiempirical models, successful attempts have recently been undertaken in order to calculate the stability of binary, and in some cases ternary, compounds from first-principle band-structure calculations. As an example we want to mention the Vienna ab-initio simulation package VASP (see Kresse and Hafner 1993, 1994a and Kresse and Furthmueller 1996a,b). It performs an iterative solution of the Kohn-Sham equations of the local-density-functional (LDF) theory and allows one to use generalised gradient corrections. The electronic states are expanded in terms of plane waves, the electron-ion interaction is described in terms of ultrasoft pseudopotentials (see Vanderbilt 1990 and Kresse and Hafner 1994b). VASP allows for the calculations of the Hellmann-Feynman forces acting on the atoms and of the stresses on the unit cell. Hence the total energy may be optimised with respect to the volume and shape of the unit cell and of the positions of the atoms within the cell, with no other restrictions than those imposed by space-group symmetry. If such calculations are performed for several structure types it is possible to predict that structure which has the lowest equilibrium total energy, i.e. which is the stable one. Furthermore, it is possible to calculate the structural parameters (lattice parameters, atomic positions within the unit cell) from first principles, i.e. with no fitted parameters.

In any case a systematic analysis and generalisation of the available experimental data on the phase diagrams and compounds can contribute to improve the existing empirical or theoretical concepts. These regularities can also be used to predict the structure type and the properties of system not yet investigated. Below, some regularities and peculiarities of scandium metal systems and intermetallics found as a result of an analysis of the experimental data presented in sects. 2–4 are summarised.

#### 5.1. Regularities found in binary scandium phase diagrams

- All 65 investigated Sc-E binary phase diagrams can be divided into four types:
- Systems with complete mutual solubility of components in liquid and solid (in at least one phase). Binary compounds do not occur. (E=3A (except Eu, Yb, U), or 4A element).
- (2) Systems with immiscibility gap in liquid (monotectic). Binary compounds do not occur (E=2A element or 3A element Eu, Yb, or U).
- (3) Systems with low or no mutual solubility of the components in solid (eutectic). Binary compounds do not occur (E = 5A, 6A element).
- (4) Systems with one or more binary compounds. Limited mutual solubility of the components in solid. (E=2A, 7A-8A, 1B-6B element).

There are only two exceptions: the systems with U and Pu. Pu forms one binary compound with Sc, and in the Sc–U system appreciable limited mutual solubility of components in solid occurs. All rare earths (except Eu and Yb) and the 4A elements (Ti, Zr and Hf) are completely miscible with Sc in liquid and solid. It is necessary to indicate that Sc is the only element among the rare earths which forms continuous series

of solid solutions with other rare earths and with 4A elements. Zr and Hf, which have nearly the same atomic radius as Sc (1.602, 1.580 and 1.641 Å, respectively), usually form binary systems of the eutectic type with other rare earths, e.g. Zr–Y, Zr–Gd, Zr–Dy, Zr–Er, Hf–Y, Hf–Er (Massalski 1990).

Only Eu and Yb, among the rare earths, form immiscibility gaps with Sc in the liquid and solid. The difference in valence of these two rare earths and Sc is, perhaps, the main reason of this difference of interaction. The divalent state is more typical for Eu and Yb, whereas the other rare earths are usually trivalent. The same divalent state is characteristic for alkaline earths which are immiscible with Sc in the liquid and solid too. Therefore, it is possible to predict the same type of binary phase diagrams of Sc with alkaline metals. These elements are even more different from Sc in the valence state and other characteristics (melting temperature, electronegativity, etc.) than are the alkaline-earth metals.

All 5A–6A elements form eutectic-type binary systems with Sc with a low mutual solid solubility. With increasing melting temperature of the transition element the eutectic point shifts towards scandium.

The elements of all other groups form binary compounds with scandium. The number of binary compounds in each system is indicated in table 1 (above). Within each large period Sc forms the largest number of binary compounds with 8A and 3B elements. In the rows of the p-elements the number of binary compounds decreases with the increase of the group number of the element. The number of binary compounds changes inconsiderably with the increase of the period's number.

In the Sc-M (M=d element) binary systems, binary compounds of equiatomic composition ScM usually have the highest absolute values of enthalpy (Colinet and Pasturel 1994) and the highest melting temperature in the system. In the systems of scandium with p-elements the richest in scandium compound usually is the most thermodynamically stable one. Its composition is  $Sc_5E_3$  (E=Ga, Si, Ge, Sn, Pb), or  $ScE_2$  (E=B), or  $ScE_{1-x}$  (E=C). As was stated by Lukashenko et al. (1990a,b, 1991) scandium silicides and germanides are much more thermodynamically stable in comparison to silicides and germanides of other 3d elements. The thermodynamic properties are closer to those of the silicides and germanides of the lanthanides, than the 3d elements.

114 binary intermetallic compounds of scandium with definite crystal structure crystallize in 29 different compositions and belong to 56 structure types (table 28). The majority of them occur at constant compositions. In the cases when compounds have a variable composition their homogeneity ranges usually do not exceed 1 to 5 at.%. The compounds  $ScMg(\beta')$  and  $ScC_{1-x}$  are the only two exceptions. The most common compositions of the scandium intermetallics occur at the stoichiometries ScE (30 compounds),  $ScE_2$  (20 compounds),  $ScE_3$  (9 compounds),  $Sc_2E$  (8 compounds) and  $Sc_5E_3$  (8 compounds). Thus, more than 55% of binary scandium intermetallics (75 compounds among 134 known today) occur only at five simple stoichiometries out of 29 known to date. At these stoichiometries the compounds crystallize in different structure types depending on the position of element in the periodic table, as seen in table 28.

Formula	Sc content (at.%)	Structure type	Pearson's symbol	Element (E) which forms the compound
ScE ₁₃	7.14	NaZn ₁₃	cF112	Be
ScE ₁₂	7.69	ThMn ₁₂	tI26	Zn
		$UB_{12}$	cF52	В
ScE ₇	12.50	αMn	cI58	Tc
		$ScCd_{\gamma}$	oS32	Cd
$Sc_3E_{17}$	15.00	$\operatorname{Ru}_3\operatorname{Be}_{17}$	cI160	Zn
ScE ₅	16.67	CaCu ₅	hP6	Be, Ni
$Sc_5E_{24}$	17.24	αMn	cI56	Re
Sc13E58	18.31	Gd ₁₃ Cd ₅₈	hP142	Zn
$ScE_4$	20.00	MoNi ₄	tI10	Ag, Au
$Sc_2E_7$	22.22	Ce ₂ Ni ₇	hP36	Ni
ScE ₃	25.00	AuCu ₃	cP4	Rh, Pd, Ir, Pt, Al, Ga, In
		SnNi ₃	hP8	Cd, Hg
$ScE_2$	33.33	MgZn ₂	hP12	Mn, Tc, Re, Fe, Ru, Os
		MgCu ₂	cF24	Co, Ni, Ir, Al
		MgNi ₂	hP24	Fe
		MoSi ₂	tI6	Cu, Ag, Au
		$AlB_2$	hP3	Zn, B
		KHg ₂	oI12	Ga
		ZrGa ₂	oS12	In
		ZrSi ₂	oS12	Ge
		$ScSn_2$	tI24	Sn
ScE _{1.74}	36.50	MgCu ₂	cF24	Fe
$Sc_3E_5$	37.50	Tm ₃ Ga ₅	oP32	Ga
		Pu ₃ Pd ₅	o\$32	T1
$Sc_2E_3$	40.00	$AlB_2$	hP3	Si
		$Sc_2S_3$	oF80	Se
		$Ti_7S_{12}$	hR8	Te
$Sc_3E_4$	42.86	$Sc_3C_4$	tP70	С
ScE	50.00	CsC1	cP2	Mg, Co, Ni, Ru, Rh, Pd, Ir, Pt, Cu, Ag, Au, Zn, Cd, Hg, Sn
		CrB	oS8	Al, Ga, Si, Ge
		AuCu	tP4	In
		NaCl	cF8	C, P, As, Sb, Bi, Se
		NiAs	hP4	Te, Po
$Sc_{11}E_{10}$	52.38	Ho ₁₁ Ge ₁₀	tI84	Ge
$Sc_6E_5$	54.55	Ti ₆ Ge ₅	oI44	Sn, Pb

Table 28 Stoichiometries and structure types of binary scandium intermetallics

continued on next page

Formula	Sc content (at.%)	Structure type	Pearson's symbol	Element (E) which forms the compound
Sc ₅ E ₄	55.56	Ho ₁₁ Ge ₁₀	tI84	Ga
		CsCl	cP2	In
		Ti₅Ga₄	hP18	TI
		$Sm_5Ge_4$	oP36	Ge
$Sc_4E_3$	57.14	$Th_3P_4$	cI28	С
$Sc_3E_2$	60.00	$Gd_3Ga_2$	tI80	Ga
		$Cr_3C_2$	oP20	P, As
		$S_3Sb_2$	oP20	P, As
		$V_3As_2$	tP32	As
$Sc_5E_3$	62.50	Mn ₅ Si ₃	hP16	Ga, Tl, Si, Ge, Sn, Pb
		$\beta Yb_5Sb_3$	oP32	As, Sb
$Sc_2E$	66.67	Al ₂ Cu	tI12	Co
		Ti ₂ Ni	cF96	Ni, Pd, Ir
		Co ₂ Si	oP12	Pt
		Ni ₂ In	hP6	In, Tl
		Cu ₂ Sb	tP6	Sb
$Sc_7E_3$	70.00	Th ₇ Fe ₃	hP10	P
		Sc ₇ As ₃	t180	As
$Sc_{11}E_4$	73.33	$Sc_{11}Ir_4$	cF120	Ru, Os, Ir
$Sc_3E$	75.00	Sc ₃ Co	oP32	Со
		Ni ₃ Sn	hP8	In
		Fe ₃ C	oP16	Р
$Sc_{57}E_{13}$	81.43	$Sc_{57}Rh_{13}$	cP140	Ru, Rh, Ir, Pt
$Sc_{29}E_6$	82.86	$Sc_{29}Fe_6$	cP140	Fe
$Sc_{44}E_7$	86.27	$Mg_{44}Rh_7$	cF408	Os, Ir

Table 28. continued

Some binary compounds occur in two (ScFe₂, ScNi₅, Sc₄C₃, ScSi_{1.5}, Sc₃P₂) or in three (Sc₃As₂) polymorphic modifications. The crystal structures of polymorphic forms are structurally related.

There is also a relation between the interval of stoichiometries (i.e. the composition range where the intermetallic phases are formed in the binary Sc–E system, see fig. 92) of binary compounds and the position of element in the periodic table. The widest intervals of compositions of the binary compounds with Sc display 8A and 3B elements (fig. 92). These are the elements which form the largest number of binary compounds with scandium. In the rows of d elements the least scandium content in compounds increases from 7A to 1B element and then sharply decreases for the 2B elements. A similar relation



Fig. 92. Intervals of stoichiometries of Sc–E binary compounds depending on the position of the E element in the periodic table.

is observed in the rows of p elements. The least scandium content sharply increases from 3B to 5B element and then decreases.

#### 5.2. Regularities found in ternary scandium phase diagrams

Assuming that the data concerning a certain ternary system are complete if at least one isothermal section of the system has been investigated for  $\frac{3}{4}$  of the concentration region. There are about 70 such Sc–M–X ternary systems preferably with M=d, f element and X=B, Al, Ga, C, Si, Ge (table 13, above). The corresponding data are summarised in the tables 29 and 30. However, in such ternary systems additional ternary compounds which are stable over a limited temperature range may also exist. They, of course, will not be observed in investigation of the system at one temperature only, or if only a part of the system has been studied. In total, 420 ternary scandium intermetallic compounds have been synthesized. For 348 compounds (82.9%) the crystal structure was defined, and these compounds belong to 111 structure types.

The crystal structures have been investigated most completely for ternary compounds of the Sc-M-X systems with M=3d, 4d, 5d, 4f element: with X=B, Al, Ga 102 compounds are known and with X=C, Si, Ge 178 compounds are known. Their compositions are given in figs. 93 and 94. Similarly as in the case of the binary systems, within the sequence of these ternary systems Sc-M-B, Sc-M-Al and Sc-M-Ga etc., within each period of the periodic table the number of ternary compounds usually increases with increasing atomic number of component M. The 8A-group elements therefore form the largest number of ternary compounds. Among the systems with 3B and 4B elements the ternary systems with boron differ considerably from those with aluminium and gallium. Also, the carbon systems behave different when compared with the Si and Ge systems. These systems differ by the number of ternary compounds occurring and by their compositions (tables 29 and 30, figs. 93 and 94). The ternary compounds ScMB₂ and ScMC₂ are exceptions in this sense. However, even in these cases the crystal structures of the ScMB₂ and ScMC₂ compounds are different from those of the ScMAl₂, ScMSi₂ or ScMGe₂ compounds. In all other cases the stoichiometries of the ternary borides and carbides are different from

 Table 29

 Summary of information known about the Sc-M-B(Al,Ga) and Sc-X-B(Al,Ga) ternary systems

	1A	2A	3A	4A	5A	6A	7A		8A		1B	2B	3B	4B	5B	6B
	Li	Be											В	C		
2	<b>□</b> 0															
	Na	Mg											Al	Si	Р	
5		<b>0</b>														
	K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	As	Se
4		<b>□</b> 0		<b>0</b> <b>3</b>	<b>1</b>				□ 3 ■17	■ 5 ■ 4 ■14	■ 10 ■ 9					
	Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te
С		<b>0</b>	<b>1</b>	■ 0 ■ 1	■ 0 ■ 2	• 0		□ 3 ■ 6 □ 1		<b>II</b> 5	<b>D</b> 1		U 1	Ц 1		
	Cs	Ba	La	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	T1	Pb	Bi	Ро
0		<b>0</b>		■ 0 ■ 2			$\square 2$ $\square 1$ $\square 1$				<b>ロ</b> 1		[]]]			
7	Fr	Ra	Ac	Ku	Ns											



Lack of the symbol means the system has not been investigated.

the stoichiometries of ternary compounds of their neighbours among 3B and 4B elements, respectively.

In inorganic chemistry it is known that within each group of the periodic table the elements of the second period differ considerably in their properties from those

 Table 30

 Summary of information known about the Sc-M-C(Si,Ge) and Sc-X-C(Si,Ge) ternary systems

	1A	2A	3A	4A	5A	6A	7A		8A		1B	2B	<b>3</b> B	4B	5B	6B
2	Li	Be											B □ 3	С		
3	Na	Mg												Si □ ₀	Р	
4	K	Са	Sc	Ti ∎ °	V	Cr	Mn ■ 4 ■ 6	Fe ² ¹⁶ ⁸	Co 3 12 8	Ni 2 15	Cu	Zn	Ga	Ge ∎ º	As	Se
5	Rb	Sr	Y ■ 1 ■ 3	Zr ∎ º	Nb	Mo	Тс	Ru ■ 1 □ 2 □ 3	Rh ■ 0 ■ 10 □ 3	Pd ■ 0 □ 1 □ 1	Ag ■ 0 ■ 1	Cd	In	Sn □ 1	Sb	Te
6	Cs	Ba	La 2 2 2		Ta ■ 0 ■ 1	W	Re □ 1 ■ 5 □ 1	Os $\square$ 1 $\square$ 3		Pt	Au	Hg	Tl	Pb □ 1	Bi	Ро
7	Fr	Ra	Ac	Ku	Ns							i				
1	<b>_</b>															
	Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu		
6	<b>8</b> 8		5		<b>5</b>				<b>2</b>		<b>•</b> 0		2	<b>0</b>		
7	Th □ 0	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr		
Pl	One o hase en oncent	r more quilibr ration e symt	select ia wer range ool me	ted allo e estation or for g	bys we blished part of e syste	re inve for th it. m has	estigat e who not be	M ed le xen inv		Re □ 1 □ 1 □ 1 ted.		Syste Syste Syste Num	em Sc- em Sc- em Sc- ber of	M-C M-Si M-Ge	y com	pounds

of their neighbours in the group. This difference exists also among their intermetallic compounds.

Intermetallic compounds of scandium with the 6B elements Se, Te and Po are different compared to all of the previously described scandium compounds. They crystallize in structures typical for oxides, sulphides and other ionic compounds (Al₂MgO₄, Fe₂CaO₄, ErCuS₂, ErAgAs, NaCl structure types). In these structure types each atom is coordinated



Fig. 93. Compositions of ternary compounds with established crystal structure in the systems Sc-M-X (M=3d, 4d, 5d, 4f element; solid circles: X=B; open circles: X=Al, Ga). (1) Sc_{0.15-0.55}M_{0.85-0.45}Al₃ (2 compounds); (2) Sc_{0.2}Hf_{0.8}Ga₃; (3) Sc₂Co₂₁B₆; (4) ScM_{7.1-4.0}X_{4.9-8.0} (6 compounds); (5) Sc₄Ni₂₉B₁₀; (6) Sc_{0.2-0.9}Hf_{0.8-0.1}Ga; (7) Sc_{3.4}Ni₂₀₋₁₉B₆; (8) ScCo_{4.5}Ga_{4.1}; (9) Sc₂Fe_{8.83}Ga_{8.17}; (10) ScM₄B₄ (2 compounds); (11) ScIr₃B₄; (12) ScCu_{3.7}Ga_{2.3}; (13) ScNi_{2.36}Ga_{3.64}; (14) ScM₂Ga₄ (2 compounds); (15) Sc₂Co₃Ga_{9.5}; (16) ScMGa₅ (3 compounds); (17) Sc_{3.2-4.7}Zr_{7.8-6.3}Ga₁₀; (18) Sc₂Co₇Ga₄; (19) Sc₂Ni_{7-5.5}Ga_{4-5.5}; (20) ScM₃B₂ (2 compounds); (21) ScMB₄ (5 compounds); (22) Sc₂M₃B₄ (2 compounds); (23) Sc₂MGa₈ (2 compounds); (24) ScM₃B (2 compounds); (30) ScMX₂ (2 compounds); (31) Sc₃M₂Ga₆; (28) ScM₂X (8 compounds); (29) ScM_{1.2}Ga_{1.8} (2 compounds); (30) ScMX₂ (2 compounds); (31) Sc₃M₂Ga₆ (2 compounds); (32) Sc_{6.8-9.4}M_{4.2-1.6}Ga₁₀ (2 compounds); (33) ScFe_{1.82-1.44}X_{0.18-0.56} (2 compounds); (34) ScM_{1.37-0.30}X_{0.63-1.70} (15 compounds); (35) ScMGa (2 compounds); (36) ScM_{0.5}Ga_{1.5} (2 compounds); (40) Sc_{8.5}M_{1.2}Ga_{1.65} (2 compounds); (38) ScM_{0.1}Ga_{1.9} (2 compounds); (39) Sc₅M_{1-x}Ga_{1-x} (2 compounds); (40) Sc_{8.5}M_{1.2}Ga_{1.65} (2 compounds); (37) ScM_{0.35}Ga_{1.65} (2 compounds); (38) ScM_{0.1}Ga_{1.9} (2 compounds); (39) Sc₅M_{1-x}Ga_{1-x} (2 compounds); (40) Sc_{8.5}M_{1.2}Ga_{1.65} (2 compounds); (38) ScM_{0.1}Ga_{1.9} (2 compounds); (39) Sc₅M_{1-x}Ga_{1-x} (2 compounds); (40) Sc_{8.5}M_{1.2}Ga_{1.65} (2 compounds); (37) ScM_{0.35}Ga_{1.65} (2 compounds); (38) ScM_{0.1}Ga_{1.9} (2 compounds); (39) Sc₅M_{1-x}Ga_{1-x} (2 compounds); (40) Sc_{8.5}M_{1.2}Ga_{1.65} (2 compounds); (37) ScM_{0.35}Ga_{1.65} (2 compounds); (38) ScM_{0.1}Ga_{1.9} (2 compounds); (39) Sc₅M_{1-x}Ga_{1-x} (2 compounds); (40) Sc_{8.5}M_{1.2}Ga_{1.65} (2 compounds); (38) ScM_{0.1}Ga_{1.9} (2 compounds); (39) Sc₅M_{1-x}Ga_{1-x} (2

by the atoms of the other elements, e.g. Sc atoms are surrounded by 6B atoms and vice versa. The coordination about a given atom is preferably octahedral and/or tetrahedral. At the same time these compounds show a metallic glide and a semimetal type of electrical conductivity (White and Dismukes 1965, Guittard et al. 1964, Hulliger and Vogt 1966, Julien-Pouzol et al. 1968, Julien-Pouzol and Guittard 1969). These compounds represent borderline cases between metallic and semimetal behaviours. On the other hand the atoms in the structures of typical intermetallic compounds are surrounded by both different atoms and identical atoms. The coordination number of atoms in intermetallics is rather high, from 6 to 20. The majority of scandium-containing phosphides and arsenides belong to the structure types which are typical for intermetallics, e.g. TiNiSi,  $ZrFe_4Si_2$ ,  $Zr_2Fe_{12}P_7$ , etc.



Fig. 94. Compositions of ternary compounds with established crystal structure in the systems Sc–M–X (M=3d, 4d, 5d, 4f element; solid circles: X=C; open circles: X=Si, Ge). (1)  $Sc_{0.35}M_{4.65}Si_3$  (2 compounds); (2)  $ScFe_{10}Si_2$ ; (3)  $ScM_6Ge_6$  (5 compounds); (4)  $Sc_{1.2}Fe_4Si_{9.8}$ ; (5)  $ScFe_6Ge_5$ ; (6)  $ScM_6Ge_4$  (2 compounds); (7)  $Sc_{1-1.8}V_{5-4.2}X_5$  (2 compounds); (8)  $ScM_3Si_7$  (2 compounds); (9)  $Sc_{0.2-0.4}Sm_{0.8-0.6}Si$ ; (10)  $Sc_{0.3}M_{0.7}Si_2$  (2 compounds); (11)  $Sc_6Co_{30}Si_{19}$ ; (12)  $Sc_{1.26}Pr_{3.74}Si_4$ ; (13)  $ScFe_4Si_2$ ; (14)  $Sc_{12.3}Ni_{40.7}Ge_{31}$ ; (15)  $Sc_{1.35}Y_{3.65}Ge_4$ ; (16)  $Sc_{3.5}Ni_{11}X_4$  (2 compounds); (17)  $ScNi_2Si_3$ ; (18)  $Sc_6Ni_{18}X_{11}$  (2 compounds); (19)  $Sc_2Cr_4X_5$  (2 compounds); (20)  $Sc_{0.52+x}M_{0.48-x}Si_{1.67}$  (4 compounds); (21)  $ScM_3C$  (3 compounds); (22)  $ScM_2X_2$  (9 compounds); (23)  $Sc_{1.8}Dy_{3.2}Ge_4$ ; (24)  $Sc_5Re_8Si_{12}$ ; (25)  $Sc_2M_3Si_5$  (2 compounds); (20)  $Sc_2V_3Si_3$ ; (31)  $ScMx_2$  (16 compounds); (28)  $Sc_{2+x}M_{3-x}X_4$  (11 compounds); (29)  $Sc_4M_7X_6$  (6 compounds); (30)  $Sc_2V_3Si_3$ ; (31)  $ScMx_2$  (16 compounds); (32)  $Sc_4M_4X_7$  (5 compounds); (33)  $Sc_5M_4Si_{10}$  (3 compounds); (34)  $Sc_3M_4X_4$  (4 compounds); (35)  $Sc_6Vb_5Ge_{10}$ ; (36)  $Sc(Fe, X)_2$  (2 compounds); (37)  $ScM_{1.5}X_{0.5}$  (4 compounds); (38) ScMX (34 compounds); (39)  $Sc_7M_{4+x}X_{10-x}$  (4 compounds); (40)  $Sc_3M_2Si_4$  (6 compounds); (41)  $Sc_2CrC_3$ ; (42)  $ScM_{0.25}Si_{1.75}$  (4 compounds); (43)  $Sc_5Re_2C_7$ ; (44)  $Sc_3M_{1.22}Ge_4$  (5 compounds); (45)  $Sc_3M_2X_3$  (4 compounds); (46)  $Sc_3Mc_4$  (3 compounds); (47)  $Sc_2MX_2$  (3 compounds); (48)  $Sc_9Ni_5Ge_8$ ; (49)  $Sc_3NiSi_3$ ; (50)  $Sc_4NdSi_4$ ; (51)  $Sc_2M_{0.85}Si_{0.15}$  (2 compounds).

A large number of ternary Sc-M-X compounds occur at stoichiometries which lie on three cross sections of a ternary phase diagram with the atomic ratios Sc: X=1:1, Sc-M=1:1, and M: X=1:1, and on the section with Sc content of 33.3 at.% (see figs. 93 and 94). 55 ternary compounds with X=B, Al, Ga and 111 compounds with X=C, Si, Ge occur on these sections. Thus, more than half of the ternary compounds of 3B and 4B elements with known crystal structures lies on these four characteristic cross sections.

The analysis of the stoichiometries of 68 ternary scandium intermetallics determined in other systems (Sc–M–X, X=5B, 6B element; Sc–X–X'; Sc–M–M') shows that 48 of them (~71%) also belong to these four sections. This means that about  $\frac{2}{3}$  of all scandium ternary intermetallics known today crystallize only on four appointed sections of phase diagrams and generally have simple stoichiometries.

This regularity had been discovered by Kotur and Bodak (1981) in a limited series of Sc–M–Si (M=3d element) systems. However, it seems to be characteristic for all ternary systems of scandium. As was mentioned by Villars (1995), simple stoichiometric ratios are in general preferred by intermetallic compounds.

A summary of the crystal structure data of the 463 (114 binary, 348 ternary and 1 quaternary) intermetallic compounds of scandium reviewed in this chapter are presented in Appendix A. They belong to 155 structure types, which are arranged in decreasing order according to the number of existing compounds. Structure types with the same number of representatives are arranged according to increasing number of atoms per unit cell. The number of the binary and ternary compounds representing each structure type is also given. Generalised data about the occurrence of ternary compounds of the various structure types in each group of systems is indicated too. The corresponding data for the binary systems are shown in table 28.

The largest number of ternary compounds are those with the simplest compositions: ScMX (a total of 61 compounds); ScMX₂ (19), ScM₂X (18), ScM₂X₂ (10), Sc₃MX (9). A similar regularity has been found for binary scandium intermetallics (see sect. 5.1).

As one can see from figs. 93 and 94 more than 90% of all the intermetallic Sc compounds occur in the region of ternary system where the scandium content is less than ~50 at.% and which is limited by the sections Sc:M=1:1 with X content from 0 to 33.3 at.% and Sc:X=1:1 with the M content from 0 to 33.3 at.%.

A comparison of the investigated ternary systems of scandium with the related ternary systems of other rare-earth elements, which was presented in a Handbook by Bodak and Gladyshevsky (1985), reveals that especially for the light rare earths the ternary compounds often occur at larger RE content ( $\geq$ 50 at.%). In this regard the scandium systems are closer to the systems of the d elements, especially those of the 4A group, Ti, Zr and Hf.

The majority of the scandium intermetallic structure types can also be found among intermetallic compounds of other rare earths as well as among intermetallics of the 4A elements (Villars and Calvert 1991). However, taking into consideration all 155 structure types of scandium intermetallics, from a crystal-chemical point of view, scandium appears to be closer to 4A elements, especially to Zr and Hf, rather than to the other rare earths.

The compounds of equiatomic composition ScMX, which occur frequently in ternary systems, belong to TiNiSi structure type and rarely to the ZrNiAl type structure. These two structure types are characteristic for intermetallics of d transition elements. The compounds of the other rare-earth elements prefer FClPb, ZrNiAl and AlB₂ structure types (Villars and Calvert 1991). The RM₂X₂ compounds belong to one of the most frequently occurring structure types, namely CeGa₂Al₂ (or ThCr₂Si₂) and La₂O₂S. We note that among ScM₂X₂ compounds only three representatives are known with the CeGa₂Al₂ type structure, but none with the La₂O₂S type structure. The ScFe₂Si₂ compound is isotypic with HfFe₂Si₂, which does not occur among other rare-earth intermetallics. Another typical stoichiometric ratio of the rare-earth compounds is RMX₂, however, scandium is the only rare-earth element which does not form phases with CeNiSi₂ structure type, but instead forms compounds of the

 $ZrCrSi_2$  (or TiMnSi_2) type. Scandium is the only rare earth which forms compounds with  $ZrSi_2$ ,  $Zr_4Co_4Ge_7$ ,  $Zr_2Cr_4Si_5$  structure types, which are frequently observed among intermetallics of d elements. There are no d-element compounds of the ScNiSi_3, Sc_2Fe_3Si_5, Sc_2Co_3Si_5, Sc_3Ni_{11}Si_4 structure types, however, a lot of them are found among rare-earth intermetallics. These are examples confirming the unique position of scandium within the family of rare-earth elements. To some extent Sc is the linking element between the rare earths and the d elements.

### 5.3. Atomic size factor and its influence on the nature of scandium intermetallics

The constant compositions of ternary compounds and the absence of solid solutions on the basis of binary compounds are other characteristic features of scandium systems (with the exception of the systems Sc–M–Ga with M=rare earth or 4A element). However, in some systems solid solutions of phases with narrow homogeneity regions occur. Sometimes a substitution of Sc and M atoms occurs and sometimes the M and the X atoms are mutually substituted. There is no doubt that the atomic size factor has a dominating influence on the formation of solid solutions and their nature (solid solutions of substitution, of inclusion or of subtraction of atoms). Examples of solid solutions of substitution are presented in table 31. It is interesting to note that all ternary compounds which form such solid solutions crystallize in structures characteristic for binary compounds.

Julien-Pouzol et al. (1968) found that in the Sc–Cu–Se ternary system a solid solution with the limit compositions  $ScCuSe_2-Sc_{0.67}Cu_2Se_2$  exists due to the subtraction of a

Mutually substit	uted ator	ms	Ratio of a	tomic radii	Structure type of ternary
Sc-M		X–M	$r_{\rm Sc}/r_{\rm M}$	r _x /r _M	compound
	X	М			
Y, Nd, Sm, Dy			0.91-0.93		$\alpha$ ThSi ₂ , AlB ₂
Y, Tb			0.91; 0.92		TiNi3
V			1.22		Ti ₆ Ge ₅
Nb, Mo			1.13; 1.18		Mn ₅ Si ₃ ; Ho ₁₁ Ge ₁₀
Y, Ta, Mo, W			0.91-1.18		Sm ₅ Ge ₄
Ti, Zr			1.12; 1.03		Ho ₁₁ Ge ₁₀
	Al–	Ni, Fe, Ru, Pd		1.12-1.04	MgZn ₂
		Fe, Cu		1.10; 1.09	MgZn ₂ , MgCu ₂
	Ga–	Fe, Co, Ni		1.10-1.12	MgZn ₂ , MgCu ₂
		Ni, Cu		1.12; 1.09	CaIn ₂
	Si–	Mn, Fe, Co, Ni		1.03-1.08	MgZn ₂
	Ge-	Cr, Mn		1.03; 1.06	$Ho_{11}Ge_{10}$

Table 31 Mutually substituted atoms in the structures of ternary compounds of the Sc-M-X systems



Fig. 95. Projection of the structure  $Mn_sSi_3$ along 001. CP of atoms: (a) M1 occupying 6(g) site with CN=15; (b) M2 occupying 4(f) site with CN=14; (c) Si occupying another 6(g) site with CN=11. Empty octahedra [M1₆] are labelled (d).

fraction of Sc atoms and the addition of Cu atoms in different atomic sites. Other examples of solid solutions of addition or subtraction are observed in other ternary systems, such as Sc-M-X and Sc-X'-X (X=B, C) where small boron or carbon atoms are added into the octahedral cavities of the AuCu₃ type structure, revealing the formation of perovskite-type ternary compounds ScM₃B_{1-x}, Sc₃X'B_{1-x}, ScM₃C_x and Sc₃X'C_x (Holleck 1977).

The binary compounds  $Sc_5Si_3$  and  $Sc_5Ge_3$  can be distinguished among other binary scandium intermetallics. Both crystallize in the  $Mn_5Si_3$  structure type (hP16;  $SG P6_3/mcm$ ), which is a common structure type of intermetallics. Its projection along the 001 direction is presented in fig. 95. The  $A_5B_3$  compounds with the  $Mn_5Si_3$  structure type are formed by 3A–8A elements as the A constituent with the 3B–5B elements as the B constituent (Villars and Calvert 1991). The ratios of atomic radii ( $r_A/r_B$ ) for these compounds are observed over a wide interval, from 0.83 for  $Ti_5Pb_3$  to 1.35 for  $Y_5Si_3$ . This is, perhaps, the main reason for the existence of substitutional solid solutions of Sc and the majority of d and f elements in  $Sc_5Si_3$  and  $Sc_5Ge_3$  over wide compositional intervals up to formation of continuous series of solid solutions.

Usually the lattice parameters of these solid solutions display a nonlinear dependence on the composition. These data are available in numerous papers, see e.g. Kotur and Parasiuk (1994), Kotur (1986, 1991), Kotur and Mokra (1994). The nature of mutual substitution of Sc and other atoms has been investigated by Kotur and Parasiuk (1994) for the Sc₂Er₃Si₃ and Sc₃Er₂Si₃ continuous series of solid solutions, i.e. Sc_xEr_{5-x}Si₃. Scandium and erbium atoms substitute for each other statistically in two crystallographic sites 6(g) and 4(f) of the structure within the solid solution. Contrary to these data the investigation of the ScV₄Si₃ single crystal revealed a partial ordering of Sc and V atoms in the structure (Kotur et al. 1983a). V atoms occupy the 4(f) site with CN = 14, and the rest of the V atoms together with Sc atoms occupy the 6(g) site with the higher CN = 15. The solubility of V in Sc₅Si₃ at 800°C does not exceed 1 at.%. The ternary compound Sc₂V₃Si₃ with practically a constant composition at 800°C isotypic with Mn₅Si₃ has been found in the system. The reason seems to be the considerably large difference in the atomic sizes of Sc and V in comparison to the sizes of Sc and Er atoms. The Mn₅Si₃ structure type can be also stabilized in systems by the inclusion of small C, N, O or B atoms into the empty octahedra [ $\Box$ M1₆]. Columns of these octahedra are stretched along 6₃ axes in the structure (fig. 95). Kotroczo and McColm (1987) and McColm and Kotroczo (1987) investigated hydrogen sorption into the [ $\Box$ R₆] octahedra of Sc₅Si₃, Sc₅Ge₃ binary compounds and of three- and four-component alloys of solid solutions based on these binary phases. As a result the hydrides of the Y_{5-a}Sc_aSi₃H_{2.5}, Y_{5-a}Sc_aSi₃H_{1.5}, Y_{5-a}Sc_aSi₃-bGe_bH_{2.5} and Y_{5-a}Sc_aSi_{3-b}Ge_bH_{1.5} compositions have been obtained.

Venturini et al. (1989) investigated the nature of solid solutions  $(Lu_{1-x}Sc_x)_5 Ir_4Si_{10}$ and  $(Y_{1-x}Sc_x)_5Ir_4Si_{10}$  which occur between isotypic ternary compounds  $R_5Ir_4Si_{10}$  (ST  $Sc_5Co_4Si_{10}$ ). The lattice parameters of the  $(Lu_{1-x}Sc_x)_5Ir_4Si_{10}$  solution exhibit a negative deviation from Vegard's rule within its homogeneity range. Single-crystal investigations reveal that the Lu and Sc atoms statistically occupy three R atomic sites in this structure. A statistical substitution of Sc by the heavy R atoms is commonly observed in the systems, however, such admixture is rare in ternaries with light R elements. As a result, ternary compounds with ordered or partially ordered structures in the rare-earth sites occur. This is also the result of the influence of the atomic size factor. The number of compounds in the Sc-R-Si systems decreases remarkably when passing from systems with light rare earths (Sc-Ce-Si, eight ternary compounds; Sc-Nd-Si, five compounds) towards heavy rare-earth systems (Sc-Dy-Si, two compounds; Sc-Lu-Si, no compounds known) (Kotur 1995), however, simultaneously the possibility for a mutual substitution of Sc and R atoms increases. For example, the highest solubility of Sc and R at 600°C in the binary phases in the Sc–R–Si systems is as follows: 6 at.% (R = Ce), 13 at.% (R = Sm), continuous solid solution (R = Dy, Lu). The main reason for this is the decrease of the R atomic radius from Ce towards Lu due to the lanthanide contraction.

Among the d elements only Ti, Zr and Hf can form solid solutions of substitution with Sc up to continuous series of solid solutions. Such solid solutions are observed in binary as well as in ternary systems. The atomic size factor is the main reason for these phenomena.

However, the influence of other factors (beside the atomic size factor) on the interaction of the elements is obvious when comparing the ternary systems R–Sc–Si and R–Zr(Hf)– Si. These data are presented in table 32. Although the atomic sizes of Sc, Zr and Hf are nearly the same the interaction of 4A elements with the rare earths in binary and ternary systems is different from that in the corresponding systems of scandium with the rare earths. It does not depend on whether R is a light or heavy rare earth. Sc is completely miscible with Ce and Y in binary systems while Y–Zr and Y–Hf systems are of eutectic type with low mutual solubility of the components in the solid. In the Ce–Hf system an immiscibility gap in the liquid and solid occurs (Massalski 1990). The same type of behaviour is predicted for the Ce–Zr binary system.

Thus, the position of scandium among the family of rare earths is to some extent unique. Sometimes it behaves as a typical R element (e.g. showing a complete miscibility, except with Eu and Yb), however in other cases it exhibits a behaviour more similar to the d elements (e.g. displaying complete miscibility with them too, namely with Zr and Hf).

		Sys	tems		
	Y-M-Si			Ce-M-Si	
Sc	Zr	Hf	Sc	Zr	Hf
1	1	0	8	3	0
+	-	_	-	-	_
30	10	<5	<5	<2	<2
100	3	1	100	5	1
1	2	2	2	2	2
	Sc 1 + 30 100			$\begin{tabular}{ c c c c } \hline Systems \\ \hline \hline Y-M-Si \\ \hline Sc & Zr & Hf & Sc \\ \hline 1 & 1 & 0 & 8 \\ + & - & - & - \\ \hline 30 & 10 & <5 & <5 \\ \hline 100 & 3 & 1 & 100 \\ \hline 1 & 2 & 2 & 2 \\ \hline \end{tabular}$	Systems           Y-M-Si         Ce-M-Si           Sc         Zr         Hf         Sc         Zr           1         1         0         8         3           +         -         -         -         -           30         10         <5

Table 32 Comparison of characteristics of R--M-Si (M = Sc, Zr, Hf) ternary systems

References

1. Kotur and Mokra (1994)

2. Bodak and Gladyshevsky (1985)

This peculiarity of scandium is also observed in ternary systems. It is a linking element between the rare earth and the d transition elements. Zr, Hf and the heavy rare earths are the elements with which scandium forms statistical mixtures of atoms, up to a complete mutual substitution in the structures. With other elements scandium occupies regular atomic positions in the structures and forms, as usual, ternary compounds of constant composition.

### 5.4. Relations between compositions and crystal structures of scandium intermetallics

There are 155 known structure types of scandium intermetallics having a different number of representatives from only 1 up to 20 (see Appendix A). More than half of the ternary compounds studied up to now (207, ~60%) belong to only 25 structure types with representatives from 5 to 20. Of these 25, 21 structure types also occur in binary compounds or are superstructures to corresponding binary prototypes. In the group of 27 most frequently occurring structure types of scandium intermetallics there are 9 structure types, namely MgZn₂, CsCl, AlB₂, MgCu₂, Mn₅Si₃, AuCu₃, CrB, ZrSi₂, Ti₂Ni, observed for 52 binary scandium intermetallics (46%) of 5 stoichiometric compositions (see sect. 5.1). As is seen from Pearson's symbol, the compounds with simple structures and small numbers of atoms in the unit cell (from 2 up to 20) and with high symmetry (not lower than orthorhombic) occur most frequently. Only 5 structure types among 155 types are monoclinic. 28 and 77 structure types have, respectively, only two or one representatives among scandium intermetallics. Their compositions and crystal structures usually are not simple. The highest number of atoms (408) in a unit cell has Mg₄₄Rh₇ type structure.

The formation of comparatively simple, highly symmetrical crystal structures is not only characteristic for scandium intermetallics, but is typical for intermetallics in general,

Type of relation	Operation of transition from	Examples of s	tructure types
	initial to resulting type	Initial	Resulting
I. Positions of all atoms are the same	I. Ordered substitution of atomic positions by different atoms ( $\rightarrow$ superstructure)	Sm₃Ge₄ La₂Sb CaIn₂	Ce ₂ Sc ₃ Si ₄ Mo ₂ FeB ₂ ScAuSi
II. Positions of all atoms are roughly the same	II. Distortion (internal and/or external)	CaIn ₂ CeCo ₃ B ₂	KHg ₂ ErIr ₃ B ₂
III. Positions of part of atoms are the same	IIIa. Multiple substitution of atoms $(1 \rightarrow 2)$	FClPb CaCu₅	$ScCoC_2$ ThMn ₁₂
	IIIb. Addition (subtraction) of atoms	AuCu₃ NaCl	$CaTiO_3$ $Sc_2S_3$
	IIIc. Redistribution of part of atoms and cavities	MgAgAs	MgLiAl
	IIId. Redistribution of atoms	$Th_2Zn_{17}$	Th ₂ Ni ₁₇
IV. Fragments of both structures are the same	IV. Different stacking types of fragments (homeotypic rows or structures)	MgZn ₂ AlB ₂ TiNiSi	MgCu ₂ αThSi ₂ ZrNiAl
V. Roughly the same fragments, but different ratios of them	Va. One-dimensional stacking of fragments	(CaCu ₅ , Zr ₄ Al ₃ ) (CeGa ₂ Al ₂ , $\alpha$ Po)	HfFe ₆ Ge ₆ ScNi ₂ Si ₃
	Vb. Two-dimensional stacking of fragments	(CrB, TiNiSi)	Sc ₂ CoSi ₂ , Sc ₃ NiSi ₃
	Vc. Three-dimensional stacking of fragments	$(\alpha Fe, AlB_2, FeB)$ $(\alpha Fe, AlB_2)$	$Ce_2Sc_3Si_4$ Th ₇ Fe ₃

Table 33 Types of relations between structure types of scandium intermetallics

as was stated by Villars (1995). This is due to the metallic bonding prevailing in intermetallics. Structures of higher complexity appear frequently in compounds with covalent-type bonding.

Different relations within the various structure types are known to exist in intermetallic compounds in general, and this is also valid in the case of scandium intermetallics. These relations are summarised in table 33 and illustrated using examples of scandium structure types. The relations between structure types of intermetallic compounds were treated in more details by Kripyakevich (1977). He proposed systematics of the structure types of intermetallic and other related compounds, which is based on the analysis of the coordination surroundings (CN and shape of CP) of the smallest atoms in the structure.

As already mentioned, ternary scandium intermetallics often crystallize in structure types which are superstructures to binary prototypes (table 33, Appendix A). It seems convenient to us to select structure types among them which occur in large groups of elements and their combinations, see table 34. These structure types as well as their binary prototypes are frequently observed among all intermetallics having up to hundreds of known representatives. The atomic size factor has a dominant influence on distribution of atoms in ternary phases. The largest atoms in the structure normally occupy atomic

	Occurrence of some	T. structure types of te	able 34 ernary compounds a	nd their binary protot	ypes	
Composition	M ₂ M′X ₂	M ₂ M ₅ X ₄ (M,M') ₅ X ₄	MM'X	MM'X	M ₆ M' ₁₆ X ₇ M ₆ M' ₇ X ₁₆	MM ⁵ X
	$(M_3X_2)$	$(M_5X_4)$	$(M_2X)$	$(M_2X)$	$(M_6X_{23})$	$(M_4X)$
Structure type	$Mo_2FeB_2$	Ce ₂ Sc ₃ Si ₄	TiNiSi	ZrNiAl	Mg ₆ Cu ₁₆ Si ₇	CaTiO,
(binary prototype)	$(U_3Si_2)$	$(Sm_5Ge_4)$	$(anti-PbCl_2)$	$(Fe_2P)$	$(Th_6Mn_{23})$	$(\gamma Fe_4N)$
Nature of M and M' elements	3A, 4A, 3B, 4B	3A-6A	3A-8A, 1B	3A, 7A, 8A, 1B	2A-8A, 3B-4B	3A8A, 3B4B
Nature of X element	3B, 4B, 8A	8A, 1B, 4B	3B-5B	3B, 4B	8A, 3B, 4B	3B-6B
		4.4 - 14 - 40.4				

P4(m0m)							
Atomic position	Site	CN	U ₃ Si ₂	Mo ₂ FeB ₂	Sc ₂ AlSi ₂	$Sc_2Ni_2Sn$	ScCe ₂ Si ₂
M1	2( <i>a</i> )	14	U	Fe	Al	Sn	Sc
M2	4(h)	17	U	Mo	Sc	Sc	Ce
Х	4(g)	9	Si	В	Si	Ni	Si
Reference			1	2	3	4	5

Table 35 Atomic distribution in the structure of  $U_3Si_2$  and in ternary compounds with a superstructure to  $U_3Si_2$  (SG P4/mhm)

References

(1) Gladyshevsky (1971);

(2) Kuz'ma (1983);

(3) Tyvanchuk et al. (1988);

(4) Derkach and Kotur (1994)(5) Mokra (1979)

sites with the largest CN and the smallest atoms occupy positions with the smallest CN. Scandium atoms are often the largest ones in the structures, with the exception of other R elements. In those cases scandium atoms occupy atomic sites with a medium value of CN. Ternary aluminides, gallides, silicides and germanides sometimes form isotypic compounds which belong to the same superstructure types, for e.g. ZrNiAl,  $Mg_6Cu_{16}Si_7$  (see Appendix A). The Al and Ga atoms in these structures are usually larger than transition element atoms. Therefore they occupy opposite sites in comparison with the isotypic ternary scandium transition element silicides and germanides in which Si and Ge atoms are usually the smallest ones. Some examples are presented in table 35. Sometimes it causes the change of stoichiometry of compounds:  $Sc_6Co_1GSi_7 \rightarrow Sc_6Co_7Ga_{16}, Ce_2Sc_3Ge_4 \rightarrow V_3Sc_2Ge_4, ScCo_3C \rightarrow SnSc_3B.$ 

 $Ho_{11}Ge_{10}$  is the binary prototype of differently ordered or partially ordered ternary structures (superstructures)  $Sc_7Cr_{4+x}Si_{10-x}$  (Kotur et al. 1985a),  $Sc_7Re_{4-x}Si_{10+x}$  (Zhao et al. 1988) and  $Sc_{11}Al_2Ge_8$  (Zhao and Parthé 1991) and  $Sc_6Yb_5Ge_{10}$  (Kotur et al. 1996b). A detailed analysis of these structures has been reported in the latter paper. The stoichiometries of these phases vary in wide limits as the result of substitution of different R and X atomic sites by d elements (Cr, Mn), and by statistical mixtures of d and p elements (Re, Si). Other ternary substitution variants of the  $Ho_{11}Ge_{10}$  binary prototype are also possible. It can be expected that in the near future the  $Ho_{11}Ge_{10}$  structure type may belong to the group of most frequently occurring structure types of intermetallic compounds.

The structures of many binary and ternary scandium borides and carbides may be deducted from other structure types by a multiple substitution of larger atoms by B–B or C–C pairs or by the inclusion of B or C atoms into the cavities of the parent structure types. The same is valid for the structures of scandium intermetallics with the 6B elements. The  $Ti_7S_{12}$ , NiAs,  $ErAgSe_2$  and  $Al_2MgO_4$  structure types can be obtained by an inclusion of cations of metals into the octahedral and tetrahedral cavities of different packings (usually close ones) of 6B anions. Frequently the inclusion of atoms causes a distortion of the parent close-packed structure.

A large group of scandium intermetallics contain fragments of simpler structure types connected in different manners. Some of these hybrid structures contain fragments of two, three or even more structure types. Usually the initial fragments are distorted during their connection in the hybrid structure. Such distortions are minimal in linear hybrid structures. The dimensions of initial fragments, their number and the manner of mutual connection determine the dimensions and the symmetry of the resulting hybrid structure. Often fragments of the following structure types: aPo (empty cube), aFe (bodycentered cube), AlB₂ (body-centered trigonal prism) and BaAl₄ (body-centered tetragonal antiprism), are observed as the initial fragments for hybrid structures. Besides these, atomic groups (clusters) such as octahedron- and icosahedron-shaped are found as the structure fragments. The initial fragments can be eliminated from the parent structures along the axes of the unit cells or eliminated randomly in comparison to these axes. Substitutions of atomic positions of the same structure fragments by different atoms with different sizes cause distortions of the same fragments in different structures. In the following discussion possible distortions of structure fragments will not be taken into consideration and we will use the names of ideal clusters.

While analysing the compositions of scandium intermetallic compounds we hinted at the regularity of occurrence of large numbers of compounds on some characteristic cross sections of phase diagrams (see figs. 93 and 94). The crystal structures of these compounds which are in two-phase equilibrium with each other are related and contain one or more mutual fragments, but in different ratios. For example, on the crosssection Sc:X=1:1 of the ternary systems Sc-M-X (M=Fe, Co, Ni; X=Si, Ge) the following ternary compounds occur: ScMX (ST TiNiSi), Sc₃M₂X₃ (ST Hf₃Ni₂Si₃), Sc₂MX₂ (ST Sc₂CoSi₂), Sc₃MX₃ (ST Sc₃NiSi₃), and ScX (ST CrB). These compounds form an interesting series of structures  $ScMX \rightarrow Sc_3M_2X_3 \rightarrow Sc_2MX_2 \rightarrow Sc_3MX_3 \rightarrow$ ScX (Gladyshevsky and Kotur 1978, Kotur and Gladyshevsky 1983). As can be seen from fig. 96 three intermediate members of this series contain fragments of the outer two, ScMX and ScX. In this series the Sc:X ratio remains the same, 1:1, however, the decrease of the number of the M atoms cause the decrease and finally the disappearing of the TiNiSi-type fragments. The number of CrB-type fragments increases from the Sc₃M₂X₃ structure towards ScX. Thus, TiNiSi and CrB are the parent structure types of the homological series of structures with three known members. It is possible to predict the existence of other members in this series and construct their hypothetical structures. In particular, if we add one unit cell of ScSi along the c direction in the  $Sc_3NiSi_3$  (I) structure, we obtain a structure of the same symmetry (SG C2/m) represented by the formula Sc₄NiSi₄ (II). The monoclinic unit cell of this hypothetical structure will have the following dimensions:  $a(II) \approx a(I) \approx 10$  Å,  $b(II) \approx b(I) \approx 4$  Å,  $c(II) \approx c(I) + c(ScSi) \approx 10$ 16.5 Å,  $\beta \approx 95-98^{\circ}$  (Kotur and Gladyshevsky 1983). Taking into account that the CrBtype structure is the linear hybrid structure of AlB₂ and  $\alpha$ Fe types, the structures of above discussed homological series are thus two-dimensional hybrids of three structure types, namely  $\alpha$ Fe, AlB₂ and TiNiSi.

The germanide  $Sc_9Ni_5Ge_8$  occurs very close to the Sc:X=1:1 cross-section. Its structure has been determined by Andrusyak et al. (1989), and appeared to be a more



Fig. 96. Relations between the structure types TiNiSi (ScCoSi), Hf₃Ni₂Si₃ (Sc₃Co₂Si₃), Sc₂CoSi₂, Sc₃NiSi₃ and CrB (ScSi). The structures are presented in the projections along 010 or 100. Unit cells and structure fragments are indicated by dashed and solid lines respectively.

complicated two-dimensional hybrid of four structure types, namely  $\alpha$ Fe, AlB₂, TiNiSi and Mo₂NiB₂ (fig. 97).

The structure of ScNiSi of the TiNiSi type can be presented as consisting of infinite zigzag walls of trigonal prisms  $[XM_4X_2]$  (see Kotur and Sikirica 1982b). Also the structure of Sc₃Ni₄Si₄ (ST Gd₆Cu₈Ge₈) contains trigonal prisms and is in equilibrium with ScNiSi. In the Sc–Cu–Si ternary system the compound Sc₃Cu₄Si₄ (ST Gd₆Cu₈Ge₈) is in equilibria with ScCuSi (r) (ST TiNiSi) and ScCuSi (h) (ST ZrNiAl). The structure of the latter compound is also built of trigonal prisms. As is seen from the stoichiometries of the ternary compounds presented, they occur on the cross-sections M: X = 1:1 and therefore their crystal structures are related and contain mutual fragments.

In the numerous ternary R–M–X systems on the cross-sections R:M=1:1 there are ternary compounds of the compositions RMX₂ and RMX₃, which belong to the structure types of CeNiSi₂ and ScNiSi₃ (Gladyshevsky and Bodak 1982). As follows from fig. 98, the structures of these compounds are related and contain mutual fragments of AlB₂ and CeGa₂Al₂ (superstructure to BaAl₄) types. Although there are no data to date for any scandium compound of CeNiSi₂ type, the silicide ScNiSi₃ contains its fragments in its structure. There are relations between the structures of compounds occurring on other cross-sections, e.g. Sc:M=1:2. The compounds ScNi₂Si₃ (ST ScNi₂Si₃) and ScNi₂Si₂ (ST CeGa₂Al₂) are in equilibrium with each other and contain a mutual structure fragment



Fig. 97. Connection of fragments (indicated by solid lines) of  $\alpha$ -Fe, AlB₂, Mo₂NiB₂ and TiNiSi structure types in the structure of Sc₉Ni₅Ge₈. Unit cells are indicated by dashed lines. The structures are presented in the projections along 001 or 010.

(fig. 98). The structures  $ScNiSi_3$ ,  $ScNi_2Si_3$  and  $CeNiSi_2$  presented in fig. 98 are linear hybrid structures.

The linear hybrids of two structure types,  $CeGa_2Al_2$  and  $\alpha Fe$ , are ternary carbides  $Sc_3CoC_4$  and  $ScCoC_2$ , which are in equilibrium with each other and occur on the isoconcentrate of 50 at.% C in the Sc–Co–C system.

The examples, discussed above, show that ternary compounds which are in equilibrium with each other are related with respect to their crystal structure. These compounds contain at least one mutual fragment or atomic cluster. Sometimes they form homologous series of structures. This fact can be used for the investigation of compounds with unknown crystal structure. However, to date there are a number of powerful program packages available for the determination of crystal structures by direct methods. However, the application of direct methods for structure determination using powder X-ray data is sometimes not successful, especially for complex structures. In such cases the knowledge of structure relations between compounds which are in equilibria becomes very useful if the structures of some of them are known.

We used such an approach for determination of the crystal structure of  $ScFe_6Ge_5$  (Kotur 1995). In the ternary systems Sc-Mn-Ge and Sc-Fe-Ge on the cross-sections Sc:Mn(Fe)=1:6 the compounds  $ScM_6Ge_6$  (M=Mn, Fe),  $ScFe_6Ge_5$  and  $ScM_6Ge_4$  (M=Mn, Fe) exist. The germanides  $ScM_6Ge_6$  and  $ScM_6Ge_4$  belong to the structure types  $HfFe_6Ge_6$  (Olenych et al. 1981) and  $ZrFe_6Ge_4$  (Olenych 1989), respectively. The structure of the  $HfFe_6Ge_6$  type can be deducted from the CaCu₅ type by a multiple substitution of the pair of X-X atoms for the M atoms in every second layer (fig. 99). The structure of



Fig. 98. Relations between structures  $ScNiSi_3$ ,  $CeNiSi_2$  occurring on the cross-sections R:M=1:1 and  $ScNi_2Si_3$ ,  $ScNi_2Si_2$  (ST  $CeGa_2Al_2$ ) occurring on the cross-sections R:M=1:2. The structures are presented in the projections along 100 or 010. Unit cells are indicated by dashed lines. Fragments of the structures: (I)  $\alpha$ Po, (II)  $CeGa_2Al_2$ , (III)  $AlB_2$ , (IV)  $CeNiSi_2$ .

HfFe₆Ge₆ (IV) is also a linear hybrid of the CaCu₅ (I) and the Zr₄Al₃ (II) types (fig. 99), whereas the structure of the ZrFe₆Ge₄ (V) type is a linear hybrid of the CaCu₅ (I) and Fe₃Sn₂ (III) types (fig. 99). The ZrFe₆Ge₄ type structure can also be treated as resulting from an inclusion of R(Sc) atoms into the Fe₃Sn₂ structure (fig. 99).

Expecting genetic relations between the structures of ScFe₆Ge₅ and ScFe₆Ge₆ (IV) and ScFe₆Ge₄ (V), with which the first one are in equilibria, Kotur (1995) deducted a theoretical model for the crystal structure of ScFe₆Ge₅ as a linear hybrid of the fragments IV and V. This model, containing 72 atoms in the unit cell, is presented in fig. 99. The dimensions of the fragments IV and V, their quantities, 3 + 3, and symmetry allowed one to determine roughly the unit cell dimensions and the symmetry: SG  $R\overline{3}m$ ,  $a \approx 5$  Å,  $c \approx 44$  Å. This theoretically predicted structure has been confirmed experimentally by X-ray powder diffraction data; the refined lattice parameters are: a = 5.063(1) Å, c = 44.11(1) Å (Kotur 1995).



Fig. 99. Relations of the structures  $CaCu_5$ ,  $ScFe_6Ge_6$  (ST  $HfFe_6Ge_6$ ),  $Zr_4Al_3$ ,  $Fe_3Sn_2$ ,  $ScFe_6Ge_4$  (ST  $ZrFe_6Ge_4$ ) and  $ScFe_6Ge_5$ . The structures are presented in the projections on the plane of the large diagonal of the hexagonal basis. Unit cells are indicated by dashed lines. Fragments of the structures: (I)  $CaCu_5$ , (II)  $Zr_4Al_3$ , (III)  $Fe_5Sn_2$ , (IV)  $ScFe_6Ge_6$ , (V)  $ScFe_6Ge_4$ .

The change of compositions of compounds is connected with the changes of coordination surroundings of atoms. Kotur (1995) performed a crystal structure analysis of all known structure types of scandium intermetallics based on the classification presented by Kripyakevich (1977). The structure types have been classified on the basis of the CN and the shape of the CP of the smallest atoms in the structure. In some cases the X atoms are the smallest in the structure but sometimes the M atoms are the smallest, especially if M is a d element. It was found that the compounds with a high M content (>50 at.%) and a low X content (<30 at.%) frequently have the CN 12 and the CP of icosahedra and cubooctahedra for the smallest atoms. The compounds of the central part of ternary systems with Sc content 15 up to 30 at.% and the X content between 30 and 50 at.% have CN 8 (+1 or 2) and a CP of tetragonal antiprism for the smallest atoms. For high X (>50 at.%) and Sc (>30 at.%) content the compounds are characterised by a trigonal prismatic coordination of the smallest atoms [CN 6 (+1, 2 or 3)]. At high Sc content binary compounds have icosahedral coordination of the smallest atoms. These regularities are invalid in the systems of X elements (B, C, As), with a pronounced nonmetal character. Scandium intermetallics with these elements have, as usual, trigonal prismatic, octahedral (CN 6) and tetrahedral (CN 4) coordination of the X atoms.



Fig. 100. Coordination polyhedra of atoms: (a) cubooctahedron; (b) icosahedron with two tetrangular planes; (c, d) normal icosahedron in two projections; (e) trigonal prism with three additional atoms; (f) tetragonal antiprism with one additional atom; (g, i, k) octahedron in different projections; (h) trigonal prism with one additional atom. The arrows near atoms show the approximate direction of their shifts, which cause the transformation of this CP into the neighbouring one, indicated by a long arrow (for additional explanation see text).

Figure 100 represents the transformations of the CP of atoms observed in the structures: cubooctahedron (CN 12)  $\rightarrow$  icosahedron with two quadrangular planes (CN 12)  $\rightarrow$ normal icosahedron (CN 12)  $\rightarrow$  trigonal prism with additional atoms [CN 6 (+3)]  $\rightarrow$ tetragonal antiprism with additional atom [CN 8 (+1)]  $\rightarrow$  octahedron (CN 6) and also the transformation of trigonal prism with additional atom [CN 6 (+1)]  $\rightarrow$  octahedron (CN 6). Numerous examples of these CP can be found in the original papers for the structures of intermetallics. Namely, CP (a) from fig. 100 is observed for the atoms of the AuCu₃ ST, [AuCu₁₂] and [CuAu₄Cu₈] (Kripyakevich 1977). Slightly distorted cubooctahedrons [ScRh₆Ge₆] exist in the Sc₄Rh₇Ge₆ structure (ST U₄Re₇Si₆, Engel et al. 1984). CP (b) and (c) have Cu atoms in the CaCu₅ type structure (Kripyakevich 1977). Upon formation of the superstructure of the  $CeCo_3B_2$  type to this prototype the c/a ratio (=0.600) decreases remarkably in comparison to the binary RM₅ structures (c/a = 0.774 - 0.822). This is caused by the substitution of two boron atoms for two cobalt atoms in the unit cell. The CP of boron atoms changes from icosahedra to trigonal prism with three additional atoms (Kuz'ma 1983). This example shows the mechanism of the transformation of the (d)-type CP into the (e)-type CP. A classical representative of the (e)-type CP is the AlB₂-type structure (Kripyakevich 1977). A CP of the (f) type is found in the BaAl₄ or the CeGa₂Al₂ ST (Kripyakevich 1977) or the Sc₄Rh₇Ge₆ (ST  $U_4 Re_7 Si_6$ , Engel et al. 1984) type structure. An intermediate position between the CP of the (d) and (e) types is occupied by Co atoms in the structure of  $Sc_5Co_4Si_{10}$  (Braun et al. 1980). This structure is a two-dimensional hybrid of the following four types: AlB₂ (trigonal prisms [SiSc₆]), CsCl (empty tetrahedra (Sc₂Si₂]), AuCu₃ (cubooctahedra  $[ScSi_{12}]$  and CeGa₂Al₂ (tetragonal antiprisms  $[CoSc_4Si_4]$ ) (fig. 101). A CP intermediate between (f) and (g) and between (h) and (i) [or (i) and (k)] contains the structure of





 $V_3As_2$ -type (Berger 1977). Transformation of CP of atoms can also occur in the opposite direction, from CP 6 to CP 12. It is caused by a change of the dimensions of different atoms and their content in the structures. Other types of coordination surroundings of the smallest atoms in the structures of intermetallics are observed rarely.

Figure 102 represents generalised relations between the majority of the structure types of scandium intermetallics. Some of these relations have been established by Gladyshevsky and Bodak (1982). Relations between other structure types, published after 1980, have been established by Kotur (1995). Analysis of the structure types of intermetallic compounds leads to an enrichment and a broadening of our knowledge about relationships between structure types. These investigations are basic for the illumination of the nature of intermetallics and the functional relations between the compositions and structures of compounds and the factors which govern these changes.

### 6. Physical properties of scandium based intermetallics

Among scandium compounds and in compounds where scandium replaces other rareearth elements, magnetic and nonmagnetic intermetallics exist, however, there are also scandium compounds showing superconductivity, although the scandium metal is neither magnetic nor shows superconductivity at atmospheric pressure. An extensive part of this section deals with interesting magnetic phenomena observed in the ScM₂ (M=Mn, Fe, Co, Ni) Laves phases. In the Mn- and Co-containing Laves phases the influence of spin fluctuations on the various physical properties is demonstrated.

Since scandium is one of the nonmagnetic elements among the rare-earth series one might expect that the physical properties of compounds with scandium and the other nonmagnetic rare-earth elements (Y, La or Lu) are the same or at least very similar. This supposition is true in principle, however because of the much smaller atomic size of scandium compared with yttrium and also lutetium a deviating physical behaviour of the corresponding scandium compounds is frequently observable.





#### 6.1. Compounds with non-magnetic and non-superconducting ground state

## 6.1.1. RAuGe (R = Sc, Y and Lu)

The ternary RAuGe series of compounds exhibits interesting physical properties, as shown by Rossi et al. (1992) and Pöttgen et al. (1996). Details of the crystal structure, the magnetic susceptibility, the electrical resistivity, the specific heat and the electronic band structure of the four isostructural nonmagnetic RAuGe compounds (R = Sc, Y, La, Lu) have been studied recently by Schnelle et al. (1997). These four compounds are weak diamagnets. The Sc-based compound has been included in this investigation because of the small atomic size of scandium. As will be shown, the variation of the rare-earth ionic radius among this series improves our general understanding of the physical properties in this family of rare-earth intermetallics.

The structures of these compounds are derived from the CaIn₂-type structure by an ordered arrangement of the gold and germanium atoms on the indium position. The gold and germanium atoms form two-dimensional Au–Ge polyanions. However a three-dimensional network of elongated tetrahedra is present in ScAuGe (Pöttgen et al. 1996).

The degree of puckering of the Au–Ge hexagons is strongly dependent on the size of the rare-earth atoms. While the layers are almost flat in the La compound, strong puckering is observed in the other germanides. In LaAuGe and YAuGe the interlayer Au–Ge distance is 3.858 Å and 3.106 Å, respectively; the Au–Ge polyanions are twodimensional and separated from each other. In LuAuGe the interlayer Au–Ge distance amounts to 2.927 Å, indicating a weak coupling between the layers. The transition from Au–Ge layers to a three-dimensional network of elongated tetrahedra occurs for ScAuGe. The structure of LaAuGe and YAuGe may therefore be described as being of the NdPtSb type, whereas the structures of ScAuGe and LuAuGe (with the smaller rare-earth ionic sizes) are closer to that of LiGaGe (Pöttgen et al. 1996).

The use of rare-earth atoms with different radii among this series reveals a remarkable variation of the c/a ratio (ScAuGe: c/a = 1.589, LaAuGe: c/a = 1.830) which leads to a flattening of the three-dimensional Au-Ge network of elongated tetrahedra (in ScAuGe) towards LaAuGe accompanied by an increasing of the coupling between the Au-Ge layers in the c-direction. The electronic band structure and the density of states deduced from this calculation is in general similar for the compounds with Sc, Y and Lu. Only LaAuGe shows some small but important differences. In fig. 103 the calculated densities of states of the four compounds are shown and can be compared. The Ge s bands are around 11 eV below  $\varepsilon_{\rm F}$ , except for LaAuGe where the Ge s bands are about 1 eV higher in energy. The Au d bands are situated at around -6 eV and again these bands are 1 eV higher in LaAuGe, For LuAuGe the Lu f bands coincide with the d bands. The lowest unoccupied bands are the Sc.Y. La or Lu d bands. The densities of states at the Fermi level  $N_{\rm F}$  are: ScAuGe, 1.4, YAuGe, 0.6, LaAuGe, 2.1, LuAuGe, 0.4 in units of eV⁻¹ for two spins and one RAuGe formula unit. The higher density of states of the LaAuGe compound explains its exceptional behaviour among the four compounds in this series. This will be seen from the discussion of other physical properties. The magnetic susceptibility  $(\chi)$ of the RAuGe compounds in a field of 4 T is shown in fig. 104. An attempt to fit their




Fig. 104. Magnetic susceptibility of the RAuGe compounds at a field of 4 T (Schnelle et al. 1997).

Fig. 103. The density of states of ScAuGe, YAuGe, LaAuGe and LuAuGe. The dashed line (at E = 0) is the Fermi level (Schnelle et al. 1997).

 $\chi(T)$  behaviour has been undertaken using the following formula:  $\chi(T) = C/T + \chi_0 + aT$ . The upturn in the region below 50 K described by the Curie-term (C/T) is thought to be due to magnetic impurities. The temperature-independent part  $\chi_0$  is the sum of the diamagnetic susceptibility of the closed shell and conduction-electron contributions. The linear decrease in case of ScAuGe, LaAuGe and LuAuGe towards room temperature is taken into account by the aT term and has been attributed to a temperature dependence of the conduction-electron susceptibility.

The specific heat data have been analysed in a  $c_{\rm P}/T$  vs.  $T^2$  representation. From the respective intercepts and the slopes of the straight lines fitted to the data the electronic specific heat coefficient  $\gamma$  and the Debye temperature  $\Theta_{\rm D}$  at lowest temperature are obtained. While the ScAuGe, YAuGe, and LuAuGe compound exhibit  $\gamma$  values below 1 mJ mol⁻¹ K⁻², LaAuGe has a markedly larger electronic specific term of 2.5 mJ mol⁻¹ K⁻². The so-called Wilson ratio  $\chi_{\rm P}/\gamma$  (where  $\chi_{\rm P}$  denotes the Pauli susceptibility of the conduction electrons) is similar for YAuGe, LaAuGe, and LuAuGe, however the values are enhanced over the value of unity expected for a Fermi–Sommerfeld free electron gas. Values between 3.6 and 3.8 are found for the Y, La and Lu compound, while for ScAuGe 6.4 has been obtained (the possible reasons for this high value have been discussed by Schnelle et al. 1997).

LaAuGe exhibits the highest values of  $\gamma$  and  $\chi_P$  among the four compounds. This correlates well with the larger density of states obtained in the band-structure calculations. Similar observations have been made in other series, namely LaAl₂, YAl₂ and LuAl₂ (Hungsberg and Gschneidner 1972, Bauer et al. 1985), and LaAg, YAg and LuAg (Bauer et al. 1986) for the corresponding La compounds. In this latter cases the La compounds show superconductivity below 4.2 K. Thus it might be that also in LaAuGe a superconducting transition exists at temperatures below 4.2 K. The much stronger curvature of the  $\rho(T)$  curves of LaAuGe (shown in figure 7 of Schnelle et al. 1997) is obviously a further indication for the possibility of superconductivity in this compound.

#### 6.1.2. Crystal field parameters of lanthanides diluted in ScAl₂, YAl₂ and LuAl₂

An example where a Sc compound is included in a systematic investigation (because of its small lattice parameter) is described as follows. A systematic inelastic neutron scattering experiment has been performed by Frick and Loewenhaupt (1985) on diluted lanthanide elements in the nonmagnetic matrix of ScAl₂, YAl₂ and LaAl₂. The aim was to obtain information about the origin of the crystal field (CF) in metals in general and especially to determine a set of CF parameters for the lanthanides when diluted in different nonmagnetic matrices of cubic Laves phases.

The concentration of the lanthanide elements in the hosts  $ScAl_2$ ,  $YAl_2$  and  $LaAl_2$  was chosen to be between 0.3 and 3 at%. The time-of-flight experiment was performed at an elevated temperature where the neutrons can gain energy from the system. The intensity caused by magnetic scattering was limited to the energy range below 10 meV, and it is well separated from the phonon intensity which is typically in the range of about 10 to 30 meV. The scattering data was then fitted to a theoretical model given in Becker et al. (1977) yielding the temperature-independent CF parameters x and W in the Lea-Leask-Wolf notation (Lea et al. 1962). From x and W the parameters  $A_4(r^4)$  and  $A_6(r^6)$  and finally  $A_4$  and  $A_6$  were calculated using  $(r^n)$  from Freeman and Desclaux (1979). The resultant crystal field parameters  $A_4$  and  $A_6$  in the hosts (ScAl₂, YAl₂ and LaAl₂) are plotted as a function of the atomic number of the lanthanide element in fig. 105. (There are no data for the CF levels of the elements Pm, Sm, Eu and Gd because Pm does not exist naturally, the CF of Sm, Eu show the influence of higher multiplets, and the CF influence is zero in Gd). As can be seen the  $A_4$  values are all positive whereas all the  $A_6$  values are negative. The values of  $A_4$  and  $A_6$  increase from ScAl₂ to YAl₂ to LaAl₂. The variation of  $A_4$  and  $A_6$  with the atomic number shows a similar behaviour for the three matrices. A calculation of the electronic potential of the point charges surrounding the 4f ions leads to negative A4 and A6 values, assuming positive charges of the same order for Sc, Y, La and Al. Taking into account the difference in the lattice constant of ScAl₂, YAl₂ and LaAl₂ and the difference in the electronegativity of Sc, Y and La, the relative distance between the  $A_4$  and  $A_6$  levels from in experiment and those calculated



Fig. 105. The experimentally determined crystal field parameters  $A_4$  and  $A_6$  in the hosts ScAl₂, YAl₂ and LaAl₂ as a function of the rare-earth atom [the elements Pm, Sm, Eu and Gd do not exist naturally (Pm), show the influence of higher CF level (Sm, Eu), or the CF influence is zero (Gd)] (Frick and Loewenhaupt 1985).

are in agreement. However the more surprising observation was the positive sign of the  $A_4$  CF parameters which should be negative as are the  $A_6$  values according to the simple point-charge calculation. In the paper of Frick and Loewenhaupt (1985) it is argued that not well-screened effective point charges on the neighbouring atoms of the 4f ions and the nonspherical conduction electrons are responsible for the shape of the CF potential in RAl₂ and especially for the deviation of the experiment from the calculation based on a simple point-charge model.

## 6.1.3. Spin fluctuations in $RCo_2$ compounds (R = Sc, Y, Lu)

ScCo₂ crystallises in the cubic Laves phase type structure. It belongs to the family of the rare-earth-transition metal compounds with 1:2 stoichiometry where the magnetic state of the Co sublattice is strongly influenced by the magnetic partner elements. In compounds with magnetic rare-earth atoms as partner elements, induced moments appear on the Co sites in the magnetically ordered state. These induced 3d moments exist only in the presence of a magnetic surroundings and range from  $1.05\mu_{\rm B}$  in GdCo₂ down to  $0\mu_{\rm B}$ in ScCo₂, YCo₂ and LuCo₂. Due to the variability of the Co moments in combination with the stable permanent moments on the lanthanide atoms in the magnetically ordered RCo₂ compounds Bloch and Lemaire (1970) used the concept of the exchange-enhanced paramagnetism for the Co sublattice and developed a phenomenological model to decribe the exchange-induced moment on Co. From this model it was deduced that the R-Co interaction is about twice as strong as the Co-Co interaction, which is in agreement with investigations of the magnetoelastic properties first performed by Lee and Pourarian (1976). The magnetic fields available nowadays in some laboratories are high enough to exit the critical field for induced Co moments in YCo2 which is about 70 T (Goto et al. 1990). These three Co-based Laves phases to which ScCo₂ belongs are enhanced paramagnets. The temperature variation of the susceptibility shows maxima at elevated temperatures (YCo₂: 260 K, LuCo₂: 370 K, ScCo₂: 550 K, see fig. 106) whereas in the low-temperature region an increase of  $\chi(T)$  proportional to  $T^2$  has been found (Burzo et al. 1993). The  $\chi$ -values at 0 K as given by Ikeda et al. (1991) are:  $\chi(YCo_2) = 6.0$ ,  $\chi(LuCo_2) = 3.96$ ,  $\chi(ScCo_2) = 3.67$  in units of  $10^{-4}$  emu/(g-atom). The values for YCo₂ and  $LuCo_2$  are not in complete agreement with the data shown in fig. 106 at the lowest



Fig. 106. The high-field dc magnetic susceptibility of the three spin fluctuation systems  $ScCo_2$ ,  $YCo_2$  and  $LuCo_2$  (Burzo et al. 1993).

temperatures. This is however not surprising, since the  $\chi$ -values are strongly influenced by the quality of the sample material (Steiner and Ortbauer 1974 found that grinding of the sample material can cause a rise in susceptibility by a factor of three).

There is also an enhancement of the electronic specific heat coefficients  $\gamma$  ( $\gamma$ (YCo₂)= 33.1,  $\gamma$ (LuCo₂)=26.6, and  $\gamma$ (ScCo₂)=18.4 in units of mJ (mol-Co)⁻¹ K⁻²) (Ikeda et al. 1991), which in the case of ScCo₂ is larger by a factor of three than that of ScNi₂.

The concept of spin fluctuations (details are given in the book by Moriya 1985) has been successfully used to describe the enhanced  $\gamma$ -value and the temperature variation of the susceptibility. The influence of spin fluctuations on the transport phenomena in these RCo₂ compounds (R = Sc, Y, Lu) has been investigated recently by Gratz (1997).

Spin fluctuations contribute to the transport phenomena since they scatter conduction electrons through the exchange interaction. This problem has been treated using a twoband model where the electrons in the conduction band carry charge or heat while those in the narrow d band contribute to the spin fluctuations which scatter the conduction electrons through the s-d exchange interaction. The first publications dealing with this problem date back to the late 1960s (Mills and Lederer 1966, Schindler and Rice 1967, Mathon 1968). These calculations were later continued by Coqblin et al. (1978). The results can be summarised as follows:

*Electrical resistivity:*  $\rho \propto T^2$ , with the tendency to saturate at elevated temperatures; *Thermal resistivity:*  $W \propto T$  at low temperatures, followed by a maximum. *Magnetoresistance:*  $(\Delta \rho / \rho)$  is negative and proportional to the square of the applied field.

The temperature dependence of the electrical resistivity  $\rho$  of ScCo₂, YCo₂ and LuCo₂ is shown in fig. 107. To illustrate the influence of the spin fluctuation scattering in these Co-based compounds, the  $\rho(T)$  dependence of the two isostructural non-spin-fluctuation compounds YAl₂ and LuNi₂ is given in this figure too. Both phonon scattering and spin-fluctuation scattering cause a change of  $\rho$  with temperature. For the spin-fluctuation contribution to  $\rho(T)$  the curvature at elevated temperatures and the  $T^2$  increase at low temperatures is confirmed by the experiment. A quantitative analysis of  $\rho(T) - \rho_0$  versus  $T^2$  is depicted in the inset of fig. 107. The low-temperature resistivity is dominated by the quadratic increase due to the spin-fluctuation scattering giving rise to the enhanced

498



Fig. 107. The electrical resistivity of ScCo₂, YCo₂ and LuCo₂ from 4K to 1000 K, where  $\rho_0(\text{RCo}_2)=18$ , 24 and 17  $\mu\Omega$ cm, respectively. The increase of  $\rho(T)$  in the non-spin-fluctuation systems YAl₂ and LuNi₂ ( $\rho_0=5.6$  and 4.2  $\mu\Omega$ cm, respectively) is shown for comparison. Inset: low-temperature  $T^2$  dependence of the spin fluctuation systems (Gratz 1997).

Fig. 108. The thermal conductivity of ScCo₂, YCo₂, LuCo₂ and YAl₂ from 4 K to 300 K. Inset: the fit of  $\lambda(T) = (aT^{-1} + bT^2 + cT)^{-1} + dT^2$  to the experimental data is given by the solid lines (Gratz 1997).

factor A. According to the theory of spin fluctuations (Coqblin et al. 1978) the factor A is related to the corresponding spin-fluctuation temperatures by the relation  $A \propto T_{sf}^{-2}$ . This factor has the following values:  $A(YCo_2) = 16$ ,  $A(LuCo_2) = 12$  and  $A(ScCo_2) = 4.3$  in units of n $\Omega$  cm K⁻². The thermal conductivity  $\lambda$  of these spin-fluctuation systems is shown in fig. 108 (again the  $\lambda(T)$  curve for YAl₂ is included). In the spin-fluctuation compounds one observes a pronounced curvature in  $\lambda(T)$  in the region 20 K  $\leq T \leq 60$  K which is not observable in YAl₂. For temperatures higher than about 50 K  $\lambda(T)$  is nearly constant and decreases from ScCo₂ towards YCo₂. Since the analysis of thermal conductivity data is not frequently shown in the literature it should be outlined here in more detail. Using the theoretically obtained  $\lambda(T)$  dependencies for the different scattering processes (see also Ziman 1960), one can account for the variation of  $\lambda(T)$  at low temperatures:

$$\lambda(T) = \lambda_{\rm e} + \lambda_{\rm l} = \frac{1}{W_{\rm e,0} + W_{\rm e,ph} + W_{\rm e,sf}} + \lambda_{\rm l},$$

where  $\lambda_e$  and  $\lambda_1$  denote the electronic and the lattice thermal conductivity, respectively, and  $W_{e,0}$ ,  $W_{e,ph}$  and  $W_{e,sf}$  are the thermal resistivities due to impurity-, phonon- and spin-



Fig. 109. The thermopower of  $ScCo_2$ ,  $YCo_2$ ,  $LuCo_2$  and  $YAl_2$  from 4K to 1000 K. Inset: correlation between the position of the high-temperature minima  $T_{min}$  and the  $\gamma$  value of the specific heat in  $ScCo_2$ ,  $YCo_2$  and  $LuCo_2$  (Gratz 1997).

fluctuation-scattering processes, respectively). With  $W_{e,0} \propto 1/T$ ,  $W_{e,ph} \propto T^2$ ,  $W_{e,sf} \propto T$ and  $\lambda_1 \propto T^2$  we finally obtain

$$\lambda(T) = \frac{1}{a(1/T) + bT^2 + cT} + dT^2.$$

Using the Wiedemann–Franz law, the coefficient *a* can be determined from the residual electrical resistivity  $\rho_0$ . Least-squares fits to the experimental data up to 75 K are given by the solid lines in the inset of fig. 108. Interestingly the fit procedure shows that the  $W_{e,ph}$  term is much smaller compared to  $W_{e,sf}$  in these RCo₂ series. The linear  $W_{e,sf}$  term is dominating and responsible for the pronounced curvature in  $\lambda$  vs. *T* between 20 K and 60 K. The *c*-values ( $W_{e,sf} = cT$ ) are related to the spin-fluctuation temperatures  $c \propto T_{sf}^{-1}$  (Coqblin et al. 1978). The *c*-values are:  $c(YCo_2) = 23 \times 10^{-5}$ ,  $c(LuCo_2) = 21 \times 10^{-5}$ , and  $c(ScCo_2) = 11 \times 10^{-5}$  in units of cm/mW. Note that, from the tendency of the *c*-values as well as from the *A* coefficients in  $\rho_{sf}(T) = AT^2$ , it follows that  $T_{sf}(YCo_2) < T_{sf}(LuCo_2) < T_{sf}(ScCo_2)$ .

In fig. 109 the temperature dependence of the thermopower S of the RCo₂ compounds is depicted and compared with YAl₂. Note that in the Co compounds the minima in S vs. T at low temperature are much more pronounced than in the non-spin-fluctuation system YAl₂. The tiny minimum at low temperature, existing also in YAl₂, has been referred to as 'phonon drag' effect (Gratz and Nowotny 1985). In general such a 'drag effect' is thought to be caused by the situation that, in addition to the conduction electron system, other subsystems (phonons or magnons) are thermally in non-equilibrium and may cause an additional contribution to the total thermopower. This is usually taken into account by putting  $S_{tot} = S_{diff} + S_{drag}$ , where  $S_{diff}$  and  $S_{drag}$  are the diffusion and drag terms (Ziman 1960). Although no theoretical confirmation for such a '*paramagnon drag effect*' yet exists, experimentally minima (or sometimes maxima, depending on the slope of the density-of-states function at  $\varepsilon_F$ ) have been observed in many paramagnetic spin fluctuation systems near their spin fluctuation temperatures, e.g. in UAl₂ (Coqblin et al. 1978). The broad minima at elevated temperatures are intimately correlated to changes of  $dN(\varepsilon)/d\varepsilon$ at  $\varepsilon_F$  with temperature (Gratz et al. 1995). Density-of-states properties at the Fermi level



Fig. 110. The locations of the three  $RCo_2$  (R=Sc, Y, Lu) spin fluctuation systems in the Kadowaki–Woods plot.

 $[N(\varepsilon_{\rm F})$  and  $dN(\varepsilon)/d\varepsilon$  at  $\varepsilon_{\rm F}]$  are much more important for the diffusion thermopower at high temperature than for any of the other transport phenomena (Ziman 1960, Gratz et al. 1995). A correlation between the position of the high-temperature minima  $T_{\rm min}$  in S(T) and the  $\gamma$ -value of the specific heat has been found by Gratz et al. (1995) and is shown in the inset of fig. 109. As has been shown by Kadowaki and Woods (1986) there exists an important relation between A (the prefactor in  $\rho = AT^2$ ) and the coefficient of the electronic specific heat  $\gamma$  for all strongly correlated electron systems. As such a Kadowaki–Woods plot (fig. 110) shows, the positions of the three RCo₂ spin-fluctuation systems fall in the range where many of the other known spin-fluctuation systems, such as Sc₃In, YMn₂ (under pressure in the paramagnetic state) UPt₂ or UAl₂, lie.

It follows from these data that spin fluctuations significantly influence transport phenomena. The question of whether these kinds of excitations (such as spin fluctuations) can be observed in an experiment depends on their characteristic time scale and the time window of the experiment used. An estimation of the characteristic time window of the transport phenomena gives about  $10^{-14}$  s, which is of the same order of magnitude as the time scale of spin fluctuations in the d-electron subsystem.

#### 6.2. Compounds with magnetic ground state

#### 6.2.1. *Sc*₃*In*

Sc₃In crystallises in the Ni₃Sn-type structure (SG:  $P6_3/mmc$ ) and has been classified as a weak ferromagnetic material. The onset of long-range ferromagnetic order as reported in the literature is between 5.5 K and 6 K depending on the stoichiometry of the sample (see Ikeda and Gschneidner 1981). The itinerant character of a ferromagnetic compound can best be seen from a so-called Rhodes–Wohlfarth plot (Rhodes and Wohlfarth 1963, Wohlfarth 1978) where  $p_s$  is the saturation moment per magnetic atom and  $p_c$  the effective moment per magnetic atom deduced from the Curie constant. Figure 111 shows the location of Sc₃In within a Rhodes–Wohlfarth plot. The  $p_c/p_s$  ratio for Sc₃In is 6.1 (Matthias et al. 1961), which is remarkably beyond the local moment limit of  $p_c/p_s = 1$ for a strongly localised magnetically ordered material such as, e.g., Gd. In the local



Fig. 111.  $p_C/p_S$  vs.  $T_C$ , a Rhodes–Wohlfarth plot;  $p_S$  is the saturation moment per magnetic atom and  $p_C$  is the corresponding effective moment deduced from the Curie constant (Wohlfarth 1978).



Fig. 112. The temperature dependence of the electrical resistivity of  $Sc_3In$  in different external magnetic fields. Inset: the  $T^2$  dependence of the resistivity under the influence of the magnetic fields (Ikeda et al. 1984).

moment limit  $p_c/p_s = 1$ , and in the opposite weakly ferromagnetic limit theory predicts the divergence of this ratio as  $p_s \rightarrow 0$  or  $T_C \rightarrow 0$ , since the Curie constant in this case is independent of  $p_s$  or  $T_C$ .

The effect of spin fluctuations in ferromagnetic and nearly ferromagnetic metals has been the subject of considerable interest for a long time. First Moriva and Kawabata (1973a,b) have developed a theory which considers the effect of spin fluctuations in a selfconsistent way, thus taking account of the interaction among the spin-fluctuation modes. For the description of the magnetic properties of Sc₃In the concept of spin fluctuations is used. Ikeda and Gschneidner (1981) performed measurements of the specific heat and resistivity (Ikeda et al. 1984) in external fields with the aim to show that in materials with large spin-fluctuation enhancement, it is possible that a field of 10 T is sufficient to produce a measurable change in the magnetic specific heat and the low-temperature resistivity behaviour. Some of these results are given in the following figures. Figure 112 shows the temperature dependence of the electrical resistivity in different magnetic fields. The zero-field measurement clearly shows a kink in  $\rho(T)$  indicating the Curie temperature at about 6 K. The inset shows a  $T^2$  plot of the electrical resistivity at 0 T, 1 T, 2.5 T, 5 T and 7.5 T. As can be seen there is a  $T^2$  dependence up to about 4 K. The prefactor A in the  $\rho = AT^2$  relation strongly decreases with increasing field and becomes constant roughly above 5 T. The strong decrease of A with the magnetic field has been referred to as quenching of spin fluctuations. It should be noted however, that one always observes a negative magnetoresistance  $\Delta \rho / \rho_0 \equiv [\rho(B) - \rho(B = 0)] / \rho(B = 0)$  in ferromagnets around  $T_{\rm C}$  with a minimum in  $\Delta \rho / \rho_0$  vs. T at  $T_{\rm C}$  (Fournier and Gratz 1993). The minimum at  $T_{\rm C}$  in  $\Delta \rho / \rho_0$  vs. T is more pronounced the lower the ferromagnetic transition takes place. If this is taken into account the question arises whether this experiment can be considered as a test for the suppression of spin fluctuations in Sc₃In.



Fig. 113. The temperature dependence of the magnetic contribution to the specific heat  $c_m$ , in different magnetic fields (Ikeda and Gschneidner 1981).

Specific-heat experiments in magnetic fields performed by Ikeda and Gschneidner (1981) are presented in fig. 113, showing the magnetic contribution to the specific heat determined from the analysis of the experimental data by  $c_{\rm m} = c - \gamma T - \beta T^3$ . As can be seen from this figure,  $c_{\rm m}$  becomes smaller with increasing magnetic field, and in fields of about 10 T the height of its peak around  $T_{\rm C}$  is only about  $\frac{1}{4}$  of the zero-field value. Moreover, another peak around 8–9 K is found to be more pronounced at 5.4 T than in the highest field of 10 T. This new peak is thought to be due to the induced magnetisation of Sc₃In by the magnetic field.

### 6.2.2. ScFe₂ and related compounds

Among the RFe₂ series only ScFe₂ crystallises in a hexagonal Laves phase (MgZn₂ type structure) whereas all the remaining compounds have the cubic Laves phase (MgCu₂ type structure). All these RFe₂ Laves phases (ScFe₂ included) form ferromagnets with the nonmagnetic lanthanides and co-linear ferromagnets with the light lanthanides, or a ferrimagnetic structure with the heavy lanthanides with comparatively high Curie temperatures (>500 K). The high T_C values are primarily caused by the strong Fe-Fe exchange interaction. The ferromagnetic transition temperature of a ScFe₂ sample with the exact 1:2 stoichiometry is close to 540 K (see below). The magnetic moments per Fe atom vary roughly from  $1.4\mu_B$  in case of Sc, Y and Lu to  $1.8\mu_B$  for the compounds with the magnetic lanthanides as partner elements, thus proving that the Fe sublattice does not reach the saturated state in ScFe2, YFe2 and LuFe2 (Rhyne 1987, Franse and Radwanski 1993). Band-structure calculations in the paramagnetic state of ScFe₂ by Ishida and Asano (1985) revealed that there is a peak in the density of states (DOS) due to the 3d bands of iron at the Fermi level on both Fe sites (2a and 6h). However, there is a small difference found in the DOS between Fe(2a) and Fe(6h) revealing different magnetic moments of  $1.4\mu_{\rm B}/{\rm Fe}(2a)$  and  $1.46\mu_{\rm B}/{\rm Fe}(6h)$ . This bandstructure calculation also reveals an induced magnetic moment on the Sc sites of  $0.27\mu_{\rm B}/{\rm Sc}$ with the direction opposite to the moments on the Fe sites. However, these induced Sc-moments have not yet been observed experimentally. The calculated value of the

magnetic moments per formula unit is within the range of experimental values obtained by magnetic measurements;  $2.9\mu_B/ScFe_2$  (Sankar and Wallace 1976),  $2.23\mu_B/ScFe_{1.96}$  and  $2.75\mu_{\rm B}/{\rm ScFe}_{2.05}$  (Grössinger et al. 1980). All these experimental values were obtained neglecting the existence of an induced Sc-moment as predicted by the theory. The slightly different values for the magnetic moments on the Fe(2a) and Fe(6h) sites are confirmed by differences in the hyperfine field observed in the Mössbauer effect which are 170 kOe for Fe(2a) sites and 176 kOe for Fe(6h) (Grössinger et al. (1980)). These authors investigated the influence of the stoichiometry on the bulk magnetisation and the hyperfine interaction by studying a second sample with a different Fe content:  $ScFe_{2.05}$ . They showed that the magnetocrystalline anisotropy differs considerably in magnitude depending on the composition. The average hyperfine field at 4.2 K increases from 176 kOe for the sample  $ScFe_{1.96}$  up to 201 kOe in the sample  $ScFe_{2.05}$ . The conclusion drawn by Grössinger et al. (1980) is that the magnetic behavior of ScFe₂ is obviously very sensitive to the average  $d_{\text{Fe-Fe}}$  value. These arguments are further supported by the study of a hydrogenised ScFe₂ sample (ScFe₂H₂) (Smit and Buschow 1980) where the lattice constants are a = 5.279 Å, c = 8.507 Å (to be compared with a = 4.977 Å, c = 8.146 Å for ScFe₂). By means of magnetic measurements an increase of the moment per Fe from  $1.4\mu_{\rm B}$  in ScFe₂ to  $2.2\mu_{\rm B}$  in ScFe₂H₂ has been found. Using ⁵⁷Fe Mössbauer spectroscopy an increase of the hyperfine splitting by about 60% was observed, whereas, on the other hand, only a rather small change in the isomer shift was observed in  $ScFe_2H_2$ . Arguments are given in Smit and Buschow (1980) that it is difficult to explain the moment change in terms of a single 3d band picture and charge-transfer effect.

The dependence of the Curie temperature on the composition in ScFe₂ has been studied by the authors (Kotur et al. 1998). This investigation showed that a sample with the composition 1:1.92 exhibits an increase of the Curie temperature by about 100 K compared to the sample with the 1:2 stoichiometry with  $T_C = 540$  K. This sensitivity of the magnetic properties to the composition has been suggested to be due to the chemical pressure the Fe atoms experience in this Sc-based hexagonal Laves phase. As noted above the ScFe₂ compound does not crystallize in the cubic MgCu₂-type structure, which is obviously due to the much smaller atomic radius of Sc. Furthermore, a change in the structural surroundings also influences the magnetic properties. Xia et al. (1996) have shown that a partial chemical disorder produced by ball milling leads to an increase of the Fe moment. Finally, amorphisation due to a long-lasting ball milling reduces the Curie temperature from 540 K down to 250 K (Xia et al. 1996).

For purpose of comparison the magnetic susceptibilities (or the magnetisations) of  $ScNi_2$ ,  $ScCo_2$  and  $ScFe_2$ , respectively, are shown in fig. 114. This picture clearly shows that among the  $ScM_2$  (M=Ni, Co, Fe) there is one weak paramagnet (ScNi₂), one enhanced paramagnet (ScCo₂, see also sect. 6.1.3) and the ferromagnetic compound  $ScFe_2$ , with a long-range ferromagnetic order, caused by the 3d exchange interaction.

Another comparison has been made in fig. 115, where the temperature dependence of the electrical resistivity of these three compounds is depicted. It is interesting to note that although ScCo₂ does not show a long-range magnetic order, there is a huge magnetic contribution to the total resistivity,  $\rho_{mag}(T) = \rho_{ges} - \rho_0 - \rho_{ph}$ , which is of the same



Fig. 114. The temperature dependence of the dc susceptibility of  $ScNi_2$  and  $ScCo_2$  (Kotur et al. 1998), and the magnetization of  $ScFe_2$  (in a field of 4.5 T) (Sankar and Wallace 1976).

Fig. 115. A comparison of the electrical resistivity of ScFe₂, ScNi₂ (Kotur et al. 1998) and ScCo₂ (Gratz 1997). Inset: the low-temperature  $T^2$  dependence of the three Febased ferromagnetic Laves phases (Kotur et al. 1998).

order of magnitude (about  $100 \,\mu\Omega \,\mathrm{cm}$ ) as in the ferromagnetic ScFe₂ compound, with a paramagnetic moment of the order of  $1.4\mu_{\rm B}/{\rm Fe}$  (see above). (The phonon resistivity  $\rho_{\rm ph}$ for all three compounds is roughly given by the  $\rho(T)$  data of ScNi₂, the residual resistivity  $\rho_0$  has been subtracted from the data in this presentation). This picture underlines the statement in sect. 6.1.3 that the electrical resistivity (transport phenomena in general) is very sensitive to scattering processes of the conduction electrons with spin fluctuations. In sect. 6.1.3 it has been shown that there is a  $T^2$  dependence of  $\rho_{\rm mag}(T)$  at low temperatures due to the spin-fluctuation scattering of the conduction electrons. Note that there is also a  $\rho(T)=AT^2$  dependence in ScFe₂, caused by the spin-wave (magnon) scattering of the conduction electrons (Gratz et al. 1989). However A for ScFe₂ is roughly one order of magnitude smaller than the A-values found in the RCo₂ spin-fluctuation systems. The inset in fig. 115 shows the  $T^2$  dependence of the resistivity for the three ferromagnetic RFe₂ (R = Sc, Y, Lu) compounds.

6.2.2.1.  $Sc(M_{1-x}Si_x)_2$  (M = Fe, Co, Ni). As discussed in sect. 3.6, the substitution of Fe by Si in ScFe₂ reveals a change of the structure from the hexagonal MgZn₂-type structure (ScFe₂) to the cubic MgCu₂ type structure, if about 6 at% of Fe are substituted



Fig. 116. Arrott plots of the Sc(Fe_{0.75}Si_{0.25})₂ compound. Inset: the low-temperature magnetisation in an M vs.  $T^{3/2}$  representation. The spin wave stiffness thus obtained is 66 meV Å (Kotur et al. 1998).

by Si. The MgZn₂-type structure reappears around a substitution of 16 at% Fe by Si (Gladyshevsky et al. 1977). The influence of the Si substitution on the physical properties in the series of the  $Sc(Fe_{1-x}Si_x)_2$  has been investigated by Kotur et al. (1998). In this investigation the Co- and Ni-based  $Sc(M_{1-x}Si_x)_2$  compounds are included. Starting with ScFe₂, two other samples,  $Sc(Fe_{0.94}Si_{0.06})_2$  with the MgCu₂-type structure and  $Sc(Fe_{0.75}Si_{0.25})_2$  with the MgZn₂-type structure have been investigated in order to study the change of the magnetic properties due to the Fe substitution. For this study a number of measuring methods, namely magnetisation, specific heat, thermal expansion, resistivity and Mössbauer spectroscopy have been utilized by Kotur et al. (1998). The cubic sample  $Sc(Fe_{0.94}Si_{0.06})_2$  shows a small decrease of  $T_C$  whereas all the other physical properties are similar to those of ScFe2. These investigations however revealed that there is a dramatic lowering of the onset of the magnetic order in the sample  $Sc(Fe_{0.75}Si_{0.25})_2$  ( $T_C = 145$  K) in combination with a decrease of the averaged Fe moment (0.67 $\mu_{\rm B}/{\rm Fe}$ ). The  $M^2$  vs. B/Mplot (Arrott plot) of the sample Sc(Fe_{0.75}Si_{0.25})₂ is given in fig. 116. The curvature of the  $M^2$  vs. B/M curves in the ordered state was thought to be due to the local character of the Fe moments in these compound. The inset in fig. 116 shows the low-temperature magnetisation in a M vs.  $T^{3/2}$  representation. From this an estimation of the spin-wave stiffness constant has been obtained. The value for  $Sc(Fe_{0.75}Si_{0.25})_2$  is 66 meVÅ³, which is distinctly reduced when compared to  $ScFe_2$  (465 meV Å³).

The resistivity behaviour for the sample with  $Sc(Fe_{0.75}Si_{0.25})_2$  is remarkable, since there is a negative slope in the temperature range from 4 K up to room temperature. The normalised resistivity curves  $(\rho(T)/\rho(295 \text{ K}) \text{ vs. } T)$  for the  $Sc(Fe_{0.75}Si_{0.25})_2$  sample, together with the resistivity of the isostructural Co- and Ni-based compounds  $Sc(Co_{0.75}Si_{0.25})_2$ , and  $Sc(Ni_{0.75}Si_{0.25})_2$  are given in fig. 117. The residual resistivity for these compounds is of the order of  $300-400 \,\mu\Omega$  cm. This has been interpreted as a sign for a charge transfer from the silicon p bands to the 3d band of Fe, Co or Ni and the begin of a gap-opening.

There is an increase of the electronic specific heat coefficient  $\gamma$  from  $\gamma(\text{ScFe}_2) = 10 \text{ mJ mol}^{-1} \text{ K}^{-2}$  to  $\gamma(\text{Sc}(\text{Fe}_{0.75}\text{Si}_{0.25})_2) = 38 \text{ mJ mol}^{-1} \text{ K}^{-2}$ . Sc $(\text{Fe}_{0.75}\text{Si}_{0.25})_2$  has a small thermal expansion coefficient ( $\alpha = 12 \times 10^{-6} \text{ K}^{-1}$ ) without any anomaly at  $T_{\text{C}} = 145 \text{ K}$ .



Fig. 117. The normalised resistivity  $\rho(T)/\rho(295 \text{ K})$  for Sc(Fe_{0.75}Si_{0.25})₂, Sc(Co_{0.75}Si_{0.25})₂, and Sc(Ni_{0.75}Si_{0.25})₂ (Kotur et al. 1998).

These investigations also revealed that an annealing procedure as well as a change of the 1:2 stoichiometry within the corresponding homogeneity range changes the physical properties considerably.

6.2.2.2.  $(Sc_{1-x}Ti_x)Fe_2$ . ScFe₂ is a ferromagnet (as shown above) whereas TiFe₂ shows antiferromagnetism with  $T_{\rm N} \approx 270 \, {\rm K}$  (Nakamichi 1968). Both compounds crystallise in the hexagonal MgZn₂ Laves phase structure. Thus in the pseudobinary system  $(Sc_{1-x}Ti_{x})Fe_{2}$  the magnetic properties change from ferromagnetism to antiferromagnetism as the Sc: Ti ratio changes. The system shows the  $MgZn_2$  type structure over the whole concentration range. Along this pseudobinary the Curie temperature on the Sc-rich side (up to x = 0.2) is nearly constant with a saturation magnetisation for ScFe_{1.95} of about 81 emu/g (Nishihara and Yamaguchi 1986). However, with increasing Ti concentration the saturation magnetisation increases up to about 94 emu/g for x = 0.65 and a decreasing saturation field. This tendency however changes abruptly at about x = 0.7, the saturation magnetisation for this sample is about half (48 emu/g) of that for the sample with x = 0.65. A small discontinuity at 150 K in the temperature dependence of the magnetisation for x=0.7 has been interpreted as the onset of antiferromagnetism in the low-temperature region causing the decrease of the saturation magnetisation (Nishihara and Yamaguchi 1985, 1986). Interestingly, in the temperature dependence of the magnetisation for x = 0.65 to x = 0.4 there is a step-like increase of the ferromagnetic magnetisation at the corresponding transition temperature (for x = 0.65 at 80 K) due to a temperature-induced increase of the ferromagnetic Fe moments. The saturation magnetisation at 0 K is  $1.3 \mu_{\rm B}/{\rm Fe}$ and about  $0.9\mu_{\rm B}/{\rm Fe}$  just above the transition temperature for the sample x = 0.65. This difference in the saturation moment between both ferromagnetic states become smaller as the Ti content is further decreased. No such a transition has been found for  $0 \le x \le 0.2$ .

Investigations of the paramagnetic susceptibility exhibit that for all the samples the Curie–Weiss law is fulfilled however the Curie constants are larger for the sample with x > 0.75 than for that with x < 0.5. Interestingly the  $\chi^{-1}$  vs. *T* plots for  $0.5 \le x \le 0.75$  show kinks at temperatures about 100 K higher than the corresponding Curie temperatures. The

change in the effective moment, deduced from the Curie constant, is  $2.5\mu_{\rm B}/{\rm Fe}$  above the kink in  $\chi^{-1}$  vs. T and about  $1.6\mu_{\rm B}/{\rm Fe}$  below the kink.

It seems that this finding is a confirmation that the change in the chemical pressure the Fe atoms experience within this pseudobinary caused by the small atomic diameter (of both Sc and Ti) destabilises the magnetic moments of the Fe atoms. This is, for example, quite in contrast to  $YFe_2$  with stable moments on the iron sites.

#### 6.2.3. Sc substitution in $YMn_2$

Rare-earth Laves phases with 3d transition metals as a partner element are interesting mainly because of the great variety of magnetic phenomena observed in this family of intermetallics. The intercorrelation between the two types of Laves phases C15 (cubic) and C14 (hexagonal) is similar to that between the fcc and hcp, i.e., a different order of packing of atomic layers. Therefore, the coordination number is the same for both structures. One of the characteristics of this structure is that the nearest neighbour of a transition-metal atom is also a transition-metal atom. The atomic distances between the transition metals in RM₂ is similar to that in the pure 3d metals. Comparing the density of states of the elementary "heavy" 3d elements (Mn, Fe, Co, Ni) shows that the 3d density of states is similar to that of the Laves phases RMn₂, RFe₂, RCo₂ and RNi₂. However within one such a series the position of the Fermi level can be shifted by selecting RE elements with different atomic diameter. This is why Sc with its small atomic size is frequently used as an alloying element.

In the following a well-known example, Y(Sc)Mn₂, will be discussed. In a number of investigations it has been shown that the magnetic state of Mn in these Laves phases depends sensitively on the Mn-Mn distance  $(d_{Mn-Mn})$  (Shiga 1988). Above a critical value of  $d_{Mn-Mn} = 2.7$  Å there exist spontaneous Mn moments which in general are antiferromagnetically ordered at low enough temperatures. Below this critical  $d_{Mn-Mn}$ value the spontaneous Mn moments are zero, however, induced Mn moments can appear in RMn₂ compounds with magnetic rare-earth elements as partner elements (for a review see Hauser et al. 1994). The sensitivity of the magnetic ground state to  $d_{Mn-Mn}$  is why in  $YMn_2$  a relatively small pressure of about 3 kbar is enough to suppress the antiferromagnetic order (Oomi et al. 1987). However, what is interesting for the subject under consideration, is that a substitution of a small amount of Sc in YMn₂ causes also a nonmagnetic ground state, due to the negative chemical pressure. In the  $\chi$  vs. T curves of the pseudobinary  $(Y_{1-x}Sc_x)Mn_2$  system the discontinuity at  $T_N$  shifts below 4.2 K for x > 0.02, indicating the collapse of the antiferromagnetic state (Nakamura et al. 1988). Another indication for the suppression of the antiferromagnetic state within this pseudobinary system is the vanishing zero-field NMR spectrum with increasing Sc concentration (Yoshimura et al. 1987). However the collapse of the antiferromagnetic order in  $(Y_{1-x}Sc_x)Mn_2$  can most clearly be seen in the temperature dependence of the lattice parameter within this pseudobinary system. These measurements are given in fig. 118 (Shiga 1988). The sharp decrease of the lattice constant at  $T_N$  is due to the partial collapse of the Mn moments from  $2.7\mu_{\rm B}/{\rm Mn}$  (estimated from neutron diffraction



Fig. 118. The temperature dependence of the cubic lattice parameters of  $(Y_{1-x}Sc_x)Mn_2$ . The step-like increase of a(T) indicates the onset of long-range antiferromagnetic order in YMn₂. This transition is of first-order type with a huge hysteresis (the arrows indicate the measurements on heating and cooling) (Shiga 1988).

experiments, Nakamura et al. 1989) to about  $1.7\mu_{\rm B}/{\rm Mn}$  just above  $T_{\rm N}$ . The huge hysteresis is an indication that the magnetic transition is of first-order type. Interestingly the very large thermal expansion coefficient  $\alpha$  measured in pure YMn₂ in the paramagnetic temperature range ( $\alpha = 50 \times 10^{-6} {\rm K}^{-1}$ ) is still observable in the compounds with the Sc substitution. This large  $\alpha$ -value has been attributed to the existence of strong spin fluctuations in YMn₂ by Shiga (1988). Recently it has been proposed that the large coefficient  $\alpha$  observed in nearly all the Mn intermetallics in their paramagnetic state (e.g. in YMn₂, YMn₁₂, Y₆Mn₂₃ and also in the Mn metal) might be due to different valence states of the Mn atoms. The assumption is made that this multi-valence state changes as a function of temperature, pressure or composition (Gratz et al. 1997).

#### 6.3. Compounds with superconducting ground state

#### 6.3.1. $Sc_{1-x}M_x$ alloys (M = Co, Rh, Ir, Pd, Pt)

The appearance of superconductivity in Sc-based binary alloys with Co, Rh, Ir, Pd and Pt has been investigated by Geballe et al. (1965). Superconductivity with transition temperatures above 0.35 K (the lowest available temperature of the experiments in this investigation) has been found in the  $Sc_xCo_{1-x}$  system in the range x=0.28-0.32. It was however reported by Geballe et al. (1965) that it was not possible to isolate the superconducting phase. Indications for superconductivity occur at 0.8 K in a Sc–Rh alloy in the Sc-rich concentration region, however as it was expressed there, only about  $\frac{1}{4}$  of the sample was superconducting as deduced from the smaller signal obtained for a powder. In the Sc–Ir system only one superconducting phase has been identified, namely that with the MgCu₂-type structure ScIr₂ which has a transition temperature of 2.07 K according to Geballe et al. (1965). The maximum transition temperature for the C15-type alloys is 2.46 K which occurs in ScIr_{2.5}, however after powdering the sample two transitions exist, one at 2.13 K (which is that of the C15 type) and one that begins at 0.42 K. The lower temperature has been ascribed to the transition of a nonstoichiometric ScIr₂ alloy. According to Geballe et al. (1965) there is no superconducting phase in the Sc–Pd and

Sc-Pt system. This has been ascribed to the lack of favourable intermediate phases in these systems.

Alloys of Y and Lu with Co, Rh, Ir, Pd and Pt have been studied and compared. This comparison shows that in the alloys with Sc the smallest number of superconducting compounds exist. Interestingly, in none of these series based on Sc, Y or Lu superconductivity has been observed in compounds with Pd.

## 6.3.2. $Sc_5M_4Si_{10}$ (M = Co, Rh, Ir) and $R_2Fe_3Si_5$ (R = Sc, Y, Lu)

Among the Sc-containing superconductors the most interesting are the superconducting ternary iron and cobalt silicides. The discovery of  $Sc_5Co_4Si_{10}$  with a superconducting transition temperature of  $T_{\rm S}$  = 4.9 K demonstrated that relatively high transition temperatures may be found among compounds containing 3d transition elements as intrinsic constituents (Braun and Segre 1980). In this paper a class of ternary compounds with the general formula  $R_5M_4X_{10}$ , (where R=Sc or Y, M=Co, Rh, Ir, and X=Si or Ge) has been described the first time. These R₅M₄X₁₀ compounds crystallise in a primitive tetragonal lattice with SG P4/mbm. The superconducting transition temperatures of the Sc-containing samples are: 4.9K for Sc₅Co₄Si₁₀, 8.5K for Sc₅Rh₄Si₁₀, and 8.4K for  $Sc_5Ir_4Si_{10}$ . The occurrence of superconductivity at temperatures up to 8.4 K in the  $Sc_5M_4Si_{10}$  phases is remarkable since elements like Sc and Si become superconducting only under pressure. Ir is superconducting below 0.66K and Rh and Co are not superconducting at all. The comparatively high  $T_{\rm S}$  of Sc₅Co₄Si₁₀ indicates that the magnetic character of the Co atoms is either lost in these phases or does not interfere significantly with the BCS pairing. This behaviour is intriguing in view of the existence of "isolated" transition-metal atoms in these compounds.

Later it has been shown that there are other ternary superconducting compounds containing iron as the transition metal (Vining et al. 1983). The ternary iron silicides  $R_2Fe_3Si_5$  (R = Lu, Sc, Y) were first reported to become superconducting by Braun (1980). The crystal structure of  $Sc_2Fe_3Si_5$  which belongs to the SG P4/mnc has been solved by Bodak et al. (1977). The superconducting transition temperatures for the three compounds are not very sharp and are given by Braun (1980) as:  $T_{\rm S} = 4.52 - 4.25 \,\text{K}$  for Sc₂Fe₃Si₅,  $T_{\rm S} = 2.4 - 2.0 \,\text{K}$  for Y₂Fe₃Si₅, and  $T_{\rm S} = 6.1 - 5.8 \,\text{K}$  for Lu₂Fe₃Si₅. ⁵⁷Fe Mössbauer effect measurements of these Fe-based series in magnetic fields show quadrupole-splitted spectra with small positive values of the isomer shift, indicating the absence of magnetic moments at the iron sites (Braun et al. 1981). An estimation of the upper limit of the magnetic moments on the two iron sites at 4.2 K with a magnetic field (5.6 T) and without a magnetic field has been given in Cashion et al. (1980, 1981). These measurements revealed  $\mu_{\text{Fe}} \leqslant 0.03 \mu_{\text{B}}$ . To explain the nonmagnetic ground state of Fe in these compounds two models have been discussed earlier in the literature. One model is based on the assumption that a charge transfer from Si to Fe takes place in these compounds. The other concept assumes an influence of the crystal field on the 3d orbital. The charge transfer model requires a rather unrealistic large charge transfer from the d⁶ configuration of Fe into a d¹⁰ configuration. However, the very small Fe-Si interatomic distances



Fig. 119. The temperature variation of the specific heat of Lu₂Fe₃Si₅ in a c/T vs.  $T^2$  presentation. Inset: the coefficient of the linear term in the heat capacity for the normal state ( $\gamma_n$ ) and the superconducting state ( $\gamma_s$ ) in mJ mol⁻¹ K⁻² (Vining et al. 1983).

Fig. 120. The temperature variation of the specific heat of  $Sc_2Fe_3Si_5$  in a c/T vs.  $T^2$  presentation. Inset: the coefficient of the linear term in the heat capacity for the normal state ( $\gamma_n$ ) and the superconducting state ( $\gamma_s$ ) in mJ mol⁻¹ K⁻² (Vining et al. 1983).

in this compound (see table 2 in Braun 1981) might support this explanation. The assumption that the crystal field in a transition metal compound is strong enough to cause a zero Fe moment seems questionably too. We feel that as yet the question of why Fe is nonmagnetic in such systems is unsolved. The low-temperature heat capacity measurements performed on the three  $R_2Fe_3Si_5$  (R=Lu, Sc, Y) compounds by Vining et al. (1983) revealed several anomalous properties in their superconducting state. Most remarkable in these heat-capacity results are the large linear term in the superconducting state and a reduced normalised jump in the specific heat at  $T_{\rm S}$ . These measurements are shown in figs. 119, 120 and 121 in c/T vs.  $T^2$  representations. The respective c/T vs.  $T^2$ plots around  $T_{\rm S}$  are shown in the insets. The superconducting transition temperatures as obtained from these specific-heat measurements are 6.3 K, 4.4 K and 1.7 K for Lu₂Fe₃Si₅,  $Sc_2Fe_3Si_5$  and  $Y_2Fe_3Si_5$ , respectively. Deviations from linearity above  $T_S$  especially in  $Lu_2Fe_3Si_5$  are apparent. A fit of these data in the temperature range from above  $T_8$  to about 18 K with  $c = \gamma_n T + \beta_n T^3 + \alpha_n T^5$  (the subscript n denotes the non-superconducting state) with a root mean square deviation of about 1% revealed that in each case the lattice contribution  $\beta_n T^3 + \alpha_n T^5$  to the total specific heat represents less than 20% of the total heat capacity at  $T_s$ . The prefactor  $\alpha_n$  is smallest in the Sc compound. The jump at  $T_s$  is



Fig. 121. The temperature variation of the specific heat of  $Y_2Fe_3Si_5$  in a c/T vs.  $T^2$  presentation. Inset: the coefficient of the linear term in the heat capacity for the normal state ( $\gamma_p$ ) in mJ mol⁻¹ K⁻² (Vining et al. 1983).

sharp for Lu₂Fe₃Si₅ and Sc₂Fe₃Si₅ whereas it is broad in Y₂Fe₃Si₅; this is ascribed to a somewhat lower quality of the latter sample. The normalised jump  $\Delta c/(\gamma_n T_s)$  in the heat capacity at  $T_s$  in Sc₂Fe₃Si₅ and Y₂Fe₃Si₅ is less than 60% of the BCS value of 1.43. Below  $T_s$  the heat capacity of Lu₂Fe₃Si₅ and Sc₂Fe₃Si₅ has been fitted to the expression  $c = \gamma_s T + \beta_s T^3$  (the subscript s denotes the superconducting state). The measured Y₂Fe₃Si₅ data do not permit an estimation of  $\gamma_s$ . An extrapolation towards lowest temperatures reveals  $\gamma_s = 13.6 \text{ mJ mol}^{-1} \text{ K}^{-2}$  for Sc₂Fe₃Si₅ and 10.1 mJ mol⁻¹ K⁻² for Lu₂Fe₃Si₅. The reduced normalised jump at  $T_s$  and the large linear  $\gamma_s$  values have been explained by Vining et al. (1983) assuming a two-band model in which one band remains in the normal state. These can be understood in terms of a topological complex Fermi surface in which pockets of electrons remain.

#### 6.3.3. $RRu_4B_4$

Within the RRu₄B₄ series of compounds the body-centred tetragonal (bct) structure occurs for all members except for La, the largest of the rare-earth elements (Johnston 1977). Similarly, within the set of primitive tetragonal  $RRh_4B_4$  compounds  $NdRh_4B_4$ , which contains the largest rare-earth ion which forms this structure, has been found to be metastable (Johnston 1977). A structural instability of the various RM₄B₄ structure classes also occurs with decreasing size of the rare-earth ions; the smallest rare-earth atom which has been reported to form any of these phases is Lu. Ku et al. (1979) reported that Sc, with a much smaller ionic radius, does form ScRu₄B₄, however it was found that this compound is metastable. Surprisingly however, ScRu₄B₄ becomes superconducting at a temperature of about 7.2 K, much higher than the  $T_{\rm S}$  of the other two superconducting members of the body-centred tetragonal RRu₄B₄ series, namely 1.8 K for LuRu₄B₄ and 1.4 K for  $YRu_4B_4$ . Since the ScRu₄B₄ sample, where the superconductivity has been found, was a multi-phase sample, a comprehensive investigation around the ScRu₄B₄ composition in the Sc-Ru-B ternary phase diagram has been undertaken. However, no single-phase ScRu₄B₄ sample could be obtained. The effect of annealing was that the superconductivity disappeared in these ternary body-centred tetragonal phases.

#### 6.3.4. $ScNi_2B_2C$

Superconductivity with relatively high transition temperatures up to 23 K has been reported in R–M–B–C systems (R = Y and M = Ni, Pd or Pt) (see e.g. Ku et al. 1994). In the Ni-based system superconductivity was first observed in the compound with R = Lu with the tetragonal LuNi₂B₂C-type structure (SG *I*4/*mmm*). Among the RNi₂B₂C the highest T_s (16.6 K) has been reported for LuNi₂B₂C followed by YNi₂B₂C with 15.6K (Nagarajan et al. 1994, Cava et al. 1994, Siegrist et al. 1994). For magnetic rare-earth compounds lower superconducting transition temperatures (due to the pairbreaking effect) have been observed. Superconductivity has been observed in ScNi₂B₂C by Ku et al. (1994), however, only in an as-cast multi-phase sample. As in the other RNi₂B₂C systems the superconducting phase in ScNi₂B₂C is found only in those phases with the tetragonal LuNi₂B₂C-type structure. Obviously because of the much smaller ionic radius of Sc³⁺ this superconducting phase is metastable in ScNi₂B₂C and vanishes (together with the superconductivity) after the sample has been annealed at 1050°C for 24 h. The superconducting transition temperature for this metastable ScNi₂B₂C compound is between 15 and 16 K, thus only slightly lower than 16.7 K for the LuNi₂B₂C compound and almost equal to 15.6 K for YNi₂B₂C, which indicates that the superconducting properties of these systems are essentially independent of the relative size of the nonmagnetic  $R^{3+}$  ions (R = Sc, Y or Lu).

# Acknowledgement

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### Appendix 1. Structure types of intermetallic compounds of scandium

Table 36 collects the structure types of intermetallic compounds of scandium.

				Stru	ucture 1	ypes	of ir	ltern	netalli	ic col	nodu	spur	of sc	andit	E			
Structure type	Pearson's	Space	Number of	Inclu	Iding			Incluc	ling in	terni	ary sy	/stem:	s Sc-l	М	Sc		Binary	Composition of ternary
	symbol	group	compounds	binary	ternary	m	AI	Ga	Ц	0	Si	Ge	Sn 51	b- 6[	X	X, M-	M' prototype	compound(s)
MgZn ₂	hP12	P63/mmc	20	9	14	I	6	3		1	3				I		24 	$ScM_{2-x}X_x$ ; $ScM_{1.5}X_{0.5}$
TiNiSi	oP12	Pnma	19	0	19	T	T	7	1	I	~	4	4 1		I	I	anti-PbCl ₂	ScMX
MnCu ₂ Al	cF16	Fm3m	18	0	18	T	5	3	9	í		۲ ا	। स		1	1	- BiF ₃	$ScM_2X$
CsCl	cP2	Pm3m	16	16	0	I	I	T			1	, I	1	5	I	I		
$Mg_6Cu_{16}Si_7$	cF116	Fm3m	15	0	15	I	4	S	1	1	5	1	1		I	I	Th ₆ Mn ₂₃	$Sc_6M_{16}X_7; Sc_6M_7X_{16}$
CaTiO ₃	cP5	Pm3m	14	0	14	7	T	1	1		1	1	1	 ,	6	I	$\gamma'Fe_4N$	ScM ₃ C; Sc ₃ XX'
ZrNiAl	6dy	$P\overline{6}2m$	14	0	14	I	I	I	i.	1	e	~	2 1	1	I	I	Fe ₂ P	ScMX
Ce ₂ Sc ₃ Si ₄	oP36	Pnma	12	0	12	I	J	T		Í	5		1		1	ł	· Sm5Ge4	$Sc_2M_3X_4; Sc_3M_{2-x}X_4$
ScCeSi	t112	I4/mmm	11	0	11	I	I	ł		I	5	. 6	1		I	1	La ₂ Sb	ScMX
Sm5 Ge4	oP36	Pnma	10	1	6	T	ł	I	1	1	5		F	-	I			$Sc_{2-4}M_{3-1}X_4$
ZrCrSi ₂	0P48	Pbam	10	0	10	I	I	T	T	1		8	1		I	I		$ScMX_2$
$MgCu_2$	cF24	Fd3m	6	5	4	1	г	1	1	1	_	-	1		1	1		$ScM_{2-x}X_x$
$AIB_2$	hP3	P6/mmm	8	÷	\$	T	T	T	· I		4		1	1	1	1		$Sc_{1-x}M_xSi_{2-x};$
Mns Si2	hP16	P6, mcm	~	9	7	I	I	I	1		5		1	I	I	1		ScaU2 - x Udx ScaU2 Siat: Scare Feares Sia
AnCh	cP4	DmJm	٢	٢	C	I	I	,	1				1		I	1		
cuont i			- 1	- •												.		
Caln ₂	hP6	P63/mmc	r	0	r-	I	I	ŝ		t	I			1	1	-		ScM ₂ - _x Ga _x ; ScCuSn; ScCuZn
Mo ₂ FeB ₂	tP10	P4/mbm	٢	0	7	I.	I	1	· I	1	Ś	1	-	t	-	I	U ₃ Si ₂	ScM ₂ Si ₂ ; Sc ₂ Ni ₂ Sn; Sc ₂ AlSi ₂
MgAgAs	cF12	$F\overline{4}3m$	7	0	٢	Ţ	Ţ	I	1		ī	1	4		I	1	$CaF_2$	ScMX
$ThMn_{12}$	t126	I4/mmm	7	-	9	I	7	Э	I	I	-	,	1	1	I	I		$ScM_{4+x}X_{8-x}$ ; $ScFe_{10}Si_2$
HfFe,Ge,	hP13	P6/mmm	9	0	9	I	I	I	1		-	4	-		I	1		$ScM_6X_6$
U4Re7Si6	cI34	lm3m	9	0	9	T	[	I	· I	T	-	5	1		I	1		$Sc_4M_7X_6$
Ho ₁₁ Ge ₁₀	t184	I4/mmm	9	17	4	I.	I	3		•	1	-	1	T	I	I		Sc9.4 - xM1.6 + xGa10; Sc6Yb5Ge10
CrB	oS8	Cmcm	5	4	1	I	Ι	I		I	, 	1	1	1	I	1		$Sc_{0.2-0.4}Sm_{0.8-0.6}Si$
																		continued on next page

Table 36 types of intermetallic commoninds of s

514

# B.Ya. KOTUR and E. GRATZ

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Structure type	Pearson's	Space	Number of	Includ	ling			nclud	ing ir	1 terna	ury sy	stems	Sc-N	1	Sc		Binar	<u>م</u>	Composition of ternary
	symbol	group	compounds	binary t _i	crnary	m	AI	Ga	ľ	0	3	je S	n 5b	- 69	-X -	V M-	-M' proto	type	compound(s)
ZrSi ₂	oS12	Cmcm	5	1	4	1	I	I	1	7	- 			1					ScM _{0,25} Si _{1.75}
$YCrB_4$	oP24	Pbam	5	0	5	5	I	I	I	, I		1	1	Ι	Ţ	1	í		ScMB ₄
$\mathrm{Zr}_4\mathrm{Co}_4\mathrm{Ge}_7$	t134	<i>I</i> 4/ <i>mmm</i>	5	0	5	I	ł	1	1		~	-	1	1	1	I			$Sc_4M_4Si_7$ ; $Sc_4M_4Ge_{7-x}$
Ti ₂ Ni	cF96	Fd3m	ŝ	ŝ	7	T	ſ	T	I	1		1		I	I	I	1		$Sc_2M_{1-x}Si_x$ (M = Co, Cu)
$Zr_2Fe_{12}P_7$	hP21	$P\overline{6}$	4	0	4	I	ſ	1	1	' 	1		4	I	T	I			$\mathrm{Sc}_{2}\mathrm{M}_{12}\mathrm{P}_{7}$
Gd ₆ Cu ₈ Ge ₈	0122	Immm	4	0	4	ł	T	1	I		~	-	1	1	T	I			$Sc_3M_4X_4$ (M = Ni, Cu)
MgCu4Sn	cF24	$F\overline{4}3m$	4	0	4	ſ	T	T	1	I		- 2	I	I	I	-	MgCu ₂		ScM ₄ X; ScNi ₄ Au
$Hf_3Ni_2Si_3$	oS32	Cmcm	4	0	4	T	1	I	I	-	-	]	1	1	I	I	,		$Sc_3M_2X_3$
Ti ₆ Ge ₅	oĬ44	Ibam	4	7	5	1	I	I	I.		_	-	1	I	I	I			ScV ₅ Si ₅ ; Sc _{1-1.8} V _{5-4.2} Ge ₅
$Sc_7Cr_{4+x}Si_{10}$	_x t184	I4/mmm	4	0	4	T	I	I	1	. 1	~			ſ	I	I	- Ho ₁₁ G	010	$\mathrm{Sc}_7\mathrm{M}_{4+x}\mathrm{X}_{10-x}$
Sc ₅₇ Rh ₁₃	cP140	$Pm\overline{3}$	4	4	0	T	I	I	I	1	1	I	1	I	I	I			
$MoSi_2$	tI6	I4/mmm	ŝ	Э	0	T	I	I	I	•		1	1	ł	Ι	3			
Ni ₂ In	իթ6	$P6_3/mmc$	Э	÷	0	1	I	Ι	Ī	I			1	I	l	I	1		
HoCoGa ₅	tP7	P4/mmm	3	0	ŝ	T	I	3	1	' I				1	I	1			ScMGa ₅ ( $M = Co$ , Ni)
ScCoC ₂	tP8	P4/mm	3	0	3	ł	I	I	ſ	÷	1	1	1	1	I	1			$ScMC_2$ (M = Fe, Co, Ni)
Ni ₃ Sn	hP8	$P6_3/mmc$	3	÷	0	I	ı	I	1	1	1	-	1	1	T	1			
CeGa2Al2	0110	I4/mmm	£	0	ŝ	I	I.	1	ſ	1	-	1	1	I	I		- BaAl4		ScM ₂ Si ₂ (M = Co, Ni, Cu)
KHg ₂	oI12	Imma	£	1	5	T	1	2	I	1	1	I	1	l	ſ		1		$ScM_2 - xGa_x$ (M = Co, Cu)
$ZrFe_4Si_2$	tP14	$P4_2/mnm$	ŝ	0	ŝ	I	I	Ι	T	1		1	2	1	I	I			$ScM_4X_2$
Sc ₃ CoC4	ol16	Immm	ŝ	0	ŝ	ł	I.	I	1	33	1	1	I .	I	1	1	I		$Sc_3MC_4$ (M = Fe, Co, Ni)
$Sc_2CoSi_2$	mS20	B2/m	3	0	ŝ	T	I	T	1	.ч Т	-		1	I	ſ	1			$Sc_2MX_2$
Sc2Re3 Si4	tP36	$P4_{1}2_{1}2$	ε	0	ŝ	I	I	1	I		-		I	I	I	I	- Zr ₅ Si4		$Sc_2M_3Si_4$ (M = V, Cr, Re)
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# SCANDIUM ALLOY SYSTEMS AND INTERMETALLICS

515

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Structure type	Pearson's	Space	Number of	Inclue	ling		I	nclud	ing in	terna	ıry sy	stems	Sc-N	1	Sc		Binary	Composition of ternary
	symbol	group	compounds 1	binary t	ernary	В	AI	Ga	ln	0	Si C	je S	n 5b	- 6b-	X-X'	M-M′	prototype	compound(s)
Sc ₅ Co ₄ Si ₁₀	tP38	P4/mbm	3	0	3	1	I	I			~			I	I	I		$Sc_5M_4Si_{10}$ (M = Co, Rh, Ir)
Al ₂ MgO ₄	cF56	Fd3m	3	0	б	ı	I	I.	· I	1			1	б	Ι	L		$Sc_2MSe_4$ (M = Mg, Mn, Cd)
$Sc_{11}Ir_4$	cF120	Fm3m	3	3	0	Ţ	Ι	I		1	,		1	I	I	I		
Ru ₃ Be ₁₇	c1160	Im3	б	-	2	I	I	7	T	1	1		1	T	ſ	I		ScCu _{3.7} Ga _{2.3} ; ScNi _{2.16} Ga _{3.64}
NiAs	hP4	$P6_3/mmc$	2	2	0	I	I	i	ŀ	1	1	1	1	1	I	I		
CaCu ₅	hP6	P6/mmm	7	7	0	ı	ŧ	Ţ		1	ı t		1	I	Ι	I		
MoNi ₄	t110	I4/m	2	2	0	ī	T	ł	T	I	'			Ι	ł	I		
Ho ₂ CoGa ₈	tP11	P4/mmm	2	0	2	ī	Ι	2		1		,	1	Ι	I	1		$Sc_2MGa_8 (M = Co, Ni)$
$\alpha ThSi_2$	tl16	$I4_1/amd$	2	0	7	I.	I	ι	I		5	ı ı	1	I	I	I		$Sc_{0.3}M_{0.7}Si_2$ (M = Sm, Dv)
AlLiSi	cF12	$F\overline{4}3m$	2	0	7	I	l	T	I	1	1		-	I	I	I		ScMSn ( $M = Pt$ , Au)
YbMo ₂ Al4	ti 14	I4/mmm	2	0	2	I	T	7	i.				- 1	T	T	I		$ScM_2Ga_4$ (M = Ti, V)
TiNi ₃	hP16	P63/mmc	6	0	0	I.	7	I.	i I	1				I	I	1		$\operatorname{Sc}_{1-x}M_x\operatorname{Al}_3(M=Y, Tb)$
$Cr_3C_2$	oP20	Pnma	2	6	0	I	I	I		1		1	ſ	T	ſ	I		
$Sb_2S_3$	oP20	Pnma	7	2	0	I	ī	l	T	1	1			T	T	I		
$Sc_2Ru_5B_4$	mP22	P2/m	2	0	7	7	T	Ţ	1	1	1		1	I	I	I		$Sc_2M_5B_4$ (M = Ru, Os)
$MgNi_2$	hP24	$P6_3/mmc$	2	-	1	1	1	ſ	ſ	i			ì	Ι	T	I		ScCu _{0.6} Al _{1.4}
Sc ₅ Ni _{1 - x} Ga _{1 -}	x hP28	$P6_{3}/mmc$	7	0	2	I.	I	5	I	1	1	1	I	Ι	1	I		$Sc_5M_{1-x}Ga_{1-x}$ (M = Co, Ni)
$\beta Y b_5 S b_3$	oP32	Pnma	2	2	0	I	T	I	ſ	-	'		-	1	ſ	I		
ZrFe ₆ Ge ₄	hR33	$R\overline{3}m$	2	0	7	I	I	I		1		-	1	T	I	I		$ScM_6Ge_4$ (M = Mn, Fe)
$YCo_5P_3$	oP36	Pnma	2	0	7	I	I	t	r				- 2	T	ł	I		$ScM_5P_3$ (M = Fe, Co)
TiFeSi	ol36	Ima2	7	0	5	f	E	2	I		1		ł	t	I	I		$ScM_{0.35}Ga_{1.65}$ (M = Co, Ni)
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516

## B.Ya. KOTUR and E. GRATZ

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Structure type	Pearson's	Space	Number of	Includ	ing		Ц	Icludi	ng in 1	ternar	y syst	ems S	sc-M-	ŝ	 		Binary	Composition of ternary
	symbol	group	compounds [	oinary te	ernary	в	AI C	ja I		Si	Ge	$\mathbf{Sn}$	5b-	- <del>6</del> 9-	XX	M-M'	prototype	compound(s)
Sc ₃ Ni ₁₁ Si ₄	hP36	P63/mmc	2	0	2	I			   .		-	T	I	T	1	Т		$Sc_3Ni_{11}X_4$ (X = Si, Ge)
Sc ₃ Mn ₂ Ga ₆	oP44	Pnma	2	0	2	I	1	0	ł	I	T	T	I	I	I	ł		$Sc_3M_2Ga_6$ (M = Mn, Fe)
Nb2Cr4Si5	oI44	Ibam	2	0	7	I	1	1		1	1	T	Ι	I	t		li ₆ Ge ₅	$Sc_2Cr_4X_5$ (X = Si, Ge)
$ m Y_2Co_3Ga_9$	oS56	Cmcm	2	0	2	I	_		1	Ι	I	I	I	1	I	i		$Sc_2Co_3X_9$ (X = Al, Ga)
αMn	cI58	$I\overline{4}3m$	2	2	0	t	'		1	1	Ι	T	I	I	I	I		
$ScRh_3Si_7$	hR66	$R\overline{3}c$	2	0	7	I		1	1	7	I	Т	1	I	I	I		$ScM_3Si_7$ (M = Rh, Ir)
ScCo _{1.2} Ga _{1.8}	tP80	P4mm	2	0	2	i I		- -	1	T	T	T	ſ	4	I	I		$ScM_{1.2}Ga_{1.8}$ (M = Co,
$W_2Cr_{21}C_6$	cF116	Fm3m	7	0	7	7	, I	1	I	I	I	T	1	I	I	I	Cr23 C6	Sc2C021B6; Sc2-LAVi-1:0B6
$\mathrm{Sc}_6\mathrm{Ni}_{18}\mathrm{Si}_{11}$	oI140	Immm	2	0	7			1	t	1	-	I	T	I	I	Ţ		$Sc_6Ni_{18}X_{11}$ (X = Si, Ge)
Sc _{8.5} Mn _{1.2} Ga	oI142	Immm	7	0	2	· I			1	ſ	1	I	1	T	ŀ	J		Sc _{8.5} M _{1.2} Ga (M = Mn, Fe)
$Mg_{44}Rh_7$	cF408	$F\overline{4}3m$	2	2	0	· I			1	I	ł	1	1	I	I	I		
AuCu	tP4	P4/mmm	1	1	0				I	1	T	T	I	ŀ	T	I		
γCuTi	tP4	P4/nmm	1	0	1	· ·		1	I	I	I	I	1	T	I	-		ScHf4Ir ₅
ErCuS ₂	hP5	$P\overline{3}$	1	0	-	· 1	1	1	ł	Ι	Ι	I	I	-	I	I		Sc _{1-0.67} Cu ₁₋₂ Se ₂
Cu ₂ Sb	tP6	P4/nmm	1	1	0				T	ł	Т	1	T	T	I	I		
ScAuSi	hP6	$P\overline{6}m2$	1	0	1	1	1	1	1	1	Ι	T	ι	ł	I	1	$CaIn_2$	ScAuSi
$CeCo_3B_2$	hP6	P6/mmm	1	0	1	ľ	1		I	I	I	T	I	I	1	-	CaCu ₅	$ScCo_3B_2$
$\rm YCo_6Ge_6$	hP7	P6/mmm	-	0	1	, T			1	I	I	-	ł	ł	I	I		$ScCo_6Sn_6$
TbCu ₇	hP8	P6/mmm	1	0	-		-		ſ	I	I	ł	I	I	1	I		ScC04.5 Ga4.1
ScCrC ₂ (β)	hP8	P63/mmc	1	0	1	Ì			-	I	T	T	I	ł	I	I		ScCrC ₂ (β)
$Sc_2BC_2$	tI10	I4/mmm	_	0	I	1	4	1	I	I	I	I	I	I	-	I		$Sc_2BC_2$
$Erlr_3B_2$	mS12	C2/m	1	0	1				1	I	T	I	I	ł	I		<b>JaCu</b> 5	$ScIr_3B_2$
Co ₂ Si	oP12	Рпта	I	-	0	1	1		l	I	T	I	I	T	1	I		

# SCANDIUM ALLOY SYSTEMS AND INTERMETALLICS

517 ക

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Structure type	Pearson's	Space	Number of	Includ	ing		Ir	ncludi	ng in 1	ernar	/ syste	sms S	c−M−	Sc			Binary	Composition of ternary
	symbol	group	compounds	binary te	rnary	в	AI (	3a 1	9	Si	Ge	Sn	5b-	-q9	XX/	M-M'	prototype	compound(s)
$ZrGa_2$	oS12	Сттт	1	1	0	I	· I			T	1	I	T	I	I	1		
Al ₂ Cu	t112	<i>I</i> 4/ <i>m</i> cm	1	1	0	I			1	l	T	I	1	Т	1	Т		
ScAl ₃ C ₃	hP14	$P6_3/mmc$	1	0	-	1	· 1	1	1	I	ł	T	I	T	1	I		ScAl ₃ C ₃
$\mathbf{Sc}_{1,2}\mathbf{Fe_4Si_{9,8}}$	hP15	$P6_3/mmc$	1	0	1	I	1	1	1	1	I	T	I	I	T	I		Sc _{1.2} Fe ₄ Si _{9.8}
DyAI	oP16	Pbcm	Ţ	0	-	1	, T	1		I	ł	I	I	Ι	-	I		ScGa _{0.4} Al _{0.6}
$Fe_3C$	oP16	Pnma	1	-	0	I				T	Ι	I	I	ł	T	T		
$LuRuB_2$	oP16	Pnna	1	0	-	г	1		1	1	T	T	Ι	I	ſ	-	èB	$ScOsB_2$
$ScCrC_2$ ( $\alpha$ )	oP16	Pmmn	1	0	1	I		1	-	Ι	1	Т	I	I	I	I		$ScCrC_2$ ( $\alpha$ )
$ScRhSi_2$	oP16	Pnma	1	0	I	I				Ι	Т	I	T	]	I	-	(Zn ₃	ScRhSi ₂
$ErAgSe_2$	oP16	$P2_{1}2_{1}2_{1}$	1	0	Г	I			1	I	Т	I	l	-	ł	I		ScAgSe ₂
$MgCuAl_2$	oS16	Cmcm	1	0	1	L	1	, _	1	T	I	T	1	I	Ι	1	te ₃ B	ScNiGa ₂
MoB	t116	$I4_1/amd$	1	0	-	T	ſ	-	1	I	I	T	l	I	Ę	I		Sc _{0,2-0.9} Hf _{0,8-0.1} Ga
ZrAl ₃	t116	I4/mmm	1	0	-	T	1	_		I	T	I	ł	I	I	1		$\mathrm{Sc}_{0.2}\mathrm{Hf}_{0.8}\mathrm{Ga}_3$
$Z_{\rm T} l_{\rm T_3} B_4$	hP16	$P6_{3}/m$	1	0	-	-			1	I	ł	T	T	T	I	I		Sclr ₃ B ₄
CeCo4B4	tP18	$P4_2/nmc$	1	0	1	Т	1			T	I	ł	ł	I	I	1		$ScCo_4B_4$
Ti5Ga₄	hP18	$P6_3/mcm$	1	I	0	1				T	ł	I	I	I	ŀ	I		
$HfFe_2Si_2$	oP20	Pbcm	1	0	1	T	I	1	1	-	T	ł	ł	I	I	I		$ScFe_2Si_2$
$ScB_2C_2$	oP20	Pbam	1	0	-	1	1	1	1	T	ł	I	I	Ţ	1	I		$ScB_2C_2$
ScNiSi ₃	oS20	Amm2	1	0	1	I	-	i		1	I	}	ł	I	I	1		ScNiSi ₃
$V_3As_2$	tP20	P4/m	1	1	0	I				I	I	I	I	I	ŕ	T		
$\mathrm{Th}_7\mathrm{Fe}_3$	hP20	$P6_{3}mc$	1	-	0	T				I	T	I	I	I	I	I		
Sc ₂ CrC ₃	oP24	Pbam	I	0	-	ł	1	1	-	T	ł	I	I	I	I	I		Sc ₂ CrC ₃
$ScNi_2Si_3$	tI24	I4/mmm	1	0	1	I		4		I	T	3	1	I	I	ł		$ScNi_2Si_3$
$ScSn_2$	t124	$14_1/amd$	1	1	0	1			1	I	I	T	T	I	I	T		
${\rm Ti}_7{\rm S}_{12}$	hR24	$R\overline{3}m$	1	-	0	Ι		:	1	I	T	I	T	ł	T	I		
$ScFe_6Ga_6$	o126	Immm	1	0	ŗ	I		_	1	I	Т	T	I	I	I	۲ ۱	hMn ₁₂	$ScFe_6Ga_6$
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518

# B.Ya. KOTUR and E. GRATZ

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Structure type	Pearson's	Space	Number of	Incluc	ling		ц	clud	ing in	ternat	sys yr	stems	Sc-M	:	Sc		Binary	Composition of ternary
	symbol	group	compounds	binary t	crnary	В	AI (	Ga	ц Ц	S D	0	e St	1 5b-	-6b-	X-X	′ M−M′	_ prototype	compound(s)
Eu2Pt7AlP 3	tI26	I4/mmm	1	0	0		1				I	I	I	1	1			ScCa ₂ Pt ₇ P ₃
Sc ₃ NiSi ₃	mS28	C2/m	1	0	-		1		1		I	I	I	I	I	I		Sc ₃ NiSi ₃
$Fe_2CaO_4$	oP28	Pnma	1	0	-			ŀ	1	1	1	I	Ι	-	I	I		$Sc_2EuSe_4$
$Sc_5Re_2C_7$	oS28	Cmmm	1	0	-	1	1		-	-	1	I	ł	I	ł	I		$Sc_5Re_2C_7$
${\rm Th}_3{\rm P}_4$	c128	1 <u>4</u> 3d	-	-	0		1	-	I.	1	1	I	1	I	I	I		
Sc ₃ Co	oP32	Pnma	1	-	0		1		1		1	ł	I	I	I	J		
$Tm_3Ga_5$	oP32	Pnma	1	Н	0	· I			1		1	I	1	I	I	I		
Pu ₃ Pd ₅	oS32	Cmcm	1	-	0	•	1			1	I	T	I	l	1	I		
ScCd ₇	oS32	Cmcm	1	-	0		1		ı I	1	I	1	I	I	ſ	T		
$YB_2C$	tP32	$P4_2/mbc$	1	0	1	ī	1		1	1	I	1	I	I	-	I		$ScB_2C$
W ₅ Si ₃	t132	I4/mcm	1	0	ŗ		1	, I	1	-	1	I	Ι	I	1	I		Sc _{0.4} Nb _{4.6} Sí ₃
$YCo_5P_3$	oP36	Pnma	1	0	-				1	1	I	T	-	I	I	1		ScCo ₅ P ₃
$Y_2 ReB_6$	oP36	Pbam	1	0	I	-	1	1	1	1	1	I	T	I	I	I		$Sc_2ReB_6$
Sc ₃ Ni ₂ Si ₄	oP36	Pnma	1	0	-		1		1	- 1	I	I	1	I	I	T		$Sc_3Ni_2Si_4$
$Ce_2Ni_7$	hP36	$P6_{3}/mmc$	-	1	0	1	, I		1	1	I	I	ł	I	I	I		
Sc ₅ Co ₁₉ P ₁₂	'nP36	$P\overline{6}2m$	1	0	1	· ·	•			1	1	1	1	í	1	T		Sc ₅ Co ₁₉ P ₁₂
$Mg_2Zn_{11}$	cP39	$Pm\overline{3}$	1	0	-		1	-	1	1	I	Ι	1	I	I	I		$Sc_2Co_7Ga_4$
$U_2 Co_3 Si_5$	oI40	Ibam	-	0	I				1	-	I	I	Ι	I	I	Ι		Sc ₂ Co ₃ Si ₅
$Sc_2Fe_3Si_5$	tP40	P4/mnc	1	0	1	1	1		I		I	I	I	I	I	I		$Sc_2Fe_3Si_5$
Sc9Ni ₅ Ge8	oI44	Immm	1	0	T				1	1	-	I	I	ł	I	I		Sc ₉ Ni ₅ Ge ₈
ScNi ₆ Ge ₆	hP52	P6/mmm	1	0	-	ī			1	1	1	ł	T	I	ł	I		ScNi ₆ Ge ₆
$UB_{12}$	cF52	Fm3m	-	-	0		1		1	1	I	I	I	I	I	I		
$\mathrm{Sc_6Co_{30}Si_{19}}$	hP55	$P6_3/m$	1	0	-		1		1	-	[	1	I	I	I	I		Sc ₆ Co ₃₀ Si ₁₉
$Th_2Zn_{17}$	hR57	$R\overline{3}m$	-	0	-	, T	1	Ļ	I I	1	I	I	1	I	Ι	I		Sc ₂ Fe _{8.83} Ga _{8.17}
Gd ₁₄ Ag ₅₁	hP65	P6/m	1	0	-	ï	1	-	1		I	ł	Ι	ĺ	I	ł		Sc ₁₄ Cu ₃₇ Ga ₁₄
Sc ₃ C ₄	tP70	P4/mnc	П	1	0	1	1	, T	I I	1	I	I	I	I	I	I		
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## SCANDIUM ALLOY SYSTEMS AND INTERMETALLICS

519

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Structure type	Pearson's	Space	Number of	Inclue	ding			Inclu	ding i	n terr	ary s	systen	as Sc	-M-	Sc			Binary	Composition of ternary
	symbol	group	compounds	binary t	ternary	в	Al	Ga	ц	υ	Si	Ge	Sn	5b-	6-1	<u> </u>	M-M′	prototype	compound(s)
Sc ₃ Re ₂ Si ₄	mS72	C2/c	1	0	1	I	I	I	i	I	1	1		1		I			Sc3Re2Si4
LuRu4B4	tl72	$I4_1/acd$	1	0	-	-	I	I	I	I	I	ſ	I	1	1	Ι	I		$ScRu_4B_4$
ScFe ₆ Ge ₅	hR72	$R\overline{3}m$	1	0		ī	I	I	ţ	I	I	1	1	I	I	1	I		$ScFe_6Ge_5$
$Se_2S_3$	0F80	Fddd	1	1	0	I	ł	I	I	ļ	ī	I	T	I	f	1	Ι		
$Gd_3Ga_2$	tI80	I4/mcm	1	-	0	I	Ι	I	I	T	T	T	I	T	I	I	I		
$Sc_7As_3$	t <b>I</b> 80	I4/mcm	1	-	0	I	T	T	1	T	I	T	T	I	T	I	1		
$Sc_{11}AI_2Ge_8$	t184	I4/mmm	1	0	1	I	I	I	I	T	ŧ	I	I	1	I	1	н Т	$10_{11}$ Ge $1_0$	$ m Sc_{11}Al_2Ge_8$
$\mathrm{Sc_4Ni_{29}B_{10}}$	tI86	$I4_1/amd$	1	0	Н	_	Ι	ł	T	I	T	1	I	I	I	1	1		$Sc_4Ni_{29}B_{10}$
$ScFeSi_2$	oS96	Cmca	-	0	1	I	T	T	I	ł	1	I	1	I	I	Ι	ł		$ScFeSi_2$
$Sc_5Re_8Si_{12}$	oS100	Amm2	1	0	1	I	I	T	L	I	l	t	T	I	I	ŀ	I		Sc ₅ Re ₈ Si ₁₂
NaZn ₁₃	cF112	$Fm\overline{3}c$	1	1	0	1	Ι	I	I	ł	T	I	1	I	I	Ι	ι		
$Sc_{29}Fe_6$	cP140	$Pm\overline{3}$	1	-	0	I	1	I	I	I	1	T	T	I	Ţ	l	I		
Gd13 Cd58	hP142	P63/mmc	1	-	0	(	I	I	T	L	I	I	T	Т	I	I	I		
Hf2Ni _{6.5} Ga4.5	hP169	P6/mmm	1	0	1	I.	T	-	I	T	ļ	I	1	T	]	T	Ι		Sc ₂ Ni _{7,0-5.5} Ga _{4.0-5.5}
Se12.3 Ni40.7 Ge3	1 hP169	P6/mmm	Ţ	0	1	I	I	I	ł	I	I.		I	I	I.	ţ	I		$Sc_{12.3}Ni_{40.7}Ge_{31}$

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## **AUTHOR INDEX**

Acker, F., see Braun, H.F. 510 Akselrud, L.G., see Dzianii, R.B. 182, 186 Akselrud, L.G., see Gribanov, A.V. 79, 234 Akselrud, L.G., see Olenych, R.R. 42, 43, 448, 488 Aldred, A.T. 355, 358, 359, 362 Aldred, A.T., see Cashion, J.D. 510 Alekseeva, N.V., see Belyavina, N.M. 124, 125, 232 Alekseeva, N.V., see Markiv, V.Ya. 124 Alexander, D.G., see Gschneidner Jr, K.A. 361 Allenspach, P., see Gajewski, D.A. 466 Altofer, E.B., see Schöbinger-Papamantellos, P. 231 Altynbaev, R.A. 347, 387 Altynbaev, R.A., see Dzuraev, T.D. 346 Andrianov, M.A., see Kutaitsev, VI 350 Andrusyak, R.I. 41-45, 248, 251, 272, 278, 285, 363, 365, 438-440, 447, 448, 450, 486 Andrusyak, R.I., see Bodak, O.I. 45, 440 Andrusyak, R.I., see Kotur, B.Ya. 40-46, 300, 354, 355, 438-441, 445, 448, 450, 451 Anisimova, E.V. 130 Arbuckle, J. 373 Arnold, G.P., see Krikorian, N.H. 372 Arskaya, E.P. 463 Arskaya, E.P., see Savitskii, E.M. 463 Artyukh, L.V. 410, 412 Artyukh, L.V., see Ilyenko, S.M. 410 Artyukh, L.V., see Velikanova, T.Ya. 410, 411 Asano, S., see Ishida, S. 503 Aslan, A.M. 151, 152, 154 Auer-Welsbach, H. 373 Auer-Welsbach, H., see Nowotny, H. 373, 410 Auffret, S., see Boutarek, N. 298 Avillez, R.R., see Xia, S.R. 504 Badaeva, T.A. 349 Baggio-Saitovich, E., see Xia, S.R. 504 Baivel'man, M.G., see Marusin, E.P. 412 Baivel'man, M.G., see Tsokol', A.O. 458 Ballagny, A. 350

Ballou, R., see Lelievre-Berna, E. 460 Banakh, O.E. 417, 422 Banakh, O.E., see Kotur, B.Ya. 417 Bara, J.J. 59, 67, 82, 106, 135, 165 Barakatova, J.M. 113, 114, 116, 117, 247, 313 Baran, S. 288 Baranyak, V.M., see Koterlyn, G.M. 177, 193, 296 Baranyak, V.M., see Zaremba, V.I. 409 Barrett, R., see Matkovich, M.V. 365 Barz, H., see Espinosa, G.P. 452, 453 Barz, H., see Ku, H.C. 381, 385, 466, 512 Barz, H., see Matthias, B.T. 464, 465 Batlogg, B., see Cava, R.J. 513 Bauer, E. 496 Bauer, E., see Gratz, E. 500, 501, 505 Bauer, E., see Hauser, R. 508 Bauer, E., see Kotur, B.Ya. 419, 420, 431, 432, 504-507 Bauer, J. 457, 458 Bauer, J., see Halet, J.F. 458 Bauer, J., see Schuster, J.C. 366, 367, 393 Beaudry, B.J. 345-348, 351 Beaudry, B.J., see Ito, T. 460 Becker, K.W. 496 Belan, B.D. 118-122 Beloborodova, O.Ya., see Belyavina, N.M. 124, 125, 232 Beloborodova, O.Ya., see Markiv, V.Ya. 124 Belsky, V.K. 69, 324 Belsky, V.K., see Kotur, B.Ya. 354, 355 Bel'sky, V.K., see Mruz, O.Ya. 106, 107, 109 Belsky, V.K., see Oniskovetz, B.D. 120, 292 Bel'sky, V.K., see Pavlyuk, V.V. 19, 303 Belsky, V.K., see Pecharsky, V.K. 134, 283, 309 Belsky, V.K., see Salamakha, P.S. 98, 99, 102, 103 Belyavina, N.M. 32, 124, 125, 232, 367, 368, 397-399, 401, 402, 404-406 Belyavina, N.M., see Golovata, N.V. - 33 Belyavina, N.M., see Kuzmenko, P.P. 397-399, 404, 406

Belyavina, N.M., see Markiv, V.Ya. 124, 355, 356, 361, 362, 366-369, 389, 396-408, 456, 458 Benesovsky, F., see Gangleberger, E. 381 Benesovsky, F., see Haschke, H. 36 Benesovsky, F., see Jedlichka, H. 372, 373 Berezina, A.L. 386 Bereziuk, D.A., see Bodak, O.I. 416, 430 Berger, R. 378, 492 Besnus, M.J., see Rogl, P. 79 Bilonishko, N.S., see Fedyna, M.F. 144, 151, 191 Bilonizhko, N.S., see Kuz'ma, Yu.B. 381 Bingzychka, H., see Szytuła, A. 152 Bloch, D. 497 Block, H. 455, 456 Bodak, O.I. 11, 13, 18, 19, 35, 36, 45, 52, 55, 56, 60, 62, 70, 74, 83, 86, 90, 93, 95, 98, 107-109, 111, 119, 126, 127, 136, 137, 144-146, 151-154, 157, 160, 166, 168, 175, 176, 184, 191, 192, 197, 236, 250, 257, 311, 314, 354, 355, 372, 416, 419-421, 430, 432, 437, 438, 440, 442, 478, 482, 510 Bodak, O.I., see Belsky, V.K. 69, 324 Bodak, O.I., see Bruskov, V.A. 54, 243, 322 Bodak, O.I., see Dzianii, R.B. 182, 183, 186 Bodak, O.I., see Fedyna, M.F. 127, 152, 153, 168, 176, 185, 192, 230, 255 Bodak, O.I., see Gladyshevsky, E.I. 61, 68, 84, 109, 327, 392-394, 401, 402, 418, 419, 431, 444, 445, 451, 463, 487, 492, 506 Bodak, O.I., see Gorelenko, Yu.K. 54, 56, 107, 127, 136, 137, 144, 146, 152, 153, 166, 168, 175, 177, 185, 192, 193 Bodak, O.I., see Gribanov, A.V. 76-80, 234, 235, 244, 264, 319 Bodak, O.I., see Konyk, M.B. 56, 61, 70, 96, 128, 139, 147, 154, 169, 177, 186, 260 Bodak, O.I., see Koterlyn, G.M. 54, 56, 136, 137, 145, 146 Bodak, O.I., see Kotur, B.Ya. 40, 46, 50, 312, 352-356, 418-421, 426, 428, 430, 432-434, 438, 439, 441, 444, 445, 447, 478, 480, 485 Bodak, O.I., see Marusin, E.P. 412 Bodak, O.I., see Mokra, I.R. 416-418, 422 Bodak, O.I., see Morozkin, A.V. 110-113 Bodak, O.I., see Mruz, O.Ya. 53, 54, 81, 106, 107, 109, 127, 134, 143, 145, 150, 152, 164, 166, 173, 175, 190, 240, 300 Bodak, O.I., see Muratova, L.A. 35, 37, 38 Bodak, O.I., see Oleksyn, O.Ya. 168, 248

Bodak, O.I., see Oniskovetz, B.D. 118-120, 292 Bodak, O.I., see Pavlyuk, V.V. 9-14, 16-19, 261, 273, 281, 303, 306, 311, 318 Bodak, O.I., see Pecharskaya, A.O. 410, 412 Bodak, O.I., see Pecharsky, V.K. 53-55, 60, 61, 63, 67, 68, 78, 93, 95, 106, 108, 126, 127, 134, 135, 137, 143, 144, 146, 150, 151, 153, 164, 165, 168, 174, 175, 177, 184, 191, 192, 283, 289, 309, 316, 418, 430, 455 Bodak, O.I., see Salamakha, P.S. 66, 67, 69-71, 89-95, 98-103, 185, 227, 228, 270, 306 Bodak, O.I., see Seropegin, Yu.D. 187, 188 Bodak, O.I., see Shapiev, B.I. 75, 274 Bodak, O.I., see Shpyrka, Z.M. 196-199, 202 Bodak, O.I., see Sologub, O.L. 57, 58, 63, 71, 77, 78, 80, 85-89, 99, 103, 104, 110, 114-117, 129, 130, 132, 140, 142, 148, 155, 156, 159, 161, 162, 171, 172, 179, 180, 187, 190, 246, 290, 317 Bodak, O.I., see Starodub, P.K. 132, 133, 136, 299 Bodak, O.I., see Stetskiv, A.O. 298 Bodak, O.I., see Trubniakova, E.D. 387 Bodak, O.I., see Tsokol', A.O. 412, 458 Bodak, O.I., see Yarmolyuk, Ya.P. 262 Bodak, O.I., see Zaplatynsky, O.V. 99, 100 Boichuk, L.A., see Kotur, B.Ya. 48, 436, 451 Boiko, L.I., see Mikhalenko, S.I. 381, 382 Bondar, A.A., see Eremenko, V.N. 411 Bondar, A.A., see Velikanova, T.Ya. 410, 411 Bordet, P., see Verniere, A. 57, 58, 65, 75, 78, 86, 88, 99, 103, 113, 115, 129, 131, 140, 142, 148, 170, 172, 179, 180, 194 Borisenko, O.L. 189, 190 Borisenko, O.L., see Seropegin, Yu.D. 187, 188 Borrmann, H., see Pöttgen, R. 52, 80, 181, 195, 494 Boucher, R., see Ballagny, A. 350 Boucherle, J.X., see Verniere, A. 57, 58, 65, 75, 78, 86, 88, 99, 103, 113, 115, 129, 131, 140, 142, 148, 170, 172, 179, 180, 194 Boutarek, N. 298 Bowman, A.L., see Krikorian, N.H. 372 Brabers, J.H.V.J. 52, 132, 143, 149, 163 Brabers, J.H.V.J., see Schöbinger-Papamantellos, P. 231 Braslavskava, G.S. 355, 356 Braslavskaya, G.S., see Maslenkov, S.B. 356, 463

Braun, H.F. 58, 419, 421, 432, 433, 467, 491, 510. 511 Braun, H.F., see Chabot, B. 421 Braun, H.F., see Segre, C.U. 57, 58, 74, 78, 86, 87, 98, 102, 111, 115, 123, 128, 131, 139, 141, 148, 155, 160, 170, 171, 178, 180, 187, 189, 194, 195, 242 Braun, H.F., see Vining, C.B. 510-512 Braun, R.M., see Braun, H.F. 58, 419, 421, 432, 491 Brewer, L. 352, 411 Brixner, L.H. 378 Bronger, W. 359 Brovko, A.P., see Shamrai, V.F. 391 Brozek, V. 378 Bruno, M., see Kotur, B.Ya. 40 Bruskov, V.A. 54, 61, 230, 243, 280, 313, 322, 366, 367 Bruskov, V.A., see Bodak, O.I. 45, 56, 60, 62, 70, 83, 86, 90, 93, 95, 98, 107, 109, 111, 127, 136, 137, 145, 146, 152, 154, 166, 168, 175, 192, 236, 314, 440 Bruskov, V.A., see Gorelenko, Yu.K. 54, 56, 107, 127, 136, 137, 144, 146, 152, 153, 166, 168, 175, 177, 185, 192, 193 Bruskov, V.A., see Kuz'ma, Yu.B. 381 Bruskov, V.A., see Mruz, O.Ya. 107, 300 Bruskov, V.A., see Pavlyuk, V.V. 10, 11, 16-19, 281, 318 Bruskov, V.A., see Pecharsky, V.K. 316 Bruskov, V.A., see Salamakha, P.S. 93, 103, 270, 306 Bruskov, V.A., see Shpyrka, Z.M. 196-199, 202 Bruskov, V.A., see Starodub, P.K. 136, 299 Bruvo, M., see Kotur, B.Ya. 418, 419, 426, 431, 444, 480 Buchholz, W. 44, 45, 54, 126, 136, 144, 152, 165, 175, 183, 231, 233, 439, 440, 448 Bulanova, M.V., see Eremenko, V.N. 376 Bulyo, V.S., see Zmii, O.F. 20, 241 Burkhanov, G.S., see Savitskii, E.M. 351 Burkov, A.T., see Gratz, E. 500, 501, 505 Burnashova, V.V. 468 Burnashova, V.V., see Karatygina, E.P. 389, 393, 394 Burnashova, V.V., see Markiv, V.Ya. 389, 393, 398.405 Burri, G., see Braun, H.F. 421, 433 Burri, G., see Ku, H.C. 381, 385, 466, 512 Burzo, E. 497, 498

Buschow, K.H.J., see Brabers, J.H.V.J. 52, 132, 143, 149, 163 Buschow, K.H.J., see Grössinger, R. 504 Buschow, K.H.J., see Schöbinger-Papamantellos, P. 231 Buschow, K.H.J., see Smit, P.H. 504 Butera, R.A., see McCall, W.M. 54, 60, 68 Buyanov, Yu.I., see Eremenko, V.N. 372, 373, 375 Buyanov, Yu.I., see Lukashenko, G.M. 470 Calderwood, F.W., see Gschneidner Jr, K.A. 345, 347-349, 366, 371, 377 Callmer, B. 366 Calvert, L.D., see Villars, P. 343, 478, 480 Canepa, F., see Merlo, F. 295, 296 Carrard, C., see Ballagny, A. 350 Carter, S.A., see Cava, R.J. 513 Cashion, J.D. 510 Cava, R.J. 513 Cava, R.J., see Siegrist, T. 513 Cavin, O.B. 349 Cenzual, K. 57, 86, 170, 285, 357-359 Cenzual, K., see Chabot, B. 357-359 Cenzual, K., see Gladyshevsky, R.E. 74, 324 Cenzual, K., see Zhao, J.T. 23, 263 Cerny, R., see Kotur, B.Ya. 417, 419, 438, 444, 485 Chaban, N.F., see Kuz'ma, Yu.B. 381 Chabot, B. 355, 357-359, 418, 419, 421, 430, 431, 434 Chabot, B., see Cenzual, K. 57, 86, 170, 285, 357-359 Chabot, B., see Engel, N. 47, 48, 51, 266, 421, 440, 441, 491 Chabot, B., see Hovestreydt, E. 47, 48, 51, 52, 57, 58, 63-65, 74, 76, 78, 79, 86-88, 99, 103, 113, 115, 116, 129-131, 140-142, 148, 156, 158, 161, 162, 170-172, 179, 180, 291, 399, 421, 434, 440, 441, 452 Chabot, B., see Parthé, E. 48, 62, 327, 440 Chabot, B., see Zhao, J.T. 418, 430, 485 Chakrabarti, D.J., see Subramanian, P.R. 361 Chandra, G., see Ghosh, K. 74 Chandra, G., see Ramakrishnan, S. 466 Chasanov, M.G., see Schablaske, R.V. 365 Chau, R., see Maple, M.B. 460 Chaudouet, P., see Ghetta, V.P. 455 Chebotarev, N.T., see Kutaitsev, V.I. 350 Cheldieva, G.M. 391 Chen, S.K. 465

Chenavas, J., see Verniere, A. 57, 58, 65, 75, 78, 86, 88, 99, 103, 113, 115, 129, 131, 140, 142, 148, 170, 172, 179, 180, 194 Cherkashin, E.E., see Prevarskii, A.P. 390, 395 Cherkashin, E.E., see Zalutska, O.I. 388 Chevalier, B., see Rogl, P. 79 Chu, C.W., see Gardner, W.E. 369 Chuistov, K.V., see Berezina, A.L. 386 Chuntonov, K.A., see Yatsenko, S.P. 367-369 Cirafici, S., see Palenzona, A. 351 Clark, J.B., see Naveb-Hashemi, A.A. 346 Clogston, A.M., see Matthias, B.T. 501 Colinet, C. 470 Compton, V.B. 358, 359, 368 Compton, V.B., see Geballe, T.H. 358, 509 Conner Jr, R.A., see Dwight, A.E. 358, 359, 362, 419, 420, 440 Contardi, V. 127, 185 Contardi, V., see Zanicchi, G. 130, 147 Cooper, A.S. 452 Cooper, A.S., see Espinosa, G.P. 452, 453 Cogblin, B. 498-500 Corbett, J.D., see Guloy, A.M. 304 Corenzwit, E., see Geballe, T.H. 358, 509 Corenzwit, E., see Matthias, B.T. 464, 465, 501 Czybulka, A. 9, 10, 12-16 Czybulka, A., see Schuster, H.-U. - 10 Daane, A.H., see Beaudry, B.J. 345-348, 351 Dai, P., see Maple, M.B. 460 Danilenko, V.M., see Ilyenko, S.M. 410 Darby Jr, J.B. 353 Darby Jr, J.B., see Dwight, A.E. 462 de Boer, F.R. 349 de Boer, F.R., see Brabers, J.H.V.J. 52, 132, 143, 149, 163 de Boer, F.R., see Schöbinger-Papamantellos, P. 231 Deberitz, J., see Bodak, O.I. 11, 13, 18, 19 Dennison, D.H. 352 Deportes, J., see Lelievre-Berna, E. 460 Deppe, P., see Braun, H.F. 510 Derkach, V.A. 452, 453, 485 Derkach, V.O., see Kotur, B.Ya. 361, 373, 376, 452, 454 Deschizeaux-Cherny, M.-N., see Ghetta, V.P. 455 Desclaux, J.P., see Freeman, A.J. 496 Dey, S., see Braun, H.F. 510 Dhar, S.K. 460, 466 Dhar, S.K., see Ghosh, K. 74

Dhar, S.K., see Ikeda, K. 497, 498 Dhar, S.K., see Nagarajan, R. 513 Dijkman, W.H., see de Boer, F.R. 349 DiSalvo, F.J., see Jones, C.D.W. 80 Dismukes, J.P. 378, 459 Dismukes, J.P., see White, J.G. 377, 378, 476 Dobatkina, T.V., see Drits, M.E. 366 Dobatkina, T.V., see Toropova, L.S. 458 Dobrianskaya, L.O., see Kotur, B.Ya. 417, 419, 420, 422 Domashnikov, B.P., see Berezina, A.L. 386 Dommann, A. 80 Donolato, C., see Reule, H. 362 Downey, J.W., see Darby Jr, J.B. 353 Downey, J.W., see Dwight, A.E. 358, 359, 362, 419, 420, 440 Doyle, N.J., see Taylor, A. 352 Drits, M.E. 366, 392, 460, 464 Dronskowski, R., see Pöttgen, R. 409 Drulis, H., see Bodak, O.I. 419 Dub, O.M., see Kuz'ma, Yu.B. 381 Dubenko, I.S., see Gratz, E. 509 Duh, J.G., see Chen, S.K. 465 Dunlap, C.K., see Segre, C.U. 98, 102 Duraj, M. 326 Duraj, R., see Duraj, M. 326 Dutsyak, I.S., see Kotur, B.Ya. 361 Dwight, A.E. 46, 353-355, 358, 359, 362, 389, 390, 392, 393, 396, 399, 406, 408, 409, 419-421, 440, 441, 451-456, 462-464 Dzianii, R.B. 181-186 Dzuraev, T.D. 346 Dzynyi, R., see Salamakha, P.S. 66, 185 Ebel, T., see Pöttgen, R. 410, 412 Eberz, U. 452, 454 Economy, J., see Matkovich, M.V. 365 Efimov, Yu.V., see Savitskii, E.M. 352, 397, 401, 402, 462 Efimov, Yu.V., see Shamrai, V.F. 391 Eisaki, H., see Cava, R.J. 513 Ellinger, F.H. 350, 351 Emes-Misenko, E.I., see Gladyshevsky, E.I. 372, 373 Engel, N. 47, 48, 51, 266, 421, 440, 441, 491 Engel, N., see Chabot, B. 419, 421, 431, 434 Engel, N., see Hovestreydt, E. 47, 48, 51, 52, 57, 58, 63-65, 74, 76, 78, 79, 86-88, 99, 103, 113, 115, 116, 129-131, 140-142, 148, 156, 158, 161, 162, 170-172, 179, 180, 291, 399, 421, 434, 440, 441, 452

Erdmann, B. 358, 359 Eremenko, V.N. 358, 359, 372, 373, 375, 376, 411, 463 Eremenko, V.N., see Gordijchuk, O.V. 371 Eremenko, V.N., see Velikanova, T.Ya. 410, 411 Ermolaev, E.E., see Prokin, E.S. 378 Ershova, Z.V., see Prokin, E.S. 378 Espinosa, G.P. 452, 453 Etourneau, J., see Peshev, P. 365-367 Etourneau, J., see Rogl, P. 79 Eymond, S. 367 Falco, C.M., see Cashion, J.D. 510 Falkowski, K., see Pawlak, L. 456 Farsam, H., see Guittard, M. 456, 476 Fedorova, E.G., see Yatsenko, S.P. 367-370 Fedyna, M.F. 53, 55, 81-85, 127, 144-146, 150-153, 165, 166, 168, 173-177, 183, 185, 191, 192, 230, 238, 239, 247, 255, 283 Fedyna, M.F., see Bodak, O.I. 126, 136, 144, 151, 166, 175, 184, 191 Fedyna, M.F., see Koterlyn, G.M. 177, 193, 296 Fedyna, M.F., see Mruz, O.Ya. 54, 107, 127, 145, 152, 166, 175 Fedyna, M.F., see Oleksyn, O.Ya. 54, 127, 136, 145, 152, 166, 175, 192 Fedyna, M.F., see Pecharsky, V.K. 53-55, 60, 61, 67, 68, 93, 95, 106, 108, 126, 127, 134, 135, 137, 143, 144, 146, 150, 151, 153, 164, 165, 168, 174, 175, 177, 184, 191, 192 Felder, R.J., see Cava, R.J. 513 Felner, I. 59, 73, 74, 92, 106, 110, 117, 119 Felner, I., see Mayer, I. 20, 22 Felser, C., see Pöttgen, R. 52, 80, 181, 195, 494 Ferro, R., see Bodak, O.I. 11, 13, 18, 19 Ferro, R., see Contardi, V. 127, 185 Ferro, R., see Rossi, D. 53, 58, 59, 61, 65-67, 72, 76, 79-82, 85, 88, 96, 99, 103-105, 110, 117, 124, 126, 129, 131-I33, 142-144, 148-150, 163, 164, 172, 182, 183, 187, 190, 494 Flahaut, J., see Brozek, V. 378 Flahaut, J., see Julien-Pouzol, M. 456, 476, 479 Fomenko, V.S., see Samsonov, G.V. 379 Fornasini, M.L. 421, 436 Fornasini, M.L., see Merlo, F. 20, 123, 295, 296 Fornasini, M.L., see Pani, M. 365 Fournier, J.M. 502 Fradin, E.Y., see Segre, C.U. 98, 102

Francois, M. 57-59, 61-65, 71, 73, 74, 78, 80, 85, 86, 88, 99, 103, 105, 106, 110, 112, 115, 117, 121, 123, 125–134, 137, 139–144, 146-150, 153-159, 161, 164, 168-174, 177-181, 186-195 Francois, M., see Malaman, B. 327 Franse, J.J.M. 503 Freeman, A.J. 496 Frick, B. 496, 497 Frolova, T.M., see Savitskii, E.M. 397, 401, 402Frost, C.D., see Mathur, N.D. 253 Fukamichi, F., see Goto, T. 497 Fulde, P., see Becker, K.W. 496 Furthmueller, J., see Kresse, G. 469 Gajewski, D.A. 466 Gajewski, D.A., see Maple, M.B. 460 Galatanu, A., see Gratz, E. 500, 501 Galera, R.M., see Lelievre-Berna, E. 460 Gambino, R.J., see Holtzberg, F. 38 Gangleberger, E. 381 Ganiev, I.N., see Odinaev, H.O. 386 Ganiev, I.N., see Trubniakova, E.D. 387 Gardner, W.E. 369 Gavrilenko, I.S. 397-400, 402, 404-408 Gavrilenko, I.S., see Bodak, O.I. 354, 355 Gavrilenko, I.S., see Grin', Yu.N. 397, 401 Gavrilenko, I.S., see Markiv, V.Ya. 355, 356, 361, 362, 366-368, 399, 408 Gavrilenko, I.S., see Savitskii, E.M. 397, 401, 402 Geballe, T.H. 358, 509 Gebhardt, E., see Stapf, I. 361, 362 Ghetta, V.P. 455 Ghfari, M., see Xia, S.R. 504 Ghosh, K. 74 Ghosh, K., see Dhar, S.K. 460, 466 Ghosh, K., see Ramakrishnan, S. 466 Gibson, B. 58, 114, 115, 130, 141, 147, 159, 171, 179, 188, 195 Giese Jr, R.F., see Matkovich, M.V. 365

- Giorgi, A.L., see Krikorian, N.H. 372
- Giorgi, A.L., see Krupka, M.C. 409
- Gladyshevsky, E.I. 45, 61, 68, 84, 109, 327, 345, 354, 355, 372, 373, 390, 392–395, 401, 402, 418–420, 431, 444, 445, 451, 463, 485–487, 492, 506
- Gladyshevsky, E.I., see Anisimova, E.V. 130

Gladyshevsky, E.I., see Bodak, O.I. 52, 56, 62, 70, 86, 90, 98, 111, 119, 236, 372, 419-421, 432, 478, 482, 510 Gladyshevsky, E.I., see Bruskov, V.A. 313, 322 Gladyshevsky, E.I., see Kotur, B.Ya. 355, 356, 419-421, 432, 433, 436, 486 Gladyshevsky, E.I., see Mokra, I.R. 417 Gladyshevsky, E.I., see Muratova, L.A. 35, 38 Gladyshevsky, E.I., see Muravyeva, A.A. 23, 24 Gladyshevsky, E.I., see Pecharsky, V.K. 134, 283, 309, 418, 430 Gladyshevsky, E.I., see Protasov, V.S. 345 Gladyshevsky, E.I., see Savysyuk, I.A. 87 Gladyshevsky, E.I., see Stetskiv, L.V. 201 Gladyshevsky, E.I., see Voroshilov, Yu.V. 419, 420 Gladyshevsky, E.I., see Zarechnyuk, O.S. 26 - 32, 254 Gladyshevsky, E.I., see Zmii, O.F. 20, 241 Gladyshevsky, R.E. 57, 62, 74, 75, 86, 99, 113, 129, 140, 158, 160, 170, 179, 194, 277, 307, 324 Gmelin, E., see Schnelle, W. 494-496 Godart, C., see Nagarajan, R. 513 Goebel, S. 355, 356, 389, 393 Golovata, N.V. 33 Golubets, Ya.O., see Koshel', O.S. 460 Golubiak, L.S., see Markiv, V.Ya. 397, 400 Gopaalakrishnan, K.V., see Nagarajan, R. 513 Gordijchuk, O.V. 371, 373, 412, 414 Gordijchuk, O.V., see Artyukh, L.V. 410, 412 Gordijchuk, O.V., see Velikanova, T.Ya. 410, 411 Gordon, R.A., see Jones, C.D.W. 80 Gorelenko, Yu.K. 54, 56, 107, 127, 136, 137, 144, 146, 152, 153, 166, 168, 175, 177, 185, 192, 193 Gorelenko, Yu.K., see Bodak, O.I. 126, 136, 144, 151, 166, 175, 184, 191 Gorelenko, Yu.K., see Mruz, O.Ya. 109 Gorina, N.B., see Savitskii, E.M. 357-359 Goto, T. 497 Granovsky, S.A., see Gratz, E. 509 Gratz, E. 498-501, 505, 509 Gratz, E., see Bauer, E. 496 Gratz, E., see Burzo, E. 497, 498 Gratz, E., see Fournier, J.M. 502 Gratz, E., see Hauser, R. 508 Gratz, E., see Kotur, B.Ya. 419, 420, 431, 432, 504--507

Gribanov, A.V. 75-80, 234, 235, 244, 264, 319 Grill, A., see Felner, I. 106 Grin', Yu.N. 397, 401 Grin', Yu.N., see Gryniv, I.O. 32, 279 Grin', Yu.N., see Opainych, I.M. 32, 325 Grin', Yu.N., see Yarmolyuk, Ya.P. 419, 431 Grössinger, R. 504 Grund, I. 8, 11, 15, 18, 438, 451, 452 Gryniv, I.A., see Yarmolyuk, Ya.P. 262 Gryniv, I.O. 32, 33, 279, 282, 305 Gschneidner Jr, K.A. 342, 343, 345-353, 357, 358, 361, 363, 366, 370, 371, 377, 388 Gschneidner Jr, K.A., see Dennison, D.H. 352 Gschneidner Jr, K.A., see Ghosh, K. 74 Gschneidner Jr, K.A., see Hungsberg, R.E. 496 Gschneidner Jr, K.A., see Ikeda, K. 497, 498, 501-503 Gschneidner Jr, K.A., see McMasters, O.D. 362 Gschneidner Jr, K.A., see Pecharsky, V.K. 39, 60, 63, 68, 78, 289, 321 Gschneidner Jr, K.A., see Rider, P.E. 363 Guan, W.Y., see Ku, H.C. 467, 513 Guillot, M., see Baran, S. 288 Guittard, M. 456, 476 Guittard, M., see Brozek, V. 378 Guittard, M., see Julien-Pouzol, M. 456, 476, 479 Guljak, O.V., see Fedyna, M.F. 85 Guloy, A.M. 304 Gulyak, O.V., see Fedyna, M.F. 144, 151, 191 Gupta, L.C., see Nagarajan, R. 513 Gurjazkas, D., see Gratz, E. 509

Gushchina, F.L., see Drits, M.E. 392

Haferl, R., see Grössinger, R. 504 Hafner, J., see Kresse, G. 469 Hairidinov, S.H., see Altynbaev, R.A. 347, 387 Halet, J.F. 458 Hanel, G. 56, 110, 138, 154, 177, 186, 421 Harmelin, M., see Bodak, O.I. 11, 13, 18, 19 Harper, W.C., see Dwight, A.E. 46, 421, 452 Harris, I.R., see Hines, W.A. 368 Harris, I.R., see Norman, M. 358 Harris, L.A., see Cavin, O.B. 349 Haschke, H. 36 Häufler, Th., see Hauser, R. 508 Hauser, R. 508 Hellawell, A. 353 Henn, R., see Pöttgen, R. 52, 80, 181, 195, 494 Hickman, W.M., see Taylor, A. 352

Hiebl, K., see Le Bihan, T. 56, 128, 139, 147, 154, 169, 178, 186, 193 Hiebl, K., see Sologub, O.L. 57, 58, 63, 71, 77, 78, 80, 85-89, 99, 103, 104, 110, 114-117, 129, 130, 132, 140, 142, 148, 162, 171, 172, 179, 180, 187, 190 Hilscher, G., see Grössinger, R. 504 Hilscher, G., see Hauser, R. 508 Hilscher, G., see Kotur, B.Ya. 419, 420, 431, 432, 504-507 Hines, W.A. 368 Hodeau, J.L. 453 Hohnke, D., see Parthé, E. 367 Holleck, H. 381, 385, 412, 414, 415, 457, 458, 480 Holtzberg, F. 38 Hossain, Z., see Nagarajan, R. 513 Hovestreydt, E. 47, 48, 51, 52, 57, 58, 63-65, 74, 76, 78, 79, 86-88, 99, 103, 113, 115, 116, 129-131, 140-142, 148, 156, 158, 161, 162, 170-172, 179, 180, 291, 399, 421, 434, 440, 441.452 Hovestreydt, E., see Jorda, J.L. 57, 63, 76, 87, 99, 114, 122, 130, 140, 148, 158, 171, 179, 188, 194 Howlett, B.W., see Gardner, W.E. 369 Hrynkiewicz, H.U., see Bara, J.J. 59, 67, 82, 106, 135, 165 Hu, Z., see Ghosh, K. 74 Hull Jr, G.W., see Geballe, T.H. 358, 509 Hull Jr, G.W., see Hulliger, F. 378 Hulliger, F. 378, 456, 476 Hulliger, F., see Dommann, A. 80 Hungsberg, R.E. 496 Hyun, O.-B., see Pecharsky, V.K. 60, 68 Iandelli, A. 56, 61, 70, 85, 110, 120, 128, 138, 146, 154, 169, 177, 185, 193, 295, 387, 436 Iandelli, A., see Fornasini, M.L. 421, 436 Iglesias-Sicardi, J.R., see Coqblin, B. 498-500 Ikeda, K. 497, 498, 501-503 Ilyenko, S.M. 410 Ilyenko, S.M., see Artyukh, L.V. 410 Ishida, S. 503 Ishikawa, N., see Jorda, J.L. 57, 63, 76, 87, 99, 114, 122, 130, 140, 148, 158, 171, 179, 188, 194 Ito, K., see Ito, T. 460 Ito, T. 460 Ivanchenko, V.G., see Bodak, O.I. 354, 355 Ivanchenko, V.G., see Svechnikov, V.M. 352

Jansen, K. 454 Jedlichka, H. 372, 373 Jeitschko, W. 374, 454, 455 Jeitschko, W., see Block, H. 455, 456 Jeitschko, W., see Parthé, E. 367 Jeitschko, W., see Pöttgen, R. 372, 373, 410-412 Jeitschko, W., see Reinbold, E.J. 454, 455 Jepsen, O., see Pöttgen, R. 52, 80, 181, 195, 494 Jepsen, O., see Schnelle, W. 494-496 Johnson, K.A., see Ellinger, F.H. 350 Johnson, M.J. 452 Johnson, Q., see Smith, G. 458 Johnston, D.C. 512 Johnston, D.C., see Ku, H.C. 381, 385, 466, 512 Jones, C.D.W. 80 Jorda, J.L. 57, 63, 76, 87, 99, 114, 122, 130, 140, 148, 158, 171, 179, 188, 194 Julien-Pouzol, M. 456, 476, 479 Julien-Pouzol, M., see Brozek, V. 378 Jullien, R., see Coqblin, B. 498-500 Kadaner, E.S., see Drits, M.E. 366 Kadowaki, K. 501 Kalychak, Ya.M., see Bodak, O.I. 416, 430 Kalychak, Ya.M., see Zaremba, V.I. 33, 308, 409 Kamardinkin, A.N., see Kotur, B.Ya. 390, 425, 426 Kamardinkin, A.N., see Toropova, L.S. 390 Kamta, M., see Venturini, G. 48 Karamishev, M.I., see Zalutska, O.I. 388 Karatygina, E.P. 389, 393, 394 Kawabata, A., see Moriya, T. 502 Kawano, S., see Nakamura, Y. 509 Kazachkova, A.S., see Markiv, V.Ya. 367, 368, 397.400-402 Kazakova, E.F., see Cheldieva, G.M. 391 Kazakova, E.F., see Sokolovskaya, E.M. 391 Keller, C., see Erdmann, B. 358, 359 Keller, J., see Becker, K.W. 496 Keller, N., see Verniere, A. 57, 58, 65, 75, 78, 86, 88, 99, 103, 113, 115, 129, 131, 140, 142, 148, 170, 172, 179, 180, 194

Ivanov, A.V., see Burnashova, V.V. 468

- Khamidov, O.Kh., see Savitskii, E.M. 353
- Kharakterova, M.L. 395

- Kharakterova, M.L., see Toropova, L.S. 395, 458
- Kharakterova, M.L., see Tyvanchuk, A.T. 458, 485
- Kharchenko, O.I., see Bodak, O.I. 416, 430
- Khar'kova, A.M., see Eremenko, V.N. 411
- Khorlin, E.M., see Savitskii, E.M. 357, 358
- Khorujaya, V.G. 357, 358, 463
- Khorujaya, V.G., see Eremenko, V.N. 358, 359, 463
- Kiessler, G., see Stapf, I. 361, 362
- Kimball, C.W., see Dwight, A.E. 46, 389, 390, 392, 393, 396, 399, 409, 421, 452, 453
- Kinzhibalo, V.V., see Kotur, B.Ya. 390, 425, 426
- Kinzhibalo, V.V., see Odinaev, H.O. 386
- Kinzhibalo, V.V., see Toropova, L.S. 390
- Kirchmayr, H., see Bauer, E. 496
- Klepp, K., see Hovestreydt, E. 47, 48, 51, 52, 57, 58, 63–65, 74, 76, 78, 79, 86–88, 99, 103, 113, 115, 116, 129–131, 140–142, 148, 156, 158, 161, 162, 170–172, 179, 180, 291, 399, 421, 434, 440, 441, 452
- Klesnar, H., see Weitzer, F. 60, 82, 92
- Klyuchka, I.P., see Kotur, B.Ya. 452, 453
- Kobayashi, N., see Ikeda, K. 502
- Kobzenko, G.F., see Svechnikov, V.M. 352
- Kochetkov, Yu.V., see Seropegin, Yu.D. 187, 188
- Kokhan, O.M., see Shpyrka, Z.M. 202
- Kokhan, Z.M., see Bodak, O.I. 197, 437, 438, 442
- Kolesnichenko, V.E., see Savitskii, E.M. 352, 361, 362
- Komatsu, H., see Goto, T. 497
- Komissarova, L.N. 377
- Komissarova, L.N., see Men'kov, A.A. 377-379
- Komura, Y., see Nakamura, H. 508
- Kondrashov, A.I. 379
- Kondrashov, A.I., see Samsonov, G.V. 379
- Konev, V.N., see Kutaitsev, V.I. 350
- Kontsevii, V.G., see Zalutska, O.I. 388
- Konyk, M.B. 56, 61, 65–68, 70, 71, 85, 96, 128, 139, 147, 154, 169, 177, 186, 260, 268, 275, 276
- Konyk, M.B., see Belsky, V.K. 69, 324
- Konyk, M.B., see Gladyshevsky, E.I. 390, 395
- Konyk, M.B., see Pecharsky, V.K. 53–55, 60, 61, 67, 68, 93, 95, 106, 108, 126, 127, 134, 135, 137, 143, 144, 146, 150, 151, 153, 164, 165, 168, 174, 175, 177, 184, 191, 192

- Konyk, M.B., see Salamakha, P.S. 66, 67, 69–71, 92, 94, 95, 185
- Korniyenko, K.Ye., see Eremenko, V.N. 463
- Korniyenko, K.Ye., see Khorujaya, V.G. 357, 358, 463
- Koshel', O.S. 460
- Koterlyn, G.M. 54, 56, 136, 137, 145, 146, 177, 192, 193, 296
- Koterlyn, G.M., see Bodak, O.I. 192
- Koterlyn, G.M., see Fedyna, M.F. 127, 152, 153, 168, 176, 185, 192
- Koterlyn, G.M., see Oleksyn, O.Ya. 54, 127, 136, 145, 152, 166, 175, 192
- Kotroczo, V. 372, 416, 458, 481
- Kotroczo, V., see McColm, I.J. 467, 481
- Kottar, A., see Gratz, E. 509
- Kottar, A., see Kotur, B.Ya. 419, 420, 431, 432, 504–507
- Kotur, B.Ya. 39–46, 48–50, 300, 312, 348, 349, 352–356, 361, 372, 373, 376, 390, 395, 416–426, 428, 430–434, 436, 438–442, 444, 445, 447, 448, 450–454, 478, 480–482, 485–490, 492, 504–507
- Kotur, B.Ya., see Andrusyak, R.I. 41–45, 251, 363, 365, 439, 440, 447, 448, 450, 486
- Kotur, B.Ya., see Banakh, O.E. 417, 422
- Kotur, B.Ya., see Bodak, O.I. 45, 354, 355, 372, 419-421, 432, 440, 510
- Kotur, B.Ya., see Derkach, V.A. 452, 453, 485
- Kotur, B.Ya., see Gladyshevsky, E.I. 418–420, 431, 486, 506
- Kotur, B.Ya., see Mruz, O.Ya. 106, 107
- Kotur, B.Ya., see Odinaev, H.O. 386
- Kotur, B.Ya., see Toropova, L.S. 395
- Kotur, B.Ya., see Tyvanchuk, A.T. 458, 485
- Kotur, B.Ya., see Yarmolyuk, Ya.P. 419, 431
- Kotur, O.Ya., see Kotur, B.Ya. 418, 430
- Kovachikova, M.V., see Seropegin, Yu.D. 187, 188
- Kozlov, A.A., see Savitskii, E.M. 357, 358
- Krajewski, J.J., see Cava, R.J. 513
- Krajewski, J.J., see Siegrist, T. 513
- Kravs, A.B., see Kotur, B.Ya. 40, 438, 439, 445
- Kremer, R.K., see Gibson, B. 58, 114, 115, 130,
  - 141, 147, 159, 171, 179, 188, 195
- Kremer, R.K., see Jones, C.D.W. 80
- Kremer, R.K., see Pöttgen, R. 52, 80, 124, 181, 195, 292, 494
- Kremer, R.K., see Schnelle, W. 494-496
- Kresse, G. 469
- Krikorian, N.H. 372

Kripvakevich, P.1. 328, 353, 363, 365, 483, 490, 491 Kripyakevich, P.1., see Bodak, O.I. 70, 119 Kripyakevich, P.I., see Gladyshevsky, E.I. 345, 354, 355 Kripyakevich, P.I., see Kuz'ma, Yu.B. 381 Kripyakevich, P.I., see Zalutskii, I.1. 367 Krivdin, B.P., see Savitskii, E.M. 357, 358 Krupka, M.C. 409 Krupka, M.C., see Krikorian, N.H. 372 Ku, H.C. 381, 385, 466, 467, 512, 513 Ku, H.C., see Shelton, R.N. 381 Kubashewski, O. 354 Kutaitsev, V.1. 350 Kuz'ma, Yu.B. 381, 485, 491 Kuz'ma, Yu.B., see Bruskov, V.A. 366, 367 Kuz'ma, Yu.B., see Gladyshevsky, E.I. 45, 345, 354, 355, 420 Kuz'ma, Yu.B., see Kripyakevich, P.I. 353, 363, 365 Kuz'ma, Yu.B., see Marko, M.A. 20, 21 Kuz'ma, Yu.B., see Mikhalenko, S.I. 381, 382 Kuz'ma, Yu.B., see Stepanchikova, G.F. 381, 383, 384 Kuz'ma, Yu.B., see Zavalii, L.V. 381, 384 Kuzmenko, P.P. 397-399, 404, 406 Kuzmina, V.I., see Turkina, A.I. 386 Kuznetsova, R.I., see Badaeva, T.A. 349 Kyrchiv, G.I. 463 Kyrchiv, G.I., see Koterlyn, G.M. 54, 56, 136, 137, 145, 146 Lai, C.C., see Ku, H.C. 467, 513 Lam, D.J., see Darby Jr, J.B. 353 Lam, D.J., see Dwight, A.E. 462 Lambert-Andron, B., see Boutarek, N. 298 Lambert-Andron, B., see Ghetta, V.P. 455 Lamoreaux, R.H., see Brewer, L. 352, 411 Land, C.C., see Ellinger, F.H. 350 Laube, E. 345, 364, 365 Laughlin, D.E., see Subramanian, P.R. 361 Le Bihan, T. 56, 128, 139, 147, 154, 169, 178, 186, 193 Lea, K.R. 496 Leask, M.J.M., see Lea, K.R. 496 Lebedev, I.G., see Kutaitsev, V.I. 350 Leciejewicz, J., see Baran, S. 288 Lederer, P., see Mills, D.L. 498 Lee, E.W. 497 Lee, K.J., see Smith, J.F. 352

Lejav, P., see Verniere, A. 57, 58, 65, 75, 78, 86, 88, 99, 103, 113, 115, 129, 131, 140, 142, 148, 170, 172, 179, 180, 194 Lelievre-Berna, E. 460 Lemaire, R., see Bloch, D. 497 Liao, P.K., see Spear, K.E. 366 Litvinko, N.Z., see Kotur, B.Ya. 421, 434 Loewenhaupt, M., see Frick, B. 496, 497 Longinotti, L.D., see Geballe, T.H. 358, 509 Luciyevich, J., see Szytuła, A. 152 Lukas, H.L., see Bodak, O.I. 11, 13, 18, 19 Lukashenko, G.M. 470 Lux, C. 468 Madar, R., see Boutarek, N. 298 Madar, R., see Ghetta, V.P. 455 Malaman, B. 327, 452, 453 Malaman, B., see Francois, M. 57-59, 61-65, 71, 73, 74, 78, 80, 85, 86, 88, 99, 103, 105, 106, 110, 112, 115, 117, 121, 123, 125-134, 137, 139-144, 146-150, 153-159, 161, 164, 168-174, 177-181, 186-195 Malaman, B., see Méot-Meyer, M. 53, 60, 68, 93, 106, 126, 135, 144, 148, 151, 165, 170-172, 175, 180, 184, 189, 191, 194, 195 Malaman, B., see Meyer, M. 190, 271, 439, 447 Malaman, B., see Norlidah, M.N. 326 Malaman, B., see Thirion, F. 46, 441, 451 Malaman, B., see Venturini, G. 41-43, 48, 53-55, 57, 58, 60, 62-65, 68, 73, 74, 78, 80, 83, 85, 86, 88, 93, 94, 99, 103, 105, 107, 108, 111-113, 115, 116, 118, 121, 123-126, 128, 129, 131-136, 139-144, 148-152, 155, 156, 161, 163, 164, 166, 170, 171, 173, 175, 178, 180-183, 187, 189-191, 194, 195, 233, 234, 239, 254, 256, 258, 265, 326, 466, 481 Malaman, B., see Welter, R. 59, 60, 62, 66, 68, 73, 81, 86, 91, 93, 105, 111, 286 Malik, S.K. 452 Malik, S.K., see Ghosh, K. 74 Manfrinetti, P., see Palenzona, A. 363, 365, 367, 368, 370, 373, 374, 376 Manfrinetti, P., see Pani, M. 365 Maple, M.B. 460 Maple, M.B., see Gajewski, D.A. 466 Marazza, R., see Contardi, V. 127, 185 Marazza, R., see Rossi, D. 53, 58, 59, 65-67, 76, 79-82, 88, 99, 103-105, 117, 124, 126, 129, 131-133, 142-144, 148-150, 163, 164, 172, 182, 183, 187, 190, 494

- Marazza, R., see Zanicchi, G. 130, 147
- Mareche, J.F., see Méot-Meyer, M. 148, 170–172, 180, 184, 189, 194, 195
- Mareche, J.F., see Venturini, G. 54, 57, 58, 68,
  73, 74, 85, 86, 88, 94, 99, 103, 107, 111, 113,
  115, 126, 128, 129, 131, 136, 139–141, 144,
  148, 152, 155, 156, 166, 170, 178
- Mareche, J.M., see Francois, M. 57, 58, 65, 73, 74, 78, 85, 86, 88, 99, 103, 110, 112, 115, 121, 123, 128, 131, 139–142, 148, 155–157, 161, 169–172, 178–180, 186–189, 194, 195
- Mareche, J.M., see Venturini, G. 48, 57, 129, 131, 140, 141, 157, 161, 175, 179, 180, 187, 256
- Marezio, M., see Hodeau, J.L. 453
- Markiv, V.Ya. 124, 355, 356, 361, 362, 366–369, 389, 390, 393, 394, 396–408, 456, 458
- Markiv, V.Ya., see Belyavina, N.M. 32, 124, 125, 232, 367, 368, 397–399, 401, 404–406
- Markiv, V.Ya., see Bodak, O.I. 354, 355
- Markiv, V.Ya., see Gavrilenko, I.S. 397–400, 402, 404–408
- Markiv, V.Ya., see Gladyshevsky, E.I. 45, 420
- Markiv, V.Ya., see Golovata, N.V. 33
- Markiv, V.Ya., see Grin', Yu.N. 397, 401
- Markiv, V.Ya., see Kuzmenko, P.P. 397–399, 404, 406
- Markiv, V.Ya., see Savitskii, E.M. 397, 401, 402
- Markiv, V.Ya., see Voroshilov, Yu.V. 419, 420
- Marko, M.A. 20, 21
- Markosyan, A.S., see Gratz, E. 500, 501, 509
- Markosyan, A.S., see Kotur, B.Ya. 419, 420, 431, 432, 504–507
- Markova, I.A., see Savitskii, E.M. 352, 361, 362
- Martsenyuk, P.S., see Eremenko, V.N. 358, 359, 372, 373, 376
- Martsenyuk, P.S., see Khorujaya, V.G. 357, 358
- Marusin, E.P. 412
- Marusin, E.P., see Anisimova, E.V. 130
- Marusin, E.P., see Pecharskaya, A.O. 410, 412
- Marusin, E.P., see Tsokol', A.O. 412, 458
- Maslenkov, S.B. 356, 463
- Maslenkov, S.B., see Braslavskaya, G.S. 355, 356
- Massalski, T.B. 343, 348, 349, 351, 361, 431, 470, 481, 482
- Mathon, J. 498
- Mathur, N.D. 253
- Matkovich, M.V. 365
- Mattens, W.C.M., see de Boer, F.R. 349

- Matthias, B.T. 464, 465, 501
- Matthias, B.T., see Compton, V.B. 358, 359, 368
- Matthias, B.T., see Geballe, T.H. 358, 509
- Matthias, B.T., see Krikorian, N.H. 372
- Matthias, B.T., see Ku, H.C. 381, 385, 466, 512
- Matthias, B.T., see Vandenberg, J.M. 464-466
- Mayer, I. 20, 22, 34
- Mayer, I., see Felner, I. 106
- Mazumdar, Z., see Nagarajan, R. 513
- Mazus, M.D., see Pecharskaya, A.O. 410, 412 Mazzone, D., see Rossi, D. 53, 59, 66, 81, 82,
- 105, 124, 133, 143, 149, 163, 164, 182
- Mazzone, D., see Zanicchi, G. 130, 147
- McCall, W.M. 54, 60, 68
- McColm, I.J. 467, 481
- McColm, I.J., see Kotroczo, V. 372, 416, 458,
- 481
- McGuire, T.R., see Holtzberg, F. 38
- McMasters, O.D. 362
- McMasters, O.D., see Gschneidner Jr, K.A. 361
- McMasters, O.D., see Rider, P.E. 363
- McRae, E., see Francois, M. 58, 80, 88, 115, 117, 131, 132, 142, 148, 161, 172, 181
- McRae, E., see Méot-Meyer, M. 148, 170-172, 180, 184, 189, 194, 195
- McRae, E., see Venturini, G. 48, 57, 129, 131, 140, 141, 157, 161, 175, 179, 180, 187
- Meisen, U., see Jeitschko, W. 454, 455
- Meissner, G.P., see Ku, H.C. 381
- Meleshevich, K.A., see Eremenko, V.N. 372, 373, 375
- Meleshevich, K.A., see Lukashenko, G.M. 470
- Men'kov, A.A. 377-379
- Men'kov, A.A., see Komissarova, L.N. 377
- Menshikova, T.S., see Kutaitsev, V.I. 350
- Méot-Meyer, M. 53, 60, 68, 93, 106, 126, 135, 144, 148, 151, 165, 170–172, 175, 180, 184, 189, 191, 194, 195
- Méot-Meyer, M., see Venturini, G. 40, 42–44, 47, 50, 51, 54, 57, 58, 60, 62, 64, 68, 73, 74, 78, 83, 85, 86, 88, 93, 94, 99, 103, 107, 108, 111–113, 115, 118, 121, 123, 126, 128, 129, 131, 135, 136, 139–141, 144, 148, 151, 152, 155–157, 161, 166, 170, 171, 175, 178–180, 183, 187, 189, 191, 194, 195, 256, 258, 439, 440, 445,
- 448
- Merlo, F. 20, 123, 295, 296
- Mewis, A., see Lux, C. 468
- Meyer, M. 190, 271, 439, 447
- Miasnikova, E.A., see Shamrai, V.F. 391

Michel, M., see Beaudry, B.J. 348 Michor, H., see Kotur, B.Ya. 419, 420, 431, 432, 504-507 Miedema, A.R. 348, 468 Miedema, A.R., see de Boer, F.R. 349 Mikhalenko, S.I. 381, 382 Mikhalenko, S.I., see Zavalii, L.V. 379, 381, 382, 384 Mills, D.L. 498 Milos, A., see Bara, J.J. 59, 67, 82, 106, 135, 165 Miner, W.N., see Ellinger, F.H. 350, 351 Mirkovic, J., see Gribanov, A.V. 78-80 Mizuhashi, K., see Cava, R.J. 513 Mizuno, K., see Ito, T. 460 Mokra, I.R. 416-418, 422, 485 Mokra, I.R., see Bodak, O.I. 416, 430, 438 Mokra, I.R., see Fedyna, M.F. 85 Mokra, I.R., see Kotur, B.Ya. 348, 349, 416-418, 423, 424, 438, 442, 444, 480, 482, 485 Mokra, I.R., see Shpyrka, Z.M. 196-199, 202, 437, 438, 442 Mokraya, I.R., see Pecharsky, V.K. 134, 283, 309 Mokraya, I.R., see Starodub, P.K. 136, 299 Mook, H.A., see Maple, M.B. 460 Moriya, T. 498, 502 Morozkin, A.V. 110-113 Mosel, B.D., see Pöttgen, R. 124, 292 Movshovich, R., see Maple, M.B. 460 Mruz, O.Ya. 53, 54, 81, 105-109, 127, 134, 143, 145, 150, 152, 164, 166, 173, 175, 190, 236, 240, 300 Mruz, O.Ya., see Bodak, O.I. 55, 93, 95, 107, 108, 127, 136, 137, 145, 146, 152, 153, 166, 168, 175, 176, 192, 257 Mruz, O.Ya., see Pecharsky, V.K. 53-55, 60, 61, 67, 68, 93, 95, 106, 108, 126, 127, 134, 135, 137, 143, 144, 146, 150, 151, 153, 164, 165, 168, 174, 175, 177, 184, 191, 192 Mruz, O.Ya., see Starodub, P.K. 125 Müller, H., see Gratz, E. 509 Mullmann, R., see Pöttgen, R. 124, 292 Murata, K., see Goto, T. 497 Muratova, L.A. 34, 35, 37, 38, 298, 458 Muratova, L.A., see Bodak, O.I. 35, 36, 416, 430 Muravyeva, A.A. 23-25 Muravyeva, A.A., see Zarechnyuk, O.S. 26-32, 254 Murray, J.L. 351

Myakush, O.R., see Gryniv, I.O. 33, 282, 305 Mydlarz, T., see Bodak, O.I. 419 Mys'kiv, M.G., see Kotur, B.Ya. 420 Nagarajan, R. 513 Nagender Naidu, S.V., see Pandian, S. 353 Nakamichi, T. 507 Nakamura, H. 508 Nakamura, H., see Yoshimura, K. 508 Nakamura, Y. 509 Nakamura, Y., see Nakamura, H. 508 Nakamura, Y., see Oomi, G. 508 Nakamura, Y., see Yoshimura, K. 508 Nakonechna, N.Z. 390, 396 Nalyvaiko, M.S., see Marko, M.A. 20 Narasimhan, K.S.V.L., see McCall, W.M. 54, 60, 68 Naslain, R., see Peshev, P. 365-367 Naumkin, O.P. 347-349, 351, 354, 355, 361, 366, 367, 391 Naumkin, O.P., see Savitskii, E.M. 352, 361, 362 Nayeb-Hashemi, A.A. 346 Neumann, J.P., see Venkatraman, M. 352 Nevitt, M.V., see Dwight, A.E. 462 Niarchos, D., see Cashion, J.D. 510 Nikiforov, V.N., see Gribanov, A.V. 78-80, 234 Nikiforov, V.N., see Seropegin, Yu.D. 187, 188 Nikitina, N.I., see Drits, M.E. 460, 464 Nikitina, N.I., see Sviderskaya, Z.A. 345 Nishihara, Y. 462, 507 Noël, H., see Le Bihan, T. 56, 128, 139, 147, 154, 169, 178, 186, 193 Noga, A.S., see Gryniv, I.O. 32, 279 Noland, B.I., see Berger, R. 378 Nordine, P., see Smith, G. 458 Norlidah, M.N. 326 Norman, M. 358 Norton, L.J., see Darby Jr, J.B. 353 Noto, K., see Ikeda, K. 502 Novik, I., see Felner, I. 117, 119 Nowik, I., see Felner, I. 73, 74, 110 Nowotny, H. 373, 410 Nowotny, H., see Auer-Welsbach, H. 373 Nowotny, H., see Bauer, E. 496 Nowotny, H., see Gangleberger, E. 381 Nowotny, H., see Gratz, E. 500, 505 Nowotny, H., see Hanel, G. 56, 110, 138, 154, 177, 186, 421 Nowotny, H., see Haschke, H. 36 Nowotny, H., see Jedlichka, H. 372, 373

Nowotny, H., see Laube, E. 345, 364, 365 Nowotny, H., see Rogl, P. 381 Nychyporuk, G.P., see Zaremba, V.I. 33, 308 Obidov, F.U., see Altynbaev, R.A. 387 O'Boyle, D.R., see Ellinger, F.H. 350, 351 Obushenko, I.M., see Eremenko, V.N. 373, 375 Odinaev, H.O. 386 Okamoto, H. 350, 375 Okhremchuk, L.N., see Samsonov, G.V. 379 Olcese, G.L., see Iandelli, A. 387 Oleksyn, O.Ya. 53-55, 126, 127, 136, 137, 144-146, 152, 153, 164-168, 175-177, 191-193, 248 Oleksyn, O.Ya., see Bodak, O.I. 250 Oleksyn, O.Ya., see Fedyna, M.F. 144, 151, 191 Olenych, R.R. 42, 43, 448, 488 Oniskovetz, B.D. 118-120, 292 Oomi, G. 508 Opainych, I.M. 32, 71, 72, 236, 298, 325 Ortbauer, H., see Steiner, W. 498 Ott, H.R., see Dommann, A. 80 Ouladdiaf, B., see Lelievre-Berna, E. 460 Pacheco Espejel, J.V., see Kotur, B.Ya. 417, 419 Padalia, B.D., see Nagarajan, R. 513 Palenzona, A. 351, 363, 365, 367, 368, 370, 373, 374, 376 Palenzona, R., see Palenzona, A. 370 Pandian, S. 353 Pani, M. 365 Pani, M., see Fornasini, M.L. 421, 436 Pani, M., see Merlo, F. 20, 123, 295, 296 Pankevich, Yu.V., see Pecharsky, V.K. 455 Parasiuk, O.V., see Kotur, B.Ya. 423, 480 Pardo, M.-P., see Brozek, V. 378 Parthé, E. 48, 62, 327, 367, 378, 440 Parthé, E., see Arbuckle, J. 373 Parthé, E., see Cenzual, K. 57, 86, 170, 285, 357-359 Parthé, E., see Chabot, B. 355, 357-359, 418, 419, 421, 430, 431, 434 Parthé, E., see Engel, N. 47, 48, 51, 266, 421, 440, 441, 491 Parthé, E., see Eymond, S. 367 Parthé, E., see Gladyshevsky, R.E. 57, 62, 74, 75, 86, 99, 113, 129, 140, 158, 160, 170, 179, 194, 277, 307, 324 Parthé, E., see Hovestreydt, E. 47, 48, 51, 52, 57, 58, 63-65, 74, 76, 78, 79, 86-88, 99, 103, 113, 115, 116, 129-131, 140-142, 148, 156, 158,

161, 162, 170-172, 179, 180, 291, 399, 421, 434, 440, 441, 452 Parthé, E., see Jeitschko, W. 374 Parthé, E., see Rieger, W. 55, 56, 60, 61, 70, 71, 84, 85, 95, 96, 108-110, 126-128, 137-139, 146, 147, 153, 154, 168, 169, 177, 185, 186, 193 Parthé, E., see Schob, O. 345, 366, 367, 372, 373 Parthé, E., see Zhao, J.T. 23-32, 258, 263, 294, 301, 315, 327, 418, 420, 430, 433, 458, 459, 468, 485 Parthé, Edda, see Parthé, E. 378 Passamani, E., see Xia, S.R. 504 Pasturel, A., see Colinet, C. 470 Patel, C.K.N., see Matthias, B.T. 464, 465 Pavlyshyn, A.Z., see Kotur, B.Ya. 361 Pavlyuk, V.V. 9-19, 261, 267, 273, 281, 303, 306, 311, 318 Pavlyuk, V.V., see Bodak, O.I. 11, 13, 18, 19, 45, 440 Pavlyuk, V.V., see Dzianii, R.B. 182, 183 Pavlyuk, V.V., see Gribanov, A.V. 76, 79, 234, 244, 319 Pavlyuk, V.V., see Oniskovetz, B.D. 118, 119 Pavlyuk, V.V., see Stetskiv, A.O. 298 Pawlak, L. 456 Pech Jr, W.F., see Siegrist, T. 513 Pecharskaya, A.O. 410, 412, 414 Pecharsky, V.K. 39, 53-55, 60, 61, 63, 67, 68, 78, 93, 95, 106, 108, 126, 127, 134, 135, 137, 143, 144, 146, 150, 151, 153, 164, 165, 168, 174, 175, 177, 184, 191, 192, 283, 289, 309, 316, 321, 418, 430, 455 Pecharsky, V.K., see Anisimova, E.V. 130 Pecharsky, V.K., see Belsky, V.K. 69, 324 Pecharsky, V.K., see Bodak, O.I. 45, 55, 56, 60, 62, 70, 74, 83, 86, 90, 93, 95, 98, 107-109, 111, 126, 127, 136, 137, 144-146, 151-154, 166, 168, 175, 176, 184, 191, 192, 236, 250, 257, 311, 314, 416, 430, 440 Pecharsky, V.K., see Bruskov, V.A. 54, 243, 313, 322 Pecharsky, V.K., see Fedyna, M.F. 127, 152, 153, 168, 176, 185, 192, 230, 255, 283 Pecharsky, V.K., see Ghosh, K. 74 Pecharsky, V.K., see Gladyshevsky, E.I. 327, 392-394, 401, 402, 444, 445, 451, 463 Pecharsky, V.K., see Gorelenko, Yu.K. 54, 56, 107, 127, 136, 137, 144, 146, 152, 153, 166, 168, 175, 177, 185, 192, 193

546

Pecharsky, V.K., see Gribanov, A.V. 76, 79, 244, 264.319 Pecharsky, V.K., see Konyk, M.B. 56, 61, 70, 96, 128, 139, 147, 154, 169, 177, 186, 260 Pecharsky, V.K., see Mruz, O.Ya. 54, 107, 127, 145, 152, 166, 175, 240, 300 Pecharsky, V.K., see Oniskovetz, B.D. 120, 292 Pecharsky, V.K., see Pavlyuk, V.V. 9-14, 19, 261, 273, 281, 303, 306, 318 Pecharsky, V.K., see Salamakha, P.S. 93, 98, 99, 102, 103, 270, 306 Pecharsky, V.K., see Shpyrka, Z.M. 196-199. 202 Pecharsky, V.K., see Sologub, O.L. 159, 161, 162, 246, 290, 317 Pecharsky, V.K., see Starodub, P.K. 136. 299 Pecharsky, V.K., see Yarmolyuk, Ya.P. 262 Peck Jr, W.F., see Cava, R.J. 513 Pelizzone, M., see Vining, C.B. 510-512 Peshev, P. 365-367 Peshev, P.D., see Tsolovski, L.A. 379 Petkov, V.V., see Markiv, V.Ya. 355, 356, 361, 362, 366-368 Petyukh, V.M., see Artyukh, L.V. 410 Petyukh, V.M., see Semenova, O.L. 462 Pierre, J., see Boutarek, N. 298 Pillmayr, N., see Bauer, E. 496 Podchernyaeva, A.I., see Samsonov, G.V. 379 Poddiakonova, E.I., see Sokolovskaya, E.M. 391 Pokrzywnicki, S., see Pawlak, L. 456 Polikha, V.I., see Prevarskii, A.P. 390, 395 Pollmeier, P.G., see Jeitschko, W. 454, 455 Polyakova, V.P., see Savitskii, E.M. 357-359, 408 Polyakova, V.P., see Urvachev, V.P. 409 Pop, V., see Burzo, E. 497, 498 Pöttgen, R. 52, 80, 121, 124, 181, 195, 292, 294, 297, 372, 373, 409-412, 494 Pöttgen, R., see Gibson, B. 58, 114, 115, 130. 141, 147, 159, 171, 179, 188, 195 Pöttgen, R., see Jones, C.D.W. 80 Pöttgen, R., see Schnelle, W. 494-496 Pourarian, F., see Lee, E.W. 497 Preston, R.S., see Dwight, A.E. 392, 393 Prevarskii, A.P. 390, 395 Prokin, E.S. 378 Protasov, V.S. 345 Protasov, V.S., see Gladyshevsky, E.I. 345, 354, 355

Protasov, V.S., see Kripyakevich, P.I. 353, 363, 365 Protasov, V.S., see Teslyuk, M.Yu. 389, 390, 393, 395 Prots', Yu.M., see Salamakha, P.S. 89-91 Prots', Yu.M., see Sologub, O.L. 155, 156, 159, 161, 162, 246, 290, 317 Protsyk, A.S. 58, 63, 77, 78, 87, 114, 115, 122, 123, 141, 194, 195 Protsyk, A.S., see Pecharsky, V.K. 63, 78, 289 Protsyk, A.S., see Sologub, O.L. 159, 291 Protsyk, A.S., see Zaplatynsky, O.V. 99, 100 Przybylska, M. 365 Radwanski, R.J., see Franse, J.J.M. 503 Raevskaya, M.B. 389, 393 Raevskaya, M.V., see Karatygina, E.P. 389, 393, 394 Rama Rao, P., see Pandian, S. 353 Ramakrishnan, S. 466 Ramakrishnan, S., see Dhar, S.K. 460, 466 Ramakrishnan, S., see Ghosh, K. 74 Raman, A. 24-26 Rambaldi, G., see Zanicchi, G. 130, 147 Ratush, G.M., see Kotur, B.Ya. 426 Rebko, R.I., see Koshel', O.S. 460 Rechkin, V.N. 367 Reddoch, A.H., see Przybylska, M. 365 Reichl, Ch., see Kotur, B.Ya. 419, 420, 431, 432, 504-507 Reinbold, E.J. 454, 455 Reinbold, E.J., see Jeitschko, W. 454, 455 Resel, R., see Gratz, E. 500, 501 Ressouche, E., see Welter, R. 59, 60, 62, 66, 68, 73, 81, 86, 91, 93, 105, 111, 286 Reule, H. 362 Rhodes, P. 501 Rhyne, J.J. 503 Riabov, V.R., see Zalutska, O.I. 388, 389 Riabov, V.R., see Zarechnyuk, O.S. 389, 392 Riabtsev, L.A., see Shamrai, V.F. 391 Rice, M.J., see Schindler, A.L. 498 Rider, P.E. 363 Rieger, W. 55, 56, 60, 61, 70, 71, 84, 85, 95, 96, 108-110, 126-128, 137-139, 146, 147, 153, 154, 168, 169, 177, 185, 186, 193, 279 Rinderer, L., see Braun, H.F. 421, 433 Rinderer, L., see Ku, H.C. 381, 385, 466, 512 Ritter, G.J., see Przybylska, M. 365 Rizzo-Assuncao, F.C., see Xia, S.R. 504

Rodrigues, V.A., see Xia, S.R. 504

- Rogl, P. 79, 381, 385, 416, 430, 433
- Rogl, P., see Bodak, O.I. 11, 13, 18, 19
- Rogl, P., see Le Bihan, T. 56, 128, 139, 147, 154, 169, 178, 186, 193
- Rogl, P., see Sologub, O.L. 57, 58, 63, 71, 77, 78, 80, 85–89, 99, 103, 104, 110, 114–117, 129, 130, 132, 140, 142, 148, 162, 171, 172, 179, 180, 187, 190
- Rogl, P., see Weitzer, F. 60, 82, 92
- Rokhlin, L.L., see Drits, M.E. 460
- Roques, B., see Francois, M. 57–59, 61–65, 71, 73, 74, 78, 80, 85, 86, 88, 99, 103, 105, 106, 110, 112, 115, 117, 121, 123, 125–134, 137, 139–144, 146–150, 153–159, 161, 164, 168–174, 177–181, 186–195
- Roques, B., see Malaman, B. 327, 452, 453
- Roques, B., see Méot-Meyer, M. 53, 60, 68, 93, 106, 126, 135, 144, 148, 151, 165, 170–172, 175, 180, 184, 189, 191, 194, 195
- Roques, B., see Meyer, M. 190, 271, 439, 447
- Roques, B., see Venturini, G. 40, 42–44, 47, 48, 50, 51, 54, 57, 58, 60, 62, 64, 65, 68, 73, 74, 78, 80, 83, 85, 86, 88, 93, 94, 99, 103, 107, 108, 111–113, 115, 116, 118, 121, 123, 126, 128, 129, 131, 135, 136, 139–142, 144, 148, 151, 152, 155–157, 161, 166, 170, 171, 175, 178–180, 183, 187, 189, 191, 194, 195, 254, 256, 258, 326, 439, 440, 445, 448, 466, 481
- Rosen, S. 458
- Rosen, S., see Goebel, S. 355, 356, 389, 393
- Rosenberg, H., see Braun, H.F. 510
- Roshan, N.R., see Savitskii, E.M. 357, 359
- Rossi, D. 53, 58, 59, 61, 65–67, 72, 76, 79–82, 85, 88, 96, 99, 103–105, 110, 117, 124, 126, 129, 131–133, 142–144, 148–150, 163, 164, 172, 182, 183, 187, 190, 494
- Rossi, D., see Contardi, V. 127, 185
- Rossi, D., see Zanicchi, G. 130, 147
- Rusetskaya, N.Yu., see Semenova, O.L. 462
- Ryabokon', T.I. 26-28
- Rybakov, V.B., see Bodak, O.I. 74, 311
- Rykhal, R.M., see Zarechnyuk, O.S. 389, 393
- Sabirzyanov, N.A. 368, 370
  Saillard, J.Y., see Halet, J.F. 458
  Sakakibara, T., see Goto, T. 497
  Sakurai, J., see Nakamura, H. 508
  Salamakha, P.S. 66, 67, 69–71, 75, 89–104, 149, 150, 157, 163, 185, 227, 228, 252, 269, 270, 287, 302, 304, 306

- Salamakha, P.S., see Bodak, O.I. 55, 62, 86, 90, 93, 95, 98, 107, 108, 111, 127, 136, 137, 145, 146, 152, 153, 166, 168, 175, 176, 192, 236, 257
- Salamakha, P.S., see Gladyshevsky, R.E. 277
- Salamakha, P.S., see Gribanov, A.V. 76, 79, 244, 264, 319
- Salamakha, P.S., see Konyk, M.B. 56, 61, 70, 96, 128, 139, 147, 154, 169, 177, 186, 260
- Salamakha, P.S., see Pecharsky, V.K. 53–55, 60,
  61, 67, 68, 93, 95, 106, 108, 126, 127, 134, 135,
  137, 143, 144, 146, 150, 151, 153, 164, 165,
  168, 174, 175, 177, 184, 191, 192
- Salamakha, P.S., see Shapiev, B.I. 75, 274
- Salamakha, P.S., see Sologub, O.L. 155, 156, 159, 161, 162, 246, 289, 290, 317, 326
- Salamakha, P.S., see Zaplatynsky, O.V. 99, 100
- Samsonov, G.V. 379
- Sankar, S.G. 393, 504, 505
- Savitskii, E.M. 351–353, 357–359, 361, 362, 397, 401, 402, 408, 462, 463
- Savitskii, E.M., see Arskaya, E.P. 463
- Savitskii, E.M., see Naumkin, O.P. 347–349, 351, 354, 355, 361, 366, 367, 391
- Savitskii, E.M., see Rechkin, V.N. 367
- Savitskii, E.M., see Urvachev, V.P. 409
- Savysyuk, I.A. 87
- Schablaske, R.V. 365
- Schauerte, W., see Czybulka, A. 12, 13, 15, 16
- Schieber, M., see Felner, I. 59, 92, 106
- Schindler, A.L. 498
- Schnelle, W. 494-496
- Schnelle, W., see Pöttgen, R. 124, 292
- Schob, O. 345, 366, 367, 372, 373
- Schob, O., see Parthé, E. 367
- Schöbinger-Papamantellos, P. 231
- Schuster, H.-U. 10
- Schuster, H.-U., see Buchholz, W. 44, 45, 54, 126, 136, 144, 152, 165, 175, 183, 231, 233, 439, 440, 448
- Schuster, H.-U., see Czybulka, A. 9, 10, 12-16
- Schuster, H.-U., see Eberz, U. 452, 454
- Schuster, H.-U., see Grund, I. 11, 15, 18
- Schuster, J.C. 366, 367, 393
- Schuster, J.K., see Bodak, O.I. 11, 13, 18, 19
- Seaman, C.L., see Gajewski, D.A. 466
- Seaman, C.L., see Maple, M.B. 460
- Seelentag, W., see Eberz, U. 452, 454
- Segre, C.U. 57, 58, 74, 78, 86, 87, 98, 102, 111, 115, 123, 128, 131, 139, 141, 148, 155, 160, 170, 171, 178, 180, 187, 189, 194, 195, 242

Segre, C.U., see Braun, H.F. 421, 467, 510 Semenenko, K.N., see Burnashova, V.V. 468 Semenov, B.G., see Yatsenko, S.P. 367-369 Semenova, O.L. 462 Semenyshyn, O.E., see Kotur, B.Ya. 417 Semvannikov, A.A., see Yatsenko, S.P. 367-370 Senateur, J.-P., see Ghetta, V.P. 455 Seropegin, Yu.D. 187, 188 Seropegin, Yu.D., see Gribanov, A.V. 76-80, 234, 235, 244, 264, 319 Seropegin, Yu.D., see Morozkin, A.V. 110-113 Seropegin, Yu.D., see Shapiev, B.I. 75, 274 Shakarov, H.O., see Yatsenko, S.P. 367-370 Shamrai, V.F. 391 Shapiev, B.I. 72-75, 274 Shcherba, I.D., see Kotur, B.Ya. 417, 419, 420, 422 Shelton, R.N. 381 Shelton, R.N., see Johnson, M.J. 452 Shelton, R.N., see Vining, C.B. 510-512 Shenoy, G.K., see Cashion, J.D. 510 Shenoy, G.K., see Malik, S.K. 452 Sherwood, R.C., see Matthias, B.T. 501 Shestakov, V.P., see Markiv, V.Ya. 367, 368, 456, 458 Shevchuk, M.M., see Bodak, O.I. 416, 430 Shidlowsky, I., see Mayer, I. 34 Shieh, J.H., see Ku, H.C. 467, 513 Shiga, M. 508, 509 Shiga, M., see Nakamura, H. 508 Shiga, M., see Nakamura, Y. 509 Shiga, M., see Oomi, G. 508 Shiga, M., see Yoshimura, K. 508 Shonfeld, F.W., see Ellinger, F.H. 350, 351 Shpyrka, Z.M. 196-204, 260, 287, 320, 437, 438, 441, 442 Shpyrka, Z.M., see Bodak, O.I. 438 Shpyrka, Z.M., see Gladyshevsky, E.I. 390, 395 Shpyrka, Z.M., see Nakonechna, N.Z. 390, 396 Shpyrka, Z.M., see Stetskiv, L.V. 201 Sichevich, O.M., see Opainych, I.M. 32, 325 Sidorko, V.R., see Lukashenko, G.M. 470 Siegrist, T. 513 Siegrist, T., see Cava, R.J. 513 Sikirica, M., see Kotur, B.Ya. 40, 45, 417-421, 426, 431-433, 436, 440, 444, 480, 487 Siman, N.I., see Samsonov, G.V. 379 Simanov, Yu.P., see Men'kov, A.A. 377-379 Simon, A., see Gibson, B. 58, 114, 115, 130, 141, 147, 159, 171, 179, 188, 195

Simon, A., see Pöttgen, R. 52, 80, 181, 195, 494 Sinyakova, S.U., see Terekhov, G.I. 349 Skolozdra, R.V., see Bodak, O.I. 126, 136, 144, 151, 166, 175, 184, 191 Skolozdra, R.V., see Gorelenko, Yu.K. 54, 56, 107, 127, 136, 137, 144, 146, 152, 153, 166, 168, 175, 177, 185, 192, 193 Skolozdra, R.V., see Mruz, O.Ya. 109 Skripka, A.I., see Belyavina, N.M. 401 Skripka, A.I., see Markiv, V.Ya. 397, 400 Skvorchuk, V.P., see Gladyshevsky, E.I. 418, 419, 431, 506 Smidt-Fetzer, R., see Bodak, O.I. 11, 13, 18, 19 Smirnova, E.M., see Zhuravlev, N.N. 378 Smit, P.H. 504 Smit, P.H., see Grössinger, R. 504 Smith, G. 458 Smith, J.F. 352 Smith, R.T., see Yim, W.M. 378, 459 Smith, T.F., see Gardner, W.E. 369 Sobolev, A.N., see Mruz, O.Ya. 240 Sobolev, A.N., see Pavlyuk, V.V. 19, 306 Sobolev, O.I., see Pavlyuk, V.V. 18, 19, 273 Sokolovskaya, E.M. 391 Sokolovskaya, E.M., see Cheldieva, G.M. 391 Sokolovskaya, E.M., see Karatygina, E.P. 389. 393, 394 Sokolovskaya, E.M., see Raevskaya, M.B. 389, 393 Sologub, O.L. 57, 58, 63, 71, 77, 78, 80, 85-89, 99, 103, 104, 110, 114-117, 129, 130, 132, 140, 142, 148, 155-163, 171, 172, 179, 180, 187, 190, 246, 267, 289-291, 317, 326 Sologub, O.L., see Bodak, O.I. 74, 157, 160, 311 Sologub, O.L., see Gladyshevsky, R.E. 158, 160, 277, 307 Sologub, O.L., see Gribanov, A.V. 76, 79, 244, 264.319 Sologub, O.L., see Salamakha, P.S. 66, 67, 69-71, 75, 89-92, 94, 95, 98-102, 149, 150, 157, 163, 185, 227, 228, 304 Sologub, O.L., see Shapiev, B.I. 75, 274 Sologub, O.L., see Zaplatynsky, O.V. 99, 100 Souleau, O., see Guittard, M. 456, 476 Spear, K.E. 365-367 Speca, M.V., see Belyavina, N.M. 32 Spedding, F.H., see Beaudry, B.J. 348 Sperlich, G., see Jansen, K. 454

Sprang, P.G., see Rosen, S. 458 Stapf, I. 361, 362 Starodub, P.K. 125, 132-136, 138, 139, 299 Starodub, P.K., see Bodak, O.I. 93, 107, 127, 136, 145, 152, 166, 175, 192 Starodub, P.K., see Fedyna, M.F. 127, 152, 153, 168, 176, 185, 192 Starodub, P.K., see Gorelenko, Yu.K. 54, 56, 107, 127, 136, 137, 144, 146, 152, 153, 166, 168, 175, 177, 185, 192, 193 Starodub, P.K., see Koterlyn, G.M. 54, 56, 136, 137, 145, 146 Starodub, P.K., see Mruz, O.Ya. 53, 81, 106, 134, 143, 150, 164, 173, 190 Starodub, P.K., see Pecharsky, V.K. 53-55, 60, 61, 67, 68, 93, 95, 106, 108, 126, 127, 134, 135, 137, 143, 144, 146, 150, 151, 153, 164, 165, 168, 174, 175, 177, 184, 191, 192, 283, 309 Starodub, P.K., see Salamakha, P.S. 96, 100 Stash, A., see Salamakha, P.S. 149, 150, 304 Steeb, S., see Reule, H. 362 Steele, R.M., see Cavin, O.B. 349 Steinberg, G., see Czybulka, A. 9, 14 Steiner, W. 498 Steinfink, H., see Raman, A. 24-26 Steinmetz, J., see Meyer, M. 190, 271, 439, 447 Steinmetz, J., see Thirion, F. 46, 441, 451 Stepanchikova, G.F. 381, 383, 384 Stepanova, A.A., see Zhuravlev, N.N. 367 Stepień-Damm, J., see Bodak, O.I. 419 Stepień-Damm, J., see Salamakha, P.S. 98, 101, 102, 149, 150, 304 Stepień-Damm, J., see Sologub, O.L. 155, 156 Stepień-Damm, J., see Zaremba, V.1. 33, 308 Stetskiv, A.O. 268, 285, 298, 305, 323 Stetskiv, L.V. 201 Stofko, E.J., see Yim, W.M. 378, 459 Storozhenko, A.I., see Markiv, V.Ya. 389, 390, 393, 394, 399, 407 Stroganova, V.F., see Savitskii, E.M. 352, 361, 362 Stusser, N., see Baran, S. 288 Subramanian, P.R. 361 Suski, W., see Bodak, O.I. 419 Svechnikov, V.M. 352 Sviderskaya, Z.A. 345 Sviderskaya, Z.S., see Drits, M.E. 460, 464 Sweedler, A., see Gardner, W.E. 369 Szklarz, E.G., see Krikorian, N.H. 372

Spitsyn, V.I., see Men'kov, A.A. 377-379

Szklarz, E.G., see Krupka, M.C. 409 Szytuła, A. 152 Szytuła, A., see Bara, J.J. 59, 67, 82, 106, 135, 165 Szytuła, A., see Baran, S. 288 Szytuła, A., see Duraj, M. 326 Takagi, H., see Cava, R.J. 513 Takeuchi, A.Y., see Xia, S.R. 504 Takigawa, H., see Yoshimura, K. 508 Taneja, S.P., see Dwight, A.E. 392, 393 Tani, B.S., see Schablaske, R.V. 365 Taylor, A. 352 Terada, T., see Oomi, G. 508 Terbuchte, L.J., see Jeitschko, W. 454, 455 Terekhov, G.I. 349 Terekhova, V.F., see Naumkin, O.P. 347-349, 351, 354, 355, 361, 366, 367, 391 Terekhova, V.F., see Rechkin, V.N. 367 Terekhova, V.F., see Savitskii, E.M. 352, 361, 362 Tergenius, L.E., see Berger, R. 378 Teslyuk, M.Yu. 389, 390, 393, 395 Thirion, F. 46, 441, 451 Tholence, J.L., see Verniere, A. 57, 58, 65, 75, 78, 86, 88, 99, 103, 113, 115, 129, 131, 140, 142, 148, 170, 172, 179, 180, 194 Tomkowicz, Z., see Baran, S. 288 Toporinskii, A.Ya., see Kotur, B.Ya. 348, 417, 418, 423 Torchiniva, R.S., see Savitskii, E.M. 352, 361, 362 Toropova, L.S. 390, 395, 458 Toropova, L.S., see Drits, M.E. 392 Trofimova, L.N., see Berezina, A.L. 386 Trubniakova, E.D. 387 Tschetter, M.J., see Dennison, D.H. 352 Tsokol', A.O. 412, 458 Tsokol', A.O., see Marusin, E.P. 412 Tsolovski, L.A. 379 Turkina, A.I. 386 Turkina, N.I., see Drits, M.E. 366 Tylkina, M.A., see Arskaya, E.P. 463 Tylkina, M.A., see Savitskii, E.M. 353, 463 Tyvanchuk, A.T. 458, 485 Tyvanchuk, A.T., see Kotur, B.Ya. 390, 425, 426 Tyvanchuk, A.T., see Toropova, L.S. 390 Tyvanchuk, Yu.B., see Zaremba, V.I. 33, 308 Uchida, U., see Cava, R.J. 513

Umarji, A.M., see Malik, S.K. 452 Urvachev, V.P. 409 Urvachev, V.P., see Savitskii, E.M. 408 Vagizov, F.G., see Bodak, O.I. 419 Vahobov, A.V., see Altynbaev, R.A. 347, 387 Vahobov, A.V., see Odinaev, H.O. 386 Vahobov, A.V., see Trubniakova, E.D. 387 van Dover, R.B., see Cava, R.J. 513 Vandenberg, J.M. 464-466 Vandenberg, J.M., see Matthias, B.T. 464, 465 Vanderbilt, D. 469 Vasil'eva, L.M., see Komissarova, L.N. 377 Vedernikov, M.V., see Gratz, E. 505 Velikanova, T.Ya. 410, 411 Velikanova, T.Ya., see Artyukh, L.V. 410, 412 Velikanova, T.Ya., see Eremenko, V.N. 411, 463 Velikanova, T.Ya., see Gordijchuk, O.V. 371 Velikanova, T.Ya., see Ilyenko, S.M. 410 Velikanova, T.Ya., see Semenova, O.L. 462 Velikhovskii, A.A., see Gribanov, A.V. 78-80, 234 Venkatraman, M. 352 Venteicher, R.F., see Gschneidner Jr, K.A. 361 Venteicher, R.F., see McMasters, O.D. 362 Venturini, G. 40-44, 47, 48, 50, 51, 53-55, 57, 58, 60, 62-65, 68, 73, 74, 78, 80, 83, 85, 86, 88, 93, 94, 99, 103, 105, 107, 108, 111-113, 115, 116, 118, 121, 123-126, 128, 129, 131-136, 139-144, 148-152, 155-157, 161, 163, 164, 166, 170, 171, 173, 175, 178-183, 187, 189-191, 194, 195, 233, 234, 239, 254, 256, 258, 265, 325, 326, 439, 440, 445, 448, 466, 481 Venturini, G., see Francois, M. 57-59, 61-65, 71, 73, 74, 78, 80, 85, 86, 88, 99, 103, 105, 106, 110, 112, 115, 117, 121, 123, 125-134, 137, 139-144, 146-150, 153-159, 161, 164, 168-174, 177-181, 186-195 Venturini, G., see Malaman, B. 327, 452, 453 Venturini, G., see Méot-Meyer, M. 53, 60, 68, 93, 106, 126, 135, 144, 148, 151, 165, 170-172, 175, 180, 184, 189, 191, 194, 195 Venturini, G., see Meyer, M. 190, 271, 439, 447 Venturini, G., see Norlidah, M.N. 326 Venturini, G., see Welter, R. 59, 60, 62, 66, 68, 73, 81, 86, 91, 93, 105, 111, 286 Vereshchak, V.M., see Semenova, O.L. 462 Verniere, A. 57, 58, 65, 75, 78, 86, 88, 99, 103, 113, 115, 129, 131, 140, 142, 148, 170, 172,

179, 180, 194

Viccaro, P.J., see Cashion, J.D. 510 Vijayaraghavan, R., see Nagarajan, R. 513 Villars, P. 343, 468, 478, 480, 483 Vining, C.B. 510–512 Vivchar, O.I., see Zarechnyuk, O.S. 389, 392 Vogt, O., see Hulliger, F. 456, 476 Volkov, V.A., see Berezina, A.L. 386 Vomhof, T., see Jeitschko, W. 454, 455 Voroshilov, Yu.V. 419, 420 Voroshilov, Yu.V., see Kuz'ma, Yu.B. 381 Vozniak, O.M., see Kotur, B.Ya. 50, 312, 353, 418, 428, 447 Vytvitska, G.M., see Bodak, O.I. 55, 95, 108, 127, 137, 146, 153, 168, 176, 192, 257 Wada, H., see Nakamura, H. 508 Wallace, W.E., see Sankar, S.G. 393, 504, 505 Weber, L., see Dwight, A.E. 392, 393 Weitzer, F. 60, 82, 92 Welter, R. 59, 60, 62, 66, 68, 73, 81, 86, 91, 93, 105, 111, 286 Welter, R., see Venturini, G. 41-43, 53, 105, 124, 125, 132, 134, 143, 149, 150, 163, 164, 173, 181, 182, 190, 191, 233, 234 Wenski, G., see Lux, C. 468 White, J.G. 377, 378, 476 White, J.G., see Dismukes, J.P. 378, 459 Wiesinger, G., see Grössinger, R. 504 Wiesinger, G., see Hauser, R. 508 Wiesinger, G., see Kotur, B.Ya. 419, 420, 431, 432, 504-507 Williams, H.J., see Matthias, B.T. 501 Witte, A.M., see Pöttgen, R. 410, 412 Wochowski, K., see Bodak, O.I. 419 Wohlfarth, E.P. 501, 502 Wohlfarth, E.P., see Rhodes, P. 501 Wolf, W.P., see Lea, K.R. 496 Wolpl, T., see Block, H. 455, 456 Woods, S.B., see Kadowaki, K. 501 Xia, S.R. 504 Yakel, H.L., see Cavin, O.B. 349 Yamaguchi, Y., see Nishihara, Y. 462, 507 Yanson, T.I. 23, 24, 29–31, 293 Yanson, T.I., see Tyvanchuk, A.T. 458, 485

- Yanson, T.I., see Zarechnyuk, O.S. 28, 29
- Yarmolyuk, Ya.P. 262, 419, 431
- Yarmolyuk, Ya.P., see Grin', Yu.N. 397, 401
- Yarmolyuk, Ya.P., see Olenych, R.R. 42, 43, 448, 488

Yarovets, V.I., see Bodak, O.I. 419, 510 Yarovetz, V.I., see Gorelenko, Yu.K. 54, 56, 107, 127, 136, 137, 144, 146, 152, 153, 166, 168, 175, 177, 185, 192, 193 Yartys', V.A., see Burnashova, V.V. 468 Yasuoka, H., see Yoshimura, K. 508 Yatsenko, S.P. 367-370 Yelon, W.B., see Ghosh, K. 74 Yim, W.M. 378, 459 Yoshimura, K. 508 Yoshimura, K., see Nakamura, H. 508 Yoshizawa, M., see Ikeda, K. 497, 498 You, Y.B., see Ku, H.C. 467, 513 Yvon, K., see Braun, H.F. 58, 419, 421, 432, 491 Yvon, K., see Chabot, B. 421 Yvon, K., see Kotur, B.Ya. 419, 438, 444, 485 Yvon, K., see Segre, C.U. 57, 58, 74, 78, 86, 87, 98, 102, 111, 115, 123, 128, 131, 139, 141, 148, 155, 160, 170, 171, 178, 180, 187, 189, 194, 195, 242 Zalutska, O.I. 388, 389 Zalutskii, I.I. 367 Zalutskii, I.I., see Zalutska, O.I. 388, 389 Zandbergen, H.W., see Cava, R.J. 513 Zandbergen, H.W., see Siegrist, T. 513 Zanicchi, G. 130, 147

- Zaplatynsky, O.V. 99, 100
- Zaplatynsky, O.V., see Salamakha, P.S. 95, 99, 100
- Zapotots'ka, L.M., see Starodub, P.K. 132, 133
- Zarechnyuk, O.S. 26-32, 254, 389, 392, 393
- Zarechnyuk, O.S., see Muravyeva, A.A. 23-25

Zarechnyuk, O.S., see Prevarskii, A.P. 390, 395 Zarechnyuk, O.S., see Tyvanchuk, A.T. 458, 485 Zaremba, V.I. 33, 308, 409 Zavalii, L.V. 379, 381, 382, 384 Zavalii, L.V., see Bruskov, V.A. 366, 367 Zavalii, L.V., see Kuz'ma, Yu.B. 381 Zavalii, L.V., see Mikhalenko, S.I. 381, 382 Zavalii, P.Yu., see Bodak, O.I. 160 Zavodnik, V.E., see Andrusyak, R.I. 363, 365, 486 Zavodnik, V.E., see Bodak, O.I. 55, 95, 108, 127, 137, 146, 153, 160, 168, 176, 192, 257 Zavodnik, V.E., see Fedyna, M.F. 191 Zavodnik, V.E., see Kotur, B.Ya. 40, 41, 300, 354, 355, 418, 438-440, 450, 485 Zavodnik, V.E., see Mruz, O.Ya. 106, 107 Zavodnik, V.E., see Pavlyuk, V.V. 9, 14, 16, 18, 19, 311 Zavodnik, V.E., see Yarmolyuk, Ya.P. 262 Zhao, J.T. 23-32, 258, 263, 294, 301, 315, 327, 418, 420, 430, 433, 458, 459, 468, 485 Zhao, J.T., see Gladyshevsky, R.E. 57, 62, 74, 75, 86, 99, 113, 129, 140, 170, 179, 194, 324 Zhunkivska, T.G., see Markiv, V.Ya. 367, 368, 396, 397 Zhuravlev, N.N. 367, 378 Ziebeck, K., see Gibson, B. 58, 114, 115, 130, 141, 147, 159, 171, 179, 188, 195 Ziman, J.M. 499-501 Zmii, O.F. 20, 241 Zvolinskii, O.I., see Savitskii, E.M. 401, 462 Zwiener, G., see Grund, I. 11, 15, 18

Zygmunt, A., see Baran, S. 288

## SUBJECT INDEX

addition of atoms 483 atomic coordination 476 atomic size factor 479, 483 binary compounds 471, 473 - compositions 482 - intervals of stoichiometries 472, 473 - most common compositions 470 - polymorphic modifications 472 - stoichiometries 471 -- ScE 471  $- - ScE_{1.74}$  471  $- - ScE_2 - 471$  $--ScE_{3}$  471  $- - ScE_4 - 471$  $- - ScE_5$ 471  $--ScE_{7}$  471  $- - ScE_{12}$  471  $- - ScE_{13} - 471$  $- - Sc_2E - 472$  $--Sc_2E_3$  471  $- - Sc_2 E_7 = 471$  $- - Sc_3E - 472$  $- - Sc_3E_2 - 472$  $- - Sc_3E_4$ 471  $- - Sc_3E_5$ 471  $- - Sc_3E_{17} - 471$  $- - Sc_4E_3$ 472  $- - Sc_5E_3$ 472  $- - Sc_5E_4$ 472  $- - Sc_5E_{24}$ 471  $- - Sc_6E_5$ 471  $- - Sc_7E_3$ 472  $- - Sc_{11}E_4 - 472$  $- - Sc_{11}E_{10}$ 471 471  $- - Sc_{13}E_{58}$  $- - Sc_{29}E_6$ 472  $- - Sc_{44}E_7 - 472$  $- - Sc_{57}E_{13} - 472$ - structure types 470, 471, 482 -- AlB₂ 471

 $- - Al_2Cu 472$ --- αMn 471 - - AuCu 471 -- AuCu₃ 471  $- - \beta Y b_5 S b_3 = 472$ - - CaCu₅ 471 - - Ce₂Ni₇ 471  $- - Co_2 Si 472$ – – CrB 471  $- - Cr_3C_2$  472 - - CsCl 471, 472  $- - Cu_2Sb 472$ – – Fe₃C 472 - - Gd₁₃Cd₅₈ 471  $- - Gd_3Ga_2$  472  $- - Ho_{11}Ge_{10}$  471, 472 - - KHg₂ 471 - - MgCu₂ 471 - - MgNi₂ 471  $- - Mg_{44}Rh_7 472$ - - MgZn₂ 471 - - Mn₅Si₃ 472 -- MoNi₄ 471 - - MoSi₂ 471 - - NaCl 471 - - NaZn₁₃ 471 - - NiAs 471  $- - Ni_2 In 472$ - - Ni₃Sn 472  $- - Pu_3Pd_5 = 471$  $- - Ru_3Be_{17} - 471$  $- - S_3Sb_2 - 472$  $- - Sc_7 As_3 = 472$  $- - Sc_3C_4 - 471$ - - ScCd₇ 471  $- - Sc_3Co - 472$  $- - Sc_{29}Fe_6 = 472$  $- - Sc_{11}Ir_4 - 472$  $- - Sc_{57}Rh_{13}$  472  $- - Sc_2S_3 = 471$ 

-- ScSn₂ 471

binary compounds - structure types (cont'd)  $--Sm_{5}Ge_{4}$  472 -- SnNi₃ 471  $- - \text{Th}_7\text{Fe}_3 = 472$  $- - ThMn_{12} - 471$  $- - Th_3P_4 = 472$  $- - Ti_5Ga_4$  472 - - Ti₆Ge₅ 471  $- - Ti_2Ni - 472$  $- - Ti_7S_{12} - 471$ - - Tm₃Ga₅ 471  $- - UB_{12} 471$  $- - V_3As_2 = 472$ - - ZrGa₂ 471  $- - ZrSi_2 = 471$ binary phase diagrams of scandium 343-379 - predictions 470 regularities in 469–473 - types 469 CN (coordination number) 490 CP (coordination polyhedron) 490, 491 - cubooctahedron 490, 491 - icosahedron 490, 491 - octahedron 490, 491 - tetragonal antiprism 490, 491 - tetrahedron 490 - trigonal prism 490, 491 characteristic cross-sections 489 -M: X = 1:1 487 -R:M=1:1 487 - Sc : M = 1 : 2 487 - Sc : Mn(Fe) = 1 : 6 488 - Sc : X = 1 : 1 486 close-packed structures 485, 493 Co magnetic moment 497 crystal chemistry scandium compounds 479–493 - ternary R-Ge compounds 227-325 crystal structures (see also phase equilibrium and crystal structures) - binary scandium compounds 343-379 - quaternary and higher-order scandium compounds 464-468 - ternary R-Ge compounds 8-204, 227-335 - ternary scandium compounds 379-464 enhanced paramagnets 497 Fe magnetic moment 503, 504, 506, 508, 510

homeotypic rows 483 homological series of structures 486, 488 hybrid structures 486 - linear 488, 489 - one-dimensional 483 - three-dimensional 483 - two-dimensional 483, 486, 487, 491 hydrides 481 immiscibility gaps 470 Kadowaki-Woods plot 501 LaAl₂ 497 LaAuGe 495 - density of states 495 lanthanides (diluted), crystal field parameters 496, 497 LuAl₂, lanthanides diluted in 496 LuAuGe 495 density of states 495 Lu₂Fe₃Si₅ 511 - specific heat 511 Mn magnetic moment 508 Mn₅Si₃, projection of structure 480 multiple substitution of atoms 483, 485, 488 ordered substitution of atoms 483 perovskite-type ternary compounds 480 phase equilibrium and crystal structures - Ce-Ag-Ge 77 - Ce-Al-Ge 25 - Ce-Au-Ge 80 – Ce–B–Ge 21 - Ce--Co--Ge 67 - Ce--Cu--Ge 69 - Ce-Dy-Ge 202 - Ce-Er-Ge 203 – Ce-Fe-Ge 66 - Ce-Ga-Ge 32 - Ce-Gd-Ge 202 - Ce-Ho-Ge 202 - Ce-Ir-Ge 78 - Ce-Li-Ge 9 - Ce-Lu-Ge 203 - Ce-Mn-Ge 65 – Ce–Ni–Ge 69 – Ce–Os–Ge 78

- Ce--Pd--Ge 75 - Ce-Pt-Ge 78 - Ce-Rh-Ge 74 - Ce-Ru-Ge 72 - Ce-Si-Ge 36 - Ce--Tm--Ge 203 – Ce–Zn–Ge 71 - Dy-Ag-Ge 147 - Dy-Al-Ge 29 - Dy-Au-Ge 149 – Dy-B-Ge 22 - Dy-Co-Ge 144 - Dy-Cr-Ge 143 - Dy-Cu-Ge 146 - Dy-Fe-Ge 143 - Dy-Ho-Ge 204 - Dy-Li-Ge 15 - Dy-Mn-Ge 143 – Dy-Mo-Ge 147 - Dy-Nb-Ge 147 - Dy-Ni-Ge 145 - Dy-Os(Ir, Pt)-Ge 147 - Dy-Ru(Rh, Pd)-Ge 147 - Er-Ag-Ge 171 - Er-Al-Ge 30 - Er-Au-Ge 172 - Er-Co-Ge 165 - Er--Cr--Ge 163 - Er--Cu--Ge 169 - Er-Fe-Ge 164 - Er-Ir-Ge 171 - Er--Li--Ge 16 - Er-Mn-Ge 163 - Er--Mo--Ge 169 - Er-Nb-Ge 169 – Er–Ni–Ge 167 - Er-Os-Ge 171 - Er-Pd-Ge 170 - Er-Pt-Ge 172 - Er-Rh-Ge 170 - Er--Ru--Ge 169 - Er-Tm-Ge 204 - Eu-Ag-Ge 122 - Eu-Al-Ge 27 - Eu-Au-Ge 124 - Eu-Co-Ge 118 - Eu--Cu--Ge 120 - Eu-Fe-Ge 118 - Eu-Ir-Ge 123 - Eu-Li-Ge 14

- Eu-Mg-Ge 20 – Eu–Mn–Ge 117 - Eu-Ni-Ge 119 - Eu-Os-Ge 123 - Eu-Pd-Ge 121 - Eu-Pt-Ge 123 – Eu--Rh--Ge 121 - Eu-Ru-Ge 121 – Eu–Zn–Ge 121 - Gd-Ag-Ge 130 - Gd-Al-Ge 28 - Gd-Au-Ge 132 - Gd-B-Ge 22 - Gd-Co-Ge 126 - Gd--Cu--Ge 128 - Gd-Fe-Ge 125 - Gd-Ga-Ge 33 - Gd-Ir-Ge 131 - Gd-Li-Ge 14 - Gd-Mn-Ge 124 - Gd-Nb-Ge 128 - Gd-Ni-Ge 127 - Gd-Os-Ge 130 - Gd-Pd-Ge 129 - Gd-Pt-Ge 131 - Gd-Re-Ge 130 - Gd-Rh-Ge 129 - Gd-Ru-Ge 128 - Gd-Si-Ge 38 - germanium-rare earth-M systems 8-204, 227-335 - Ho-Ag-Ge 159 - Ho-Al-Ge 30 – Ho–Au–Ge 163 - Ho--Co--Ge 151 - Ho--Cr--Ge 149 - Ho--Cu--Ge 154 - Ho--Fe--Ge 149 - Ho-Ir-Ge 160 - Ho-Li-Ge 15 - Ho-Mn-Ge 149 - Ho-Mo-Ge 154 - Ho-Nb-Ge 154 - Ho-Ni-Ge 152 - Ho-Os-Ge 160 - Ho-Pd-Ge 157 - Ho--Pt--Ge 162 - Ho-Re-Ge 159

– Ho--Ru--Ge 155

phase equilibrium and crystal structures (cont d)	– Nd–Ni–Ge 94
– La–Ag–Ge 63	– Nd–Os–Ge 101
– La–Al–Ge 24	– Nd–Re–Ge 101
– La–Au–Ge 65	– Nd–Rh(Pd)–Ge 99
– La–B–Ge 20	NdRuGe 98
– La–Ce–Ge 201	– Nd–Ta–Ge 100
– La–Co–Ge 59	– Nd–V–Ge 89
– La–Cu–Ge 61	– Nd–W–Ge 100
– La–Fe–Ge 59	– Nd–Zn–Ge 96
– La–Gd–Ge 201	– Nd–Zr–Ge 96
– La–Ir–Ge 64	– Pr–Ag–Ge 87
– La–Li–Ge 9	– Pr–Al–Ge 26
– La–Mn–Ge 59	– Pr–Au–Ge 88
– La–Ni–Ge 60	– Pr–Co–Ge 82
– La-Os-Ge 64	– Pr–Cu–Ge 84
– La–Pd–Ge 63	– Pr–Fe–Ge 81
– La–Pt–Ge 65	– Pr–Ir–Ge 88
– La–Rh–Ge 62	– Pr–Li–Ge 11
– La–Ru–Ge 62	– Pr–Mn–Ge 81
– La–Si–Ge 35	– Pr–Ni–Ge 83
– La–Zn–Ge 61	– Pr–Os–Ge 87
– Lu–Ag–Ge 194	– Pr–Pd–Ge 86
– Lu–Al–Ge 32	– Pr–Pt–Ge 88
– Lu–Au–Ge 195	– Pr–Rh–Ge 86
- Lu-Co-Ge 191	– Pr–Ru–Ge 85
– Lu–Cu–Ge 193	– Pr–Si–Ge 37
– Lu–Fe–Ge 190	– Pr–Zn–Ge 85
– Lu–Li–Ge 19	– R–Al–Ge systems 206
– Lu–Mn–Ge 190	– R–B–Ge systems 206
– Lu–Mo–Ge 193	– R–Co–Ge systems 208
– Lu–Nb–Ge 193	- R-Cu(Ag, Au)-Ge systems 212
– Lu-Ni-Ge 192	– R–Fe–Ge systems 207
– Lu-Os(Ir)–Ge 195	- R-Ga(In, C)-Ge systems 207
– Lu–Re–Ge 195	R-Ge-M 8-204, 227-335
– Lu-Ru(Rh. Pd)–Ge 194	– R–Li–Ge systems 204
– Nd–Ag–Ge 99	– R–Mg–Ge 206
- Nd-Al-Ge = 26	– R–Ni–Ge systems 209
- Nd - Au - Ge = 104	- R-nlatinum metals-Ge systems 213
- Nd-B-Ge 22	– R–Si–Ge systems 207
- Nd-Co-Ge = 92	- Sc-Ag-Ge 48, 451
- Nd-Cr-Ge 89	- Sc-Al-Ge 23. 459
- Nd-Cu-Ge 94	- Sc-Au-Ge 52
- Nd-Fe-Ge 91	- Sc-Ce-Ge 197 437
- Nd-Ga-Ge 32	- Sc-Co-Ge 43 448
- Nd-Hf-Ge 100	- Sc-Cr-Ge 40 445
$\sim \text{Nd} - \text{Ir}(\text{Pt}) - \text{Ge} = 103$	- Sc-Cu-Ge 45 451
- Nd I I - Ge = 12	- Sc-Dv-Ge 199 442
$= Nd_{m} = 30$	- Sc-Eu-Ge 199 442
= Nd = Mo = Ge = 97	- Sc-Fe-Ge 42 448
Nd Nh Ge 97	-5c-Gd-Ge = 100
- INU-UC 7/	- 50-04-06 177

_	Sc-Hf-Ge 49, 444
_	Sc-Ir-Ge 51, 450
_	Sc-La-Ge 196, 437
_	Sc-Li-Ge 8, 437
_	ScMnGe 41, 447
_	Sc-Mo-Ge 46, 446
	ScNbGe 46, 445
_	ScNdGe 198, 442
_	Sc-Ni-Ge 44, 450
_	Sc-Os-Ge 51, 450
_	ScPdGe 48, 450
_	Sc-Pr-Ge 197, 441
_	Sc-Pt-Ge 51
_	Sc-Re-Ge 50, 448
_	Sc-Rh-Ge 450
_	Sc-Ru-Ge 450
_	ScSmGe 198, 441
_	Sc-Ta-Ge 49, 445
_	Sc-Tb-Ge 199
_	Sc-V-Ge 39. 444
_	ScWGe 50, 447
_	Sc-Y-Ge 196, 437, 438
_	Sc-Yb-Ge 442 443
_	scandium-M 343-379
	scandium M M' (ass also individual
_	Scanting view the and manually
_	compounds) 379–464
_	compounds) 379–464 Sm–Ag–Ge 114
_	compounds) 379–464 Sm–Ag–Ge 114 Sm–Al–Ge 27
	compounds) 379–464 Sm–Ag–Ge 114 Sm–Al–Ge 27 Sm–Au–Ge 117
	compounds) 379–464 Sm–Ag–Ge 114 Sm–Al–Ge 27 Sm–Au–Ge 117 Sm–Co–Ge 106
	compounds) 379–464 Sm–Ag–Ge 114 Sm–Al–Ge 27 Sm–Au–Ge 117 Sm–Co–Ge 106 Sm–Cu–Ge 109
	compounds) 379–464 Sm–Ag–Ge 114 Sm–Al–Ge 27 Sm–Au–Ge 117 Sm–Co–Ge 106 Sm–Cu–Ge 109 Sm–Fe–Ge 105
	compounds) 379–464 Sm–Ag–Ge 114 Sm–Al–Ge 27 Sm–Au–Ge 117 Sm–Co–Ge 106 Sm–Cu–Ge 109 Sm–Fe–Ge 105 Sm–Ir–Ge 115
	compounds) 379–464 Sm–Ag–Ge 114 Sm–Al–Ge 27 Sm–Au–Ge 117 Sm–Co–Ge 106 Sm–Cu–Ge 109 Sm–Fe–Ge 105 Sm–Ir–Ge 115 Sm–Li–Ge 13
	scandini-M-Mi (see also individual compounds) 379-464         Sm-Ag-Ge 114         Sm-Al-Ge 27         Sm-Au-Ge 117         Sm-Co-Ge 106         Sm-Fe-Ge 109         Sm-Fe-Ge 105         Sm-Ir-Ge 115         Sm-Li-Ge 13         Sm-Lu-Ge 204
	scandini-M-Mi (see also individual compounds) 379-464         Sm-Ag-Ge 114         Sm-Al-Ge 27         Sm-Au-Ge 117         Sm-Co-Ge 106         Sm-Cu-Ge 109         Sm-Fe-Ge 105         Sm-Li-Ge 13         Sm-Lu-Ge 204         Sm-Mn-Ge 104
	scandini-M-Mi (see also individual compounds) 379-464         Sm-Ag-Ge 114         Sm-Al-Ge 27         Sm-Au-Ge 117         Sm-Co-Ge 106         Sm-Cu-Ge 109         Sm-Fe-Ge 105         Sm-I-Ge 115         Sm-Li-Ge 13         Sm-Lu-Ge 204         Sm-Mn-Ge 108
	scandini-M-Mi (see also individual compounds) 379-464         Sm-Ag-Ge 114         Sm-Al-Ge 27         Sm-Au-Ge 117         Sm-Co-Ge 106         Sm-Cu-Ge 109         Sm-Fe-Ge 105         Sm-Ir-Ge 115         Sm-Lu-Ge 204         Sm-Mn-Ge 108         Sm-Os-Ge 115
	scandini-M-Mi (see also individual compounds) 379-464         Sm-Ag-Ge 114         Sm-Al-Ge 27         Sm-Au-Ge 117         Sm-Co-Ge 106         Sm-Cu-Ge 109         Sm-Fe-Ge 105         Sm-Ir-Ge 115         Sm-Li-Ge 13         Sm-Lu-Ge 204         Sm-Mn-Ge 108         Sm-Os-Ge 115         Sm-Pd-Ge 113
	scandini-M-Mi (see also individual compounds) 379-464         Sm-Ag-Ge 114         Sm-Al-Ge 27         Sm-Au-Ge 117         Sm-Co-Ge 106         Sm-Cu-Ge 109         Sm-Fe-Ge 105         Sm-Ir-Ge 115         Sm-Li-Ge 13         Sm-Lu-Ge 104         Sm-Ni-Ge 108         Sm-Os-Ge 115         Sm-Pd-Ge 113         Sm-Pt-Ge 116
	scandul = M-Wi (see also individual compounds) 379-464         Sm-Ag-Ge 114         Sm-Al-Ge 27         Sm-Au-Ge 117         Sm-Co-Ge 106         Sm-Cu-Ge 109         Sm-Fe-Ge 105         Sm-Ir-Ge 115         Sm-Li-Ge 13         Sm-Lu-Ge 104         Sm-Ni-Ge 108         Sm-Os-Ge 115         Sm-Pt-Ge 116         Sm-Rh-Ge 112
	scandali = M-M       (see also individual compounds)         379-464         Sm-Ag-Ge       114         Sm-Al-Ge       27         Sm-Au-Ge       117         Sm-Co-Ge       106         Sm-Cu-Ge       109         Sm-Fe-Ge       105         Sm-Li-Ge       115         Sm-Li-Ge       13         Sm-Lu-Ge       204         Sm-Ni-Ge       108         Sm-Os-Ge       115         Sm-Pd-Ge       113         Sm-Pt-Ge       116         Sm-Rh-Ge       112         Sm-Ru-Ge       110
	scandali = M-M       (see also individual compounds)         379-464         Sm-Ag-Ge       114         Sm-Al-Ge       27         Sm-Au-Ge       117         Sm-Co-Ge       106         Sm-Cu-Ge       109         Sm-Fe-Ge       105         Sm-Li-Ge       13         Sm-Lu-Ge       204         Sm-Mn-Ge       104         Sm-Os-Ge       115         Sm-Os-Ge       115         Sm-Pt-Ge       108         Sm-Pd-Ge       113         Sm-Pt-Ge       116         Sm-Rh-Ge       112         Sm-Ru-Ge       110
	scandul = M-M       (see also individual         compounds)       379-464         Sm-Ag-Ge       114         Sm-Al-Ge       27         Sm-Al-Ge       117         Sm-Co-Ge       106         Sm-Cu-Ge       109         Sm-Fe-Ge       105         Sm-Li-Ge       115         Sm-Li-Ge       13         Sm-Lu-Ge       204         Sm-Mn-Ge       104         Sm-Ni-Ge       108         Sm-Os-Ge       115         Sm-Pd-Ge       113         Sm-Pt-Ge       116         Sm-Ru-Ge       110         Sm-Zn-Ge       110         Sm-Zn-Ge       110
	scanduli-M-Mi (see also individual compounds) 379-464         Sm-Ag-Ge 114         Sm-Al-Ge 27         Sm-Au-Ge 117         Sm-Co-Ge 106         Sm-Cu-Ge 109         Sm-Fe-Ge 105         Sm-Ir-Ge 115         Sm-Li-Ge 13         Sm-Lu-Ge 204         Sm-Mn-Ge 108         Sm-Os-Ge 115         Sm-Pd-Ge 113         Sm-Pt-Ge 116         Sm-Ru-Ge 110         Sm-Zn-Ge 110         Tb-Ag-Ge 141         Tb-Al-Ge 29
	scandalin=ni-ni       (see also individual compounds)         379-464         Sm-Ag-Ge       114         Sm-Al-Ge       27         Sm-Au-Ge       117         Sm-Co-Ge       106         Sm-Cu-Ge       109         Sm-Fe-Ge       105         Sm-Li-Ge       13         Sm-Li-Ge       104         Sm-Ni-Ge       104         Sm-Ni-Ge       108         Sm-Os-Ge       115         Sm-Pd-Ge       113         Sm-Pt-Ge       116         Sm-Ru-Ge       110         Sm-Zn-Ge       110         Tb-Ag-Ge       141         Tb-Al-Ge       29         Tb-Au-Ge       142
	scandalin=ni-ni       (see also individual compounds)         379-464         Sm-Ag-Ge       114         Sm-Al-Ge       27         Sm-Au-Ge       117         Sm-Co-Ge       106         Sm-Cu-Ge       109         Sm-Fe-Ge       105         Sm-Li-Ge       115         Sm-Li-Ge       13         Sm-Lu-Ge       204         Sm-Mn-Ge       104         Sm-Ni-Ge       108         Sm-Os-Ge       115         Sm-Pd-Ge       113         Sm-Pt-Ge       116         Sm-Ru-Ge       110         Sm-Zn-Ge       110         Tb-Ag-Ge       141         Tb-Al-Ge       29         Tb-Au-Ge       142
	scandali = M-M       (see also individual compounds)         379-464         Sm-Ag-Ge       114         Sm-Al-Ge       27         Sm-Au-Ge       117         Sm-Co-Ge       106         Sm-Cu-Ge       109         Sm-Fe-Ge       105         Sm-Li-Ge       115         Sm-Li-Ge       13         Sm-Lu-Ge       204         Sm-Mn-Ge       104         Sm-Ni-Ge       108         Sm-Pd-Ge       115         Sm-Pd-Ge       113         Sm-Pd-Ge       113         Sm-Pd-Ge       112         Sm-Ru-Ge       110         Sm-Zn-Ge       110         Sm-Zn-Ge       141         Tb-Al-Ge       29         Tb-Au-Ge       142         Tb-B-Ge       22         Tb-Co-Ge       135
	scandalin=ni-ni       (see also individual compounds)         379-464         Sm-Ag-Ge       114         Sm-Al-Ge       27         Sm-Au-Ge       117         Sm-Co-Ge       106         Sm-Cu-Ge       109         Sm-Fe-Ge       105         Sm-Li-Ge       13         Sm-Li-Ge       13         Sm-Lu-Ge       204         Sm-Mn-Ge       104         Sm-Ni-Ge       108         Sm-Pd-Ge       115         Sm-Pd-Ge       113         Sm-Pt-Ge       116         Sm-Ru-Ge       112         Sm-Ru-Ge       110         Sm-Zn-Ge       110         Sm-Zn-Ge       141         Tb-Al-Ge       29         Tb-Au-Ge       142         Tb-B-Ge       22         Tb-Co-Ge       135

- Tb-Fe-Ge 134 – Tb–Ir–Ge 141 – Tb–Li–Ge 15 - Tb-Mn-Ge 132 - Tb-Mo-Ge 139 - Tb-Nb-Ge 139 - Tb-Ni-Ge 136 - Tb-Os-Ge 141 - Tb-Pd-Ge 140 – Tb–Pt–Ge 142 – Tb–Rh–Ge 140 – Tb-Ru-Ge 139 - Tm-Ag-Ge 179 - Tm-Al-Ge 31 - Tm-Au-Ge 181 - Tm-Co-Ge 174 - Tm-Cu-Ge 177 - Tm-Fe-Ge 173 – Tm–Ga–Ge 33 – Tm–Ir–Ge 180 – Tm–Li–Ge 17 - Tm-Mn-Ge 172 – Tm–Mo–Ge 178 - Tm-Nb--Ge 178 - Tm-Ni-Ge 175 - Tm-Os-Ge 179 - Tm-Pd-Ge 179 – Tm–Pt–Ge 180 – Tm–Rh–Ge 178 – Tm–Ru–Ge 178 - Y-Ag-Ge 58 - Y-Al-Ge 23 - Y-Au-Ge 58 – Y–B–Ge 20 - Y-Ce-Ge 200 - Y-Co-Ge 53 – Y–Cr–Ge 52 – Y–Cu–Ge 56 – Y–Fe–Ge 53 – Y–Ga–Ge 32 - Y-Li-Ge 9 - Y--Mn--Ge 53 – Y–Mo–Ge 56 – Y–Nb–Ge 56 – Y–Ni–Ge 54 - Y-Os(Ir, Pt)-Ge 58 - Y-Ru(Rh, Pd)-Ge 57

- Y-Si-Ge 34
- Yb-Ag-Ge 188
- Yb-Al-Ge 31

phase equilibrium and crystal structures (cont'd) - Yb-Au-Ge 190 - Yb-Co-Ge 183 - Yb--Cu--Ge 185 - Yb-Fe-Ge 182 - Yb-Ir-Ge 189 - Yb-Li-Ge 18 - Yb-Mg-Ge 20 - Yb-Mn-Ge 181 - Yb-Nb-Ge 186 - Yb-Ni-Ge 184 - Yb-Os-Ge 188 - Yb-Pd--Ge 187 - Yb-Pt-Ge 189 - Yb-Rh-Ge 187 - Yb-Ru-Ge 186 R-M-Si (M = Sc, Zr, Hf) systems 482 - characteristics 482 RAuGe (R = Sc, Y, La, Lu) 494, 495 - density of states 494 - magnetic susceptibility 494, 495 - specific heat 495 structures 494 RAuGe (R = Sc, Y, Lu), physical properties 494  $RCo_2$  (R = Sc, Y, Lu) - electrical resistivity 498, 499 - electronic specific heat 498 - magnetic susceptibility 497, 498 - spin fluctuations 497-501 - thermal conductivity 499 - thermopower 500 - transport phenomena 498-501  $RFe_2$  (R = Sc, Y, Lu) 505 - electrical resistivity 505 RFe₂ series 503 - magnetic properties 503 - structure 503  $R_2Fe_3Si_5$  (R = Sc, Y, Lu) 510 - Mössbauer measurements 510 - specific heat 511 - superconductivity 510 RRu₄B₄ 512 - superconductivity 512 redistribution of atoms 483 Rhodes-Wohlfarth plot 501, 502  $(Sc_{0-0.2}R_{1-0.8})_2Fe_{14}B$  solid solutions 465 - Curie temperature 465

- lattice parameters 465 Sc-Ag 361 - compounds 361 - phase diagram 361, 363 Sc-Ag-Ge 48, 451 - isothermal section 48, 451 - ternary compound 48, 451 Sc-Ag-Si 436 isothermal section 436 Sc-Al 366 - compounds 366 - phase diagram 366 Sc-Al-Ge 23, 459 - ternary compound 23, 458, 459 Sc-Al-Si 458 isothermal section 459 - ternary compound 458 Sc-As-P 459 Sc-Au 363 - compounds 363 - phase diagram 363 Sc-Au-Ge 52 - compound 52 Sc-Au-Si 436 - ternary compound 436 Sc-Au-Sn 454 - ternary compound 454 Sc-B 365 - compounds 365 - phase diagram 365, 366 Sc-Ba 347 - phase diagram 347 Sc-Ba-Al 387 - isothermal section 387, 388 Sc-Be 345 - compounds 345 Sc-C 371 - compounds 371 - phase diagram 371, 412, 414 Sc-C-B(Al) 457 - ternary compounds 457 Sc-Ca 347 - phase diagram 346, 347 Sc-Ca-Al 387 Sc-Ca-Pt-P 468 - quaternary compound 468 Sc--Ca--Rh--B 464 - compound 464 Sc--Cd 363 - compounds 364

- phase diagram 363, 364 Sc--Ce 348 - phase diagram 348 Sc-Ce-Fe 460 - isothermal section 460, 461 Sc-Ce-Ge 197, 437, 438, 441 - isothermal section 197, 437, 441 - ternary compounds 197, 437, 438 Sc-Ce-Si 416 - isothermal section 416 - ternary compounds 416 Sc-Ce(Pr, Nd, Sm, Gd, Tb, Dy, Ho, Er, Tm)-Rh-B 464 Sc-Co 355 - compounds 355 - phase diagram 355, 356 Sc-Co-Al 393 - ternary compounds 393 Sc--Co--B 384 - isothermal sections 384 - ternary compounds 384 Sc--Co--C 412 - isothermal section 412, 413 - ternary compounds 412 Sc-Co-Ga 405 - isothermal section 405 - ternary compounds 405 Sc-Co-Ge 43, 44, 448-450 - isothermal section 43, 448, 449 - ternary compounds 43, 44, 448 Sc-Co-Si 432 isothermal section 432, 433 ternary compounds 432 Sc-Co-Sn 453 ternary compounds 453 Sc--Cr 352 – phase diagram 352 Sc-Cr-Al 391 - isothermal section 391, 392 Sc-Cr-B 379 - ternary compound 381 Sc--Cr--C 410 hypothetical phase diagram 410 - phase equilibria 410 - projection of solidus surface 411 - ternary compound 410 Sc-Cr-Ga 402 - isothermal section 402 - ternary compound 402 Sc--Cr--Ge 40, 445

- isothermal section 40, 445, 446 - ternary compounds 40, 445 Sc--Cr--Ni 463 - isothermal sections 463 Sc-Cr-Si 428 - isothermal section 428, 429 - ternary compounds 428 Sc--Cu 361 - compounds 361 - phase diagram 361, 362 Sc--Cu-Al 395 - isothermal section 395 ternary compounds 395 Sc--Cu--Ga 407 isothermal section 407, 408 - ternary compounds 407 Sc-Cu-Ge 45, 46, 441, 451 - isothermal section 45, 451 - ternary compounds 46, 441, 451 Sc-Cu-Si 434 - isothermal section 434, 435 - ternary compounds 436 Sc-Cu-Sn 454 - isothermal section 454 - ternary compounds 454 Sc--Cu--Zn 464 - ternary compound 464 Sc-Dy 348 Sc-Dy-Ge 199, 200, 438, 442, 443 - isothermal section 199, 200, 442, 443 - ternary compounds 199, 200, 438, 442 Sc-Dy-Ir-Si 466 Sc-Dy-Si 423 - isothermal section 423, 424 - ternary compounds 423 Sc--Er 349 - phase diagram 349 Sc-Er-Si 423 - isothermal section 423, 424 Sc-Eu 348 - phase diagram 348 Sc-Eu-Ge 199, 442 - ternary compound 199, 442 Sc-Fe 354 - compounds 354 - phase diagram 354 Sc-Fe-Al 392 - isothermal section 392 - ternary compounds 392 Sc-Fe-B 383

## SUBJECT INDEX

Sc-Fe-B (cont'd) - isothermal sections 383 - ternary compound 384 Sc--Fe--C 412 - isothermal section 412, 413 - ternary compounds 412 Sc-Fe-Ga 404 - isothermal section 404 - ternary compounds 404 Sc--Fe--Ge 42, 43, 448, 449 - isothermal section 42, 448, 449 - ternary compounds 42, 448 Sc-Fe-Si 431 - isothermal section 431, 432 ternary compounds 431 Sc-Fe-Sn 453 - ternary compound 453 Sc-Ga 366 - compounds 368 - phase diagram 366-369 Sc-Ga-Al 456 - isothermal section 456, 457 - ternary compounds 456 Sc-Gd 348 Sc-Gd-Ge 199 Sc-Gd-P 454 Sc-Ge 375 - compounds 375 - phase diagram 375 Sc-Ge-Si 458 - isothermal section 458 Sc-Hf 351 - phase diagram 351 Sc-Hf-Al isothermal section 390 Sc-Hf-Ga 401 - isothermal section 401, 402 - ternary compounds 401 Sc--Hf--Ge 49, 444 - isothermal section 49, 444 Sc-Hf-Ir 462 - ternary compound 462 Sc-Hf-Si 426 - isothermal section 426 Sc-Hg 364 - compounds 364 Sc-Ho 349 Sc-In 369 - compounds 370 - phase diagram 369, 370

Sc-In(Tl, Sn, Pb)-B 457 - ternary compounds 457 Sc-In(Tl, Sn, Pb)-C 457 - ternary compounds 457 Sc-Ir 359 - compounds 359 - phase diagram 359, 360 Sc-Ir-B 386 Sc-Ir-C 415 - ternary compound 415 Sc-Ir-Ge 51, 450 - ternary compounds 51 Sc-La 347 - phase diagram 347 Sc-La-B 379 Sc-La-Ge 196, 197, 437 - ternary compounds 196, 437, 438 Sc-La-Si 416 - ternary compounds 416 Sc-Li-Al 386 Sc-Li-Ge 8, 437, 438 Sc-Li-Sn 451 - ternary compound 451 Sc-Lu 349 Sc-Lu-Ni-C-B 467 Sc-Lu-Ru-B 466 Sc-Lu-Si 424 - isothermal section 424, 425 Sc-M-Al compounds 389 - ScAg₂Al 390 - ScAu₂Al 390 - ScCoAl 389 - Sc₂Co₃Al₉ 389  $- \sim Sc_6 Co_8 Al_{15} - 389$ - ScCu_{0.6}Al_{1.4} 390 - ScCuAl 390 - ~ScCu_{1.4}Al_{0.6} 390 - ScCu₂Al 390 - ScCu₂Al₂ 390 - ~ScCu₄Al₃ 390 - ScCu_{4.0-6.15}Al_{8.0-5.85} 390 - Sc₃Cu₉Al₇ 390  $- Sc_6Cu_{16.4}Al_{13.9} - 390$ - ScFe_{0.30-1.35}Al_{1.70-0.65} 389 - ScFe_{4.0-7.1}Al_{8.0-4.9} 389  $- Sc_6 Ir_7 Al_{16} - 390$ - ~ScNiAl₂ 389 - ~ScNiAl₄ 389 - ScNi₂Al 389 - ScNi_{1-0.6}Al_{1-1.4} 389

## 560

 $- \sim Sc_6 Ni_7 Al_{16} - 389$  $- Sc_6Os_7Al_{16} - 390$ - ScPd_{0.30-0.57}Al_{1.70-1.43} 389  $-\sim$ ScPdAl₃ 389 - ~ScPd_{1.73}Al_{6.36} 389 - ScPd₂Al 389 - Sc₆Pd₇Al₁₆ 389 – Sc₆Rh₇Al₁₆ 389 - ScRu_{0.68-0.26}Al_{1.32-1.74} 389  $- \sim ScRu_{0.8}Al_{3.7}$  389  $- \sim ScRu_{0.9-0.8}Al_{1.1-1.2}$ 389  $-\sim$ ScRuAl₂ 389 - ~ScRu_{1.1-1.04}Al_{0.9-0.96} 389 - ~ScRu_{2.3}Al_{3.9} 389  $- Sc_6 Ru_7 Al_{16} 389$  $- Sc_{0.15-0.45}Tb_{0.85-0.55}Al_3$ 389  $- Sc_{0.18-0.50}Y_{0.82-0.50}Al_3$ 389 Sc-M-Al (M = Ag, Au) 396ternary compounds 396 Sc-M-Al (M = Rh, Os, Ir, Pt) 394ternary compounds 394 Sc-M-Al (M = Ti, Zr, Hf) 390- isothermal sections 390 Sc-M-Al ternary systems 386-396 Sc-M-B compounds 381 - ScCoB₄ 381 - ScCo₃B₂ 381 - ScCo₄B₄ 381  $- Sc_2Co_{21}B_6 - 381$ - ScCrB₄ 381 - ScFeB₄ 381 - ScIr₃B_{1-x} 381 - ScIr₃B₂ 381 - ScIr₃B₄ 381 - ScMnB₄ 381 - ScNiB₄ 381 - ScNi₃B 381  $- \sim Sc_4 Ni_{15}B_6 - 381$  $- Sc_4Ni_{29}B_{10} - 381$  $- Sc_{3-4}Ni_{20-19}B_6$  381 - ScOsB₂ 381  $-Sc_2Os_5B_4 = 381$ - Sc₂ReB₆ 381 - ScRuB₄ 381 - ScRu₄B₄ 381 - Sc₂Ru₅B₄ 381 Sc-M-B (M = Os, Ir) 386 ternary compounds 386 Sc-M-B ternary systems 379-386 Sc-M-C compounds 412

- ScCoC₂ 412 - ScCo₃C 412 - Sc₃CoC₄ 412 - ScCrC₂ ( $\alpha$ ) 412 - ScCrC₂ ( $\beta$ ) 412 - Sc₂CrC₃ 412 - ScFeC₂ 412 - Sc₃FeC₄ 412 - ScIr₃C_{1-x} 412 - ScNiC₂ 412 - Sc₃NiC₄ 412  $- Sc_5Re_2C_7 = 412$ - ScRu₃C 412 Sc-M-C (M = Ru, Rh, Pd) 414 isothermal sections 414 - ternary compound 414 Sc-M-C (M = W, Re, Tc) 411- hypothetical phase diagram 411 - ternary compound 411 Sc-M-C (M = Zr, Hf, V, Nb, Ta) 410 - hypothetical phase diagram 410 Sc-M-C ternary systems 409-415 Sc-M-Ga compounds 397 - ScCo_{0.14}Ga_{1.86} 398 - ScCo_{0.35}Ga_{1.65} 398 - ScCo_{0.5}Ga_{1.5} 398 - ScCoGa₅ 398 - ScCo₁₂Ga₁₈ 398 - ScCo_{4.5}Ga_{4.1} 398 - ScCo_{5.8}Ga_{6.2} 397 - Sc₂Co₃Ga₉ 398 - Sc₂Co₇Ga₄ 398  $- Sc_5Co_{0.925}Ga_{0.925}$ 398 398 - Sc₆Co_{7.2-6.3}Ga_{15.8-16.7}  $-\sim Sc_{17}Co_{64-62}Ga_{19-21}$ 398  $-\sim Sc_{22}Co_{53-49}Ga_{25-29}$ 398  $-\sim Sc_{22}Co_{63-60}Ga_{15-18}$ 398  $-\sim Sc_{37}Co_{14}Ga_{49}$  398 - Sc₂₉₋₃₄Co₄₈₋₂₄Ga₂₉₋₄₂ 398 - Sc₂CoGa₈ 398 - ~Sc₄Cr₄Ga₃ 397 399 ScCu_{0.77-0.26}Ga_{1.23-1.74} - ScCu_{1.40-0.86}Ga_{0.60-1.14} 399 ScCu₂Ga 399 - ~ScCu_{3.2}Ga_{1.6} 399 - ~ScCu_{3.6}Ga_{1.4} 399 - ScCu_{3.7}Ga_{2.3} 399 - ScCu_{5.49-4.85}Ga_{6.51-7.15} 399

- $-Sc_{14}Cu_{37}Ga_{14}$  399
- ScFe_{0.14}Ga_{1.86} 397

Sc-M-Ga compounds (cont'd) - ScFe_{0.33}Ga_{1.67} 397 ScFeGa₅ 397 - ScFe_{1.37-0.71}Ga_{0.63-1.29} 397 397 ScFe_{1.82-1.44}Ga_{0.18-0.56} - ScFe_{4.73}Ga_{7.27} 397 - ScFe_{6-4.73}Ga_{6-7.27} 397 - Sc₂Fe_{8 83}Ga_{8 17} 397 - Sc₃Fe₂Ga₆ 397 - Sc_{8.5}Fe_{1.2}Ga 397  $- Sc_{0.2-0.9}Hf_{0.8-0.1}Ga 397$ - Sc_{0.2}Hf_{0.8}Ga₃ 397 - Sc₆Ir₇Ga₁₆ 399 - ScMn_{0.33}Ga_{1.67} 397 - Sc₃Mn₂Ga₆ 397 - Sc_{8.5}Mn_{1.2}Ga 397 – ~ScNbGa₄ 397  $- Sc_{8.4-9.4}Nb_{2.6-1.6}Ga_{10}$ 397 ScNi_{0.14}Ga_{1.86} 399 ScNi_{0.35}Ga_{1.65} 399 - ScNiGa 399 ScNiGa₂ 399 - ScNiGa₅ 398 - ScNi₁₂Ga₁₈ 398 - ScNi₂Ga 398 - ScNi_{2.36}Ga_{3.64} 398 - ScNi_{1-0.67}Ga_{1-1.33} 399  $- Sc_2Ni_{7-5.5}Ga_{4-5.5}$  398 - Sc₅Ni_{0.963}Ga_{0.963} 399  $- \ {\sim} Sc_{17} Ni_{64-59} Ga_{19-24} \quad 398$  $- \sim Sc_{22}Ni_{58}Ga_{20} 398$  $-\sim Sc_{23}Ni_{61}Ga_{16}$  398 - Sc₃₀₋₃₆Ni₅₅₋₃₉Ga₁₅₋₂₅ 399 - Sc₂NiGa₈ 398 - Sc₆Os₇Ga₁₆ 399 - ScPdGa 399 - ScPd₂Ga 399 - ScPtGa 399 - Sc₆Rh₇Ga₁₆ 399 - Sc₆Ru₇Ga₁₆ 399 - ScTi₂Ga₄ 397 - Sc_{6.8-9.4}Ti_{4.2-1.8}Ga₁₀ 397 – Sc₁₋₄Ti₄₋₁Ga₃ 397 - ScV₂Ga₄ 397  $- \ Sc_{1.26-3.82}Y_{3.74-1.18}Ga_4 \quad 397$  $- \ Sc_{3.2-4.7} Zr_{7.8-6.3} Ga_{10} \quad 397$ Sc-M-Ga (M = Ru, Rh, Pd, Os, Ir, Pt) 407 ternary compounds 407 Sc-M-Ga ternary systems 396-408 Sc-M-Ge 441

- ternary compounds 438 Sc--M--Ge compounds 39-52, 438-441 ScAgGe 48, 441 ScCeGe 197, 438  $- \sim Sc_2Ce_5Ge_6 = 197, 438$ - Sc₃Ce_{1.22}Ge₄ 197, 438  $- \sim Sc_{4.5}Ce_{0.5}Ge_4$  438  $- \sim Sc_5 Ce_{0.5} Ge_{4.5}$  197 - ScCoGe 44, 440 - ScCoGe₂ 44, 440 - ScCo₆Ge₆ 44, 439 – Sc₃Co₂Ge₃ 440 - Sc₄Co₄Ge₆ 440 - Sc₄Co₄Ge₇ 44  $- Sc_4Co_7Ge_6 44, 439$  $- \sim Sc_4 Co_{11} Ge_5$  44, 439 - Sc₂CoGe₂ 44, 440 - ScCrGe₂ 40, 439 - ScCr₆Ge₆ 40, 438  $- Sc_2Cr_4Ge_5$  40, 438 - Sc₇Cr_{5.2}Ge_{8.8} 40, 439 ScCuGe 46, 441 - Sc₃Cu₄Ge₄ 46, 441  $- \sim Sc_{0.3}Dy_{0.7}Ge_2$  438 - Sc_{1.8}Dy_{3.2}Ge₄ 199, 438 - Sc_{2.7}Dy_{2.3}Ge₄ 199, 438 ScEuGe 199, 438 - ScFeGe 42, 439 - ScFeGe₂ 42, 439 ScFe_{1.5}Ge_{0.5} 42, 439 - ScFe₆Ge₄ 42, 439 ScFe₆Ge₅ 42, 439 - ScFe6Ge6 42, 439 - Sc₄Fe₄Ge₆₆ 42, 439  $- Sc_{1-1.17}Fe_{1.94-1.70}Ge_{0.06-0.30}$  42, 439 - ScIrGe 51, 441 - Sc₄Ir₇Ge₆ 51, 441 - ScLaGe 196, 197, 438 - Sc₃La_{1.22}Ge₄ 196, 438 - ScLiGe 8, 438 - ScMnGe 41, 439 - ScMnGe₂ 41, 439 - ScMn₆Ge₄ 41, 439 - ScMn₆Ge₆ 41, 439 - Sc₃Mn₇Ge₈ 41  $- \sim Sc_5 Mn_7 Ge_8 = 439$ - Sc₇Mn_{5.3}Ge_{8.7} 41, 439 - Sc₂₋₄Mo₃₋₁Ge₄ 47, 439 - Sc₂Nb₃Ge₄ 46, 438 - ScNdGe 198, 438

 $- \sim Sc_2Nd_5Ge_6$  198, 438  $- Sc_3Nd_{1.22}Ge_4$  198, 438 - ScNiGe 45, 440 - ScNi₆Ge₆ 45, 440 - Sc₃Ni₄Ge₄ 45, 440 - Sc₃Ni₁₁Ge₄ 45, 440 - Sc₄Ni₄Ge_{6.2} 45, 440 - Sc₆Ni₁₆Ge₇ 45, 440 - Sc₆Ni₁₈Ge₁₁ 45, 440 – Sc₉Ni₅Ge₈ 440  $- Sc_{12.3}Ni_{40.7}Ge_{31}$  45, 440  $- \sim Sc_{13}Ni_6Ge_{15}$  45, 440 - ScOsGe 51, 440 - ScOsGe₂ 51, 440 - Sc₄Os₇Ge₆ 51, 440 - ScPdGe 48, 440 - ScPrGe 198, 438  $- Sc_3Pr_{1.22}Ge_4 = 198, 438$ - ScReGe₂ 50, 439 - ScRhGe₂ 48, 440 - Sc₄Rh₇Ge₆ 48, 440 - ScRhGe (I) 48, 440 - ScRhGe (II) 48, 440 – ScRuGe 47, 440 - ScRuGe₂ 47, 440 - Sc₄Ru₇Ge₆ 47, 440 - ScSmGe 199, 438 - Sc₃Sm₁₂₂Ge₄ 199, 438  $- Sc_{2-3}Ta_{3-2}Ge_4 50, 438$  $- Sc_2V_3Ge_4 - 40, 438$  $- Sc_{1-1.8}V_{5-4.2}Ge_5$  40, 438  $- \sim Sc_{0.3}Y_{0.7}Ge_2$  196, 438 - Sc_{1.35}Y_{3.65}Ge₄ 196, 438 - Sc_{2.7}Y_{2.3}Ge₄ 196, 438 - ~Sc_{0.3}Yb_{0.7}Ge₂ 438  $- Sc_6Yb_5Ge_{10}$  438 Sc-M-Ge ternary compounds 200 Sc-M-Ge ternary systems 8, 23, 39-52, 196-199, 437-451 Sc--M--In compounds 409 - ScAg₂In 409 - ScAu₂In 409 - ScCu₂In 409 - ScNi₂In 409 - ScNi₄In 409 - Sc₂Ni₂In 409  $- Sc_{0.76-1.44}Pd_2In_{1.24-0.56}$  409 - ScPt₂In 409 Sc-M-In (M = Cu, Ag, Au) 409- ternary compound 409

Sc-M-In ternary systems 408, 409 Sc-M-M' compounds 380, 462 - ScCuZn (I) 462 - ScCuZn (II) 462  $-Sc_{0.2}Hf_{0.8}Ir$  462 - ScNi₄Au 462 Sc-M-M' ternary systems 460-464 Sc-M-P(As, Sb, Bi) compounds 455 - ScCoP 455 - ScCo₅P₃ 455  $- Sc_2Co_{12}P_7 455$  $- Sc_5Co_{19}P_{12}$  455 - ScFe₄P₂ 455 - ScFe₅P₃ 455  $- Sc_2Fe_{12}P_7 455$  $-Sc_2Mn_{12}P_7$  455 - ScNi₄As₂ 455 - ScNiBi 455 - ScNiSb 455 - ScPdBi 455 - ScPtSb 455 - ScRuP 455  $- Sc_2Ru_{12}P_7 - 455$ Sc-M-P(As, Sb, Bi) ternary systems 454-456 Sc-M-Se compounds 456 - ScAgSe₂ 456 - Sc₂CdSe₂ 456  $- Sc_{1-0.67}Cu_{1-2}Se_2$ 456 - Sc₂EuSe₄ 456 - Sc₂MgSe₄ 456 - Sc₂MnSe₄ 456 Sc-M-Se ternary systems 456 Sc-M-Si compounds 417 - ScAuSi 421 - ScCeSi 417 - ScCe₂Si₂ 417  $- Sc_3Ce_2Si_4$  417  $-\sim Sc_3Ce_8Si_9$  417  $- \sim Sc_3Ce_{11}Si_6 - 417$  $- \sim Sc_4 Ce_7 Si_9$  417  $- \sim Sc_5 Ce_6 Si_9 = 417$  $- \sim Sc_7 Ce_3 Si_{10} 417$ - ScCo_{0.25}Si_{1.75} 420 - ScCoSi 420  $- \ ScCo_{1.52-1.46}Si_{0.48-0.54}$ 420 - ScCo₂Si₂ 419  $- \ Sc_2 Co_{0.85} Si_{0.15} \quad 420$ - Sc₂Co₃Si₅ 419 - Sc₃Co₂Si₃ 420

 $- \sim Sc_4 Co_{14} Si_9$  419

Sc-M-Si compounds (cont'd)  $- Sc_5Co_4Si_{10} - 419$ - Sc₆Co₁₆Si₇ 419 - Sc₆Co₃₀Si₁₉ 419 - Sc₂CoSi₂ 420 - Sc₂Cr₃Si₄ 418  $- Sc_2Cr_4Si_5 418$ - Sc₇Cr_{4.8}Si_{9.2} 418 - ScCu₂Si₂ 421 - Sc₂Cu_{0.8}Si_{0.2} 421 - Sc₃Cu₄Si₄ 421 - ScCuSi (h) 421 - ScCuSi (r) 421 - Sc_{0.3}Dy_{0.7}Si₂ 418 - Sc_{0.4-0.7}Dy_{0.6-0.3}Si_{1.67} 418 - Sc_{0.35}Fe_{4.65}Si₃ 418 - ScFe_{0.25}Si_{1.75} 419 - ScFeSi 419  $- \ ScFe_{1.5-1.42}Si_{0.5-0.58} \quad 419$  ScFe₂Si₂ 419 - ScFe₄Si₂ 419 - ~ScFe₅Si₃ 419 - ScFe₁₀Si₂ 419 - Sc_{1.2}Fe₄Si_{9.8} 419 - Sc₂Fe₃Si₅ 419 - Sc₃Fe₂Si₃ 419 - Sc₄Fe₄Si₇ 419 - Sc_{1-1.09}Fe_{1.97-1.82} Si_{0.06-0.12} 419 - ScFeSi₂ (I) 419 - ScFeSi₂ (II) 419 - Sc₂FeSi₂ 419 - ScIrSi 421 - ScIr₃Si₇ 421 - Sc₄Ir₇Si₆ 421  $- Sc_5 Ir_4 Si_{10} 421$ - ScLaSi 417 - ScLa₂Si₂ 417 - ScMn_{0.25}Si_{1.75} 418 - ScMnSi 418 - ScMnSi₂ 418 - Sc₄Mn₄Si₇ 418 - Sc₂Mo₃Si₄ 418 - Sc04Nb46Si3 418  $- Sc_2Nb_3Si_4 418$  $- \ Sc_{0.85-0.95}Nd_{0.15-0.05}Si_{1.67} \quad 417$ - ScNdSi 417 - ScNd₂Si₂ 417 - ~ScNd₄Si₃ 417 - Sc₄NdSi₄ 417

- Soli Si 420
- ScNi_{0.25}Si_{1.75} 420

- ScNiSi 420 - ScNiSi₃ 420 - ScNi_{1.52-1.49}Si_{0.48-0.51} 420 - ScNi₂Si₂ 420 - ScNi₂Si₃ 420 - ~Sc₂Ni₅Si₃ 420  $- \sim Sc_2Ni_9Si_9 - 420$ - Sc₃Ni₂Si₃ 420  $- Sc_3Ni_2Si_4 - 420$ - Sc₃Ni₄Si₄ 420  $- Sc_3Ni_{11}Si_4 420$ - Sc₆Ni₁₆Si₇ - 420  $- Sc_6Ni_{18}Si_{11} - 420$ - Sc₃NiSi₃ 421  $-\sim Sc_3Os_2Si_6$  421 - ScPdSi 421  $- Sc_{0.89}Pr_{0.11}Si_{1.53}$  417 - ScPrSi 417 - ScPr₂Si₂ 417 - ~ScPr₄Si₃ 417 - Sc_{1.26}Pr_{3.74}Si₄ 417  $- \sim Sc_2 Pr_3 Si_4 - 417$  $- \sim Sc_2Pr_5Si_3 \quad 417$ - Sc₃Pr₂Si₄ 417 - ScPtSi 421 - ~ScReSi₂ 418  $- Sc_2Re_3Si_4 418$  $- Sc_3Re_2Si_4 - 418$  $- Sc_5 Re_8 Si_{12}$  418  $- Sc_7 Re_{3,35} Si_{10.65} - 418$ - ScRhSi 421 - ScRhSi₂ 421 - ScRh₃Si₇ 421  $- \sim Sc_2Rh_3Si_4$  421  $- \sim Sc_3Rh_2Si_4 = 421$ - ~Sc₃Rh₂Si₉ 421 - ~Sc₃Rh₃Si₅ 421  $- Sc_5Rh_4Si_{10} - 421$ - ~Sc₆Rh₄Si₉ 421 - ~Sc₄RhSi₈ 421 - ScRuSi 421  $- \sim Sc_3Ru_2Si_6 - 421$ - Sc_{0.2-0.4}Sm_{0.8-0.6}Si 417  $- Sc_{0.3}Sm_{0.7}Si_2 418$ - ScSmSi 418 - ScSm₂Si₂ 418  $- Sc_3Sm_2Si_4 - 418$ - ScV₅Si₅ 418

- $Sc_2V_3Si_3 418$
- $Sc_2V_3Si_4 418$

564

 $- Sc_{2-3}W_{3-2}Si_4 418$  $- \mathrm{Sc}_{0.95-0.52} \mathrm{Y}_{0.05-0.48} \mathrm{Si}_{1.67}$  417 Sc-M-Si ternary systems 416-436 Sc-M-Sn compounds 452 - ScAuSn (I) 452 - ScAuSn (II) 452 - ScCoSn 452 - ScCo_{1.1}Sn_{3.6} 452 - ScCo₂Sn 452 - ScCo₆Sn₆ 452 - ScCuSn 452 - ScCu₄Sn 452  $-\sim Sc_6 CuSn_2$  452 - ScFe₆Sn₆ 452 - ScIr_{1.1}Sn_{3.6} 452 - ScLiSn 452 - ScMn₆Sn₆ 452 - ScNiSn 452 - ScNi₂Sn 452 - ScNi₄Sn 452 - Sc₂Ni₂Sn 452 - ScOs_{1.1}Sn_{3.6} 452 - ScPd₂Sn 452 - ScPdSn (I) 452 - ScPdSn (II) 452 - ScPt₂Sn 452 - ScPtSn (I) 452 - ScPtSn (II) 452 - ScPtSn (III) 452 - ScRh_{1.1}Sn_{3.6} 452 - ScRu_{1.1}Sn_{3.6} 452 Sc-M-Sn ternary systems 451-454 Sc-M-X 480 Sc-M-X compounds 380 Sc-M compounds 345, 351, 353, 355, 358, 362, 365 - ScAg 362 – ScAg₂ 362 - ScAg₄ 362 – ScAu 362 - ScAu₂ 362 - ScAu₄ 362 – Sc₂Au 362 - ScBe₅ 345 - ScBe₁₃ 345  $- Sc_2Be_{17} - 345$ – ScCd 365 - ScCd₃ 365 - ScCd₇ 365 - ScCo 355

- ScCo₂ 355 - Sc₂Co 355 - Sc₃Co 355 - ScCu 362 - ScCu₂ 362 - ScCu₄ 362 - Sc₂₉Fe₆ 355 - ScFe_{1.74}( $\lambda_2$ ) 355 - ScFe₂( $\lambda_1$ ) 355 - ScFe₂( $\lambda_3$ ) 355 - ScHg 365 - ScHg₃ 365 - ScIr 359 - ScIr₂ 359 - ScIr₃ 358 - Sc₂Ir 359  $- Sc_{11}Ir_4 - 359$  $- Sc_{44}Ir_7 359$ - Sc₅₇Ir₁₃ 359 - ScMg( $\beta'$ ) 345 - ScMn₂ 353 - ScNi 355 - ScNi₂ 355 - Sc₂Ni 355 - Sc₂Ni₇ 355 - ScNi₅(HT) 355 - ScNi₅(LT) 355 - ScOs₂ 358  $- Sc_{11}Os_4 - 358$ - Sc44Os7 358 - ScPd 358 - ScPd₂ 358 - ScPd₃ 358 - Sc₂Pd 358 - ~Sc₄Pd 358 - ScPt 359 - ScPt₃ 359 - Sc₂Pt 359 - Sc57Pt13 359  $- \sim Sc_2Pu_3 - 351$ - ScRe₂ 353 - Sc₅Re₂₄ 353 - ScRh 358 - ScRh₃ 358 - Sc₂Rh 358 - Sc₃Rh 358 - Sc₅₇Rh₁₃ 358 – ScRu 358 - ScRu₂ 358  $-Sc_{11}Ru_4 - 358$ 

Sc-M compounds (cont'd) - Sc₅₇Ru₁₃ 358 - ScTc₂ 353 - ~ScTc₃ 353 – ScTc₇ 353  $- \sim Sc_3Tc_2 - 353$ - ~Sc₄Tc 353 – ScZn 365 - ScZn₂ 365 - ScZn₁₂ 365  $- Sc_3Zn_{17} - 365$ - Sc₁₃Zn₅₈ 365 Sc-M systems -M = 5A, 6A element 351 - M = 1A element 345 -M = 2A element 345 -M = 4A element 351 -M = 1B element 361 -M = 2B element 363 - M = actinide element 349 - M = Fe, Co, Ni 354- M = Mn, Tc, Re 353- M = platinum group element 357 Sc-Mg 345, 346 - compound 346 phase diagram 345 Sc-Mg-Al 386 isothermal section 386 Sc-Mg-Mn 460 isothermal sections 460 Sc-Mg-Mn-Li(Ca, Y, Ce, Nd, Zr, Ni, Cd, Zn, Al, In, Si, Ge, Sn) 464 Sc-Mg(Eu, Mn, Cu, Ag, Cd)-Se 456 - ternary compound 456 Sc-Mn 353 - compound 353 phase diagram 353 Sc-Mn-Al 392 Sc-Mn-B 382 ternary compound 382 Sc-Mn-Fe 463 Sc-Mn-Ga 402 - isothermal section 402, 403 ternary compounds 402 Sc-Mn-Ge 41, 447, 448 - isothermal section 41, 447, 448 - ternary compounds 41, 447 Sc-Mn-Si 430 - isothermal section 430

- ternary compounds 430 Sc-Mn-Sn 453 - ternary compound 453 Sc-Mn(Fe, Co)-P ternary compounds 455 Sc-Mn(Fe, Co)-P 454 Sc-Mo 352 phase diagram 352 Sc-Mo-Al 391 Sc-Mo-C 411 - hypothetical phase diagram 411 - phase equilibria 411 - projection of solidus surface 411 Sc-Mo-Ge 46, 47, 446, 447 - isothermal section 47, 446 - ternary compound 47, 447 Sc-Mo-Si 428 - isothermal section 428, 429 - ternary compound 428 Sc--Nb 352 phase diagram 352 Sc-Nb-Al 391 - phase equilibria 391 Sc-Nb-Ga 402 isothermal section 402, 403 - ternary compounds 402 Sc-Nb-Ge 46, 445 - isothermal section 46, 445 - ternary compound 46, 445 Sc-Nb-Si 426 - isothermal section 426, 427 Sc-Nd 348 Sc--Nd--Ge 198, 442 - isothermal section 198, 442 - ternary compounds 198, 442 Sc-Nd-Si 422 isothermal section 422 ternary compounds 422 Sc-Ni 356 - compounds 356 phase diagram 356, 357 Sc-Ni-Al 393 isothermal sections 393 ternary compounds 393 Sc-Ni-As 455 - ternary compound 455 Sc-Ni-Au 463 - ternary compound 463 Sc-Ni-B 384 - isothermal section 385

ternary compounds 384 Sc-Ni-C 414 isothermal section 414 ternary compounds 414 Sc-Ni-C-B 467 Sc-Ni-Ga 406 - isothermal section 406, 407 - ternary compounds 406 Sc-Ni-Ge 44, 45, 450 - isothermal section 44, 450 - ternary compounds 44, 45, 450 Sc-Ni-In 408 - ternary compounds 408 Sc-Ni-Si 432 - isothermal section 432, 434 - ternary compounds 432 Sc-Ni-Sn 453 - phase equilibria 453 - ternary compounds 453 Sc-Ni(Pd)-Bi 456 - ternary compounds 456 Sc-Ni(Pt, Au)-Sb - ternary compounds 455 Sc-Ni(Pt, Au)-Sb 455 Sc-Os 359 - compounds 359 Sc-Os-B 386 Sc-Os-Ge 51, 450 - ternary compounds 51, 450 Sc--Pb 376 - compounds 376 - phase diagram 376, 377 Sc-Pd 357 - compounds 359 - phase diagram 357 Sc-Pd-Al 394 - isothermal section 394 - ternary compounds 394 Sc-Pd-C, isothermal section 415 Sc-Pd-Ge 48, 450 Sc-Pd-In 408 - ternary compound 409 Sc-Pd(Os, Ir, Pt)-Si 434 - ternary compounds 434 Sc--Pm 348 Sc-Po 379 Sc-Pr 348 Sc--Pr-Si 422 - ternary compounds 422 Sc-Pr(Sm)-Ge 197-199, 441

 ternary compounds 198, 199, 441 Sc-Pt 359 - compounds 361 - phase diagram 359 Sc--Pt--Ge 51, 52 Sc-Pt-In 409 - ternary compound 409 Sc-Pu 350 - compound 351 - phase diagram 350 Sc--R 347-349 Sc-R-Al 387, 388 - phase equilibria 388 - ternary compounds 388 Sc-R-Rh-B alloys 465 - Sc_{0.3}Ce_{0.7}Rh₄B₄ 465  $- Sc_{0.3}Dy_{0.7}Rh_4B_4$ 465  $- Sc_{0.2}Er_{0.8}Rh_4B_4$ 465  $- \operatorname{Sc}_{0.3}\operatorname{Er}_{0.7}\operatorname{Rh}_4\operatorname{B}_4$ 465 - Sc_{0.3}Gd_{0.7}Rh₄B₄ 465 - Sc_{0.3}Ho_{0.7}Rh₄B₄ 465 - Sc_{0.4}Ho_{0.6}Rh₄B₄ 465  $- Sc_{0.3}Nd_{0.7}Rh_4B_4$ 465  $- Sc_{0.3}Pr_{0.7}Rh_4B_4 = 465$  $- Sc_{0.3}Sm_{0.7}Rh_4B_4$ 465  $- Sc_{0.3}Tb_{0.7}Rh_4B_4$  465  $- Sc_{0.3}Tm_{0.7}Rh_4B_4$  465 Sc-Re 353 - compounds 353 - phase diagram 353 Sc-Re-B 382 - isothermal section 383 - ternary compound 382 Sc-Re-Ge 50, 51, 448 isothermal section 51 - ternary compounds 50, 448 Sc-Re-Ni 463 Sc-Re-Ni-Si 468 Sc-Re-Si 430 - isothermal section 430, 431 ternary compounds 430 Sc-Rh 357 - compounds 357 - phase diagram 357, 360 Sc-Rh-B 385 Sc-Rh-C, isothermal section 415 Sc-Rh-Ge 47, 48, 450, 451 Sc-Rh-Os-Si 467 Sc-Rh-Si 433 - isothermal section 433
Sc-Rh-Si (cont'd) - ternary compounds 433 Sc--Ru 357 - compounds 357 - phase diagram 357 Sc-Ru-Al 393 - isothermal section 393 - ternary compound 393 Sc-Ru-B 385 - metastable equilibria 385 - ternary compounds 385 Sc-Ru-C, isothermal section 415 Sc-Ru-Ge 47, 450 Sc-Ru-P 455 - ternary compounds 455 Sc--Ru--Rh 463 Sc-Ru-Si 433 ternary compounds 433 Sc-Ru(Rh, Pd, Os, Ir, Pt)-Sn - ternary compounds 453 Sc-Ru(Rh, Pd, Os, Ir)-Ge - ternary compounds 450 Sc-Ru(Rh, Pd, Os, Ir, Pt)-Sn 453 Sc-Ru(Rh, Pd, Os, Ir)-Ge 450 Sc-Se 377 Sc-Si 372 compounds 372–375 - phase diagram 372-375 Sc-Si-C 458 Sc-Sm-Ge 438, 441 - ternary compounds 438 Sc-Sm-Si 423 - isothermal section 423 ternary compounds 423 Sc--Sn 376 - compounds 376 - phase diagram 376 Sc-Sr - phase diagram 346, 347 Sc-Sr-Al 387 - isothermal section 387 Sc-Ta 352 - phase diagram 352 Sc-Ta-Ge 49, 50, 445 - isothermal section 49, 445 ternary compounds 50, 445 Sc-Ta-Si 428 - isothermal section 428 Sc-Tb 348 Sc-Tb-Ge 199

Sc-Tb-Mn 460 Sc-Tc 353 - compounds 353 Sc-Te-Se 459 Sc-Th 349 phase diagram 349, 350 Sc-Th-C 409 Sc-Th-Rh-B 466 Sc-Ti 351 - phase diagram 351 Sc-Ti-Al - isothermal section 390 Sc-Ti-C 410 - hypothetical phase diagram 410 - phase equilibria 410 Sc-Ti-Fe 462 Sc-Ti-Ga 400 - isothermal section 400 - ternary compounds 400 Sc-Ti-Ni 462 Sc-Ti-Pt 462 Sc-Ti-Si 425 - isothermal section 425 Sc-T1 370 - compounds 370 - phase diagram 370, 371 Sc-Tm 349 Sc-U 349 - phase diagram 349, 350 Sc-U-Pd 460 Sc-U-Pd-B 466 Sc-V 352 - phase diagram 352 Sc-V-Ga 401 - isothermal section 401 - ternary compound 401 Sc-V-Ge 39, 40, 444 - isothermal section 39, 444 - ternary compounds 40, 444 Sc-V-Nb 462 Sc-V-Si 426 - isothermal section 426, 427 - ternary compounds 426 Sc-W 353 - phase diagram 353 Sc-W-B 382 - isothermal section 382 Sc--W--Ge 50, 447 - isothermal section 50, 447 Sc-W-Si 428

568

- isothermal section 428, 430 - ternary compound 429 Sc-X-X' compounds 380, 458 - ScAl₃C₃ 458 - Sc₁₁Al₂Ge₈ 458 - Sc₃AlC 458 - Sc₂AlSi₂ 458 - ScB₂C 458 - ScB₂C₂ 458  $- Sc_2BC_2 458$  $- ScGa_{0.4}Al_{0.6} 458$  $- \sim ScGa_{0.56-0.64}Al_{0.44-0.36}$  458 - ScGa_{0.75-1.23}Al_{1.25-0.77} 458 – ~Sc₄Ga₄Al 458 - Sc₃InB_{1-x} 458 - Sc₃InC_x 458  $-Sc_3PbB_{1-x}$  458 - Sc₃PbC_x 458 - Sc₃SnB_{1-x} 458 - Sc₃SnC_x 458  $- Sc_3 TlB_{1-x} 458$ - Sc₃TlC_x 458 Sc-X-X' ternary systems 456-459 Sc-X'-X (X = B, C) 480 Sc-X compounds 367, 373, 378 - ScAl 367 - ScAl₂ 367 - ScAl₃ 367  $- Sc_2A1 - 367$ – ScAs 378 - Sc₅As₃ 378 - Sc₇As₃ 378  $- Sc_3As_2$  (I) 378 - Sc₃As₂ (II) 378  $- Sc_3As_2(III) - 378$ - ScB₂ 367 - ScB₁₂ 367 - ScBi 378 - ScC_{1-x} 373  $- Sc_3C_4 - 373$  $- Sc_{15}C_{19} - 373$  $- Sc_4C_3(\alpha) - 373$  $- Sc_4C_3(\beta) - 373$ - ScGa 367 - ScGa₂ 367 - ScGa₃ 367 - Sc₂Ga 367  $- Sc_3Ga_2 - 367$ - Sc₃Ga₅ 367

- Sc₅Ga₃ 367

- Sc₅Ga₄ 367 – ScGe 373 - ScGe₂ 373 - Sc₅Ge₃ 373 - Sc₅Ge₄ 373 - Sc₁₁Ge₁₀ 373 - ScIn_{1-x} 368 - ScIn 368 - ScIn₂ 367 - ScIn₃ 367 - Sc₂In 368 - Sc₃In 368 – ScP 378  $- Sc_{3}P - 378$  $- Sc_7P_3 - 378$  $- Sc_3P_2$  (I) 378  $-Sc_3P_2$  (II) 378 - Sc₅Pb₃ 374 - Sc₆Pb₅ 374 – ScPo 378 – ScSb 378  $- Sc_2Sb 378$  $-Sc_5Sb_3 - 378$ - ScSe 378  $-Sc_2Se_3 - 378$ – ScSi 373 - Sc₅Si₃ 373  $- \text{ScSi}_{2-x}(\alpha) = 373$  $- \text{ScSi}_{2-x}(\beta) = 373$ - ScSn 373 - ScSn₂ 373  $-Sc_5Sn_3 = 374$  $- Sc_6 Sn_5 - 373$ - ScTe 378  $-Sc_2Te_3 = 378$ - ScT1 368 - ~ScTl₂ 368 - Sc₂T1 368 - ~Sc₃Tl 368 - Sc₃Tl₅ 368  $- Sc_5Tl_4 - 368$ - Sc₅Tl_{3-3.85} 368 Sc-X (X = 3B element) systems Sc-X (X = 4B element) systems Sc-X (X = P, As, Sb, Bi) – compounds 377 Sc-X (X = P, As, Sb, Bi) systems 376 Sc-X (X = Se, Te, Po) systems 377– compounds 377

365

371

Sc-Y 347

Sc-Y (cont'd) - phase diagram 347 Sc-Y-Fe 460 - isothermal section 460, 461 Sc-Y-Ga 396 isothermal section 396 - ternary compound 396 Sc-Y-Gd 460 Sc-Y-Ge 196, 437 - isothermal section 196, 437 - ternary compounds 196, 437 Sc-Y-Ge-Si 467 Sc-Y-Si 416 isothermal section 416 Sc-Y-Ti-Co 468 Sc-Y(Lu)-Ir-Si 466 Sc-Y(Nd, Dy, Er, Lu)-Fe-B 465 Sc-Yb 349 phase diagram 349 Sc-Yb-Ge 442 - isothermal section 442, 443 - ternary compounds 444 Sc--Zn 363 - compounds 363 phase diagram 363, 364 Sc-Zr 351 - phase diagram 351 Sc--Zr--Al - isothermal section 390 Sc-Zr-Ga 400 - isothermal section 400, 401 - ternary compound 400 Sc-Zr-Si 425 - isothermal section 425 ScAg₄ 361 ScA1 366 ScAl₂ 497 - dilution of lanthanides 496 - lanthanides diluted 496 Sc₃As₂ 377 - polymorphic modifications, 377 ScAuGe 495 - density of states 495 ScB₂ 365 ScB₁₂ 365  $Sc_3C_4 = 372$ Sc₄C₃ 372 - polymorphic modifications 372 Sc₁₅C₁₉ 372 ScCd 364

ScCd₂ 364 ScCd₇ 364 ScCo 355 ScCo₂ 355, 505 - dc susceptibility 505 Sc₂Co 355 Sc3Co 355 ScCoB₄ 384 ScCo₄B₄ 384 ScCrB₄ 381 ScCu 361 ScCu₂ 361 ScCu₄ 361 ScCuZn, polymorphic modifications 464  $Sc_{5-r}Dy_{r}Ir_{4}Si_{10}$  466 magnetic ordering 467 - solid solution 466 superconductivity 467 ScFe_{1.74} 354 ScFe₂ 354, 503, 505 band-structure calculations 503 - hydrogenised 504 - magnetic properties 503 - magnetization 505 polymorphic modifications 354 Sc₂₉Fe₆ 354 Sc(Fe_{0.75}Si_{0.25})₂ 506 - Arrott plot 506 low-temperature magnetization 506 Sc₂Fe₃Si₅ 511 - specific heat 511 ScGe 375 ScGe₂ 375 Sc5Ge3 375 Sc₅Ge₄ 375 Sc11 Ge10 375 ScHg 364 ScHg₃ 364  $ScIn_{1-x}$  370 ScIn 370 ScIn₂ 370 ScIn₃ 370 Sc₂In 370 Sc₃In 370, 502 - electrical resistivity 502 - ferromagnetic order 501 - specific heat 503 - spin fluctuations 502 ScIr₃ 359 Sc₂Ir 359

570

 $Sc_{11}Ir_4 = 359$  $Sc_5Ir_4Si_{10}$ -Lu₅Ir₄Si₁₀ 466 solid solutions 466 ScLiGe - ternary compound 437  $Sc(M_{0.75}Si_{0.25})_2$  (M = Fe, Co, Ni) 506, 507 - resistivity 506, 507  $Sc(M_{1-x}Si_{x})_{2}$  (M = Fe, Co, Ni) 505 - physical properties 506 - structure 505  $Sc_{1-x}M_x$  (M = Co, Rh, Ir, Pd, Pt) 509 - superconductivity 509  $ScM_2$  (M = Ni, Co, Fe) 504 - electrical resistivity 504, 505 - magnetic susceptibility 504  $Sc_5M_4Si_{10}$  (M = Co, Rh, Ir) 510 - superconductivity 510 ScMg 346 ScMn₂ 353 ScMnB₄ 382 ScNi 356 ScNi₂ 356, 505 - dc susceptibility 505 ScNi₅ 356 - polymorphism 356 Sc₂Ni 356 Sc₂Ni₇ 356 ScNi₂B₂C 513 - superconductivity 513 ScOs₂ 359 ScP 377 Sc₃P₂ 377 - polymorphic modifications 377 Sc₅Pb₃ 376 ScPd₃ 357 Sc₂Pd 357 ScPt 361 ScPt₃ 361 Sc₂Pu₃ 351 Sc₂ReB₆ 382 ScRh 357 ScRh₃ 357 Sc₂Rh 357 Sc₃Rh 357 Sc57Rh13 357 ScRu 357 ScRu₂ 357 Sc11Ru4 357 Sc57Ru13 357 ScSi 372

ScSi15 372 - polymorphism 372 Sc₃Si₅ 372 Sc₅Si₃ 372  $ScSn_2$ 376  $Sc_5Sn_3 = 376$  $Sc_6Sn_5$  376 ScTc₂ 353 Sc5Tc24 353 ScTe 378 Sc₂Te₃ 377  $(Sc_{1-x}Ti_{x})Fe_{2} = 507$  magnetic properties 507 ScTl₂ 370 Sc₃Tl 370 Sc5Tl3-3.85 370 Sc₃Zn₁₇ 363 Sc13Zn58 363 scandium alloys 339-520 – binary 343–379 - physical properties of 492-513 quaternary and higher-order 464–468 - ternary 379-464 scandium intermetallics 339-520 magnetic 501–509 - non-magnetic 494-501 - non-superconducting 494-501 - physical properties 492-513 - relations 482-492 - ScMX compounds 478 - ScM₂X₂ compounds 478 - structure types 482, 514-520 - superconducting 509-513 solid solutions 479 - addition 480 - continuous 480, 481  $- (Lu_{1-x}Sc_{x})_{5}Ir_{4}Si_{10}$  481  $-Sc_{r}Er_{5-r}Si_{3}$  480 - substitution 479, 481 structure fragments 486, 488, 489, 492 - connections 486, 488, 492 - dimensions symmetry 486 - distortion 486 structure types 227-327, 471, 472, 483, 487, 489, 490, 493, 513-520 - AlB₂ 287, 514 - AlCr₂C 267 – Al₂Cu 518 - AlLiSi 516 – Al₂MgO₄ 516

structure types (cont'd)  $-\alpha$ -GdSi₂ 298  $-\alpha Mn = 517$  $-\alpha$ -ThSi₂ 298  $-\alpha ThSi_2$  516 - α-YbAuGe 295 – AuCu 517 - AuCu₃ 514 - Ba2Cd3Bi4 258 - BaNiSn₃ 258 - β-YbAuGe 296  $-\beta Yb_5Sb_3$  516 - CaAl₂Si₂ 254 - CaBe₂Ge₂ 253 - CaCu₅ 247, 516 - CaCuGe 295 - CaIn₂ 288, 514 - CaLiSi₂ 273 - CaTiO₃ 484, 514 - Ce₂Al₂Co₁₅ 236 - CeCo₃B₂ 517 - CeCo₄B₄ 518 - Ce₂Cu₃Ge₃ 268 - Ce₂CuGe₆ 260 - Ce₂(Ga, Ge)₇ 262 - CeGa₂Al₂ 252, 515 - Ce₂Li₂Ge₃ 281 - Ce₂₆Li₅Ge_{23 - v} 318 - Ce₂MnGe₅ 276 - Ce₂Ni₇ 519 - CeNiSi₂ 269 - CeNi_{8.5}Si_{4.5} 230 - Ce₅NiGe₂ 324 - Ce₃Pd₂₀Ge₆ 235 - Ce₇Pd₄Ge₂ 319 - Ce₂Pt₇Ge₄ 244 - Ce₃Pt₄Ge₆ 264 - Ce₃Pt₂₃Ge₁₁ 234  $- \text{CeRh}_{1-x}\text{Ge}_{2+x} = 274$ - CeScSi 287 - Ce₂Sc₃Si₄ 260, 484, 514  $- CeSi_{1-y}Ge_{1-x} - 298$ - Co₂Si 517 - CrB 313, 514 - Cr₅B₃ 325  $-Cr_{3}C_{2}$  516 - Cr₂₃C₆ 331 - CsCl 514 - Cu₂Sb 517

- DyA1 518

- DyAlGe 293 - ErAgSe₂ 518 - ErCo₃Ge₂ 250 - ErCuS₂ 517  $- Er_{26}Ge_{23 - x} = 331$ - ErIr₃B₂ 517 - ErNi₃Ge₂ 248 - EuAuGe 294 - EuMg₃Ge₃ 241 - EuNiGe 292 - Eu₂Pt₇AlP₃ 519 – FeB 313 - Fe₃C 518 - Fe2CaO4 519 - γCuTi 517 - Gd₁₄Ag₅₁ 519 - Gd₁₃Cd₅₈ 520  $- Gd_3Cu_4Ge_4 \quad 279$ - Gd₆Cu₈Ge₈ 515 - GdFe₆Ge₆ 233 - Gd₃Ga₂ 520 - GdMn₆Ge₆ 232 - Gd₃NiSi₂ 314 - Gd₅Si₂Ge₂ 321 - HfFe₆Ge₆ 514 - HfFe₂Si₂ 518  $- Hf_2Ni_{6.5}Ga_{4.5} - 520$ - Hf₃Ni₂Si₃ 304, 515 - HoCoGa₅ 515 - Ho2CoGa8 516 - HoFe₆Sn₆ 234  $- Ho_{11}Ge_{10} - 514$ - Ho₄Ir₁₃Ge₉ 246  $- Ho_{26}Pd_4(Pd, Ge)_{19}$ 317 - KHg₂ 289, 515 - La₂AlGe₆ 263  $-La_3Co_2Sn_7 - 275$ - La₄Ga₄Ge₇ 279  $- La_3In_4Ge = 304$ - La₃InGe 323 – LaIrSi 292 - La3Ni2Ga2 311 - La11Ni4Ge6 316 - La₂NiGe 313 - La₈NiGe₅ 322 - LaPt₂Ge₂ 254 - LaPt_{1.42}Pd_{0.58}Ge₂ 326 – LaPtSi 291 - LaTmIr₂Ge₄ 327

– LiGaGe 289

 $-\ Lu_2Co_3Si_5 \quad 256$ - LuMnGe₂ 271 - LuNiGe 296 - LuRuB₂ 518  $-LuRu_4B_4$  520 - MgAgAs 514 - MgCu₂ 285, 514 - MgCuAl₂ 518 - Mg₆Cu₁₆Si₇ 484, 514 – MgCu₄Sn 515 - MgFe₆Ge₆ 231 – MgNi₂ 516  $-Mg_{44}Rh_{7}$  517 – MgZn₂ 285, 514  $-Mg_2Zn_{11}$  519 - MnCu₂Al 514 - Mn₅Si₃ 514 - MoB 518 - Mo₂FeB₂ 308, 484, 514 – MoNi₄ 516 – MoSi₂ 515 - NaZn₁₃ 230, 520 - Nb₂Cr₄Si₅ 251, 517 - Nb₅Cu₄Si₄ 306 - Nd₆Co₅Ge₄ 306 - Nd2Cr9Ge8 236 - Nd₆Fe₁₃Si 283 - NdPtSb 289  $- Nd_4Rh_4Ge_3 = 302$ - NiAs 516  $-Ni_2In$  515 - Ni₃Sn 515 - PbFCl 286 - Pr₂LiGe₆ 261  $- Pu_3Pd_5 \quad 519$ - relations 483, 487, 489, 490, 493  $- Ru_3Be_{17} - 516$  $- Sb_2S_3 - 516$ - ScAl₃C₃ 518 - Sc₁₁Al₂Ge₈ 315, 520 - Sc₇As₃ 520 - ScAuSi 517  $-ScB_2C_2$  518 - Sc₂BC₂ 517  $- Sc_3C_4 - 519$ - ScCd₇ 519 - ScCeSi 514 - Sc₃Co 519 - ScCoC₂ 515 - ScCo_{1.2}Ga_{1.8} 517

 $- Sc_5Co_{19}P_{12} - 519$ - Sc₅Co₄Si₁₀ 277, 516 - Sc₆Co₃₀Si₁₉ 519  $- Sc_3CoC_4 - 515$ - Sc₂CoSi₂ 307, 515 - ScCrC₂ ( $\alpha$ ) 518 - ScCrC₂ ( $\beta$ ) 517  $- Sc_7 Cr_{4+x} Si_{10-x}$  300, 515  $-Sc_2CrC_3$  518  $- Sc_{29}Fe_6 520$ - ScFe₆Ga₆ 518  $- \ ScFe_6Ge_5 - 520$ - ScFeSi₂ 520  $-Sc_{1,2}Fe_4Si_{9,8}$  518 - Sc₂Fe₃Si₅ 519  $- Sc_{11}Ir_4 - 516$ - Sc₃Mn₂Ga₆ 517 - Sc_{8.5}Mn_{1.2}Ga 517  $- Sc_4 Ni_{29}B_{10} 520$  $- Sc_5Ni_{1-x}Ga_{1-x} - 516$ - ScNi₆Ge₆ 233, 519 - Sc₃Ni₁₁Ge₄ 248 - Sc₉Ni₅Ge₈ 312, 519 - Sc_{12.3}Ni_{40.7}Ge₃₁ 520 - ScNiSi₃ 518 - ScNi₂Si₃ 518  $- Sc_3Ni_2Si_4 519$ - Sc₃Ni₁₁Si₄ 247, 517 - Sc₆Ni₁₈Si₁₁ 251, 517 - Sc₃NiSi₃ 519  $- Sc_5 Re_2 C_7 = 519$  $- Sc_2 Re_3 Si_4 515$ - Sc₃Re₂Si₄ 520  $- Sc_5 Re_8 Si_{12} - 520$  $- Sc_{57}Rh_{13} - 515$ - ScRhSi₂ 518 - ScRh₃Si₇ 517 - Sc₂Ru₅B₄ 516  $-Sc_2S_3$  520 - ScSn₂ 518 - scandium intermetallics 478, 513-520 - Sm₄Co_{1-x}Ge₇ 300 - Sm₅Ge₄ 320, 514 - SmNiGe₃ 257 - SmNi₃Ge₃ 240 - Tb₃Co₂Ge₄ 299 – TbCu₇ 517 - Tb₁₁₇Fe₅₂Ge₁₁₂ 309

- TbFeSi₂ 326
- TbFe₆Sn₆ 234

structure types (cont'd) - Te₂Ag₃T1 298 - Th₇Fe₃ 518  $- ThMn_{12} - 514$  $- Th_3P_4 = 519$ - Th₂Zn₁₇ 236, 519 – TiAl₃ 268 - TiFeSi 516 - Ti₅Ga₄ 518 - Ti₆Ge₅ 515 – TiNi₃ 516 – Ti₂Ni 515 - TiNiSi 290, 484, 514  $- Ti_7 S_{12} - 518$ - Tm₉Fe₁₀Ge₁₀ 283 - Tm₃Ga₅ 519  $- Tm_3(Ga_{0.5}Ge_{0.5})_5 = 305$  $- Tm_2Ga_0 Ge_{45} 282$  $- \text{TmLi}_{1-x}\text{Ge}_2 = 273$ - Tm₄LiGe₄ 311 - UB₁₂ 519  $- U_2 Co_3 Si_5 = 255, 519$ - U₃Ni₄Si₄ 280 - U4Re7Si6 266, 514 - U₃Sb₃Cu₂ 305  $-V_{3}As_{2}$  518  $-W_2Cr_{21}C_6$  517 - W₅Si₃ 519 – YAlGe 294 - YB₂C 519 - Y₂Co₃Ga₉ 517 - YCo₆Ge₆ 231, 517  $- Y_3 Co_4 Ge_{13} = 243$ - YCo₅P₃ 239, 516, 519 – YCrB₄ 515 - Y2HfS5 324 - YIrGe₂ 270 - YNi₅Si₃ 238 - Y₃NiAl₃Ge₂ 327 - YPd₂Si 267 - Y3Pt4Ge6 265  $- Y_2 ReB_6 = 519$ - Y2Rh3Ge 285 - Yb₇Al₅Ge₈ 301 - Yb₈LiGe₁₃ 303 - YbMo₂Al₄ 516

 $- Yb_3Rh_4Sn_{13} = 242$ 

- ZrAl₃ 268, 518 – ZrBeSi 297 - Zr₄Co₄Ge₇ 278, 515 - ZrCrSi₂ 272, 514 - ZrFe6Ge4 516  $- Zr_2Fe_{12}P_7 - 515$  $- \ ZrFe_4Si_2 \quad 239, \ 515$ - ZrGa₂ 518 - ZrIr₃B₄ 518 - ZrNiAl 291, 484, 514 – ZrOS 292 - ZrSi₂ 285, 515 ternary compounds 8-216, 225-335, 379-464, 473, 476, 477, 484, 485 - binary prototypes 484 - characteristic cross sections 486 - compositions 476, 477 - Mo₂FeB₂ 485 - most common compositions 478 - Sc-M-B(Al, Ga) 474 - Sc-M-C(Si, Ge) 475 - Sc-M-X 479 - Sc-X-B(Al, Ga) 474 - Sc-X-C(Si, Ge) 475 - Sc₂AlSi₂ 485 - ScCe₂Si₂ 485 - Sc₂Ni₂Sn 485 - stoichiometries 473, 477 - structure types 473, 484 - superstructures 483, 485, 491 ternary scandium phase diagrams, regularities 473-479 ternary systems 379 characteristic cross sections 477 tetrahedra 491 YA1, 497 - dilution of lanthanides 496 - lanthanides diluted 496 YAuGe 495 - density of states 495 Y₂Fe₃Si₅ 511, 512 - specific heat 511, 512  $(Y_{1-x}Sc_x)Mn_2$  508, 509

- lattice parameter 508, 509

- magnetic properties 508